TEXAS INSTRUMENTS

Low-Voltage Logic

ALB, ALVC, LV, LVC, LVT, LVTZ, and GTL Families

Data Book

Low-Voltage Logic
ALB, ALVC, LV, LVC, LVT, LVTZ, and GTL Families

1996

1996

Advanced System Logic Products

Low-Voltage Logic Data Book

ALB, ALVC, LV, LVC, LVT, LVTZ, and GTL Families

IMPORTANT NOTICE

Texas Instruments (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Certain applications using semiconductor products may involve potential risks of death, personal injury, or severe property or environmental damage ("Critical Applications").

TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS.

Inclusion of TI products in such applications is understood to be fully at the risk of the customer. Use of TI products in such applications requires the written approval of an appropriate TI officer. Questions concerning potential risk applications should be directed to TI through a local SC sales office.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

Printed in U.S.A. by
Custom Printing Company
Owensville, Missouri

INTRODUCTION

The 3.3-V era has arrived! The combination of continuous advancement in semiconductor wafer fabrication technologies and the proliferation of battery-powered computing devices has changed system-design methodologies of the past, and indeed our entire industry. This new era brings a new set of possibilities for computing and hand-held instruments: products that run faster, consume less power, and use fewer total system components than ever before; products that are smaller and lighter, yet maintain interface compatibility with existing industry standard bus architectures; and products that will bring on the next era in the computer industry.

Welcome to the 1996 Texas Instruments Low-Voltage Logic Data Book. A single family of 3.3-V logic products could not possibly cover the diverse needs of all of the end-equipment segments. Products ranging from hand-held point-of-sale terminals, notebook and laptop personal computers, low-power environmentally conscious desktop computers and peripherals, and high-performance RISC and CISC workstation platforms share the need for low-voltage technology, but have radically different price, performance, and feature requirements for the logic they employ. As a response to these diverse needs, Texas Instruments has developed four independent logic families:

Advanced Low-Voltage CMOS (ALVC)
Low-Voltage HCMOS (LV)
Low-Voltage CMOS (LVC)
Low-Voltage Technology (LVT)

These products span four generations of CMOS and BiCMOS process technologies and years of fine-pitch packaging and innovative circuit developments to deliver a set of products for each of these end-equipment segments. In addition to popular octal and Widebus™ bus-interface circuits, two of the families also include SSI and MSI logic functions to help streamline design and facilitate time to market.

Voltage translators are provided to bridge the gap between the 5-V and 3.3-V environments. In addition to the LVT family, the LVC family also is 5 V tolerant. This creates even more flexibility in the mixed-signal environments. Also new this year is the addition of the 2.5-V specification to the ALVC family. Designers of high-speed backplane applications will have great interest in the GTL family of transceivers.

Some of the information in this data book is in product-preview or advance-information form. For more information on these products including availability dates, pricing, and final timing specifications, please contact your local Texas Instruments field sales representative, authorized distributor, or call our Advanced System Logic hotline at (903) 868-5202.

We are sure you will agree that Texas Instruments has developed the most complete line of low-voltage logic products in the industry. We hope that these products will meet your system and design needs. Texas Instruments has been and will continue to be the logic leader for bus-interface products.

PRODUCT STAGE STATEMENTS

Product stage statements are used on Texas Instruments data sheets to indicate the development stage(s) of the product(s) specified in the data sheets.

If all products specified in a data sheet are at the same development stage, the appropriate statement from the following list is placed in the lower left corner of the first page of the data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

ADVANCE INFORMATION concerns new products in the sampling or preproduction phase of development. Characteristic data and other specifications are subject to change without notice.

PRODUCT PREVIEW information concerns products in the formative or design phase of development. Characteristic data and other specifications are design goals. Texas Instruments reserves the right to change or discontinue these products without notice.

If not all products specified in a data sheet are at the PRODUCTION DATA stage, then the first statement below is placed in the lower left corner of the first page of the data sheet. Subsequent pages of the data sheet containing PRODUCT PREVIEW information or ADVANCE INFORMATION are then marked in the lower left-hand corner with the appropriate statement given below:

UNLESS OTHERWISE NOTED this document contains PRODUCTION DATA information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

ADVANCE INFORMATION concerns new products in the sampling or preproduction phase of development. Characteristic data and other specifications are subject to change without notice.

PRODUCT PREVIEW information concerns products in the formative or design phase of development. Characteristic data and other specifications are design goals. Texas Instruments reserves the right to change or discontinue these products without notice.

Contents

ALPHANUMERIC INDEX

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

INTRODUCTION

These symbols, terms, and definitions are in accordance with those currently agreed upon by the JEDEC Council of the Electronic Industries Association (EIA) for use in the USA and by the International Electrotechnical Commission (IEC) for international use.

operating conditions and characteristics (in sequence by letter symbols)

C_i — Input capacitance

The internal capacitance at an input of the device

C_{io} — Input/output capacitance

Input-to-output internal capacitance; transcapacitance

C_o — Output capacitance

The internal capacitance at an output of the device

C_{pd} — Power dissipation capacitance

Used to determine the no-load dynamic power dissipation per logic function (see individual circuit pages):
$P_D = C_{pd} V_{CC}^2 f + I_{CC} V_{CC}$

f_{max} — Maximum clock frequency

The highest rate at which the clock input of a bistable circuit can be driven through its required sequence while maintaining stable transitions of logic level at the output with input conditions established that should cause changes of output logic level in accordance with the specification

I_{CC} — Supply current

The current into* the V_{CC} supply terminal of an integrated circuit

ΔI_{CC} — Supply current change

The increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}

I_{CEX} — Output high leakage current

The maximum leakage current into the collector of the pulldown output transistor when the output is high and the output forcing condition V_O = 5.5 V

$I_{I(hold)}$ — Input hold current

Input current that holds the input at the previous state when the driving device goes to a high-impedance state

I_{IH} — High-level input current

The current into* an input when a high-level voltage is applied to that input

I_{IL} — Low-level input current

The current into* an input when a low-level voltage is applied to that input

I_{off} — Input/output power-off leakage current

The current into a circuit mode when the device or a portion of the device affecting that circuit node is in the off state

I_{OH} — High-level output current

The current into* an output with input conditions applied that, according to the product specification, will establish a high level at the output

*Current out of a terminal is given as a negative value.

I_{OL} **Low-level output current**

The current into* an output with input conditions applied that, according to the product specification, will establish a low level at the output

$I_{OZPU/PD}$ **Off-state (high-impedance-state) output current (of a 3-state output)**

The current flowing into* an output having 3-state capability with input conditions established that, according to the product specification, will establish the high-impedance state at the output

t_a **Access time**

The time interval between the application of a specified input pulse and the availability of valid signals at an output

t_c **Clock cycle time**

Clock cycle time is $1/f_{max}$

t_{dis} **Disable time (of a 3-state or open-collector output)**

The propagation time between the specified reference points on the input and output voltage waveforms with the output changing from either of the defined active levels (high or low) to a high-impedance (off) state

NOTE: For 3-state outputs, $t_{dis} = t_{PHZ}$ or t_{PLZ}. Open-collector outputs will change only if they are low at the time of disabling, so $t_{dis} = t_{PLH}$.

t_{en} **Enable time (of a 3-state or open-collector output)**

The propagation time between the specified reference points on the input and output voltage waveforms with the output changing from a high-impedance (off) state to either of the defined active levels (high or low)

NOTE: In the case of memories, this is the access time from an enable input (e.g., $\overline{OE}$). For 3-state outputs, $t_{en} = t_{PZH}$ or t_{PZL}. Open-collector outputs will change only if they are responding to data that would cause the output to go low, so $t_{en} = t_{PHL}$.

t_h **Hold time**

The time interval during which a signal is retained at a specified input terminal after an active transition occurs at another specified input terminal

NOTES: 1. The hold time is the actual time interval between two signal events and is determined by the system in which the digital circuit operates. A minimum value is specified that is the shortest interval for which correct operation of the digital circuit is to be expected.

2. The hold time may have a negative value in which case the minimum limit defines the longest interval (between the release of the signal and the active transition) for which correct operation of the digital circuit is to be expected.

t_{pd} **Propagation delay time**

The time between the specified reference points on the input and output voltage waveforms with the output changing from one defined level (high or low) to the other defined level ($t_{pd} = t_{PHL}$ or t_{PLH})

t_{PHL} **Propagation delay time, high-to-low level output**

The time between the specified reference points on the input and output voltage waveforms with the output changing from the defined high level to the defined low level

t_{PHZ} **Disable time (of a 3-state output) from high level**

The time interval between the specified reference points on the input and the output voltage waveforms with the 3-state output changing from the defined high level to the high-impedance (off) state

*Current out of a terminal is given as a negative value.

t_{PLH} **Propagation delay time, low-to-high level output**

The time between the specified reference points on the input and output voltage waveforms with the output changing from the defined low level to the defined high level

t_{PLZ} **Disable time (of a 3-state output) from low level**

The time interval between the specified reference points on the input and the output voltage waveforms with the 3-state output changing from the defined low level to the high-impedance (off) state

t_{PZH} **Enable time (of a 3-state output) to high level**

The time interval between the specified reference points on the input and output voltage waveforms with the 3-state output changing from the high-impedance (off) state to the defined high leve

t_{PZL} **Enable time (of a 3-state output) to low level**

The time interval between the specified reference points on the input and output voltage waveforms with the 3-state output changing from the high-impedance (off) state to the defined low level

$t_{sk(o)}$ **Output Skew**

The difference between any two propagation delay times when a single switching input or multiple inputs switching simultaneously cause multiple outputs to switch, as observed across all switching output. This parameter is used to describe the fanout capability of a clock driver and is of concern when making decisions on clock buffering and distribution networks.

t_{su} **Setup time**

The time interval between the application of a signal at a specified input terminal and a subsequent active transition at another specified input terminal

NOTES: 1. The setup time is the actual time interval between two signal events and is determined by the system in which the digital circuit operates. A minimum value is specified that is the shortest interval for which correct operation of the digital circuit is guaranteed.

2. The setup time may have a negative value, in which case the minimum limit defines the longest interval (between the active transition and the application of the other signal) for which correct operation of the digital circuit is guaranteed.

t_w **Pulse duration (width)**

The time interval between specified reference points on the leading and trailing edges of the pulse waveform

V_{IH} **High-level input voltage**

An input voltage within the more positive (less negative) of the two ranges of values used to represent the binary variables

NOTE: A minimum is specified that is the least-positive value of high-level input voltage for which operation of the logic element within specification limits is to be expected.

V_{IL} **Low-level input voltage**

An input voltage within the less positive (more negative) of the two ranges of values used to represent the binary variables

NOTE: A maximum is specified that is the most-positive value of low-level input voltage for which operation of the logic element within specification limits is to be expected.

V_{OH} **High-level output voltage**

The voltage at an output terminal with input conditions applied that, according to product specification, will establish a high level at the output

V_{OL} Low-level output voltage

The voltage at an output terminal with input conditions applied that, according to product specification, will establish a low level at the output

V_{IT+} Positive-going input threshold level

The voltage level at a transition-operated input that causes operation of the logic element according to specification as the input voltage rises from a level below the negative-going threshold voltage, V_{IT-}

V_{IT-} Negative-going input threshold level

The voltage level at a transition-operated input that causes operation of the logic element according to specification as the input voltage falls from a level above the positive-going threshold voltage, V_{IT+}

The following symbols are used in function tables on TI data sheets:

H	=	high level (steady state)
L	=	low level (steady state)
↑	=	transition from low to high level
↓	=	transition from high to low level
→	=	value/level or resulting value/level is routed to indicated destination
↶	=	value/level is re-entered
X	=	irrelevant (any input, including transitions)
Z	=	off (high-impedance) state of a 3-state output
a . . . h	=	the level of steady-state inputs A through H respectively
Q_0	=	level of Q before the indicated steady-state input conditions were established
$\overline{Q}_0$	=	complement of Q_0 or level of $\overline{Q}$ before the indicated steady-state input conditions were established
Q_n	=	level of Q before the most recent active transition indicated by ↓ or ↑
⎍	=	one high-level pulse
⎴	=	one low-level pulse
Toggle	=	each output changes to the complement of its previous level on each active transition indicated by ↓ or ↑

If, in the input columns, a row contains only the symbols H, L, and/or X, this means the indicated output is valid whenever the input configuration is achieved and regardless of the sequence in which it is achieved. The output persists so long as the input configuration is maintained.

If, in the input columns, a row contains H, L, and/or X together with ↑ and/or ↓, this means the output is valid whenever the input configuration is achieved but the transition(s) must occur following the achievement of the steady-state levels. If the output is shown as a level (H, L, Q_0, or $\overline{Q}_0$), it persists so long as the steady-state input levels and the levels that terminate indicated transitions are maintained. Unless otherwise indicated, input transitions in the opposite direction to those shown have no effect at the output. (If the output is shown as a pulse, ⎍ or ⎴, the pulse follows the indicated input transition and persists for an interval dependent on the circuit.)

EXPLANATION OF FUNCTION TABLES

Among the most complex function tables are those of the shift registers. These embody most of the symbols used in any of the function tables, plus more. Below is the function table of a 4-bit bidirectional universal shift register, e.g., type SN74194.

FUNCTION TABLE

INPUTS										OUTPUTS			
CLEAR	MODE		CLOCK	SERIAL		PARALLEL				Q_A	Q_B	Q_C	Q_D
	S1	S0		LEFT	RIGHT	A	B	C	D				
L	X	X	X	X	X	X	X	X	X	L	L	L	L
H	X	X	L	X	X	X	X	X	X	Q_{A0}	Q_{B0}	Q_{C0}	Q_{D0}
H	H	H	↑	X	X	a	b	c	d	a	b	c	d
H	L	H	↑	X	H	H	H	H	H	H	Q_{An}	Q_{Bn}	Q_{Cn}
H	L	H	↑	X	L	L	L	L	L	L	Q_{An}	Q_{Bn}	Q_{Cn}
H	H	L	↑	H	X	X	X	X	X	Q_{Bn}	Q_{Cn}	Q_{Dn}	H
H	H	L	↑	L	X	X	X	X	X	Q_{Bn}	Q_{Cn}	Q_{Dn}	L
H	L	L	X	X	X	X	X	X	X	Q_{A0}	Q_{B0}	Q_{C0}	Q_{D0}

The first line of the table represents a synchronous clearing of the register and says that if clear is low, all four outputs will be reset low regardless of the other inputs. In the following lines, clear is inactive (high) and so has no effect.

The second line shows that so long as the clock input remains low (while clear is high), no other input has any effect and the outputs maintain the levels they assumed before the steady-state combination of clear high and clock low was established. Since on other lines of the table only the rising transition of the clock is shown to be active, the second line implicitly shows that no further change in the outputs will occur while the clock remains high or on the high-to-low transition of the clock.

The third line of the table represents synchronous parallel loading of the register and says that if S1 and S0 are both high then, without regard to the serial input, the data entered at A will be at output Q_A, data entered at B will be at Q_B, and so forth, following a low-to-high clock transition.

The fourth and fifth lines represent the loading of high- and low-level data, respectively, from the shift-right serial input and the shifting of previously entered data one bit; data previously at Q_A is now at Q_B, the previous levels of Q_B and Q_C are now at Q_C and Q_D, respectively, and the data previously at Q_D is no longer in the register. This entry of serial data and shift takes place on the low-to-high transition of the clock when S1 is low and S0 is high and the levels at inputs A through D have no effect.

The sixth and seventh lines represent the loading of high- and low-level data, respectively, from the shift-left serial input and the shifting of previously entered data one bit; data previously at Q_B is now at Q_A, the previous levels of Q_C and Q_D are now at Q_B and Q_C, respectively, and the data previously at Q_A is no longer in the register. This entry of serial data and shift takes place on the low-to-high transition of the clock when S1 is high and S0 is low and the levels at inputs A through D have no effect.

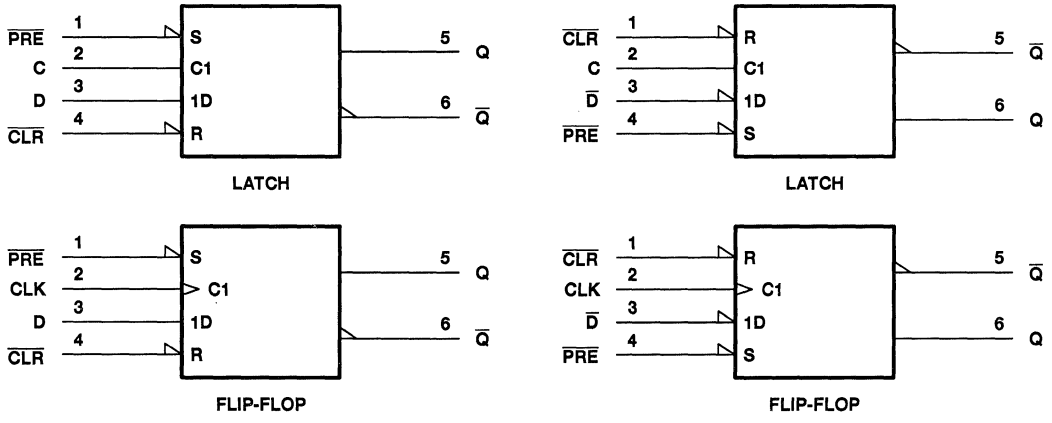
The last line shows that as long as both inputs are low, no other input has any effect and, as in the second line, the outputs maintain the levels they assumed before the steady-state combination of clear high and both mode inputs low was established.

The function table functional tests do not reflect all possible combinations or sequential modes.

It is normal TI practice to name the outputs and other inputs of a D-type flip-flop or latch and to draw its logic symbol based on the assumption of true data (D) inputs. Outputs that produce data in phase with the data inputs are called Q and those producing complementary data are called $\overline{Q}$. An input that causes a Q output to go high or a $\overline{Q}$ output to go low is called preset (PRE). An input that causes a $\overline{Q}$ output to go high or a Q output to go low is called clear (CLR). Bars are used over these pin names (PRE and CLR) if they are active low.

The devices on several data sheets are second-source designs, and the pin name conventions used by the original manufacturers have been retained. That makes it necessary to designate the inputs and outputs of the inverting circuits $\overline{D}$ and Q.

In some applications, it may be advantageous to redesignate the data input from D to $\overline{D}$ or vice versa. In that case, all the other inputs and outputs should be renamed as shown below. Also shown are corresponding changes in the graphical symbols. Arbitrary pin numbers are shown.



The figures show that when Q and $\overline{Q}$ exchange names, the preset and clear pins also exchange names. The polarity indicators (⊳) on $\overline{PRE}$ and $\overline{CLR}$ remain, as these inputs are still active low, but the presence or absence of the polarity indicator changes at D (or $\overline{D}$), Q, and $\overline{Q}$. Pin 5 (Q or $\overline{Q}$) is still in phase with the data input (D or $\overline{D}$); their active levels change together.

In digital system design, consideration must be given to thermal management of components. The small size of the small-outline package makes this even more critical. Figure 1 shows the thermal resistance of these packages for various rates of air flow. Figures 2, 3, 4, and 5 are derating curves for the DB package.

The thermal resistances in Figure 1 can be used to approximate typical and maximum virtual junction temperatures for the LVL family. In general, the junction temperature for any device can be calculated using the following equation.

$$T_J = R_{\theta JA} \times P_T + T_A$$

Where:

T_J = virtual junction temperature
$R_{\theta JA}$ = thermal resistance, junction to free air
P_T = total power dissipation of the device
T_A = free-air temperature

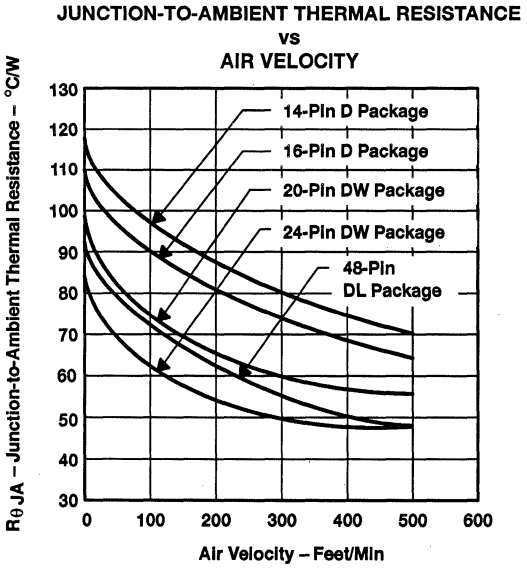


Figure 1

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

DERATING CURVES FOR 210-MIL SHRINK SMALL-OUTLINE PACKAGE (DB)

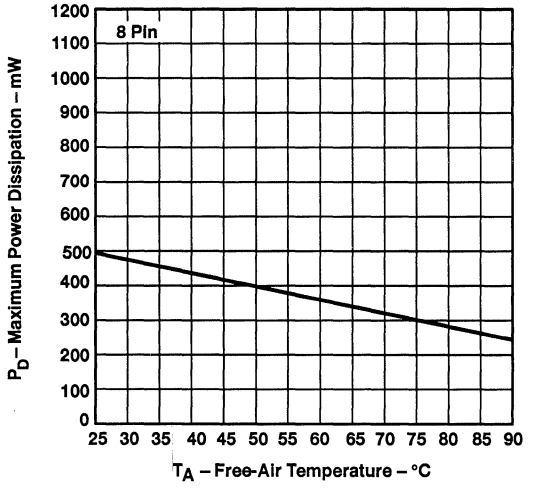


Figure 2

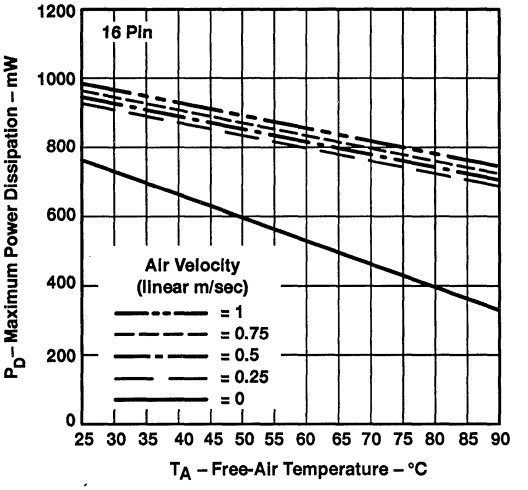


Figure 3

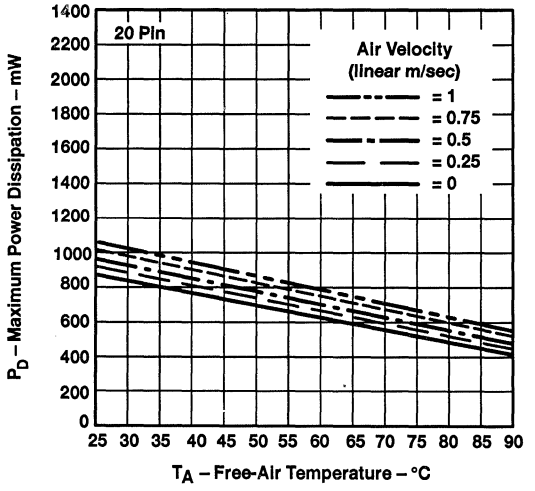


Figure 4

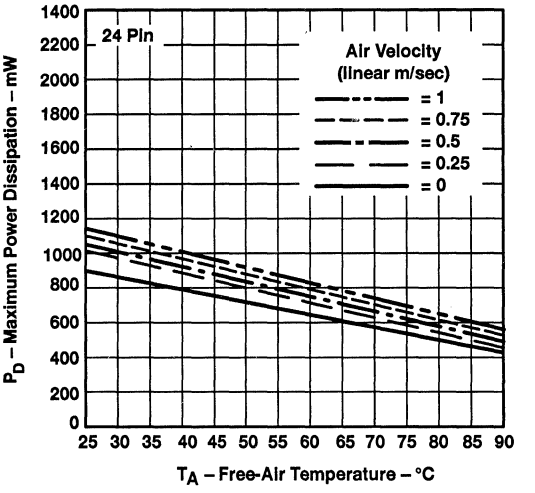


Figure 5

Current Texas Instruments Advanced Logic Publications

Listed below is the current collection of Texas Instruments logic technical documentation. The alphanumeric code is the literature number for each item listed. These documents can be ordered through a TI representative or authorized distributor by referencing the literature number.

Document	*Literature Number*
Advanced BiCMOS Technology Data Book (1994)	SCBD002B
Advanced Bus-Interface SPICE I/O Models Data Book (1995)	SCBD004A
Advanced CMOS Logic Data Book (1993)	SCAD001C
Advanced Logic and Bus-Interface Logic Data Book (1991)	SCYD001
ALS/AS Logic Data Book (1995)	SDAD001C
BCT BiCMOS Bus-Interface Logic Data Book (1994)	SCBD001B
Boundary-Scan Logic, IEEE Std. 1149.1 (JTAG) 5-V and 3.3-V Bus-Interface and Scan-Support Products Data Book (1994)	SCTD002
CBT Bus Switches Crossbar Technology Data Book (1995)	SCDD001
CDC Clock-Distribution Circuits Data Book (1994)	SCAD004
F Logic Data Book (1994)	SDFD001B
High-Performance FIFO Memories Data Book (1996)	SCAD003C
High-Performance FIFO Memories Designer's Handbook (1996)	SCAA012A
High-Speed CMOS Logic Data Book (1989)	SCLD001C
Low-Voltage Logic Data Book (1996)	SCBD003B
TTL Logic Data Book (TTL, LS, S) (1988)	SDLD001A
Semiconductor Group Package Outlines Reference Guide	SSYU001A

In addition to the books listed above, the following documents are available only in Europe.

Document	*Literature Number*
Advanced BiCMOS Technology Data Book (1994)	SCBDE08
CBT Crossbar Technology Data Book (1995)	SCDDE01
CDC Data and Applications Manual (1995)	SCBTE07B
Packaging Data Book (1995)	SCYDE04
ASL SCOPE™ Products Data and Applications Manual (1994)	SCBDE09

GATES

Positive-NAND Gates

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
8 Input		'30	✔	✔	✔	✔	✔	✔								
13 Input		'133	✔				✔									
Dual 4 Input		'20	✔	✔	✔	✔	✔						✔			
Triple 3 Input		'10	✔	✔	✔	✔	✔		✔	✔			✔			✔
Quad 2 Input		'00	✔	✔	✔	✔	✔	✔	✔•	✔	✔	✔	✔	✔	✔	✔
		'37	✔			✔	✔	✔								
	OC	'38	✔		✔	✔	✔	✔								
		'132				✔	✔	✔					✔			
		'1000		✔												
Hex 2 Input		'804	✔	✔												
		'1804		✔												
Quad 2 Input	OC	'03	✔			✔							✔			
Dual 2 Input		'8003	✔													

Positive-AND Gates

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
Quad 2 Input	OC	'09	✔			✔	✔									
		'7001											✔			
Dual 4 Input		'21	✔	✔	✔	✔							✔			
Triple 3 Input		'11	✔	✔	✔	✔	✔		✔	✔			✔			
Quad 2 Input		'08	✔	✔	✔	✔	✔		✔•	✔•	✔	✔	✔	✔	✔	✔
		'1008		✔												
Hex 2 Input		'808		✔												
		'1808		✔												

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Positive-OR/NOR Gates

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
Quad 2 Input		'32	✔	✔	✔	✔	✔	✔	✔•	✔•	✔	✔	✔	✔	✔	✔
		'1032		✔												
Hex 2 Input		'832	✔	✔												
		'1832		✔												
Dual 5 Input		'260			✔		✔									
Triple 3 Input		'27	✔	✔	✔	✔							✔			
Quad 2 Input		'02	✔	✔	✔	✔	✔						✔	✔	✔	✔
	OC	'33				✔										
		'7002											✔			
Hex 2 Input		'805	✔	✔												
		'1805		✔												

OR/NOR Gates

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
Quad 2-Input Exclusive-OR Gates With Totem-Pole Outputs		'86	✔		✔	✔			✔•	✔	✔	✔	✔			✔
Quad 2-Input Exclusive-NOR Gates	OD	'266				✔							✔			

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

INVERTING/NONINVERTING BUFFERS

Hex Inverters/Noninverters

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY													
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	HC	HCT	LV	LVC
Hex Inverters		'04	✔	✔	✔	✔	✔	✔	✔•	✔•	✔	✔	✔	✔	✔	✔
		'U04									✔		✔		✔	✔
	OC	'05	✔			✔	✔	✔					✔			
		'06						✔								
		'14				✔		✔	✔	✔	✔	✔	✔		✔	✔
		'1004	✔	✔												
		'1005	✔													
Hex Noninverters	OC	'35	✔													
		'1034	✔	✔												
	OC	'1035	✔													

BUFFERS/DRIVERS AND BUS TRANSCEIVERS

Buffers/Drivers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																	
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
2-Bit Buffers	3S	'306		✔																	
Quad Buffers/Drivers	3S	'125	✔	✔	✔			✔	✔					+	+		✔	✔	✔	✔	
		'126	✔	✔				✔	✔					+	+		✔				
Hex Buffers	OC	'07									✔										
Noninverting Hex Buffers/Drivers	3S	'365							✔								✔				
	3S	'367							✔		✔						✔				
Inverting Hex Buffers/Drivers	3S	'368							✔		✔						✔				

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Buffers/Drivers (Continued)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																		
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Noninverting Octal Buffers/Drivers	3S	'241	✔	✔	✔	✔	✔	✔	✔	✔		✔	✔				✔				
		'244	✔	✔	✔	✔	✔	✔	✔	✔		✔•	✔•	✔	✔		✔	✔	✔	✔	+LVCH
		'1240				✔															
		'1244				✔															
		'25244		✔																	
		'541	✔	✔		✔		✔	✔					✔	✔		✔	✔		✔	
	OC	'757					✔														
		'760		✔		✔	✔														
Inverting Octal Buffers/Drivers	3S	'240	✔	✔	✔	✔	✔	✔	✔	✔		✔•	✔•	✔	✔		✔	✔	✔	✔	
		'540	✔	✔		✔			✔					✔	✔		✔	✔		✔	
	OC	'756		✔			✔														
Inverting and Noninverting Octal Buffers/Drivers	3S	'230					✔														
Noninverting 10-Bit Buffers/Drivers	3S	'827	✔																	✔	
		'29827		✔		✔															
Inverting 10-Bit Buffers/Drivers	3S	'828																		✔	
		'29828		✔		✔															
Noninverting 16-Bit Buffers/Drivers	3S	'16241	✔										✔			✔				✔	
		'16244	✔		✔							✔	✔			✔				✔	
		'16541	✔										✔							✔	
Inverting 16-Bit Buffers/Drivers	3S	'16240	✔									✔	✔			✔				✔	
		'16540	✔										✔							✔	
Noninverting 18-Bit Buffers/Drivers	3S	'16825	✔										✔			✔					
		'16835			✔											✔					
Noninverting 20-Bit Buffers/Drivers	3S	'16827	✔										✔			✔					

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

Universal Bus Transceivers (UBT™)/Universal Bus Exchangers (UBE™)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY						
			ABT	BCT	LVT	LV	LVC	ALVC	OTHER
Noninverting 9-Bit 4-Port UBE™	3S	'16409						✔	
Noninverting 17-Bit UBT™ With Buffered Clock Outputs and Output Edge Control (OEC™)	OD	'16616							✔GTL
Noninverting 18-Bit UBT™	3S	'16500	✔		✔			✔	
		'16501	✔		✔			✔	
		'16600	✔					✔	
		'16601	✔					✔	
Noninverting 18-Bit UBT™ With Output Edge Control (OEC™)	OD	'16612							✔GTL
Noninverting 18-Bit UBT™	OD	'16622							+GTL
Noninverting 36-Bit UBT™	3S	'32501	✔						
Noninverting 16-Bit Tri-Port UBE™	3S	'32316	✔						
Noninverting 18-Bit Tri-Port UBE™	3S	'32318	✔						
18-Bit UBT™ With Series Resistors on B Port	3S	'162500	✔						
		'162501	✔						
		'162601	✔					✔	
Noninverting 18-Bit UBT™ With Parity Generators /Checkers	3S	'16901						✔	
SCOPE™ 18-Bit UBT™	3S	'18502	✔		✔				
SCOPE™ 20-Bit UBT™	3S	'18504	✔		✔				

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

BUFFERS/DRIVERS AND BUS TRANSCEIVERS

Bus Transceivers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																	
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Inverting Quad Transceivers	OC	'758				✔															
Noninverting Quad Transceivers	3S	'243				✔		✔	✔												
Noninverting Octal Transceivers	3S	'245	✔	✔	✔	✔	✔	✔	✔			✔•	✔•	✔	✔		✔	✔	✔	✔	+LVCH
		'1245				✔															
		'25245	✔	✔																	
		'645				✔	✔		✔								✔	✔			
		'1645				✔															
	OC	'621				✔															
		'641				✔	✔		✔												
	OC/3S	'639				✔	✔														
Inverting Octal Transceivers	3S	'620	✔			✔															
		'623	✔	✔		✔		✔	✔								✔	✔			
		'640	✔	✔		✔	✔		✔								✔				
		'1640				✔															
	OC	'642				✔			✔												
	OC/3S	'638				✔	✔														
Noninverting 9-Bit Transceivers	3S	'863	✔																	✔	
		'29863		✔		✔															
Noninverting 10-Bit Transceivers	3S	'861	✔																	✔	
Noninverting 16-Bit Transceivers	3S	'16245	✔		✔							✔	✔			✔				✔	✔ABTE
		'16623	✔										✔								
Noninverting 16-Bit Transceivers, 3.3-V-to-5-V Level Shifter	3S	'164245														✔					
Inverting 16-Bit Transceivers	3S	'16640	✔									✔	✔								
		'16620										✔	✔								
Noninverting 18-Bit Transceivers	3S	'16863	✔										✔			✔					

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Bus Transceivers (Continued)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																	
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Inverting 18-Bit Transceivers	3S	'16864											✔								
Noninverting 20-Bit Transceivers	3S	'16861											✔								
Noninverting Octal Registered Transceivers	3S	'543	✔	✔	✔			✔												✔	
		'646	✔	✔	✔	✔	✔		✔								✔	✔		✔	
		'652	✔	✔	✔	✔	✔		✔			•	•				✔	✔		✔	
		'2952	✔		✔															✔	
	OC/3S	'653				✔															
		'654				✔															
Inverting Octal Registered Transceivers	3S	'648				✔	✔		✔												
		'651	✔			✔	✔														
		'2953		✔																	
Noninverting 16-Bit Registered Transceivers	3S	'16470	✔										✔								
		'16543	✔		✔							✔	✔			✔				✔	
		'16646	✔		✔							✔	✔			✔				✔	
		'16652	✔		✔							✔	✔							✔	
		'16952	✔		✔								✔							+	
Inverting 16-Bit Registered Transceivers	3S	'16544											✔								
		'16648											✔								
		'16651											✔								
Noninverting 18-Bit Registered Transceivers	3S	'16474											✔								
		'16500	✔		✔											✔					
		'16501	✔		✔											✔					
		'16600	✔													✔					
		'16601	✔													✔					
Noninverting 36-Bit Transceivers	3S	'32245	✔																		
Noninverting 36-Bit Registered Transceivers	3S	'32501	✔																		
		'32543	✔																		

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Bus Transceivers (Continued)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																	
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
8-/9-Bit Bus Transceivers With Parity Checkers/ Generators	3S	'657	✔																		
		'833	✔																		
		'853	✔																		
	3S/OC	'29833				✔															
		'29834		✔																	
		'29854		✔																	
Dual 8-/9-Bit Bus Transceivers With Parity Checkers/ Generators	3S	'16833	✔										✔								
		'16657	✔										✔								
		'16853	✔																		
Noninverting 16-Bit Tri-Port Registered Bus Exchangers	3S	'32316	✔																		
Noninverting 18-Bit Tri-Port Registered Bus Exchangers	3S	'32318	✔																		
7-Bit TTL/BTL Transceivers	OC	'2041																			✔FB
8-Bit TTL/BTL Transceivers	OC	'2040																			✔FB
8-Bit TTL/BTL Registered Transceivers	OC	'2033																			✔FB
9-Bit TTL/BTL Competition Transceivers	OC	'2032																			+FB
9-Bit TTL/BTL Address/ Data Transceivers	OC	'2031																			✔FB
17-Bit TTL/BTL Universal Storage Transceivers	OC	'1651																			✔FB
18-Bit TTL/BTL Universal Storage Transceivers	OC	'1650																			✔FB

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

MOS Memory Drivers/Transceivers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY											
			ABT	BCT	LVT	ALS	AS	F	AC	ACT	ALVC	LV	LVC	OTHER
Octal Buffers/Drivers With Series Resistors on Output	3S	'2240	✔	✔		✔								
		'2241	✔											
		'2244	✔	✔				✔						
		'2541				✔								
Octal Transceivers With Series Resistors on B Port	3S	'2245	✔	✔				✔						
10-Bit Buffers/Drivers With Series Resistors	3S	'2827		✔										
		'2828		✔										
10-Bit Flip-Flops With Dual Outputs and Series Resistors	3S	'162820									✔			
11-Bit Buffers/Drivers With Series Resistors	3S	'5400	✔											
		'5401	✔											
12-Bit Buffers/Drivers With Series Resistors	3S	'5402	✔											
		'5403	✔											
16-Bit Buffers/Drivers With Series Resistors	3S	'162244	✔		✔						✔		✔	
16-Bit Transceivers With Series Resistors	3S	'162245	✔		✔						✔			✔LVTH
16-Bit D-Type Latches With Series Resistors	3S	'162373			✔									
16-Bit D-Type Flip-Flops With Series Resistors	3S	'162374			✔									
4-to-1 Multiplexed/Demultiplexed Registered Transceivers With Series Resistors	3S	'162460	✔											
18-Bit UBT™ With Series Resistors on B Port	3S	'162500	✔											
		'162501	✔											
		'162601	✔								✔			
18-Bit Bus-Interface Flip-Flops With Series Resistors	3S	'162823	✔											
18-Bit Buffers/Drivers With Series Resistors	3S	'162825	✔											
20-Bit Buffers/Drivers With Series Resistors	3S	'162827	✔											
12-to-24 Multiplexed D-Type Latches With Series Resistors on B Port	3S	'162260	✔											

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

TESTABILITY BUS-INTERFACE CIRCUITS

IEEE 1149.1 (JTAG) Boundary-Scan Logic

DESCRIPTION	NO. OF BITS	OUTPUT	TYPE	TECHNOLOGY									
				ABT	BCT	LVT	F	LS	S	TTL	AC	ACT	OTHER
Buffers/Drivers	8	3S	'8240	+	✔								
			'8244	+	✔								
Transceivers	8	3S	'8245	✔	✔								
	18	3S	'18245	✔		✔							
Transparent Latches	8	3S	'8373	+	✔								
Flip-Flops	8	3S	'8374	+	✔								
Registered Transceivers	8	3S	'8543	✔									
			'8646	✔									
			'8652	✔									
			'8952	✔									
	18	3S	'18502	✔		✔							
			'18646	✔		✔							
			'18652	✔		✔							
	20	3S	'18504	✔		✔							
Test Bus Controllers		3S	'8990									✔	

FLIP-FLOPS AND LATCHES

Flip-Flops

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																	
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Dual J-K Edge Triggered		'109				✔	✔	✔	✔								✔				
		'112				✔		✔	✔	✔							✔			+	+CDC
		'113				✔															
Dual D-Type		'74				✔	✔	✔	✔	✔	✔	✔•	✔•	✔	✔		✔	✔	✔	✔	
Dual 4 Bit D-Type Edge Triggered	3S	'874				✔	✔														
		'876				✔	✔														
Quad D-Type		'175				✔	✔	✔	✔	✔	✔						✔				
Hex D-Type		'174				✔	✔	✔	✔	✔							✔		✔		
		'378						✔													

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

Flip-Flops (Continued)

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																	
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Octal D-Type True Data	3S	'374	✔	✔		✔	✔	✔	✔	✔		✔•	✔•	+	+		✔	✔	✔	✔	
		'574	✔		✔	✔	✔	✔				✔	✔	✔	✔		✔	✔	✔	✔	
Octal D-Type True Data With Clear		'273	✔		✔	✔			✔								✔	✔	✔		
	3S	'575				✔	✔														
		'874				✔	✔														
Octal D-Type True Data With Clock Enable		'377	✔					✔	✔								✔	✔			
Octal D-Type Inverting	3S	'534	✔			✔						✔	✔				✔				
		'564				✔						✔	✔								
		'576				✔	✔														
Octal Dual Ranked True Data	3S	'4374					✔														
Octal Inverting With Clear	3S	'577				✔															
Octal Inverting With Preset	3S	'876				✔	✔														
Octal True Data	3S	'825					✔														
9 Bit True Data	3S	'823	✔				✔													✔	
		'29823		✔																	
10 Bit Noninverting	3S	'16820														✔					
10 Bit True Data	3S	'821	✔				✔													+	
		'29821		✔		✔															
16 Bit Noninverting	3S	'16374	✔		✔							✔	✔			✔				✔	
18 Bit Noninverting	3S	'16823	✔									✔	✔			✔					
20 Bit Noninverting	3S	'16721														✔					
		'16821	✔										✔			✔					
20 Bit Noninverting With GTL I/O Levels	OD	'16921																			+GTL

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

FLIP-FLOPS AND LATCHES

Latches

DESCRIPTION	NO. OF BITS	OUTPUT	TYPE	TECHNOLOGY																		
				ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
D-Type Edge Triggered Inverting and Noninverting	8	3S	'996				✔															
D-Type Transparent Readback Latch, True	8	3S	'990				✔															
	9	3S	'992				✔															
	10	3S	'994				✔															
D-Type Transparent With Clear, True Outputs	8	3S	'666				✔															
D-Type Transparent With Clear, Inverting Outputs	8	3S	'667				✔															
D-Type Transparent True	8	3S	'373	✔	✔		✔	✔	✔	✔	✔		✔•	✔•	+	+		✔	✔	✔	✔	
			'573	✔		✔	✔	✔	✔				✔	✔	✔	✔		✔	✔	✔	✔	
	16	3S	'16373	✔		✔							✔	✔			✔				✔	
D-Type Dual 4 Bit Transparent True	8	3S	'873				✔	✔														
D-Type Transparent Inverting	8	3S	'533	✔			✔	✔					✔	✔								
			'563				✔						✔	✔				✔				
			'580				✔															
Addressable	8	2S	'259				✔			✔								✔				
D-Type True Inputs	8	3S	'845				✔															
	9	3S	'843	✔			✔														+	
			'29843		✔																	
	10	3S	'841	✔			✔														✔	
			'29841		✔		✔															
	18	3S	'16843	+													✔					
	20	3S	'16841	✔										✔			✔					
D-Type Inverting Inputs	10	3S	'842				✔															

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

REGISTERS

Shift Registers

DESCRIPTION	NO. OF BITS	OUTPUT	TYPE	TECHNOLOGY													
				ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AHC	AHCT	HC	HCT	LV
Parallel In, Parallel Out, Bidirectional	4		'194					✔		✔	✔						
	8		'299				✔		✔	✔	✔						
			'323				✔			✔							
Parallel In, Parallel Out	4		'195							✔	✔						
Serial In, Parallel Out	8		'164				✔			✔					✔		✔
Parallel In, Serial Out	8		'165				✔			✔					✔		
			'166				✔			✔					✔		
Serial In, Parallel Out With Output Latches	8	3S	'594							✔					✔		
			'595							✔					✔		
Noninverting	8	3S	'299				✔		✔	✔	✔						
	9	3S	'29823		✔												

Register Files

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY										
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT
Dual 16 Word × 4 Bits	3S	'870				✔							

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

COUNTERS

Synchronous Counters – Positive Edge Triggered

DESCRIPTION	PARALLEL LOAD	TYPE	TECHNOLOGY												
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AHC	AHCT	HC	HCT
4 Bit Decade Up/Down	Sync	'568				✔									
4 Bit Binary	Sync	'161				✔	✔	✔	✔					✔	
		'163				✔	✔	✔	✔	✔				✔	
		'561				✔									
4 Bit Binary Up/Down	Sync	'169				✔	✔	✔	✔	✔					
		'569				✔									
		'191				✔			✔					✔	
		'193				✔			✔		✔			✔	
8 Bit Up/Down	Sync Clear	'869				✔	✔								
	Async Clear	'867				✔	✔								

Asynchronous Counters (Ripple Clock) – Negative Edge Triggered

DESCRIPTION	PARALLEL LOAD	TYPE	TECHNOLOGY												
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AHC	AHCT	HC	HCT
Dual 4 Bit Binary	None	'393							✔					✔	
12 Bit Binary	Async	'4040												✔	
14 Bit Binary	Async	'4020												✔	
		'4060												✔	

8-Bit Binary Counters With Registers

DESCRIPTION	PARALLEL LOAD	TYPE	TECHNOLOGY												
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AHC	AHCT	HC	HCT
Parallel Register Outputs	3S	'590							✔					✔	
Parallel Register Inputs	3S	'593							✔						

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

DECODERS, ENCODERS, DATA SELECTORS/MULTIPLEXERS

Encoders/Data Selectors/Multiplexers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY																
			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC
Quad 2-to-1		'157				✔	✔	✔	✔	✔	✔			+	+		✔	✔		✔
		'158				✔	✔	✔	✔	✔				+	+		✔			
		'298					✔		✔											
	3S	'257				✔	✔	✔	✔	✔			•	+	+		✔	✔		✔
		'258				✔	✔	✔	✔					+	+					
Hex 2-to-1 Universal Multiplexers	3S	'857				✔														
Dual 4-to-1		'153				✔	✔	✔	✔	✔							✔			
	3S	'253				✔	✔	✔	✔								✔			
		'353					✔													
4-to-1 Registered Transceivers	3S	'16460	✔																	
Cascadable Octals		'148							✔		✔						✔			
8-to-1		'151				✔	✔	✔	✔	✔							✔			
	3S	'251				✔		✔	✔	✔							✔			
16-to-1	3S	'250					✔													
12-to-24 Multiplexed D-Type Latches	3S	'16260	✔													✔				
12-to-24 Registered Bus Exchangers	3S	'16269														✔				
		'16270														✔				

Decoders/Demultiplexers

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY														
			ALS	AS	F	LS	S	TTL	AC	ACT	AHC	AHCT	ALVC	HC	HCT	LV	LVC	OTHER
Dual 2-to-4		'131		✔														
		'139	✔			✔	✔		•	•	+	+		✔	✔			
	OC	'156	✔			✔		✔										
Dual 2-to-4 for Battery Backed-Up Memories		'2414																
3-to-8		'138	✔	✔	✔	✔	✔		•		+	+		✔	✔	✔	✔	
3-to-8 With Address Registers		'137	✔	✔		✔											+	
4-to-10 BCD-to-Decimal		'42				✔								✔				

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

COMPARATORS AND PARITY GENERATORS/CHECKERS

Comparators

DESCRIPTION								TYPE	TECHNOLOGY							
INPUT	P=Q	$\overline{P=Q}$	P>Q	$\overline{P>Q}$	P<Q	OUTPUT	ENABLE		ALS	AS	F	LS	AC	ACT	HC	HCT
8 Bit With 20-kΩ Pullup	No	Yes	No	No	No	2S	Yes	'520	✔				•			
	No	Yes	No	Yes	No	2S	No	'682				✔			✔	
8 Bit Standard	No	Yes	No	No	No	2S	Yes	'521	✔		✔					
	No	Yes	No	Yes	No	2S	No	'684				✔			✔	
	No	Yes	No	No	No	2S	Yes	'688	✔			✔			✔	
8 Bit Latched P	No	No	Yes	No	Yes	2S	Yes	'885		✔						

Parity Generators/Checkers

DESCRIPTION	NO. OF BITS	TYPE	TECHNOLOGY								
			ALS	AS	F	LS	S	TTL	AC	ACT	HC	HCT
Odd/Even	9	'280	✔	✔	✔	✔	✔					
		'286		✔						•		

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

BUS SWITCHES AND 5-V/3-V VOLTAGE TRANSLATORS

Bus Switches

DESCRIPTION	TYPE	TECHNOLOGY			
		CBT	CBTS	CBTD	OTHER
Quad Bus Switches	'3125	✔			
Dual 4-Bit Bus Switches With '244 Pinout	'3244	✔			
8-Bit Bus Switches With '245 Pinout	'3245	✔			
Quad 2-to-1-Bit FET Multiplexers/Demultiplexers	'3257	✔			
Dual Bus Switches	'3306	✔	✔	✔	
8-Bit Bus Switches	'3345	✔			
10-Bit Bus-Exchange Switches	'3383	✔			
Dual 5-Bit Bus Switches	'3384	✔	✔	✔	
10 Bit With Precharged Outputs for Live Insertion	'6800	✔			
18-Bit Bus-Exchange Switches	'16209	✔			
24-Bit Bus-Exchange Switches	'16211	✔			
	'16212	✔			
	'16213	✔			
12-Bit 3-to-1 Bus Select	'16214	✔			
Synchronous 16-Bit-to-32-Bit FET Multiplexers	'16232	✔			
16-Bit-to-32-Bit FET Multiplexers/Demultiplexers	'16233	✔			

ARITHMETIC CIRCUITS

Parallel Binary Adders

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY											
			ALS	AS	F	LS	S	TTL	HC	HCT	AC	ACT	LV	LVC
4 Bit		'283			✔	✔	✔							

Arithmetic Logic Units

DESCRIPTION	OUTPUT	TYPE	TECHNOLOGY											
			ALS	AS	F	LS	S	TTL	HC	HCT	AC	ACT	LV	LVC
4-Bit Arithmetic Logic Units: Function Generator		'181		✔										

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

First-In, First-Out (FIFO) Memories

DESCRIPTION		OUTPUT	TYPE	TECHNOLOGY											
SIZE	TYPE†			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	ALVC
16 Words × 4 Bits	U	3S	'232				✔								
16 Words × 5 Bits	U	3S	'225								✔				
			'233				✔								
32 Words × 9 Bits	B	3S	'2238				✔								
64 Words × 4 Bits	U	3S	'234				✔								
			'236				✔								
64 Words × 5 Bits	U	3S	'235				✔								
64 Words × 8 Bits	U	3S	'2232				✔								
64 Words × 9 Bits	U	3S	'2233				✔								
64 Words × 18 Bits	U, C	3S	'7813											✔	✔
	U	3S	'7814											✔	✔
64 Words × 36 Bits	B, C	3S	'3612	✔											
			'3614	✔											
	U, C	3S	'3611	✔											
			'3613	✔											
Dual 64 × 1	C	3S	'2226											✔	
			'2227											✔	
Dual 256 × 1	C	3S	'2228											✔	
			'2229											✔	
256 Words × 9 Bits	U	3S	'7200L											✔	
256 Words × 18 Bits	U, C	3S	'7805											✔	
	U	3S	'7806											✔	✔
256 × 36 × 2 Bits	B, C	3S	'3622											✔	
512 Words × 9 Bits	U	3S	'7201LA											✔	

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

† U = Unidirectional
B = Bidirectional
C = Clocked
S = Synchronized

First-In, First-Out (FIFO) Memories (Continued)

DESCRIPTION		OUTPUT	TYPE	TECHNOLOGY											
SIZE	TYPE†			ABT	BCT	LVT	ALS	AS	F	LS	S	TTL	AC	ACT	ALVC
512 Words × 18 Bits	U, C	3S	'7803											✔	✔
	U	3S	'7804											✔	✔
	B, C	3S	'7819	✔											
	B	3S	'7820	✔											
512 Words × 32 Bits	B, C	3S	'3638											✔	
512 Words × 36 Bits	U, C	3S	'3631											✔	
	B, C	3S	'3632											✔	
1K Words × 9 Bits	B	3S	'2235											✔	
			'2236											✔	
	U	3S	'7202LA											✔	
1K Words × 18 Bits	U, C	3S	'7811											✔	
			'7881											✔	
	U	3S	'7802											✔	
1K Words × 36 Bits	U, C	3S	'3641											✔	
1K × 36 × 2 Bits	B, C	3S	'3642											+	
2K Words × 9 Bits	U, C	3S	'7807											✔	
	U	3S	'7203L											✔	
			'7808											✔	
2K Words × 18 Bits	U, C	3S	'7882											✔	
2K Words × 36 Bits	U, C	3S	'3651											+	
4K Words × 9 Bits	U	3S	'7204L											✔	
4K Words × 18 Bits	U, C	3S	'7884											✔	

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

† U = Unidirectional
B = Bidirectional
C = Clocked
S = Synchronized

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

3.3-V Clock-Distribution Circuits (CDC)

DESCRIPTION	I/O LEVELS	TYPE	TECHNOLOGY			
			AS	AC	ACT	ABT
3.3-V Hex Inverting Clock Drivers/Buffers	CMOS/CMOS	'203		✔		
1-to-9 Differential LVPECL Buffers	LVPECL/LVPECL	'111				+
1-to-9 Differential LVPECL Buffers With Output Enable	LVPECL/LVPECL	'112				+
1-to-10 Buffers With Output Enable	TTL/TTL	'351				✔
		'2351				✔
1-to-6 PLL Clock Drivers	TTL/TTL	'536				+
		'2536				+
1-to-12 PLL Clock Drivers	TTL/TTL	'586				✔
		'2586				✔
	LVPECL/TTL	'582				+
		'2582				+
Phase-Locked-Loop 1-to-16 Clock Drivers	SSTL/TTL	'587				+
		'2587				+
P5 Motherboard Clock Synthesizers/Drivers	TTL/TTL	'9841				✔
		'9842				✔
		'9843				✔
P6 Motherboard Clock Synthesizers/Drivers	TTL/TTL	'916				+
PC Motherboard Clock Generators With Dual 1-to-4 Buffers	TTL/TTL	'913				+

✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

5-V Clock-Distribution Circuits (CDC)

DESCRIPTION	I/O LEVELS	TYPE	TECHNOLOGY			
			AS	AC	ACT	ABT
Hex Inverters	CMOS/CMOS	'204		✔		
		'204-7		✔		
1-to-6 Exclusive ORs	TTL/TTL	'328				✔
	TTL/CMOS	'329				✔
1-to-6 Exclusive ORs With Output Enable	TTL/TTL	'391				✔
	TTL/CMOS	'392				✔
Dual 1-to-4 Buffers (2 inputs, 8 outputs)	TTL/CMOS	'208			✔	
		'208-7			✔	
	CMOS/CMOS	'209		✔		
		'209-7		✔		
1-to-8 Divide-by-2 Flip-Flops (6 inverting, 2 noninverting)	TTL/TTL	'303	✔			
1-to-8 Divide-by-2 Flip-Flops (8 noninverting)	TTL/TTL	'304	✔			
1-to-8 Divide-by-2 Flip-Flops (4 inverting, 4 noninverting)	TTL/TTL	'305	✔			
1-to-8 Fanouts (4 noninverting buffers, 4 divide-by-2 flip-flops)	TTL/CMOS	'337				✔
	TTL/TTL	'339				✔
1-to-8 NANDs	TTL/TTL	'340				✔
1-to-8 ANDs	TTL/TTL	'341				✔
3-Way Fanout Buffers (dual 1-to-3 noninverting buffers, 1-to-4 divide-by-2 flip-flops)	TTL/TTL	'330				✔

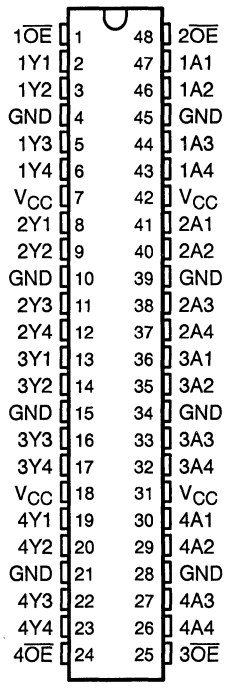
✔ Product available in technology indicated • Product available in reduced-noise advanced CMOS (11000 series) + New product planned in technology indicated

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Contents

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation
- Members of the Texas Instruments *Widebus*™ Family
- Fastest Buffer/Driver: 2 ns Maximum Input to Output Time Delay
- Schottky Diodes on All Inputs to Eliminate Overshoot and Undershoot
- Industry Standard '16244 Pinout
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

DGG OR DL PACKAGE
(TOP VIEW)



description

The SN74ALB16244 16-bit buffer and line driver is designed for high-speed, low-voltage (3.3-V) V_{CC} operation. This device is intended to replace the conventional driver in any speed-critical path. The propagation delay from input to output is 2 ns maximum. The small propagation delay is achieved using a unity gain amplifier on the input and feedback resistors from input to output, which allows the output to track the input with a small offset voltage (V_{off}). The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. This device provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

The SN74ALB16244 is characterized for operation from −40°C to 85°C.

applications

The SN74ALB16244 is particularly suitable for driving the system bus, which requires external drivers due to high capacitive loading caused by address multiplexing. The 25-mA drive capability and 2-ns delay is ideal for this application.

The SN74ALB16244 is ideal in cache memory (SRAM) or main memory (DRAM and EDO DRAM) interface; it can also be used in high-speed graphics and multimedia applications.

FUNCTION TABLE
(each buffer)

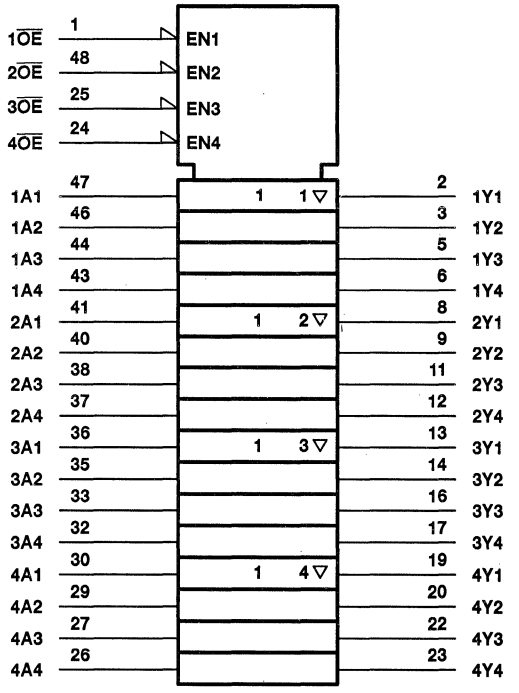
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

PRODUCT PREVIEW

Widebus is a trademark of Texas Instruments Incorporated.

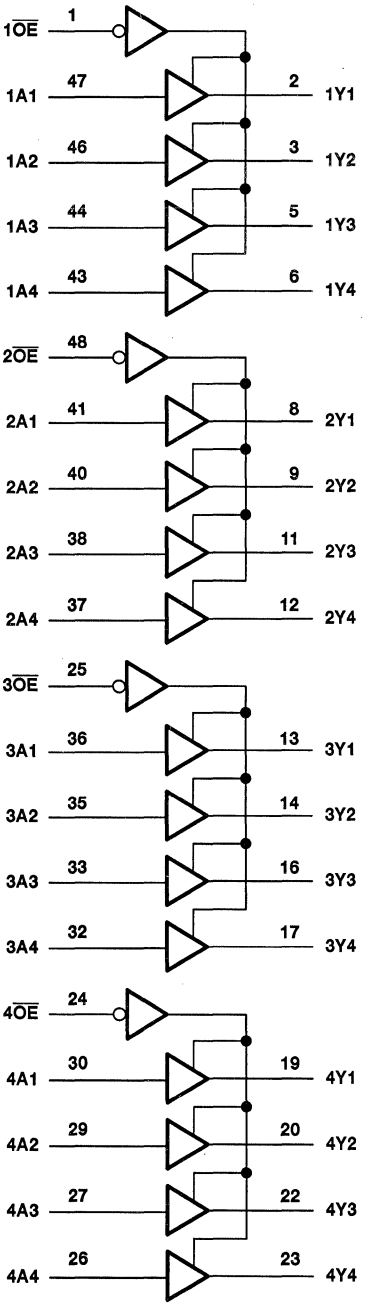
PRODUCT PREVIEW

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ± 50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ± 50 mA
Continuous current through each V_{CC} or GND ..... ± 100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The input and output positive-voltage ratings may be exceeded up to 4.6 V if the input and output clamp-current ratings are observed.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		3	3.6	V
V_{IH}‡	High-level input voltage		2.2		V
V_{IL}‡	Low-level input voltage			0.6	V
I_{OH}	High-level output current			−25	mA
I_{OL}	Low-level output current			25	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		5	ns/V
T_A	Operating free-air temperature		−40	85	°C

‡ The outputs are warranted to be TTL compatible.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP†	MAX	UNIT
V_{IK}	V_{CC} = 3 V,	I_I = –18 mA				–1.2	V
V_{OH}‡	V_{CC} = 3 V	I_{OH} = 0		V_I –0.2			V
		I_{OH} = – 25 mA		2			
V_{OL}‡	V_{CC} = 3 V	I_{OL} = 0 mA				V_I +0.2	V
		I_{OL} = 25 mA				V_I +0.2	
I_I	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs			±10	µA
		V_I = V_{CC}	Data pins			1	mA
		V_I = 0				–1.5	
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				20	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–20	µA
I_{CC} (per buffer)	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		5	9	mA
			Outputs low		5	9	
I_{CC}	Entire device in the high-impedance state					0.8	mA
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} –0.6 V,				750	µA
C_i	V_I = 3 V or 0				4		pF
C_o	V_O = 3 V or 0				10		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Limits are valid only if the buffer is in the linear region. In the nonlinear region, the output transistors are clamped at the output voltage margins.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

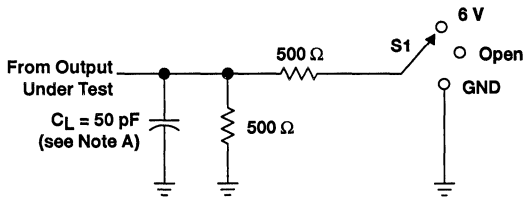
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			UNIT
			MIN	MAX	MIN	TYP†	MAX	
t_{pd}	A	Y					2	ns
t_{en}	$\overline{OE}$	Y					6	ns
t_{dis}	$\overline{OE}$	Y					6	

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

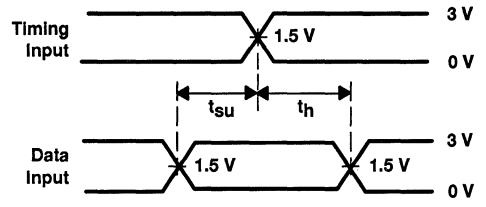
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION

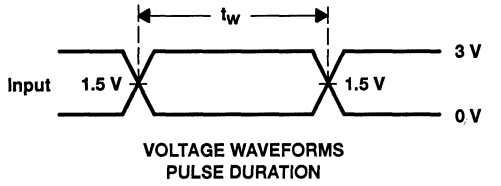


LOAD CIRCUIT

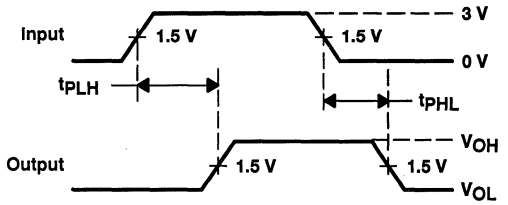
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



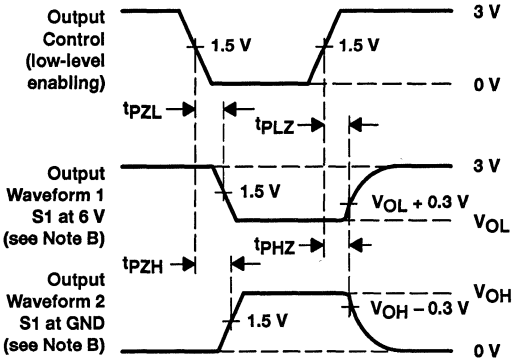
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

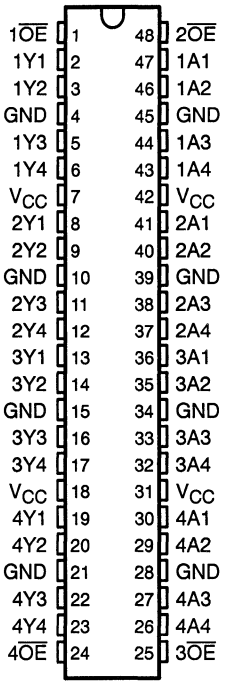
Figure 1. Load Circuit and Voltage Waveforms

PRODUCT PREVIEW

Contents

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16240 is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides inverting outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

The SN74ALVCH16240 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

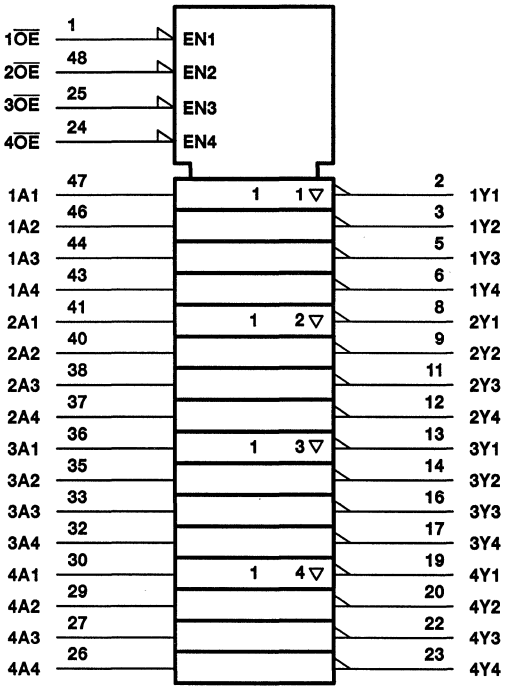
The SN74ALVCH16240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

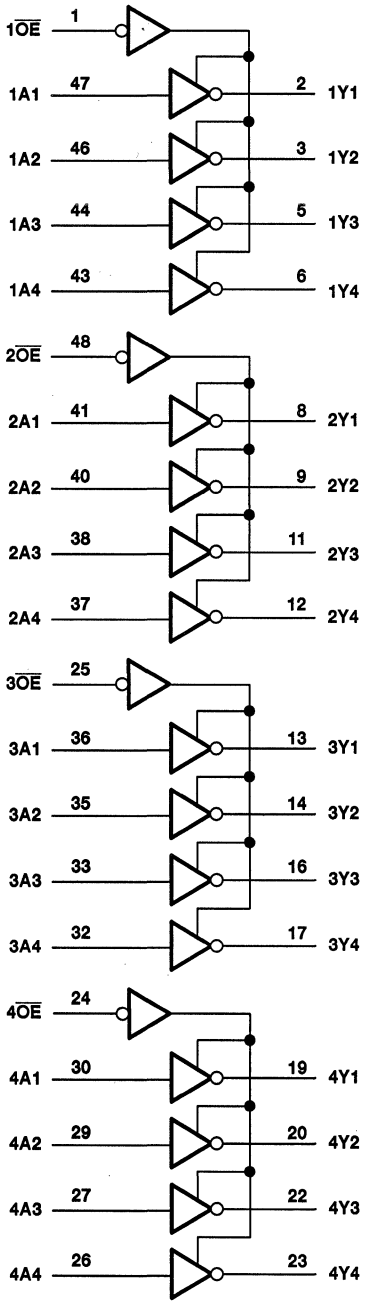
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

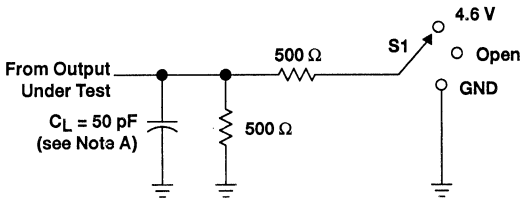
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	5.9		5.3	1	4.2	ns
t_{en}	$\overline{OE}$	Y	1	6.9		6.1	1	5	ns
t_{dis}	$\overline{OE}$	Y	1.5	5.6		4.8	1	4.4	ns

operating characteristics, T_A = 25°C

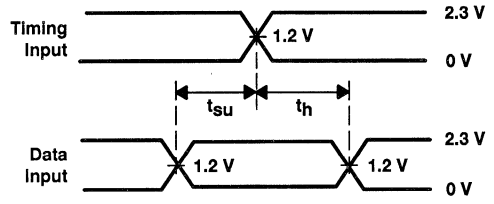
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	19	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

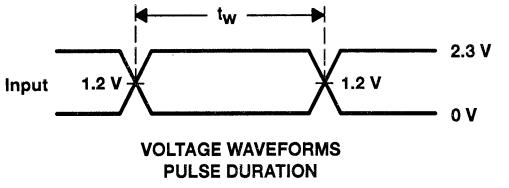


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

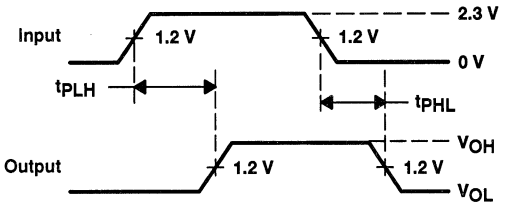
LOAD CIRCUIT



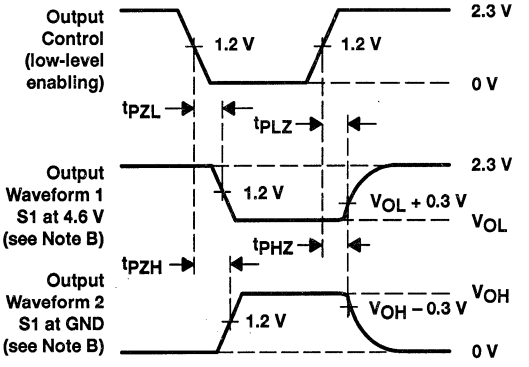
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

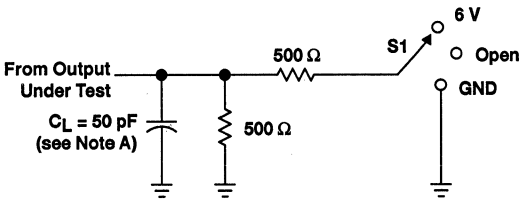


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

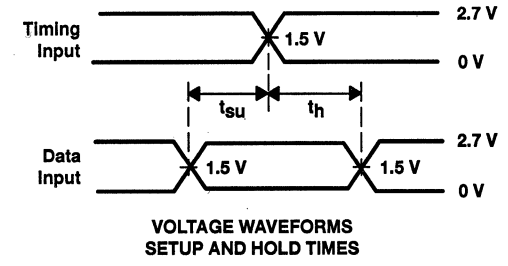
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

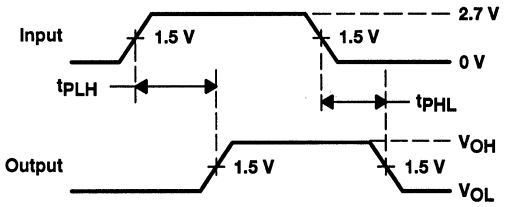


TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 6 V GND

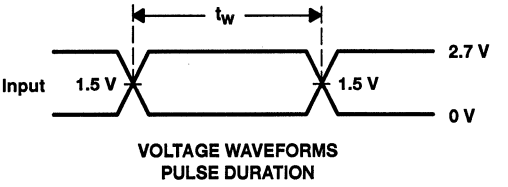
LOAD CIRCUIT



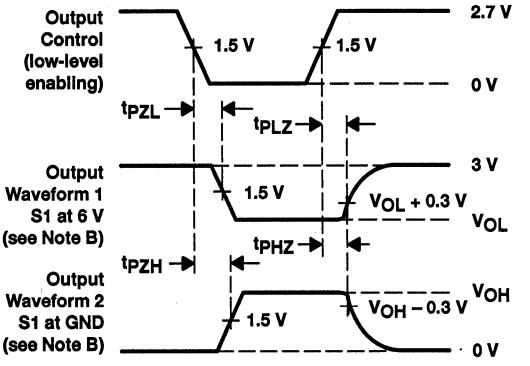
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



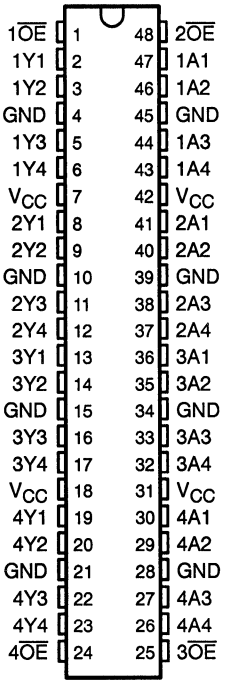
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16244 is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16244 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

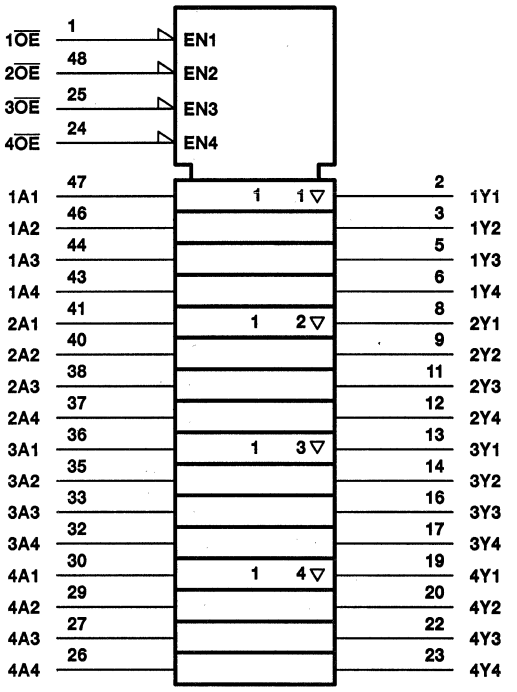
The SN74ALVCH16244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

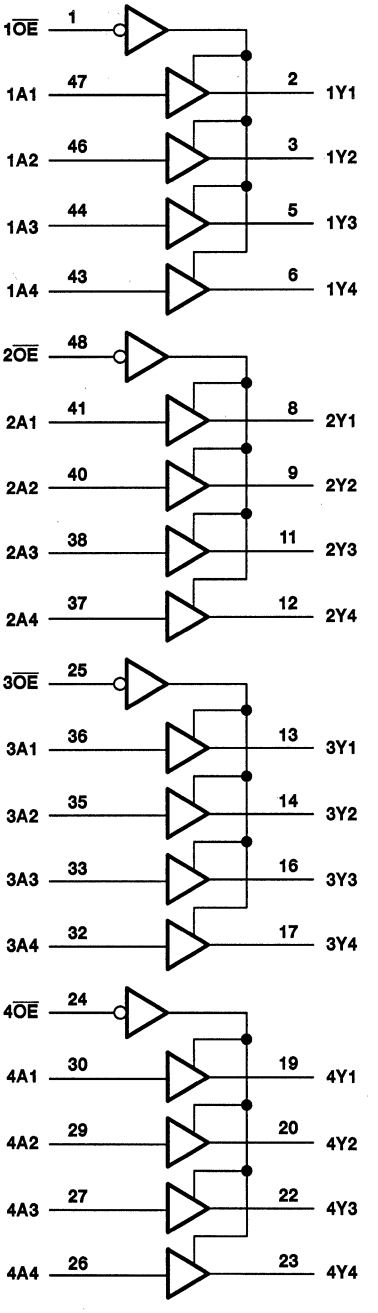
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

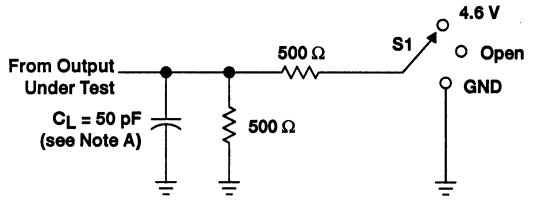
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	5		4	1	3.6	ns
t_{en}	$\overline{OE}$	Y	1	6.8		6	1	5	ns
t_{dis}	$\overline{OE}$	Y	1	6		5.2	1	5	ns

operating characteristics, T_A = 25°C

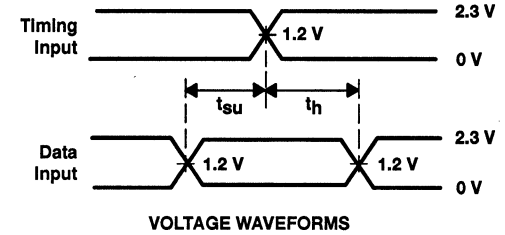
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	19	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

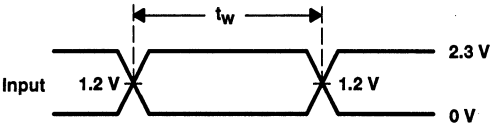


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

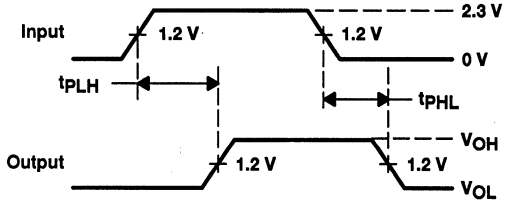
LOAD CIRCUIT



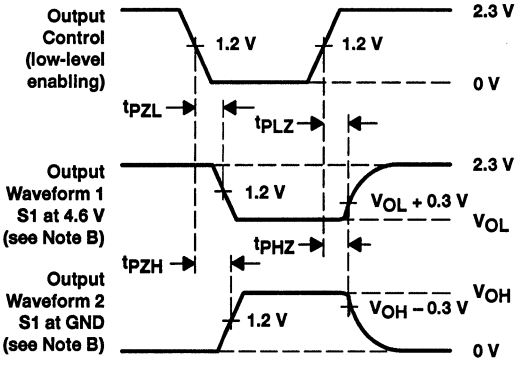
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

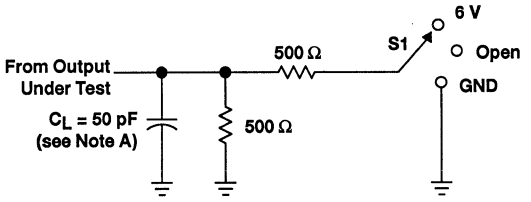


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

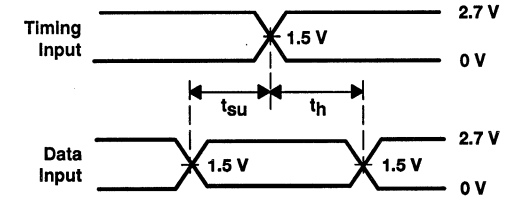
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

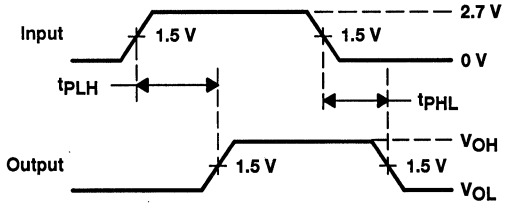


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

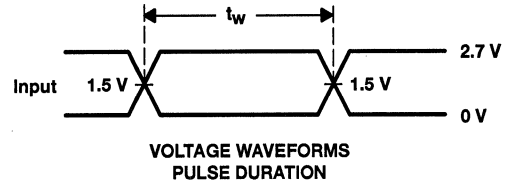
LOAD CIRCUIT



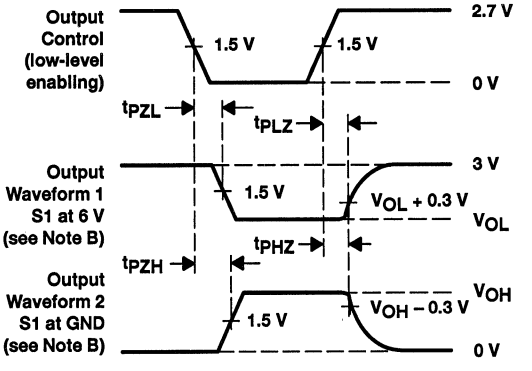
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



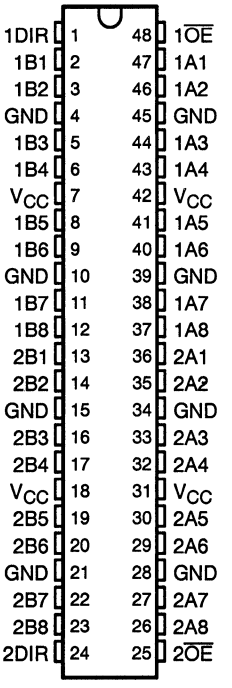
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16245 is designed for asynchronous communication between data buses. The control-function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16245 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

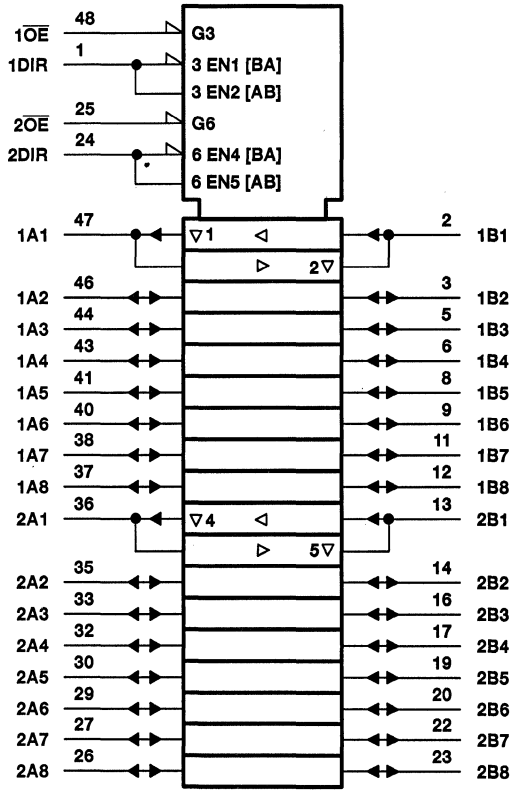
The SN74ALVCH16245 is characterized for operation from −40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 8-bit section)

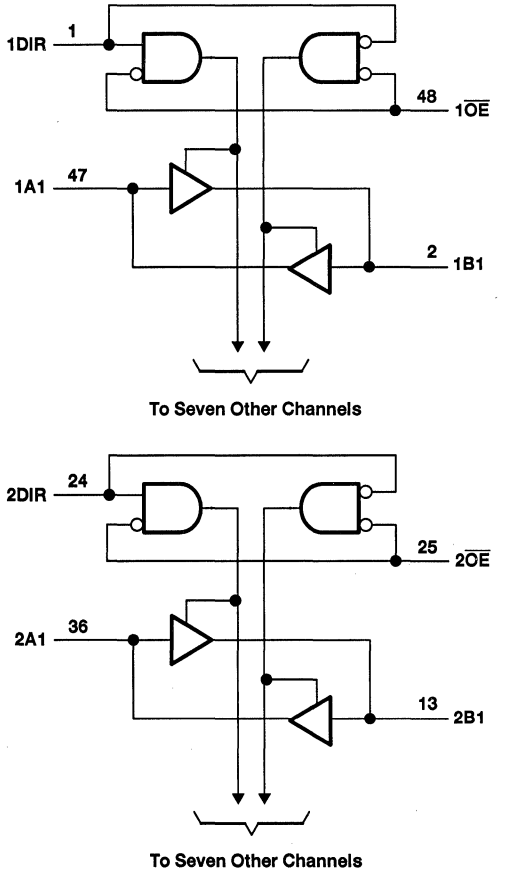
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

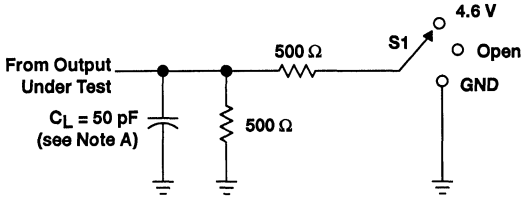
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	5		4	1	3.6	ns
t_{en}	$\overline{OE}$	B or A	1	6.8		6	1	5	ns
t_{dis}	$\overline{OE}$	B or A	1	6		5.2	1	5	ns

operating characteristics, T_A = 25°C

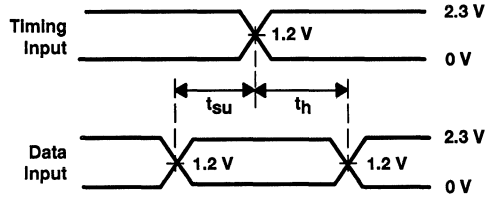
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	22	29	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

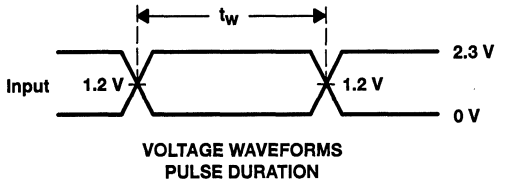


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

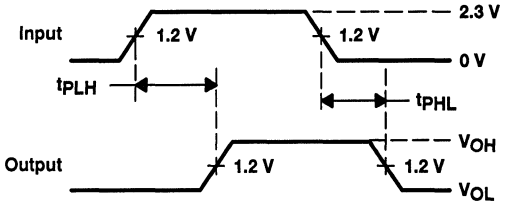
LOAD CIRCUIT



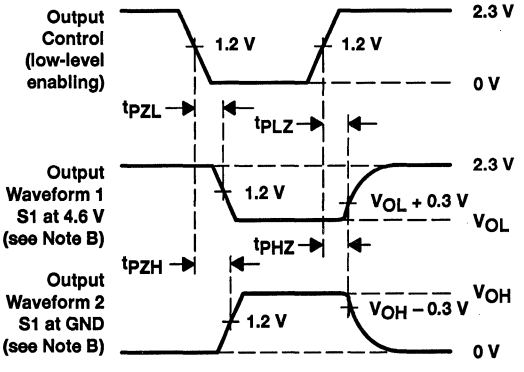
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

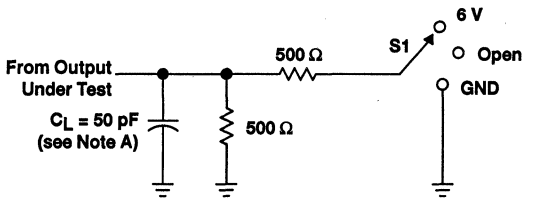


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

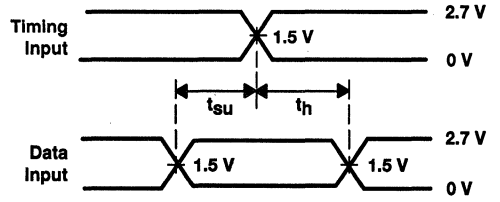
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

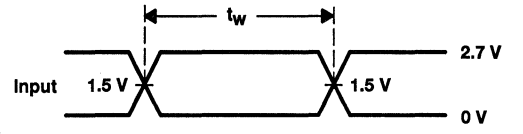


LOAD CIRCUIT

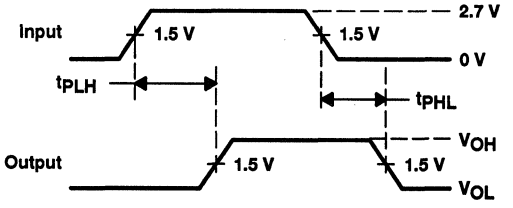
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



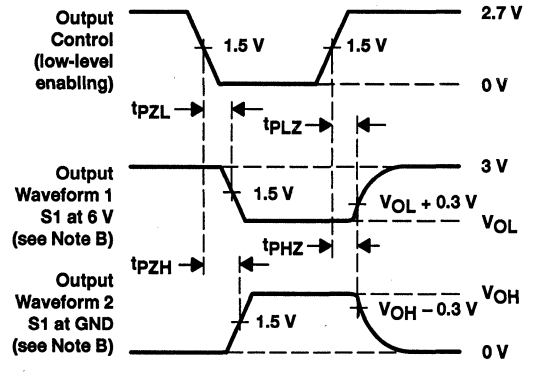
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



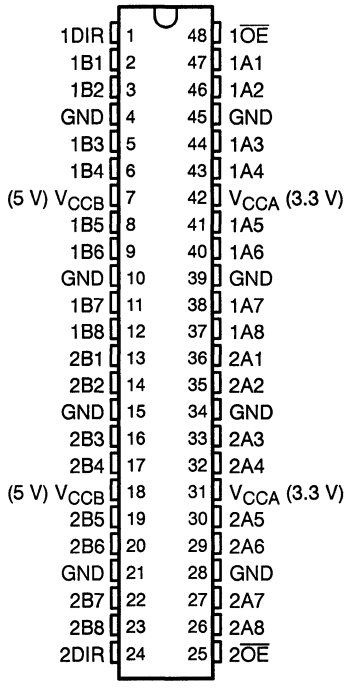
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver contains two separate supply rails; B port has V_{CCB}, which is set at 5 V, and A port has V_{CCA}, which is set to operate at 3.3 V. This allows for translation from a 3.3-V to a 5-V environment and vice-versa.

The SN74ALVC164245 is designed for asynchronous communication between data buses.

The SN74ALVC164245 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

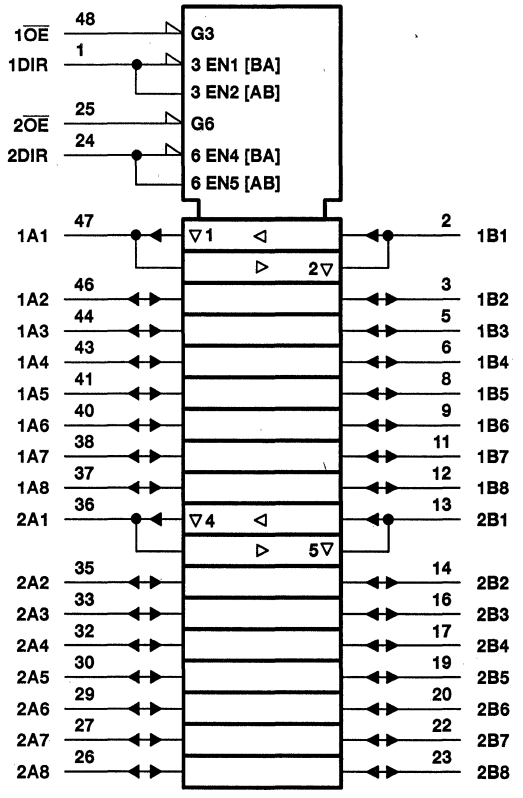
The SN74ALVC164245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

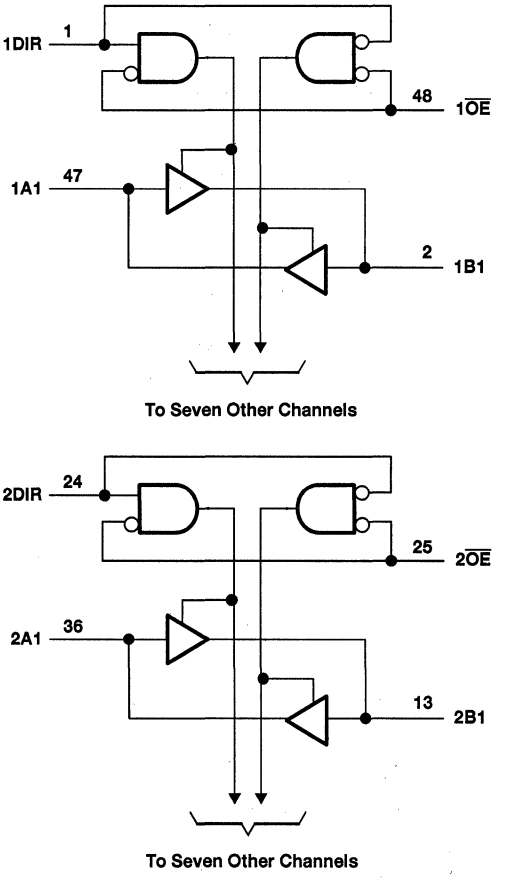
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range for V_{CCB} at 5 V (unless otherwise noted)†

Supply voltage range, V_{CCB} ..... −0.5 V to 6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6 V
Output voltage range, V_O (see Note 1) ..... −0.5 V to V_{CCB} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CCB}$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CCB}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CCB}) ..... ±50 mA
Continuous current through each V_{CCB} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. This value is limited to 6 V maximum.
2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

absolute maximum ratings over operating free-air temperature range for V_{CCA} at 3.3 V (unless otherwise noted)†

Supply voltage range, V_{CCA} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 3) ..... −0.5 V to 4.6 V
I/O ports (see Note 3) ..... −0.5 V to V_{CCA} + 0.5 V
Output voltage range, V_O (see Note 3) ..... −0.5 V to V_{CCA} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CCA}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CCA}) ..... ±50 mA
Continuous current through each V_{CCA} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.
3. This value is limited to 4.6 V maximum.

recommended operating conditions for V_{CCB} at 5 V (see Note 4)

		MIN	MAX	UNIT
V_{CCB}	Supply voltage	4.5	5.5	V
V_{IH}	High-level input voltage	2		V
V_{IL}	Low-level input voltage		0.8	V
V_{IA}	Input voltage	0	V_{CCB}	V
V_{OB}	Output voltage	0	V_{CCB}	V
I_{OH}	High-level output current		–24	mA
I_{OL}	Low-level output current		24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_A	Operating free-air temperature	–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

recommended operating conditions for V_{CCA} at 3.3 V (see Note 4)

			MIN	MAX	UNIT
V_{CCA}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CCA} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CCA} = 2.7 V to 3.6 V		0.8	V
V_{IB}	Input voltage		0	V_{CCA}	V
V_{OA}	Output voltage		0	V_{CCA}	V
I_{OH}	High-level output current	V_{CCA} = 2.7 V		–12	mA
		V_{CCA} = 3 V		–24	
I_{OL}	Low-level output current	V_{CCA} = 2.7 V		12	mA
		V_{CCA} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range for V_{CCB} = 5 V (unless otherwise noted) (see Note 5)

PARAMETER		TEST CONDITIONS		V_{CCB}	MIN	TYP†	MAX	UNIT
V_{OH} (A to B)		I_{OH} = −100 μA		4.5 V	4.3			V
				5.5 V	5.3			
		I_{OH} = −24 mA		4.5 V	3.7			
				5.5 V	4.7			
V_{OL} (A to B)		I_{OL} = 100 μA		4.5 V			0.2	V
				5.5 V			0.2	
		I_{OL} = 24 mA		4.5 V			0.55	
				5.5 V			0.55	
I_I	Control inputs	$V_I = V_{CCB}$ or GND		5.5 V			±5	μA
I_{OZ}‡	A or B ports	$V_O = V_{CCB}$ or GND		5.5 V				μA
I_{CC}		$V_I = V_{CCB}$ or GND,	I_O = 0	5.5 V				μA
ΔI_{CC}§		One input at 3.4 V,	Other inputs at V_{CCB} or GND	4.5 V to 5.5 V				μA
C_i	Control inputs	$V_I = V_{CCB}$ or GND		5 V		6.5		pF
C_{io}	A or B ports	$V_O = V_{CCB}$ or GND		5 V		6.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather then at 0 V or V_{CCA}.
NOTE 5: V_{CCA} = 2.7 V to 3.6 V

electrical characteristics over recommended operating free-air temperature range for V_{CCA} = 3.3 V (unless otherwise noted) (see Note 6)

PARAMETER		TEST CONDITIONS		V_{CCA}¶	MIN	TYP†	MAX	UNIT
V_{OH} (B to A)		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = −24 mA		3 V	2			
V_{OL} (B to A)		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	$V_I = V_{CCA}$ or GND		3.6 V			±5	μA
I_{OZ}‡		$V_O = V_{CCA}$ or GND		3.6 V			±10	μA
I_{CC}		$V_I = V_{CCA}$ or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}§		One input at V_{CCA} − 0.6 V,	Other inputs at V_{CCA} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	$V_I = V_{CCA}$ or GND		3.3 V		6.5		pF
C_{io}	A or B ports	$V_O = V_{CCA}$ or GND		3.3 V		8.5		pF

† Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather then at 0 V or V_{CCA}.
¶ For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
NOTE 6: V_{CCB} = 5 V ± .05 V

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

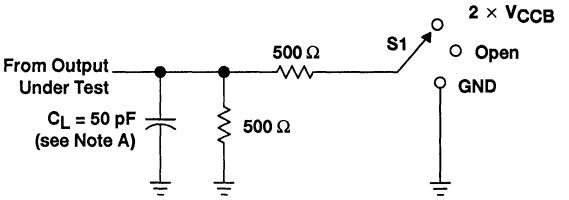
PARAMETER	FROM (INPUT)	TO (OUTPUT)	VCCB = 5 V ± 0.5 V			UNIT
			V_{CCA} = 2.7 V		V_{CCA} = 3.3 V ± 0.3 V	
			MIN	MAX†	MIN† MAX†	
t_{pd}	A	B		5.9	1 5.8	ns
	B	A		6.7	1.2 5.8	ns
t_{en}	$\overline{OE}$	B		9.3	1 8.9	ns
t_{dis}	$\overline{OE}$	B		9.2	2.1 9.5	ns
t_{en}	$\overline{OE}$	A		10.2	2 9.1	ns
t_{dis}	$\overline{OE}$	A		9	2.9 8.6	ns

† This datasheet limit can vary among suppliers.

operating characteristics, T_A = 25°C

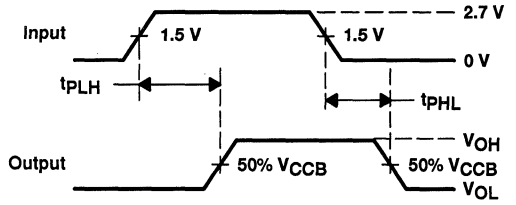
PARAMETER			TEST CONDITIONS	V_{CCA} = 3.3 V, V_{CCB} = 5 V	UNIT
				TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled (A or B)	C_L = 50 pF, f = 10 MHz	56	pF
		Outputs disabled (A or B)		6	

PARAMETER MEASUREMENT INFORMATION
V_{CCB} = 5 V ± 0.5 V

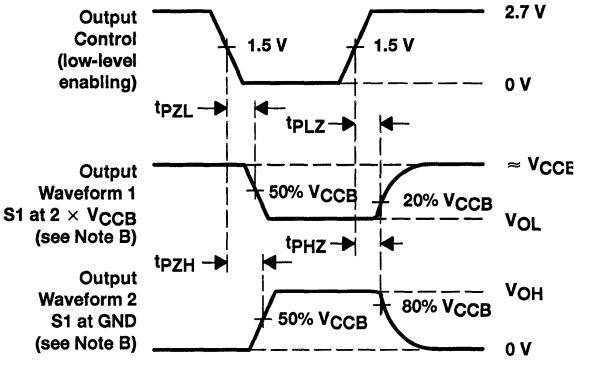


LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CCB}
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

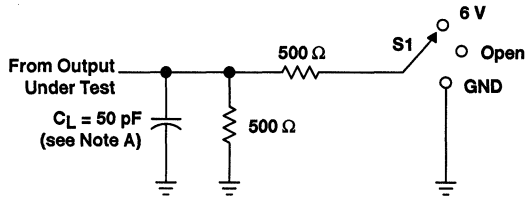


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

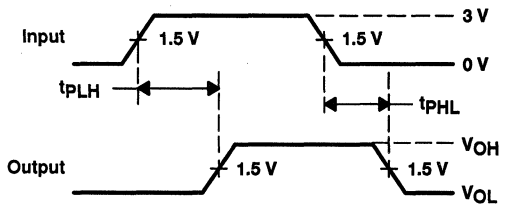
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CCA} = 2.7 V AND 3.3 V ± 0.3 V

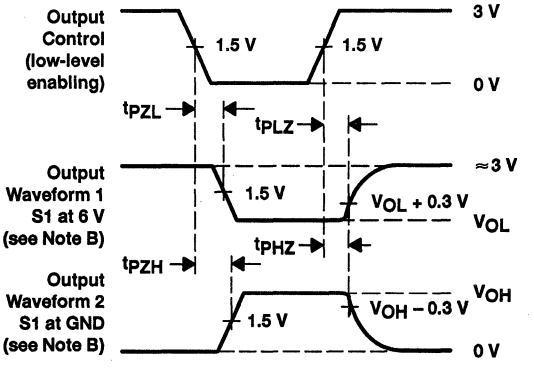


LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



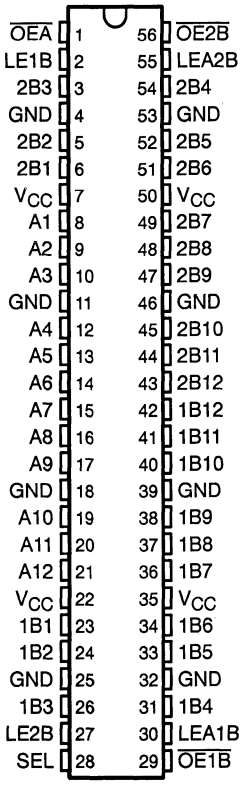
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 12-bit to 24-bit multiplexed D-type latch is designed for 2.3-V to 3.6-V_{CC} operation.

The SN74ALVCH16260 is used in applications where two separate datapaths must be multiplexed onto, or demultiplexed from, a single datapath. Typical applications include multiplexing and/or demultiplexing address and data information in microprocessor or bus-interface applications. This device is also useful in memory-interleaving applications.

Three 12-bit I/O ports (A1–A12, 1B1–1B12, and 2B1–2B12) are available for address and/or data transfer. The output-enable ($\overline{OE1B}$, $\overline{OE2B}$, and $\overline{OEA}$) inputs control the bus transceiver functions. The $\overline{OE1B}$ and $\overline{OE2B}$ control signals also allow bank control in the A-to-B direction.

Address and/or data information can be stored using the internal storage latches. The latch-enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch-enable input is high, the latch is transparent. When the latch-enable input goes low, the data present at the inputs is latched and remains latched until the latch-enable input is returned high.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16260 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16260 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

Function Tables

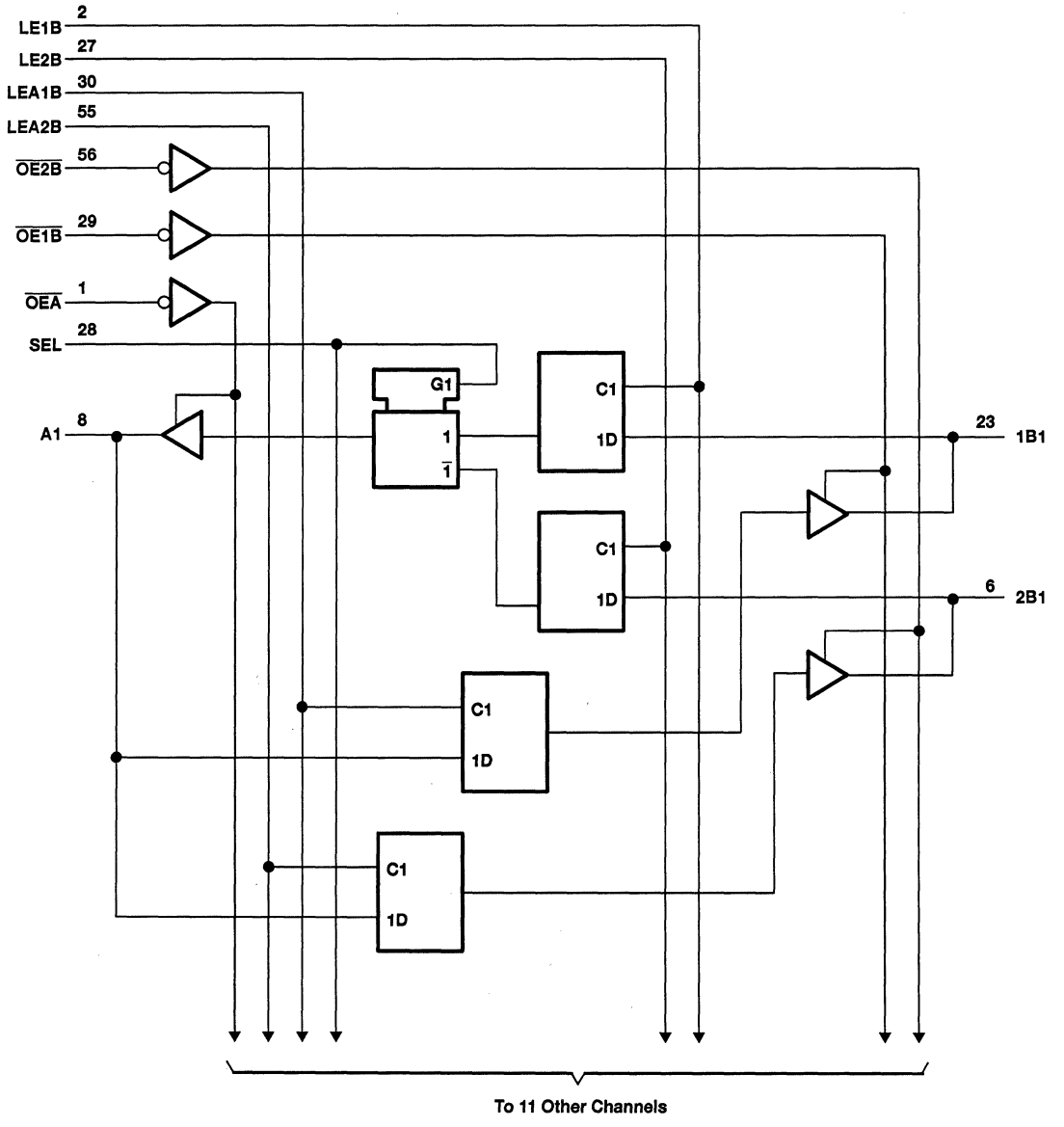
B TO A ($\overline{OEB}$ = H)

INPUTS						OUTPUT
1B	2B	SEL	LE1B	LE2B	$\overline{OEA}$	A
H	X	H	H	X	L	H
L	X	H	H	X	L	L
X	X	H	L	X	L	A_0
X	H	L	X	H	L	H
X	L	L	X	H	L	L
X	X	L	X	L	L	A_0
X	X	X	X	X	H	Z

A TO B ($\overline{OEA}$ = H)

INPUTS					OUTPUTS	
A	LEA1B	LEA2B	$\overline{OE1B}$	$\overline{OE2B}$	1B	2B
H	H	H	L	L	H	H
L	H	H	L	L	L	L
H	H	L	L	L	H	$2B_0$
L	H	L	L	L	L	$2B_0$
H	L	H	L	L	$1B_0$	H
L	L	H	L	L	$1B_0$	L
X	L	L	L	L	$1B_0$	$2B_0$
X	X	X	H	H	Z	Z
X	X	X	L	H	Active	Z
X	X	X	H	L	Z	Active
X	X	X	L	L	Active	Active

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high	3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B	1.4		1.1		1.1		ns
t_h	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B	1.6		1.9		1.5		ns

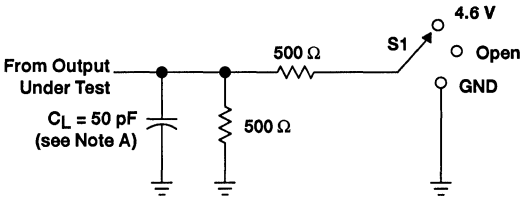
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.2	6		5.1	1.2	4.3	ns
	LE	A or B	1	6.2		5.2	1	4.4	
	SEL	A	1.2	7.5		6.6	1.1	5.6	
t_{en}	$\overline{OE}$	A or B	1	7.2		6.4	1	5.4	ns
t_{dis}	$\overline{OE}$	A or B	1.7	5.9		5	1.3	4.6	ns

operating characteristics, T_A = 25°C

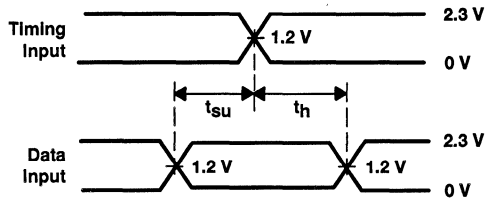
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	87	120	pF
		Outputs disabled		80.5	118	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

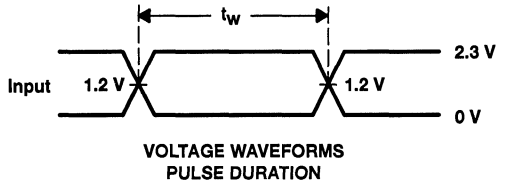


LOAD CIRCUIT

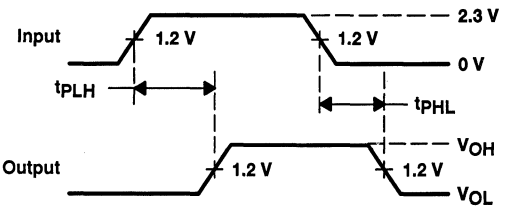
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND



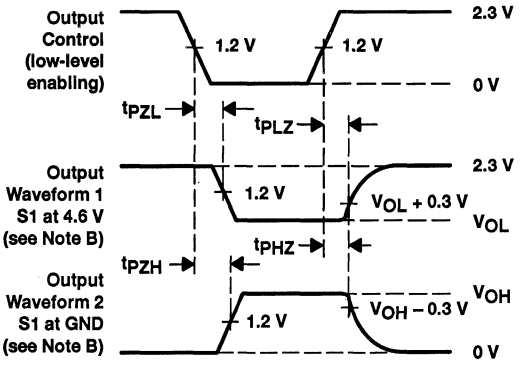
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

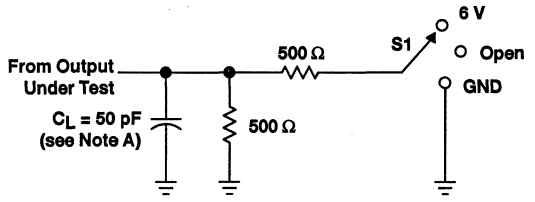


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

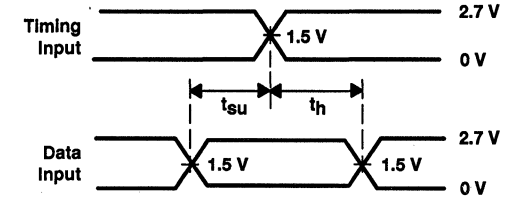
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

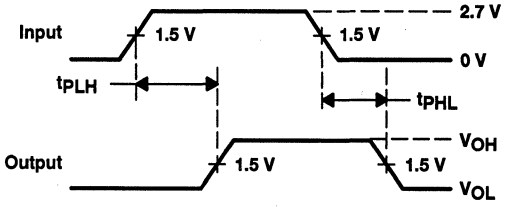


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

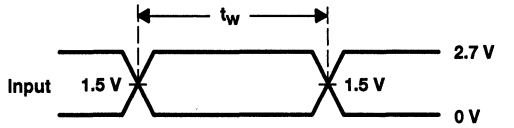
LOAD CIRCUIT



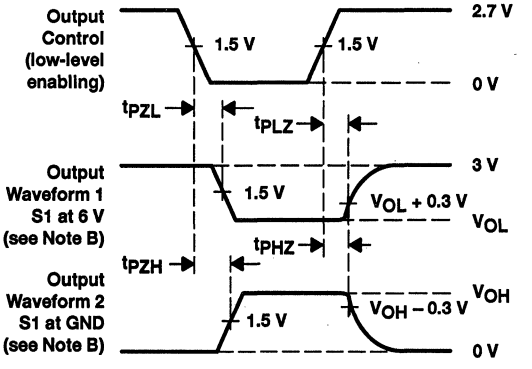
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



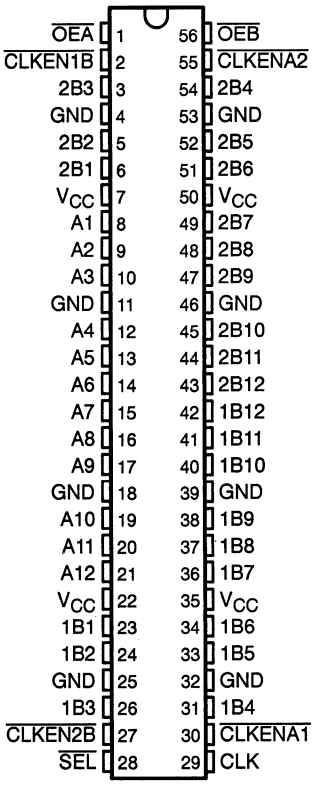
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **B-Port Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 12-bit to 24-bit registered bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162268 is used for applications where data must be transferred from a narrow high-speed bus to a wide, lower-frequency bus.

The device provides synchronous data exchange between the two ports. Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input when the appropriate clock-enable ($\overline{CLKEN}$) inputs are low. The select ($\overline{SEL}$) line is synchronous with CLK and selects 1B or 2B input data for the A outputs.

For data transfer in the A-to-B direction, a two-stage pipeline is provided in the A-to-1B path with a single storage register in the A-to-2B path. Proper control of these inputs allows two sequential 12-bit words to be presented synchronously as a 24-bit word on the B port. Data flow is controlled by the active-low output enables ($\overline{OEA}$, $\overline{OEB}$). These control terminals are registered so bus direction changes are synchronous with CLK.

The B outputs, which are designed to sink up to 12 mA, include 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162268 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

Function Tables

OUTPUT ENABLE

INPUTS			OUTPUTS	
CLK	$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
↑	H	H	Z	Z
↑	H	L	Z	Active
↑	L	H	Active	Z
↑	L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
H	H	X	X	$1B_0$‡	$2B_0$‡
L	X	↑	L	L†	X
L	X	↑	H	H†	X
X	L	↑	L	X	L
X	L	↑	H	X	H

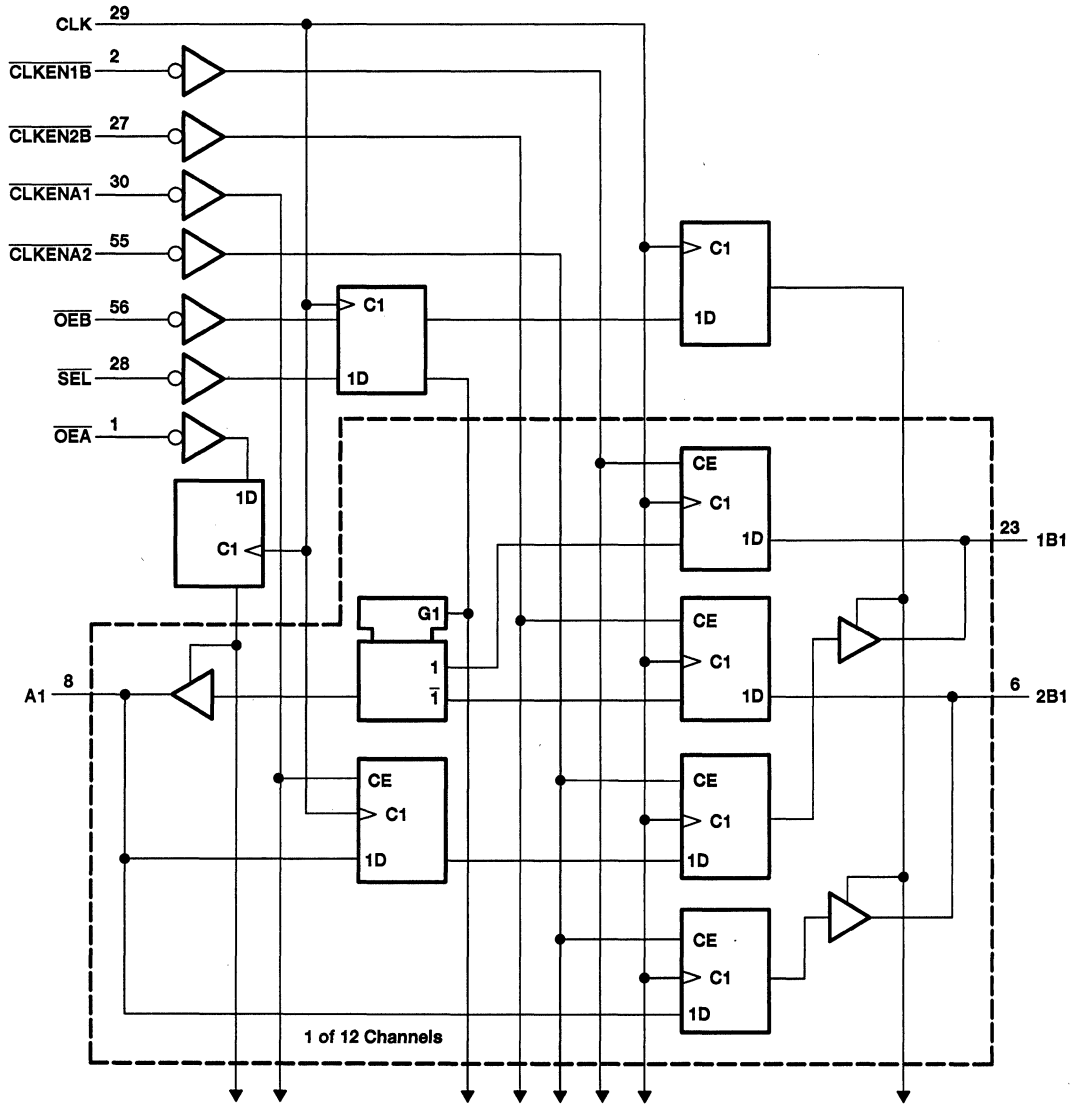
† Two CLK edges are needed to propagate data.
‡ Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS						OUTPUT
$\overline{CLKEN1B}$	$\overline{CLKEN2B}$	CLK	$\overline{SEL}$	1B	2B	A
H	X	X	H	X	X	A_0‡
X	H	X	L	X	X	A_0‡
L	X	↑	H	L	X	L
L	X	↑	H	H	X	H
X	L	↑	L	X	L	L
X	L	↑	L	X	H	H

‡ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current (B port)	V_{CC} = 2.3 V		−6	mA
		V_{CC} = 2.7 V		−8	
		V_{CC} = 3 V		−12	
I_{OL}	Low-level output current (B port)	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
I_{OH}	High-level output current (A port)	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current (A port)	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH} (B port)		I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = −6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = −12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL} (B port)		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
V_{OH} (A port)		I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL} (A port)		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input-leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	125	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	A data before CLK↑	4.5		4		3.4		ns
		B data before CLK↑	0.8		1.2		1		
		$\overline{SEL}$ before CLK↑	1.4		1.6		1.3		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ before CLK↑	3.6		3.4		2.8		
		$\overline{CLKENB1}$ or $\overline{CLKENB2}$ before CLK↑	3.2		3		2.5		
		$\overline{OE}$ before CLK↑	4.2		3.9		3.2		
t_h	Hold time	A data after CLK↑	0		0		0.2		ns
		B data after CLK↑	1.3		1.2		1.3		
		$\overline{SEL}$ after CLK↑	1		1		1		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ after CLK↑	0.1		0.1		0.4		
		$\overline{CLKENB1}$ or $\overline{CLKENB2}$ after CLK↑	0.1		0		0.5		
		$\overline{OE}$ after CLK↑	0		0		0.2		

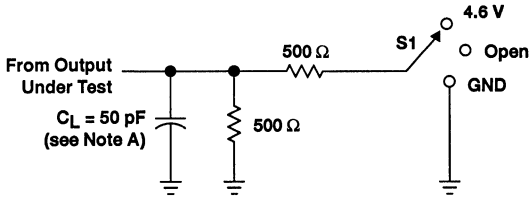
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		125		150		MHz
t_{pd}	CLK	B	2.1	6.7		5.9	1.8	5.4	ns
t_{pd}	CLK	A (1B)	2.1	6.4		5.4	1.7	4.8	ns
t_{pd}	CLK	A (2B)	2.1	6.4		5.3	1.8	4.8	ns
t_{pd}	CLK	A ($\overline{SEL}$)	3	7.9		6.5	2.4	5.8	ns
t_{en}	CLK	B	2.8	7.7		6.8	2.6	6.1	ns
t_{dis}	CLK	B	3.5	7.4		6.1	2.5	5.9	ns
t_{en}	CLK	A	2.1	6.7		5.6	1.8	5.1	ns
t_{dis}	CLK	A	2.7	6.7		5.4	2.1	5	ns

operating characteristics, T_A = 25°C

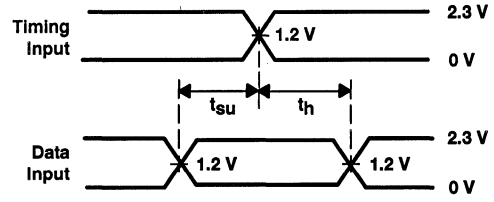
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	87	120	pF
		Outputs disabled		80.5	118	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

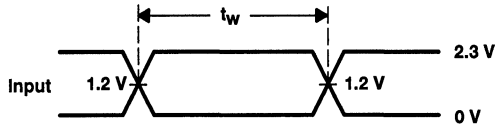


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

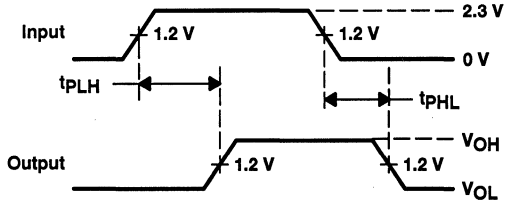
LOAD CIRCUIT



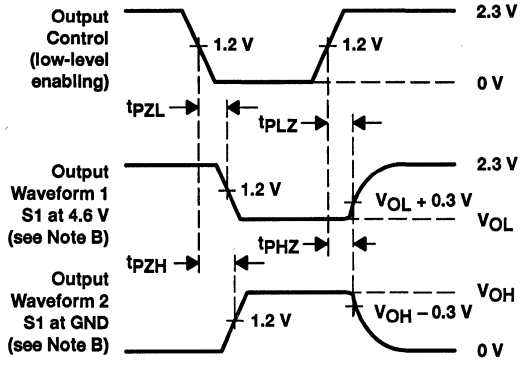
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

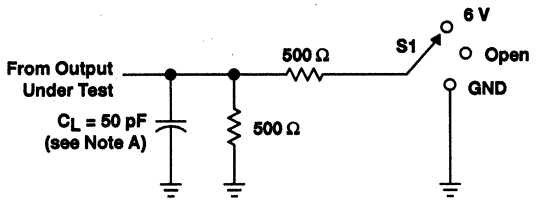


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

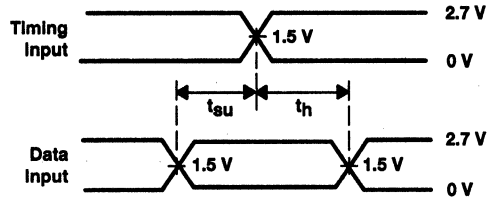
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

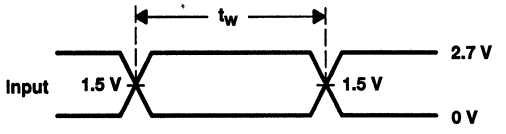


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

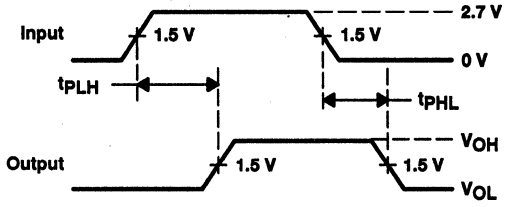
LOAD CIRCUIT



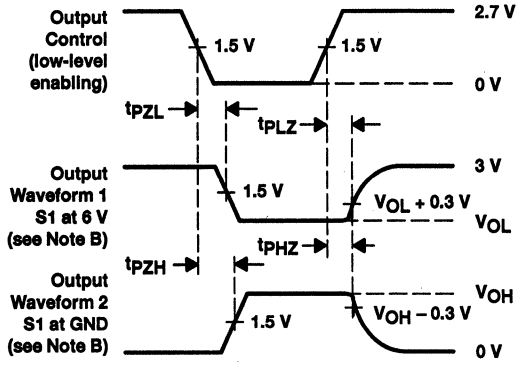
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



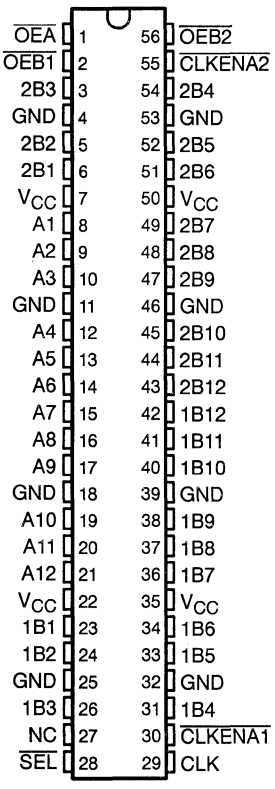
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 12-bit to 24-bit registered bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16269 is used in applications where two separate ports must be multiplexed onto, or demultiplexed from, a single port. The device is particularly suitable as an interface between synchronous DRAMs and high-speed microprocessors.

Data is stored in the internal B-port registers on the low-to-high transition of the clock (CLK) input when the appropriate clock-enable ($\overline{\text{CLKENA}}$) inputs are low. Proper control of these inputs allows two sequential 12-bit words to be presented as a 24-bit word on the B port. For data transfer in the B-to-A direction, a single storage register is provided. The select ($\overline{\text{SEL}}$) line selects 1B or 2B data for the A outputs. The register on the A output permits the fastest possible data transfer, thus extending the period that the data is valid on the bus. The control terminals are registered so that all transactions are synchronous with CLK. Data flow is controlled by the active-low output enables ($\overline{\text{OEA}}$, $\overline{\text{OEB1}}$, $\overline{\text{OEB2}}$).

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16269 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16269 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

Function Tables

OUTPUT ENABLE

INPUTS			OUTPUTS	
CLK	$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
↑	H	H	Z	Z
↑	H	L	Z	Active
↑	L	H	Active	Z
↑	L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
H	H	X	X	$1B_0$†	$2B_0$†
L	X	↑	L	L	X
L	X	↑	H	H	X
X	L	↑	L	X	L
X	L	↑	H	X	H

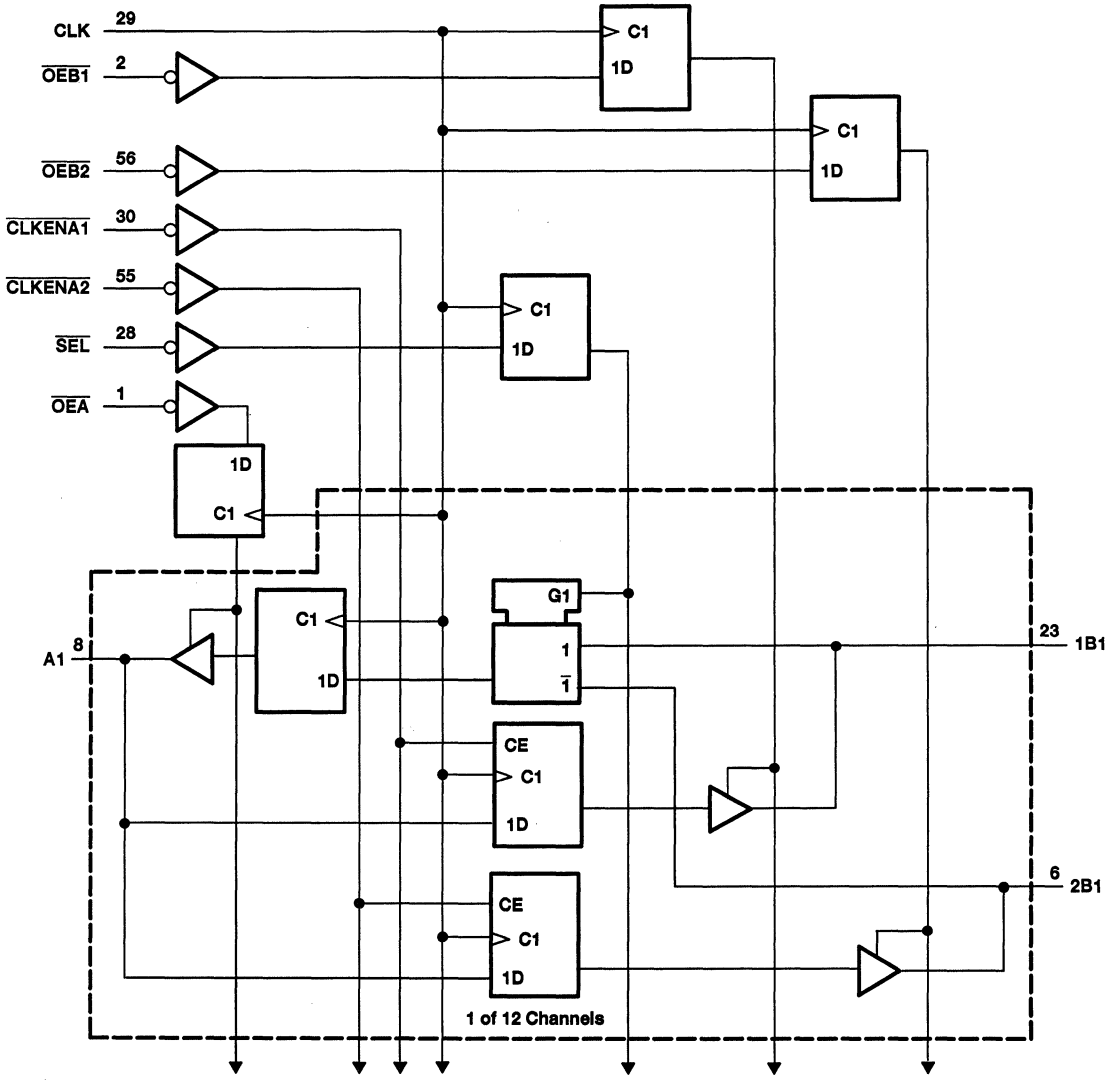
† Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS				OUTPUT
CLK	$\overline{SEL}$	1B	2B	A
X	H	X	X	A_0†
X	L	X	X	A_0†
↑	H	L	X	L
↑	H	H	X	H
↑	L	X	L	L
↑	L	X	H	H

† Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input-leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	135	0	135	0	135	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	A data before CLK↑	2		2		1.7		ns
		B data before CLK↑	2.2		2.1		1.8		
		$\overline{SEL}$ before CLK↑	1.6		1.6		1.3		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ before CLK↑	1		1.2		0.9		
		$\overline{OE}$ before CLK↑	1.5		1.6		1.3		
t_h	Hold time	A data after CLK↑	0.7		0.6		0.6		ns
		B data after CLK↑	0.7		0.6		0.6		
		$\overline{SEL}$ after CLK↑	1.1		0.7		0.7		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ after CLK↑	1		0.8		1.1		
		$\overline{OE}$ after CLK↑	0.8		0.8		0.8		

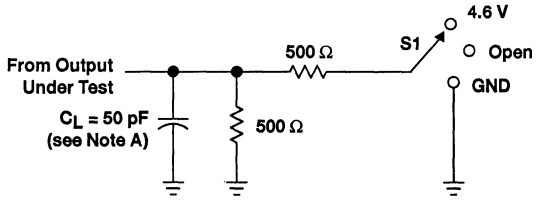
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			135		135		135		MHz
t_{pd}	CLK	B	1	8.8		7.3	1	6.2	ns
		A	1	7		5.8	1	5	
t_{en}	CLK	B	1	8.4		6.7	1	6.1	ns
		A	1	8.1		6.2	1	5.9	
t_{dis}	CLK	B	1.4	8.3		6.9	1	6.1	ns
		A	1.5	7.7		6.8	1	5.6	

operating characteristics, T_A = 25°C

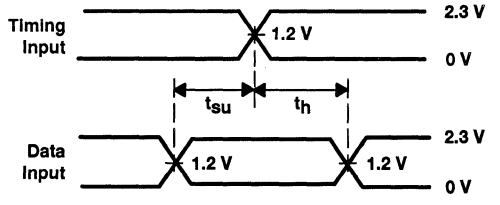
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	87	120	pF
		Outputs disabled		80.5	118	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

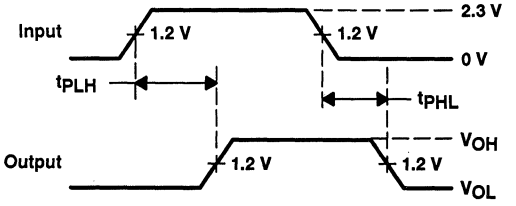


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

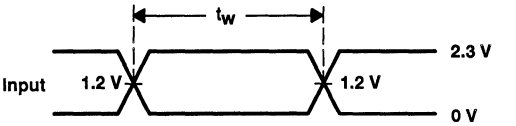
LOAD CIRCUIT



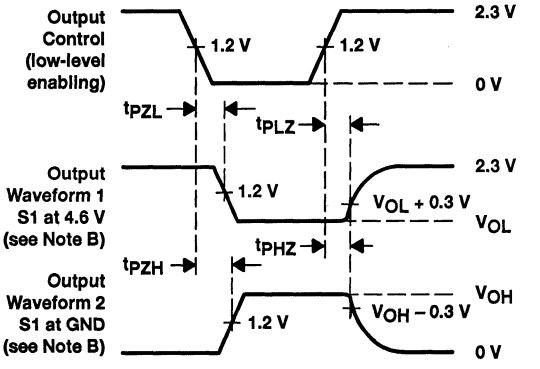
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

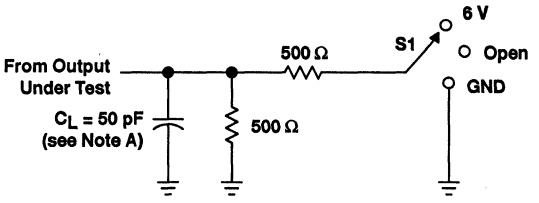


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

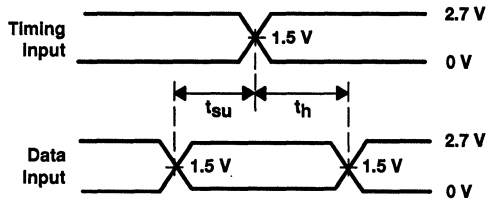
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

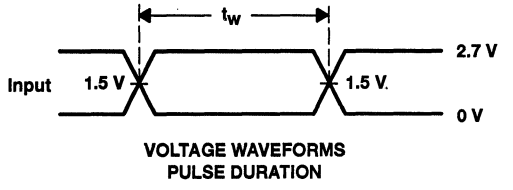


LOAD CIRCUIT

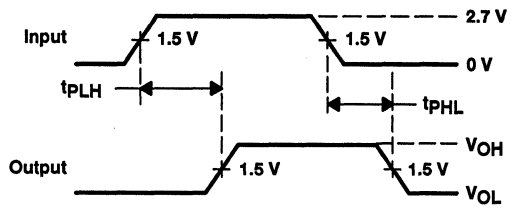
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



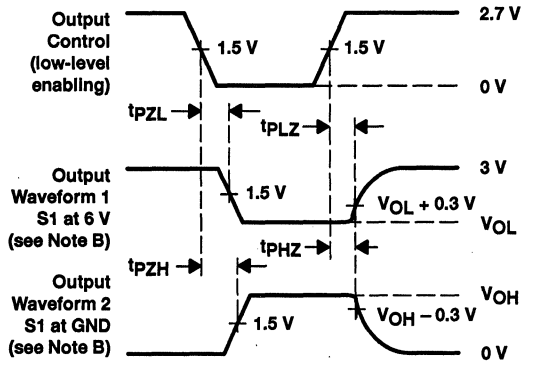
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



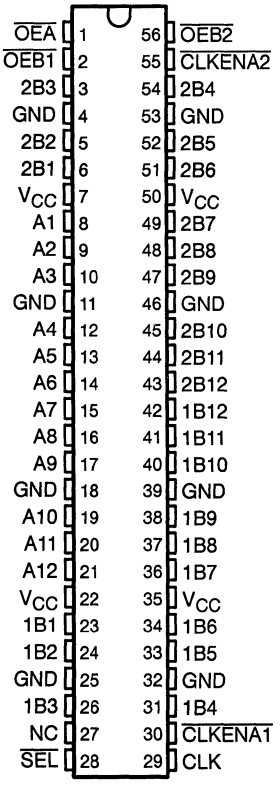
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **All Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 12-bit to 24-bit registered bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCHR162269 is used in applications where two separate ports must be multiplexed onto, or demultiplexed from, a single port. It is particularly suitable as an interface between synchronous DRAMs and high-speed microprocessors.

Data is stored in the internal B-port registers on the low-to-high transition of the clock (CLK) input when the appropriate clock enable ($\overline{\text{CLKENA}}$) inputs are low. Proper control of these inputs allows two sequential 12-bit words to be presented as a 24-bit word on the B port. For data transfer in the B-to-A direction, a single storage register is provided. The select ($\overline{\text{SEL}}$) line selects 1B or 2B data for the A outputs. The register on the A output permits the fastest possible data transfer, thus extending the period that the data is valid on the bus. The control terminals are registered so that all transactions are synchronous with CLK. Data flow is controlled by the active-low output enables ($\overline{\text{OEA}}$, $\overline{\text{OEB1}}$, and $\overline{\text{OEB2}}$).

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

All outputs are designed to sink up to12 mA and include 26-Ω resistors to reduce overshoot and undershoot.

The SN74ALVCHR162269 is characterized for operation from −40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

Function Tables

OUTPUT ENABLE

INPUTS			OUTPUTS	
CLK	$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
↑	H	H	Z	Z
↑	H	L	Z	Active
↑	L	H	Active	Z
↑	L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
L	H	↑	L	L	$2B_0$†
L	H	↑	H	H	$2B_0$†
L	L	↑	L	L	L
L	L	↑	H	H	H
H	L	↑	L	$1B_0$†	L
H	L	↑	H	$1B_0$†	H
H	H	X	X	$1B_0$†	$2B_0$†

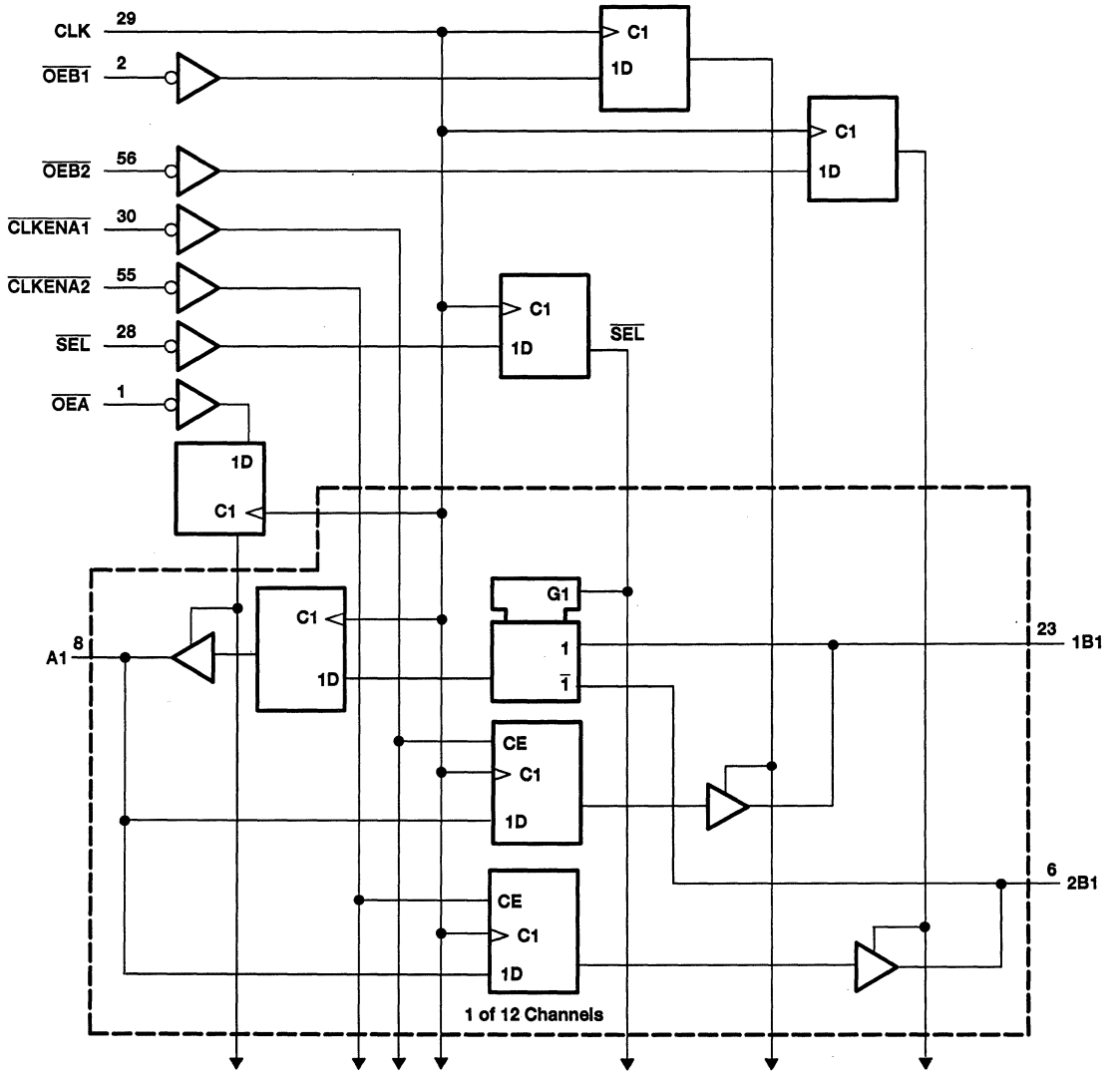
† Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS				OUTPUT
CLK	$\overline{SEL}$	1B	2B	A
X	H	X	X	A_0†
X	L	X	X	A_0†
↑	H	L	X	L
↑	H	H	X	H
↑	L	X	L	L
↑	L	X	H	H

† Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−6	mA
		V_{CC} = 2.7 V		−8	
		V_{CC} = 3 V		−12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –4 mA	V_{IH} = 1.7 V	2.3 V	1.9			
			V_{IH} = 2 V	2.7 V	2.2			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 4 mA	V_{IL} = 0.7 V	2.3 V			0.4	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	135	0	135	0	135	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	A data before CLK↑	2		2		1.7		ns
		B data before CLK↑	2.2		2.1		1.8		
		$\overline{SEL}$ before CLK↑	1.6		1.6		1.3		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ before CLK↑	1		1.2		0.9		
		$\overline{OE}$ before CLK↑	1.5		1.6		1.3		
t_h	Hold time	A data after CLK↑	0.7		0.6		0.6		ns
		B data after CLK↑	0.7		0.6		0.6		
		$\overline{SEL}$ after CLK↑	1.1		0.7		0.7		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ after CLK↑	1		0.8		1.1		
		$\overline{OE}$ after CLK↑	0.8		0.8		0.8		

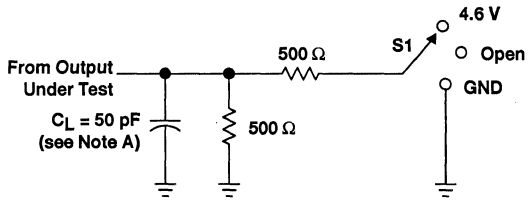
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			135		135		135		MHz
t_{pd}	CLK	B	1.5	9.2		7.9	1.6	6.7	ns
		A	1.5	7.4		6.4	1.6	5.5	
t_{en}	CLK	B	1.5	8.8		7.3	1.6	6.6	ns
		A	1.5	8.5		6.8	1.6	6.4	
t_{dis}	CLK	B	1.8	8.7		7.5	1.6	6.5	ns
		A	1.9	8.1		7.4	1.6	6	

operating characteristics, T_A = 25°C

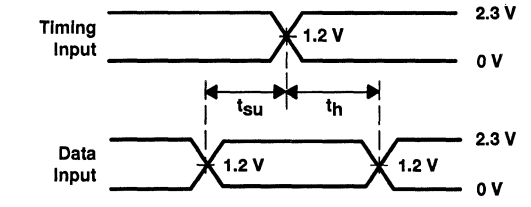
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	87	120	pF
		Outputs disabled		80.5	118	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

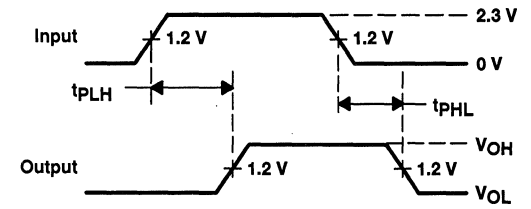


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

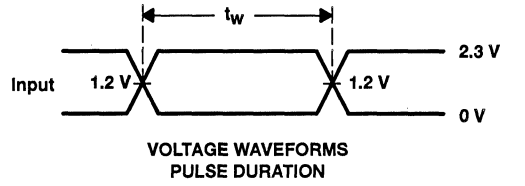
LOAD CIRCUIT



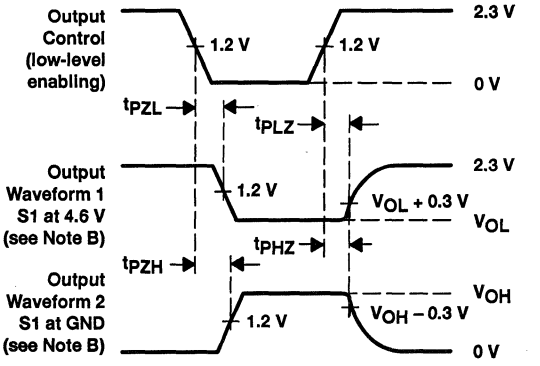
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

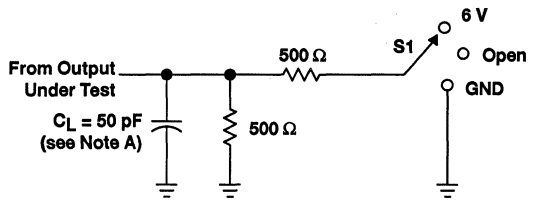


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

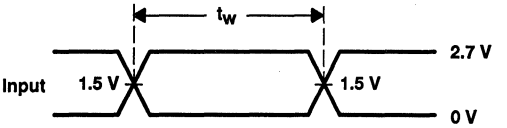
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

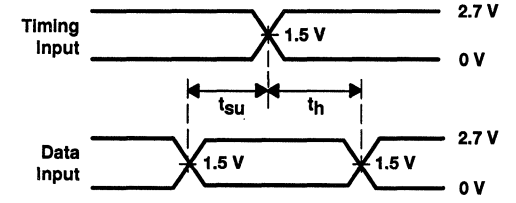


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

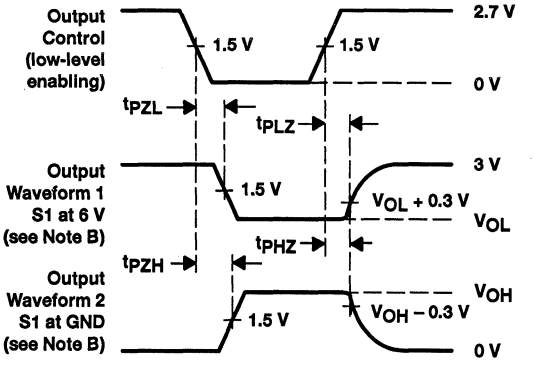
LOAD CIRCUIT



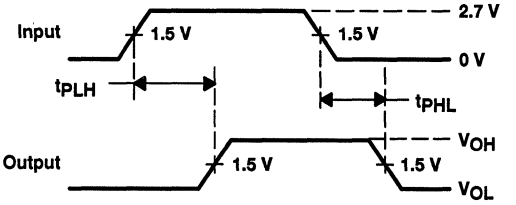
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES



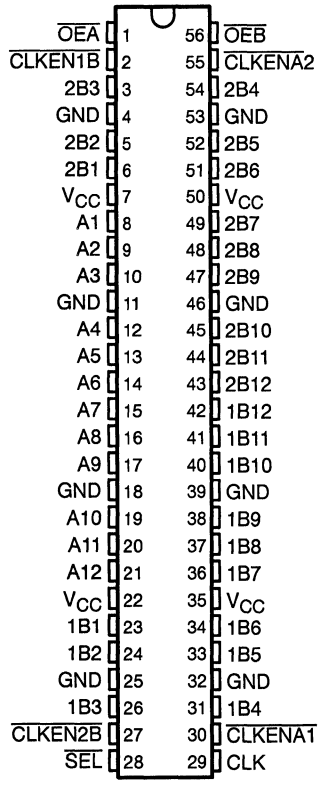
VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 12-bit to 24-bit registered bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16270 is used in applications where data must be transferred from a narrow high-speed bus to a wide lower-frequency bus.

The device provides synchronous data exchange between the two ports. Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input when the appropriate $\overline{\text{CLKEN}}$ inputs are low. The select ($\overline{\text{SEL}}$) line selects 1B or 2B data for the A outputs. For data transfer in the A-to-B direction, a two-stage pipeline is provided in the A-to-1B path, with a single storage register in the A to 2B path. Proper control of the $\overline{\text{CLKENA}}$ inputs allows two sequential 12-bit words to be presented synchronously as a 24-bit word on the B port. Data flow is controlled by the active-low output enables ($\overline{\text{OEA}}$, $\overline{\text{OEB}}$). The control terminals are registered to synchronize the bus direction changes with CLK.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16270 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16270 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

Function Tables

OUTPUT ENABLE

INPUTS			OUTPUTS	
CLK	$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
↑	H	H	Z	Z
↑	H	L	Z	Active
↑	L	H	Active	Z
↑	L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
L	H	↑	L	L†	$2B_0$‡
L	H	↑	H	H†	$2B_0$‡
L	L	↑	L	L†	L
L	L	↑	H	H†	H
H	L	↑	L	$1B_0$‡	L
H	L	↑	H	$1B_0$‡	H
H	H	X	X	$1B_0$‡	$2B_0$‡

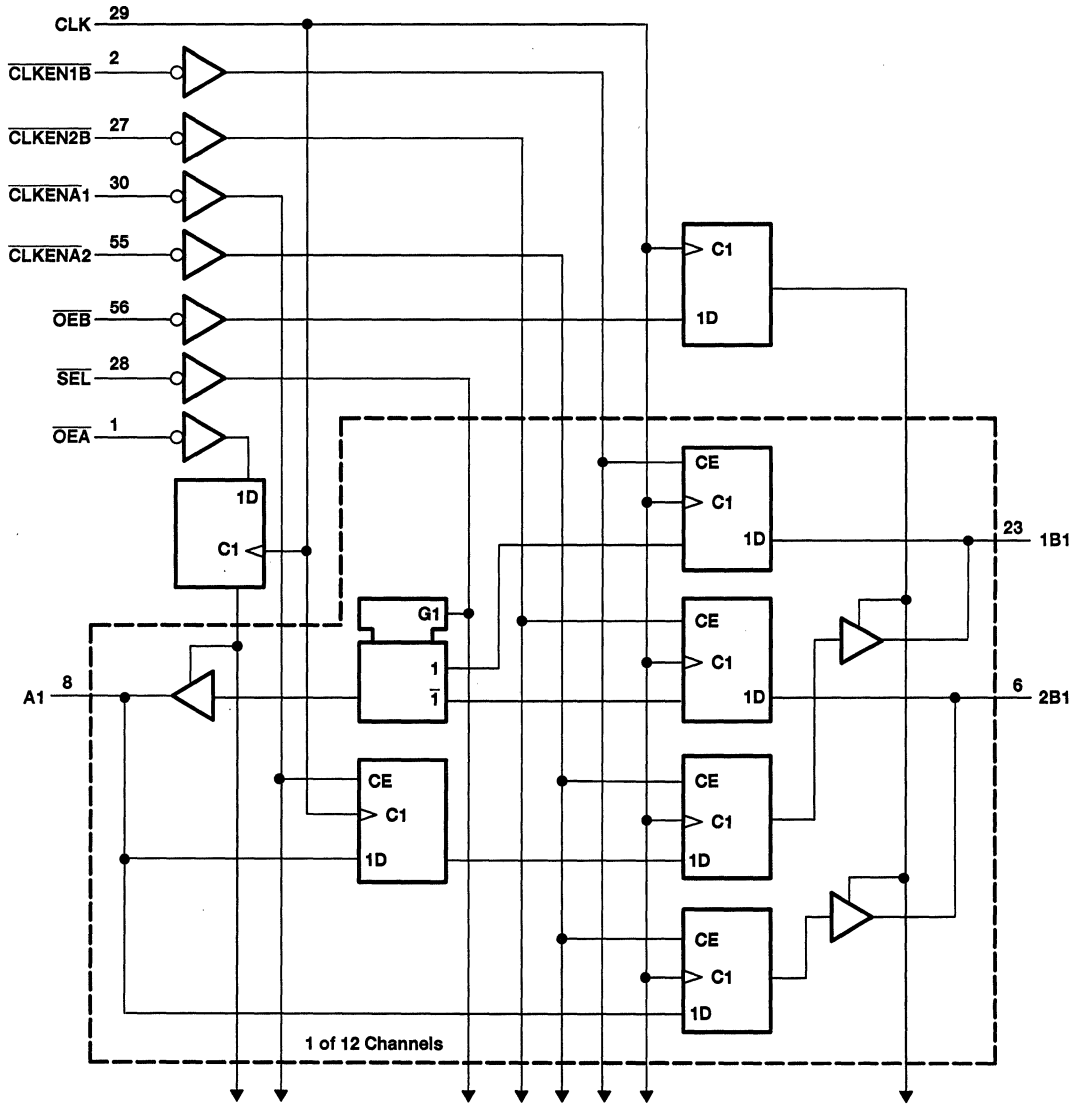
† Two CLK edges are needed to propagate data.
‡ Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS						OUTPUT
$\overline{CLKEN1B}$	$\overline{CLKEN2B}$	CLK	$\overline{SEL}$	1B	2B	A
H	X	X	H	X	X	A_0‡
X	H	X	L	X	X	A_0‡
L	X	↑	H	L	X	L
L	X	↑	H	H	X	H
X	L	↑	L	X	L	L
X	L	↑	L	X	H	H

‡ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	A data before CLK↑	4.1		3.8		3.1		ns
		B data before CLK↑	0.9		1.2		0.9		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ before CLK↑	3.5		3.2		2.7		
		$\overline{CLKEN1B}$ or $\overline{CLKEN2B}$ before CLK↑	3.4		3		2.6		
		$\overline{OE}$ data before CLK↑	4.4		3.9		3.2		
t_h	Hold time	A data after CLK↑	0		0		0.2		ns
		B data after CLK↑	1.4		1		1.7		
		$\overline{CLKENA1}$ or $\overline{CLKENA2}$ after CLK↑	0		0.1		0.3		
		$\overline{CLKEN1B}$ or $\overline{CLKEN2B}$ after CLK↑	0		0		0.6		
		$\overline{OE}$ after CLK↑	0		0		0.1		

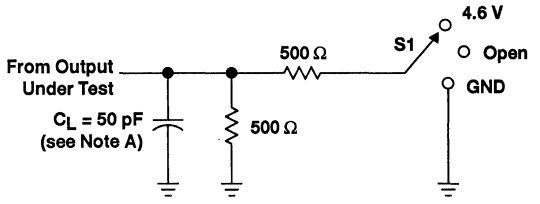
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	B	2	6.5		5.8	1.1	5.1	ns
	CLK	A	1.7	6		5.4	1	4.7	
	$\overline{SEL}$	A	1.9	6.8		6.4	1	5.5	
t_{en}	CLK	A or B	1.6	7.5		6.8	1	6	ns
t_{dis}	CLK	A or B	2.6	7.4		6.5	1.1	5.8	ns

operating characteristics, T_A = 25°C

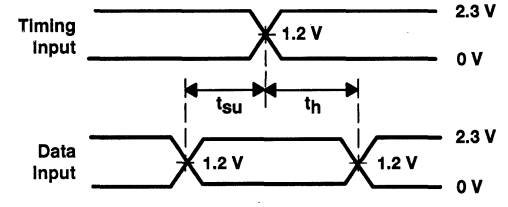
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	87	120	pF
		Outputs disabled		80.5	118	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

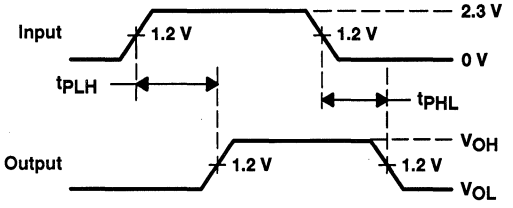


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

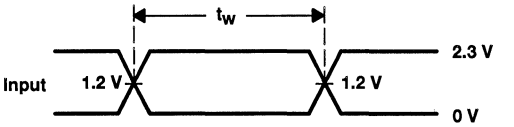
LOAD CIRCUIT



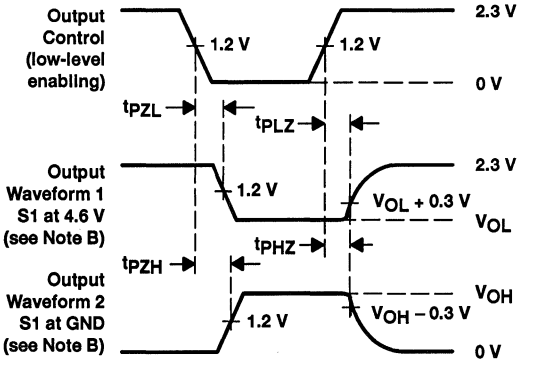
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

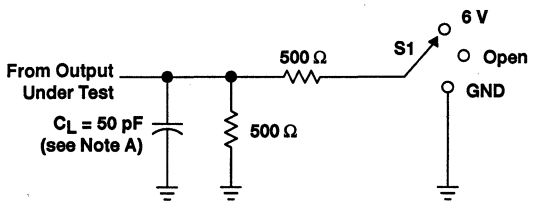


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

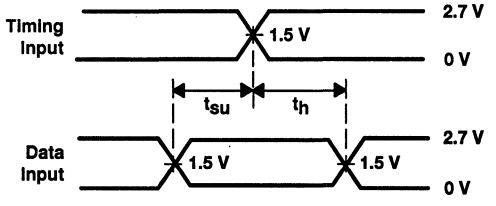
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

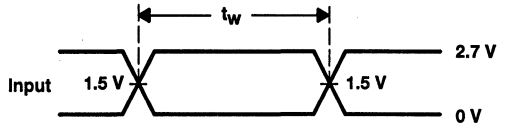


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

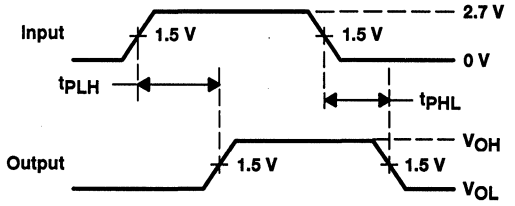
LOAD CIRCUIT



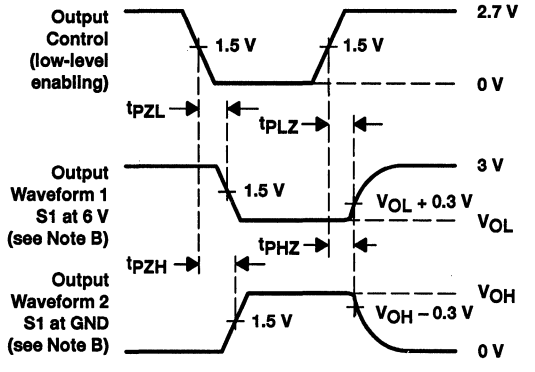
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



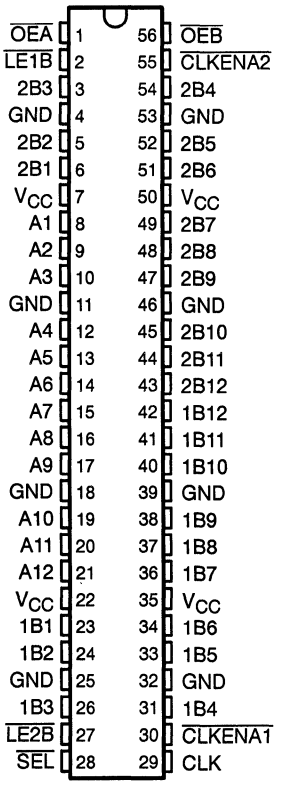
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 12-bit to 24-bit bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16271 is intended for applications where two separate datapaths must be multiplexed onto, or demultiplexed from, a single datapath. This device is particularly suitable as an interface between conventional DRAMs and high-speed microprocessors.

A data is stored in the internal A-to-B registers on the low-to-high transition of the clock (CLK) input, provided that the $\overline{CLKENA}$ inputs are low. Proper control of these inputs allows two sequential 12-bit words to be presented as a 24-bit word on the B port.

Transparent latches in the B-to-A path allow asynchronous operation in order to maximize memory access throughput. These latches transfer data when the latch-enable ($\overline{LE}$) inputs are low. The select ($\overline{SEL}$) line selects 1B or 2B data for the A outputs. Data flow is controlled by the active-low output enables ($\overline{OEA}$, $\overline{OEB}$).

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16271 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

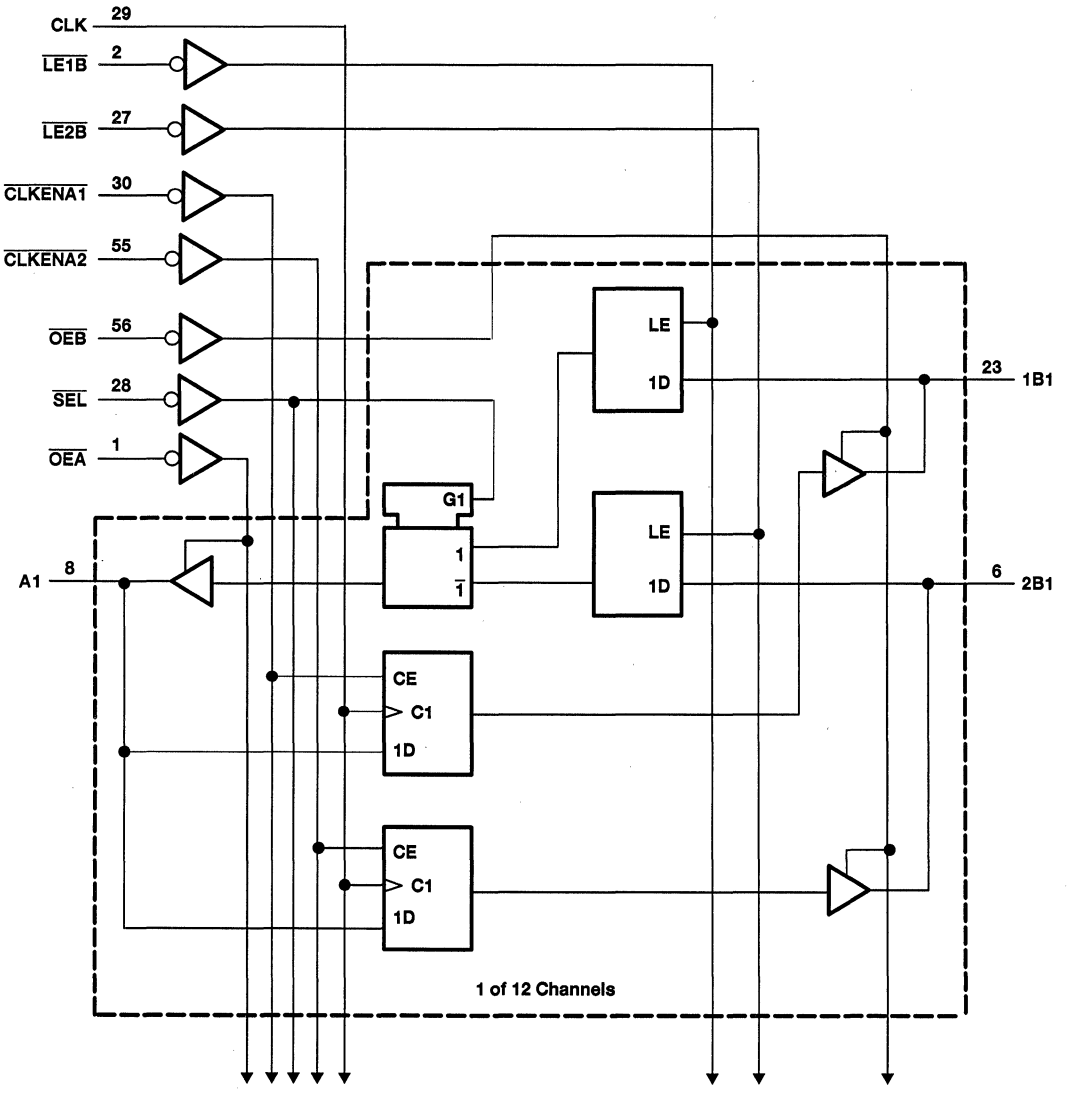
The SN74ALVCH16271 is characterized for operation from –40°C to 85°C.

PRODUCT PREVIEW

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

PRODUCT PREVIEW

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Function Tables

OUTPUT ENABLE

INPUTS		OUTPUTS	
$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
H	H	Z	Z
H	L	Z	Active
L	H	Active	Z
L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
H	H	X	X	$1B_0$†	$2B_0$†
L	X	↑	L	L	X
L	X	↑	H	H	X
X	L	↑	L	X	L
X	L	↑	H	A_0	H

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS				OUTPUT
$\overline{LE}$	$\overline{SEL}$	1B	2B	A
H	X	X	X	A_0†
H	X	X	X	A_0†
L	H	L	X	L
L	H	H	X	H
L	L	X	L	L
L	L	X	H	H

† Output level before the indicated steady-state input conditions were established

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

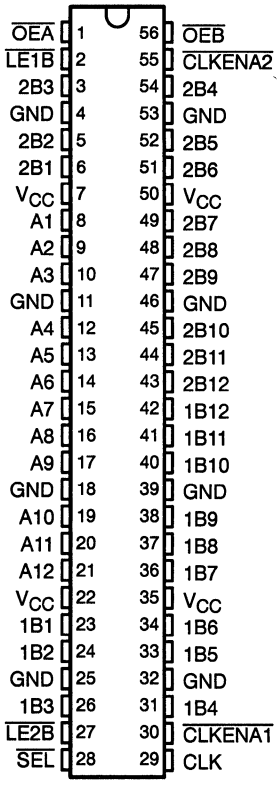
electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 12-bit to 24-bit bus exchanger is designed for 2.3-V to 3.3-V V_{CC} operation.

The SN74ALVCH16272 is intended for applications where two separate datapaths must be multiplexed onto, or demultiplexed from, a single datapath. This device is particularly suitable as an interface between conventional DRAMs and high-speed microprocessors.

Data from the A inputs is stored in the internal registers on the low-to-high transition of the clock (CLK) input, when the $\overline{\text{CLKENA}}$ inputs are low. A two-stage pipeline is provided in each of the A-to-1B and A-to-2B paths to serve as a shallow write buffer.

Transparent latches are provided in the B-to-A path to allow asynchronous operation to maximize memory access throughput. These latches transfer data when the latch-enable ($\overline{\text{LE}}$) inputs are low. The select ($\overline{\text{SEL}}$) line selects 1B or 2B data for the A outputs. Data flow is controlled by the active-low output enables ($\overline{\text{OEA}}$, $\overline{\text{OEB}}$).

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16272 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

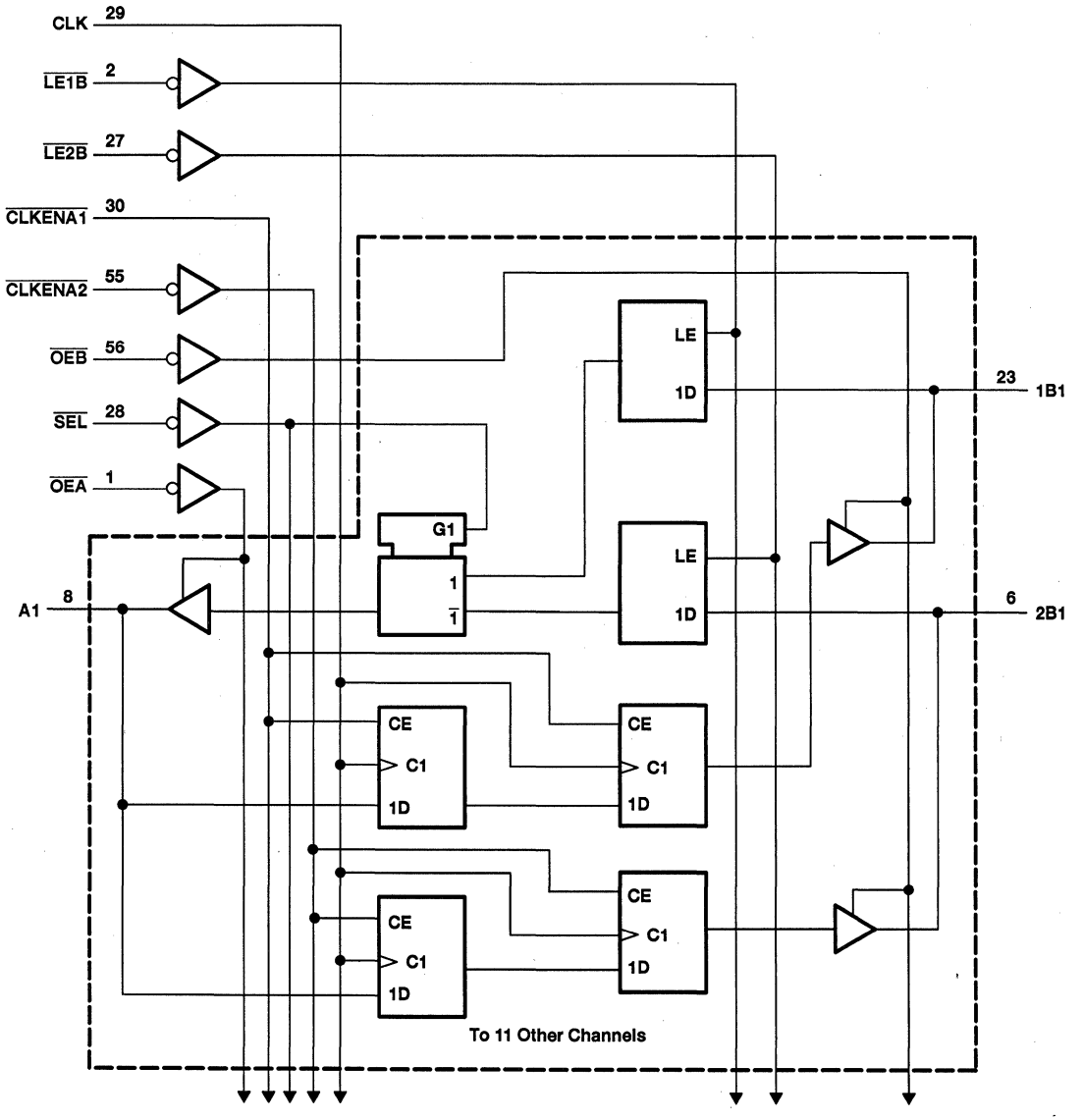
The SN74ALVCH16272 is characterized for operation from –40°C to 85°C.

PRODUCT PREVIEW

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

PRODUCT PREVIEW

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Function Tables

OUTPUT ENABLE

INPUTS		OUTPUTS	
$\overline{OEA}$	$\overline{OEB}$	A	1B, 2B
H	H	Z	Z
H	L	Z	Active
L	H	Active	Z
L	L	Active	Active

A-TO-B STORAGE ($\overline{OEB}$ = L)

INPUTS				OUTPUTS	
$\overline{CLKENA1}$	$\overline{CLKENA2}$	CLK	A	1B	2B
H	H	X	X	$1B_0$†	$2B_0$†
L	X	↑	L	L†	X
L	X	↑	H	H†	X
X	L	↑	L	X	L
X	L	↑	H	A_0	H

† Two CLK edges are needed to propagate data.

B-TO-A STORAGE ($\overline{OEA}$ = L)

INPUTS				OUTPUT
$\overline{LE}$	$\overline{SEL}$	1B	2B	A
H	X	X	X	A_0‡
H	X	X	X	A_0‡
L	H	L	X	L
L	H	H	X	H
L	L	X	L	L
L	L	X	H	H

‡ Output level before the indicated steady-state input conditions were established

PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

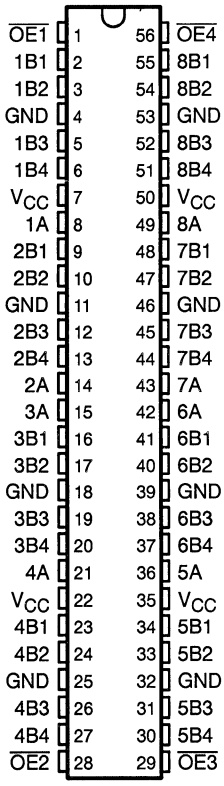
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

PRODUCT PREVIEW

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 1-bit-to-4-bit address driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16344 is used in applications where four separate memory locations must be addressed by a single address.

Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The SN74ALVCH16344 is packaged in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVCH16344 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

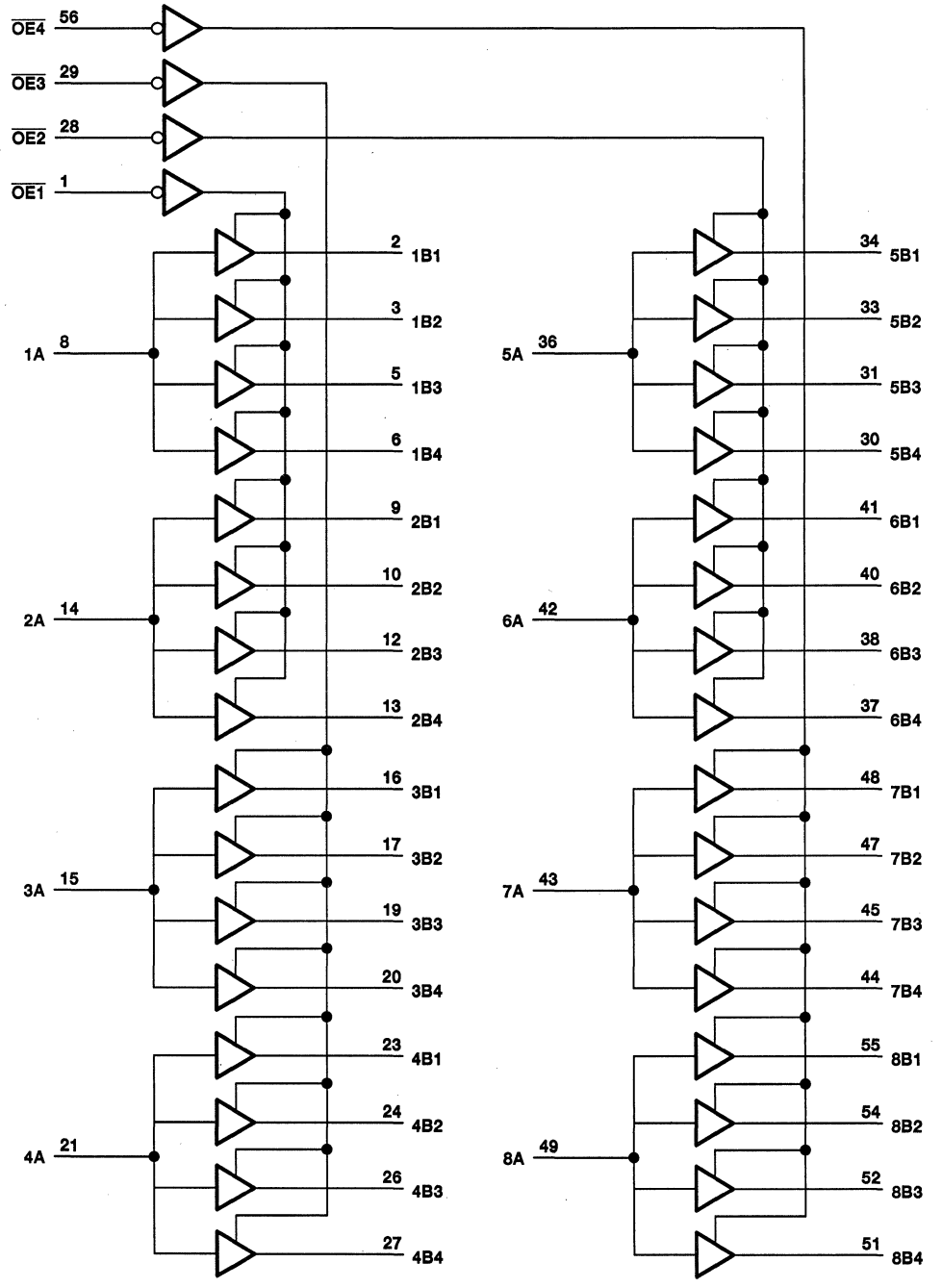
INPUTS		OUTPUT
$\overline{OE}$	A	Bn
L	H	H
L	L	L
H	H	Z

ADVANCE INFORMATION

EPIC, and Widebus are trademarks of Texas Instruments Incorporated.

ADVANCE INFORMATION

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

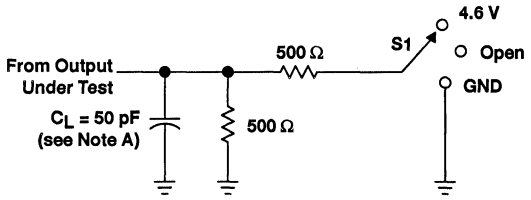
ADVANCE INFORMATION

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_I = V_{CC} or GND		3.3 V		7		pF

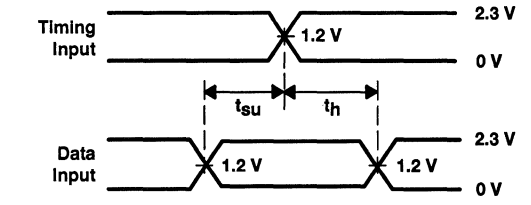
† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

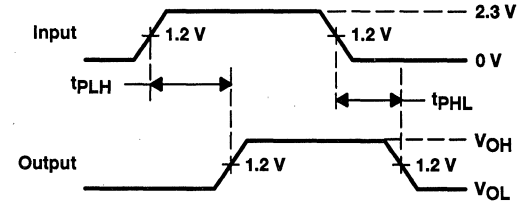


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

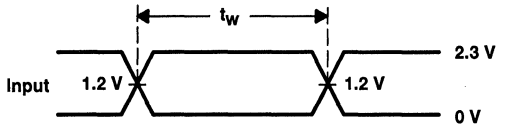
LOAD CIRCUIT



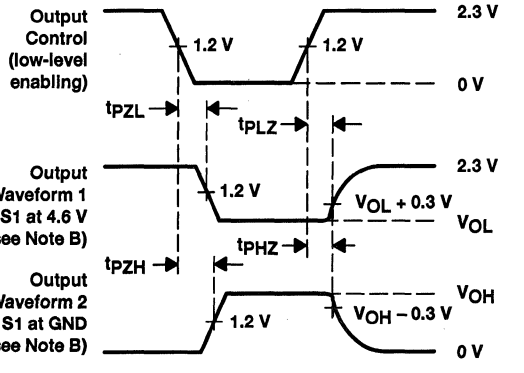
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

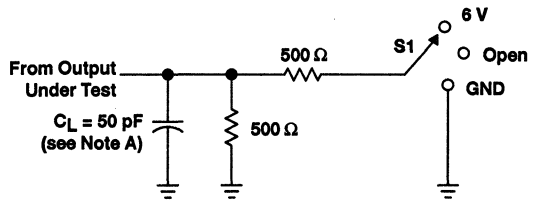
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

ADVANCE INFORMATION

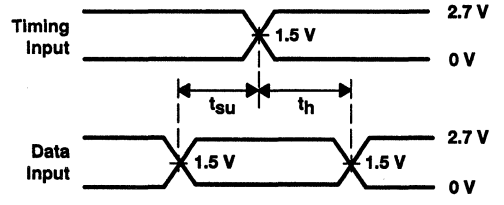
ADVANCE INFORMATION

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

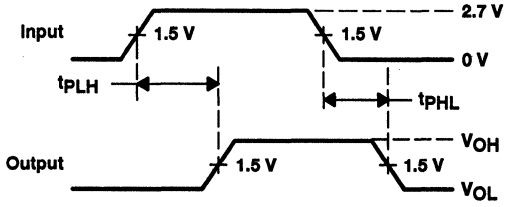


LOAD CIRCUIT

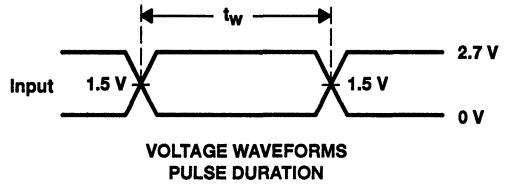
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



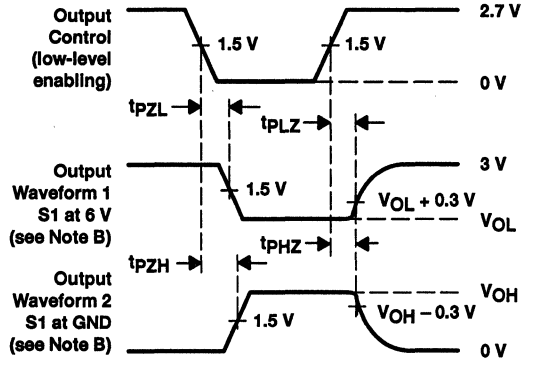
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



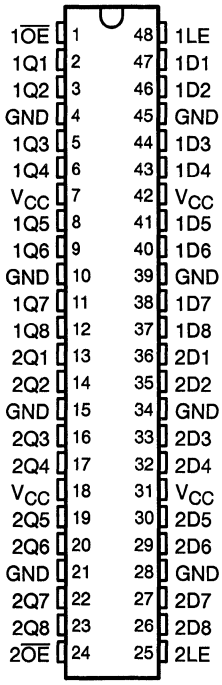
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-833C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit transparent D-type latch is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16373 is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. This device can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components. $\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16373 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

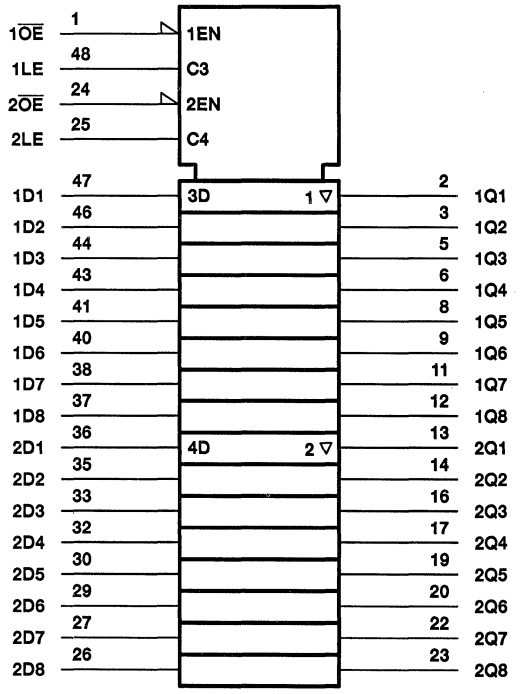
The SN74ALVCH16373 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 8-bit section)

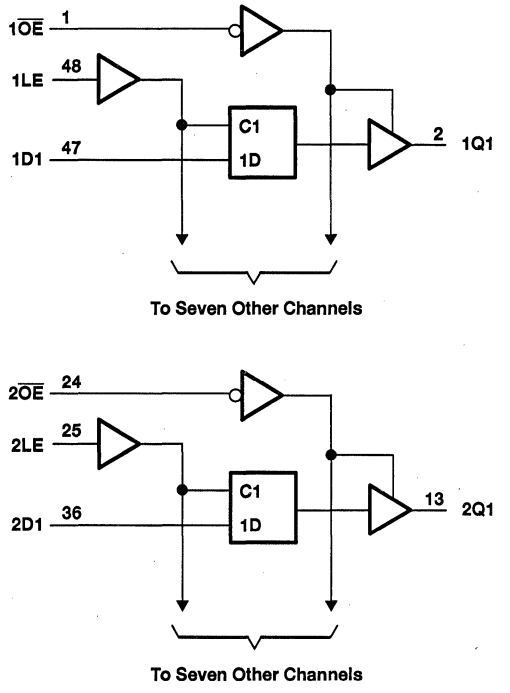
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
		I_{OL} = 12 mA	V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE↓	1		1		1.1		ns
t_h	Hold time, data after LE↓	1.5		1.7		1.4		ns

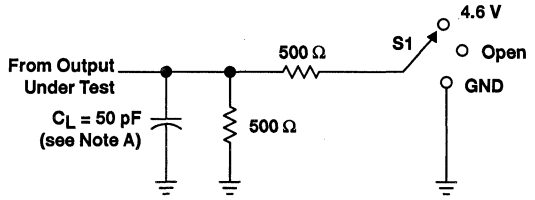
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1	5.1		4.3	1.1	3.6	ns
	LE	Q	1	5.5		4.6	1	3.9	
t_{en}	$\overline{OE}$	Q	1	6.5		5.7	1	4.7	ns
t_{dis}	$\overline{OE}$	Q	1.9	5.3		4.5	1.4	4.1	ns

operating characteristics, T_A = 25°C

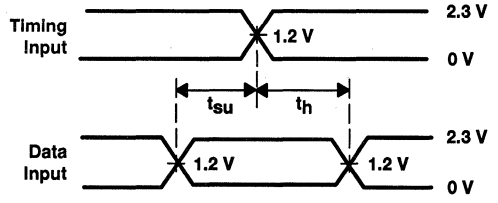
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	19	22	pF
		Outputs disabled		4	5	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

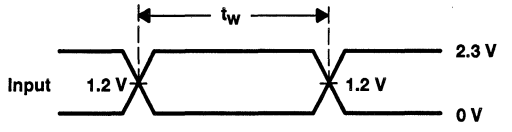


LOAD CIRCUIT

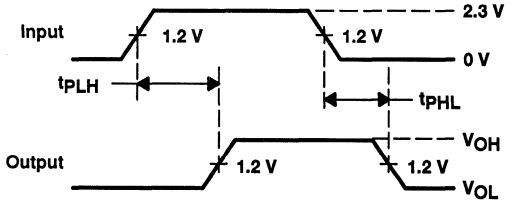
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND



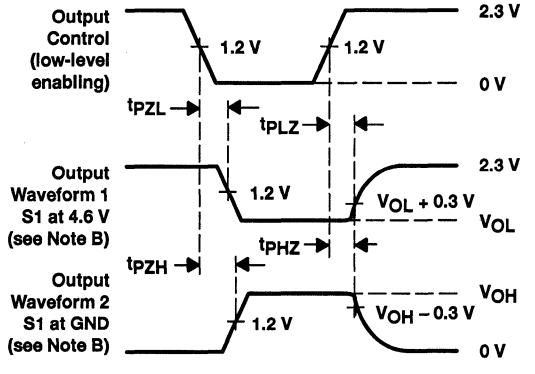
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

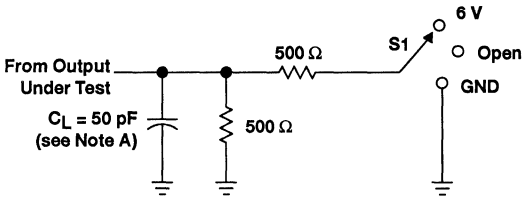


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

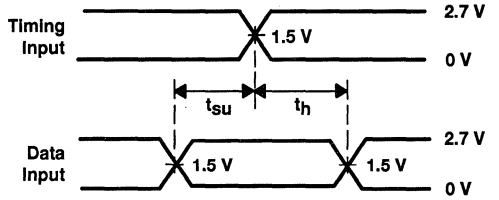
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

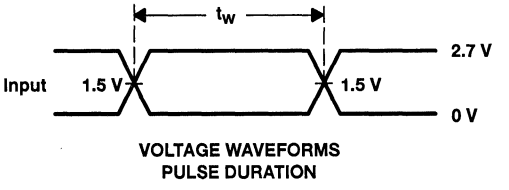


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

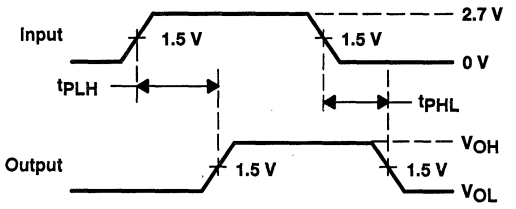
LOAD CIRCUIT



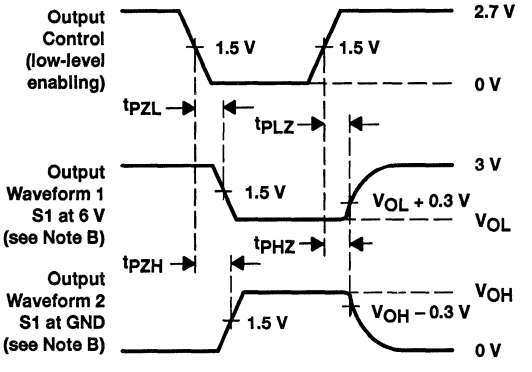
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



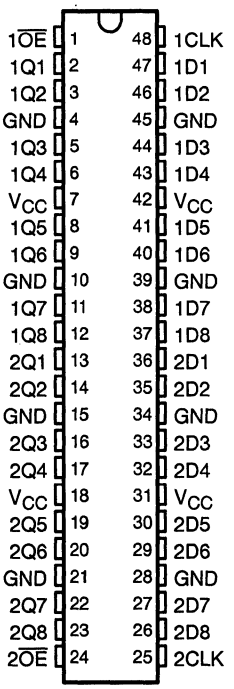
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-833C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold On Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit edge-triggered D-type flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16374 is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (CLK) input, the Q outputs of the flip-flop take on the logic levels set up at the data (D) inputs. $\overline{OE}$ can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components. $\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16374 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

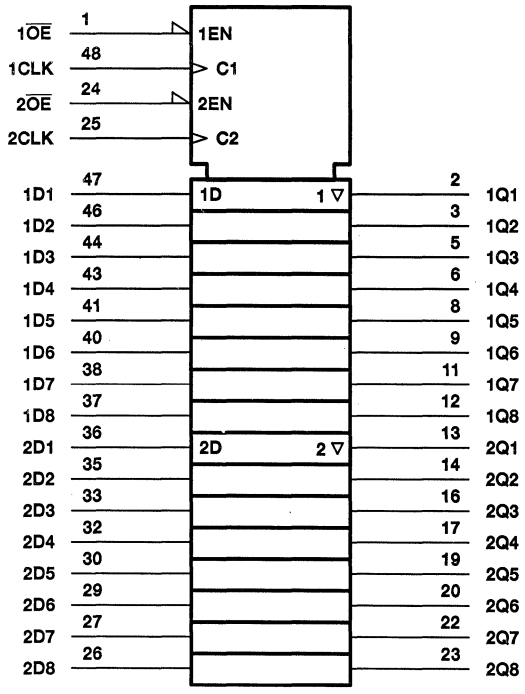
The SN74ALVCH16374 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each flip-flop)

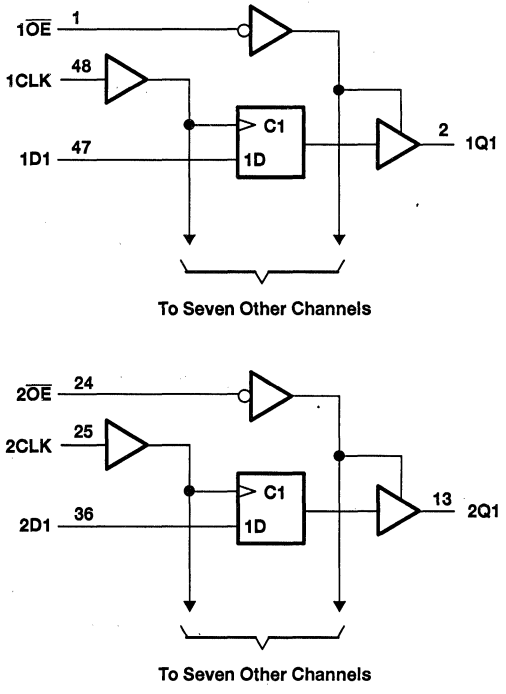
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA,	V_{IL} = 0.7 V	2.3 V			0.7	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
	Data Inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	2.1		2.2		1.9		ns
t_h	Hold time, data after CLK↑	0.6		0.5		0.5		ns

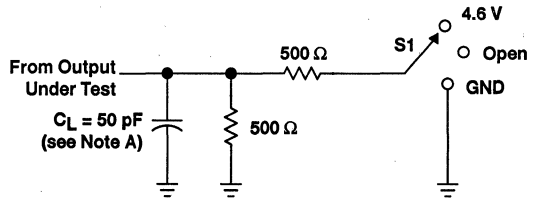
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	5.9		4.9	1	4.2	ns
t_{en}	CLK	Q	1	6.7		5.9	1	4.8	ns
t_{dis}	CLK	Q	1.7	5.5		4.7	1.2	4.3	ns

operating characteristics, T_A = 25°C

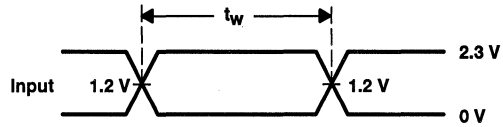
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	31	30	pF
		Outputs disabled		16	18	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

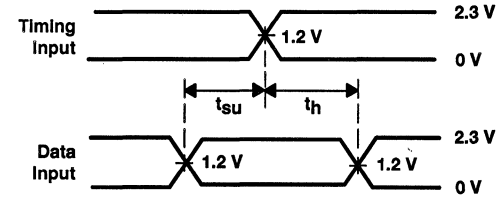


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

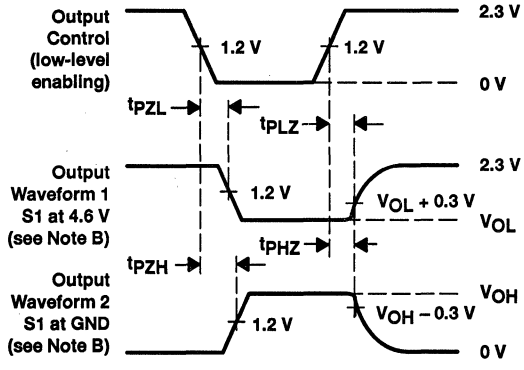
LOAD CIRCUIT



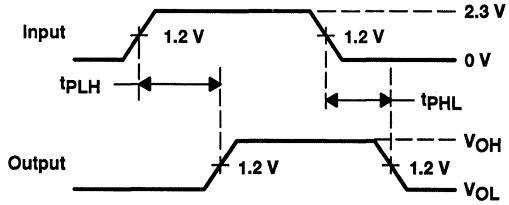
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

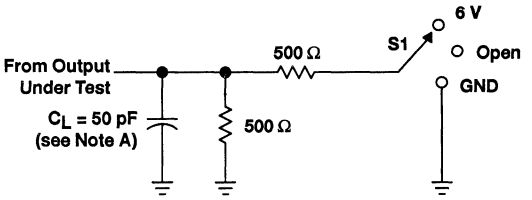


VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

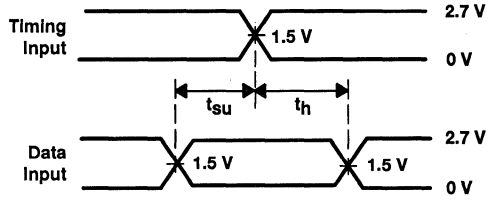
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

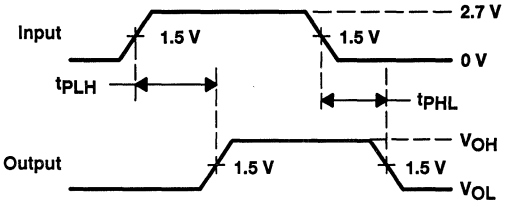


LOAD CIRCUIT

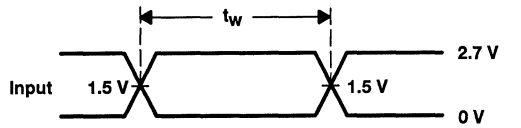
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



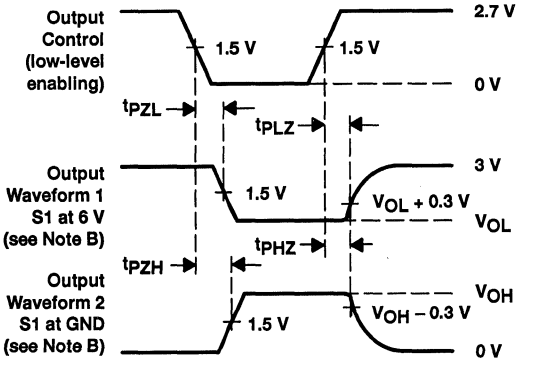
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



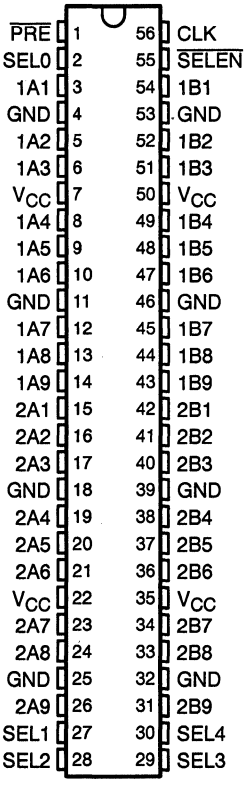
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus+*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBE*™ (Universal Bus Exchanger) Allows Synchronous Data Exchange**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 9-bit, 4-port universal bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16409 allows synchronous data exchange between four different buses.

Data flow is controlled by the select (SEL0–SEL4) inputs. A data-flow state is stored on the rising edge of the clock (CLK) input if the select-enable ($\overline{SELEN}$) input is low. Once a data-flow state has been established, data is stored in the flip-flop on the rising edge of CLK if $\overline{SELEN}$ is high.

The data-flow control logic is designed to allow glitch-free data transmission.

To ensure the high-impedance state during power up or power down, $\overline{SELEN}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

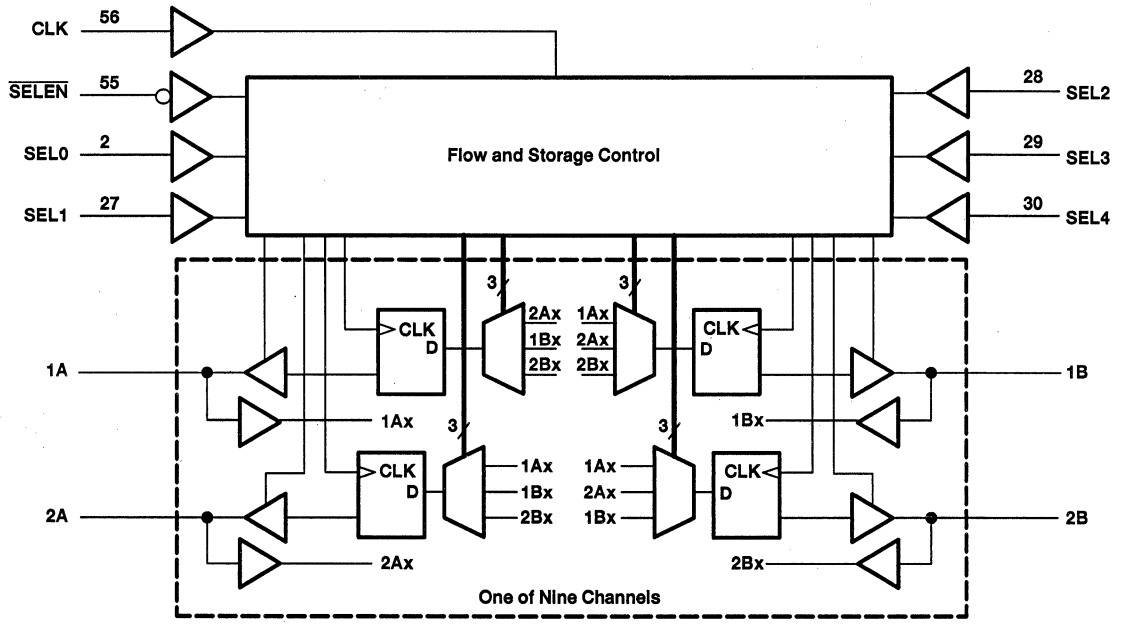
Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16409 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16409 is characterized for operation from –40°C to 85°C.

Widebus+, EPIC, and UBE are trademarks of Texas Instruments Incorporated.

logic diagram (positive logic)



FUNCTION TABLE

INPUTS		OUTPUT
CLK	SEND PORT	RECEIVE PORT
X	X	B_0†
X	L	L
X	H	H
↑	L	L
↑	H	H
H	X	B_0†
L	X	B_0†

† Output level before the indicated steady-state input conditions were established

DATA-FLOW CONTROL FUNCTION TABLE

INPUTS							DATA FLOW
$\overline{SELEN}$	CLK	SEL0	SEL1	SEL2	SEL3	SEL4	
H	↑	X	X	X	X	X	No change
L	↑	0	0	0	0	0	None, all I/Os off
L	↑	0	0	0	0	1	Not used
L	↑	0	0	0	1	0	Not used
L	↑	0	0	0	1	1	Not used
L	↑	0	0	1	0	0	Not used
L	↑	0	0	1	0	1	Not used
L	↑	0	0	1	1	0	Not used
L	↑	0	0	1	1	1	Not used
L	↑	0	1	0	0	0	2A to 1A and 1B to 2B
L	↑	0	1	0	0	1	2A to 1A
L	↑	0	1	0	1	0	2B to 1B
L	↑	0	1	0	1	1	2A to 1A and 2B to 1B
L	↑	0	1	1	0	0	1A to 2A and 1B to 2B
L	↑	0	1	1	0	1	1A to 2A
L	↑	0	1	1	1	0	1B to 2B
L	↑	0	1	1	1	1	1A to 2A and 2B to 1B
L	↑	1	0	0	0	0	1A to 1B and 2B to 2A
L	↑	1	0	0	0	1	1A to 1B
L	↑	1	0	0	1	0	2A to 2B
L	↑	1	0	0	1	1	1A to 1B and 2A to 2B
L	↑	1	0	1	0	0	1B to 1A and 2A to 2B
L	↑	1	0	1	0	1	1B to 1A
L	↑	1	0	1	1	0	2B to 2A
L	↑	1	0	1	1	1	1B to 1A and 2B to 2A
L	↑	1	1	0	0	0	2B to 1A and 2A to 1B
L	↑	1	1	0	0	1	1B to 2A
L	↑	1	1	0	1	0	2B to 1A
L	↑	1	1	0	1	1	2B to 1A and 1B to 2A
L	↑	1	1	1	0	0	1A to 2B and 1B to 2A
L	↑	1	1	1	0	1	1A to 2B
L	↑	1	1	1	1	0	2A to 1B
L	↑	1	1	1	1	1	1A to 2B and 2A to 1B

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA,		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	120	0	120	MHz
t_w	Pulse duration, CLK high or low		4.2		4.2		3		ns
t_{su}	Setup time	A or B before CLK↑	1.9		1.9		1.4		ns
		SEL before CLK↑	5.1		4.2		3.5		
		$\overline{SELEN}$ before CLK↑	2.5		2.5		1.8		
		$\overline{PRE}$ before CLK↑	1		1		0.7		
t_h	Hold time	A or B after CLK↑	0.8		0.8		1		ns
		SEL after CLK↑	0		0		0		
		$\overline{SELEN}$ after CLK↑	0.5		0.5		0.8		

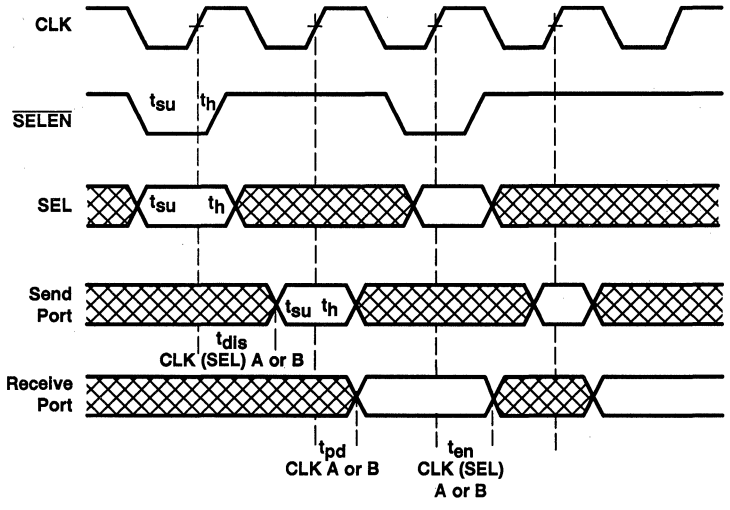
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		120		120		MHz
t_{pd}	CLK (A or B)	B or A	2	6.6		5.7	1.5	5.1	ns
t_{en}	CLK (SEL)	A or B	2.5	7.4		6.3	2	5.7	ns
t_{dis}	CLK (SEL)	A or B	3	7.3		6	2	5.7	ns
t_{dis}	$\overline{PRE}$	A or B	3.5	7.7		6.5	2.5	6.1	ns

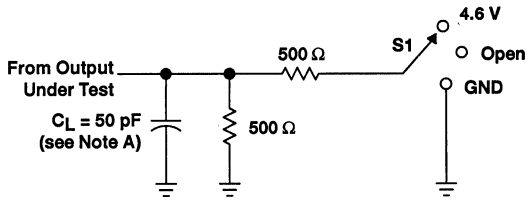
operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	60	60	pF
		Outputs disabled				

timing diagram

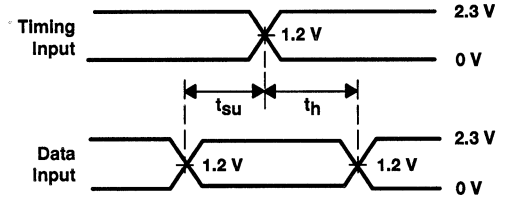


PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

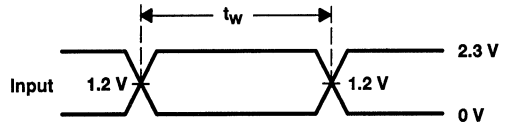


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

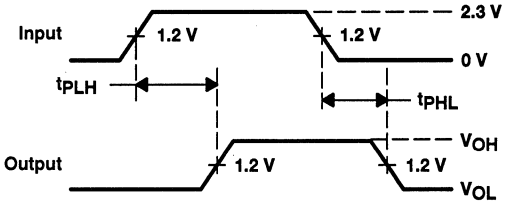
LOAD CIRCUIT



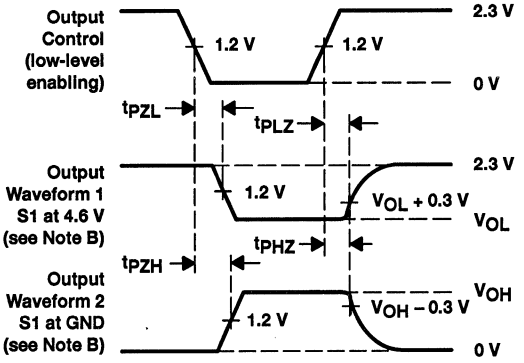
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

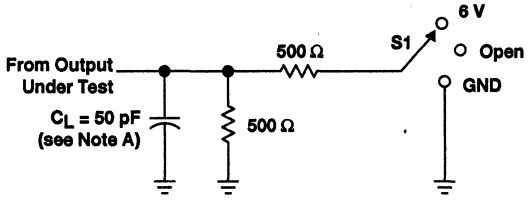


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

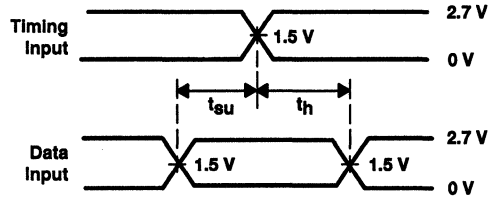
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

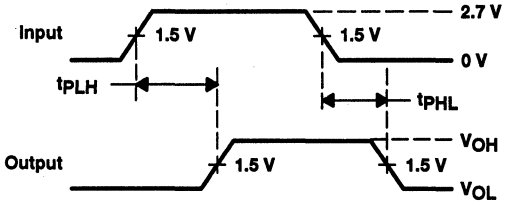


LOAD CIRCUIT

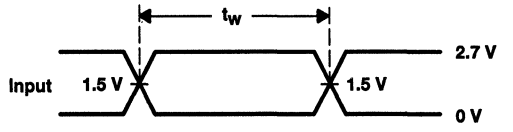
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



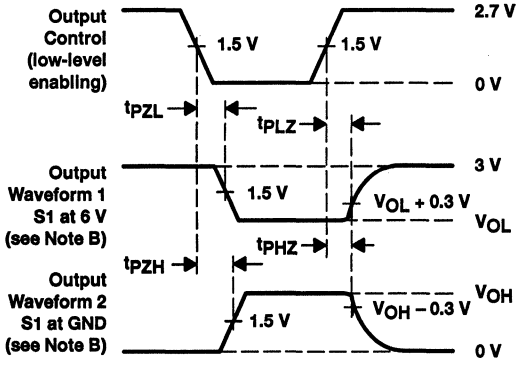
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



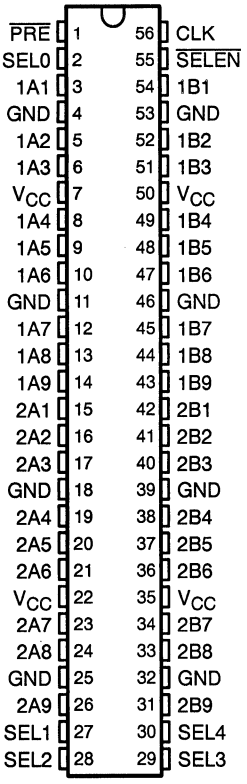
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus+*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **B-Port Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors are Required**
- ***UBE*™ (Universal Bus Exchanger) Allows Synchronous Data Exchange**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 9-bit 4-port universal bus exchanger is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCHR162409 allows synchronous data exchange between four different buses. Data flow is controlled by the select (SEL0–SEL4) inputs. A data-flow state is stored on the rising edge of the clock (CLK) input, provided the select-enable ($\overline{SELEN}$) input is low. Once a data-flow state is established, data is stored in the flip-flop on the rising edge of the CLK, provided $\overline{SELEN}$ is high.

The data-flow control logic is designed to allow glitch-free data transmission.

The B outputs, which are designed to sink up to 12 mA, include 26-Ω resistors to reduce overshoot and undershoot.

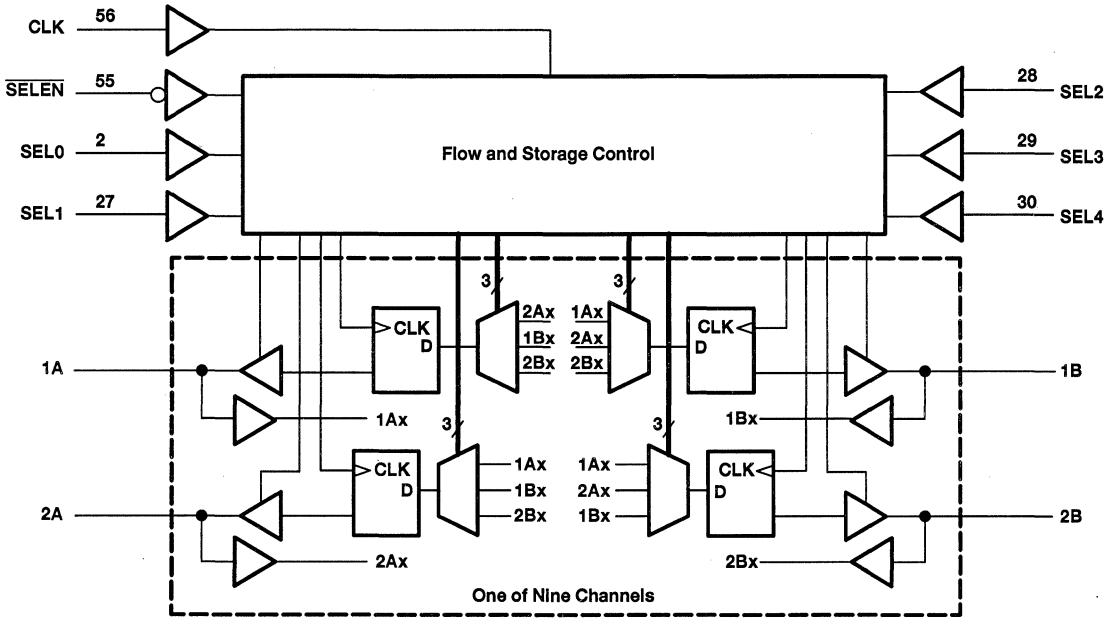
To ensure the high-impedance state during power up or power down, $\overline{SELEN}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCHR162409 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCHR162409 is characterized for operation from –40°C to 85°C.

logic diagram (positive logic)



FUNCTION TABLE

INPUTS		OUTPUT
CLK	SEND PORT	RECEIVE PORT
X	X	B_0†
X	L	L
X	H	H
↑	L	L
↑	H	H
H	X	B_0†
L	X	B_0†

† Output level before the indicated steady-state input conditions were established

DATA-FLOW CONTROL FUNCTION TABLE

INPUTS							DATA FLOW
$\overline{SELEN}$	CLK	SEL0	SEL1	SEL2	SEL3	SEL4	
H	↑	X	X	X	X	X	No change
L	↑	0	0	0	0	0	None, all I/Os off
L	↑	0	0	0	0	1	Not used
L	↑	0	0	0	1	0	Not used
L	↑	0	0	0	1	1	Not used
L	↑	0	0	1	0	0	Not used
L	↑	0	0	1	0	1	Not used
L	↑	0	0	1	1	0	Not used
L	↑	0	0	1	1	1	Not used
L	↑	0	1	0	0	0	2A to 1A and 1B to 2B
L	↑	0	1	0	0	1	2A to 1A
L	↑	0	1	0	1	0	2B to 1B
L	↑	0	1	0	1	1	2A to 1A and 2B to 1B
L	↑	0	1	1	0	0	1A to 2A and 1B to 2B
L	↑	0	1	1	0	1	1A to 2A
L	↑	0	1	1	1	0	1B to 2B
L	↑	0	1	1	1	1	1A to 2A and 2B to 1B
L	↑	1	0	0	0	0	1A to 1B and 2B to 2A
L	↑	1	0	0	0	1	1A to 1B
L	↑	1	0	0	1	0	2A to 2B
L	↑	1	0	0	1	1	1A to 1B and 2A to 2B
L	↑	1	0	1	0	0	1B to 1A and 2A to 2B
L	↑	1	0	1	0	1	1B to 1A
L	↑	1	0	1	1	0	2B to 2A
L	↑	1	0	1	1	1	1B to 1A and 2B to 2A
L	↑	1	1	0	0	0	2B to 1A and 2A to 1B
L	↑	1	1	0	0	1	1B to 2A
L	↑	1	1	0	1	0	2B to 1A
L	↑	1	1	0	1	1	2B to 1A and 1B to 2A
L	↑	1	1	1	0	0	1A to 2B and 1B to 2A
L	↑	1	1	1	0	1	1A to 2B
L	↑	1	1	1	1	0	2A to 1B
L	↑	1	1	1	1	1	1A to 2B and 2A to 1B

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		
		V_{CC} = 2.3 V to 2.7 V	1.7		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−6	mA
		V_{CC} = 2.7 V		−8	mA
		V_{CC} = 3 V		−12	mA
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	mA
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = −6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = −12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† For conditions shown as MIN or MAX, use the appropriate values specified under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	120	0	120	MHz
t_w	Pulse duration	CLK high or low	4.2		4.2		3		ns
t_{su}	Setup time	A or B before CLK↑	1.9		1.9		1.4		ns
		SEL before CLK↑	5.1		4.2		3.5		
		$\overline{SELEN}$ before CLK↑	2.5		2.5		1.8		
		$\overline{PRE}$ before CLK↑	1		1		0.7		
t_h	Hold time	A or B after CLK↑	0.8		0.8		1		ns
		S after CLK↑	0		0		0		
		$\overline{SELEN}$ after CLK↑	0.5		0.5		0.8		

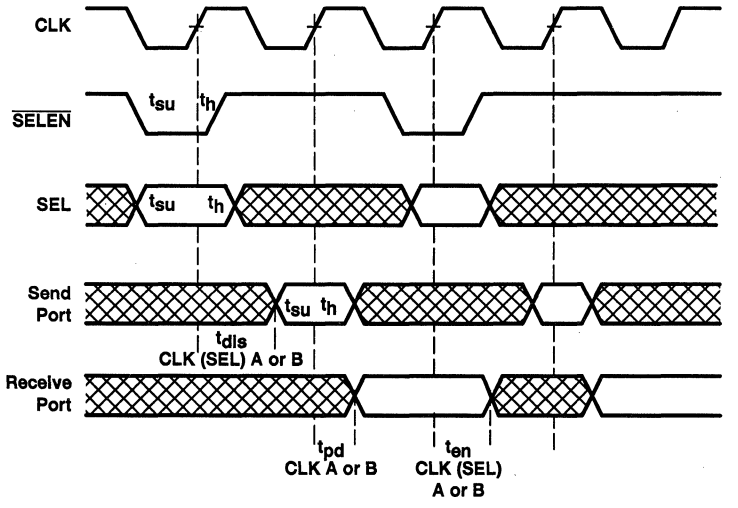
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		120		120		MHz
t_{pd}	CLK (A or B)	B or A	2	7.5		7	1.5	6.2	ns
t_{en}	CLK (SEL)	A or B	2.5	8.3		7.6	2	6.8	ns
t_{dis}	CLK (SEL)	A or B	3	7.8		6.4	2	6.1	ns
t_{dis}	$\overline{PRE}$	A or B	3.5	8.4		7	2.5	6.4	ns

operating characteristics, T_A = 25°C

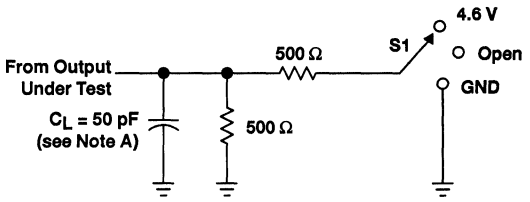
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	60	60	pF
		Outputs disabled				

timing diagram



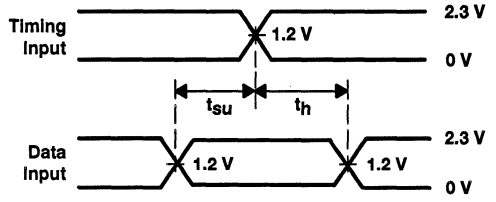
TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

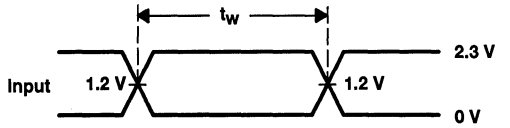


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

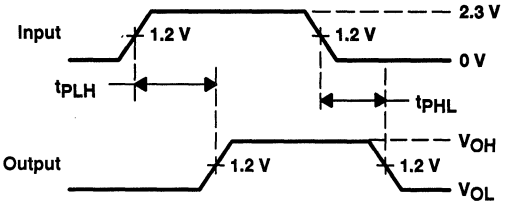
LOAD CIRCUIT



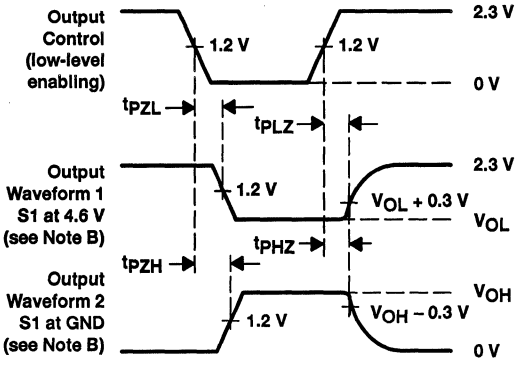
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

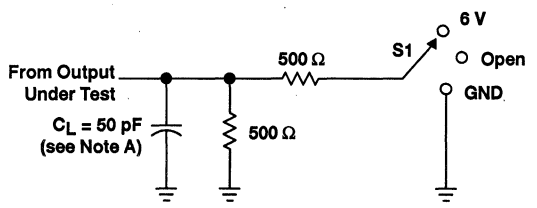


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

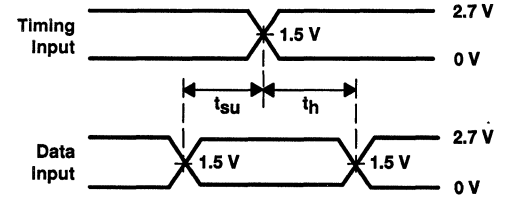
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

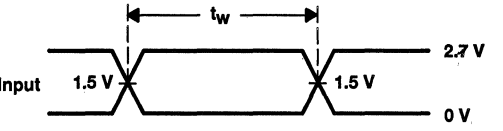


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

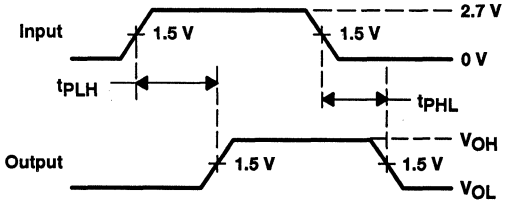
LOAD CIRCUIT



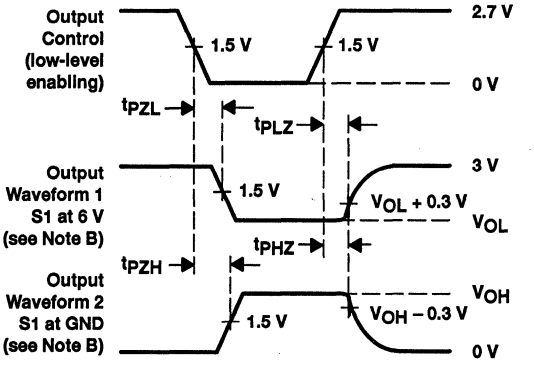
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



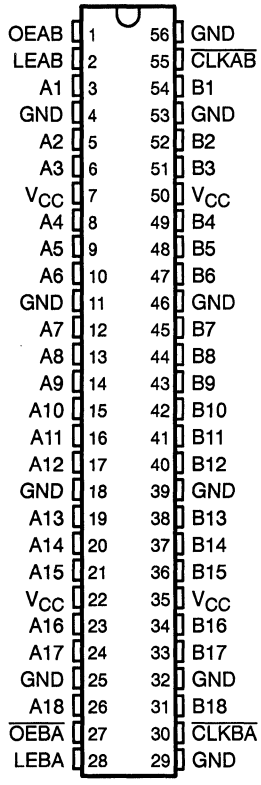
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock ($\overline{CLKAB}$ and $\overline{CLKBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if $\overline{CLKAB}$ is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the high-to-low transition of $\overline{CLKAB}$. Output-enable OEAB is active high. When OEAB is high, the B-port outputs are active. When OEAB is low, the B-port outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, and $\overline{CLKBA}$. The output enables are complementary (OEAB is active high, and $\overline{OEBA}$ is active low).

To ensure the high-impedance state during power up or power down, $\overline{OEBA}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16500 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16500 is characterized for operation from –40°C to 85°C.

ADVANCE INFORMATION

EPIC, UBT, and Widebus are trademarks of Texas Instruments Incorporated.

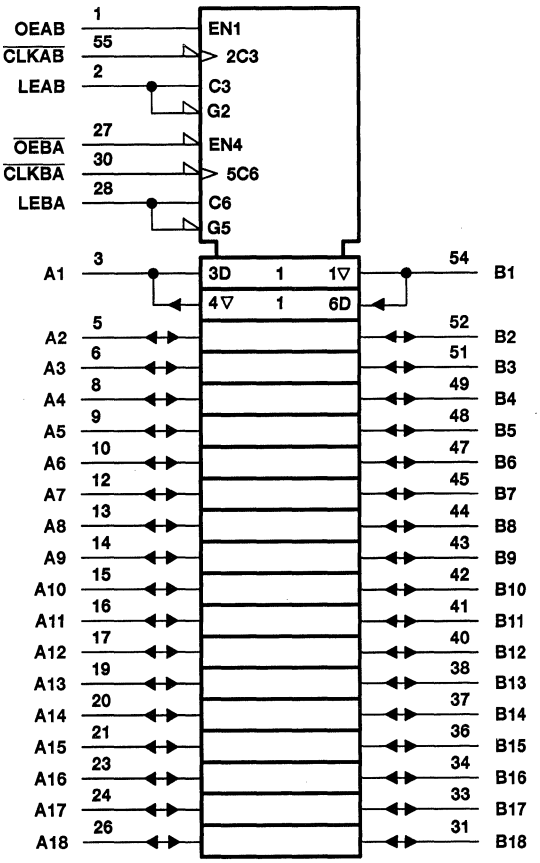
FUNCTION TABLE†

INPUTS				OUTPUT
OEAB	LEAB	$\overline{CLKAB}$	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↓	L	L
H	L	↓	H	H
H	L	H	X	B_0‡
H	L	L	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, and $\overline{CLKBA}$.
‡ Output level before the indicated steady-state input conditions were established
§ Output level before the indicated steady-state input conditions were established, provided that $\overline{CLKAB}$ was low before LEAB went low

ADVANCE INFORMATION

logic symbol†

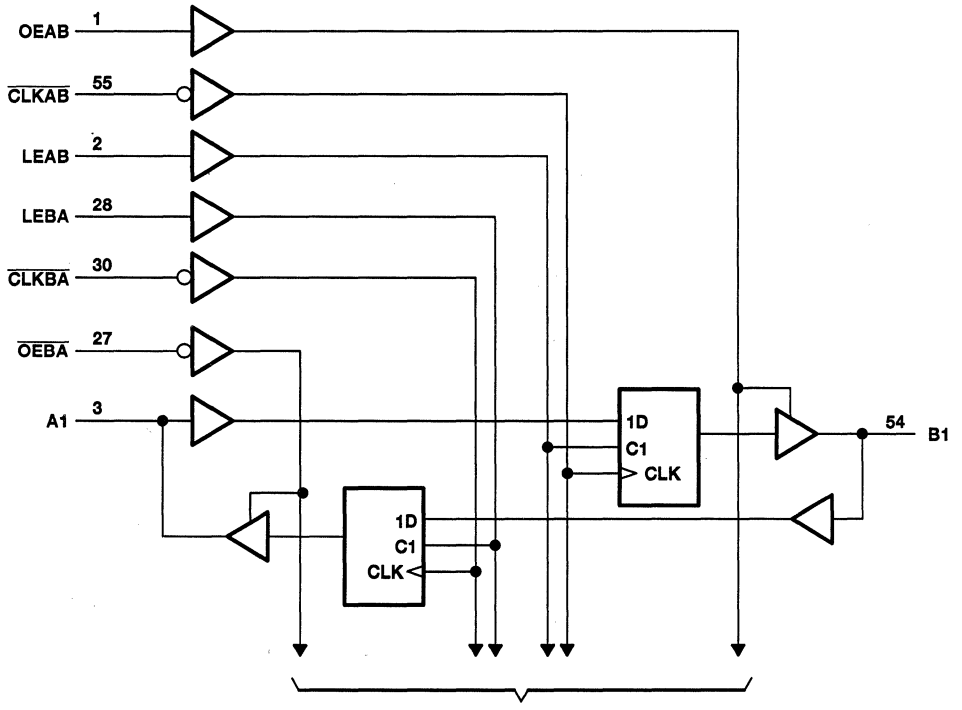


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

ADVANCE INFORMATION

ADVANCE INFORMATION

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent the from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

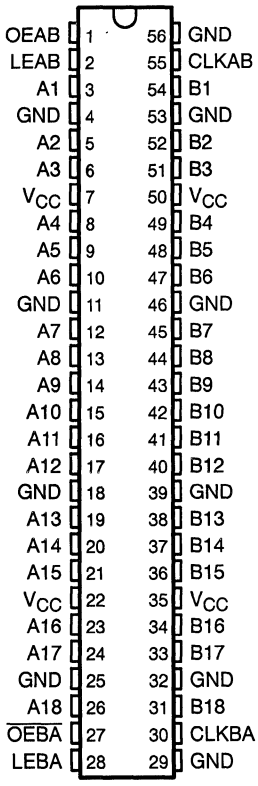
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

ADVANCE INFORMATION

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. When OEAB is high, the outputs are active. When OEAB is low, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OEBA}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, and CLKBA. The output enables are complementary (OEAB is active high and $\overline{OEBA}$ is active low).

The SN74ALVCH16501 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16501 is characterized for operation from –40°C to 85°C.

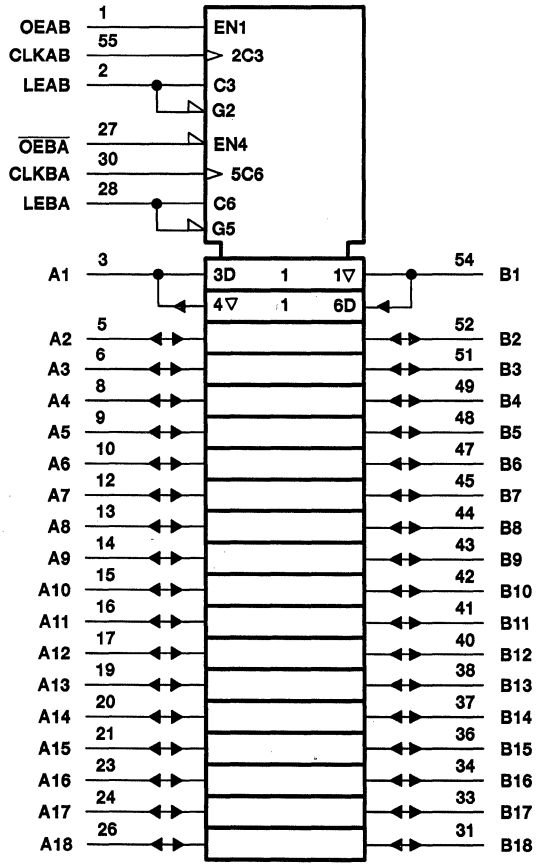
EPIC, UBT, and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE†

INPUTS				OUTPUT
OEAB	LEAB	CLKAB	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↑	L	L
H	L	↑	H	H
H	L	H	X	B_0‡
H	L	L	X	B_0§

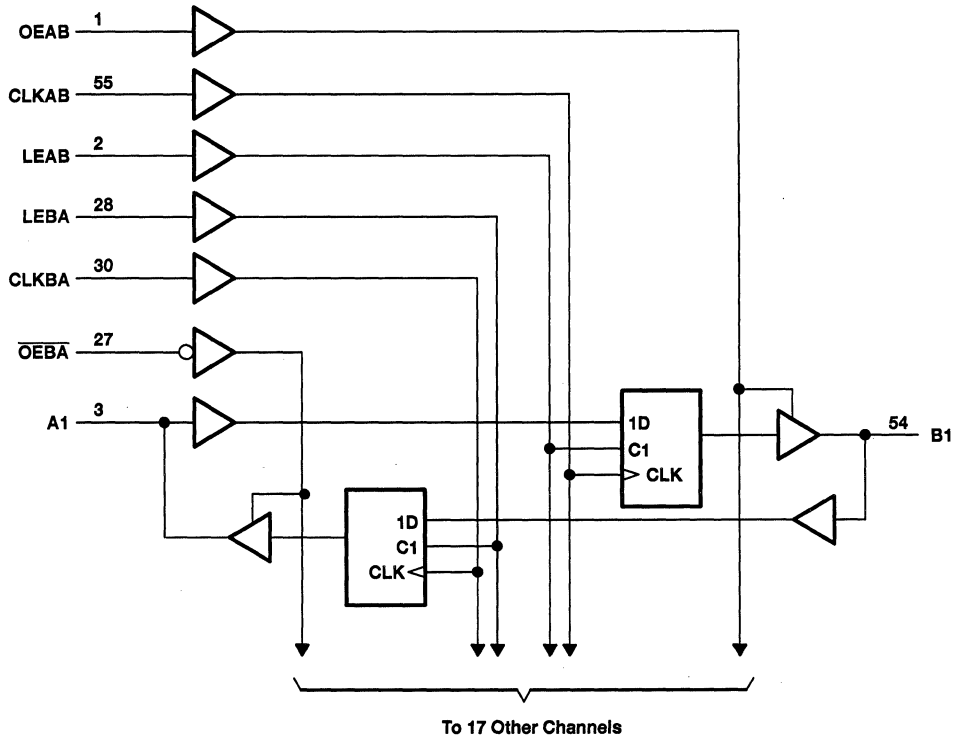
† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, and CLKBA.
‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB is high before LEAB goes low
§ Output level before the indicated steady-state input conditions were established

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
	I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
		V_{IH} = 2 V	2.7 V	2.2			
		V_{IH} = 2 V	3 V	2.4			
	I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
	I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
		V_{IL} = 0.8 V	2.7 V			0.4	
	I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I	V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.7 V		2.3 V	45			µA
	V_I = 1.7 V			−45			
	V_I = 0.8 V		3 V	75			
	V_I = 2 V			−75			
	V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io} A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration	LE high	3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑	2.2		2.1		1.7		ns
		Data before LE↓, CLK high	1.9		1.6		1.5		
		Data before LE↓, CLK low	1.3		1.1		1		
t_h	Hold time	Data after CLK↑	0.6		0.6		0.7		ns
		Data after LE↓, CLK high or low	1.4		1.7		1.4		

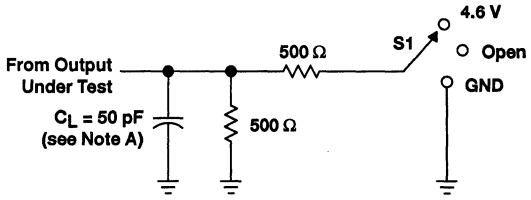
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A or B	B or A	1.2	5.4		4.5	1	3.9	ns
	LE	A or B	1.6	6.3		5.3	1.3	4.6	
	CLK	A or B	1.7	6.7		5.6	1.4	4.9	
t_{en}	OEAB	B	1.1	6.3		5.3	1	4.6	ns
t_{dis}	OEAB	B	2.2	6.4		5.7	1.4	5	ns
t_{en}	$\overline{OEBA}$	A	1.4	6.8		6	1.1	5	ns
t_{dis}	$\overline{OEBA}$	A	2	5.5		4.6	1.3	4.2	ns

operating characteristics, T_A = 25°C

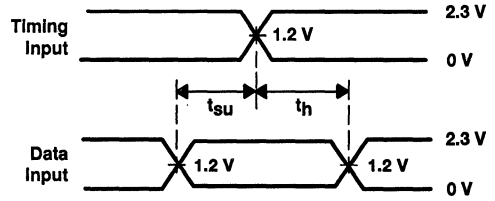
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	44	54	pF
		Outputs disabled		6	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

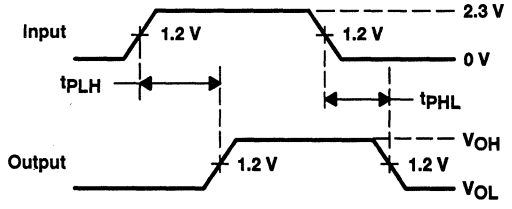


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

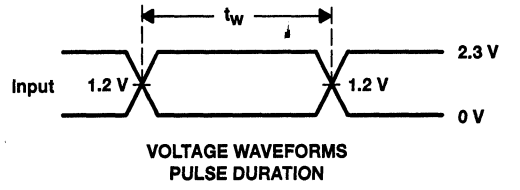
LOAD CIRCUIT



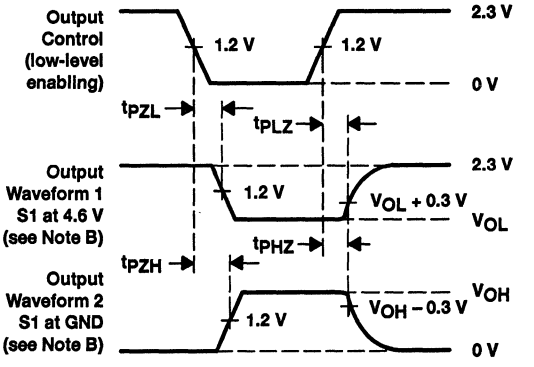
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

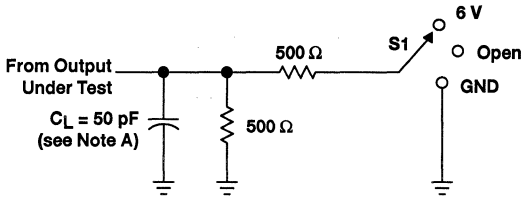


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

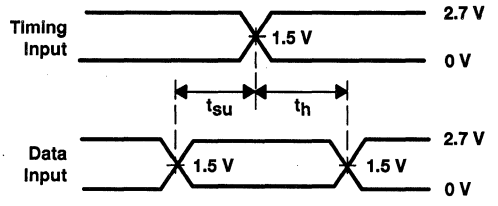
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

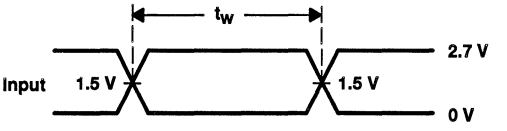


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

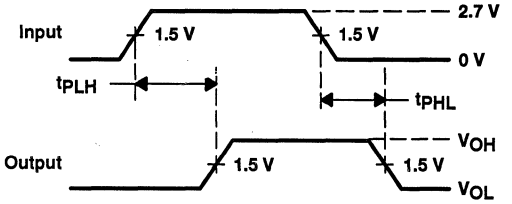
LOAD CIRCUIT



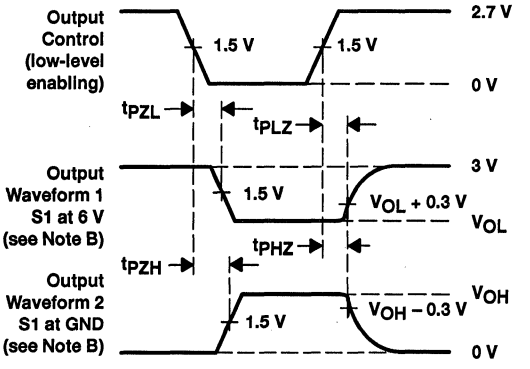
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



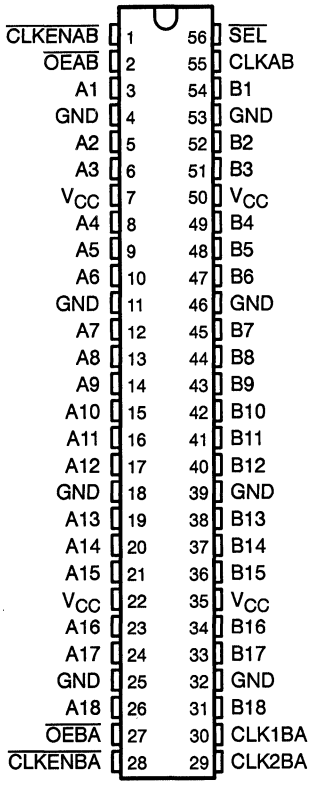
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Option Includes Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) and clock enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For the A-to-B data flow, the data flows through a single register. The B-to-A data can flow through a four-stage pipeline register path, or through a single register path, depending on the state of $\overline{SEL}$.

Data is stored in the internal registers on the low-to-high transition of the CLK input, provided that the appropriate $\overline{CLKEN}$ inputs are low. The A-to-B data transfer is synchronized to the CLKAB input, and B-to-A data transfer is synchronized with the CLK1BA and CLK2BA inputs.

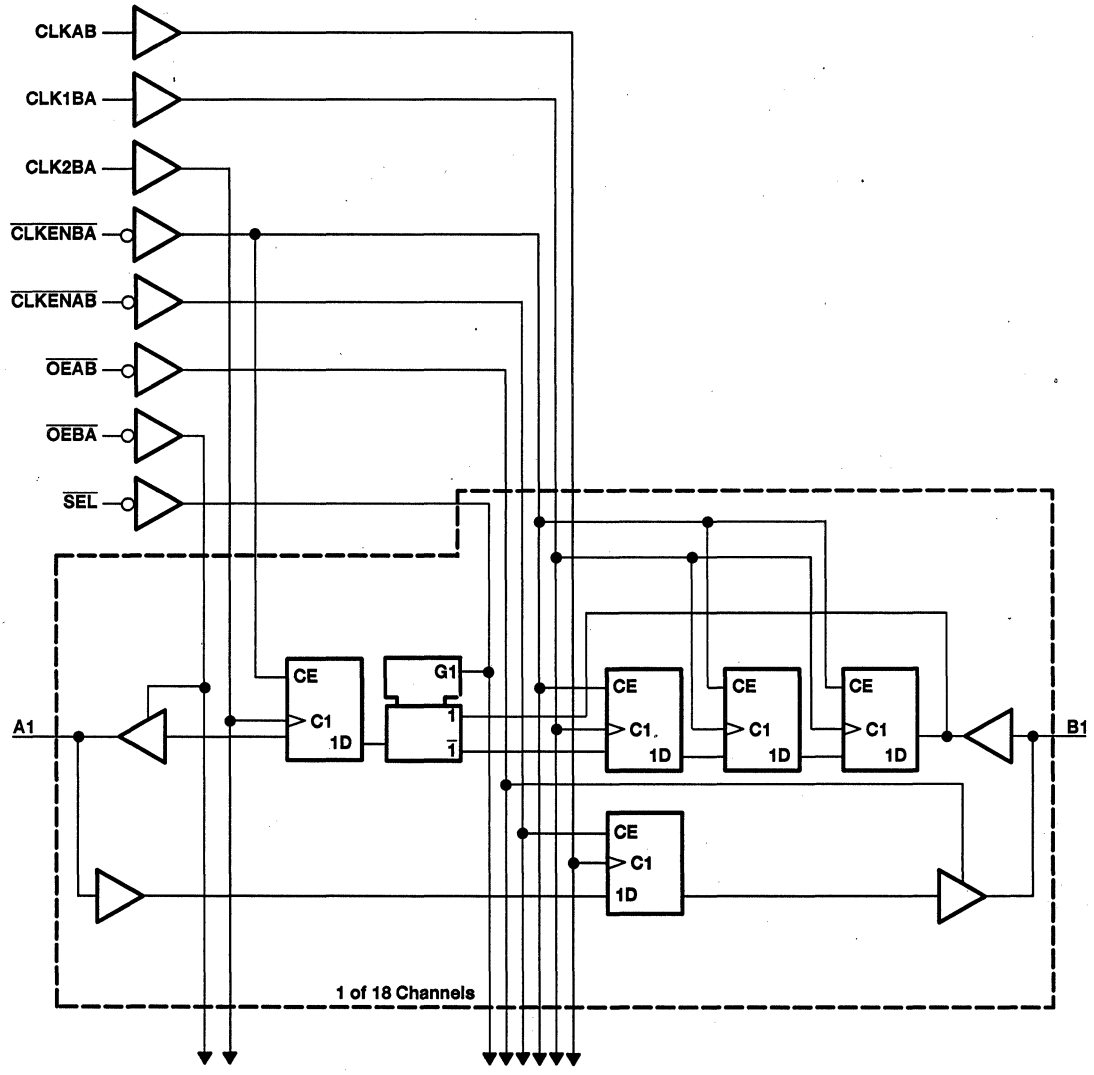
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16525 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

logic diagram (positive logic)



Function Tables

A-TO-B STORAGE ($\overline{OEAB}$ = L)

INPUTS			OUTPUT
$\overline{CLKENAB}$	CLKAB	A	B
H	X	X	B_0†
L	↑	L	L
L	↑	H	H

† Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEBA}$ = L)

INPUTS					OUTPUT
$\overline{CLKENBA}$	CLK2BA	CLK1BA	$\overline{SEL}$	B	A
H	X	X	X	X	A_0†
L	↑	X	H	L	L
L	↑	X	H	H	H
L	↑	↑	L	L	L‡
L	↑	↑	L	H	H‡

† Output level before the indicated steady-state input conditions were established

‡ Three CLK1BA edges and one CLK2BA edge are needed to propagate data from B-to-A when $\overline{SEL}$ is low.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

§ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
I_{hold}		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	A or B ports	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input-leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature range (unless otherwise noted)

			V_{CC} = 2.5 V ±0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	125	0	150	MHz
t_w	Pulse duration, CLK high or low		3.2		3.2		3		ns
t_{su}	Setup time	A data before CLKAB↑	1.3		1.3		1.3		ns
		B data before CLK2BA↑	2.1		1.8		1.7		
		B data before CLK1BA↑	1.3		1.2		1.1		
		$\overline{SEL}$ before CLK2BA↑	3.3		3.3		3.3		
		$\overline{CLKENAB}$ before CLKAB↑	2.1		1.9		1.6		
		$\overline{CLKENBA}$ before CLK1BA↑	2.7		2.5		2.1		
		$\overline{CLKENBA}$ before CLK2BA↑	2.7		2.5		2.2		
t_h	Hold time	A data after CLKAB↑	0.7		0.4		0.9		ns
		B data after CLK2BA↑	0.4		0		0.6		
		B data after CLK1BA↑	0.8		0.4		1		
		$\overline{SEL}$ after CLK2BA↑	0		0		0.1		
		$\overline{CLKENAB}$ after CLKAB↑	0.1		0.3		0.3		
		$\overline{CLKENBA}$ after CLK1BA↑	0		0		0.1		
		$\overline{CLKENBA}$ after CLK2BA↑	0		0		0		

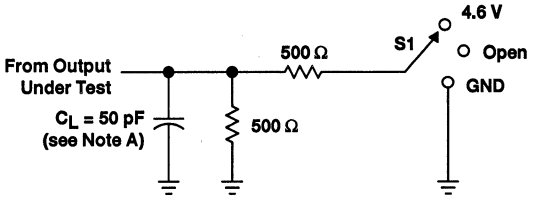
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		125		150		MHz
t_{pd}	CLKAB or CLK2BA	A or B	1	5.1		4.4	1	4.2	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	6.6		6.1	1	5.1	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1	6.5		5.4	1	4.9	ns

operating characteristics, T_A = 25°C

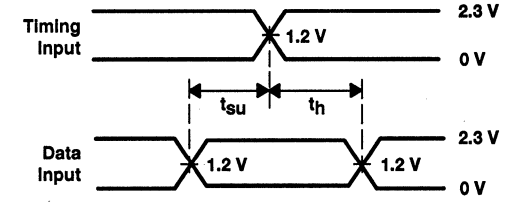
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	160	160	pF
		Outputs disabled				

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

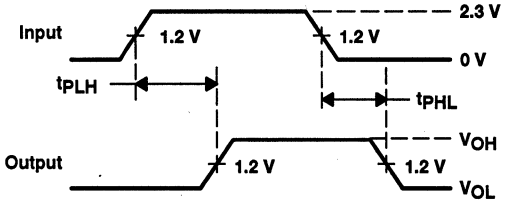


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

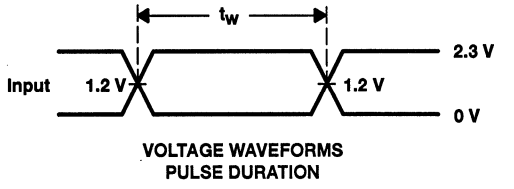
LOAD CIRCUIT



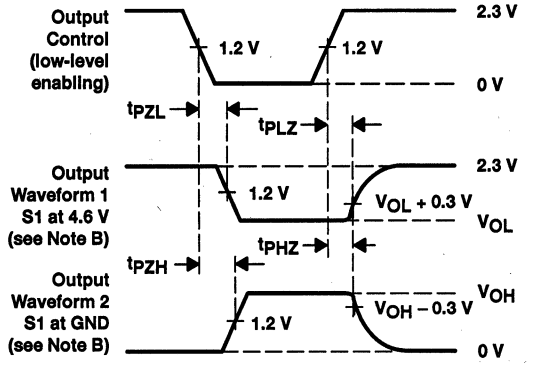
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

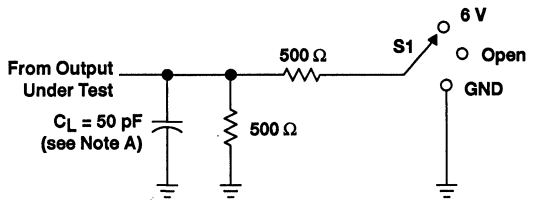


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

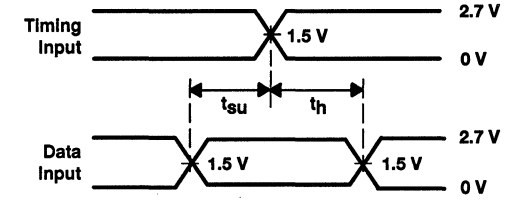
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

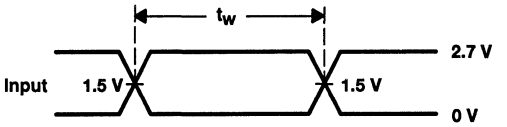


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

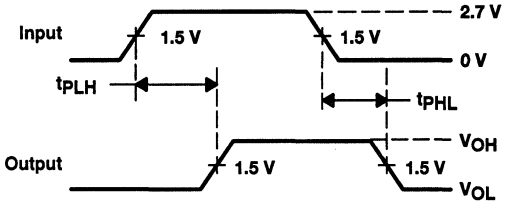
LOAD CIRCUIT



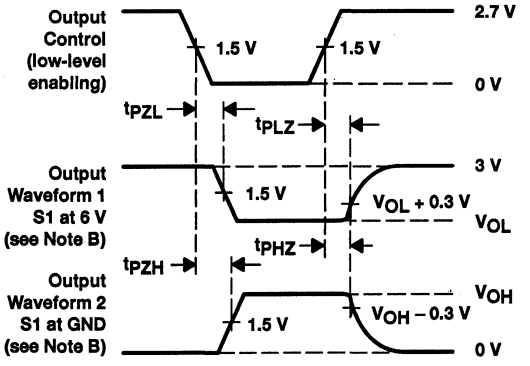
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



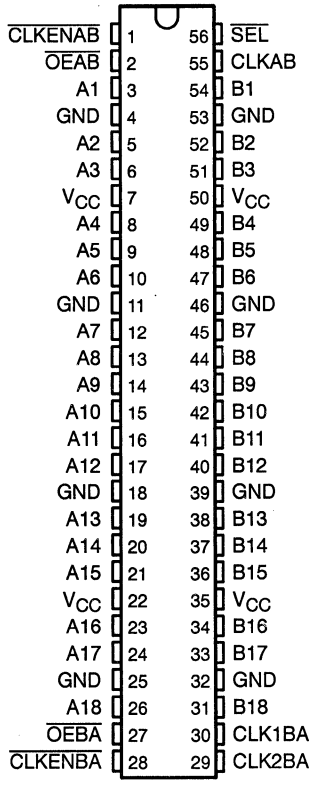
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **B-Port Outputs Have Equivalen 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Option Includes Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) and clock enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For the A-to-B data flow, the data flows through a single register. The B-to-A data can flow through a four-stage pipeline register path, or through a single register path, depending on the state of $\overline{SEL}$.

Data is stored in the internal registers on the low-to-high transition of the CLK input, provided that the appropriate $\overline{CLKEN}$ inputs are low. The A-to-B data transfer is synchronized to the CLKAB input, and B-to-A data transfer is synchronized with the CLK1BA and CLK2BA inputs.

The B outputs, which are designed to sink up to 12 mA, include 26-Ω resistors to reduce overshoot and undershoot.

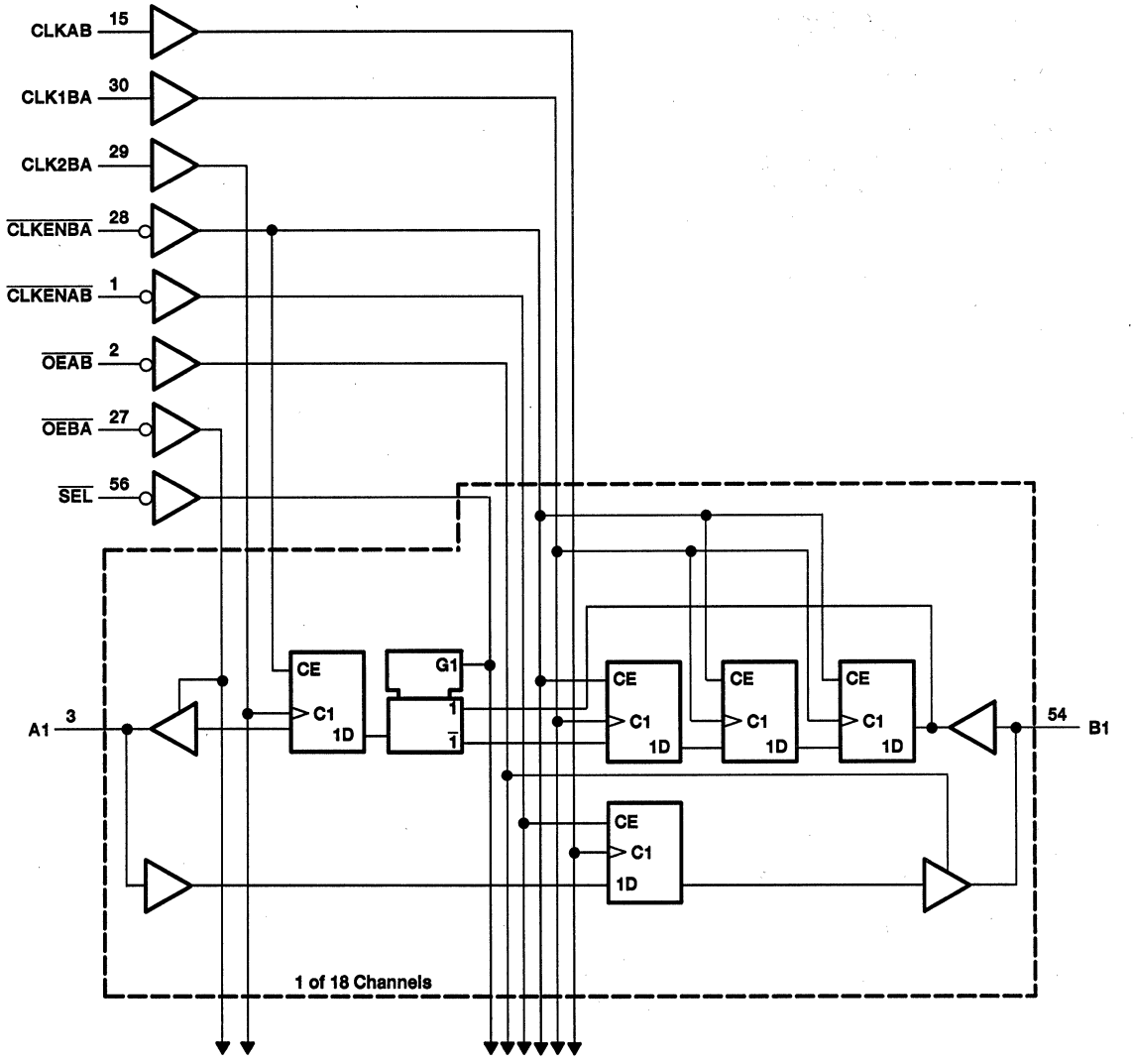
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162525 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Function Tables

A-TO-B STORAGE ($\overline{OEAB}$ = L)

INPUTS			OUTPUT
$\overline{CLKENAB}$	CLKAB	A	B
H	X	X	B_0†
L	↑	L	L
L	↑	H	H

† Output level before the indicated steady-state input conditions were established

B-TO-A STORAGE ($\overline{OEBA}$ = L)

INPUTS					OUTPUT
$\overline{CLKENBA}$	CLK2BA	CLK1BA	$\overline{SEL}$	B	A
H	X	X	X	X	A_0†
L	↑	X	H	L	L
L	↑	X	H	H	H
L	↑	↑	L	L	L‡
L	↑	↑	L	H	H‡

† Output level before the indicated steady-state input conditions were established

‡ Three CLK1BA edges and one CLK2BA edge are needed to propagate data from B-to-A when $\overline{SEL}$ is low.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

§ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current (A port)	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current (A port)	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
I_{OH}	High-level output current (B port)	V_{CC} = 2.3 V		−6	mA
		V_{CC} = 2.7 V		−8	
		V_{CC} = 3 V		−12	
I_{OL}	Low-level output current (B port)	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH} (A port)		I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OH} (B port)		I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = −6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = −12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL} (A port)		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
V_{OL} (B port)		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
I_{hold}		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	A or B ports	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature range (unless otherwise noted)

			V_{CC} = 2.5 V ±0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	120	0	125	0	150	MHz
t_w	Pulse duration, CLK high or low		3.2		3.2		3		ns
t_{su}	Setup time	A data before CLKAB↑	1.3		1.3		1.3		ns
		B data before CLK2BA↑	2.1		1.8		1.7		
		B data before CLK1BA↑	1.3		1.2		1.1		
		$\overline{SEL}$ before CLK2BA↑	3.3		3.3		3.3		
		$\overline{CLKENAB}$ before CLKAB↑	2.1		1.9		1.6		
		$\overline{CLKENBA}$ before CLK1BA↑	2.7		2.5		2.1		
		$\overline{CLKENBA}$ before CLK2BA↑	2.7		2.5		2.2		
t_h	Hold time	A data after CLKAB↑	0.7		0.4		0.9		ns
		B data after CLK2BA↑	0.4		0		0.6		
		B data after CLK1BA↑	0.8		0.4		1		
		$\overline{SEL}$ after CLK2BA↑	0		0		0.1		
		$\overline{CLKENAB}$ after CLKAB↑	0.1		0.3		0.3		
		$\overline{CLKENBA}$ after CLK1BA↑	0		0		0.1		
		$\overline{CLKENBA}$ after CLK2BA↑	0		0		0		

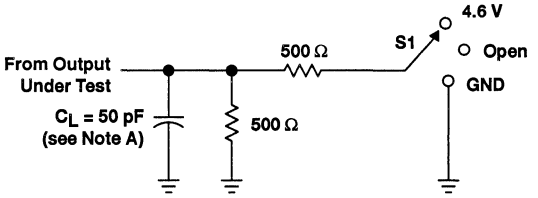
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			120		125		150		MHz
t_{pd}	CLKAB	B	1	6.1		5.4	1	4.7	ns
	CLK2BA	A	1	5.1		4.4	1	4.2	
t_{en}	$\overline{OEBA}$	A	1	6.6		6.1	1	5.1	ns
	$\overline{OEAB}$	B	1	7.2		6.8	1	5.7	
t_{dis}	$\overline{OEBA}$	A	1	6.5		5.4	1	4.9	ns
	$\overline{OEAB}$	B	1	6.5		5.4	1	4.9	

operating characteristics, T_A = 25°C

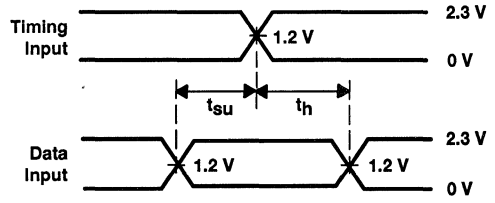
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	160	160	pF
		Outputs disabled				

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

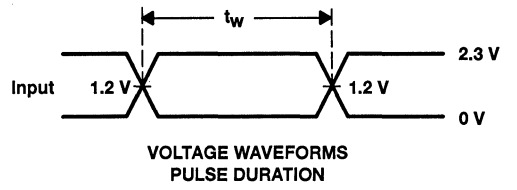


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

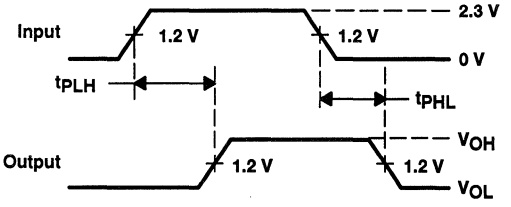
LOAD CIRCUIT



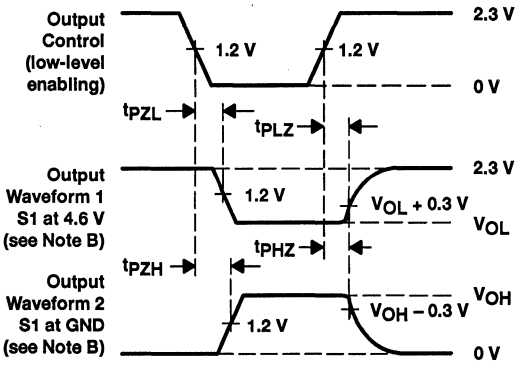
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

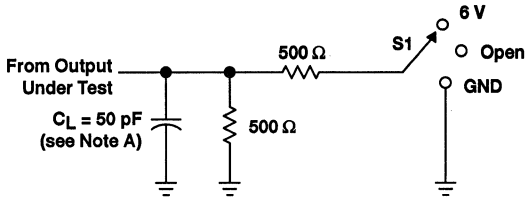


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

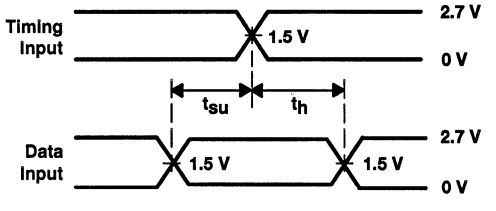
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

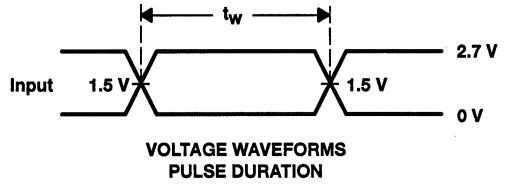


LOAD CIRCUIT

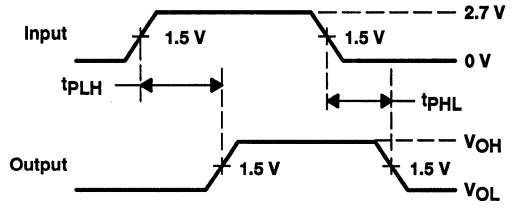
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



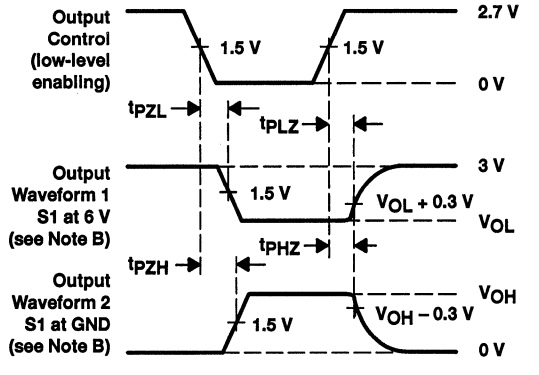
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



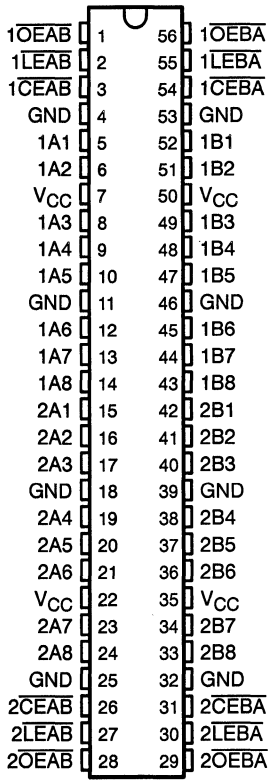
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit registered transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16543 can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low in order to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ puts the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar but requires using $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16543 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

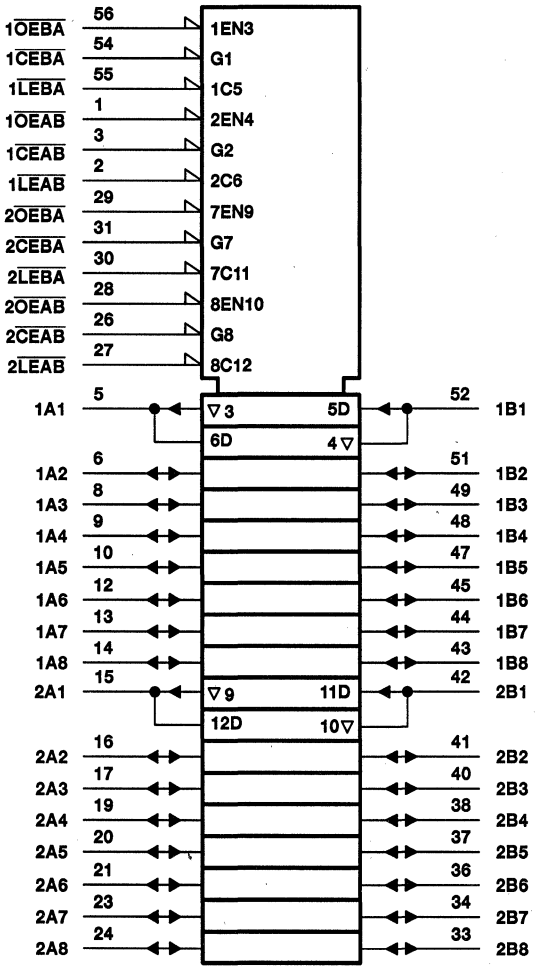
The SN74ALVCH16543 is characterized for operation from –40°C to 85°C.

ADVANCE INFORMATION

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

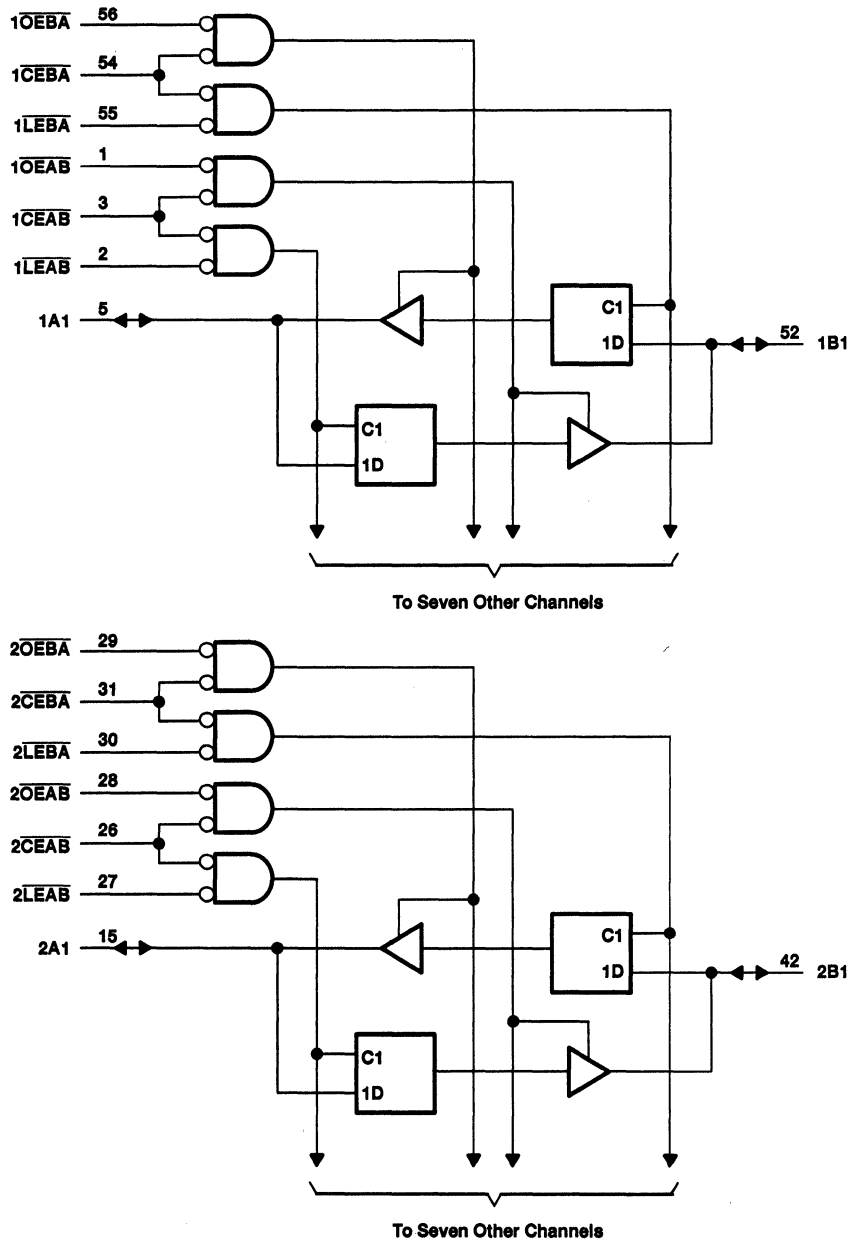
ADVANCE INFORMATION

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



FUNCTION TABLE† (each 8-bit section)

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

§ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

ADVANCE INFORMATION

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

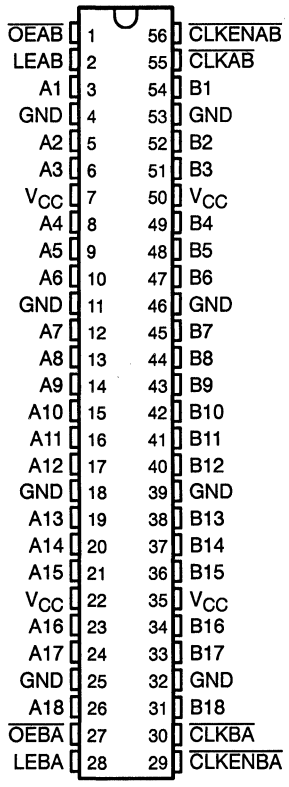
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

ADVANCE INFORMATION

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, Clocked, or Clock-Enabled Mode**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16600 combines D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock ($\overline{CLKAB}$ and $\overline{CLKBA}$) inputs. The clock can be controlled by the clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if $\overline{CLKAB}$ is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the high-to-low transition of $\overline{CLKAB}$. Output enable $\overline{OEAB}$ is active low. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, $\overline{CLKBA}$, and $\overline{CLKENBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16600 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16600 is characterized for operation from –40°C to 85°C.

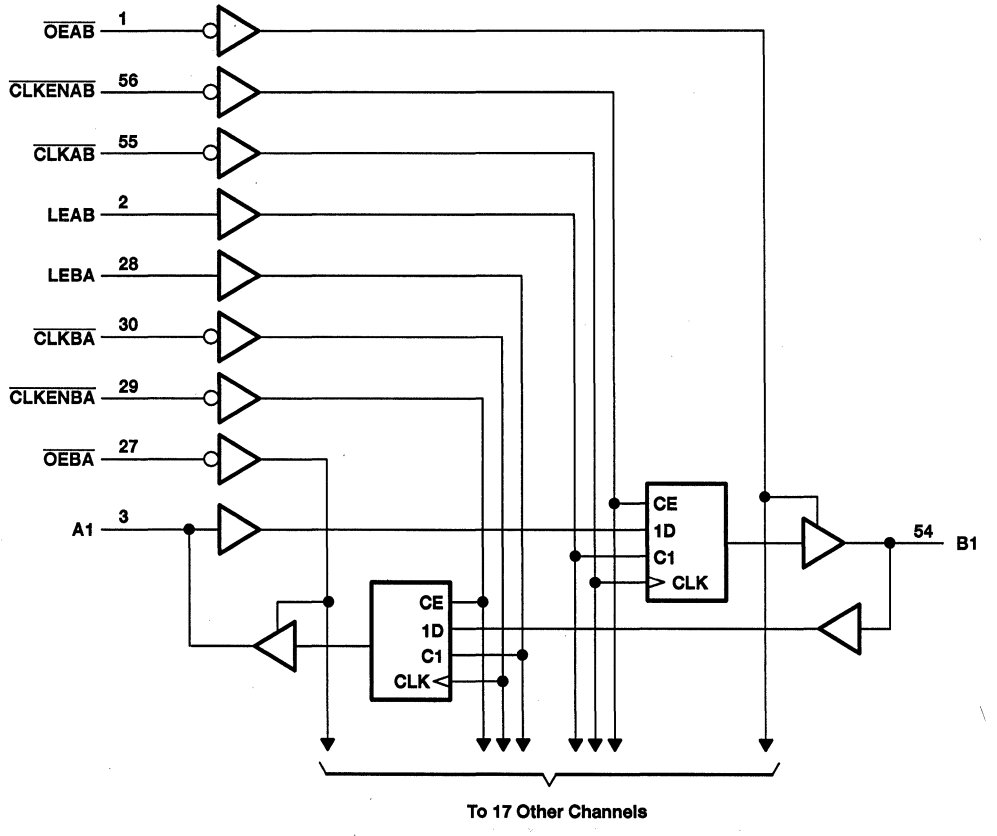
EPIC, UBT, and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE†

INPUTS					OUTPUT
$\overline{CLKENAB}$	$\overline{OEAB}$	LEAB	$\overline{CLKAB}$	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
H	L	L	X	X	B_0‡
L	L	L	↓	L	L
L	L	L	↓	H	H
L	L	L	H	X	B_0‡
L	L	L	L	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, $\overline{CLKBA}$, and $\overline{CLKENBA}$.
‡ Output level before the indicated steady-state input conditions were established
§ Output level before the indicated steady-state input conditions were established, provided that $\overline{CLKAB}$ was low before LEAB went low

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration	LE↑	3.3		3.3		3.3		ns
		$\overline{CLK}$↑	3.3		3.3		3.3		
t_{su}	Setup time	Data before $\overline{CLK}$↑	1.3		1.3		1.2		ns
		Data before LE↓, $\overline{CLK}$↑	1.2		1.1		1.1		
		Data before LE↓, $\overline{CLK}$↓	1.8		1.5		1.5		
		$\overline{CLKEN}$ before $\overline{CLK}$↑	0.7		0.7		0.8		
t_h	Hold time	Data after $\overline{CLK}$↑	1.5		1.8		1.5		ns
		Data after LE↓, $\overline{CLK}$↑	1.6		1.9		1.6		
		Data after LE↓, $\overline{CLK}$↓	1.2		1.6		1.3		
		$\overline{CLKEN}$ after $\overline{CLK}$↑	1.4		1.7		1.4		

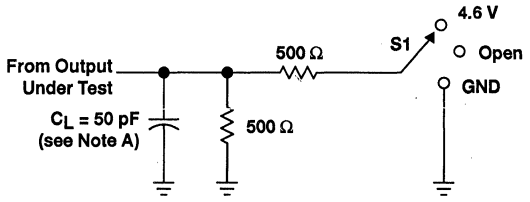
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A or B	B or A	1	5.7		4.7	1	4	ns
	LEAB or LEBA	A or B	1	6.5		5.5	1	4.8	
	$\overline{CLKAB}$ or $\overline{CLKBA}$	A or B	1.4	7.9		6.8	1.3	5.7	
t_{en}	$\overline{OEAB}$	B	1.1	7.1		6.3	1.1	5.2	ns
t_{dis}	$\overline{OEAB}$	B	1.7	5.7		4.7	1.2	4.4	ns

operating characteristics, T_A = 25°C

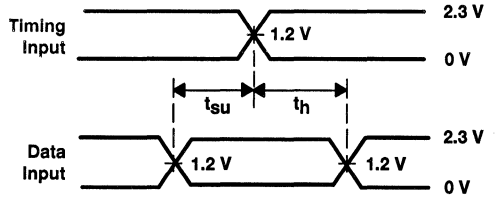
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	43	56	pF
		Outputs disabled		6	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

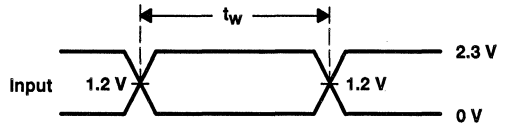


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

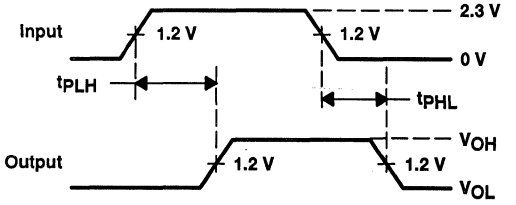
LOAD CIRCUIT



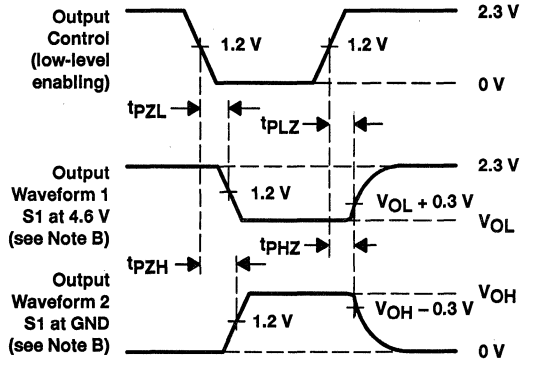
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

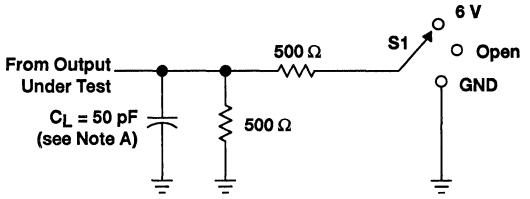


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

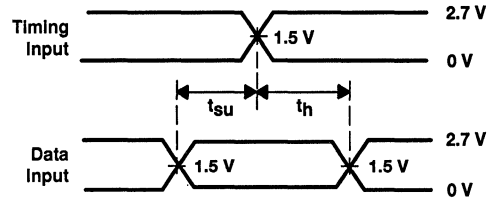
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

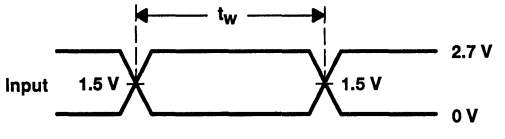


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

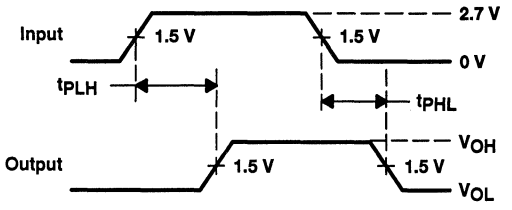
LOAD CIRCUIT



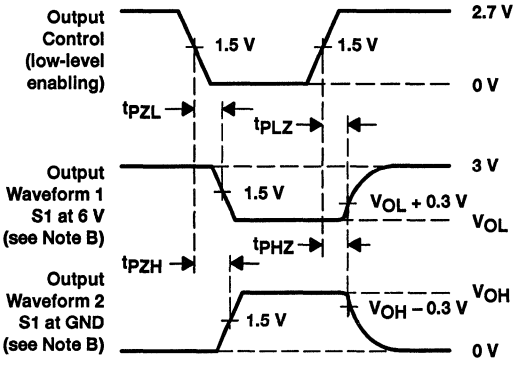
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



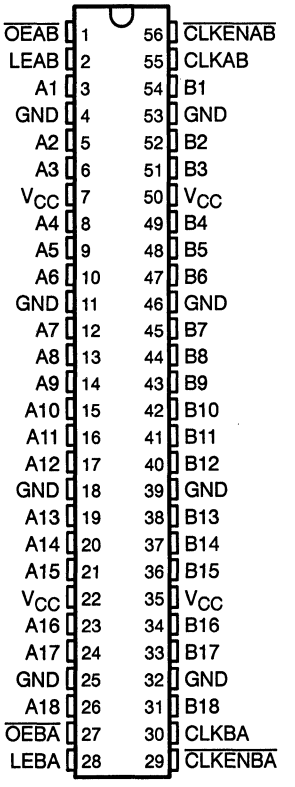
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, Clocked, or Clock-Enabled Mode**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16601 combines D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. The clock can be controlled by the clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. Output enable $\overline{OEAB}$ is active low. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CLKENBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16601 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16601 is characterized for operation from −40°C to 85°C.

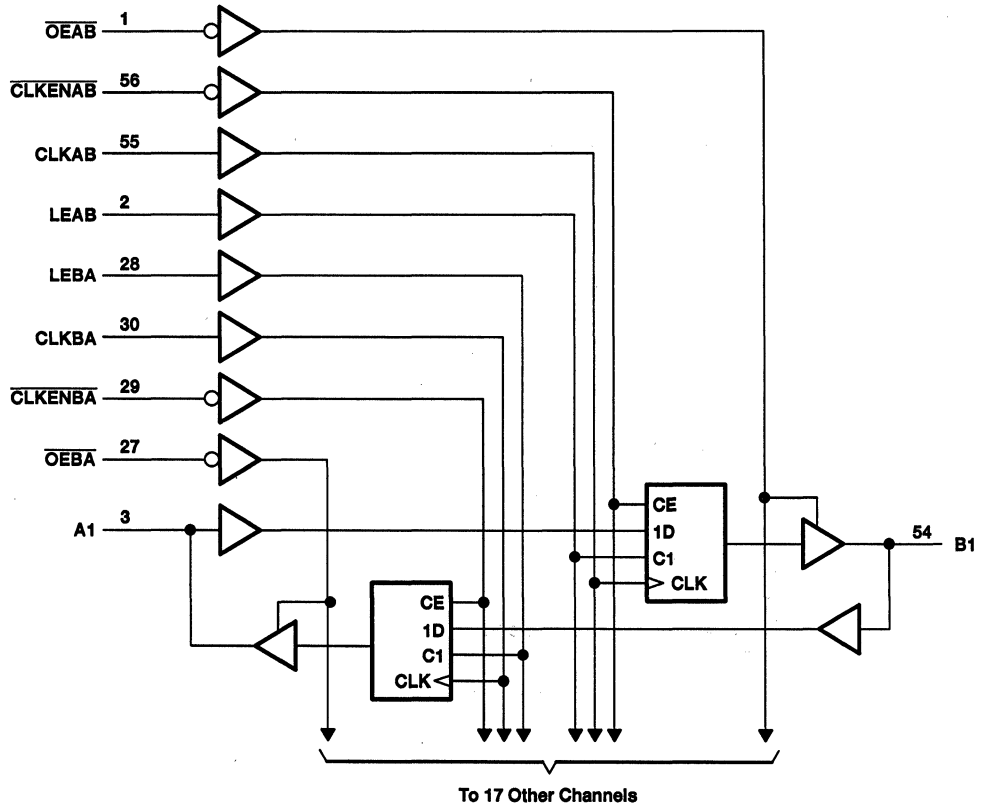
EPIC, UBT, and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE†

INPUTS					OUTPUT
$\overline{CLKENAB}$	$\overline{OEAB}$	LEAB	CLKAB	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
H	L	L	X	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	L	L	X	B_0‡
L	L	L	H	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CLKENBA}$.
‡ Output level before the indicated steady-state input conditions were established
§ Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration	LE↑	3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑	2.3		2.4		2.1		ns
		Data before LE↓, CLK↑	2		1.6		1.6		
		Data before LE↓, CLK↓	1.3		1.2		1.1		
		$\overline{CLKEN}$ before CLK↑	2		2		1.7		
t_h	Hold time	Data after CLK↑	0.7		0.7		0.8		ns
		Data after LE↓, CLK↑	1.3		1.6		1.4		
		Data after LE↓, CLK↓	1.7		2		1.7		
		$\overline{CLKEN}$ after CLK↑	0.3		0.5		0.6		

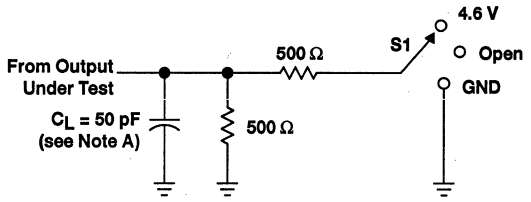
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A or B	B or A	1.3	4.9		4.6		4.1	ns
	LEAB or LEBA	A or B	1.2	5.6		5.3		4.7	
	CLKAB or CLKBA	A or B	1.7	6.2		5.8		5	
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	1.2	6.1		6.1		5.2	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.1	5.4		4.8		4.4	ns

operating characteristics, T_A = 25°C

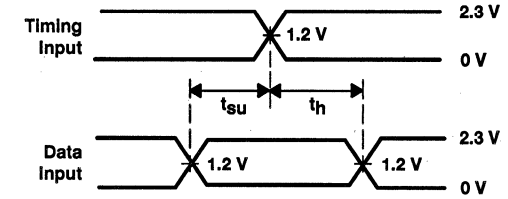
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	41	52	pF
		Outputs disabled		6	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

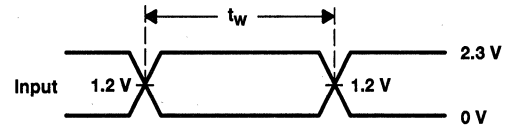


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

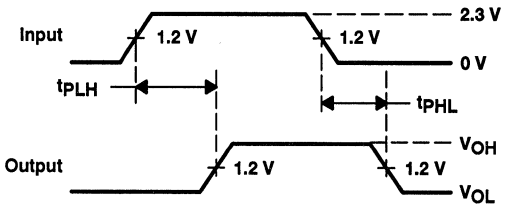
LOAD CIRCUIT



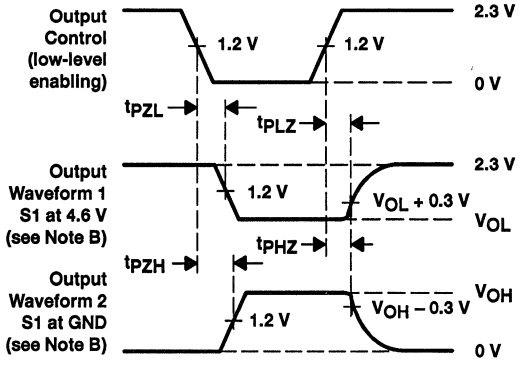
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

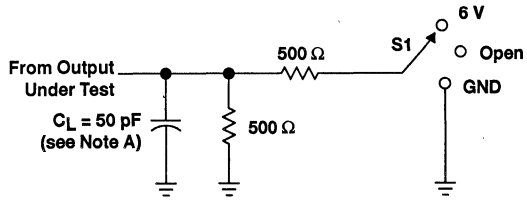


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

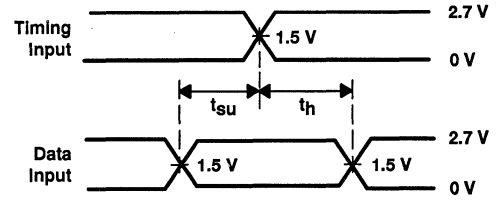
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

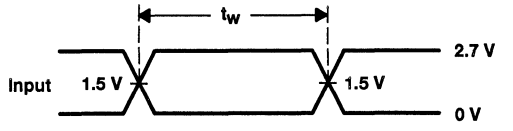


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

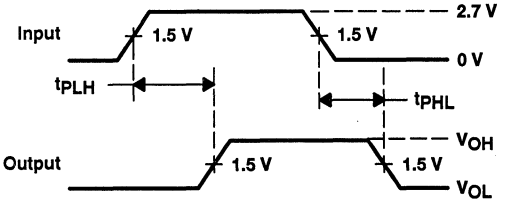
LOAD CIRCUIT



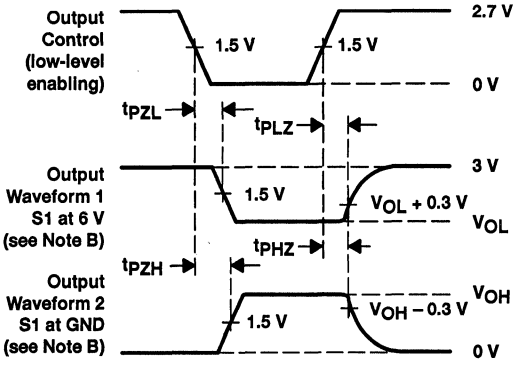
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



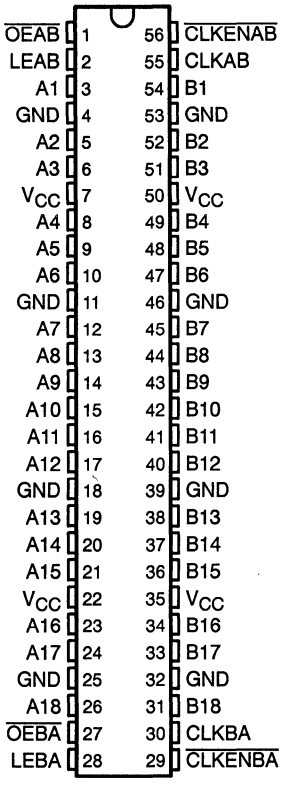
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, Clocked, or Clock-Enabled Mode**
- **Output Ports Have Equivalent 26-Ω Series Resisters, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit universal bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162601 combines D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. The clock can be controlled by the clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the high-to-low transition of CLKAB. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CLKENBA}$.

The B-port outputs include 26-Ω series resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

EPIC, UBT, and Widebus are trademarks of Texas Instruments Incorporated.

description (continued)

The SN74ALVCH162601 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH162601 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

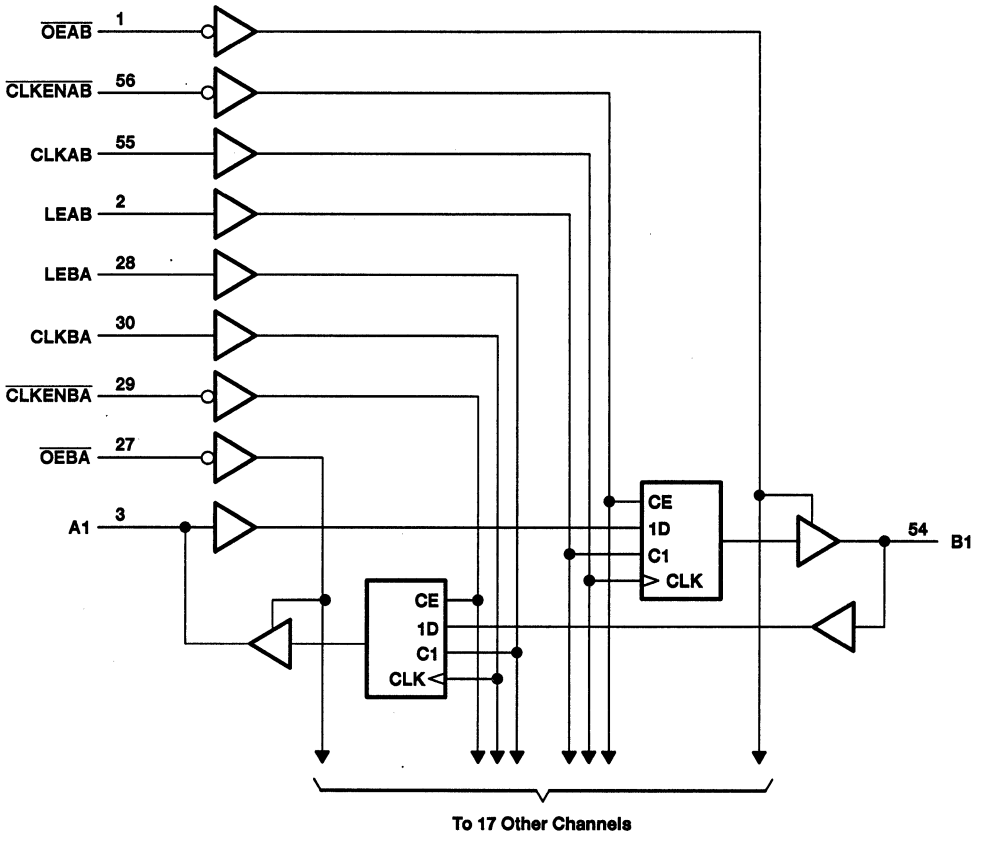
INPUTS					OUTPUT
$\overline{\text{CLKENAB}}$	$\overline{\text{OEAB}}$	LEAB	CLKAB	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
H	L	L	X	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	L	L	X	B_0‡
L	L	L	H	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{\text{OEBA}}$, LEBA, CLKBA, and $\overline{\text{CLKENBA}}$.

‡ Output level before the indicated steady-state input conditions were established

§ Output level before the indicated steady-state input conditions were established, provided that CLKAB is low before LEAB goes low

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current (A port)	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current (A port)	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
I_{OH}	High-level output current (B port)	V_{CC} = 2.3 V		−6	mA
		V_{CC} = 2.7 V		−8	
		V_{CC} = 3 V		−12	
I_{OL}	Low-level output current (B port)	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH} (B port)		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OH} (A port)		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL} (B port)		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
V_{OL} (A port)		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	140	0	150	0	150	MHz
t_w	Pulse duration	LE high	3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK high	2.3		2.4		2.1		ns
		Data before LE low, CLK high	2		1.6		1.6		
		Data before LE low, CLK low	1.3		1.2		1.1		
		$\overline{CLKEN}$ before CLK high	2		2		1.7		
t_h	Hold time	Data after CLK high	0.7		0.7		0.8		ns
		Data after LE low, CLK high	1.3		1.6		1.4		
		Data after LE low, CLK low	1.7		2		1.7		
		$\overline{CLKEN}$ after CLK high	0.3		0.5		0.6		

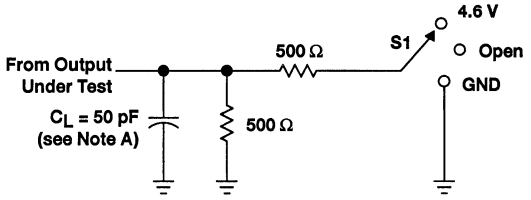
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			140		150		150		MHz
t_{pd}	A	B	1.8	5.4		5.2	1.6	4.5	ns
t_{pd}	B	A	1.3	4.9		4.6	1	4.1	ns
t_{pd}	LEAB	B	1.5	6.1		5.9	1.5	5.1	ns
t_{pd}	LEBA	A	1.4	5.6		5.3	1	4.7	ns
t_{pd}	CLKAB	B	2	6.7		6.3	1.6	5.5	ns
t_{pd}	CLKBA	A	1.8	6.2		5.8	1.4	5	ns
t_{en}	$\overline{OEAB}$	B	1.7	6.6		6.7	1.6	5.7	ns
t_{dis}	$\overline{OEAB}$	B	2.5	5.9		5.3	1.8	4.8	ns
t_{en}	$\overline{OEBA}$	A	1.2	6		6.1	1.1	5.2	ns
t_{dis}	$\overline{OEBA}$	A	2.1	5.4		4.8	1.6	4.4	ns

operating characteristics, T_A = 25°C

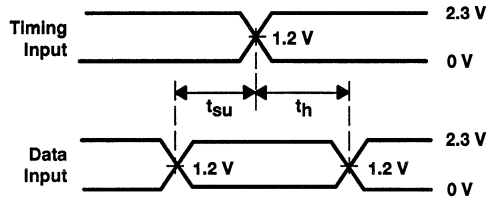
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	41	50	pF
		Outputs disabled		6	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

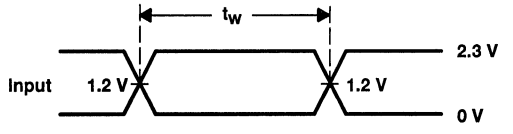


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

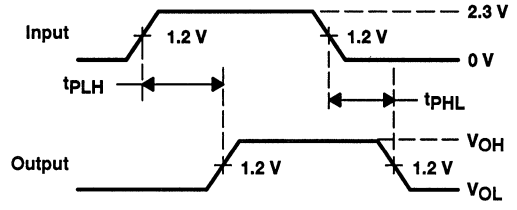
LOAD CIRCUIT



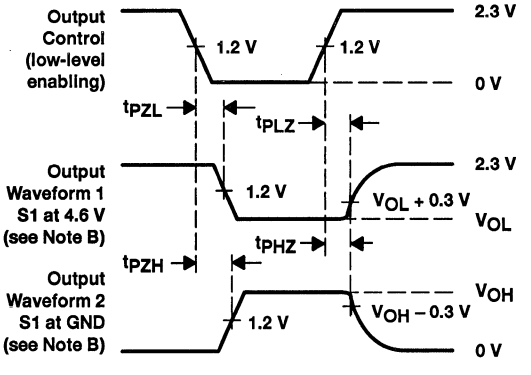
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

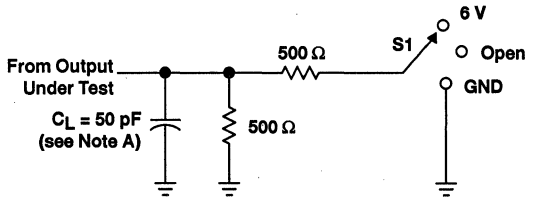


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

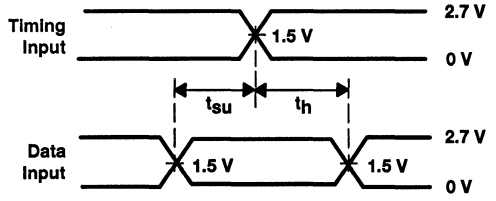
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

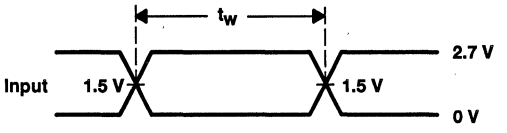


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

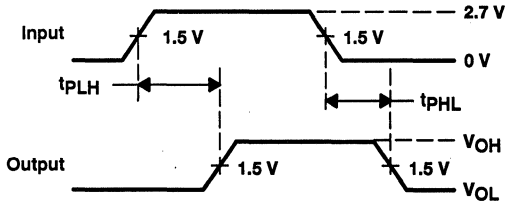
LOAD CIRCUIT



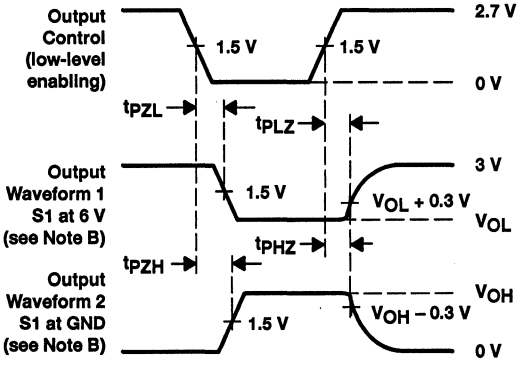
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



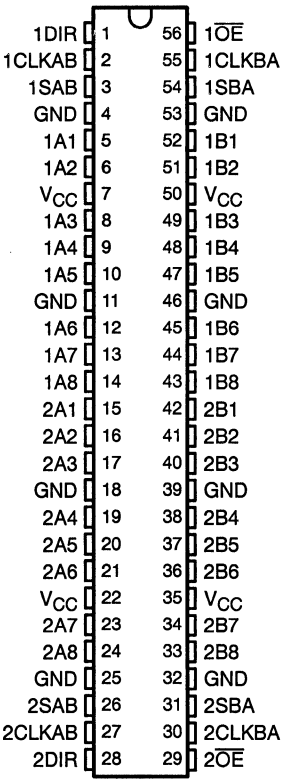
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit bus transceiver and register is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16646 can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74ALVCH16646.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs are provided to control the transceiver functions. In the transceiver mode, data present at the high-impedance port may be stored in either register or in both. The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. DIR determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data may be stored in one register and/or B data may be stored in the other register.

When an output function is disabled, the input function is still enabled and may be used to store and transmit data. Only one of the two buses, A or B, can be driven at a time.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16646 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16646 is characterized for operation from –40°C to 85°C.

ADVANCE INFORMATION

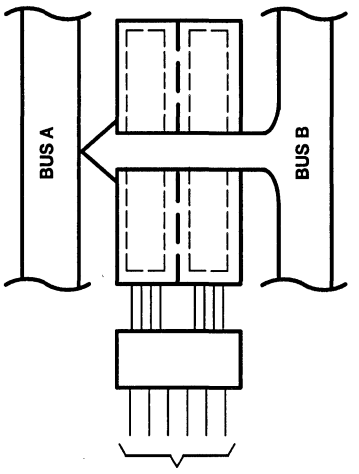
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE

INPUTS						DATA I/Os		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1 – A8	B1 – B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

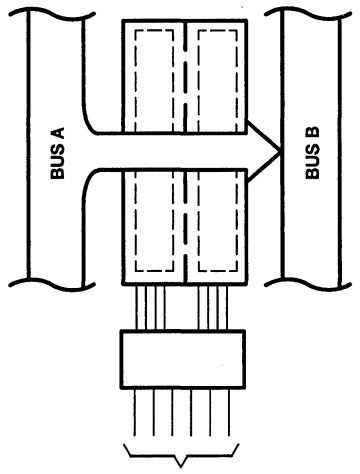
† The data output functions may be enabled or disabled by various signals at the $\overline{OE}$ and DIR inputs. Data input functions are always enabled; i.e., data at the bus pins is stored on every low-to-high transition of the clock inputs.

ADVANCE INFORMATION



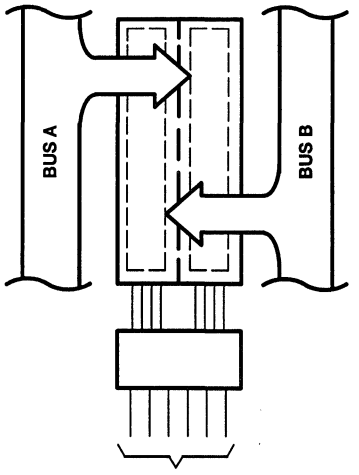
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



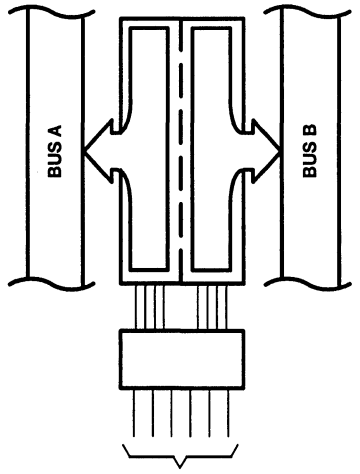
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B



$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

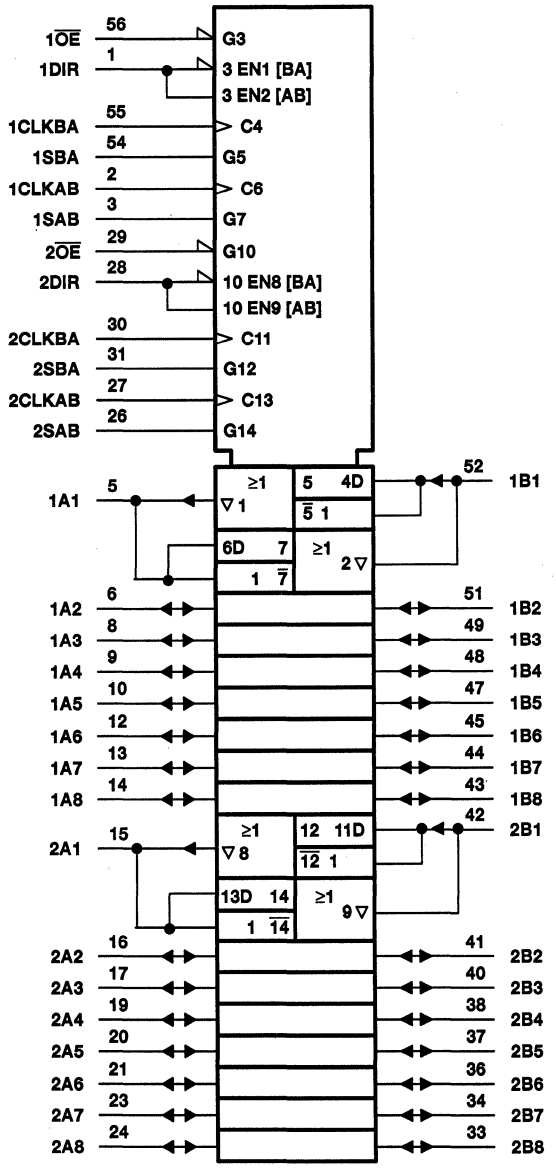
TRANSFER STORED DATA
TO A AND/OR B

Figure 1. Bus-Management Functions

ADVANCE INFORMATION

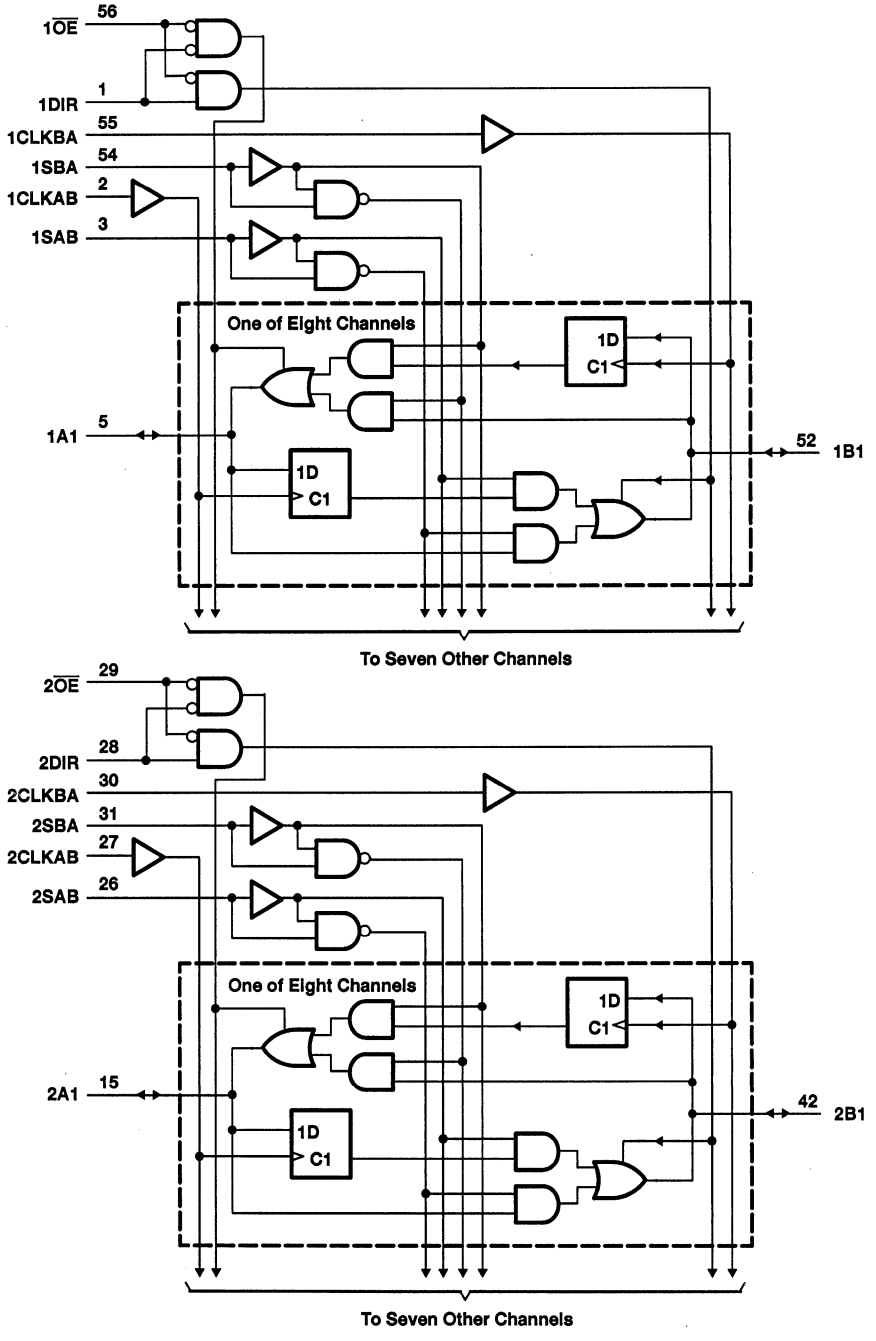
ADVANCE INFORMATION

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



ADVANCE INFORMATION

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

ADVANCE INFORMATION

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

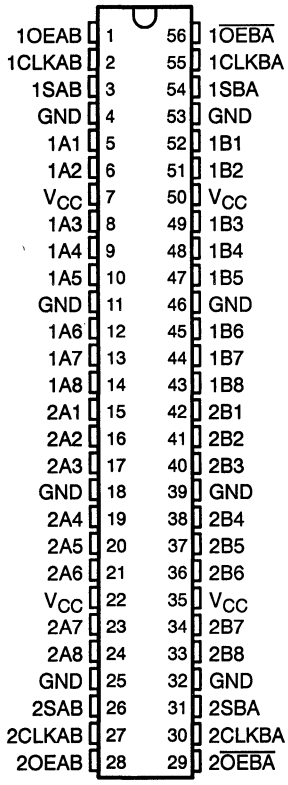
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

ADVANCE INFORMATION

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit bus transceiver and register is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16652 consists of D-type flip-flops and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers. The device can be used as two 8-bit transceivers or one 16-bit transceiver.

Complementary output-enable (OEAB and $\overline{OEBA}$) inputs are provided to control the transceiver functions. Select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. A low input level selects real-time data, and a high input level selects stored data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74ALVCH16652.

Data on the A or B bus, or both, can be stored in the internal D flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs regardless of the levels on the select-control or output-enable inputs. When SAB and SBA are in the real-time transfer mode, it also is possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{OEBA}$. In this configuration, each output reinforces its input. Thus, when all other data sources to the two sets of bus line are in the high-impedance state, each set of bus lines remains at its last level configuration.

Active bus-hold circuitry is provided to hold unused for floating inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OEBA}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking current-sourcing capability of the driver.

The SN74ALVCH16652 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16652 is characterized for operation from −40°C to 85°C.

PRODUCT PREVIEW

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE

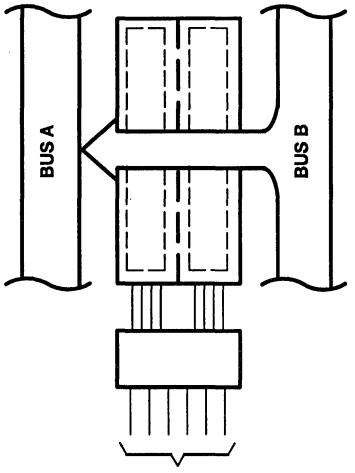
INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA	A1 – A8	B1 – B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

† The data output functions may be enabled or disabled by a variety of level combinations at the OEAB or $\overline{OEBA}$ inputs. Data input functions are always enabled; i.e., data at the bus pins is stored on every low-to-high transition of the clock inputs.

‡ Select control = L; clocks can occur simultaneously
Select control = H; clocks must be staggered in order to load both registers

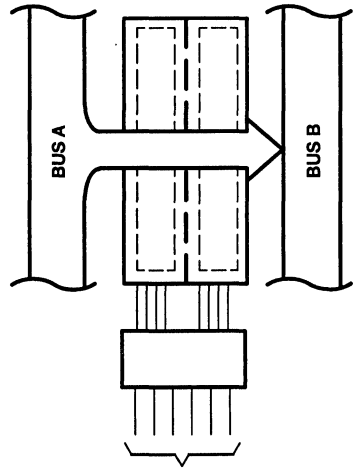
PRODUCT PREVIEW

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265



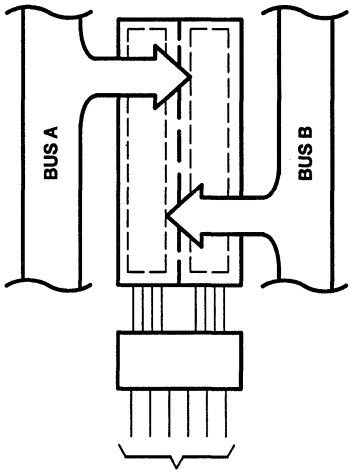
OEAB	OEBA	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



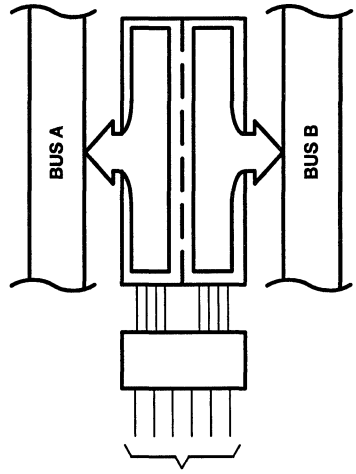
OEAB	OEBA	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



OEAB	OEBA	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B



OEAB	OEBA	CLKAB	CLKBA	SAB	SBA
H	L	H or L	H or L	H	H

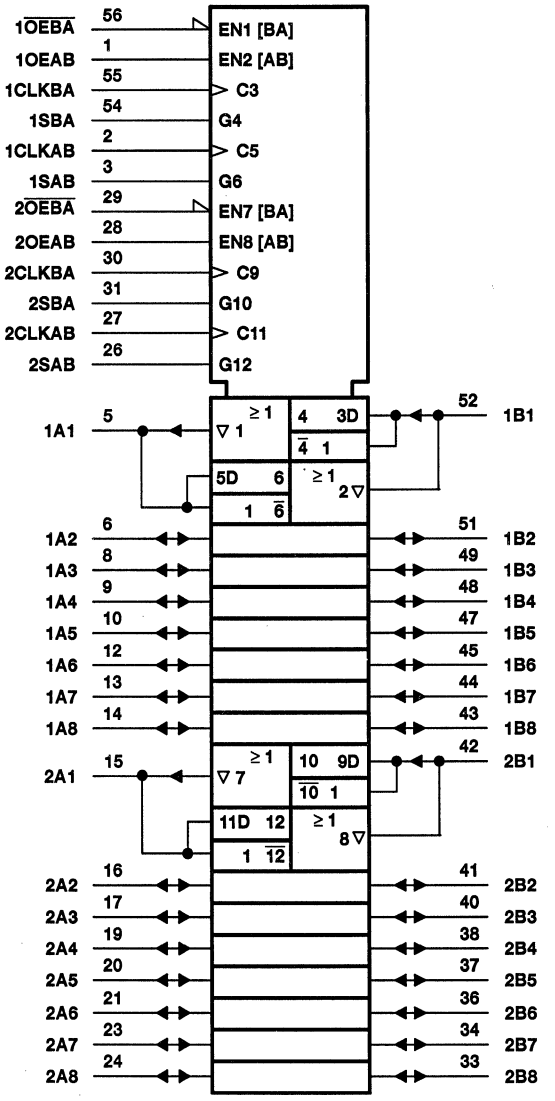
TRANSFER STORED DATA
TO A AND/OR B

Figure 1. Bus-Management Functions

PRODUCT PREVIEW

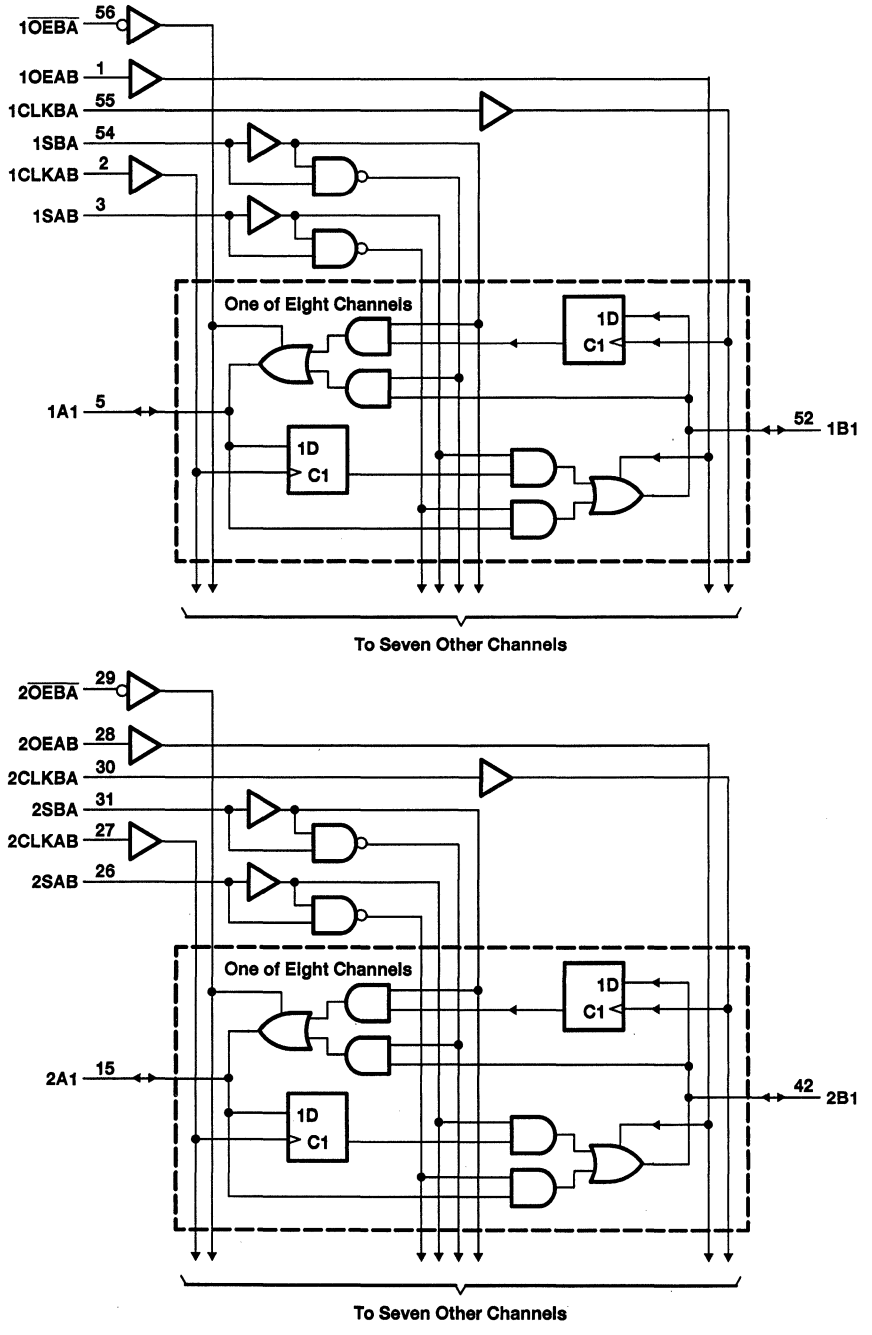
PRODUCT PREVIEW

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

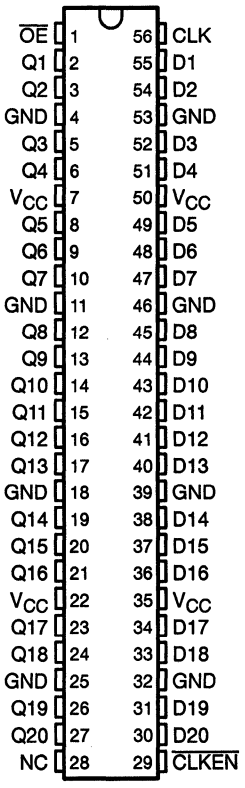
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

PRODUCT PREVIEW

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold On Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 20-bit flip-flop is designed specifically for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16721 20 flip-flops are edge-triggered D-type flip-flops with qualified clock storage. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs if the clock-enable ($\overline{CLKEN}$) input is low. If $\overline{CLKEN}$ is high, no data is stored.

A buffered output-enable ($\overline{OE}$) input places the 20 outputs in either a normal logic state (high or low) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components. $\overline{OE}$ does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16721 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

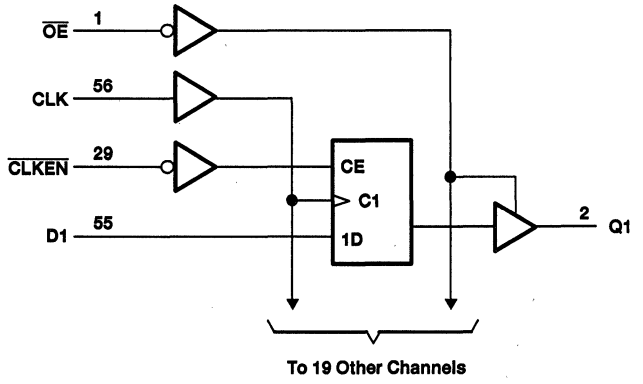
The SN74ALVCH16721 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each flip-flop)

INPUTS				OUTPUT
$\overline{OE}$	$\overline{CLKEN}$	CLK	D	Q
L	H	X	X	Q_0
L	L	↑	H	H
L	L	↑	L	L
L	L	L or H	X	Q_0
H	X	X	X	Z

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA,	V_{IH} = 1.7 V	2.3 V	1.7			
		I_{OH} = –12 mA,	V_{IH} = 2 V	2.7 V	2.2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA,	V_{IL} = 0.7 V	2.3 V			0.7	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_{io}	Data inputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figures 1 and 2)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		ns
t_{su}	Setup time	Data before CLK↑	4		3.6		3.1		ns
		$\overline{CLKEN}$ before CLK↑	3.4		3.1		2.7		
t_h	Hold time	Data after CLK↑	0		0		0		ns
		$\overline{CLKEN}$ after CLK↑	0		0		0		

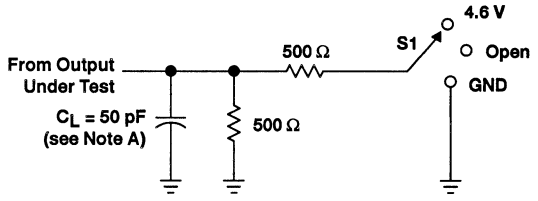
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	7	1	5.7	1	4.9	ns
t_{en}	$\overline{OE}$	Q	1	7.4	1	6.5	1	5.4	ns
t_{dis}	$\overline{OE}$	Q	1	6.2	1	5.1	1	4.8	ns

operating characteristics, T_A = 25°C

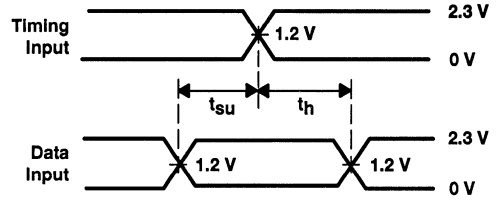
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	55	59	pF
		Outputs disabled		46	49	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

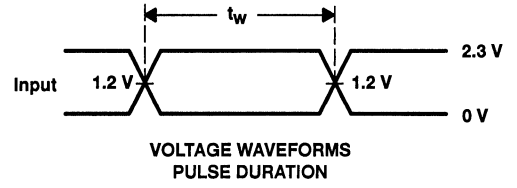


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

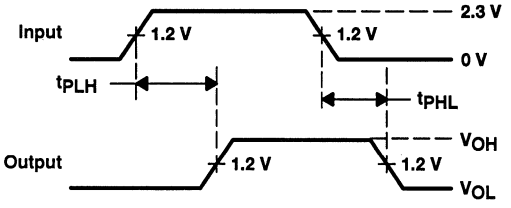
LOAD CIRCUIT



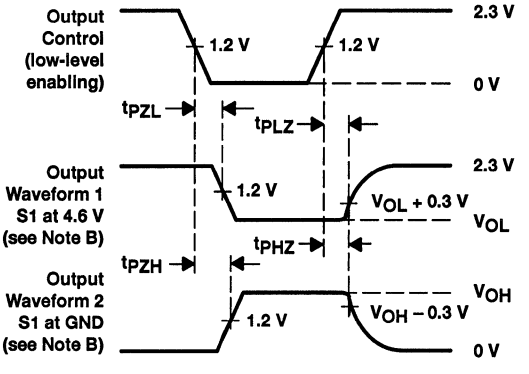
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

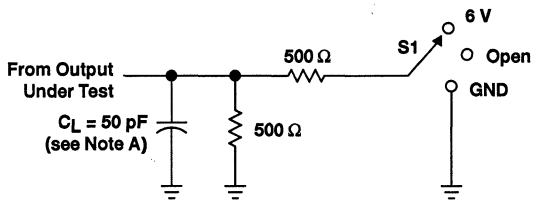


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

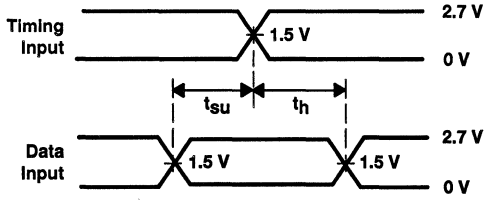
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

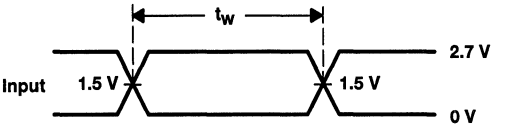


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

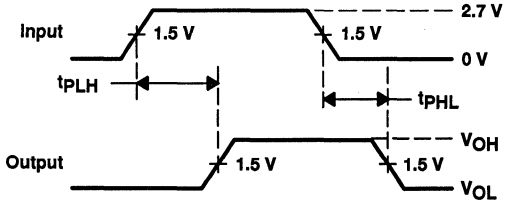
LOAD CIRCUIT



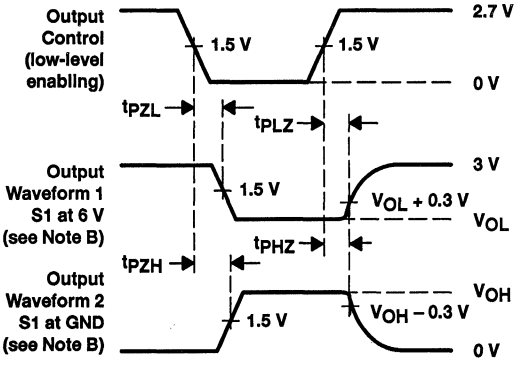
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



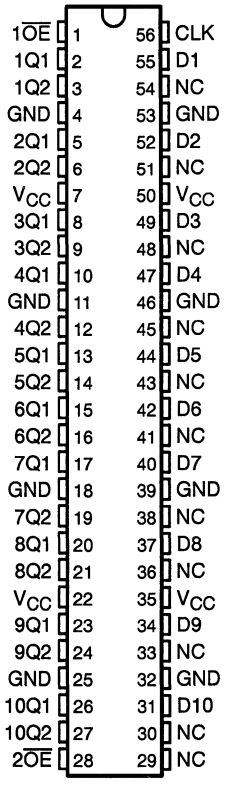
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 10-bit flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The flip-flops of the SN74ALVCH16820 are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the ten outputs in either a normal logic state (high or low logic level) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ input does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16820 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16820 is characterized for operation from –40°C to 85°C.

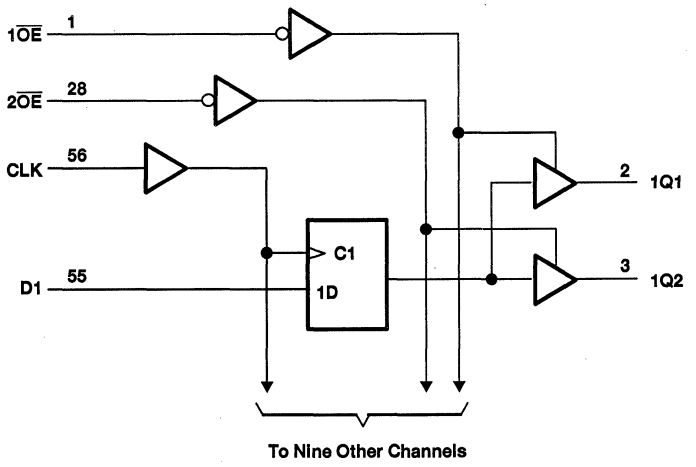
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}_n$†	CLK	D	Q_n†
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

† n = 1, 2

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		–12	mA
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.7		1.8		1.4		ns
t_h	Hold time, data after CLK↑	1.1		1.1		1		ns

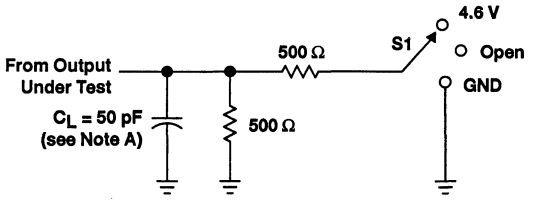
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	6.5		5.5	1	4.8	ns
t_{en}	$\overline{OE}$	Q	1	6.9		6.1	1	5	ns
t_{dis}	$\overline{OE}$	Q	1.3	5.9		5	1	4.5	ns

operating characteristics, T_A = 25°C

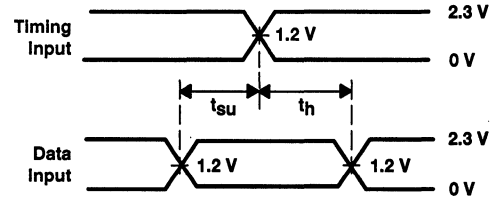
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	60	63	pF
		Outputs disabled		38	46	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

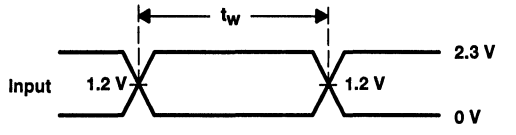


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

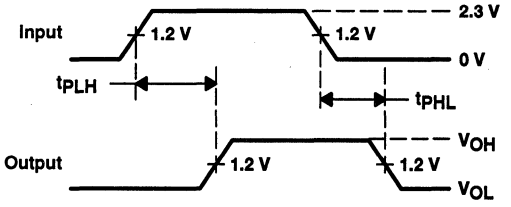
LOAD CIRCUIT



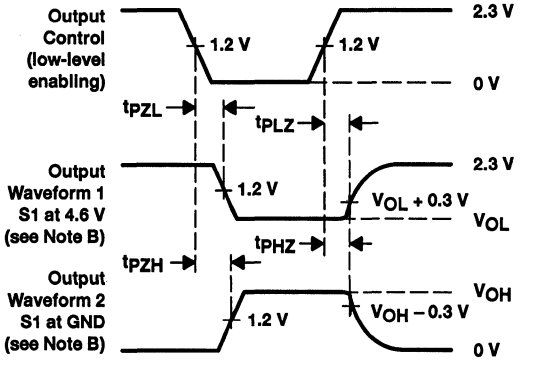
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

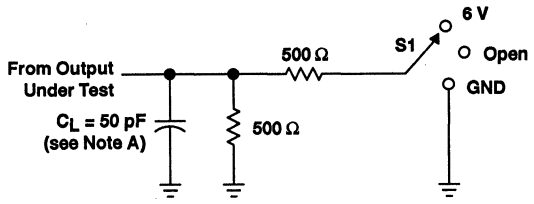


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

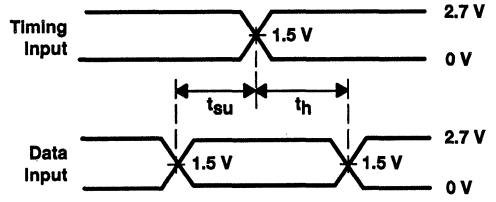
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

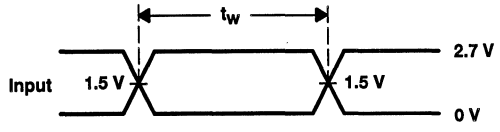


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

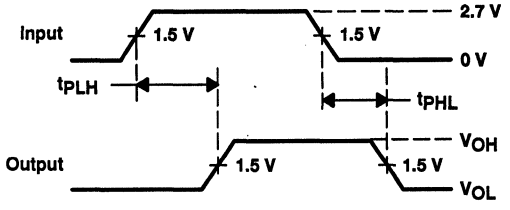
LOAD CIRCUIT



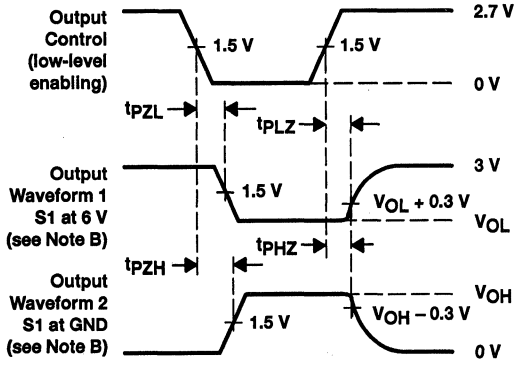
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



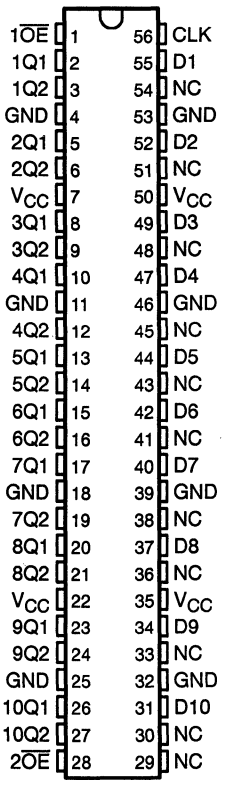
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required.**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 10-bit flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162820 flip-flops are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

description (continued)

The SN74ALVCH162820 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

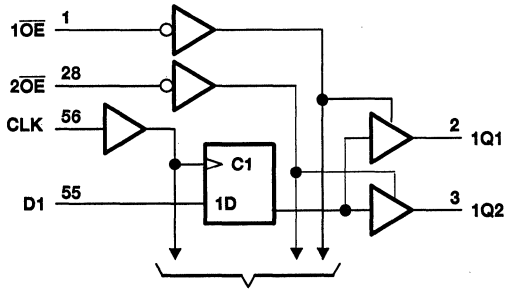
The SN74ALVCH162820 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}_n$†	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

†n = 1, 2

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−6	mA
		V_{CC} = 2.7 V		−8	
		V_{CC} = 3 V		−12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs	V_I = V_{CC} or GND		3.3 V		6		pF
C_o	Outputs	V_I = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.7		1.8		1.4		ns
t_h	Hold time, data after CLK↑	1.1		1.1		1		ns

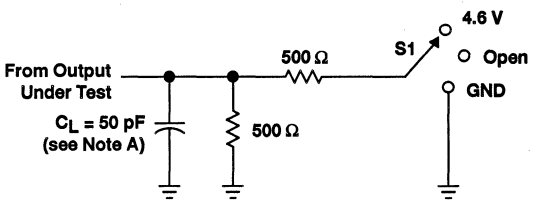
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	7		6.2	1	5.4	ns
t_{en}	$\overline{OE}$	Q	1	7.4		6.8	1	5.6	ns
t_{dis}	$\overline{OE}$	Q	1.3	6.4		5.5	1	5	ns

operating characteristics, T_A = 25°C

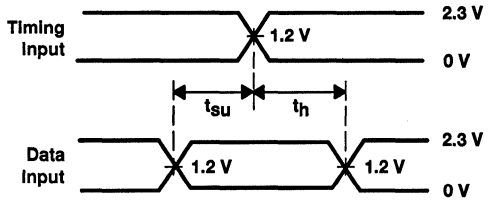
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	68	66	pF
		Outputs disabled		39	47	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

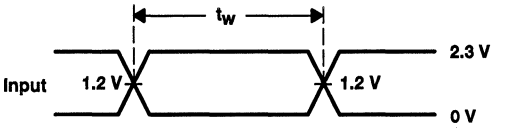


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

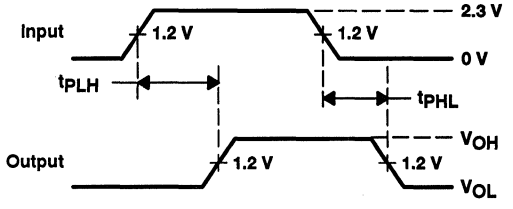
LOAD CIRCUIT



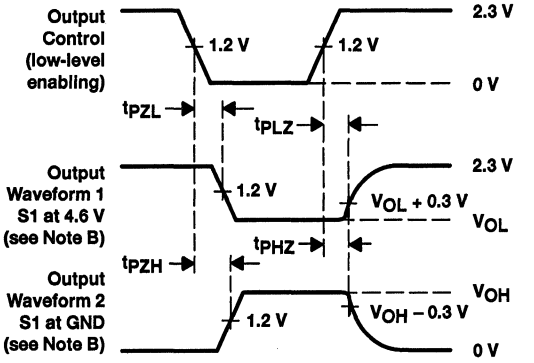
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

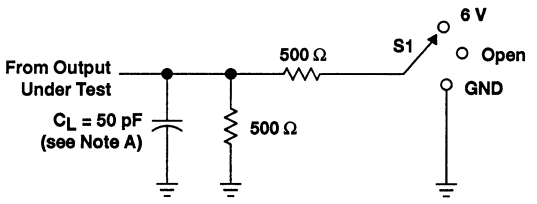


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

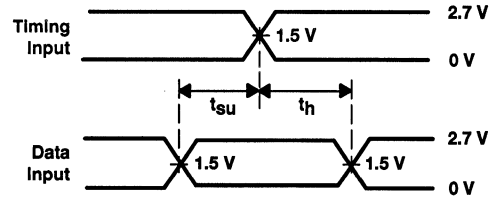
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

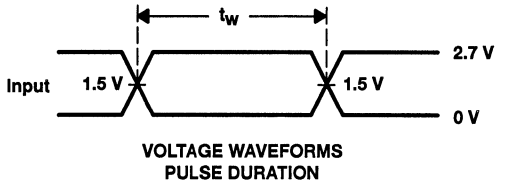


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

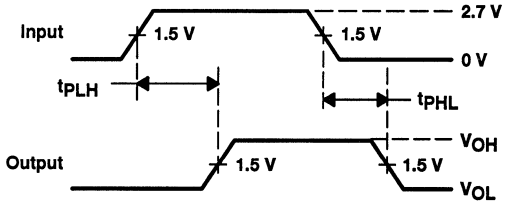
LOAD CIRCUIT



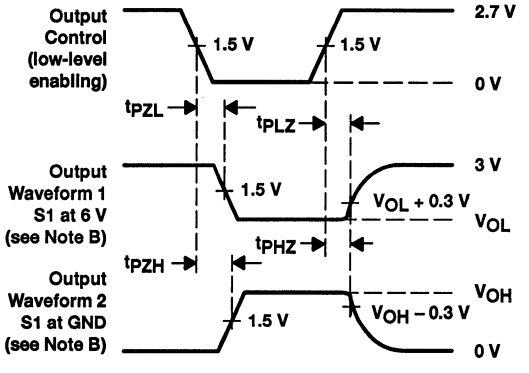
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



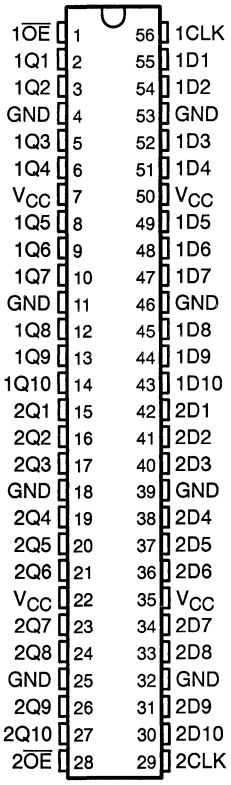
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 20-bit bus-interface flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16821 can be used as two 10-bit flip-flops or one 20-bit flip-flop. The 20 flip-flops are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the ten outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16821 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

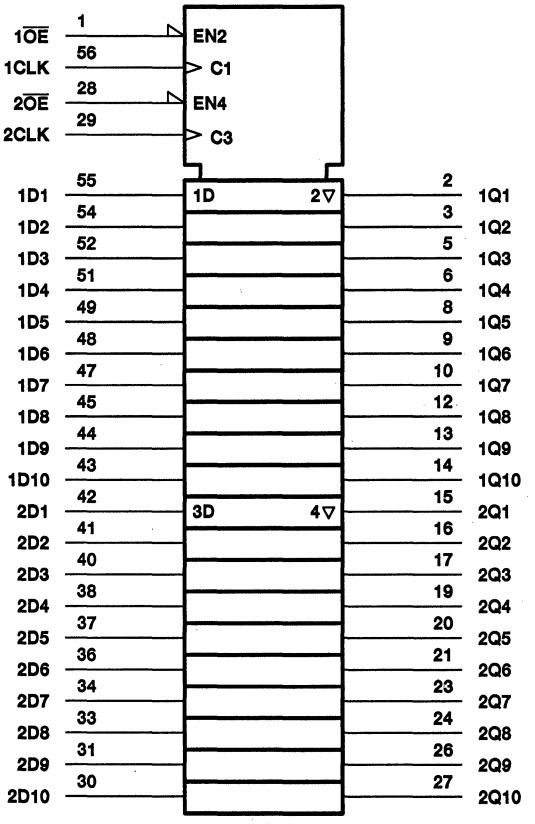
The SN74ALVCH16821 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 10-bit flip-flop)

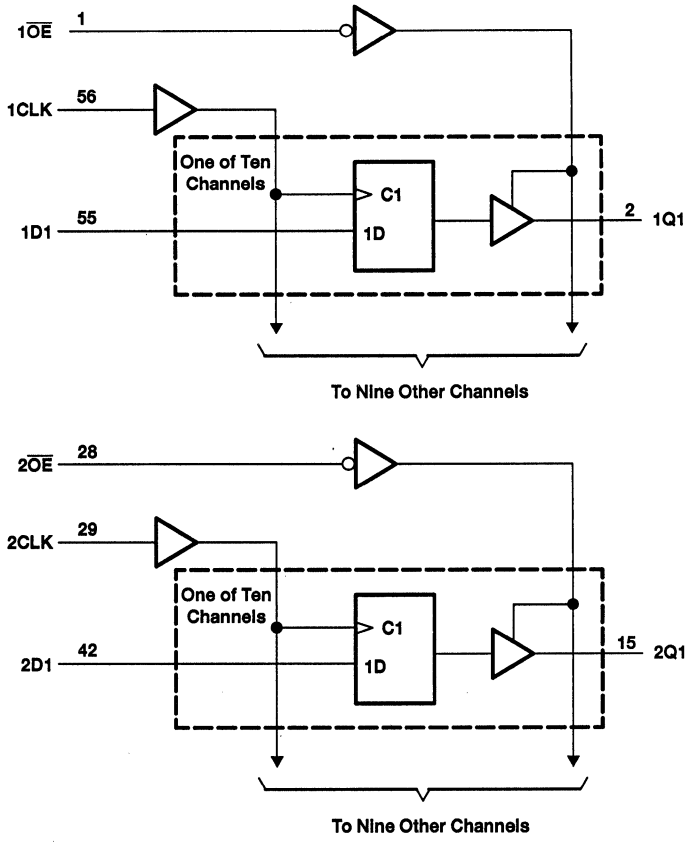
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	4.4		3.9		3.4		ns
t_h	Hold time, data after CLK↑	0		0		0		ns

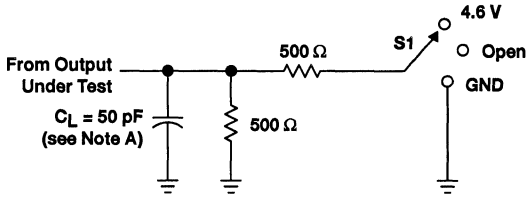
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	6.4		5.3	1	4.5	ns
t_{en}	$\overline{OE}$	Q	1	7.1		6.2	1	5.1	ns
t_{dis}	$\overline{OE}$	Q	1.4	5.9		5	1	4.6	ns

operating characteristics, T_A = 25°C

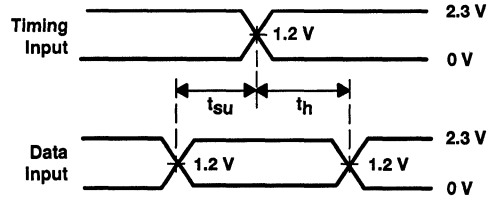
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	36	40	pF
		Outputs disabled		22	24	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

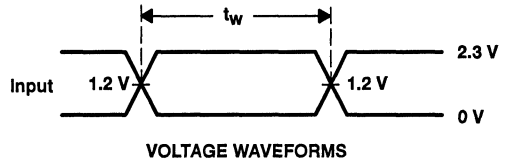


LOAD CIRCUIT

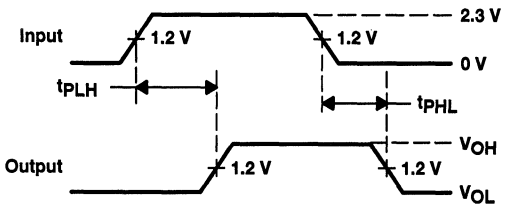
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND



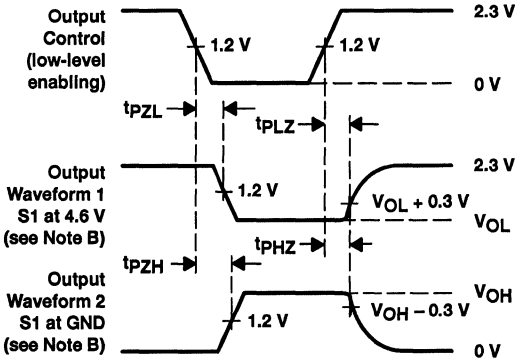
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

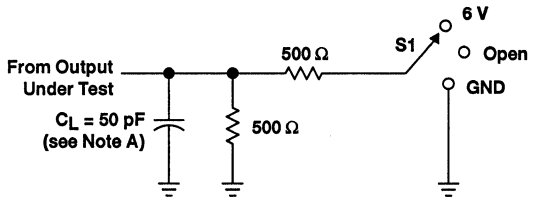


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

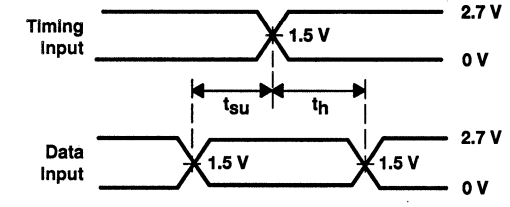
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

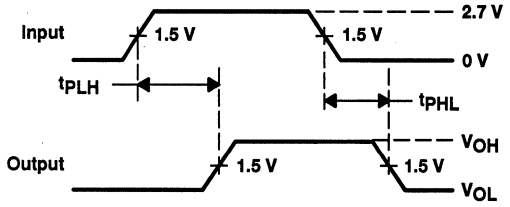


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

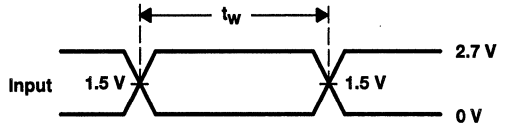
LOAD CIRCUIT



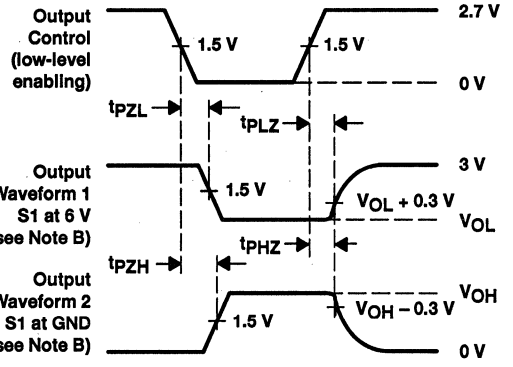
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



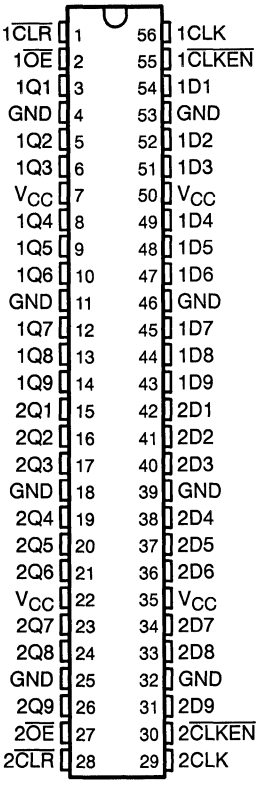
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit bus-interface flip-flop is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16823 features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing wider buffer registers, I/O ports, bidirectional bus drivers with parity, and working registers.

The SN74ALVCH16823 can be used as two 9-bit flip-flops or one 18-bit flip-flop. With the clock-enable ($\overline{CLKEN}$) input low, the D-type flip-flops enter data on the low-to-high transitions of the clock. Taking $\overline{CLKEN}$ high disables the clock buffer, thus latching the outputs. Taking the clear ($\overline{CLR}$) input low causes the Q outputs to go low independently of the clock.

A buffered output-enable ($\overline{OE}$) input can be used to place the nine outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

The output-enable ($\overline{OE}$) input does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

description (continued)

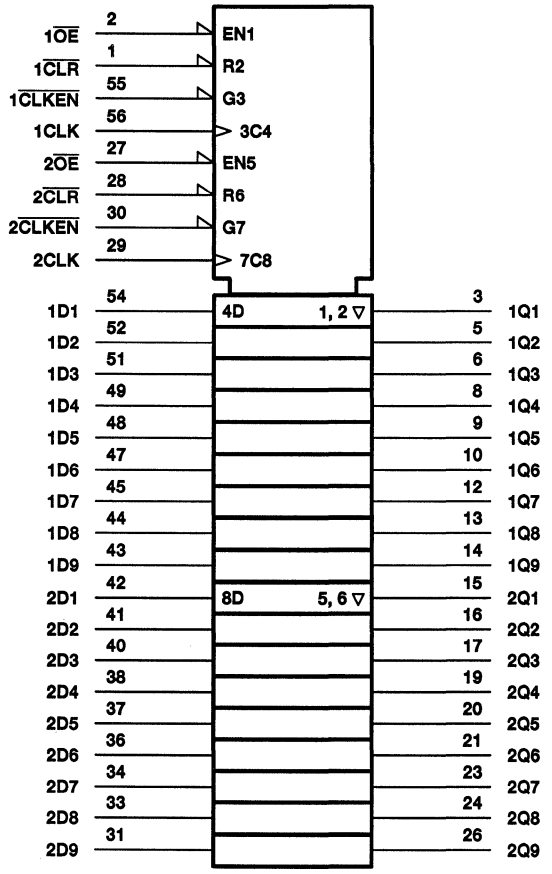
The SN74ALVCH16823 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16823 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 9-bit flip-flop)

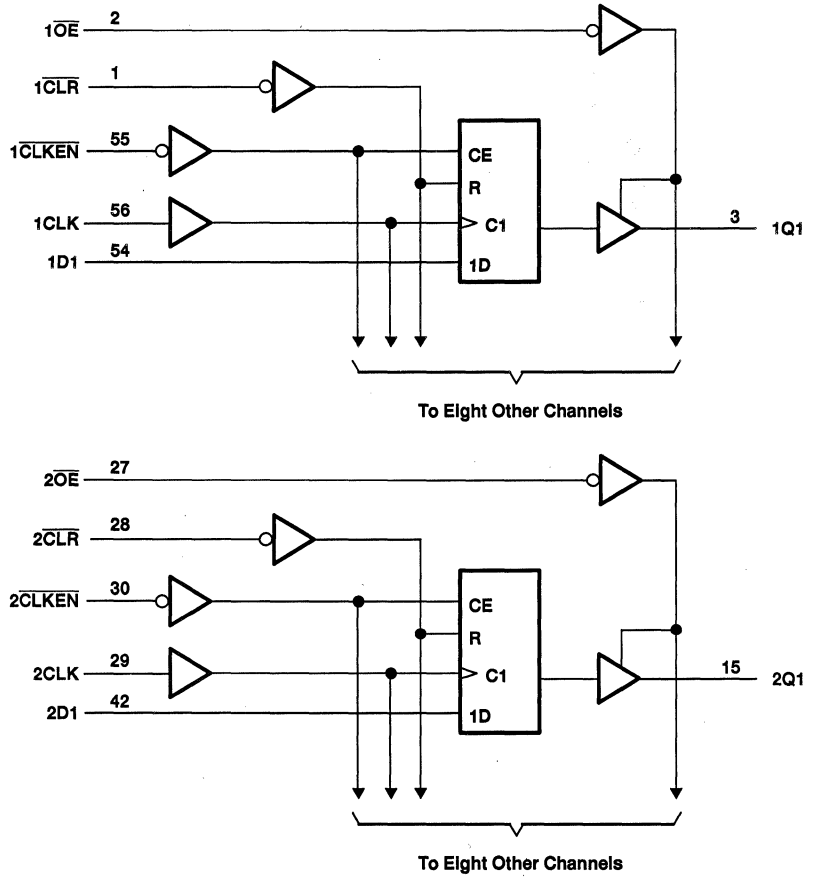
INPUTS					OUTPUT
$\overline{OE}$	$\overline{CLR}$	$\overline{CLKEN}$	CLK	D	Q
L	L	X	X	X	L
L	H	L	↑	H	H
L	H	L	↑	L	L
L	H	L	L	X	Q_0
L	H	H	X	X	Q_0
H	X	X	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
	I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
		V_{IH} = 2 V	2.7 V	2.2			
		V_{IH} = 2 V	3 V	2.4			
	I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
	I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
		V_{IL} = 0.8 V	2.7 V			0.4	
	I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I	V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.7 V		2.3 V	45			µA
	V_I = 1.7 V			−45			
	V_I = 0.8 V		3 V	75			
	V_I = 2 V			−75			
	V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i Control inputs	V_I = V_{CC} or GND		3.3 V		4.5		pF
C_i Data inputs					6.5		
C_o Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration	$\overline{CLR}$ low	3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		
t_{su}	Setup time	$\overline{CLR}$ low	0.7		0.7		0.8		ns
		Data low	1.4		1.6		1.3		
		Data high	1.1		1.1		1		
		$\overline{CLKEN}$ low	1.8		1.9		1.5		
t_h	Hold time	Data low	0.4		0.5		0.5		ns
		Data high	0.7		0.1		0.8		
		$\overline{CLKEN}$ low	0.2		0.3		0.4		

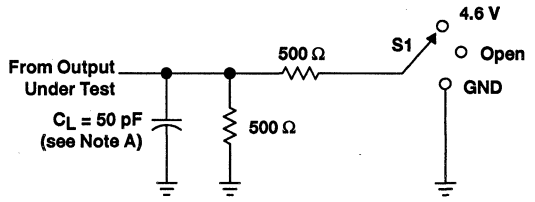
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	CLK	Q	1	6.4		5.2	1	4.5	ns
	$\overline{CLR}$	Q	1.4	6		5.2	1.2	4.6	
t_{en}	$\overline{OE}$	Q	1	6.5		5.7	1	4.8	ns
t_{dis}	$\overline{OE}$	Q	1.8	5.6		4.7	1.3	4.5	ns

operating characteristics, T_A = 25°C

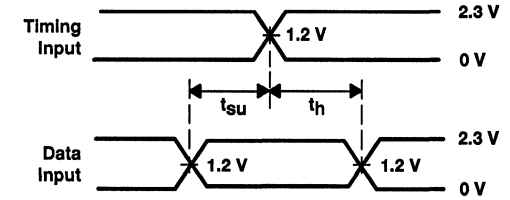
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	27	30	pF
		Outputs disabled		16	18	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

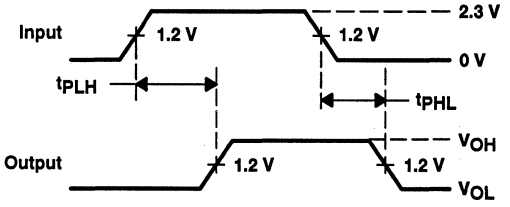


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

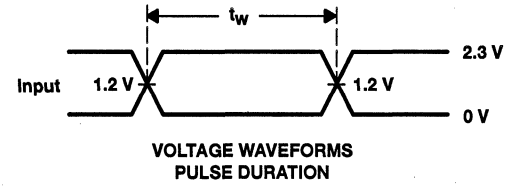
LOAD CIRCUIT



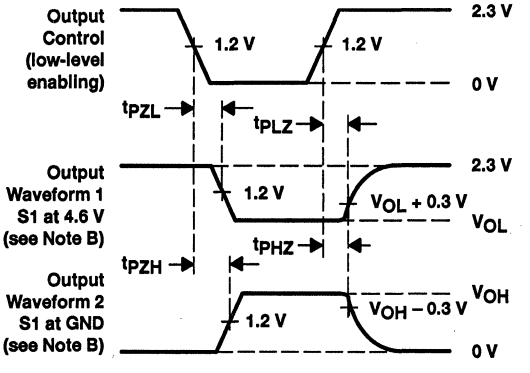
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

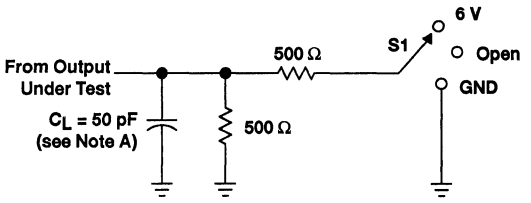


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

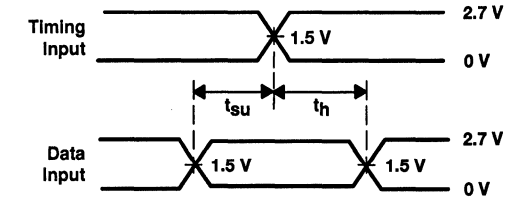
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

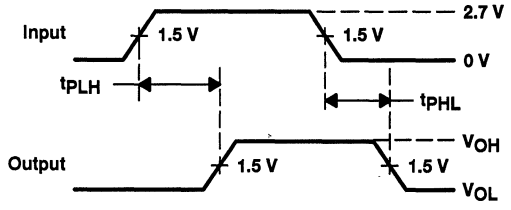


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

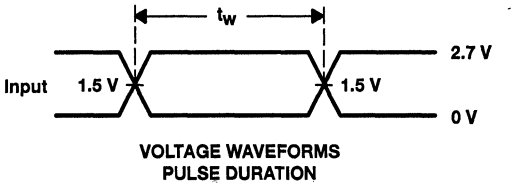
LOAD CIRCUIT



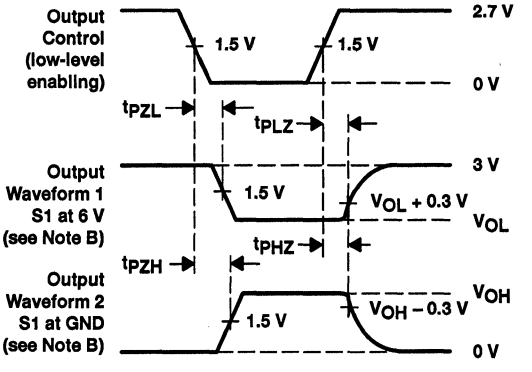
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



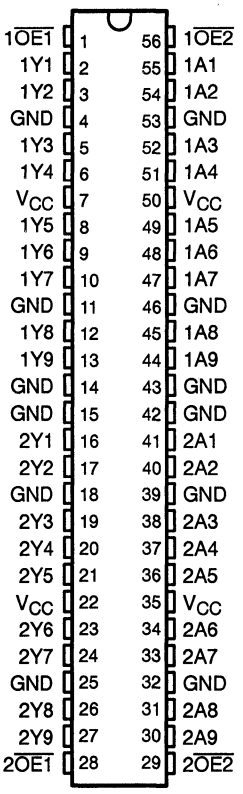
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit buffer and line driver is designed for 2.3-V to 3.6-V V_{CC} operation.

This SN74ALVCH16825 improves the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as two 9-bit buffers or one 18-bit buffer. It provides true data.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all nine affected outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The SN74ALVCH16825 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provides twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

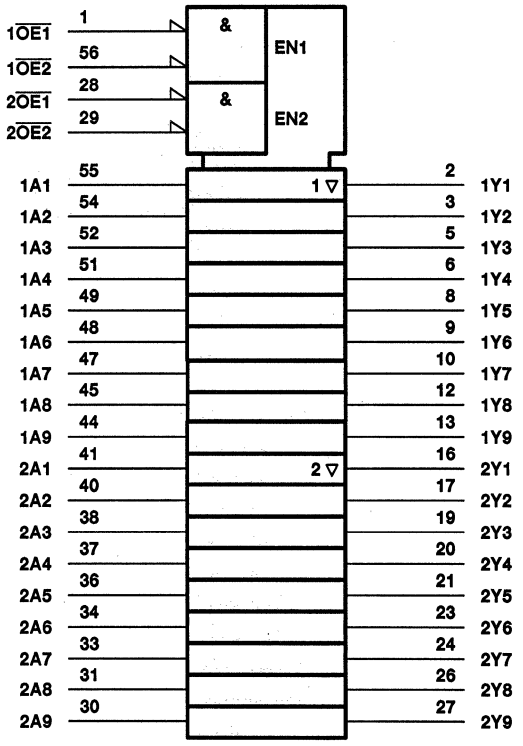
The SN74ALVCH16825 is characterized for operation from −40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 9-bit section)

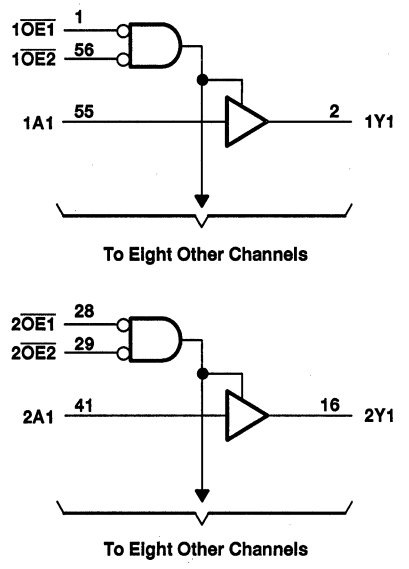
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

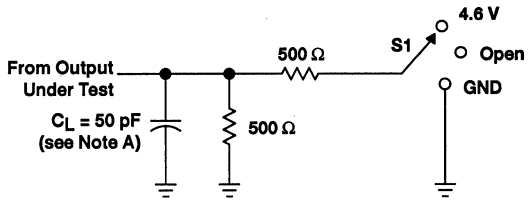
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.7		3.9	1	3.4	ns
t_{en}	$\overline{OE}$	Y	1	6.5		5.7	1	4.7	ns
t_{dis}	$\overline{OE}$	Y	1.9	5.8		4.9	1.3	4.5	ns

operating characteristics, T_A = 25°C

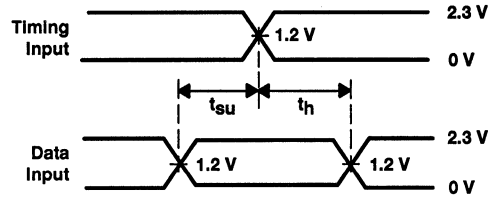
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	18	pF
		Outputs disabled		4	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

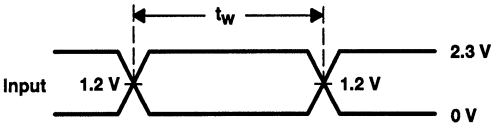


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

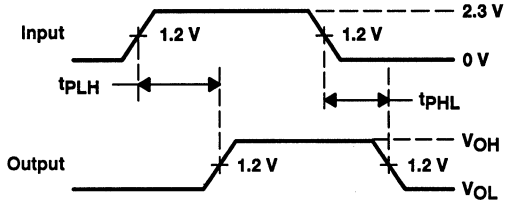
LOAD CIRCUIT



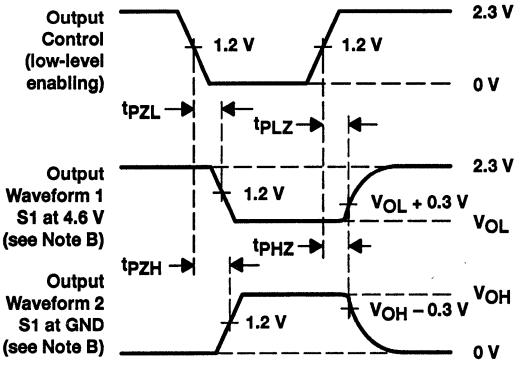
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

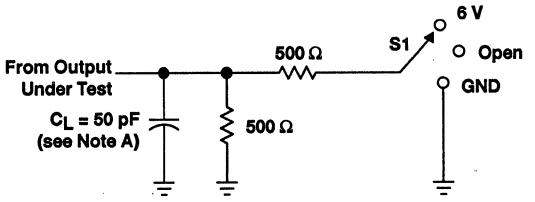


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

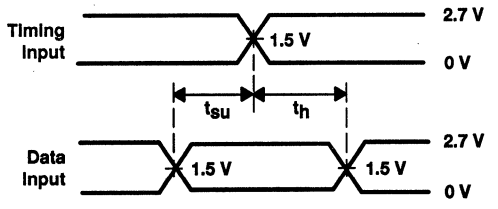
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

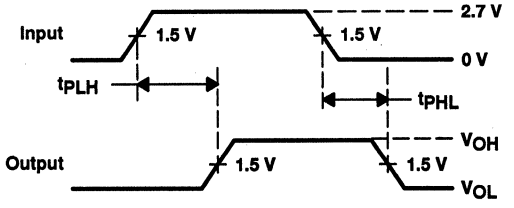


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

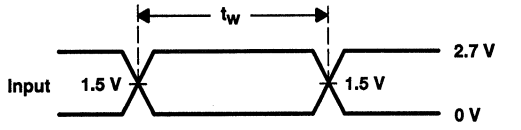
LOAD CIRCUIT



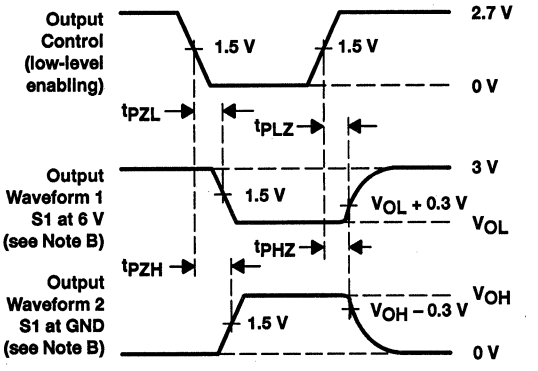
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



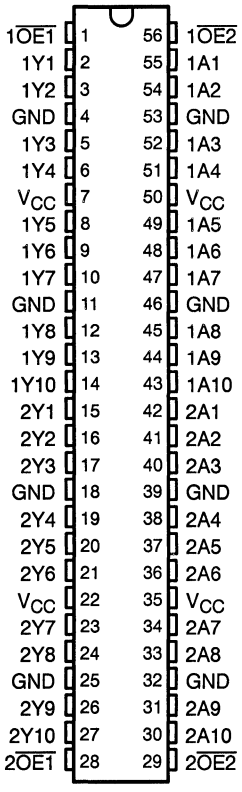
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 20-bit non-inverting buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16827 is composed of two 10-bit sections with separate output-enable signals. For either 10-bit buffer section, the two output-enable (1$\overline{OE1}$ and 1$\overline{OE2}$ or 2$\overline{OE1}$ and 2$\overline{OE2}$) inputs must both be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 10-bit buffer section are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16827 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

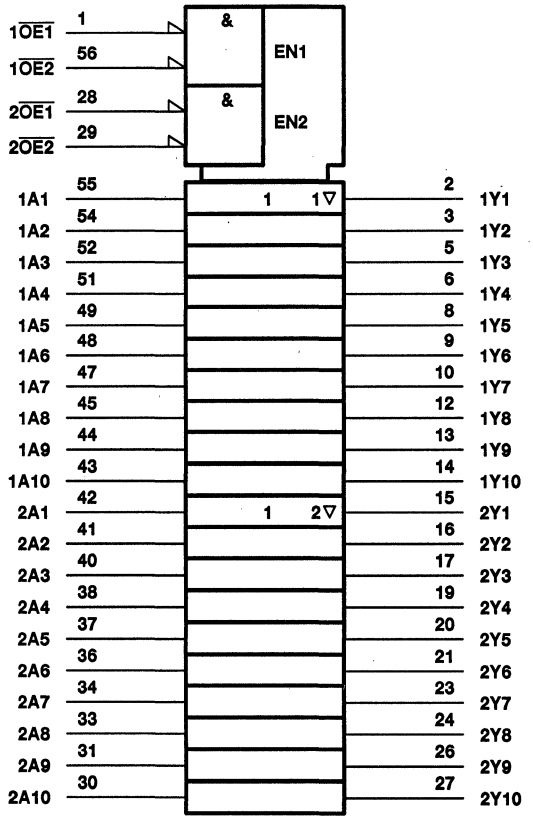
The SN74ALVCH16827 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 10-bit section)

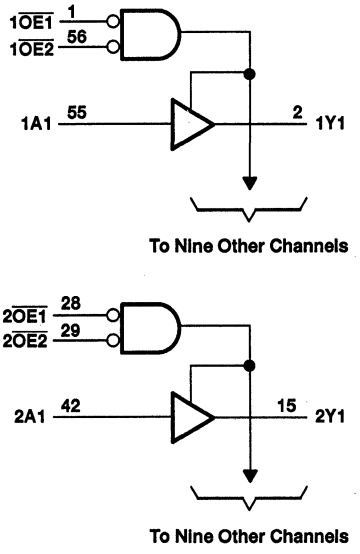
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_o	Outputs	V_O = V_{CC} or GND		3.3 V		7.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

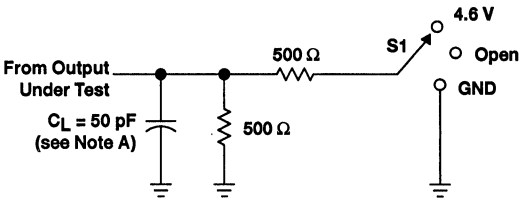
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	4.7		3.9	1	3.4	ns
t_{en}	$\overline{OE}$	Y	1	6.5		5.7	1	4.7	ns
t_{dis}	$\overline{OE}$	Y	1.9	5.8		4.9	1.3	4.5	ns

operating characteristics, T_A = 25°C

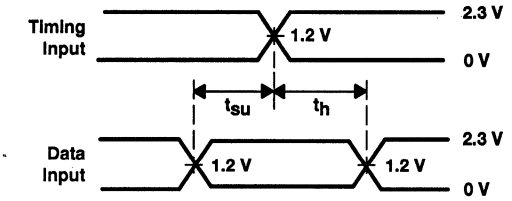
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	18	pF
		Outputs disabled		4	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

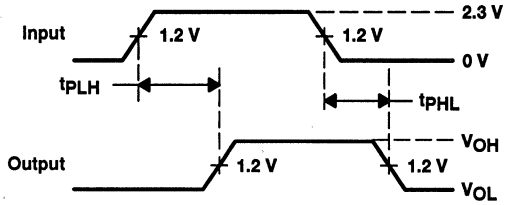


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

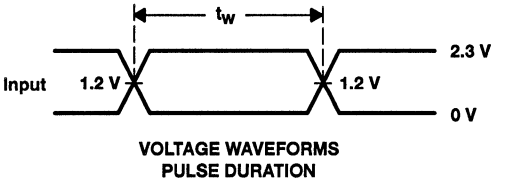
LOAD CIRCUIT



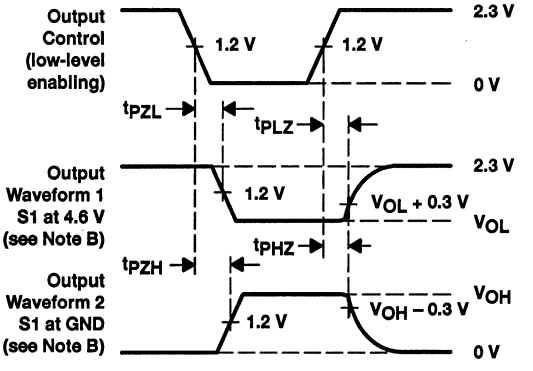
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

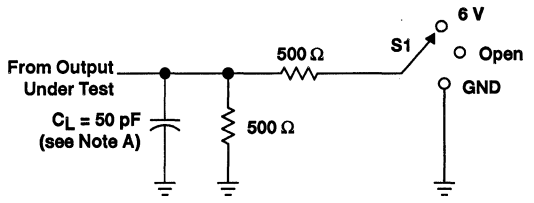


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

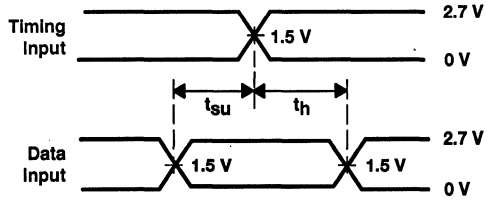
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

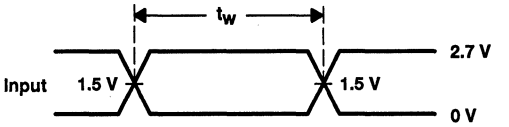


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

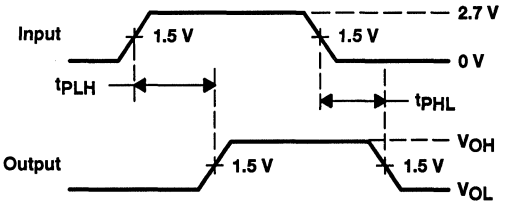
LOAD CIRCUIT



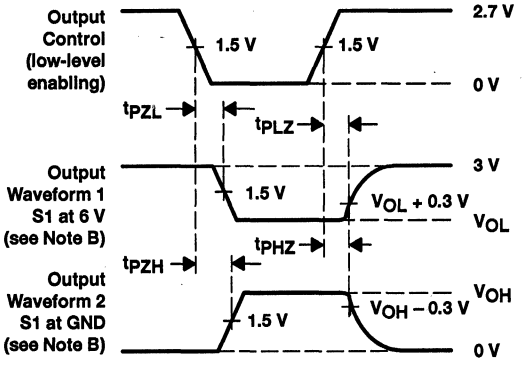
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



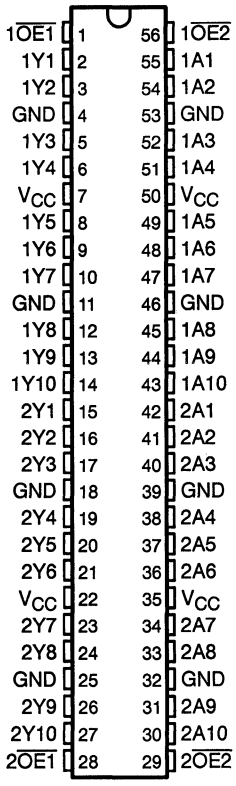
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 20-bit noninverting buffer/driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH162827 is composed of two 10-bit sections with separate output-enable signals. For either 10-bit buffer section, the two output-enable ($1\overline{OE1}$ and $1\overline{OE2}$ or $2\overline{OE1}$ and $2\overline{OE2}$) inputs must both be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 10-bit buffer section are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162827 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

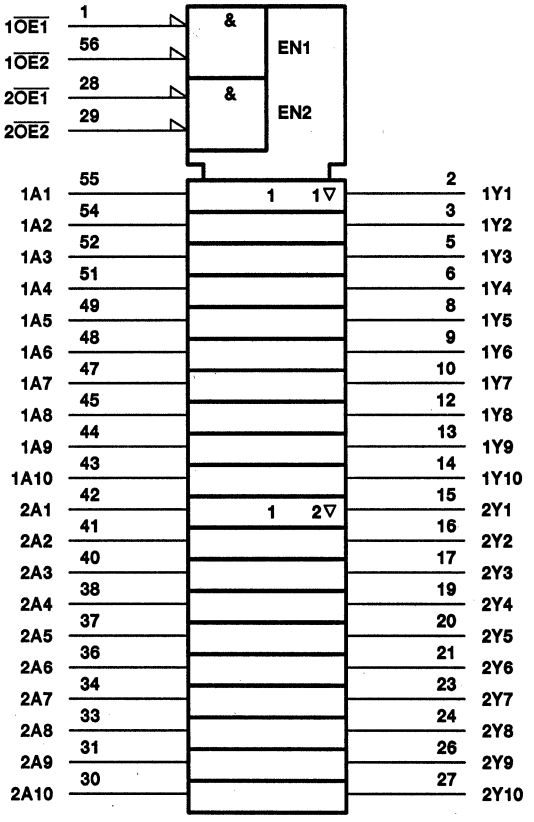
The SN74ALVCH162827 is characterized for operation from −40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 10-bit section)

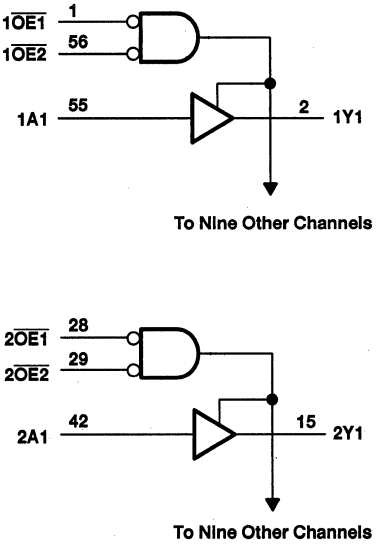
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−6	mA
		V_{CC} = 2.7 V		−8	
		V_{CC} = 3 V		−12	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		6	mA
		V_{CC} = 2.7 V		8	
		V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –4 mA,	V_{IH} = 1.7 V	2.3 V	1.9			
		I_{OH} = –6 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 4 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 6 mA	V_{IL} = 0.7 V	2.3 V			0.55	
			V_{IL} = 0.8 V	3 V			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs	V_I = V_{CC} or GND		3.3 V		6		pF
C_o	Outputs	V_I = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

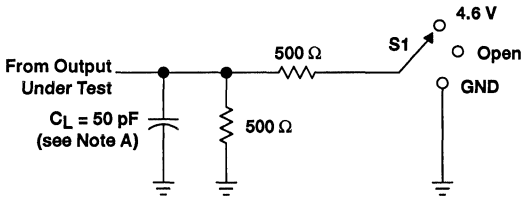
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.3	5.2		4.6	1.5	4	ns
t_{en}	$\overline{OE}$	Y	1.5	7		6.4	1.6	5.3	ns
t_{dis}	$\overline{OE}$	Y	2.4	6.3		5.4	1.8	4.9	ns

operating characteristics, T_A = 25°C

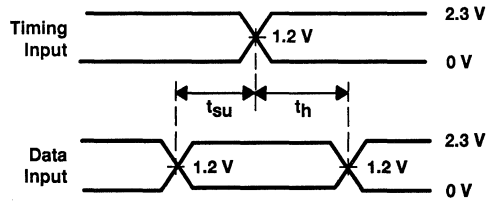
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	16	18	pF
		Outputs disabled		4	6	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

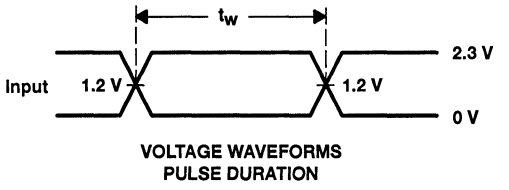


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

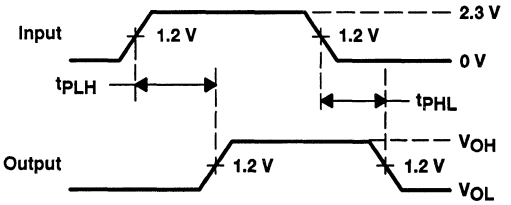
LOAD CIRCUIT



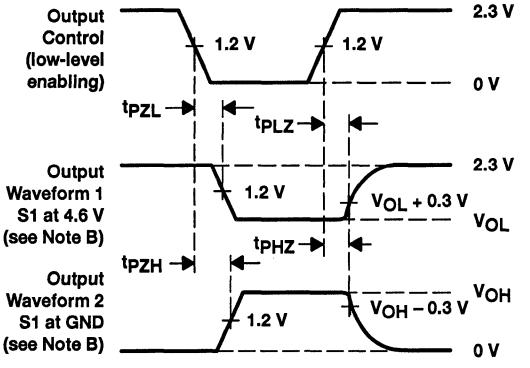
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

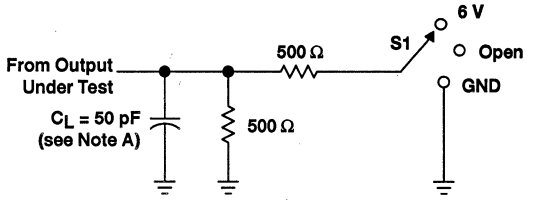


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

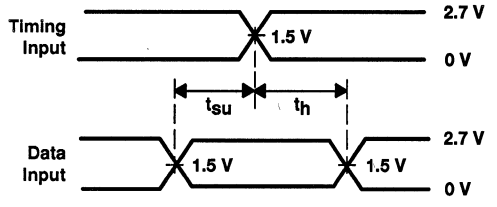
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

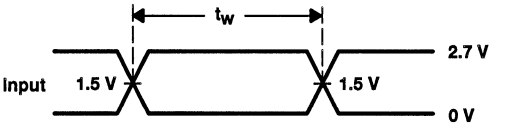


LOAD CIRCUIT

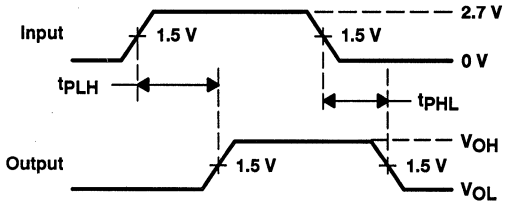
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



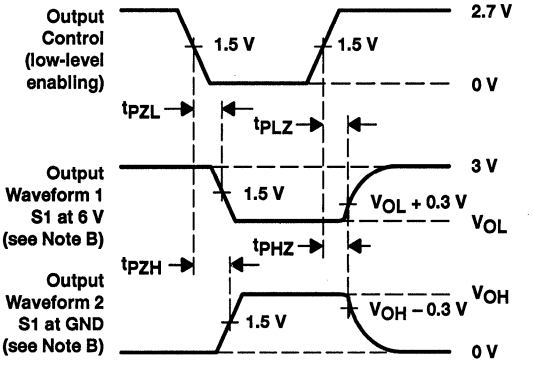
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



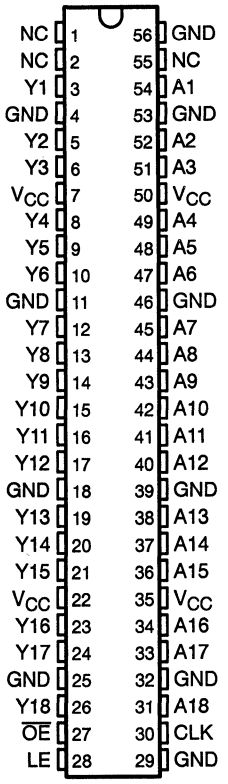
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

This 18-bit universal bus driver is designed for 2.3-V to 3.6-V V_{CC} operation.

Data flow from A to Y is controlled by the output-enable ($\overline{OE}$). The device operates in the transparent mode when LE is high. The A data is latched if CLK is held at a high or low logic level. If LE is low, the A-bus data is stored in the latch/flip-flop on the low-to-high transition of CLK. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16835 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16835 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

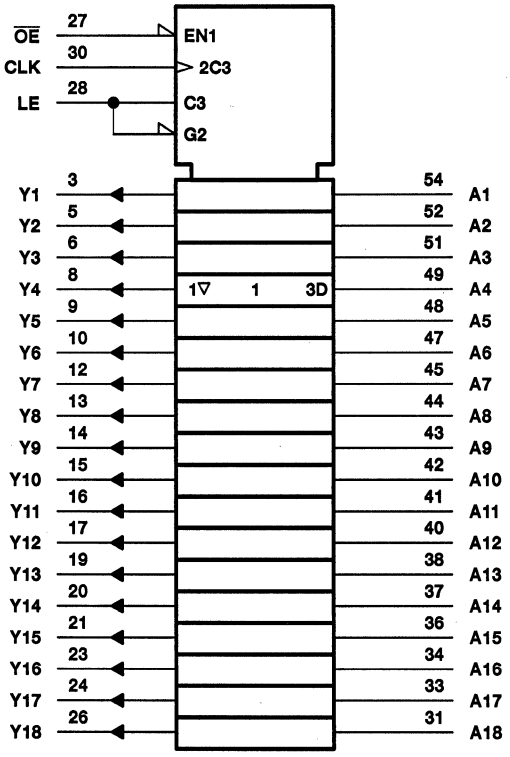
FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	LE	CLK	A	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H
L	L	H	X	Y_0†
L	L	L	X	Y_0‡

† Output level before the indicated steady-state input conditions were established, provided that CLK is high before LE goes low

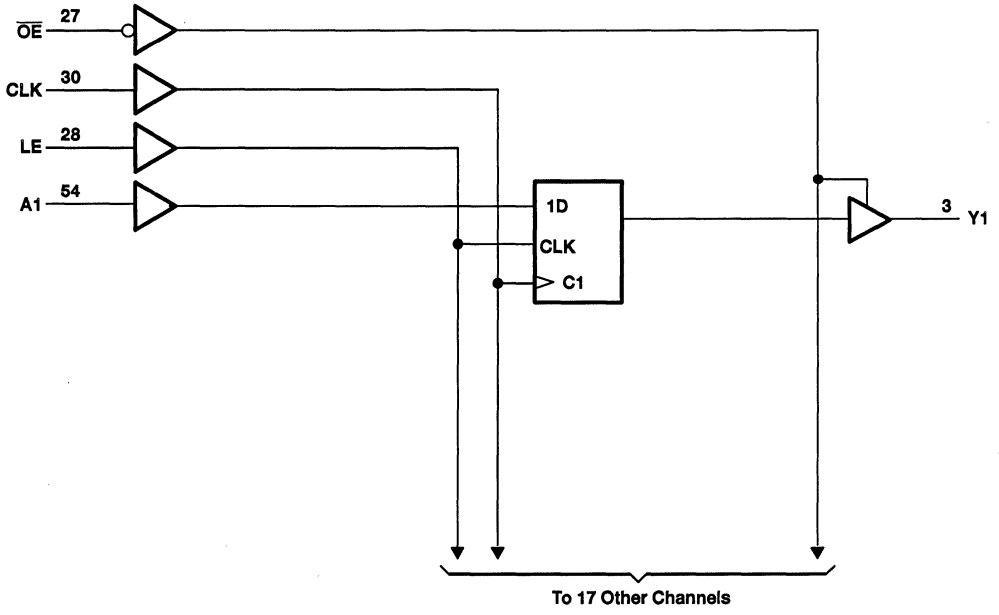
‡ Output level before the indicated steady-state input conditons were established

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
	Data inputs					6		
C_{io}	Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	MHz
t_w	Pulse duration	LE high	3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		
t_{su}	Setup time	Data before CLK↑	2.2		2.1		1.7		ns
		Data before LE↓, CLK high	1.9		1.6		1.5		
		Data before LE↓, CLK low	1.3		1.1		1		
t_h	Hold time	Data after CLK↑	0.6		0.6		0.7		ns
		Data after LE↓, CLK high or low	1.4		1.7		1.4		

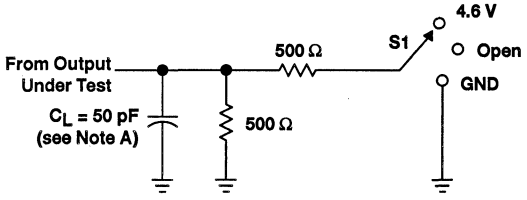
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			150		150		150		MHz
t_{pd}	A	Y	1.3	5.4		4.5	1	3.9	ns
	LE	Y	1.8	6.3		5.3	1.3	4.6	
	CLK	Y	1.9	6.7		5.6	1.4	4.9	
t_{en}	$\overline{OE}$	Y	1.5	6.8		6	1.1	5	ns
t_{dis}	$\overline{OE}$	Y	2.1	5.5		4.6	1.3	4.2	ns

operating characteristics, T_A = 25°C

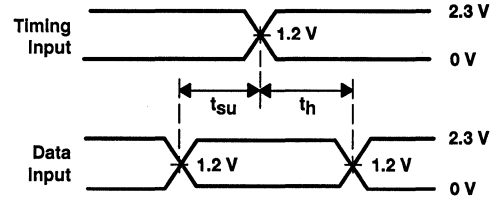
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	26	31	pF
		Outputs disabled		12	14	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

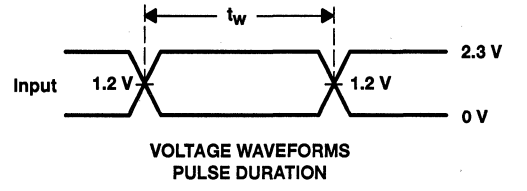


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

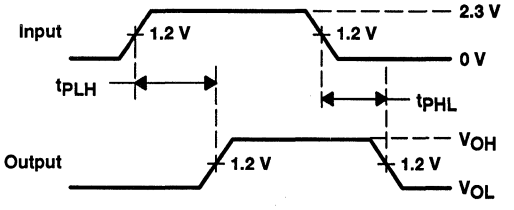
LOAD CIRCUIT



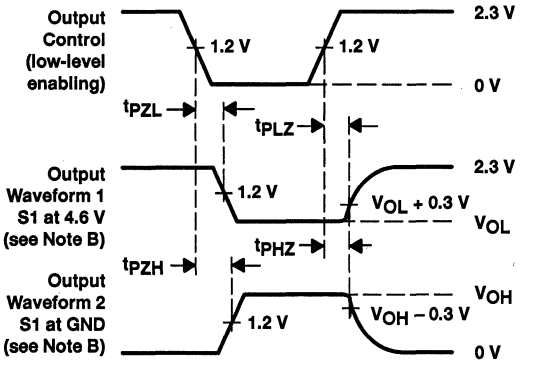
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

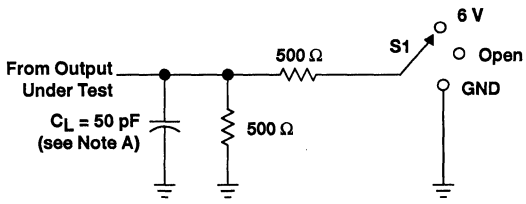


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

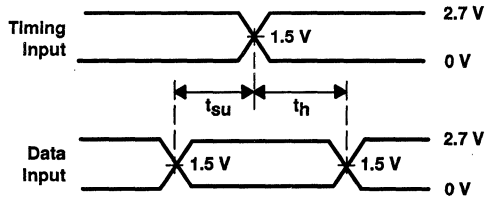
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

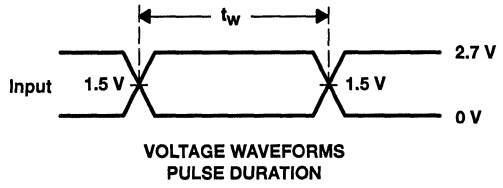


LOAD CIRCUIT

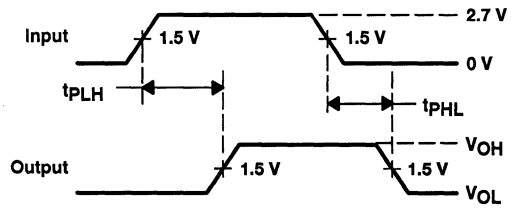
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



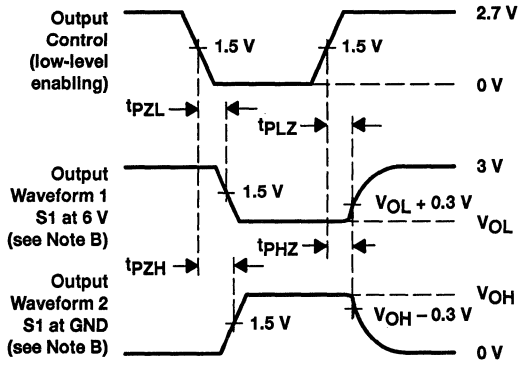
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



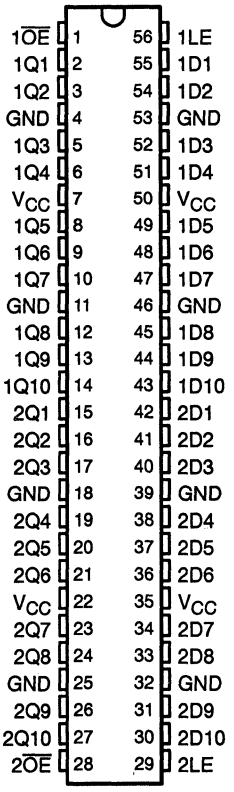
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- Member of the Texas Instruments *Widebus*™ Family
- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

DGG OR DL PACKAGE
(TOP VIEW)



description

This 20-bit bus-interface D-type latch is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16841 features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, unidirectional bus drivers, and working registers.

The SN74ALVCH16841 can be used as two 10-bit latches or one 20-bit latch. The 20 latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs. While the latch-enable (1LE or 2LE) input is high, the Q outputs of the corresponding 10-bit latch follow the D inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ($1\overline{OE}$ or $2\overline{OE}$) input can be used to place the outputs of the corresponding 10-bit latch in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly.

The output-enable ($\overline{OE}$) input does not affect the internal operation of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The SN74ALVCH16841 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

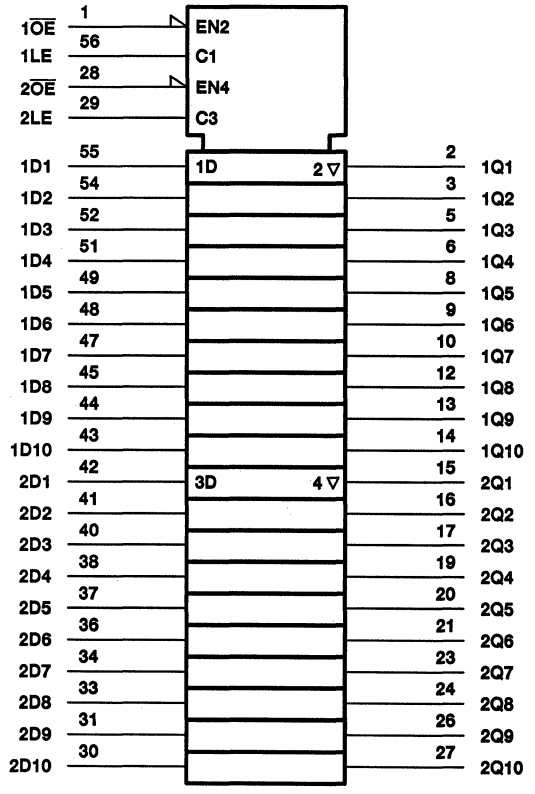
The SN74ALVCH16841 is characterized for operation from −40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 10-bit latch)

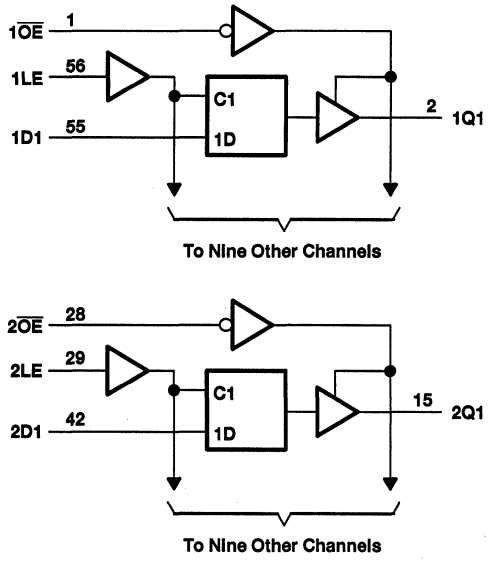
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
	I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
		V_{IH} = 2 V	2.7 V	2.2			
		V_{IH} = 2 V	3 V	2.4			
	I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
	I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
		V_{IL} = 0.8 V	2.7 V			0.4	
	I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I	V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.7 V		2.3 V	45			µA
	V_I = 1.7 V			−45			
	V_I = 0.8 V		3 V	75			
	V_I = 2 V			−75			
	V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
C_i Data inputs					6		
C_o Outputs	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended ranges of supply voltage and operating free-air temperature, (unless otherwise noted) (see Figures 1 and 2)

PARAMETER		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high or low	3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE↑	0.9		0.7		1.1		ns
t_h	Hold time, data after LE↑	1.2		1.5		1.1		ns

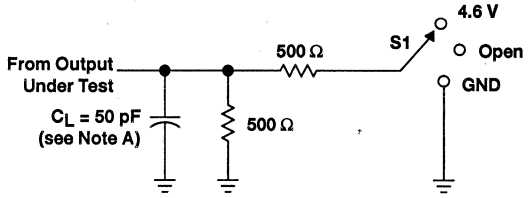
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1.1	5.6		4.7	1.2	3.9	ns
	LE	Q	1	6.2		5.1	1	4.3	
t_{en}	$\overline{OE}$	Q	1	6.7		6	1	4.9	ns
t_{dis}	$\overline{OE}$	Q	1.8	5.5		4.3	1.3	4.1	ns

operating characteristics, T_A = 25°C

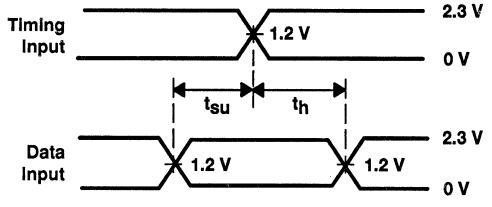
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	12	20	pF
		Outputs disabled		1	3	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

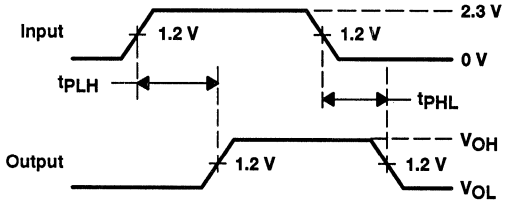


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

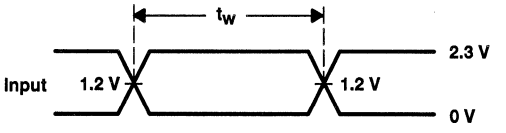
LOAD CIRCUIT



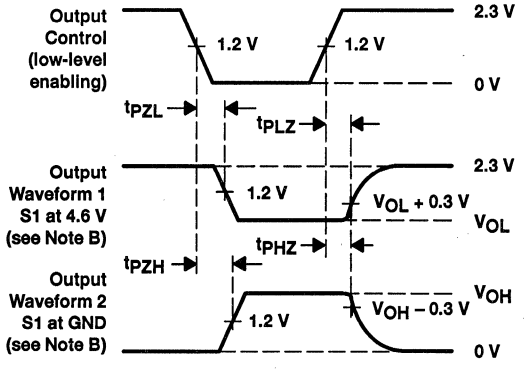
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

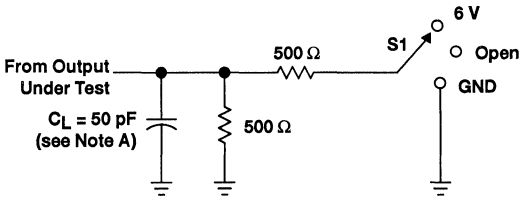


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

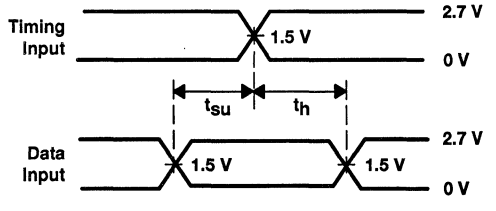
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

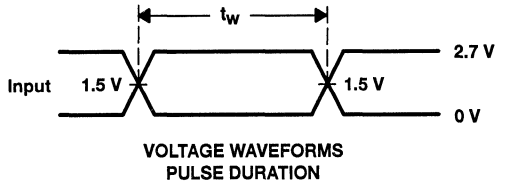


LOAD CIRCUIT

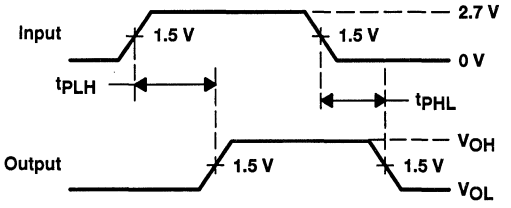
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



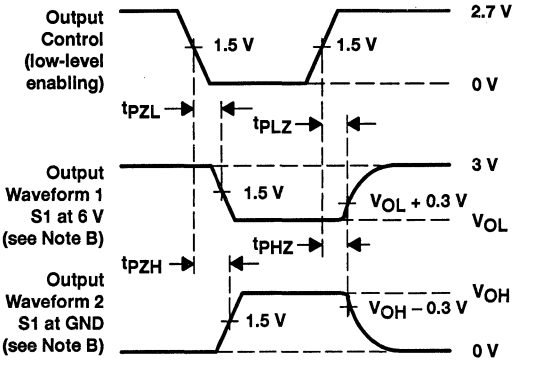
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



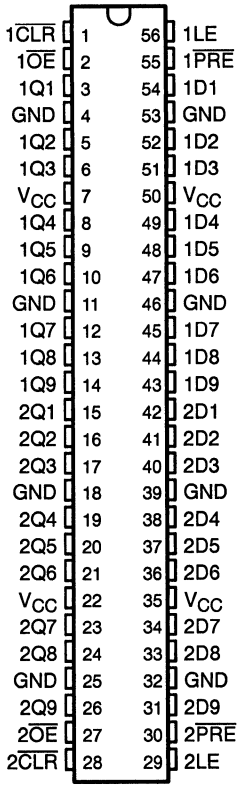
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 18-bit bus-interface D-type latch is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16843 features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, unidirectional bus drivers, and working registers.

The SN74ALVCH16843 can be used as two 9-bit latches or one 18-bit latch. The 18 latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the nine outputs in either a normal logic state (high or low logic levels) or a high-impedance state. The outputs also are in the high-impedance state during power-up and power-down conditions. The outputs remain in the high-impedance state while the device is powered down. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

The output-enable ($\overline{OE}$) input does not affect the internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating inputs at a valid logic level.

The SN74ALVCH16843 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

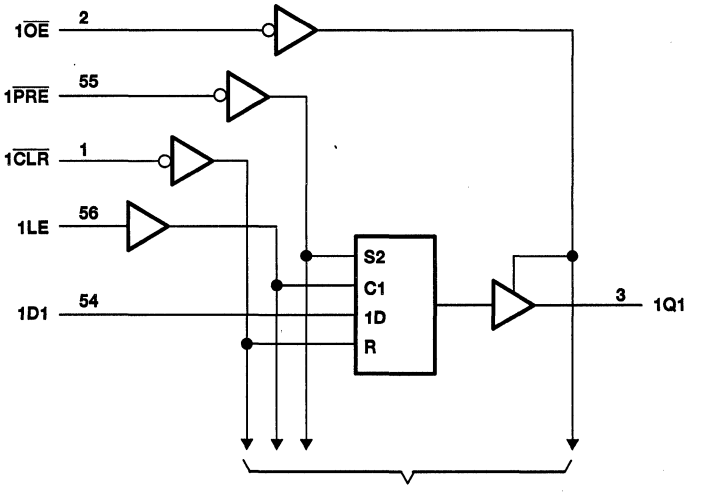
The SN74ALVCH16843 is characterized for operation from −40°C to 85°C.

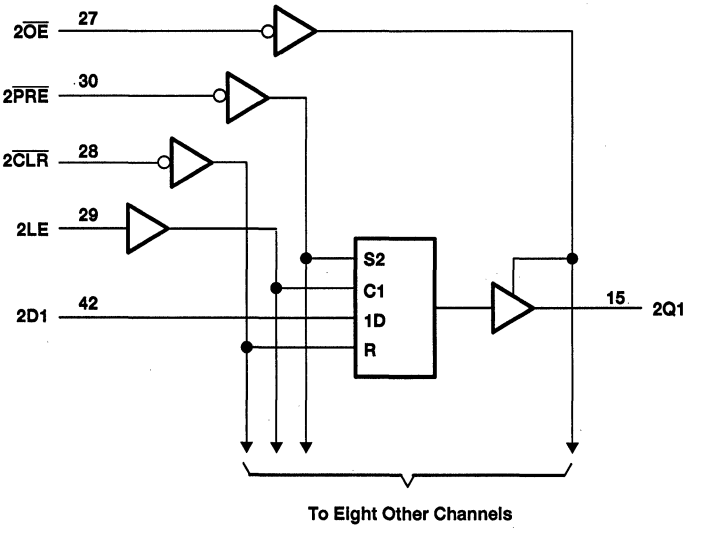
PRODUCT PREVIEW

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

PRODUCT PREVIEW

logic diagram (positive logic)





FUNCTION TABLE
(each 9-bit latch)

INPUTS					OUTPUT
$\overline{PRE}$	$\overline{CLR}$	$\overline{OE}$	LE	D	Q
L	X	L	X	X	H
H	L	L	X	X	L
H	H	L	H	L	L
H	H	L	H	H	H
H	H	L	L	X	Q_0
X	X	H	X	X	Z

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

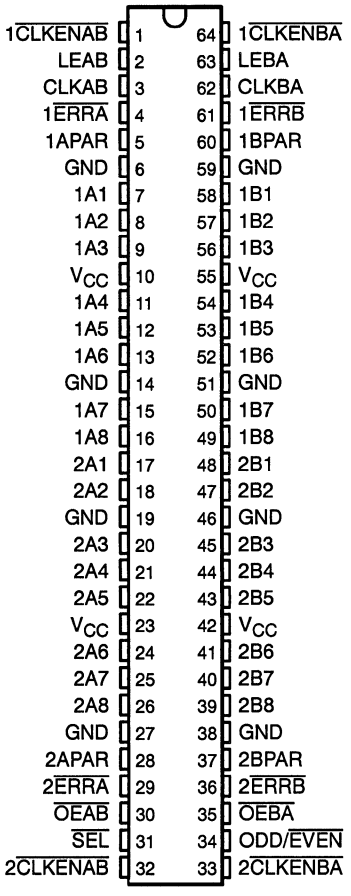
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
	Data inputs							
C_o	Outputs	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- **Member of the Texas Instruments *Widebus+*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **Simultaneously Generates and Checks Parity**
- **Option to Select Generate Parity and Check or Feed-Through Data/Parity in A-to-B or B-to-A Directions**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Thin Shrink Small-Outline (DGG) Package**

DGG PACKAGE
(TOP VIEW)



description

This 18-bit (dual-octal) noninverting registered transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16901 is a dual 9-bit to dual 9-bit parity transceiver with registers. The device can operate as a feed-through transceiver or it can generate/check parity from the two 8-bit data buses in either direction.

The SN74ALVCH16901 features independent clock (CLKAB or CLKBA), latch-enable (LEAB or LEBA), and dual 9-bit clock-enable ($\overline{\text{CLKENAB}}$ or $\overline{\text{CLKENBA}}$) inputs. It also provides parity-enable ($\overline{\text{SEL}}$) and parity-select (ODD/$\overline{\text{EVEN}}$) inputs and separate error-signal ($\overline{\text{ERRA}}$ or $\overline{\text{ERRB}}$) outputs for checking parity. The direction of data flow is controlled by $\overline{\text{OEAB}}$ and $\overline{\text{OEBA}}$. When $\overline{\text{SEL}}$ is low, the parity functions are enabled. When $\overline{\text{SEL}}$ is high, the parity functions are disabled and the device acts as an 18-bit registered transceiver.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

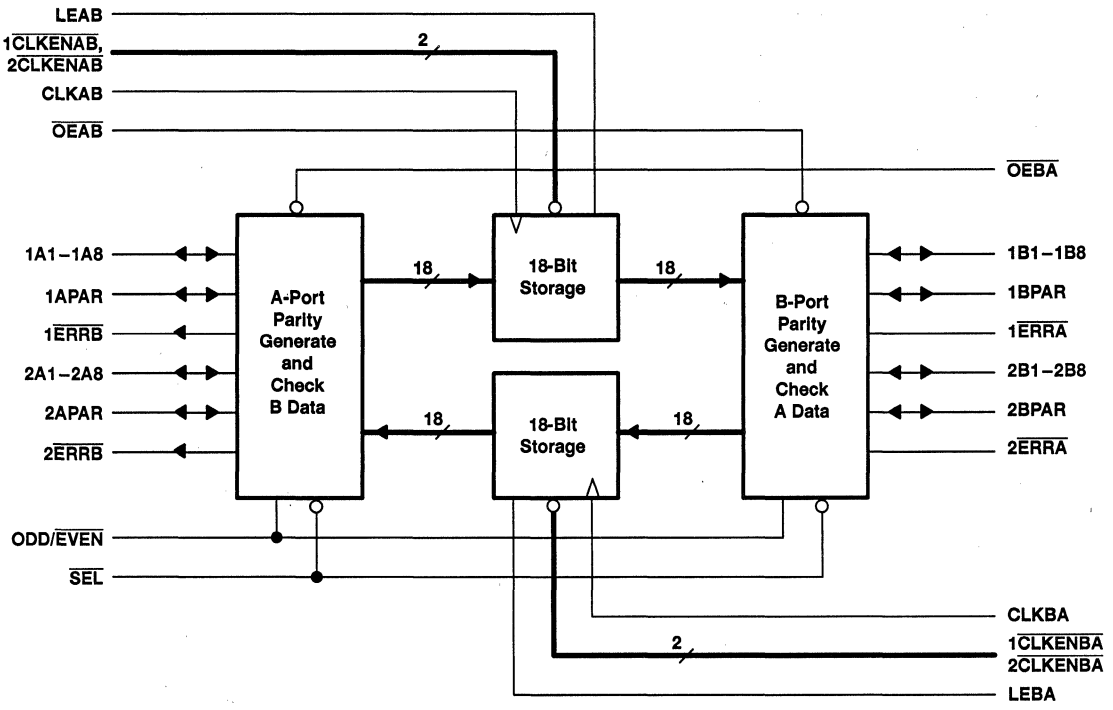
Widebus+, EPIC, and UBT are trademarks of Texas Instruments Incorporated.

description (continued)

The SN74ALVCH16901 is available in TI's thin shrink small-outline (DGG) package, which provides twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16901 is characterized for operation from –40°C to 85°C.

block diagram



FUNCTION TABLE†

INPUTS					OUTPUT
CLKENAB	OEAB	LEAB	CLKAB	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	L	L	X	B_0‡
L	L	L	H	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar, but uses OEBA, LEBA, and CLKENBA.

‡ Output level before the indicated steady-state input conditions were established

§ Output level before the indicated steady-state input conditions were established, provided that CLKAB was low before LEAB went low

PARITY-ENABLE FUNCTION TABLE

INPUTS			OPERATION OR FUNCTION	
$\overline{SEL}$	$\overline{OEBA}$	$\overline{OEAB}$		
L	H	L	Parity is checked on port A and is generated on port B.	
L	L	H	Parity is checked on port B and is generated on port A.	
L	H	H	Parity is checked on port B and port A.	
L	L	L	Parity is generated on port A and B if device is in FF mode.	
H	L	L	Parity functions are disabled; device acts as a standard 18-bit registered transceiver.	Q_A data to B, Q_B data to A
H	L	H		Q_B data to A
H	H	L		Q_A data to B
H	H	H		Isolation

PARITY FUNCTION TABLE

INPUTS								OUTPUTS			
$\overline{SEL}$	$\overline{OEBA}$	$\overline{OEAB}$	ODD/$\overline{EVEN}$	Σ OF INPUTS A1–A8 = H	Σ OF INPUTS B1–B8 = H	APAR	BPAR	APAR	$\overline{ERRA}$	BPAR	$\overline{ERRB}$
L	H	L	L	0, 2, 4, 6, 8	N/A	L	N/A	N/A	H	L	Z
L	H	L	L	1, 3, 5, 7	N/A	L	N/A	N/A	L	H	Z
L	H	L	L	0, 2, 4, 6, 8	N/A	H	N/A	N/A	L	L	Z
L	H	L	L	1, 3, 5, 7	N/A	H	N/A	N/A	H	H	Z
L	L	H	L	N/A	0, 2, 4, 6, 8	N/A	L	L	Z	N/A	H
L	L	H	L	N/A	1, 3, 5, 7	N/A	L	H	Z	N/A	L
L	L	H	L	N/A	0, 2, 4, 6, 8	N/A	H	L	Z	N/A	L
L	L	H	L	N/A	1, 3, 5, 7	N/A	H	H	Z	N/A	H
L	H	L	H	0, 2, 4, 6, 8	N/A	L	N/A	N/A	L	H	Z
L	H	L	H	1, 3, 5, 7	N/A	L	N/A	N/A	H	L	Z
L	H	L	H	0, 2, 4, 6, 8	N/A	H	N/A	N/A	H	H	Z
L	H	L	H	1, 3, 5, 7	N/A	H	N/A	N/A	L	L	Z
L	L	H	H	N/A	0, 2, 4, 6, 8	N/A	L	H	Z	N/A	L
L	L	H	H	N/A	1, 3, 5, 7	N/A	L	L	Z	N/A	H
L	L	H	H	N/A	0, 2, 4, 6, 8	N/A	H	H	Z	N/A	H
L	L	H	H	N/A	1, 3, 5, 7	N/A	H	L	Z	N/A	L
L	H	H	L	0, 2, 4, 6, 8	0, 2, 4, 6, 8	L	L	Z	H	Z	H
L	H	H	L	1, 3, 5, 7	1, 3, 5, 7	L	L	Z	L	Z	L
L	H	H	L	0, 2, 4, 6, 8	0, 2, 4, 6, 8	H	H	Z	L	Z	L
L	H	H	L	1, 3, 5, 7	1, 3, 5, 7	H	H	Z	H	Z	H
L	H	H	H	0, 2, 4, 6, 8	0, 2, 4, 6, 8	L	L	Z	L	Z	L
L	H	H	H	1, 3, 5, 7	1, 3, 5, 7	L	L	Z	H	Z	H
L	H	H	H	0, 2, 4, 6, 8	0, 2, 4, 6, 8	H	H	Z	H	Z	H
L	H	H	H	1, 3, 5, 7	1, 3, 5, 7	H	H	Z	L	Z	L
L	L	L	L	N/A	N/A	N/A	N/A	PE†	Z	PE†	Z
L	L	L	H	N/A	N/A	N/A	N/A	PO‡	Z	PO‡	Z

† Parity output is set to the level so that the specific bus side is set to even parity.
‡ Parity output is set to the level so that the specific bus side is set to odd parity.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3) ..... 1 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = −12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V			−45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.5		pF
C_o	$\overline{ERR}$ ports	V_O = V_{CC} or GND		3.3 V		6		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature range (unless otherwise noted)

			V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	125	0	125	0	125	MHz
t_w	Pulse duration	CLK↑	3		3		3		ns
		LE high	3		3		3		
t_{su}	Setup time	APAR or BPAR before CLK↑	1.9		2		1.7		ns
		$\overline{CLKEN}$ before CLK↑	2.1		2.1		1.7		
		APAR or BPAR before LE↓	1.4		1.3		1.2		
t_h	Hold time	APAR or BPAR after CLK↑	0.4		0.4		0.5		ns
		$\overline{CLKEN}$ after CLK↑	0.5		0.5		0.7		
		APAR or BPAR after LE↓	0.9		1.1		0.9		

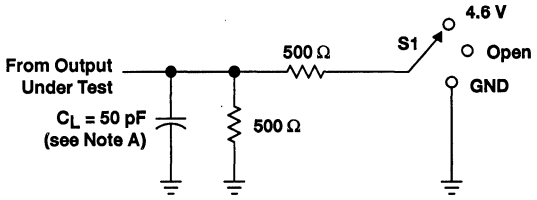
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			125		125		125		MHz
t_{pd}	A or B	B or A	1.5	5.8		4.8	1	4.4	ns
	A or B	BPAR or APAR	2.5	9.5		7.6	2	6.7	
	APAR or BPAR	BPAR or APAR	1.5	6.3		5.2	1	4.7	
	APAR or BPAR	$\overline{ERRA}$ or $\overline{ERRB}$	2.5	10.3		8.7	2	7.5	
	ODD/$\overline{EVEN}$	$\overline{ERRA}$ or $\overline{ERRB}$	2	9.3		7.9	1.5	6.8	
	ODD/$\overline{EVEN}$	BPAR or APAR	2	8.9		7.6	1.5	6.5	
	$\overline{SEL}$	BPAR or APAR	1.5	6.7		5.9	1	5.1	
	CLKAB or CLKBA	A or B	1.5	7		5.8	1	5.1	
	CLKAB or CLKBA	BPAR or APAR parity feedthrough	2	7.7		6.3	1.5	5.6	
	CLKAB or CLKBA	BPAR or APAR parity generated	3	10.8		8.7	2	7.7	
	CLKAB or CLKBA	$\overline{ERRA}$ or $\overline{ERRB}$	3	11.1		8.9	2	7.9	
	LEAB or LEBA	A or B	1.5	6.6		5.5	1	4.8	
	LEAB or LEBA	BPAR or APAR parity feedthrough	2	7.3		6	1.5	5.3	
	LEAB or LEBA	BPAR or APAR parity generated	3	10.4		8.3	2	7.4	
	LEAB or LEBA	$\overline{ERRA}$ or $\overline{ERRB}$	3	10.5		8.5	2	7.5	
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	B, BPAR or A, APAR	1.5	6.8		6.1	1	5.3	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	B, BPAR or A, APAR	2	6.3		5.2	1.5	4.9	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	$\overline{ERRA}$ or $\overline{ERRB}$	1.5	6.7		5.5	1	4.9	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	$\overline{ERRA}$ or $\overline{ERRB}$	2	7.5		6.5	1	5.7	ns
t_{en}	$\overline{SEL}$	$\overline{ERRA}$ or $\overline{ERRB}$	1.5	7.2		6.5	1	5.5	ns
t_{dis}	$\overline{SEL}$	$\overline{ERRA}$ or $\overline{ERRB}$	2	6.6		5.4	1.5	4.9	ns

operating characteristics, T_A = 25°C

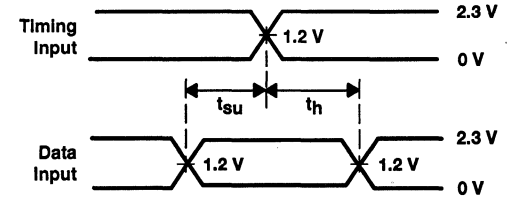
PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	22	27	pF
		Outputs disabled		5	8	

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

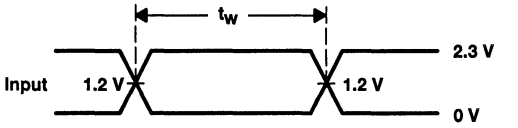


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	4.6 V
t_{PHZ}/t_{PZH}	GND

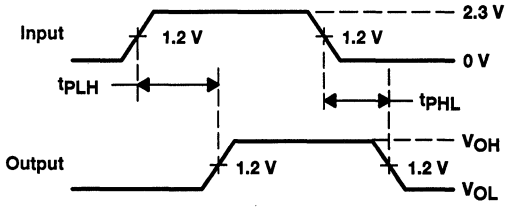
LOAD CIRCUIT



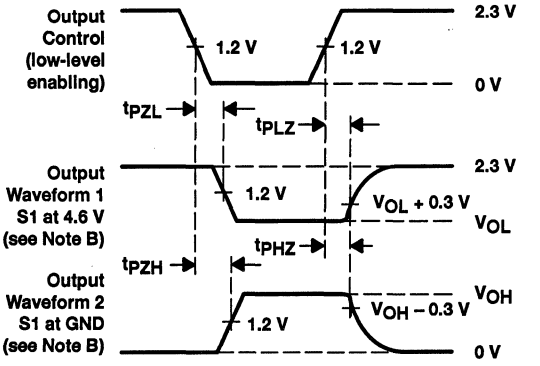
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

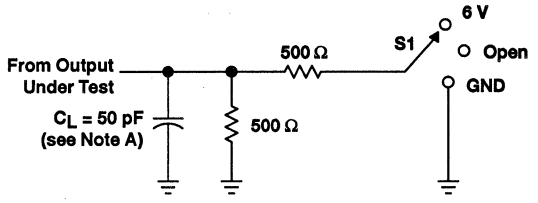


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

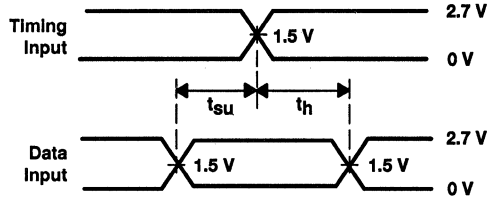
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

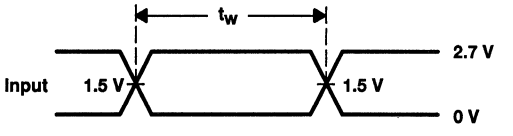


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

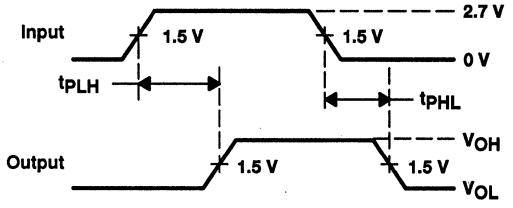
LOAD CIRCUIT



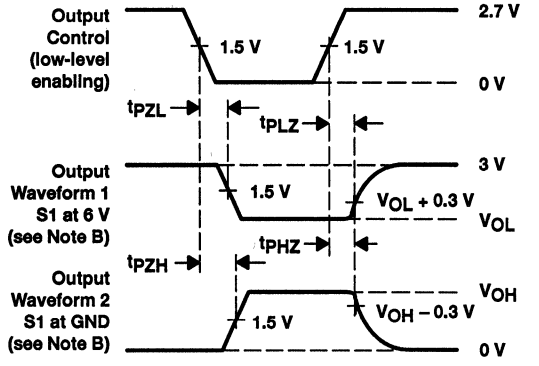
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



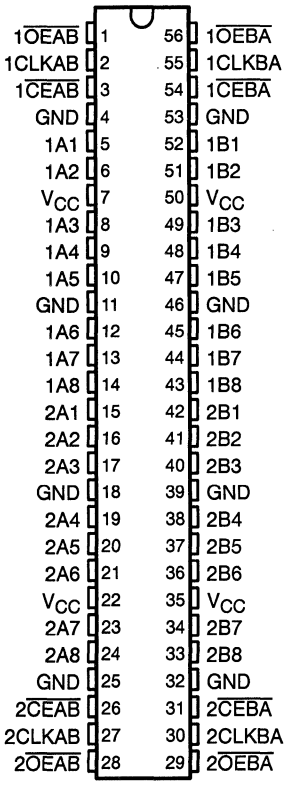
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit registered transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16952 contains two sets of D-type flip-flops for temporary storage of data flowing in either direction. This device can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input provided that the clock-enable ($\overline{CEAB}$ or $\overline{CEBA}$) input is low. Taking the output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) input low accesses the data on either port.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16952 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74ALVCH16952 is characterized for operation from –40°C to 85°C.

ADVANCE INFORMATION

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

FUNCTION TABLE†

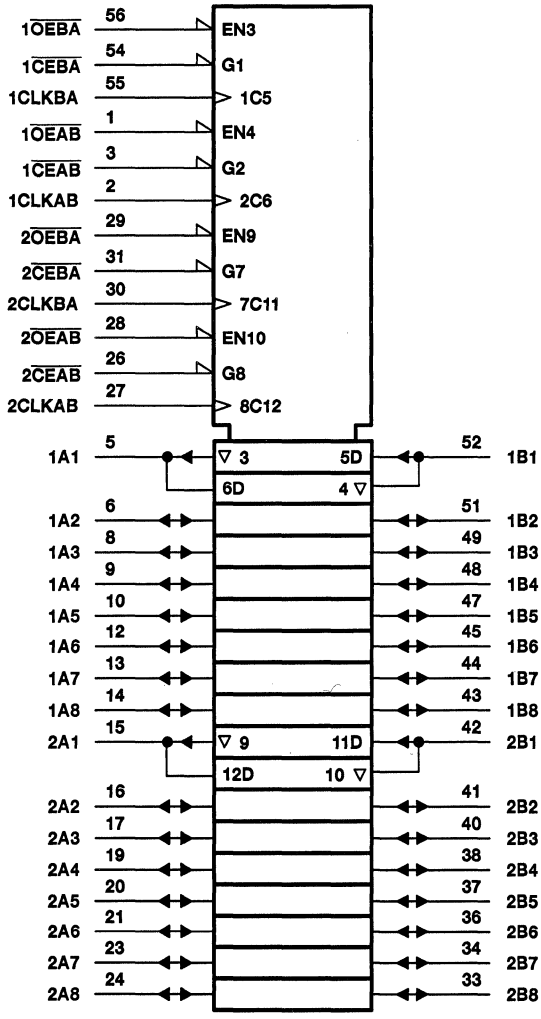
INPUTS				OUTPUT
$\overline{CLKENAB}$	CLKAB	$\overline{OEAB}$	A	B
H	X	L	X	B_0‡
X	L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

† A-to-B data flow is shown; B-to-A data flow is similar but uses $\overline{CLKENBA}$, CLKBA, and $\overline{OEBA}$.

‡ Level of B before the indicated steady-state input conditions were established

ADVANCE INFORMATION

logic symbol†

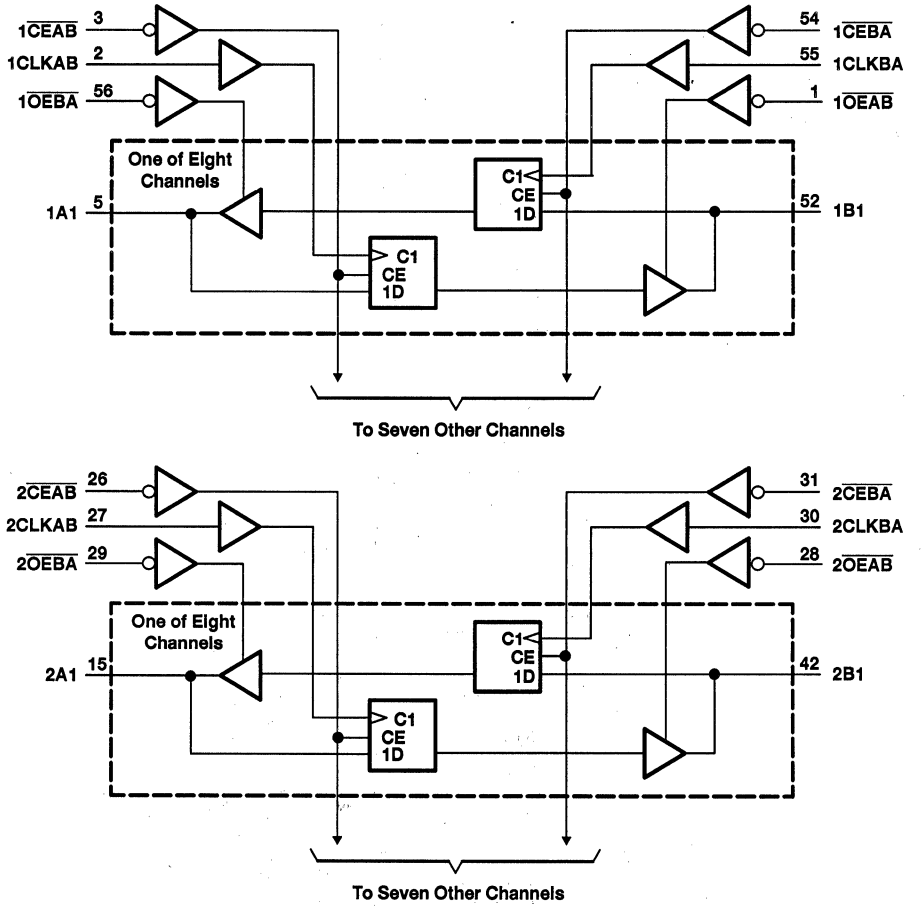


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

ADVANCE INFORMATION

ADVANCE INFORMATION

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7		V
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V		0.7	V
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V		−12	mA
		V_{CC} = 2.7 V		−12	
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V		12	mA
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

ADVANCE INFORMATION

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
			V_{IH} = 2 V	3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			µA
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V				pF

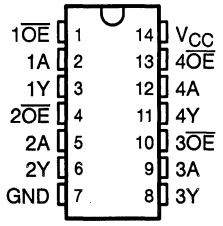
† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

ADVANCE INFORMATION

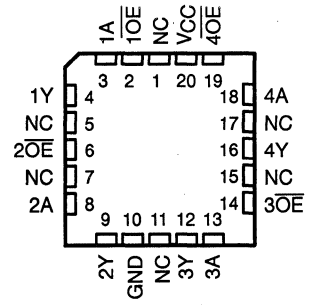
Contents

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

SN54LVT125 . . . J PACKAGE
SN74LVT125 . . . D, DB, OR PW PACKAGE
(TOP VIEW)



SN54LVT125 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These bus buffers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT125 feature independent line drivers with 3-state outputs. Each output is in the high-impedance state when the associated output-enable ($\overline{OE}$) input is high.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

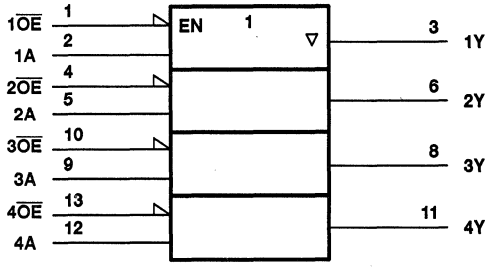
The SN74LVT125 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT125 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT125 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

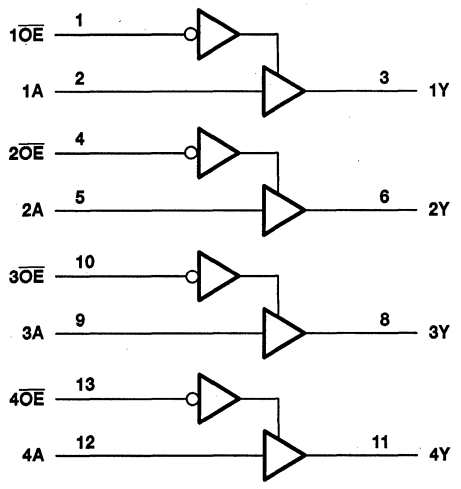
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



Pin numbers shown are for the D, DB, J, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT125 ..... 96 mA
SN74LVT125 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT125 ..... 48 mA
SN74LVT125 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT125		SN74LVT125		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT125			SN74LVT125			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = −100 μA		V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = −8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = −24 mA		2						
		I_{OH} = −32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 μA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	μA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				−5			−5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	μA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	Data inputs	75			75			μA
		V_I = 2 V		−75			−75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				5			5	μA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				−5			−5	μA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.12	0.19		0.12	0.19	mA
			Outputs low		4.5	7		4.5	7	
			Outputs disabled		0.12	0.19		0.12	0.19	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} − 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				8			8		pF

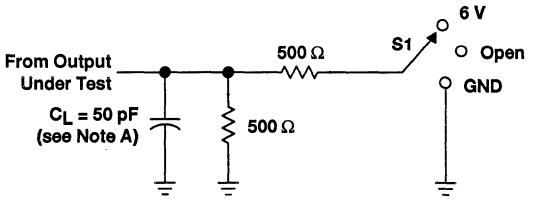
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT125				SN74LVT125				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	4.2		4.7	1	2.7	4	4.5	ns
t_{PHL}			1	4.1		5.1	1	2.9	3.9	4.9	
t_{PZH}	$\overline{OE}$	Y	1	4.9		6.2	1	3.4	4.7	6	ns
t_{PZL}			1.1	4.9		6.7	1.1	3.4	4.7	6.5	
t_{PHZ}	$\overline{OE}$	Y	1.8	5.8		5.9	1.8	3.7	5.1	5.7	ns
t_{PLZ}			1.3	4.7		4.2	1.3	2.6	4.5	4	

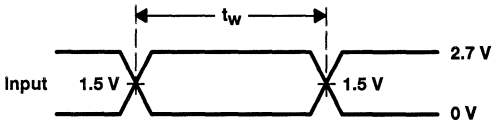
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

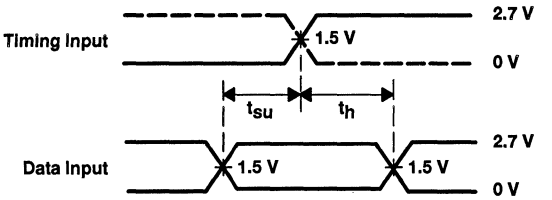


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

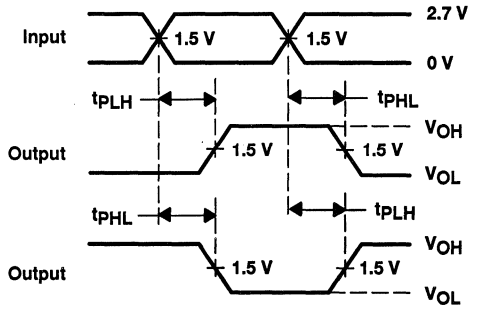
LOAD CIRCUIT FOR OUTPUTS



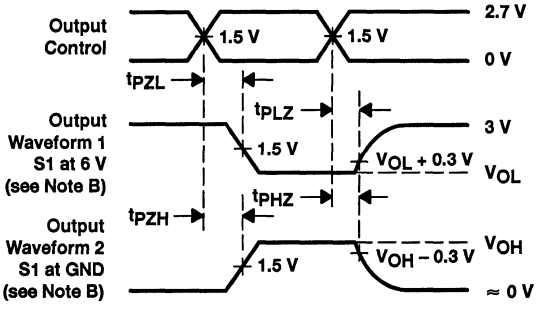
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



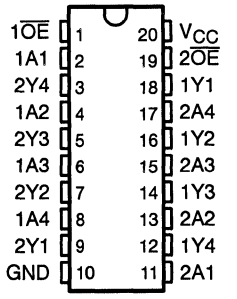
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

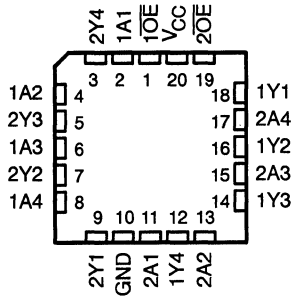
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Support Live Insertion**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs**

SN54LVT240 . . . J PACKAGE
SN74LVT240 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT240 . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers and line drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are organized as two 4-bit buffer/line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the devices pass data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

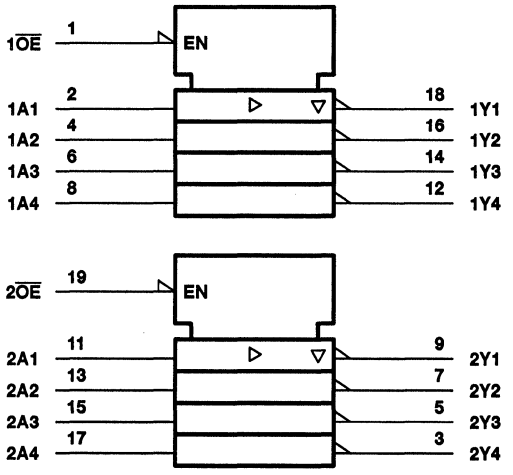
The SN74LVT240 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT240 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

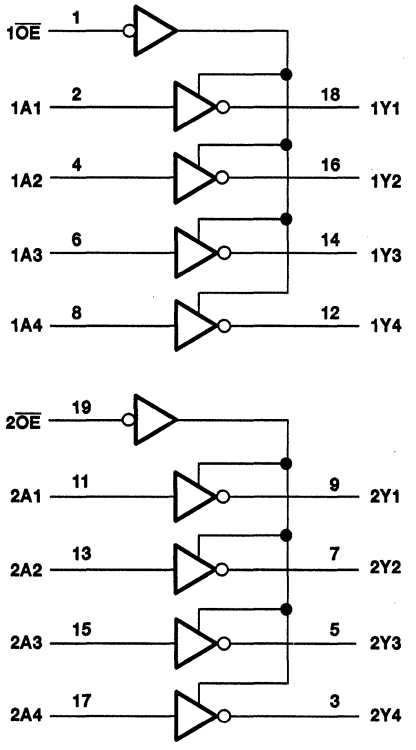
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT240 ..... 96 mA
SN74LVT240 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT240 ..... 48 mA
SN74LVT240 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT240		SN74LVT240		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT240			SN74LVT240			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	Data inputs	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				5			5	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–5			–5	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.12	0.19		0.12	0.19	mA
			Outputs low		8.6	12		8.6	12	
			Outputs disabled		0.12	0.19		0.12	0.19	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				8			8		pF

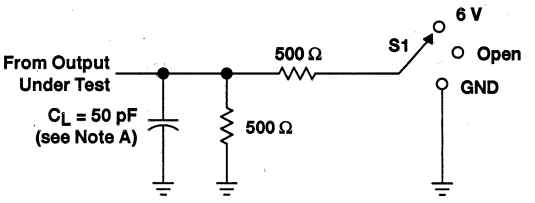
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT240				SN74LVT240					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A	Y	1	4.2		5.2	1	2.9	4.1		5.2	ns
t_{PHL}			1.3	3.7		4.1	1.3	2.5	3.5		4	
t_{PZH}	$\overline{OE}$	Y	1.2	4.7		5.7	1.2	3.2	4.6		5.6	ns
t_{PZL}			1.5	4.8		5.9	1.4	3.5	4.7		5.8	
t_{PHZ}	$\overline{OE}$	Y	2	5.3		5.7	2	3.6	5.2		5.5	ns
t_{PLZ}			1.9	4.6		4.6	1.9	3.2	4.4		4.4	

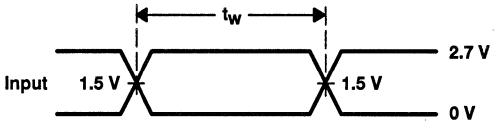
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

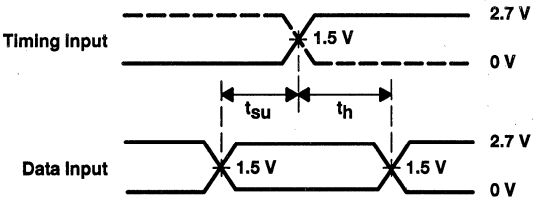


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

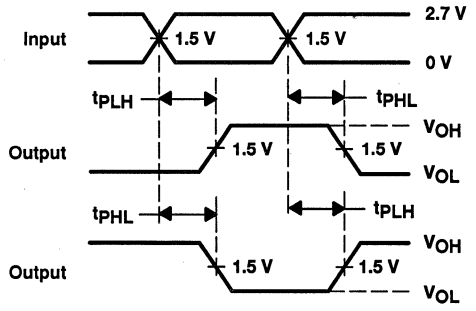
LOAD CIRCUIT FOR OUTPUTS



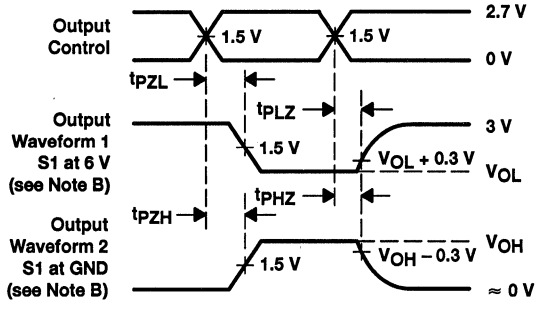
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



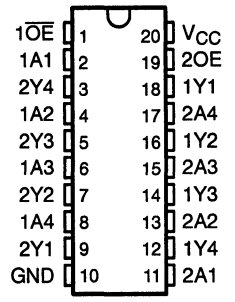
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

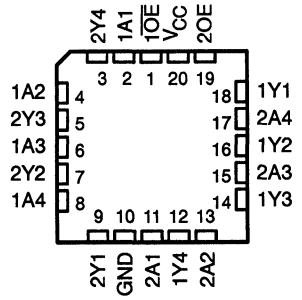
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Support Live Insertion**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs**

SN54LVT241 . . . J PACKAGE
SN74LVT241 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT241 . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT241 are organized as two 4-bit line drivers with separate output-enable ($1\overline{OE}$, 2OE) inputs. When $1\overline{OE}$ is low or 2OE is high, the devices pass data from the A inputs to the Y outputs. When $1\overline{OE}$ is high or 2OE is low, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The SN74LVT241 is available in TI's shrink small-outline package (DB), which provides the same input/output (I/O) pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

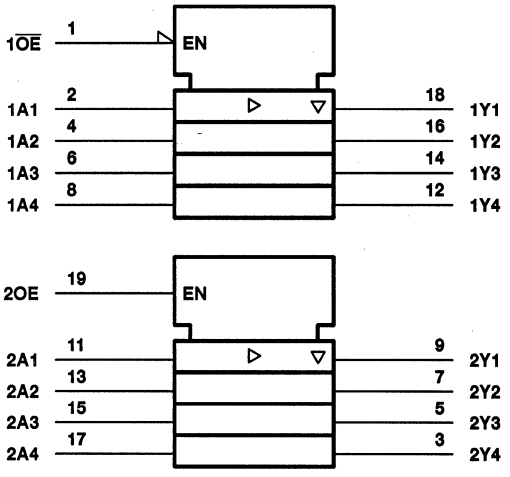
The SN54LVT241 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT241 is characterized for operation from –40°C to 85°C.

FUNCTION TABLES

INPUTS		OUTPUT
$1\overline{OE}$	1A	1Y
L	H	H
L	L	L
H	X	Z

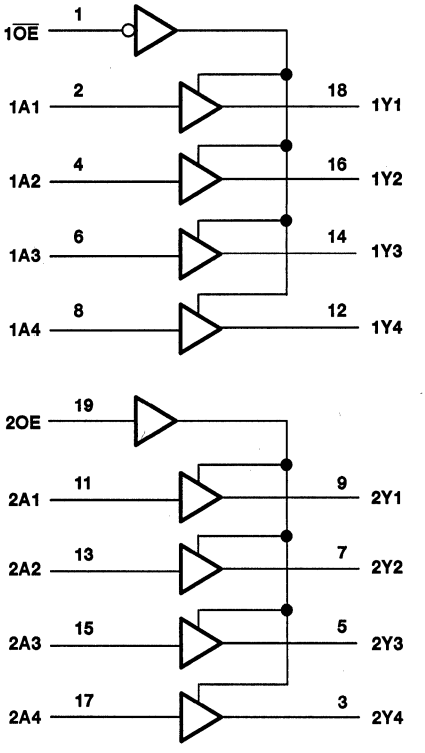
INPUTS		OUTPUT
2OE	2A	2Y
H	H	H
H	L	L
L	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT241 ..... 96 mA
SN74LVT241 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT241 ..... 48 mA
SN74LVT241 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Operating free-air temperature range, T_A: SN54LVT241 ..... −55°C to 125°C
SN74LVT241 ..... −40°C to 85°C
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT241		SN74LVT241		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT241			SN74LVT241			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	Data inputs	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				5			5	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–5			–5	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.12	0.5		0.12	0.19	mA
			Outputs low		8.6	15		8.6	15	
			Outputs disabled		0.12	0.5		0.12	0.19	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND					0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				8			8		pF

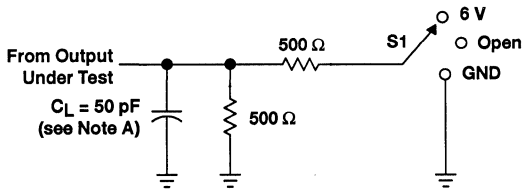
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT241				SN74LVT241				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A	Y	1	4.7		5.2	1	2.2	4.3		5	ns
t_{PHL}			1	4.4		5.4	1	2.3	4.2		5.2	
t_{PZH}	$\overline{OE}$ or OE	Y	1.3	5.4		6.5	1.4	2.8	5.2		6.3	ns
t_{PZL}			1.5	5.4		7.6	1.6	2.8	5.2		6.7	
t_{PHZ}	$\overline{OE}$ or OE	Y	1.8	5.3		8.3	1.9	3.2	6.6		7.7	ns
t_{PLZ}			1.9	6.2		7.4	2	3.1	6		7.1	

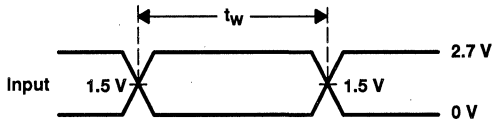
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

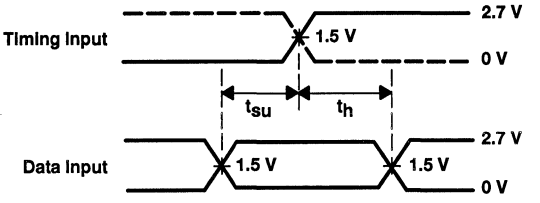


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

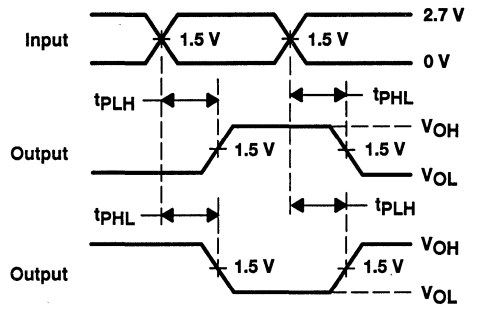
LOAD CIRCUIT FOR OUTPUTS



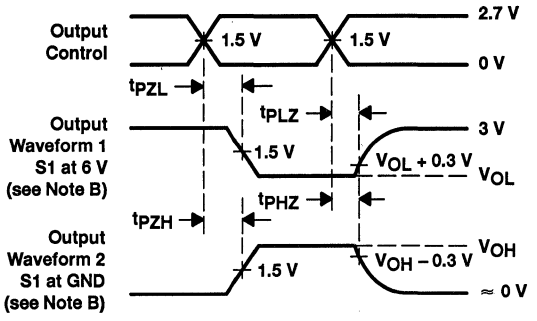
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



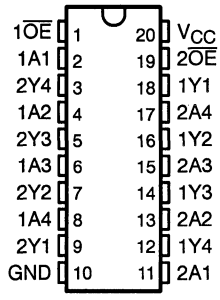
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

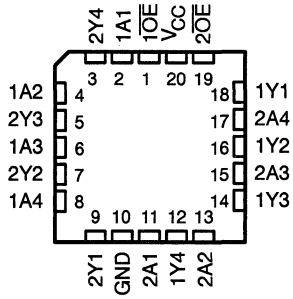
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN54LVT244 . . . J OR W PACKAGE
SN74LVT244A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT244 . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers and line drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The SN54LVT244 and SN74LVT244A are organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

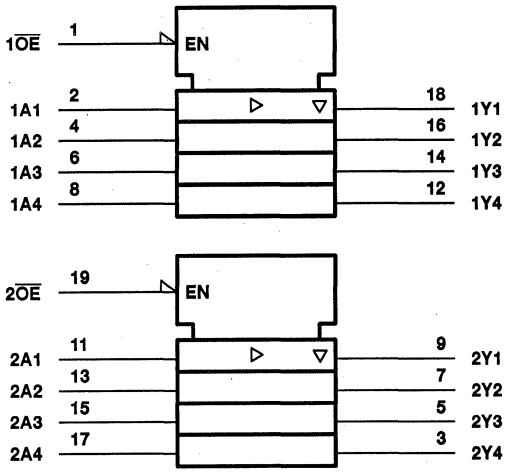
The SN74LVT244A is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT244 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

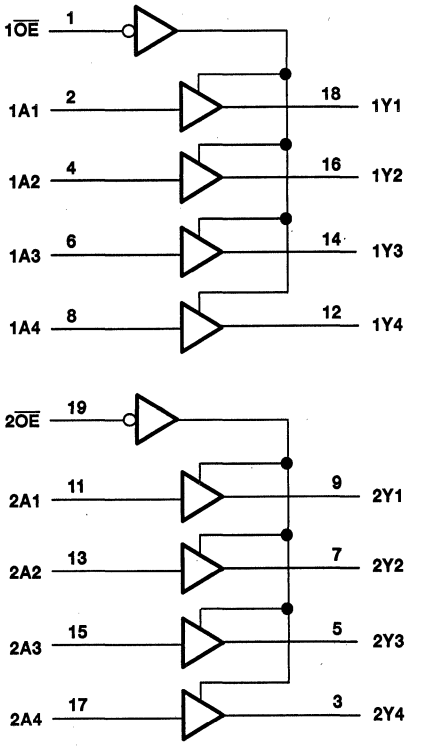
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT244 ..... 96 mA
SN74LVT244A ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT244 ..... 48 mA
SN74LVT244A ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT244		SN74LVT244A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

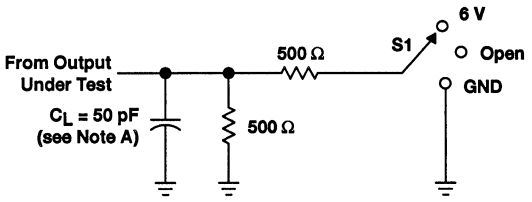
PARAMETER	TEST CONDITIONS			SN54LVT244			SN74LVT244A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				50			10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A inputs	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				5			5	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–5			–5	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.12	0.39		0.12	0.19	mA
			Outputs low		8.6	14		8.6	12	
			Outputs disabled		0.12	0.39		0.12	0.19	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

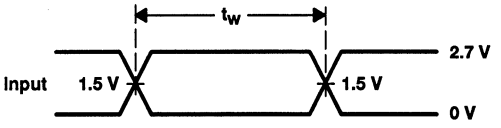
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT244				SN74LVT244A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP	MAX	MIN	MAX	
t_{PLH}	A	Y	0.5	4.7		5.2	1	2.5	4.1		5	ns
t_{PHL}			0.5	4.4		5.4	1	2.5	4.1		5.2	
t_{PZH}	$\overline{OE}$	Y	0.8	5.4		6.5	1	2.7	5.2		6.3	ns
t_{PZL}			0.8	5.4		7.6	1.1	3.1	5.2		6.7	
t_{PHZ}	$\overline{OE}$	Y	1.5	6.2		6.9	1.9	3.9	5.6		6.3	ns
t_{PLZ}			1.2	5.5		6	1.8	3.2	5.1		5.6	

PARAMETER MEASUREMENT INFORMATION

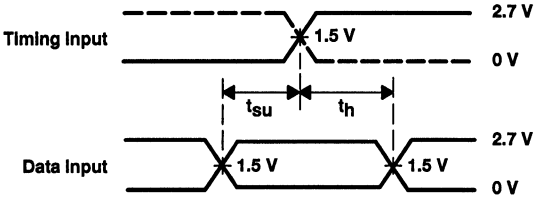


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

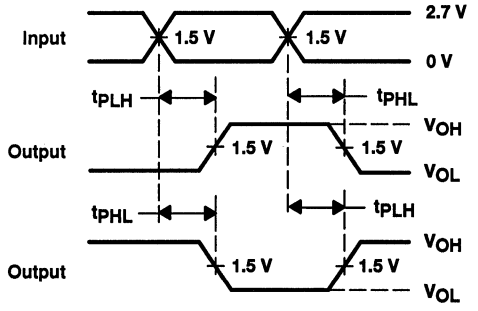
LOAD CIRCUIT FOR OUTPUTS



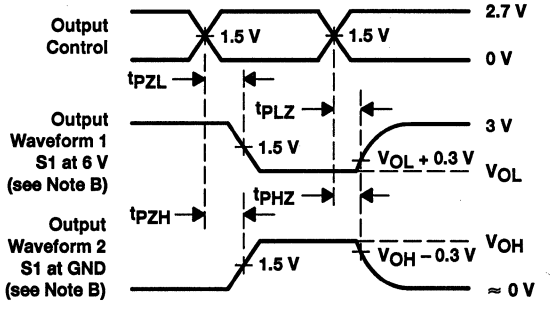
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



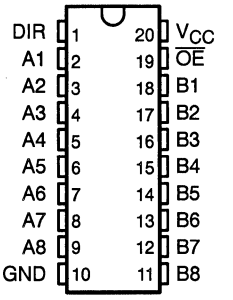
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

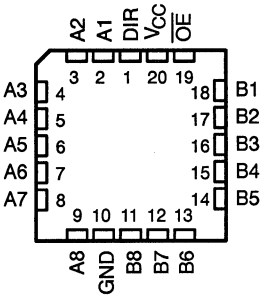
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN54LVT245 . . . J OR W PACKAGE
SN74LVT245A . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT245 . . . FK PACKAGE
(TOP VIEW)



description

These octal bus transceivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are designed for asynchronous communication between data buses. They transmit data from the A bus to the B bus or from the B bus to the A bus depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the devices so the buses are effectively isolated.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

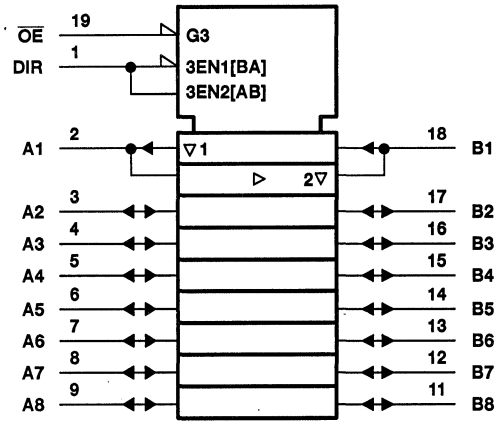
The SN74LVT245A is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT245 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

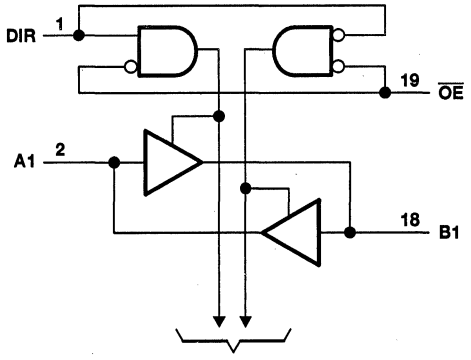
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT245 ..... 96 mA
SN74LVT245A ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT245 ..... 48 mA
SN74LVT245A ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT245		SN74LVT245A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT245			SN74LVT245A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			100			20	
		V_I = V_{CC}				5			5	
		V_I = 0				–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.13	0.39		0.13	0.19	mA
			Outputs low		8.8	14		8.8	12	
			Outputs disabled		0.13	0.39		0.13	0.19	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				10			10		pF

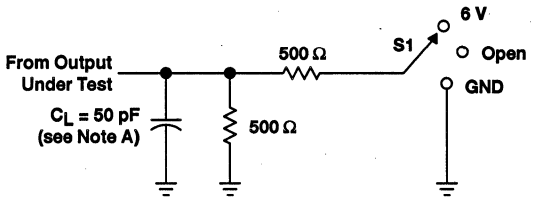
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused terminals at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT245				SN74LVT245				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A or B	B or A	0.5	4.4		5.2	1	2.5	4	5.2	ns
t_{PHL}			0.5	4.2		4.8	1	2.5	4	5.5	
t_{PZH}	$\overline{OE}$	A or B	0.8	5.9		7.3	1.1	3.3	5.9	7.1	ns
t_{PZL}			1	5.9		7.2	1.5	3.8	6.5	7.9	
t_{PHZ}	$\overline{OE}$	A or B	1.5	6.5		7.2	2.2	4.3	5.9	6.5	ns
t_{PLZ}			1.5	6.1		6.5	2	3.9	5.5	5.6	

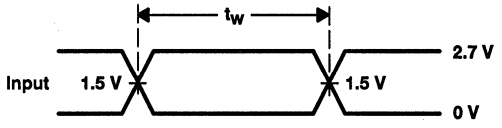
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

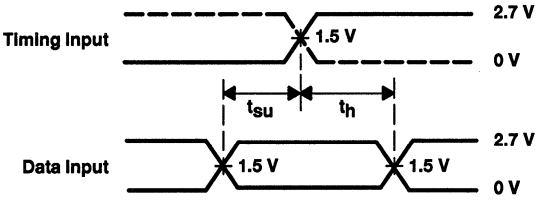


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

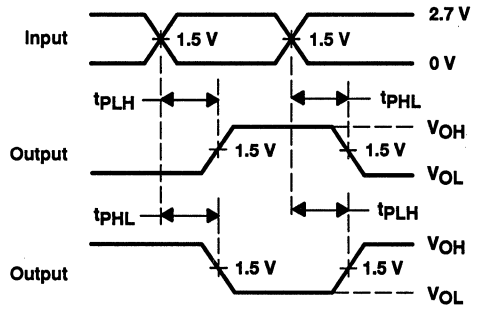
LOAD CIRCUIT FOR OUTPUTS



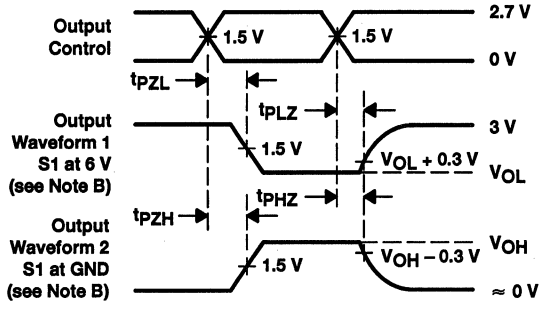
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



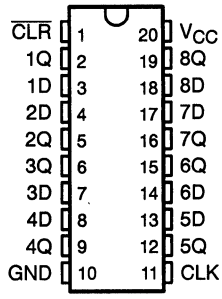
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

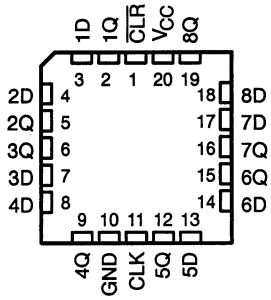
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Buffered Clock and Direct Clear Inputs
- Individual Data Input to Each Flip-Flop
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

SN54LVT273 . . . J PACKAGE
SN74LVT273 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT273 . . . FK PACKAGE
(TOP VIEW)



description

These octal D-type flip-flops are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT273 are positive-edge-triggered flip-flops with a direct clear input. Information at the data (D) inputs meeting the setup-time requirements is transferred to the Q outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock (CLK) input is at either the high or low level, the D-input signal has no effect at the output.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

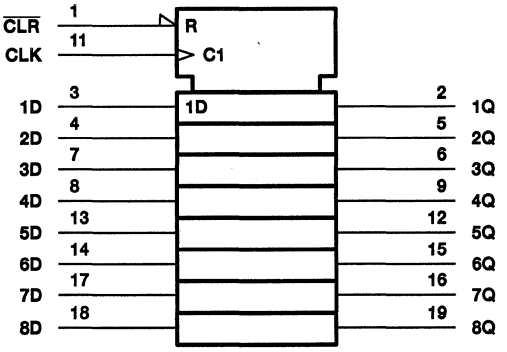
The SN74LVT273 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT273 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT273 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

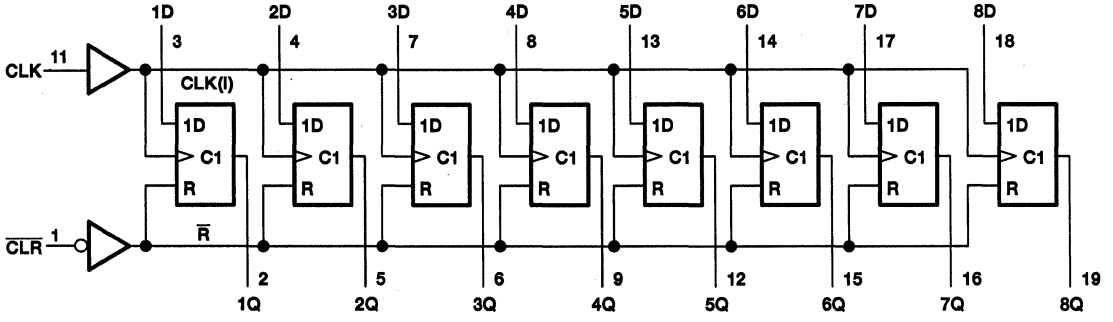
INPUTS			OUTPUT
$\overline{CLR}$	CLK	D	Q
L	X	X	L
H	↑	H	H
H	↑	L	L
H	H or L	X	Q_0

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT273 ..... 96 mA
SN74LVT273 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT273 ..... 48 mA
SN74LVT273 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

		SN54LVT273		SN74LVT273		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
V_I	Input voltage		5.5		5.5	V
I_{OH}	High-level output current		−24		−32	mA
I_{OL}	Low-level output current		48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		10		10	ns/V
T_A	Operating free-air temperature	−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT273			SN74LVT273			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA		V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = − 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = − 24 mA		2						
		I_{OH} = −32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				−5			−5	
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	Data inputs	75			75			µA
		V_I = 2 V		−75			−75			
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.12	0.19		0.12	0.19	mA
			Outputs low		8.6	12		8.6	12	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND					0.2			0.2	mA
C_i	V_I = 3 V or 0							4		pF
C_o	V_O = 3 V or 0							8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

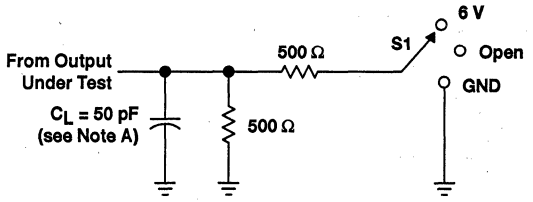
		SN54LVT273				SN74LVT273				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency					0	150			MHz
t_w	Pulse duration					3.3		3.3		ns
t_{su}	Setup time, data high or low before CLK↑					2.3		2.7		ns
	Setup time, $\overline{CLR}$ high before CLK↑					2.7		3.2		
t_h	Hold time, data high or low after CLK↑					0		0		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT273				SN74LVT273					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}							150					MHz
t_{PLH}	CLK	Any Q					1.7	3.5	5.5		6.3	ns
t_{PHL}							1.9	3.5	5.5		5.9	
t_{PHL}	$\overline{CLR}$	Any Q					1.3	3.2	5.1		6.2	ns

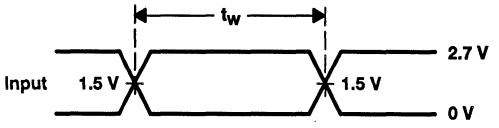
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

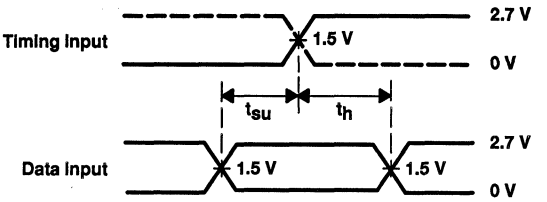


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

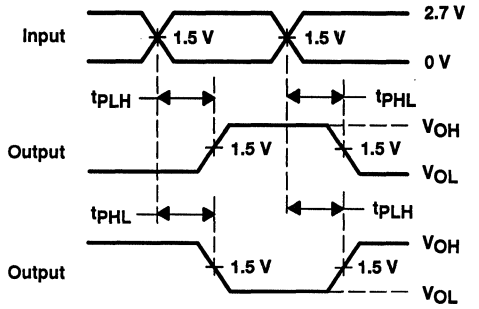
LOAD CIRCUIT FOR OUTPUTS



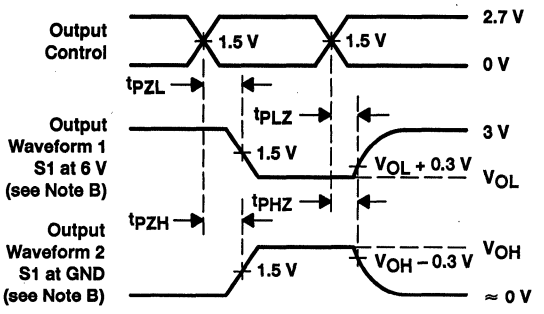
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



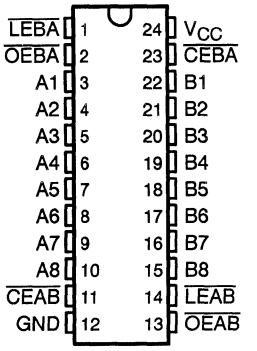
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

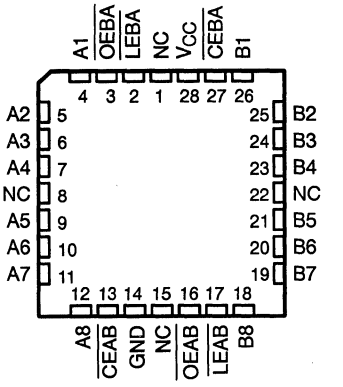
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (JT) DIPs

SN54LVT543 . . . JT PACKAGE
SN74LVT543 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT543 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These octal transceivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT543 contain two sets of D-type latches for temporary storage of data flowing in either direction. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low in order to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ puts the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar but requires using the $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$ inputs.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

description (continued)

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVT543 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

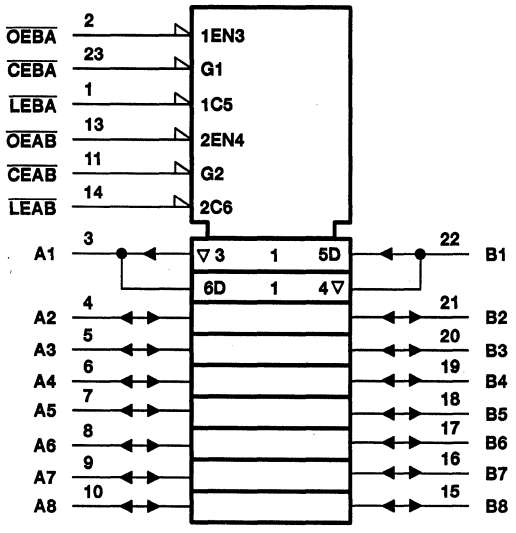
The SN54LVT543 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT543 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

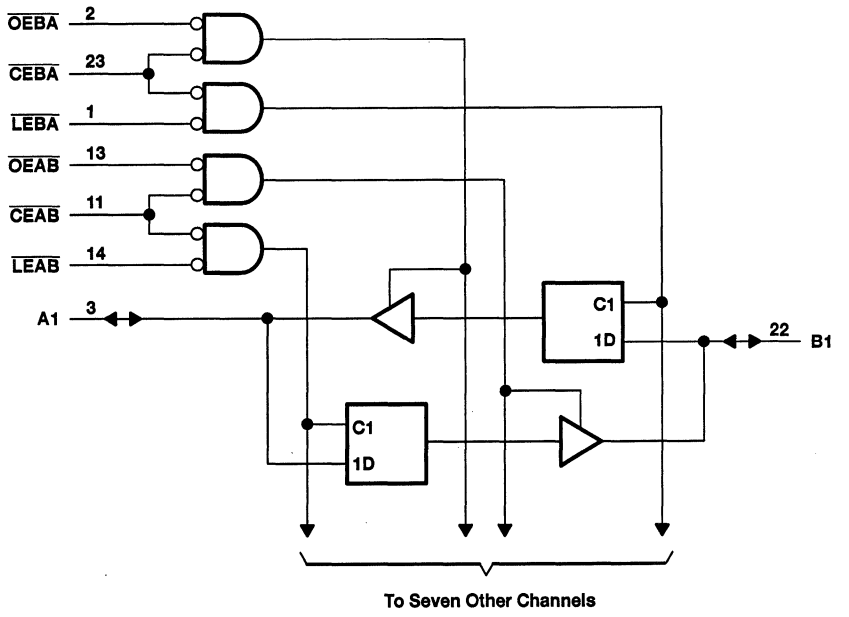
† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, and PW packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT543 ..... 96 mA
SN74LVT543 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT543 ..... 48 mA
SN74LVT543 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT543		SN74LVT543		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

PRODUCT PREVIEW

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT543			SN74LVT543			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				5			5	
		V_I = 0				–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.13	0.19		0.13	0.19	mA
			Outputs low		8.8	12		8.8	12	
			Outputs disabled		0.13	0.19		0.13	0.19	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				4.5			4.5		pF
C_{io}	V_O = 3 V or 0				11			11		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused terminals at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

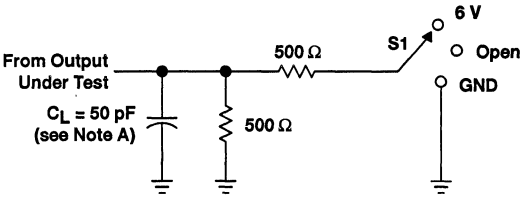
				SN54LVT543				SN74LVT543				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration,	$\overline{LEAB}$ or $\overline{LEBA}$ low		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time	A or B before $\overline{LEAB}$ or $\overline{LEBA}\uparrow$	Data high	0		0		0		0		ns
			Data low	0.8		1.1		0.8		1.1		
		A or B before $\overline{CEAB}$ or $\overline{CEBA}\uparrow$	Data high	0		0		0		0		
			Data low	0.9		1.2		0.9		1.2		
t_h	Hold time	A or B after $\overline{LEAB}$ or $\overline{LEBA}\uparrow$		1.7		1.7		1.7		1.7		ns
		A or B after $\overline{CEAB}$ or $\overline{CEBA}\uparrow$		1.8		1.8		1.8		1.8		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT543				SN74LVT543					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1	4.9		5.7	1	2.9	4.7		5.5	ns
t_{PHL}			1	4.8		6	1	3.3	4.6		5.8	
t_{PLH}	$\overline{LE}$	A or B	1	6.1		7.5	1	4	5.9		7.3	ns
t_{PHL}			1	5.9		7.5	1	4.1	5.7		7.3	
t_{PZH}	$\overline{OE}$	A or B	1	6		7.8	1	4.1	5.8		7.6	ns
t_{PZL}			1.1	6.6		8.4	1.1	4.5	6.4		8.2	
t_{PHZ}	$\overline{OE}$	A or B	2.4	6.7		7.3	2.4	4.8	6.5		7.1	ns
t_{PLZ}			2	6		6.1	2	4	5.8		5.9	
t_{PZH}	$\overline{CE}$	A or B	1	6.2		7.8	1	4.2	6		7.6	ns
t_{PZL}			1.4	6.9		8.5	1.4	4.7	6.7		8.3	
t_{PHZ}	$\overline{CE}$	A or B	2.3	6.6		7.3	2.3	4.7	6.4		7.1	ns
t_{PLZ}			2	5.6		5.8	2	3.8	5.4		5.6	

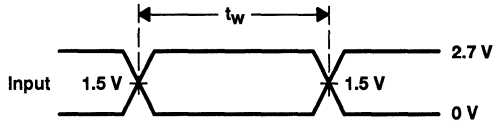
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

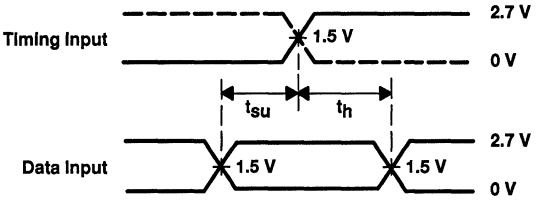


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

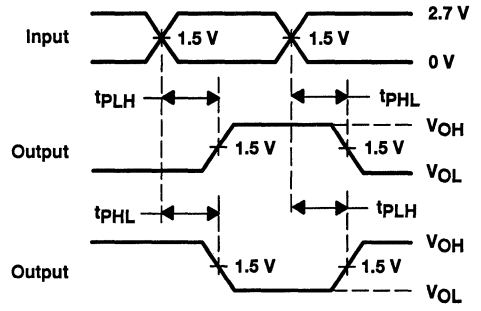
LOAD CIRCUIT FOR OUTPUTS



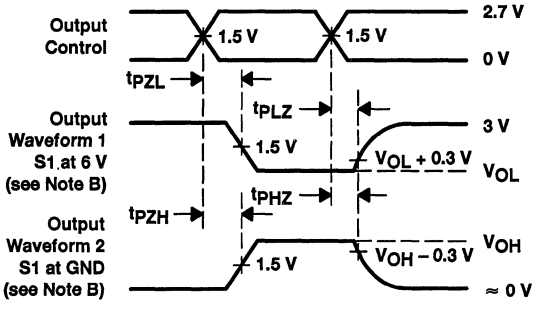
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



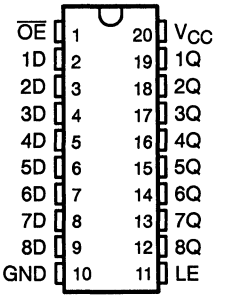
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

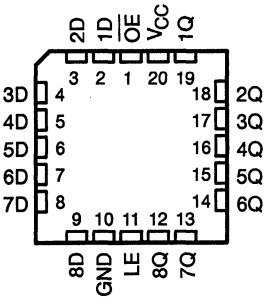
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN54LVT573 . . . J OR W PACKAGE
SN74LVT573 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT573 . . . FK PACKAGE
(TOP VIEW)



description

These octal latches are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The eight latches of the 'LVT573 are transparent D-type latches. While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components. $\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

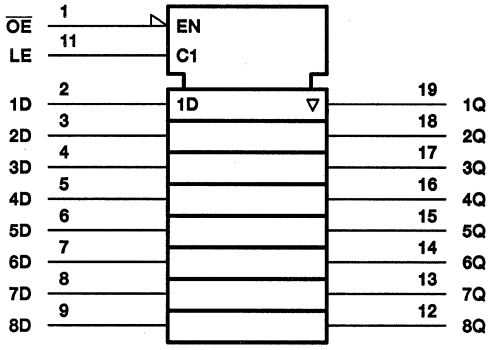
The SN74LVT573 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT573 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT573 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each latch)

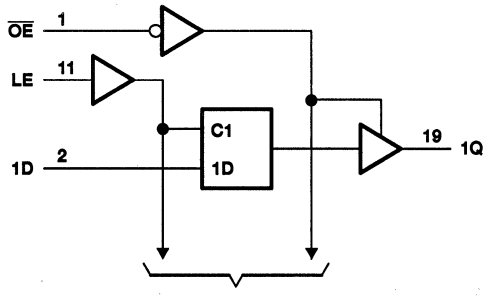
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT573 ..... 96 mA
SN74LVT573 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT573 ..... 48 mA
SN74LVT573 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT573		SN74LVT573		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT573			SN74LVT573			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA		V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = − 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = − 24 mA		2						
		I_{OH} = −32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				50			10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				−5			−5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	Data inputs	75			75			µA
		V_I = 2 V		−75			−75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				−1			−1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.13	0.39		0.13	0.19	mA
			Outputs low		8.6	14		8.6	12	
			Outputs disabled		0.13	0.39		0.13	0.19	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND					0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

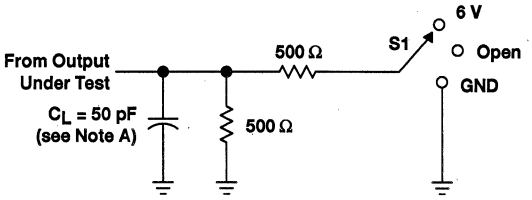
		SN54LVT573				SN74LVT573				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE↓	1		0.9		0.7		0.6		ns
t_h	Hold time, data after LE↓	1.8		2		1.6		1.8		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT573				SN74LVT573				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	D	Q	0.5	4.7		4.9	1	2.5	4.2	4.7	ns
t_{PHL}			0.5	4.9		5.4	1	2.7	4.3	5.2	
t_{PLH}	LE	Q	1	6		6.9	1.6	3.5	5.6	6.3	ns
t_{PHL}			1.4	6.9		7.6	2.5	4.3	6.5	7.2	
t_{PZH}	$\overline{OE}$	Q	0.5	5.3		6.4	1	2.8	5.1	6.2	ns
t_{PZL}			0.7	5.7		7.2	1.3	3.3	5.5	6.6	
t_{PHZ}	$\overline{OE}$	Q	1.2	5.9		6.9	2	3.7	5.7	6.7	ns
t_{PLZ}			1	5.4		5.5	1.5	3	4.6	5.1	

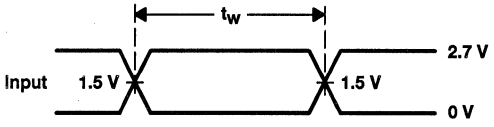
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

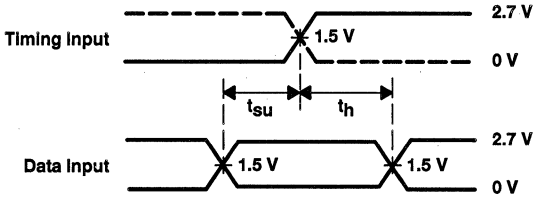


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

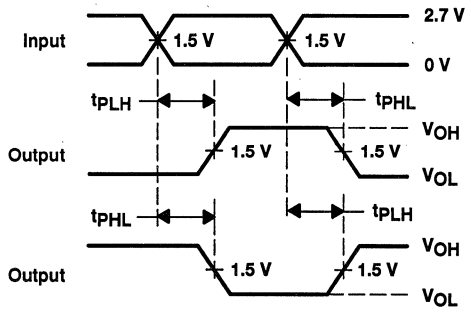
LOAD CIRCUIT FOR OUTPUTS



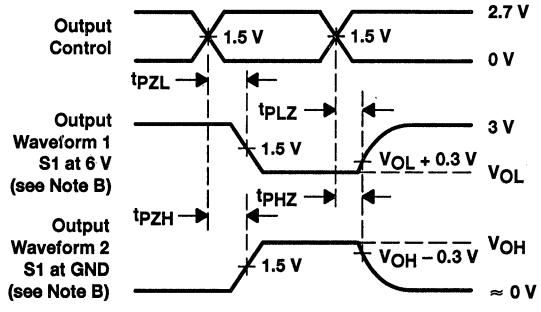
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



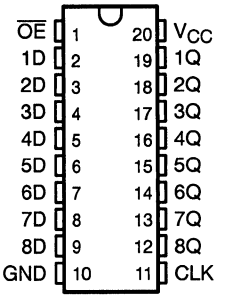
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

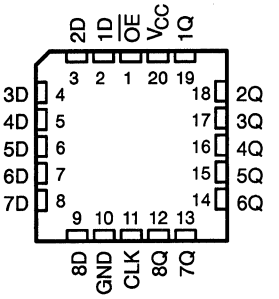
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

SN54LVT574 . . . J OR W PACKAGE
SN74LVT574 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT574 . . . FK PACKAGE
(TOP VIEW)



description

These octal flip-flops are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The eight flip-flops of the 'LVT574 are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components. $\overline{OE}$ does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

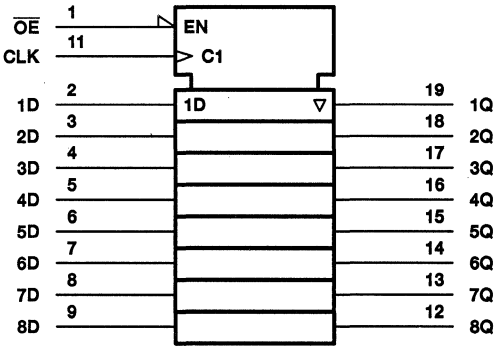
The SN74LVT574 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT574 is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74LVT574 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

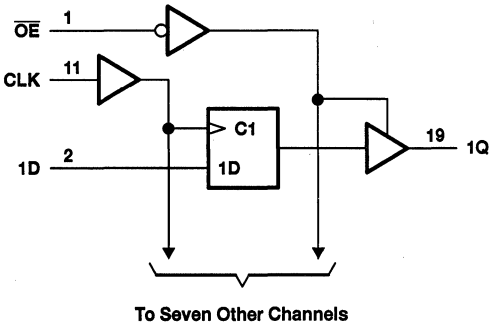
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT574 ..... 96 mA
SN74LVT574 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT574 ..... 48 mA
SN74LVT574 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT574		SN74LVT574		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT574			SN74LVT574			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				50			10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	Data inputs	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.13	0.39		0.13	0.19	mA
			Outputs low		8.7	14		8.7	12	
			Outputs disabled		0.13	0.39		0.13	0.19	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				8			8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

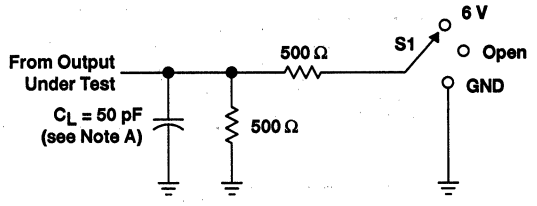
		SN54LVT574				SN74LVT574				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	2		2.4		2		2.4		ns
t_h	Hold time, data after CLK↑	0.9		0.9		0.3		0		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT574				SN74LVT574					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		150		150			150		MHz
t_{PLH}	CLK	Q	1	5.9		6.6	1.7	3.6	5.4		6.2	ns
t_{PHL}			1	6.1		6.8	2.4	4.3	5.9		6.6	
t_{PZH}	$\overline{OE}$	Q	0.5	5.9		7.1	1	2.9	4.8		5.9	ns
t_{PZL}			0.5	5.3		6.4	1.3	3.4	5.1		6.2	
t_{PHZ}	$\overline{OE}$	Q	0.7	5.9		6.6	1.9	4	5.5		5.9	ns
t_{PLZ}			0.5	5.1		5.1	1.7	3.2	4.5		4.5	

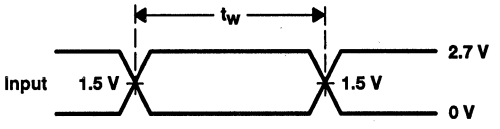
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

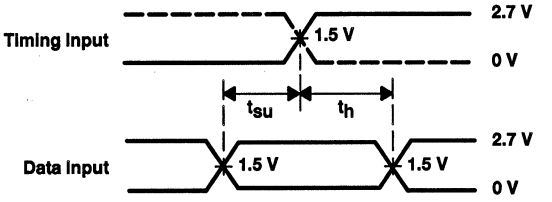


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

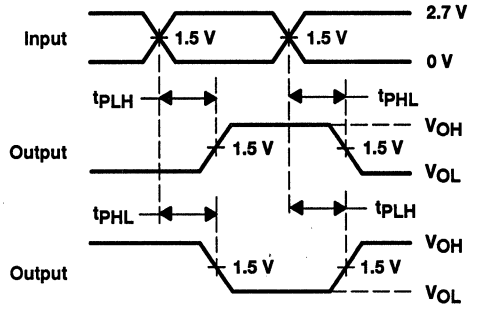
LOAD CIRCUIT FOR OUTPUTS



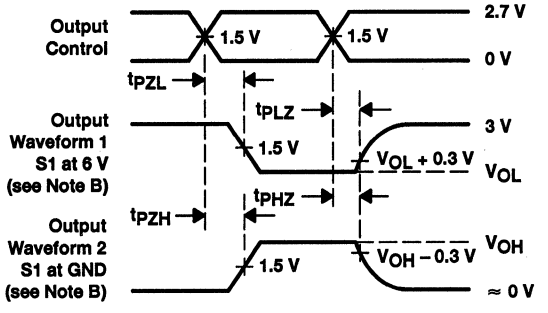
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



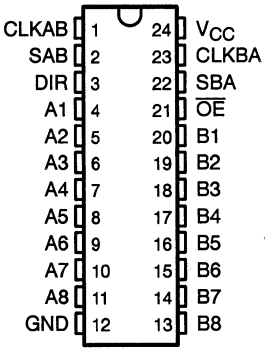
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

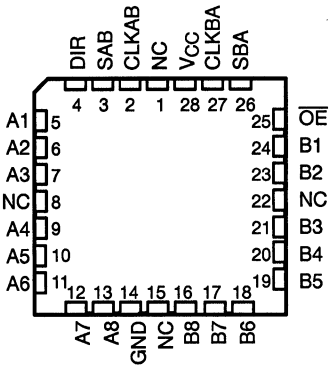
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Support Live Insertion**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (JT) DIPs**

SN54LVT646 . . . JT OR W PACKAGE
SN74LVT646 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT646 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These bus transceivers and registers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT646 consist of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'LVT646.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs are provided to control the transceiver functions. In the transceiver mode, data present at the high-impedance port may be stored in either register or in both.

The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The direction control (DIR) determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data may be stored in one register and/or B data may be stored in the other register.

When an output function is disabled, the input function is still enabled and may be used to store and transmit data. Only one of the two buses, A or B, may be driven at a time.

description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

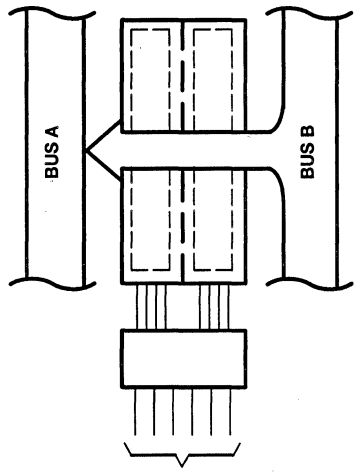
The SN74LVT646 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT646 is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74LVT646 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE

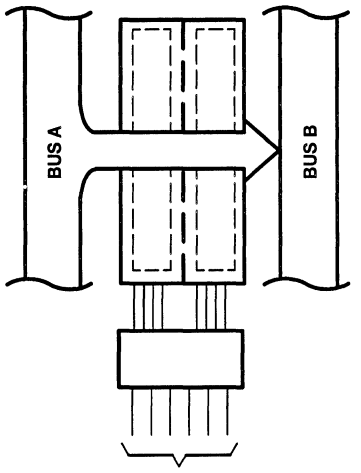
INPUTS						DATA I/Os		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

† The data output functions may be enabled or disabled by various signals at the $\overline{OE}$ and DIR inputs. Data input functions are always enabled; i.e., data at the bus pins is stored on every low-to-high transition of the clock inputs.



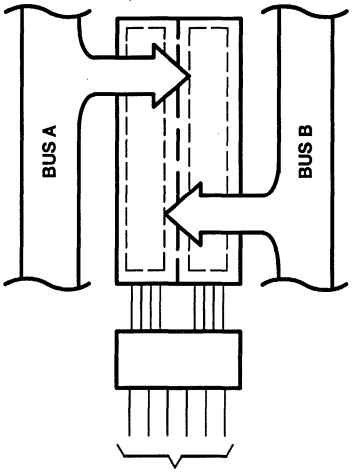
21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



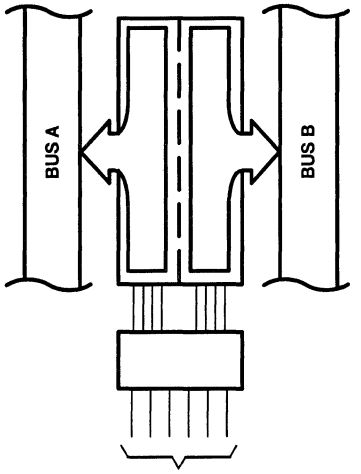
21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B



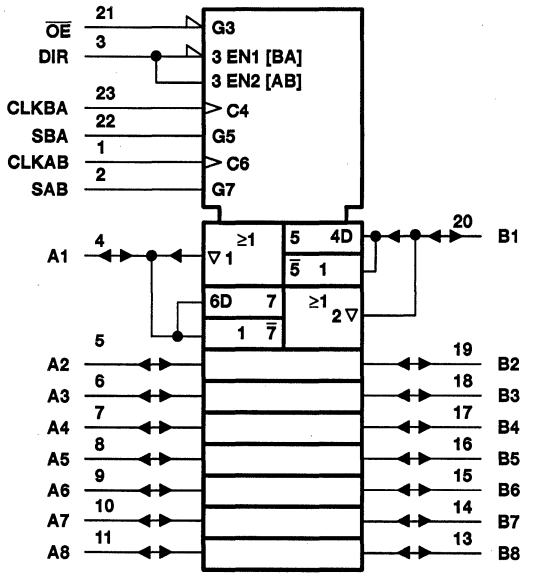
21	3	1	23	2	22
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA
TO A AND/OR B

Figure 1. Bus-Management Functions

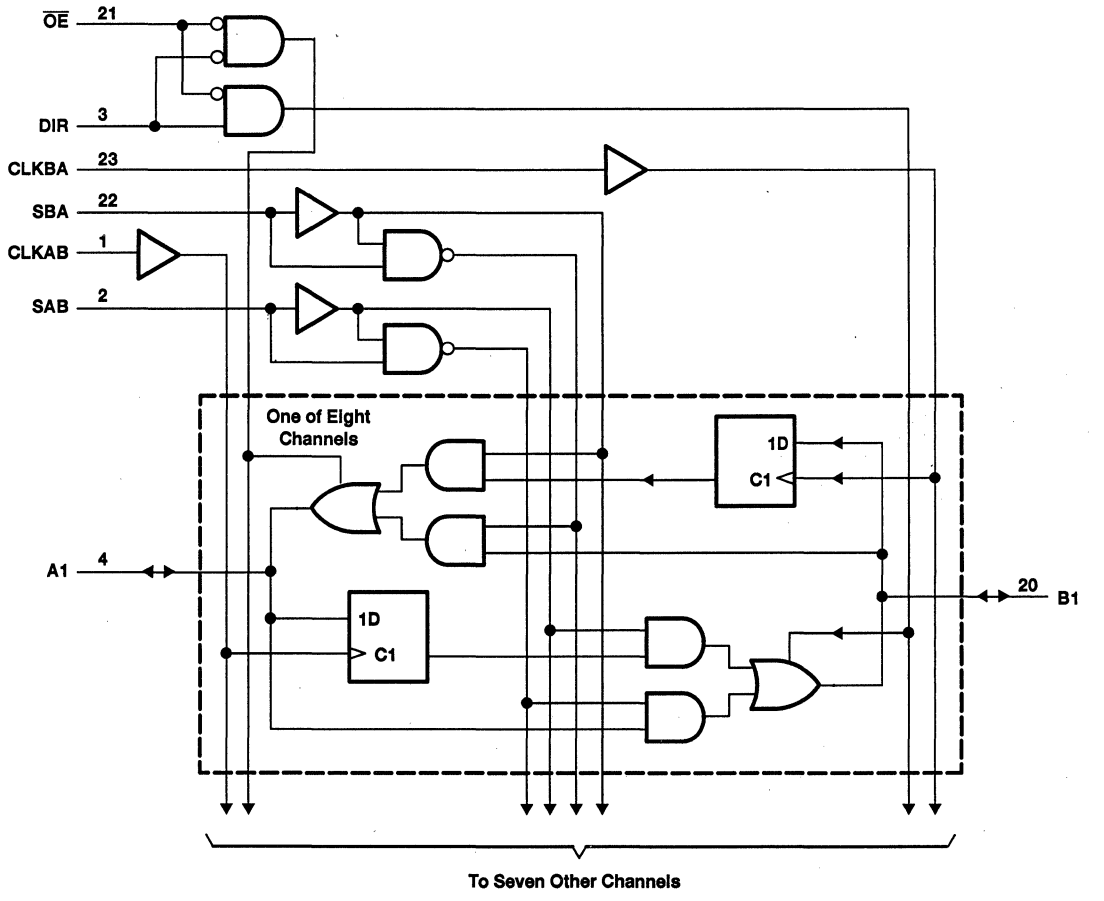
Pin numbers shown are for the DB, DW, JT, PW, and W packages.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, PW, and W packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT646 ..... 96 mA
SN74LVT646 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT646 ..... 48 mA
SN74LVT646 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT646		SN74LVT646		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT646			SN74LVT646			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			100			20	
		V_I = V_{CC}				1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.13	0.39		0.13	0.19	mA
			Outputs low		8.8	14		8.8	12	
			Outputs disabled		0.13	0.39		0.13	0.19	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4.5			4.5		pF
C_{io}	V_O = 3 V or 0				11			11		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused terminals at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

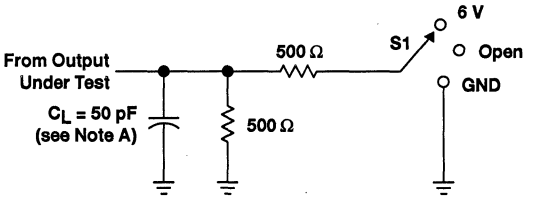
			SN54LVT646				SN74LVT646				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high	1.5		1.5		1.3		1.3		ns
		Data low	2.5		3.0		2		2.4		
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑		0.9		0.9		0.4		0.4		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT646				SN74LVT646					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150				150					MHz
t_{PLH}	CLKBA or CLKAB	A or B	1.2	5.9		6.9	1.8	3.8	5.7		6.7	ns
t_{PHL}			1.2	5.9		6.6	2.1	3.8	5.7		6.4	
t_{PLH}	A or B	B or A	0.8	4.9		5.6	1.3	2.8	4.7		5.4	ns
t_{PHL}			0.6	4.8		5.5	1	2.7	4.6		5.3	
t_{PLH}	SBA or SAB‡	A or B	1	6.4		7.4	1.4	3.7	6.2		7.2	ns
t_{PHL}			1	6.4		7	1.4	3.8	6.2		6.8	
t_{PZH}	$\overline{OE}$	A or B	0.6	6		7.4	1	3	5.8		7.2	ns
t_{PZL}			0.6	6.2		7.5	1	3.2	6		7.3	
t_{PHZ}	$\overline{OE}$	A or B	1.4	6.7		7.1	2.3	4.3	6.5		6.9	ns
t_{PLZ}			1.4	6.4		6.5	2.2	3.8	5.8		5.9	
t_{PZH}	DIR	A or B	0.6	6.7		7.7	1	3.4	6.5		7.5	ns
t_{PZL}			0.8	6.5		7.3	1.2	3.4	6.3		7.1	
t_{PHZ}	DIR	A or B	0.8	7.4		8.3	1.7	4.1	7.2		8.1	ns
t_{PLZ}			1	6.7		7	1.5	3.5	5.8		6.3	

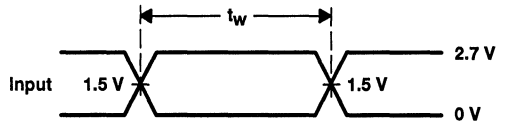
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ These parameters are measured with the internal output state of the storage register opposite to that of the bus input.

PARAMETER MEASUREMENT INFORMATION

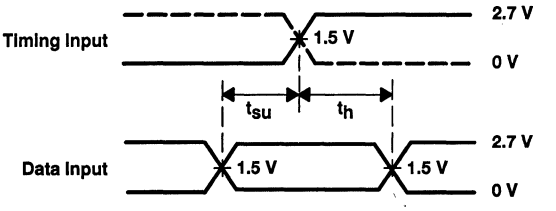


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

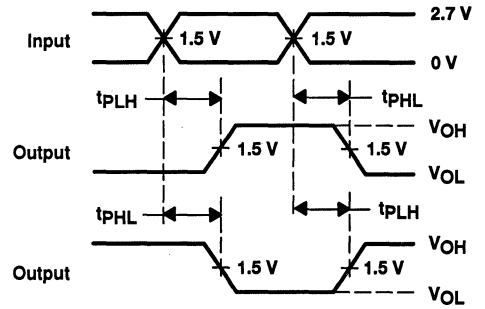
LOAD CIRCUIT FOR OUTPUTS



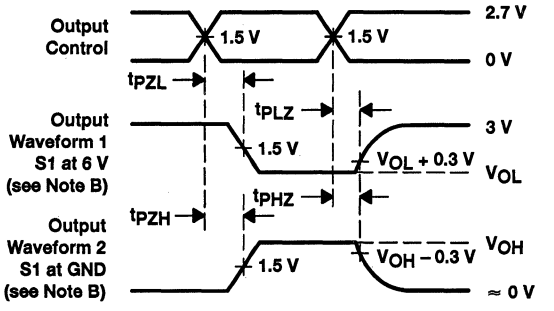
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



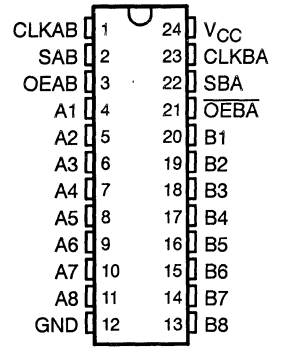
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

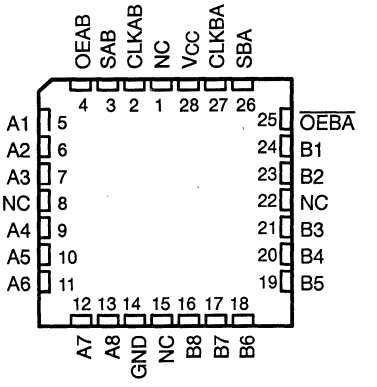
Figure 2. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Support Live Insertion**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (JT) DIPs**

SN54LVT652 . . . JT PACKAGE
SN74LVT652 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT652 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These bus transceivers and registers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT652 consist of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers.

Output-enable (OEAB and $\overline{\text{OEBA}}$) inputs are provided to control the transceiver functions. Select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between real-time and stored data. A low input selects real-time data and a high input selects stored data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'LVT652.

description (continued)

Data on the A or B data bus, or both, can be stored in the internal D-type flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs regardless of the select- or enable-control pins. When SAB and SBA are in the real-time transfer mode, it is possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{\text{OEBA}}$. In this configuration, each output reinforces its input; therefore, when all other data sources to the two sets of bus lines are at high impedance, each set of bus lines remains at its last state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

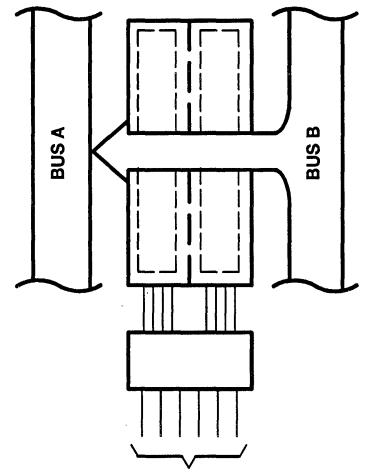
The SN74LVT652 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT652 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT652 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

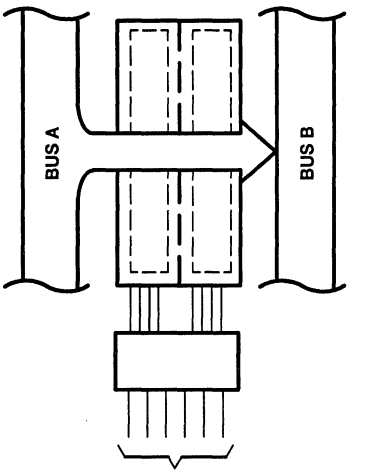
INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

† The data output functions may be enabled or disabled by a variety of level combinations at the OEAB or $\overline{\text{OEBA}}$ inputs. Data input functions are always enabled; i.e., data at the bus pins is stored on every low-to-high transition of the clock inputs.
‡ Select control = L; clocks can occur simultaneously
Select control = H; clocks must be staggered in order to load both registers



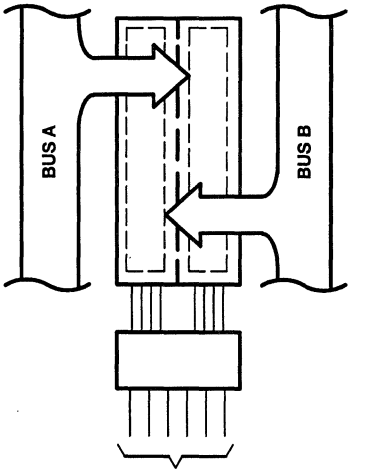
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



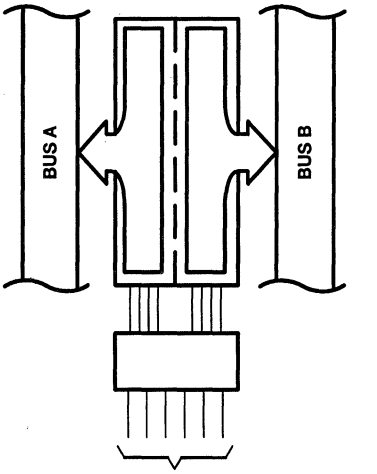
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B



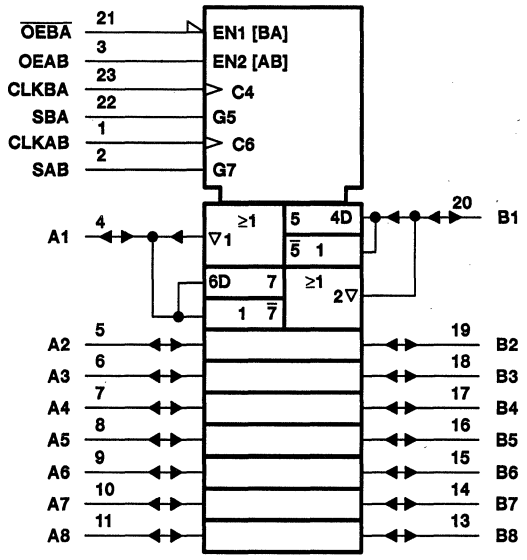
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	L	H or L	H or L	H	H

TRANSFER STORED DATA
TO A AND/OR B

Figure 1. Bus-Management Functions

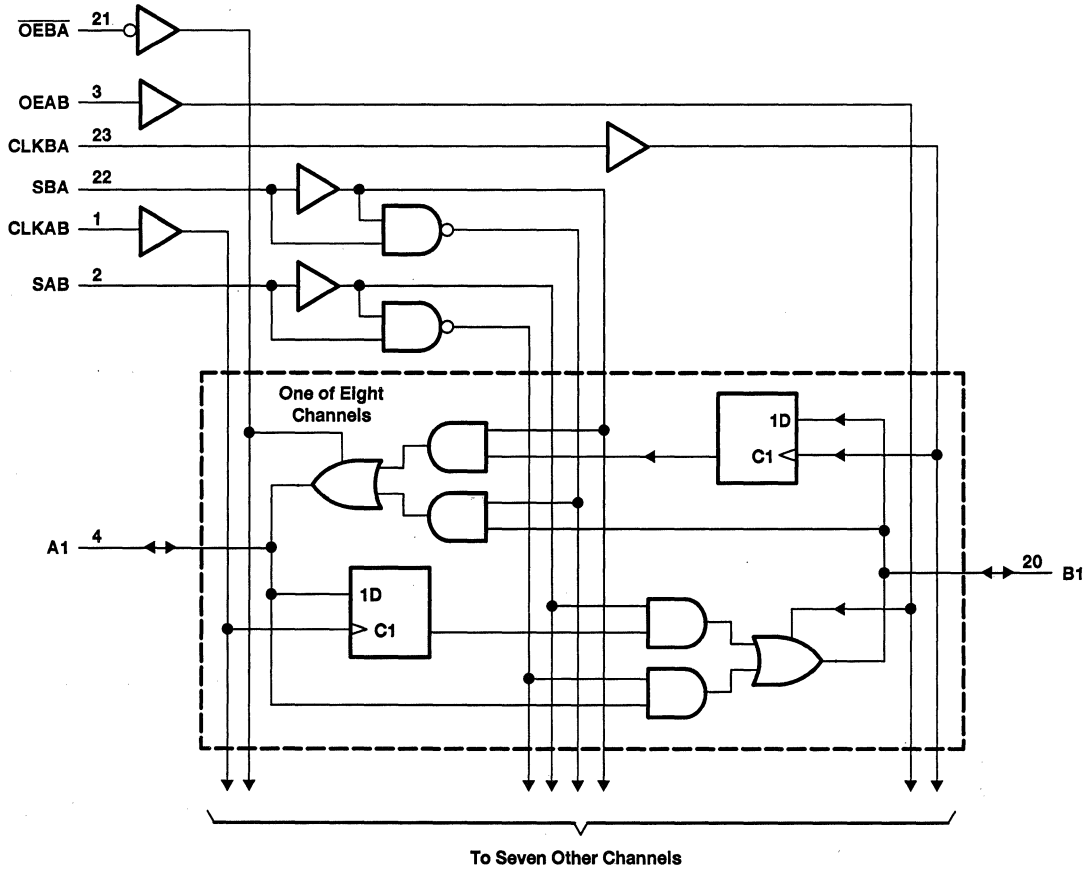
Pin numbers shown are for the DB, DW, JT, and PW packages.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, and PW packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT652 ..... 96 mA
SN74LVT652 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT652 ..... 48 mA
SN74LVT652 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT652		SN74LVT652		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT652			SN74LVT652			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA		V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = −8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = −24 mA		2						
		I_{OH} = −32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				5			5	
		V_I = 0				−10			−10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		−75			−75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				−1			−1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.13	0.19		0.13	0.19	mA
			Outputs low		8.8	12		8.8	12	
			Outputs disabled		0.13	0.19		0.13	0.19	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} − 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				4.5			4.5		pF
C_{io}	V_O = 3 V or 0				11			11		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused terminals at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

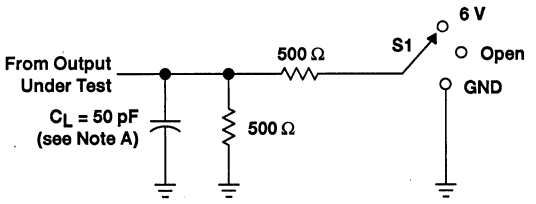
			SN54LVT652				SN74LVT652				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low						3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high					1.2		1.2		ns
		Data low					2		2.5		
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑						0.5		0.5		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT652				SN74LVT652					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}							150			150		MHz
t_{PLH}	CLKBA or CLKAB	A or B					1.8	3.7	6		6.9	ns
t_{PHL}							2	3.7	5.7		6.4	
t_{PLH}	A or B	B or A					1.2	2.8	4.7		5.5	ns
t_{PHL}							1	2.6	4.6		5.3	
t_{PLH}	SBA or SAB‡	A or B					1.4	3.7	6.4		7.6	ns
t_{PHL}							1.4	4	6.2		6.8	
t_{PZH}	$\overline{OEBA}$	A					1	2.9	5.8		7.2	ns
t_{PZL}							1	3	6		7.3	
t_{PHZ}	$\overline{OEBA}$	A					2.2	3.9	6.5		6.9	ns
t_{PLZ}							1.8	3.2	5.8		5.9	
t_{PZH}	OEAB	B					1	3.3	6.5		7.5	ns
t_{PZL}							1.2	3.4	6.3		7.1	
t_{PHZ}	OEAB	B					1.7	4.5	7.2		8.1	ns
t_{PLZ}							1.5	3.8	5.8		6.3	

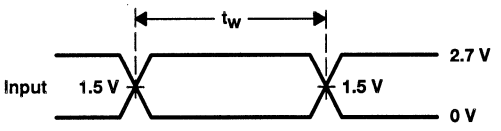
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ These parameters are measured with the internal output state of the storage register opposite to that of the bus input.

PARAMETER MEASUREMENT INFORMATION

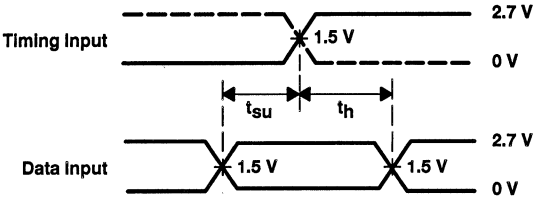


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

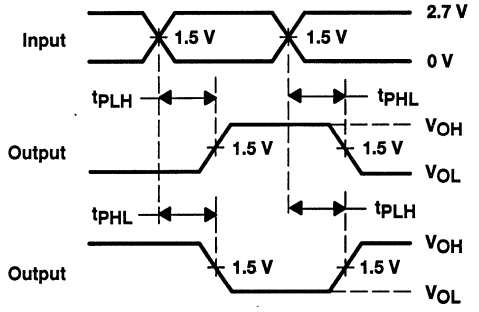
LOAD CIRCUIT FOR OUTPUTS



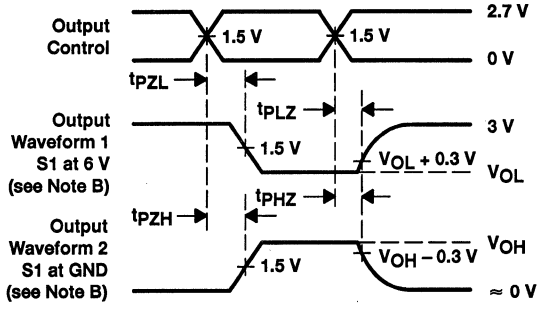
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



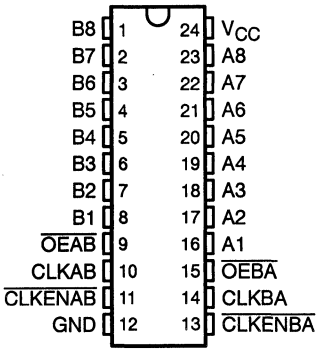
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

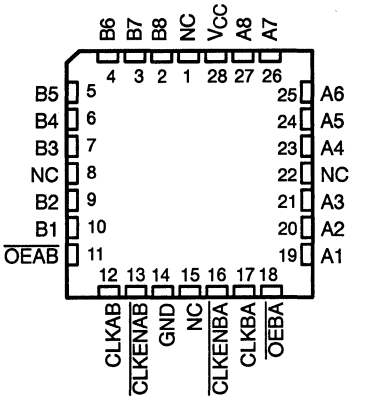
Figure 2. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Support Live Insertion**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (JT) DIPs**

SN54LVT2952 . . . JT PACKAGE
SN74LVT2952 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT2952 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These octal bus transceivers and registers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT2952 consist of two 8-bit back-to-back registers that store data flowing in both directions between two bidirectional buses. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input provided that the clock-enable ($\overline{\text{CLKENAB}}$ or $\overline{\text{CLKENBA}}$) input is low. Taking the output-enable ($\overline{\text{OEAB}}$ or $\overline{\text{OEBA}}$) input low accesses the data on either port.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVT2952 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

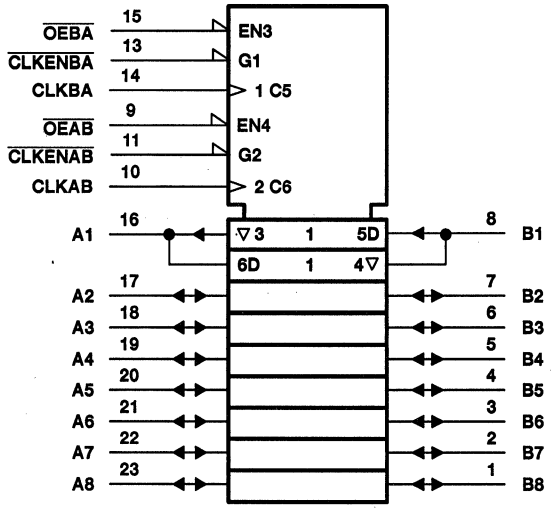
The SN54LVT2952 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT2952 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CLKENAB}$	CLKAB	$\overline{OEAB}$	A	B
H	X	L	X	B_0‡
X	H or L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

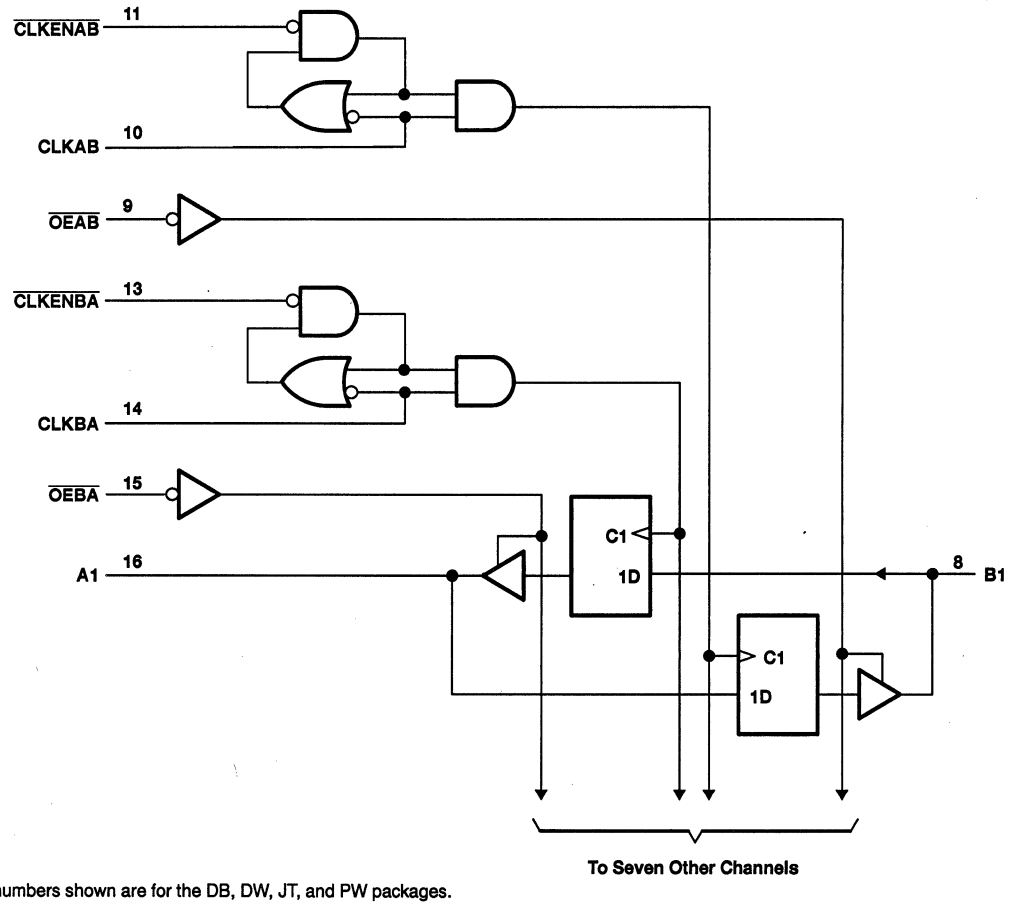
† A-to-B data flow is shown; B-to-A data flow is similar but uses $\overline{CLKENBA}$, CLKBA, and $\overline{OEBA}$.
‡ Level of B before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, and PW packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT2952 ..... 96 mA
SN74LVT2952 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT2952 ..... 48 mA
SN74LVT2952 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT2952		SN74LVT2952		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT2952			SN74LVT2952			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				5			5	
		V_I = 0				–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.13	0.19		0.13	0.19	mA
			Outputs low		8.8	12		8.8	12	
			Outputs disabled		0.13	0.19		0.13	0.19	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				4.5			4.5		pF
C_{io}	V_O = 3 V or 0				11.5			11.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused terminals at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirement over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

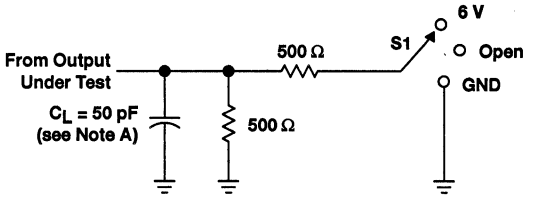
			SN54LVT2952				SN74LVT2952				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency							150		150	MHz
t_w	Pulse duration	CLK high					3.3		3.3		ns
		CLK low					3.3		3.3		
t_{su}	Setup time, A or B before CLK↑	Data high	2.6		2.9		2.5		2.8		ns
		Data low	2.6		3.1		2.5		3		
	Setup time, $\overline{CE}$ before CLK↑	Data high	0.9		0.8		0.9		0.8		
		Data low	2.5		2.7		2.4		2.7		
t_h	Hold time, A or B after CLK↑		1.5		0.7		1.5		0.7		ns
	Hold time, $\overline{CE}$ after CLK↑		2.6		2.6		2.5		2.6		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT2952				SN74LVT2952					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}							150			150		MHz
t_{PLH}	CLKBA or CLKAB	A or B	1.3	6.4	2.7	7.4	1.3	3.6	6.1	2.7	7.1	ns
t_{PHL}			1.8	6.1	2.7	7	1.8	3.7	6	2.7	6.9	
t_{PZH}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	1	6.3	2.6	7.3	1	3.2	5.6	2.6	6.7	ns
t_{PZL}			1.1	6.6	2.9	8.2	1.2	3.2	6.5	2.9	8	
t_{PHZ}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	1	7	2.7	7.6	1	4.1	6.3	2.7	6.9	ns
t_{PLZ}			1.6	5.8	1.7	6	1.6	3.3	5.1	1.8	5.3	

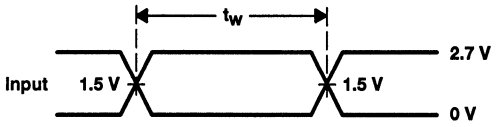
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

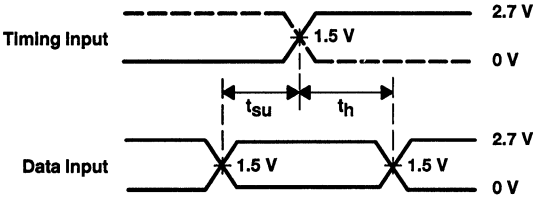


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

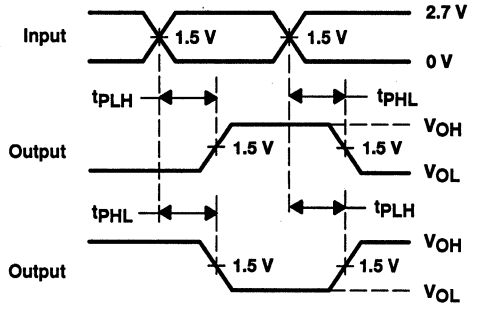
LOAD CIRCUIT FOR OUTPUTS



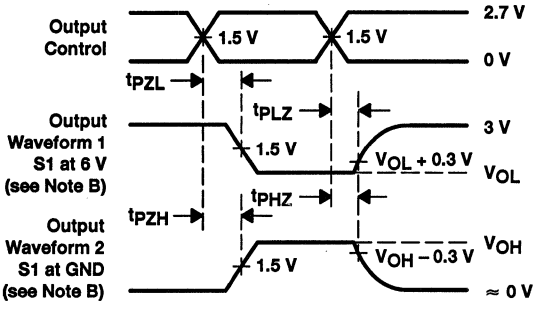
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

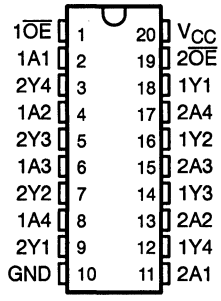
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

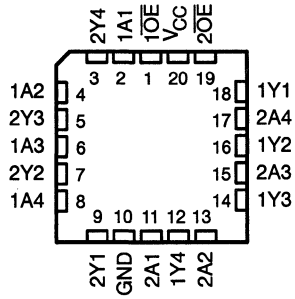
Contents

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs**

SN54LVTZ240 . . . J PACKAGE
SN74LVTZ240 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTZ240 . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers and line drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

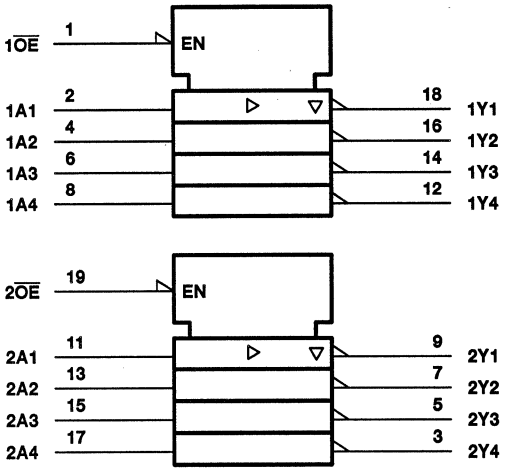
The SN74LVTZ240 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVTZ240 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTZ240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

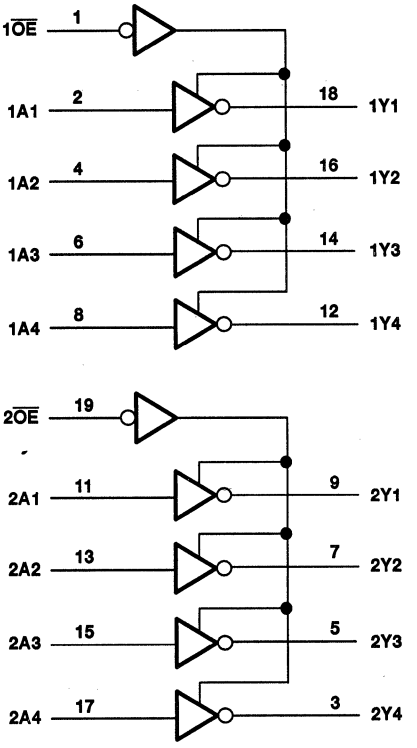
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTZ240 ..... 96 mA
SN74LVTZ240 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTZ240 ..... 48 mA
SN74LVTZ240 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVTZ240		SN74LVTZ240		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTZ240			SN74LVTZ240			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	µA
	V_{CC} = 0 to 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0 V,	V_I or V_O = 0 to 4.5 V							±100	µA
I_{OZPU}§	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V to 3 V,	$\overline{OE}$ = X						±50	µA
I_{OZPD}§	V_{CC} = 1.5 V to 0,	V_O = 0.5 V to 3 V,	$\overline{OE}$ = X						±50	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A inputs	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				5			5	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–5			–5	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.12	0.5		0.12	0.225	mA
			Outputs low		8.6	14		8.6	12	
			Outputs disabled		0.12	0.5		0.12	0.225	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				8			8		pF

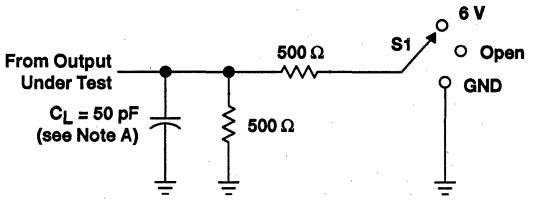
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This parameter is specified by characterization.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTZ240				SN74LVTZ240					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A	Y	1	4.5		5.4	1	2.5	4.3		5.2	ns
t_{PHL}			1	4.5		5.2	1	2.5	4.3		5	
t_{PZH}	$\overline{OE}$	Y	1	5.4		6.5	1	2.7	5.2		6.3	ns
t_{PZL}			1	5.8		7.4	1	3.1	5.2		6.7	
t_{PHZ}	$\overline{OE}$	Y	2	5.8		6.5	2	3.9	5.6		6.3	ns
t_{PLZ}			1.6	5.3		5.8	1.6	3.2	5.1		5.6	

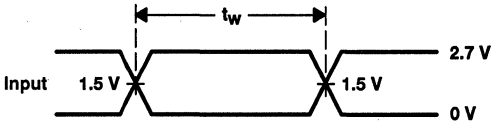
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

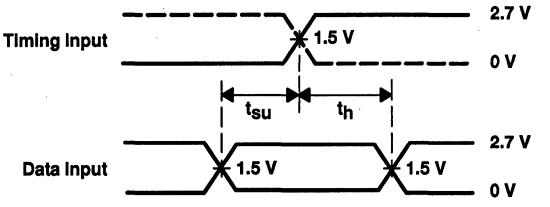


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

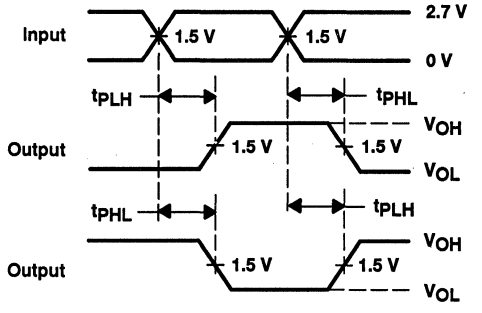
LOAD CIRCUIT FOR OUTPUTS



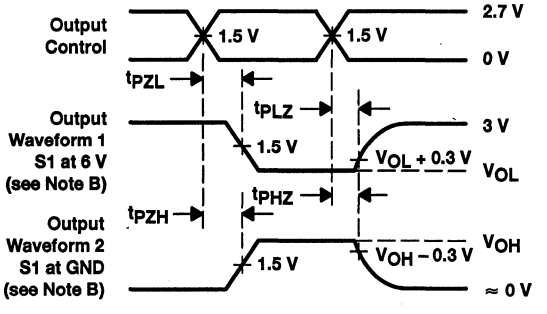
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



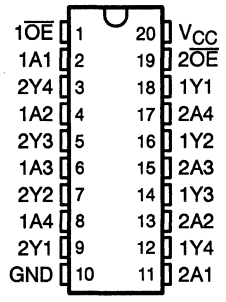
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

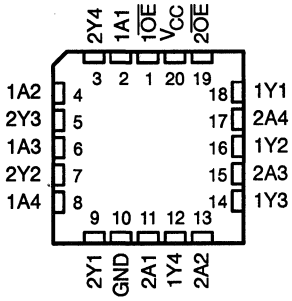
Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- High-Impedance State During Power Up and Power Down
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs

SN54LVTZ244 . . . J PACKAGE
SN74LVTZ244 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTZ244 . . . FK PACKAGE
(TOP VIEW)



description

These octal buffers/drivers are designed specifically for low-voltage (3.3-V) V_{CC} operation with the capability to provide a TTL interface to a 5-V system environment.

These devices are organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

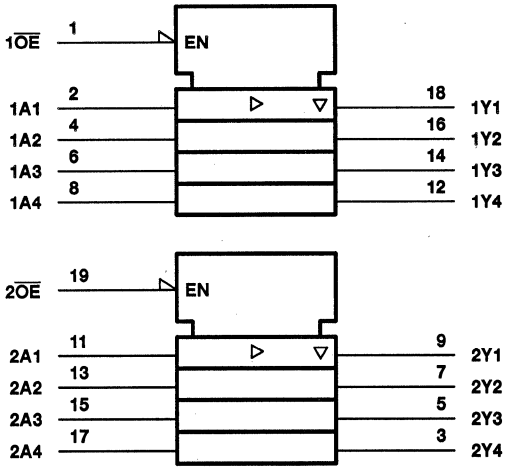
The SN74LVTZ244 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVTZ244 is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74LVTZ244 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each buffer)

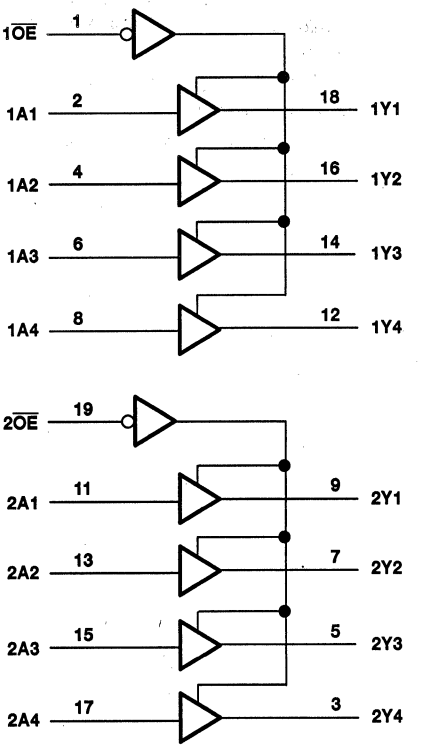
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTZ244 ..... 96 mA
SN74LVTZ244 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTZ244 ..... 48 mA
SN74LVTZ244 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Operating free-air temperature range, T_A: SN54LVTZ244 ..... −55°C to 125°C
SN74LVTZ244 ..... −40°C to 85°C
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVTZ244		SN74LVTZ244		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		μs/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTZ244			SN74LVTZ244			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA				−1.2			−1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA		V_{CC}−0.2			V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = − 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = − 24 mA		2						
		I_{OH} = −32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	µA
	V_{CC} = 0 to 3.6 V	V_I = V_{CC} or GND	Control inputs			±1			±1	
		V_I = V_{CC}	Data inputs			1			1	
		V_I = 0				−5			−5	
I_{off}	V_{CC} = 0 V,	V_I or V_O = 0 to 4.5 V							±100	µA
I_{OZPU}§	V_{CC} = 0 V to 1.5 V,	V_O = 0.5 V to 3 V,	$\overline{OE}$ = X						±50	µA
I_{OZPD}§	V_{CC} = 1.5 V to 0,	V_O = 0.5 V to 3 V,	$\overline{OE}$ = X						±50	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A inputs	75			75			µA
		V_I = 2 V		−75			−75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				5			5	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				−5			−5	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.12	0.5		0.12	0.225	mA
			Outputs low		8.6	15		8.6	15	
			Outputs disabled		0.12	0.5		0.12	0.225	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} − 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				8			8		pF

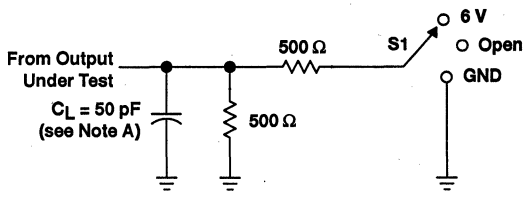
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This parameter is specified by characterization.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTZ244				SN74LVTZ244				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	Y	1	4.7		5.2	1	2.5	4.1	5	ns
t_{PHL}			1	4.4		5.4	1	2.5	4.1	5.2	
t_{PZH}	$\overline{OE}$	Y	1	5.4		6.5	1	2.7	5.2	6.3	ns
t_{PZL}			1.1	5.4		7.6	1.1	3.1	5.2	6.7	
t_{PHZ}	$\overline{OE}$	Y	1.9	6.2		6.9	1.9	3.9	5.6	6.3	ns
t_{PLZ}			1.8	5.5		6	1.8	3.2	5.1	5.6	

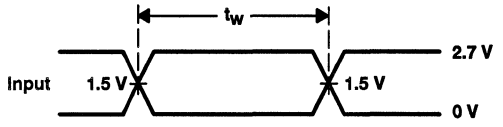
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

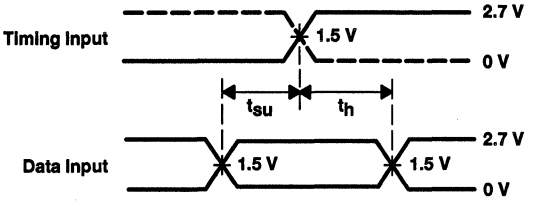


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

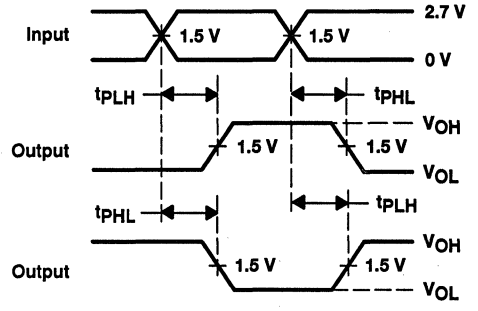
LOAD CIRCUIT FOR OUTPUTS



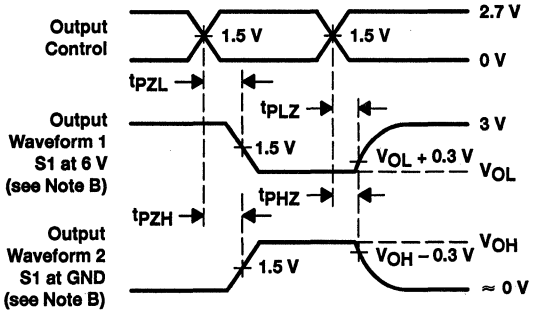
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



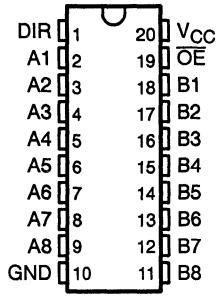
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

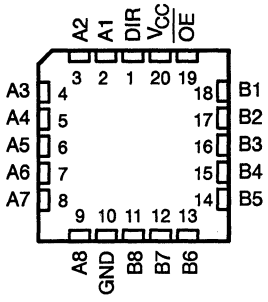
Figure 1. Load Circuit and Voltage Waveforms

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **High-Impedance State During Power Up and Power Down**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Ceramic (J) DIPs**

SN54LVTZ245 . . . J PACKAGE
SN74LVTZ245 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVTZ245 . . . FK PACKAGE
(TOP VIEW)



description

These octal bus transceivers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are designed for asynchronous communication between data buses. They transmit data from the A bus to the B bus or from the B bus to the A bus depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the devices so the buses are effectively isolated.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVTZ245 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

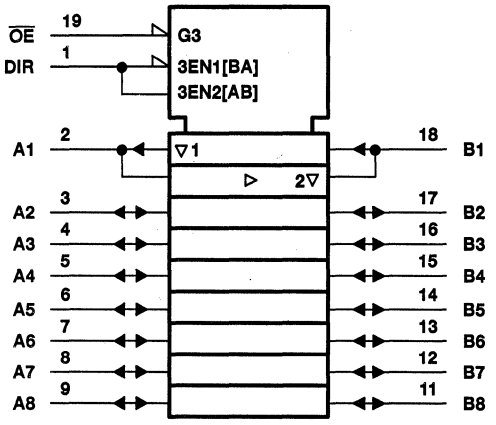
The SN54LVTZ245 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTZ245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

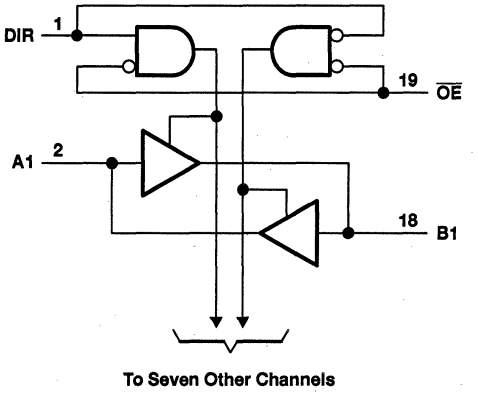
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

PRODUCT PREVIEW

logic symbol†



logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVTZ245 ..... 96 mA
SN74LVTZ245 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVTZ245 ..... 48 mA
SN74LVTZ245 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVTZ245		SN74LVTZ245		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		µs/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVTZ245			SN74LVTZ245			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V	Control inputs			10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			100			20	
		V_I = V_{CC}	A or B ports§			5			5	
		V_I = 0	A or B ports§			–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
I_{OZPU}¶	V_{CC} = 0 to 1.5 V,	V_O = 0.5 V to 3 V,	$\overline{OE}$ = X						±50	µA
I_{OZPD}¶	V_{CC} = 1.5 V to 0,	V_O = 0.5 V to 3 V,	$\overline{OE}$ = X						±50	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V	A or B ports	–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.13	0.5		0.13	0.19	mA
			Outputs low		8.8	14		8.8	12	
			Outputs disabled		0.13	0.5		0.13	0.19	
ΔI_{CC}#	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				10			10		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused terminals at V_{CC} or GND
¶ This parameter is specified by characterization but is not tested.
# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

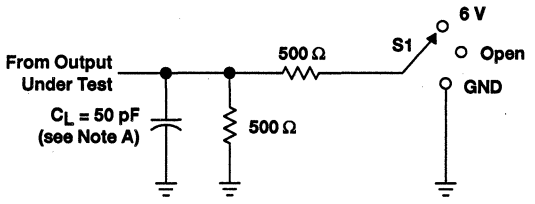
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVTZ245				SN74LVTZ245				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A or B	B or A	1	4.6		5.3	1	2.5	4	5.2	ns
t_{PHL}			1	4.1		5.7	1	2.5	4	5.5	
t_{PZH}	$\overline{OE}$	A or B	1.1	6.1		7.2	1.1	3.3	5.9	7.1	ns
t_{PZL}			1.5	6.6		8	1.5	3.8	6.5	7.9	
t_{PHZ}	$\overline{OE}$	A or B	2.2	6.2		7	2.2	4.3	5.9	6.5	ns
t_{PLZ}			2	6.3		5.9	2	3.9	5.5	5.6	

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

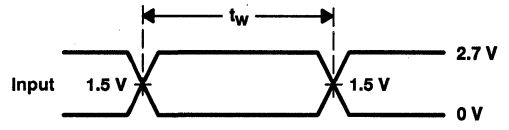
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION

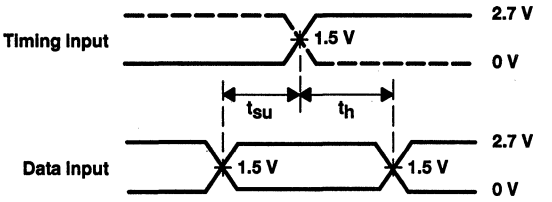


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

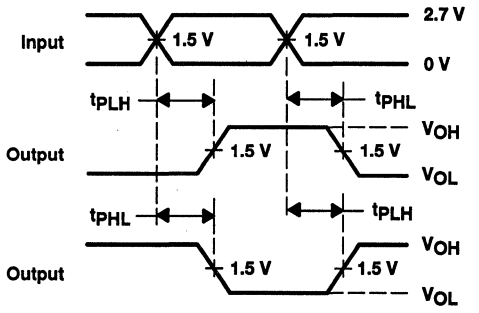
LOAD CIRCUIT FOR OUTPUTS



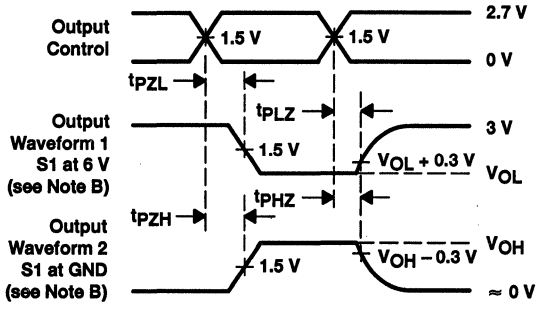
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

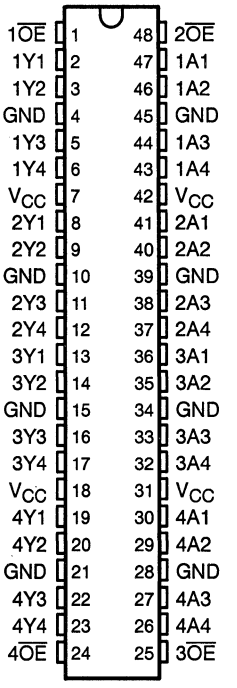
Figure 1. Load Circuit and Voltage Waveforms

PRODUCT PREVIEW

Contents

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Packaged in Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16244A . . . WD PACKAGE
SN74LVT16244A . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT16244A are 16-bit buffers and line drivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. These devices provide true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVT16244A is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

Widebus is a trademark of Texas Instruments Incorporated.

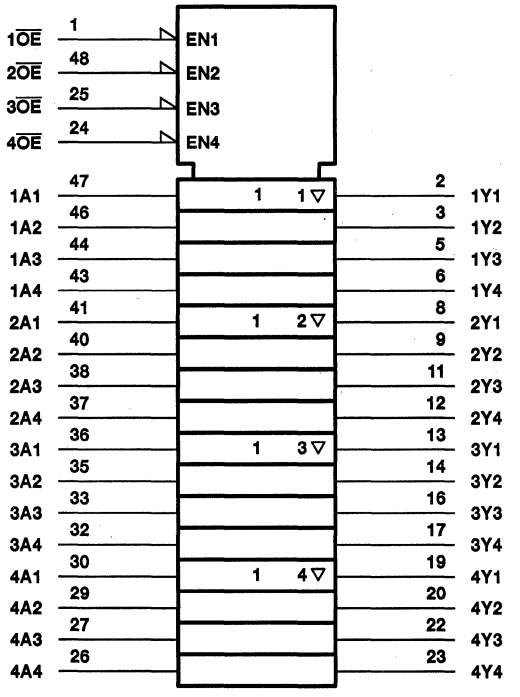
description (continued)

The SN54LVT16244A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

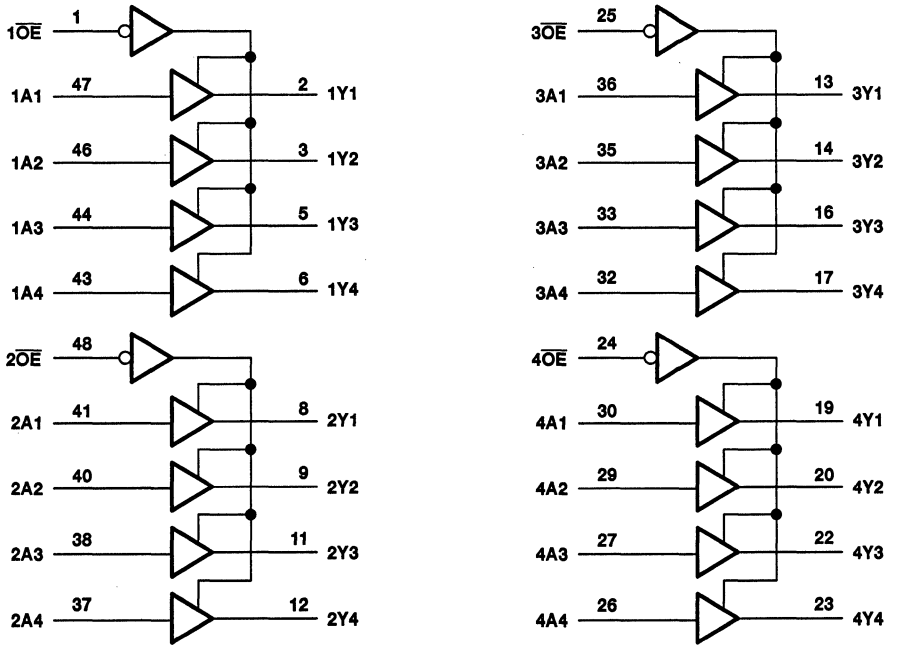
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16244A ..... 96 mA
SN74LVT16244A ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16244A ..... 48 mA
SN74LVT16244A ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT16244A		SN74LVT16244A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT16244A		SN74LVT16244A			UNIT
				MIN	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA		V_{CC}−0.2		V_{CC}−0.2			V
	V_{CC} = 2.7 V,	I_{OH} = − 8 mA		2.4		2.4			
	V_{CC} = 3 V	I_{OH} = − 24 mA		2					
		I_{OH} = −32 mA				2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
		I_{OL} = 24 mA			0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
		I_{OL} = 32 mA			0.5			0.5	
		I_{OL} = 48 mA			0.55				
		I_{OL} = 64 mA						0.55	
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V			50			10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs		±1			±1	
		V_I = V_{CC}	Data inputs		1			1	
		V_I = 0			−5			−5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A inputs	75		75			µA
		V_I = 2 V		−75		−75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V			−5			−5	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.19			0.09	mA
			Outputs low		5			5	
			Outputs disabled		0.19			0.09	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} − 0.6 V,			0.2			0.2	mA
C_i	V_I = 3 V or 0						4		pF
C_o	V_O = 3 V or 0						10		pF

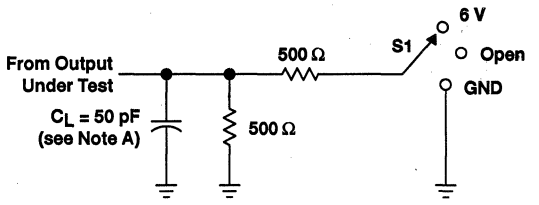
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT16244A				SN74LVT16244A					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A	Y	1	4.4		5.1	1	2.3	4.1		5	ns
t_{PHL}			1	4.5		5.3	1	2.3	4.1		5.2	
t_{PZH}	$\overline{OE}$	Y	1	5.3		6.4	1	2.6	5.2		6.3	ns
t_{PZL}			1	5.3		6.8	1	2.6	5.2		6.7	
t_{PHZ}	$\overline{OE}$	Y	2.1	7		7.7	2.2	3.9	5.7		6.3	ns
t_{PLZ}			1.9	5.9		5.9	2	3.7	5.1		5.6	

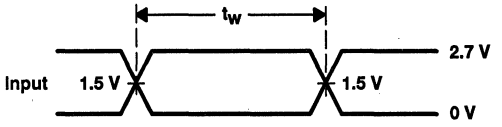
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

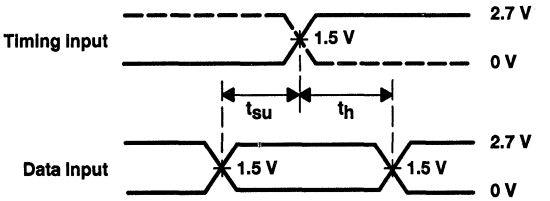


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

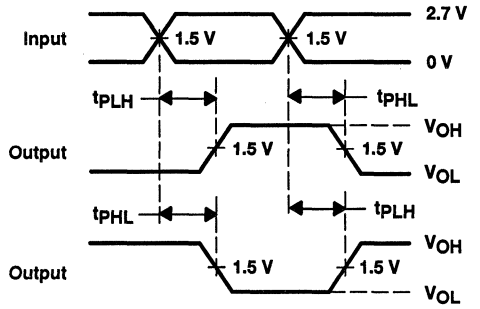
LOAD CIRCUIT FOR OUTPUTS



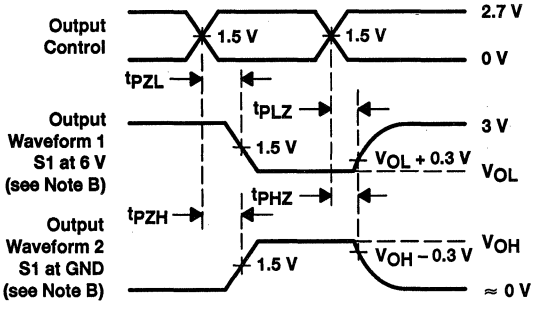
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



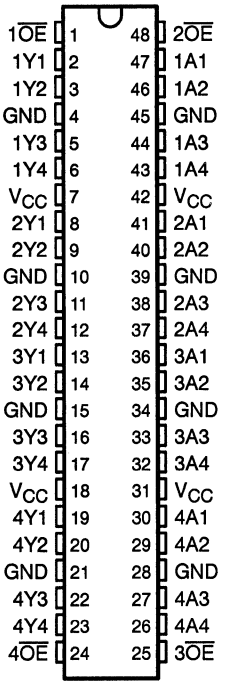
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Output Ports Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT162244 . . . WD PACKAGE
SN74LVT162244 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT162244 are 16-bit buffers and line drivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. These devices provide true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

The outputs, which are designed to source or sink up to 12 mA, include 22-Ω series resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

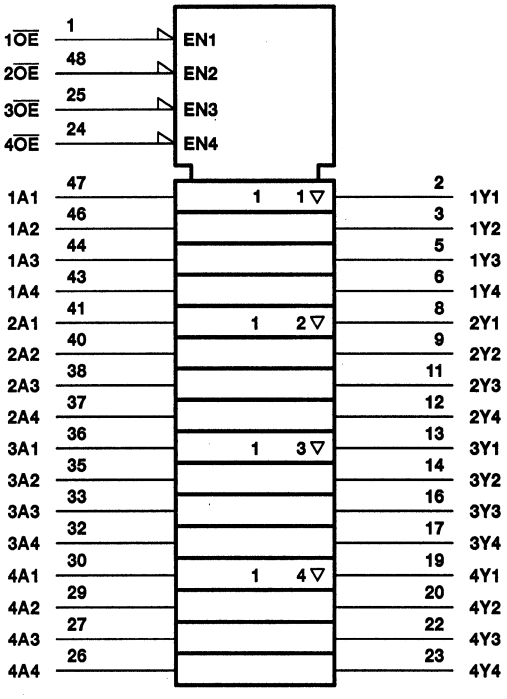
The SN74LVT162244 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT162244 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT162244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

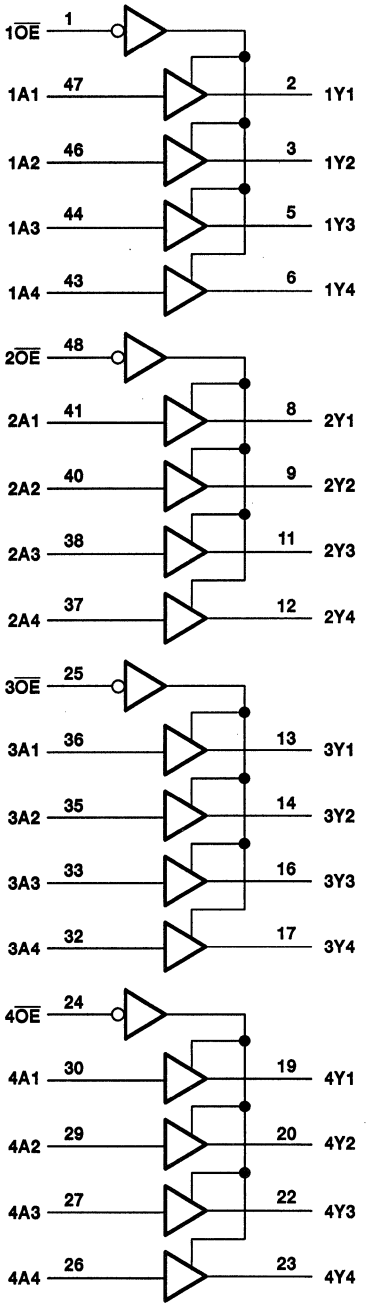
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O ..... 30 mA
Current into any output in the high state, I_O (see Note 2) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT162244		SN74LVT162244		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−12		−12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT162244			SN74LVT162244			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = 3 V,	I_{OH} = – 12 mA		2			2			V
V_{OL}	V_{CC} = 3 V,	I_{OL} = 12 mA				0.8			0.8	V
I_I	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control pins			±1			±1	
		V_I = V_{CC}	Data pins			1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A inputs	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				5			5	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–5			–5	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.19			0.09	mA
			Outputs low			5			5	
			Outputs disabled			0.19			0.09	
ΔI_{CC}§	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND					0.2			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_o	V_O = 3 V or 0				10			10		pF

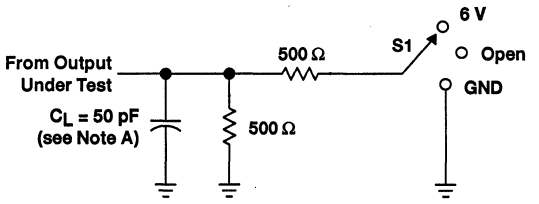
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT162244				SN74LVT162244					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A	Y	1.4	5.2		6.1	1.4	3.2	4.9		5.8	ns
t_{PHL}			1.1	5.1		6.3	1.1	3.1	5		6.1	
t_{PZH}	$\overline{OE}$	Y	1	6.6		7.3	1	4.7	6.4		7.1	ns
t_{PZL}			1.4	5.7		7.4	1.4	3.4	5.6		7.3	
t_{PHZ}	$\overline{OE}$	Y	2.6	6.9		7.6	2.6	4.5	6.6		7.3	ns
t_{PLZ}			2.6	6.1		6.8	2.6	3.6	5.8		6.5	

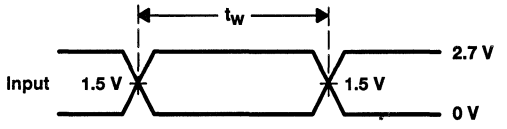
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

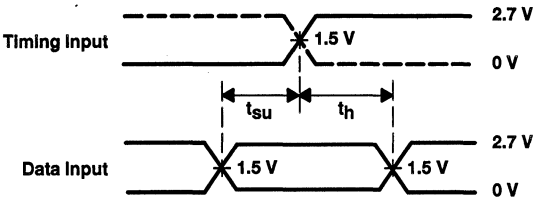


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

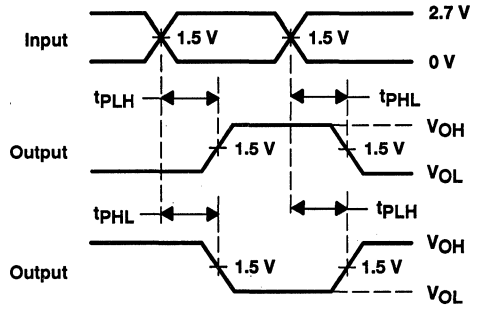
LOAD CIRCUIT FOR OUTPUTS



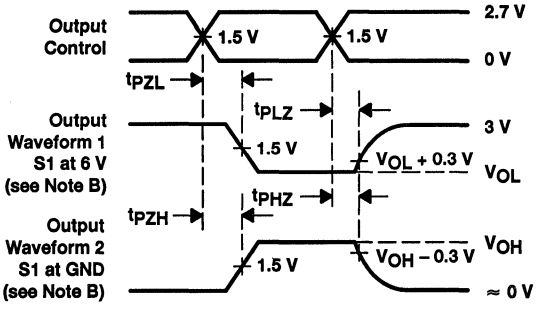
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



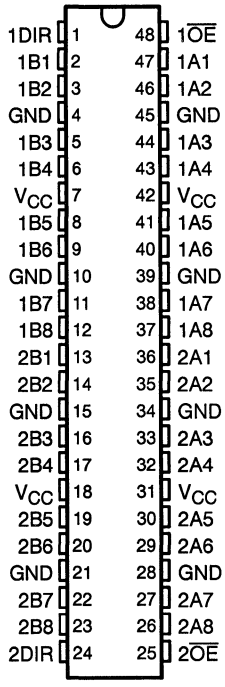
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Packaged in Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16245A . . . WD PACKAGE
SN74LVT16245A . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT16245A are 16-bit (dual-octal) noninverting 3-state transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices can be used as two 8-bit transceivers or one 16-bit transceiver. They allow data transmission from the A bus to the B bus or from the B bus to the A bus, depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

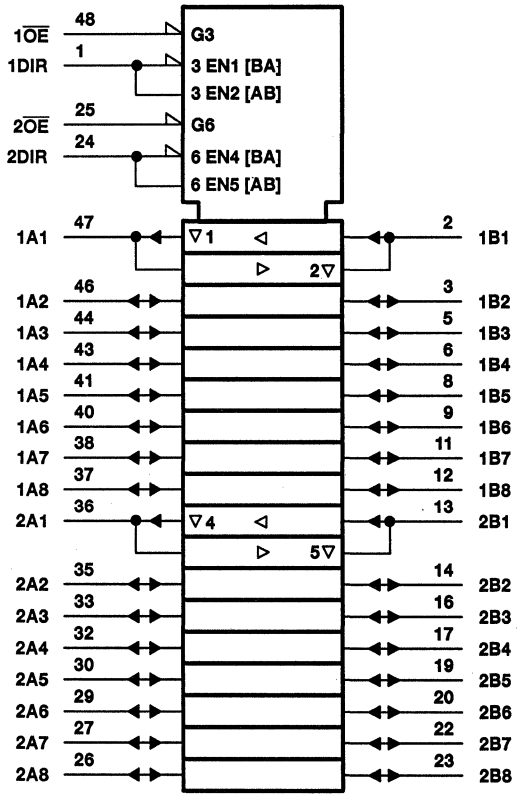
The SN74LVT16245A is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT16245A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

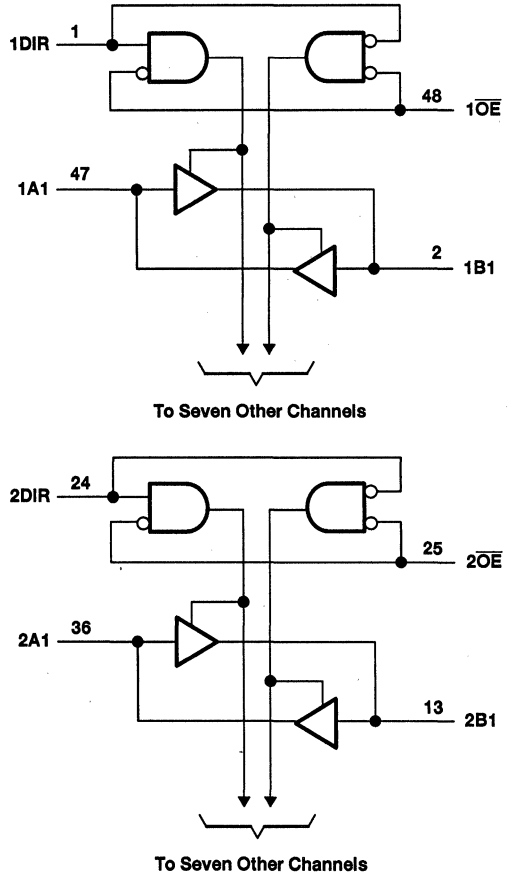
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) ..... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16245A ..... 96 mA
SN74LVT16245A ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16245A ..... 48 mA
SN74LVT16245A ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT16245A		SN74LVT16245A		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT16245A			SN74LVT16245A			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V	Control inputs			10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			100			20	
		V_I = V_{CC}	A or B ports§			1			1	
		V_I = 0	A or B ports§			–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V	A or B ports	–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				5			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–5			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.09			0.09	mA
			Outputs low			5			5	
			Outputs disabled			0.09			0.09	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				11			11		pF

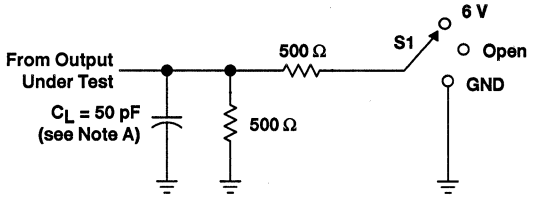
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT16245A				SN74LVT16245A				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A or B	B or A	0.5	4.4		5.3	1	2.4	4.1	5	ns
t_{PHL}			0.5	4.7		5.5	1	2.3	4.1	5.2	
t_{PZH}	$\overline{OE}$	A or B	0.5	7		7.7	1	3	5.3	6.3	ns
t_{PZL}			0.5	5.8		7.2	1	3.1	5.2	6.7	
t_{PHZ}	$\overline{OE}$	A or B	1	7.2		7.7	2.7	4.6	6.4	7.2	ns
t_{PLZ}			1	6.3		6.5	2.6	4.3	5.8	6.1	

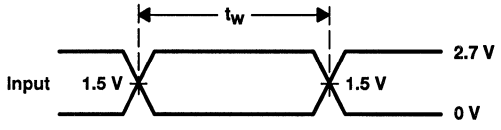
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

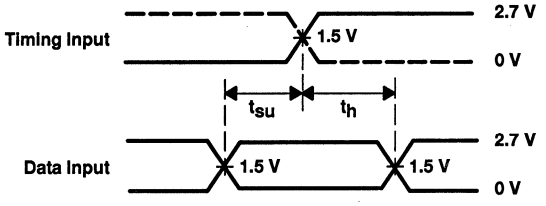


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

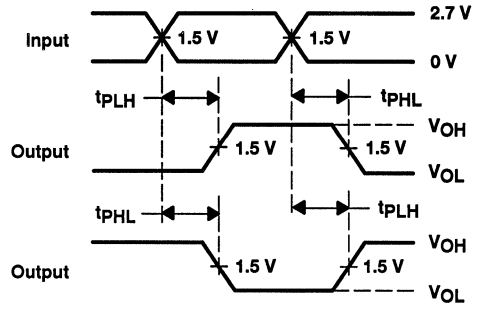
LOAD CIRCUIT FOR OUTPUTS



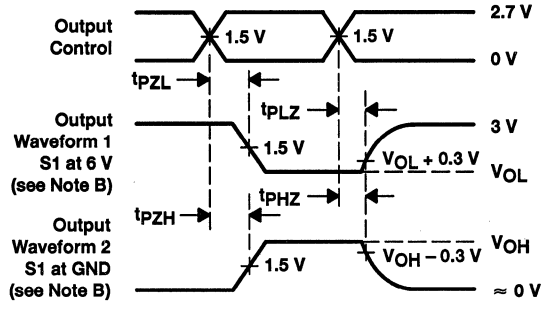
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



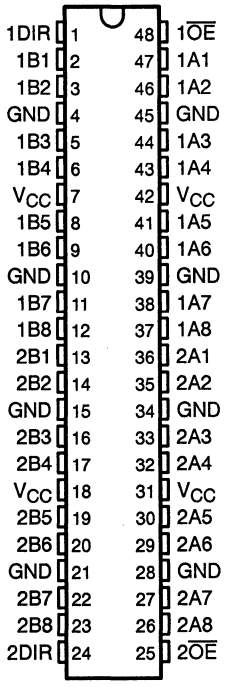
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- **A-Port Outputs Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Members of the Texas Instruments *Widebus*™ Family**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Support Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54LVT162245 . . . WD PACKAGE
SN74LVT162245 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT162245 are 16-bit (dual-octal) noninverting 3-state transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices can be used as two 8-bit transceivers or one 16-bit transceiver. The devices allow data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

The A-port outputs, which are designed to source or sink up to 8 mA, include 22-Ω series resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

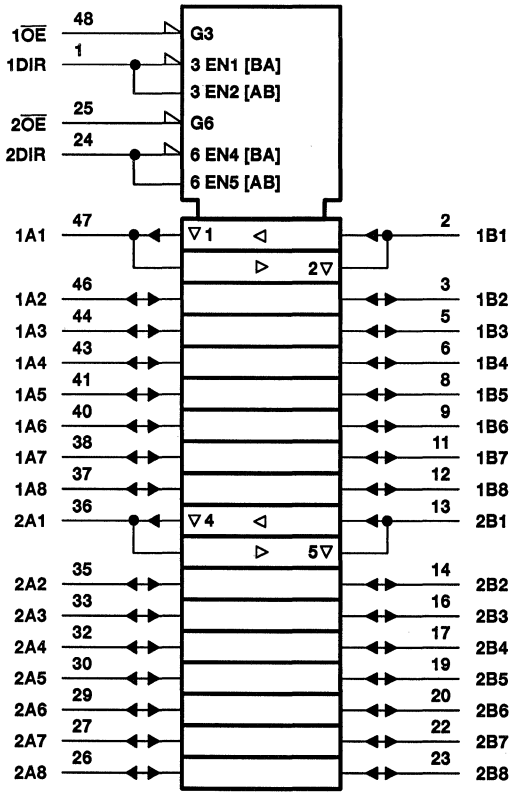
The SN74LVT162245 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the input/output (I/O) pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT162245 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT162245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

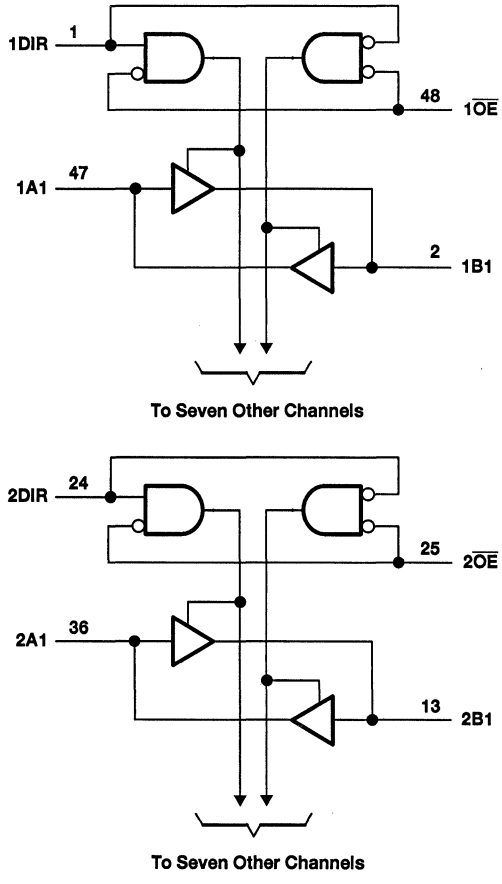
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT162245 (B port) ..... 96 mA
SN74LVT162245 (B port) ..... 128 mA
A port ..... 30 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT162245 (B port) ..... 48 mA
SN74LVT162245 (B port) ..... 64 mA
A port ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT162245		SN74LVT162245		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current	B port		−24		−32	mA
		A port		−8		−8	
I_{OL}	Low-level output current	A port		8		8	mA
		B port		48		64	
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			SN54LVT162245			SN74LVT162245			UNIT
					MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	A port	V_{CC} = 3 V,	I_{OH} = – 8 mA		2			2			V
	B port	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			
		V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
		V_{CC} = 3 V	I_{OH} = – 24 mA		2						
			I_{OH} = –32 mA					2			
V_{OL}	A port	V_{CC} = 3 V,	I_{OL} = 8 mA				0.8			0.8	V
	B port	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	
			I_{OL} = 24 mA				0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
			I_{OL} = 32 mA				0.5			0.5	
			I_{OL} = 48 mA				0.55				
			I_{OL} = 64 mA							0.55	
I_I	Control pins	V_{CC} = 3.6 V,	V_I = V_{CC} or GND				±1			±1	µA
		V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	A or B ports	V_{CC} = 3.6 V	V_I = 5.5 V				20			20	
			V_I = V_{CC}				5			5	
			V_I = 0				–10			–10	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V		75			75			µA
			V_I = 2 V		–75			–75			
		V_{CC} = 3.6 V,	V_I = 0 to 3.6 V				±500			±500	
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}		V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.09			0.09	mA
				Outputs low			5			5	
				Outputs disabled			0.09			0.09	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i		V_I = 3 V or 0				4			4		pF
C_{io}		V_O = 3 V or 0				10.5			10.5		pF

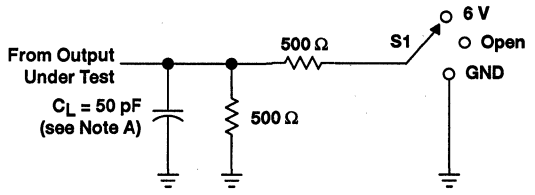
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT162245				SN74LVT162245				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	A	B	1	4.3		5.2	1	2.4	4.1	5	ns
t_{PHL}			1	4.3		5.3	1	2.3	4.1	5.2	
t_{PLH}	B	A	2	5.7		7.1	2	3.5	5.5	6.9	ns
t_{PHL}			1.9	4.8		5.7	1.9	3.3	4.7	5.6	
t_{PZH}	$\overline{OE}$	B	1	5.5		6.9	1	3	5.3	6.8	ns
t_{PZL}			1	5.4		6.8	1	3.1	5.2	6.7	
t_{PZH}	$\overline{OE}$	A	2.3	7.5		9.6	2.3	4.5	7.2	9.4	ns
t_{PZL}			2.4	6.9		8.4	2.4	4.1	6.6	8.2	
t_{PHZ}	$\overline{OE}$	B	2.7	6.7		7.4	2.7	4.6	6.4	7.2	ns
t_{PLZ}			2.6	6		6.3	2.6	4.3	5.8	6.1	
t_{PHZ}	$\overline{OE}$	A	3.3	7.6		8.3	3.3	5	7.3	8	ns
t_{PLZ}			3.4	6.9		7.5	3.4	5	6.7	7.1	

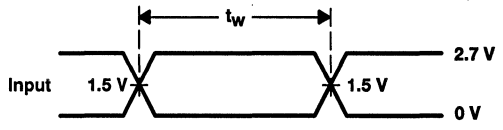
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

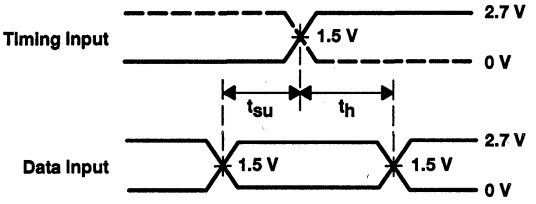


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

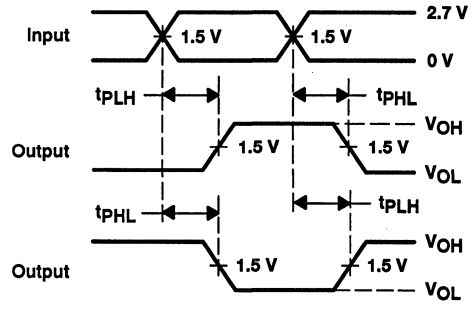
LOAD CIRCUIT FOR OUTPUTS



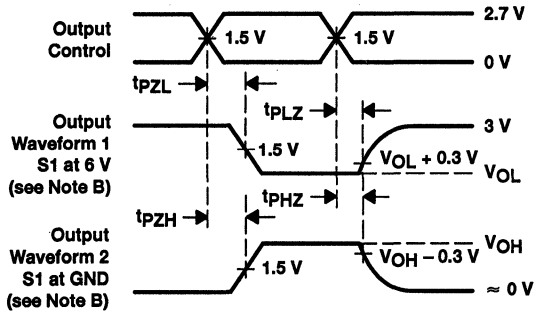
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



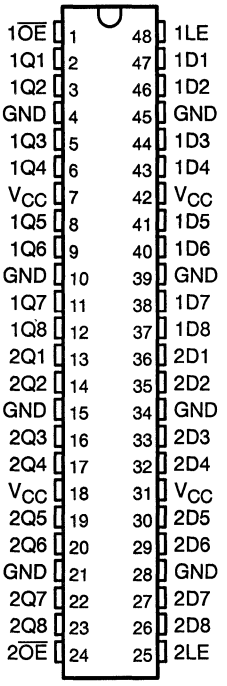
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16373 . . . WD PACKAGE
SN74LVT16373 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT16373 are 16-bit transparent D-type latches with 3-state outputs designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

These devices can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

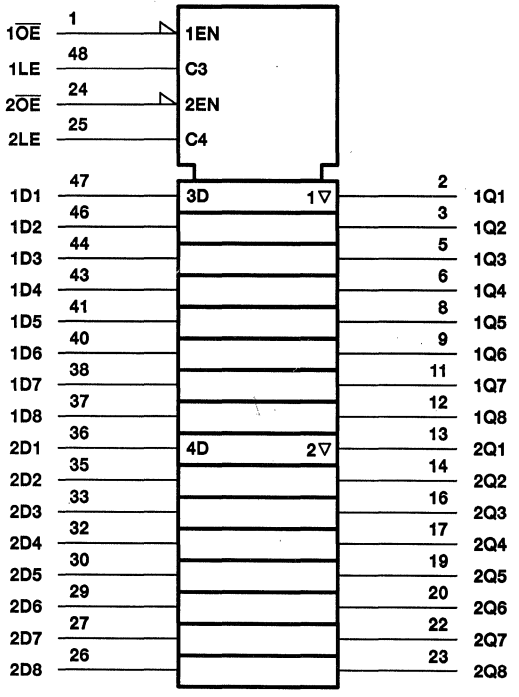
The SN74LVT16373 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT16373 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16373 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

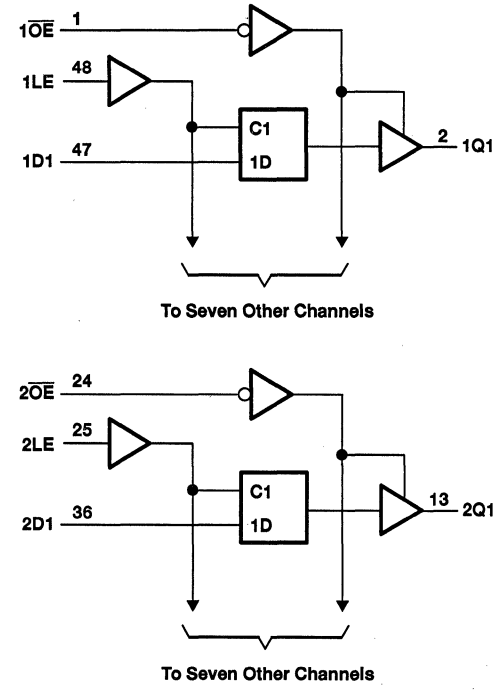
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16373 ..... 96 mA
SN74LVT16373 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16373 ..... 48 mA
SN74LVT16373 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT16373		SN74LVT16373		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVT16373			SN74LVT16373			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = – 8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = – 24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or MAX‡,	V_I = 5.5 V			40			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V			±100			±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{CC}	Outputs high	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,			0.09			0.09	mA
	Outputs low					5			5	
	Outputs disabled					0.09			0.09	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			5			5		pF
C_o		V_O = 3 V or 0			9.5			9.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

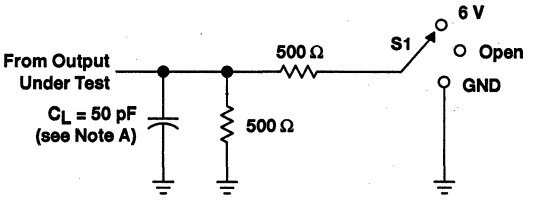
		SN54LVT16373				SN74LVT16373				UNIT
		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE↓	1		1		0.5		0.5		ns
t_h	Hold time, data after LE↓	2.6		2.9		1.8		2		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT16373				SN74LVT16373				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
t_{PLH}	D	Q	0.5	5.1		5.8	1.3	2.7	5	5.7	ns
t_{PHL}			0.5	5		5.8	1.4	2.9	4.9	5.7	
t_{PLH}	LE	Q	1	6.8		7.3	2.1	3.6	6	6.8	ns
t_{PHL}			1	7.8		8.9	3	4.7	6.9	8.8	
t_{PZH}	$\overline{OE}$	Q	0.5	5.6		6.4	1	2.9	5.3	6.3	ns
t_{PZL}			0.5	5.5		6	1.3	3	5.1	5.9	
t_{PHZ}	$\overline{OE}$	Q	1	7.2		8	2.7	4.3	6.8	7.6	ns
t_{PLZ}			1	6.1		6.2	2.6	4	5.8	5.9	

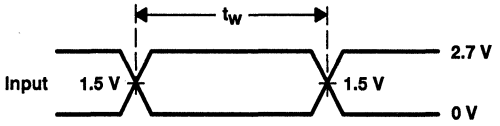
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

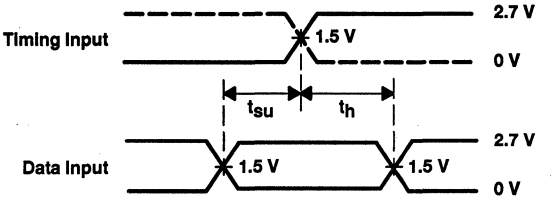


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

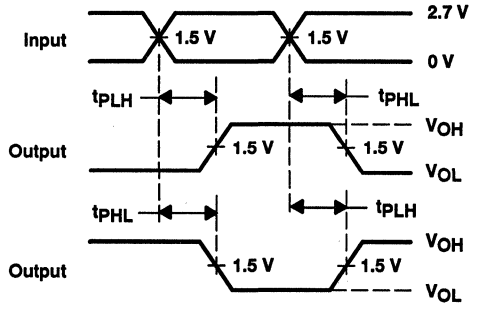
LOAD CIRCUIT FOR OUTPUTS



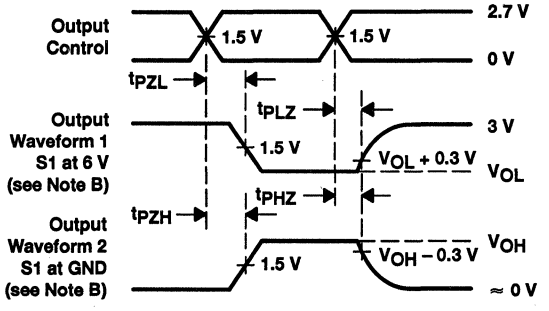
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



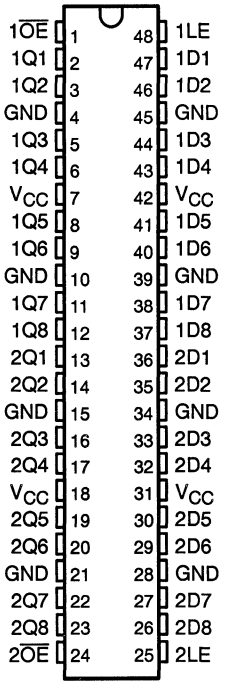
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Output Ports Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT162373 . . . WD PACKAGE
SN74LVT162373 . . . DGG OR DL PACKAGE
(TOP VIEW)



ADVANCE INFORMATION

description

The 'LVT162373 are16-bit transparent D-type latches with 3-state outputs designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The 'LVT162373 can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The outputs, which are designed to source or sink up to 12 mA, include 22-Ω series resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVT162373 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

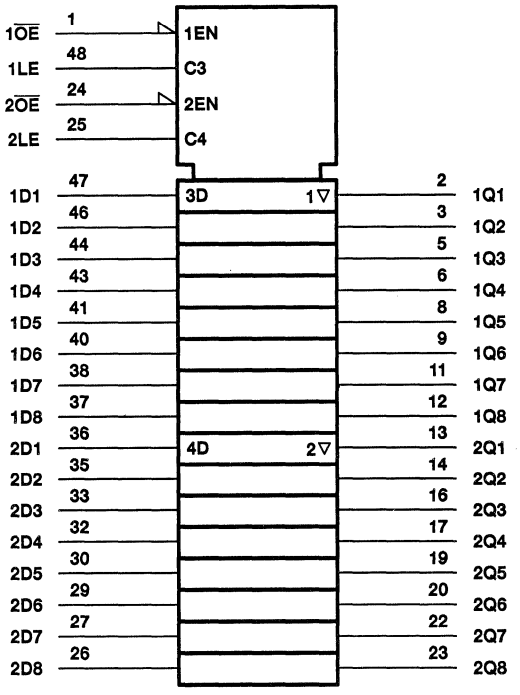
The SN54LVT162373 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT162373 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

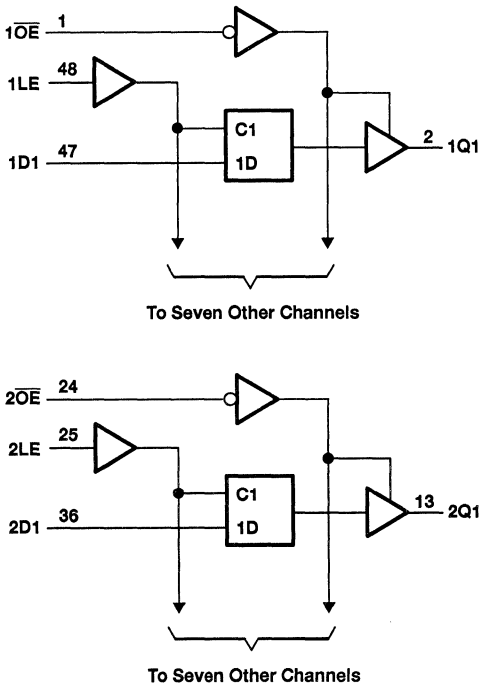
ADVANCE INFORMATION

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O ..... 30 mA
Current into any output in the high state, I_O (see Note 2) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

ADVANCE INFORMATION

recommended operating conditions (see Note 4)

			SN54LVT162373		SN74LVT162373		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–12		–12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

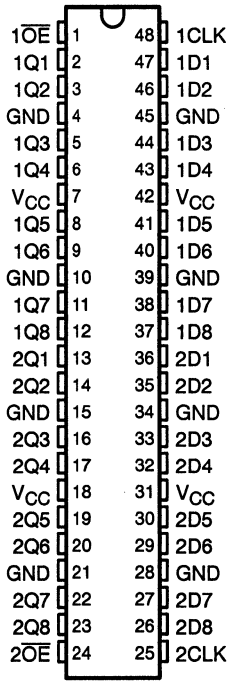
PARAMETER	TEST CONDITIONS			SN54LVT162373		SN74LVT162373		UNIT
				MIN	MAX	MIN	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA			–1.2		–1.2	V
V_{OH}	V_{CC} = 3 V,	I_{OH} = – 12 mA		2		2		V
V_{OL}	V_{CC} = 3 V,	I_{OL} = 12 mA			0.8		0.8	V
I_I	V_{CC} = 0 or MAX†,	V_I = 5.5 V			10		10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control pins		±1		±1	
		V_I = V_{CC}	Data pins		1		1	
		V_I = 0			–5		–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V					±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A inputs	75		75		µA
		V_I = 2 V		–75		–75		
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V			1		1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V			–1		–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.19		0.1	mA
			Outputs low		5		5	
			Outputs disabled		0.19		0.1	
ΔI_{CC}‡	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,			0.2		0.2	mA
C_i	V_I = 3 V or 0							pF
C_o	V_O = 3 V or 0							pF

† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
‡ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

ADVANCE INFORMATION

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16374 . . . WD PACKAGE
SN74LVT16374 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT16374 are 16-bit edge-triggered D-type flip-flops with 3-state outputs designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

These devices can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (CLK), the Q outputs of the flip-flop take on the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

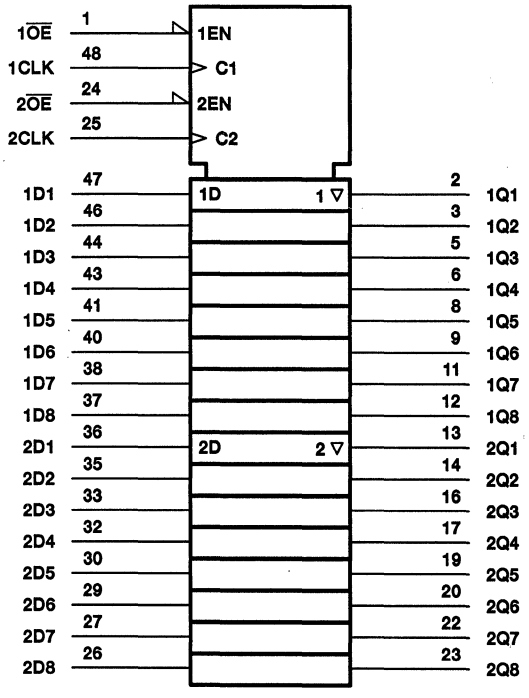
The SN74LVT16374 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT16374 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

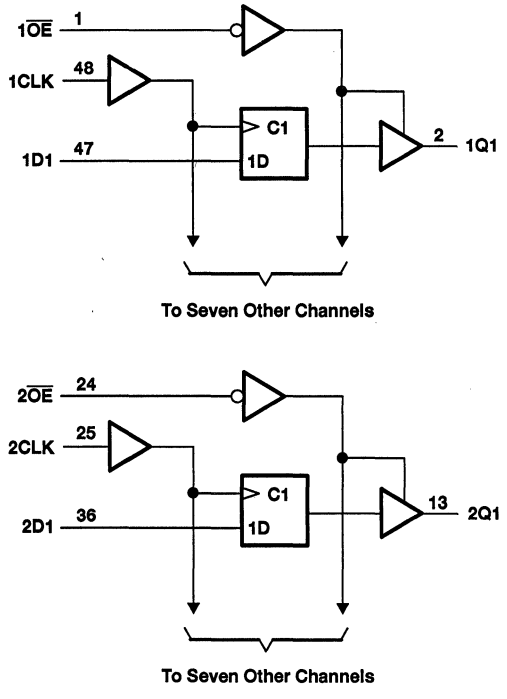
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16374 ..... 96 mA
SN74LVT16374 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16374 ..... 48 mA
SN74LVT16374 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT16374		SN74LVT16374		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54LVT16374			SN74LVT16374			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = – 8 mA	2.4			2.4			
		V_{CC} = 3 V	I_{OH} = – 24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 24 mA			0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
I_I		V_{CC} = 0 or MAX‡,	V_I = 5.5 V			10			10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	
	Data inputs	V_{CC} = 3.6 V	V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V			±100			±100	µA
$I_{I(hold)}$	Data inputs	V_{CC} = 3 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 2.7 V			5			5	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V			–5			–5	µA
I_{CC}	Outputs high	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,			0.1			0.1	mA
	Outputs low					5			5	
	Outputs disabled					0.1			0.1	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.2			0.2	mA
C_i		V_I = 3 V or 0			5			5		pF
C_o		V_O = 3 V or 0			9.5			9.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

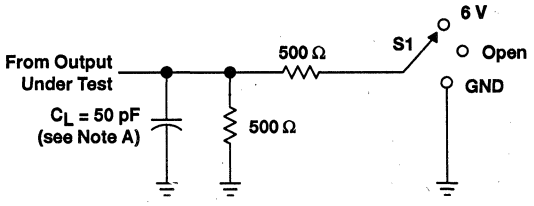
			SN54LVT16374				SN74LVT16374				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	High or low	2.8		3.3		2.2		2.6		ns
t_h	Hold time, data after CLK↑	High or low	0.6		0.5		0.6		0		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT16374				SN74LVT16374				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN MAX	
f_{max}			150		150		150			150	MHz
t_{PLH}	CLK	Q	1.9	6.6		7.4	1.9	3.6	6.3	7	ns
t_{PHL}			2.3	6.9		7.5	2.3	4.1	6.6	7.2	
t_{PZH}	$\overline{OE}$	Q	1	5.6		6.4	1	2.7	5.3	6.3	ns
t_{PZL}			1.3	5.3		6	1.3	2.8	5.1	5.9	
t_{PHZ}	$\overline{OE}$	Q	1	7.2		8.2	2.7	4.3	6.8	7.6	ns
t_{PLZ}			2.6	6.1		8.2	2.6	3.9	5.8	5.9	

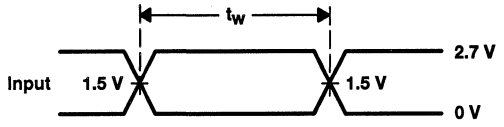
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

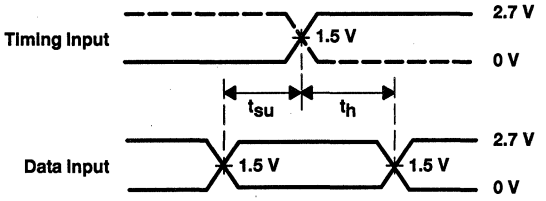


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

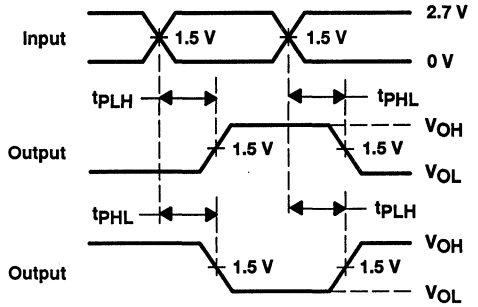
LOAD CIRCUIT FOR OUTPUTS



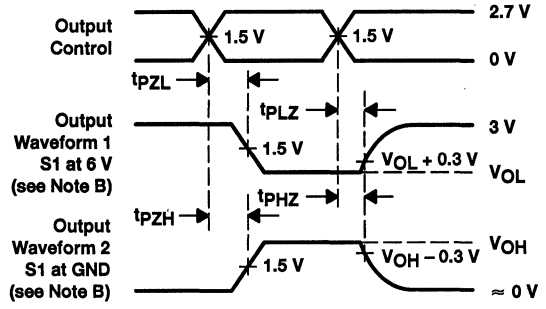
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



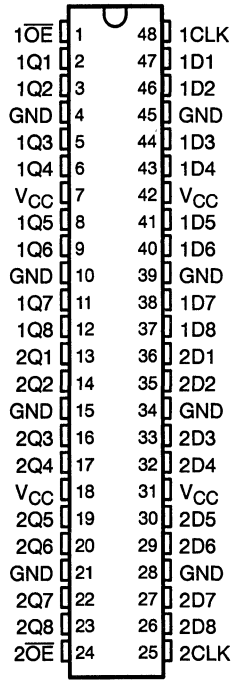
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- Output Ports Have Equivalent 22-Ω Series Resistors, So No External Resistors Are Required
- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT162374 . . . WD PACKAGE
SN74LVT162374 . . . DGG OR DL PACKAGE
(TOP VIEW)



ADVANCE INFORMATION

description

The 'LVT162374 are 16-bit edge-triggered D-type flip-flops with 3-state outputs designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. They are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The 'LVT162374 can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (CLK), the Q outputs of the flip-flop take on the logic levels set up at the D inputs.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The outputs, which are designed to source or sink up to 12 mA, include 22-Ω series resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

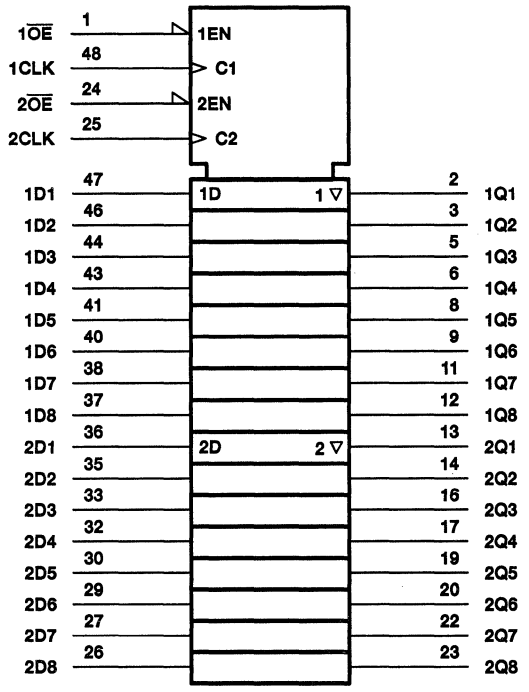
The SN74LVT162374 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT162374 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT162374 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

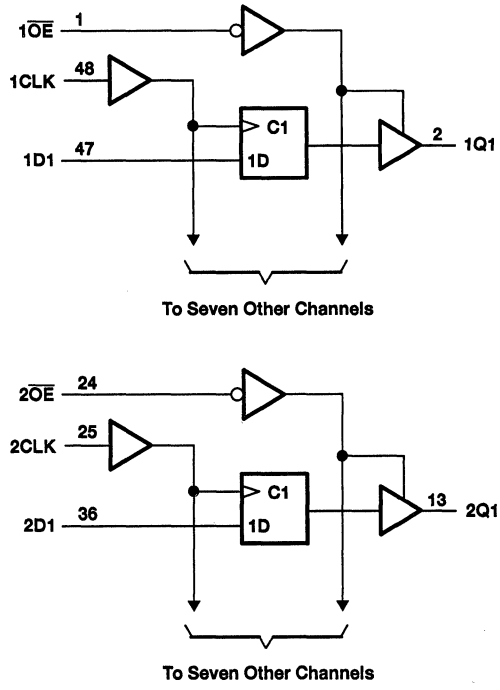
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O ..... 30 mA
Current into any output in the high state, I_O (see Note 2) ..... 30 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

ADVANCE INFORMATION

recommended operating conditions (see Note 4)

			SN54LVT162374		SN74LVT162374		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–12		–12	mA
I_{OL}	Low-level output current			12		12	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT162374		SN74LVT162374		UNIT
				MIN	MAX	MIN	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA			–1.2		–1.2	V
V_{OH}	V_{CC} = 3 V,	I_{OH} = – 12 mA		2		2		V
V_{OL}	V_{CC} = 3 V,	I_{OL} = 12 mA			0.8		0.8	V
I_I	V_{CC} = 0 or MAX†,	V_I = 5.5 V			10		10	µA
	V_{CC} = 3.6 V	V_I = V_{CC} or GND	Control inputs		±1		±1	
		V_I = V_{CC}	Data inputs		1		1	
		V_I = 0			–5		–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V					±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A inputs	75		75		µA
		V_I = 2 V		–75		–75		
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V			1		1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V			–1		–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.19		0.1	mA
			Outputs low		5		5	
			Outputs disabled		0.19		0.1	
ΔI_{CC}‡	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,			0.2		0.2	mA
C_i	V_I = 3 V or 0							pF
C_o	V_O = 3 V or 0							pF

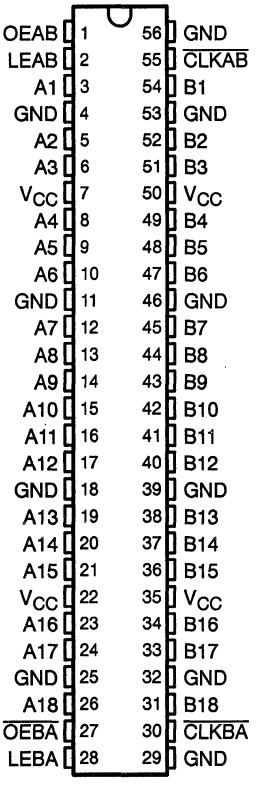
† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
‡ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

ADVANCE INFORMATION

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- *UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16500 . . . WD PACKAGE
SN74LVT16500 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT16500 are 18-bit universal bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{\text{OEBA}}$), latch-enable (LEAB and LEBA), and clock ($\overline{\text{CLKAB}}$ and $\overline{\text{CLKBA}}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if $\overline{\text{CLKAB}}$ is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the high-to-low transition of $\overline{\text{CLKAB}}$. Output-enable OEAB is active high. When OEAB is high, the B-port outputs are active. When OEAB is low, the B-port outputs are in the high-impedance state.

Widebus and UBT are trademarks of Texas Instruments Incorporated.

description (continued)

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, and $\overline{CLKBA}$. The output enables are complementary (OEAB is active high and $\overline{OEBA}$ is active low).

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The SN74LVT16500 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

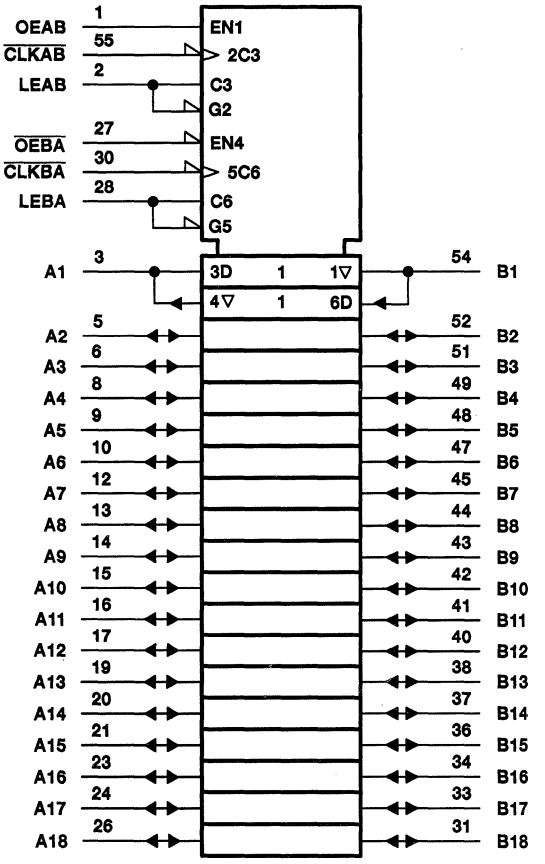
The SN54LVT16500 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16500 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
OEAB	LEAB	$\overline{CLKAB}$	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↓	L	L
H	L	↓	H	H
H	L	H	X	B_0‡
H	L	L	X	B_0§

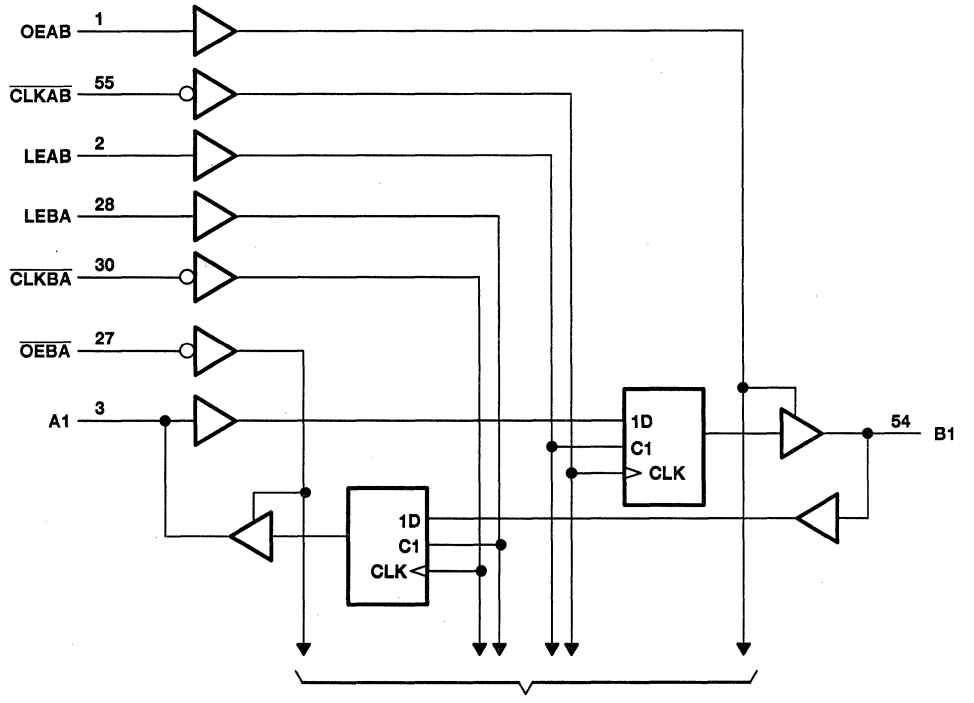
† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, and $\overline{CLKBA}$.
‡ Output level before the indicated steady-state input conditions were established
§ Output level before the indicated steady-state input conditions were established, provided that $\overline{CLKAB}$ was low before LEAB went low

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16500 ..... 96 mA
SN74LVT16500 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16500 ..... 48 mA
SN74LVT16500 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT16500		SN74LVT16500		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT16500 MIN	SN54LVT16500 TYP†	SN54LVT16500 MAX	SN74LVT16500 MIN	SN74LVT16500 TYP†	SN74LVT16500 MAX	UNIT
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				5			5	
		V_I = 0				–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.12			0.12	mA
			Outputs low			5			5	
			Outputs disabled			0.12			0.12	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				3.5			3.5		pF
C_{io}	V_O = 3 V or 0				12			12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

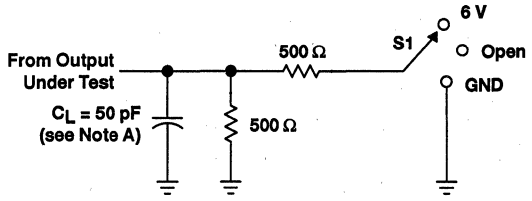
			SN54LVT16500				SN74LVT16500				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	125	0	150	0	125	MHz
t_w	Pulse duration	LE high	3.3		3.3		3.3		3.3		ns
		$\overline{CLK}$ high or low	3.3		3.3		3.3		3.3		
t_{su}	Setup time	A before $\overline{CLKAB}\downarrow$	1.8		1.1		1.8		1.1		ns
		B before $\overline{CLKBA}\downarrow$	1.9		1.2		1.9		1.2		
		A or B before LE↓, $\overline{CLK}$ high	2.2		1.3		2.2		1.3		
		A or B before LE↓, $\overline{CLK}$ low	2.7		1.9		2.7		1.9		
t_h	Hold time	A or B after $\overline{CLK}\downarrow$	1.2		1.2		1.2		1.2		ns
		A or B after LE↓	0.9		1.1		0.9		1.1		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT16500				SN74LVT16500					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		125		150			125		MHz
t_{PLH}	B or A	A or B	1.7	5.8		7	1.7	3	5.4		6.8	ns
t_{PHL}			1.6	6		7.8	1.6	3.2	5.9		7.7	
t_{PLH}	LEBA or LEAB	A or B	2.3	7.3		8.9	2.3	4	7		8.5	ns
t_{PHL}			2.7	8.2		9.8	2.7	4.3	7.9		9.7	
t_{PLH}	$\overline{CLKBA}$ or $\overline{CLKAB}$	A or B	2	7.4		8.8	2	4.1	7		8.3	ns
t_{PHL}			2.4	8		10	2.4	4.4	7.9		9.9	
t_{PZH}	$\overline{OEBA}$ or OEAB	A or B	1.2	5.2		6.1	1.2	3	5		5.9	ns
t_{PZL}			1.5	5.9		7	1.5	3	5.8		6.9	
t_{PHZ}	$\overline{OEBA}$ or OEAB	A or B	2.7	7.7		8.6	2.7	4.6	7.4		8.3	ns
t_{PLZ}			2.8	7.3		7.7	2.8	4.7	6.7		7.2	

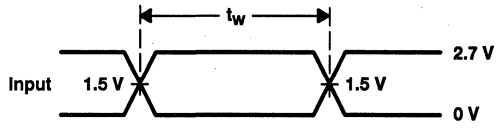
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

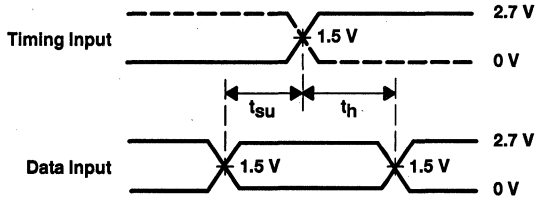


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

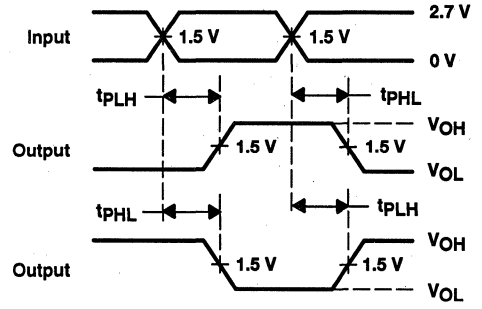
LOAD CIRCUIT FOR OUTPUTS



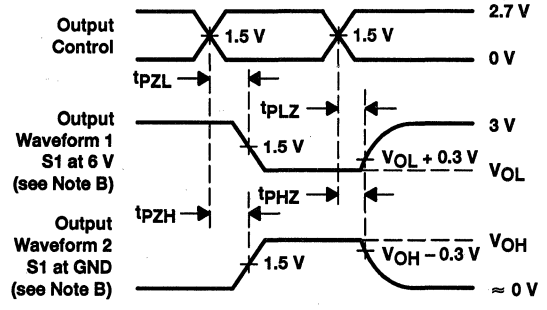
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



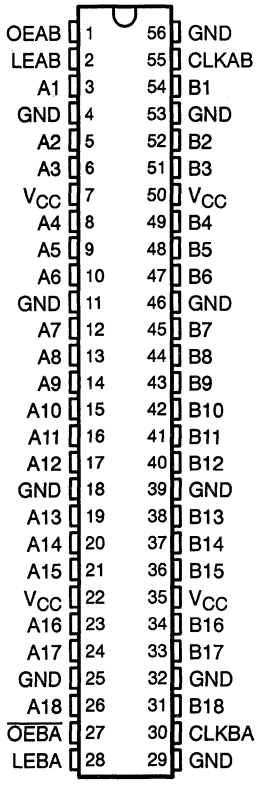
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- *UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16501 . . . WD PACKAGE
SN74LVT16501 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT16501 are 18-bit universal bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{\text{OEBA}}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. When OEAB is high, the outputs are active. When OEAB is low, the outputs are in the high-impedance state.

Widebus and UBT are trademarks of Texas Instruments Incorporated.

description (continued)

Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, and CLKBA. The output enables are complementary (OEAB is active high and $\overline{OEBA}$ is active low).

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor. The minimum value of the resistor is determined by the current-sinking capability of the driver. OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The SN74LVT16501 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the input/output (I/O) pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

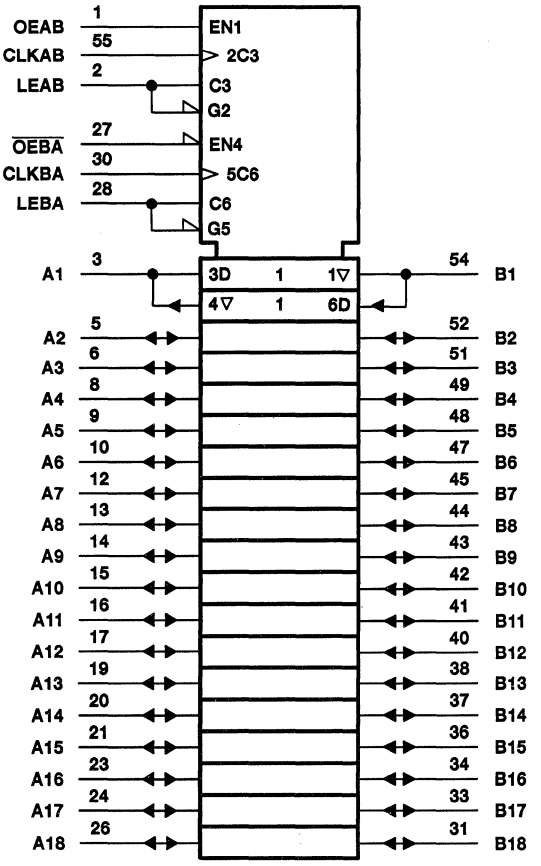
The SN54LVT16501 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16501 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
OEAB	LEAB	CLKAB	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↑	L	L
H	L	↑	H	H
H	L	H	X	B_0‡
H	L	L	X	B_0§

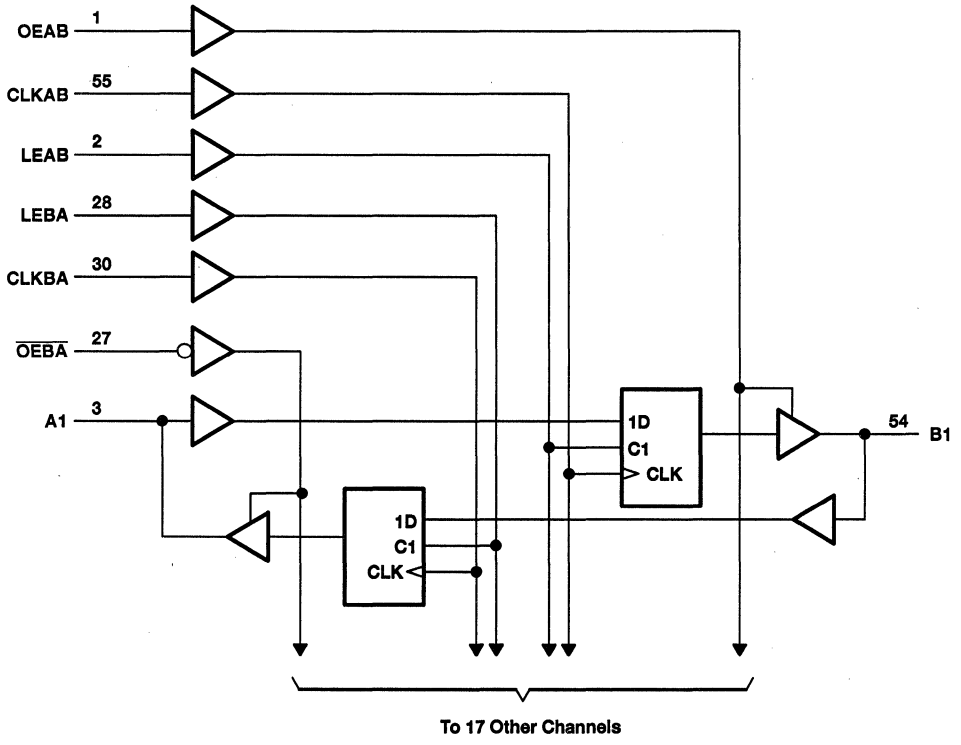
† A-to-B data flow is shown; B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, and CLKBA.
‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low
§ Output level before the indicated steady-state input conditions were established

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16501 ..... 96 mA
SN74LVT16501 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16501 ..... 48 mA
SN74LVT16501 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Operating free-air temperature range, T_A: SN54LVT16501 ..... −55°C to 125°C
SN74LVT16501 ..... −40°C to 85°C
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT16501		SN74LVT16501		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			SN54LVT16501			SN74LVT16501			UNIT
					MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}		V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
		V_{CC} = 3 V	I_{OH} = – 24 mA		2						
			I_{OH} = –32 mA					2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
			I_{OL} = 24 mA				0.5			0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
			I_{OL} = 32 mA				0.5			0.5	
			I_{OL} = 48 mA				0.55				
			I_{OL} = 64 mA							0.55	
I_I	Control pins	V_{CC} = 3.6 V,	V_I = V_{CC} or GND				±1			±1	µA
		V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	A or B ports§	V_{CC} = 3.6 V	V_I = 5.5 V				20			20	
			V_I = V_{CC}				1			1	
			V_I = 0				–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	A or B ports	V_{CC} = 3 V	V_I = 0.8 V		75			75			µA
			V_I = 2 V		–75			–75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}		V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.12			0.12	mA
				Outputs low			5			5	
				Outputs disabled			0.12			0.12	
ΔI_{CC}¶		V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i		V_I = 3 V or 0				3.5			3.5		pF
C_{io}		V_O = 3 V or 0				12			12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

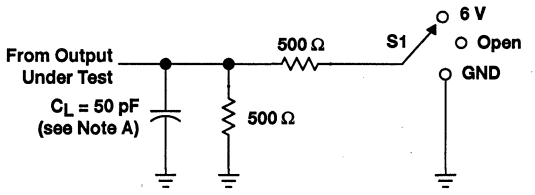
			SN54LVT16501				SN74LVT16501				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	125	0	150	0	125	MHz
t_w	Pulse duration	LE high	3.3		3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		3.3		
t_{su}	Setup time	A before CLKAB↑	1.6		2.1		1.6		2.1		ns
		B before CLKBA↑	1.6		2.1		1.6		2.1		
		A or B before LE↓, $\overline{CLK}$ high	2.6		1.9		2.6		1.9		
		A or B before LE↓, $\overline{CLK}$ low	2		1.3		2		1.3		
t_h	Hold time	A or B after CLK↑	2		2.1		2		2.1		ns
		A or B after LE↓	0.9		1.2		0.9		1.2		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT16501				SN74LVT16501					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		125		150			125		MHz
t_{PLH}	B or A	A or B	1.7	5.4		5.8	1.7	3	5.4		6.8	ns
t_{PHL}			1.6	6		7.8	1.6	3.2	5.9		7.7	
t_{PLH}	LEBA or LEAB	A or B	2.3	7.3		9	2.3	4	7		8.5	ns
t_{PHL}			2.7	8.2		9.8	2.7	4.3	7.9		9.7	
t_{PLH}	CLKBA or CLKAB	A or B	2.5	8.3		9.7	2.5	4.1	7.9		9.2	ns
t_{PHL}			3.5	9.4		10.7	3.5	5.4	8.9		10.4	
t_{PZH}	$\overline{OEBA}$ or OEAB	A or B	1.2	5.1		6.1	1.2	3	5		5.9	ns
t_{PZL}			1.5	5.9		7	1.5	3	5.8		6.9	
t_{PHZ}	$\overline{OEBA}$ or OEAB	A or B	2.7	7.5		8.5	2.7	4.6	7.4		8.3	ns
t_{PLZ}			2.8	6.8		7.5	2.8	4.7	6.7		7.2	

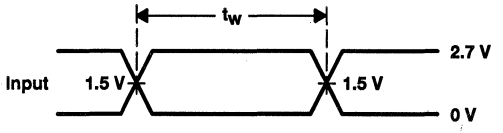
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

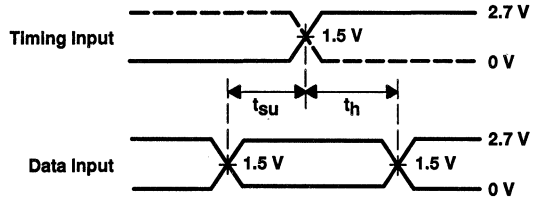


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

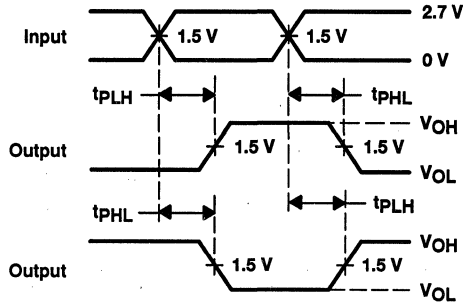
LOAD CIRCUIT FOR OUTPUTS



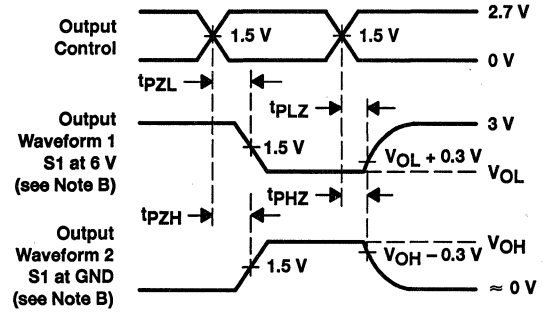
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

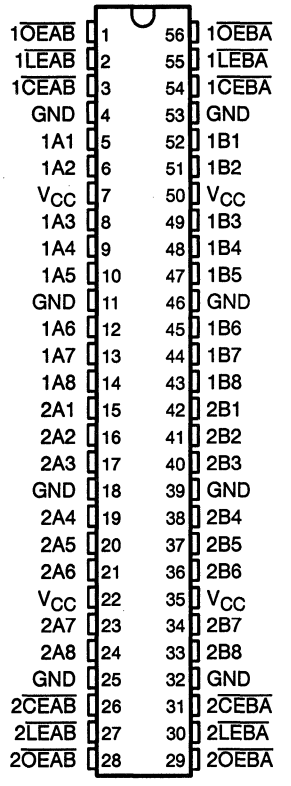
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16543 . . . WD PACKAGE
SN74LVT16543 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT16543 are 16-bit registered transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low in order to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ puts the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar but requires using the $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$ inputs.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Widebus is a trademark of Texas Instruments Incorporated.

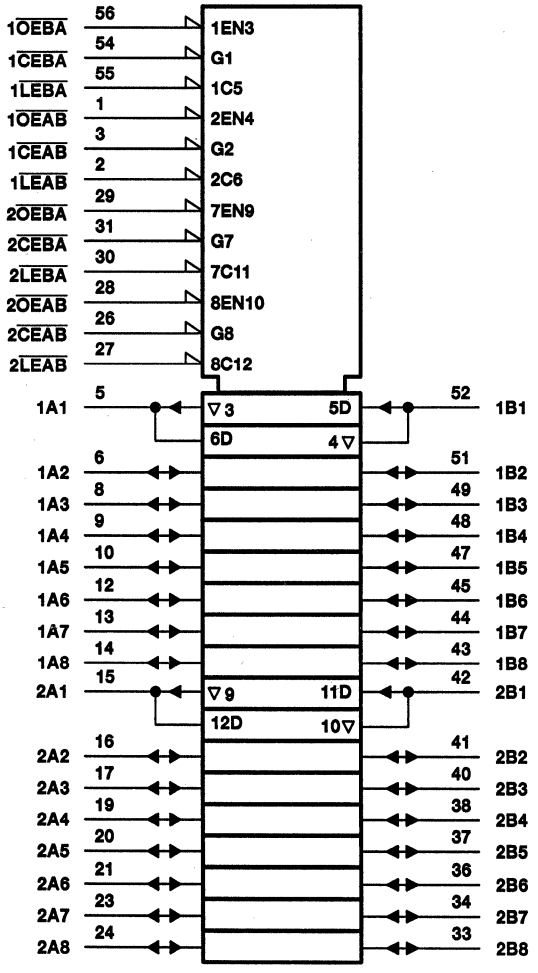
description (continued)

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVT16543 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

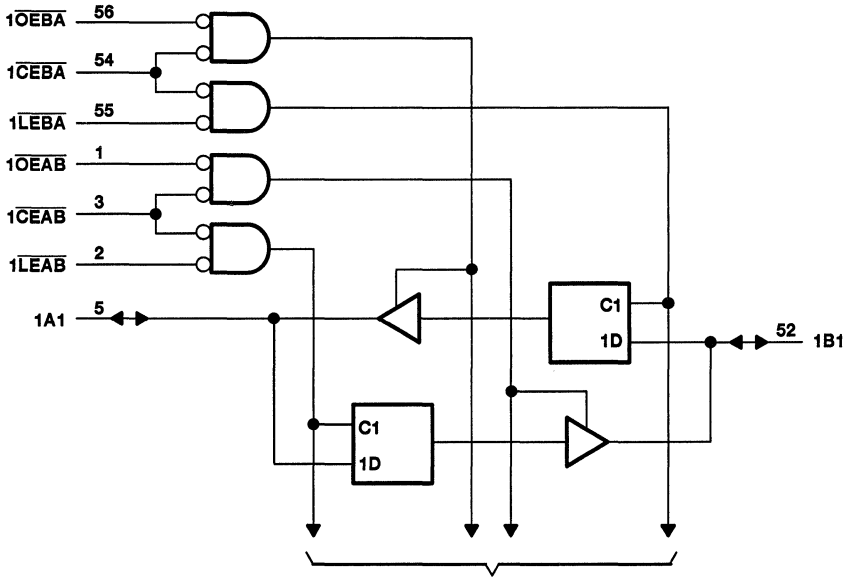
The SN54LVT16543 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16543 is characterized for operation from –40°C to 85°C.

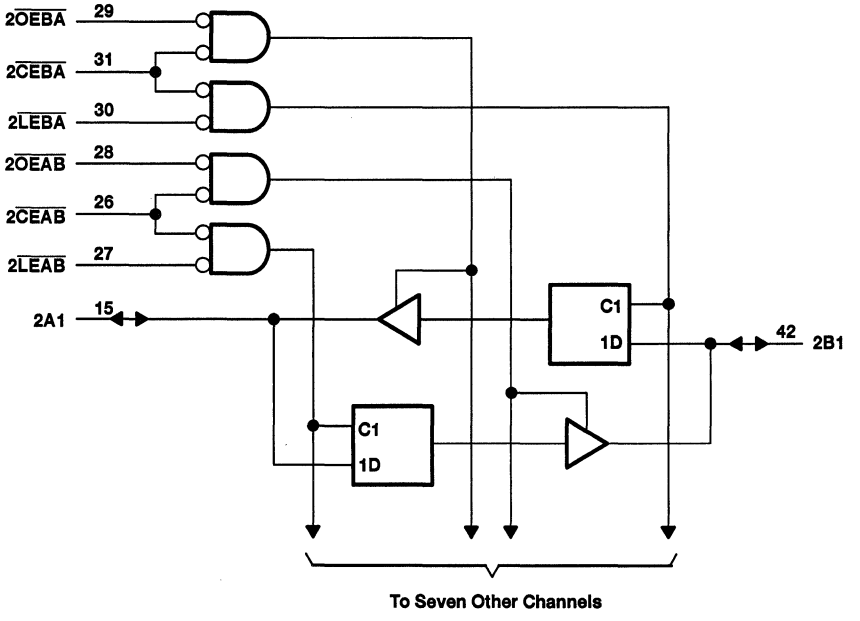
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





FUNCTION TABLE† (each 8-bit section)

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16543 ..... 96 mA
SN74LVT16543 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16543 ..... 48 mA
SN74LVT16543 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

§ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT16543		SN74LVT16543		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT16543			SN74LVT16543			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				5			5	
		V_I = 0				–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.12			0.12	mA
			Outputs low			5			5	
			Outputs disabled			0.12			0.12	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND					0.2			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				13			13		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

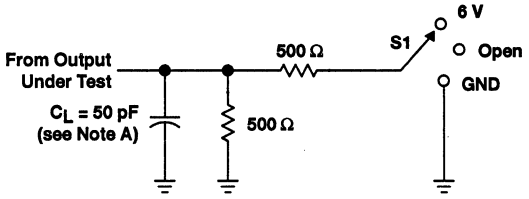
				SN54LVT16543				SN74LVT16543				UNIT
				V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, $\overline{LEAB}$ or $\overline{LEBA}$ low			3.3		3.3		3.3		3.3		ns
t_{su}	Setup time	A or B before $\overline{LEAB}$↑ or $\overline{LEBA}$↑	Data high	0.8		0.5		0.8		0.5		ns
			Data low	1.5		1.9		1.5		1.9		
		A or B before $\overline{CEAB}$↑ or $\overline{CEBA}$↑	Data high	0.7		0.4		0.7		0.4		ns
			Data low	1.6		1.9		1.6		1.9		
t_h	Hold time	A or B after $\overline{LEAB}$↑ or $\overline{LEBA}$↑	Data high	0.8		0		0.8		0		ns
			Data low	1.2		1.3		1.2		1.3		
		A or B after $\overline{CEAB}$↑ or $\overline{CEBA}$↑	Data high	0.8		0		0.8		0		ns
			Data low	1.3		1.4		1.3		1.4		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT16543				SN74LVT16543					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1.4	5		5.8	1.4	2.7	4.6		5.5	ns
t_{PHL}			1.3	4.7		5.9	1.3	2.9	4.6		5.8	
t_{PLH}	$\overline{LE}$	A or B	1.3	6.8		8.5	1.7	3.7	6.3		8.1	ns
t_{PHL}			1.5	6.5		8.3	1.9	3.7	6		7.8	
t_{PZH}	$\overline{OE}$	A or B	1.4	6		7.7	1.5	3.3	5.8		7.6	ns
t_{PZL}			1.6	6.3		8.4	1.6	3.3	6.2		8.2	
t_{PHZ}	$\overline{OE}$	A or B	2	6		7.3	2	4.1	6.5		7.1	ns
t_{PLZ}			2.7	6		6.2	2.7	3.9	5.8		5.9	
t_{PZH}	$\overline{CE}$	A or B	1.4	6.2		7.7	1.5	3.3	6		7.6	ns
t_{PZL}			1.6	6.6		8.5	1.7	3.3	6.4		8.3	
t_{PHZ}	$\overline{CE}$	A or B	2	6.6		7.2	2	4.1	6.4		7.1	ns
t_{PLZ}			2.6	5.6		5.9	2.6	4	5.4		5.6	

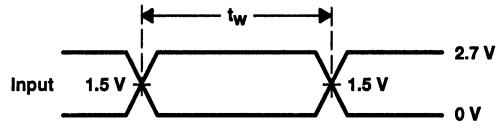
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

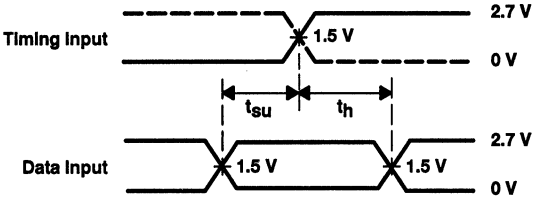


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

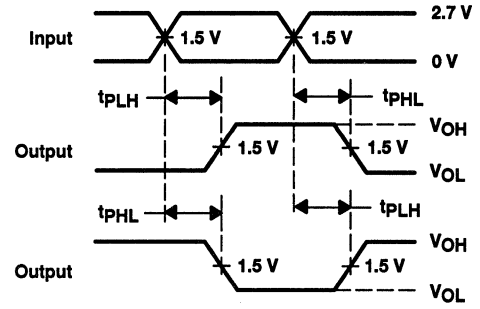
LOAD CIRCUIT FOR OUTPUTS



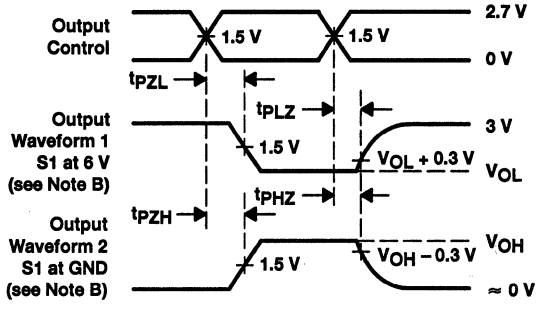
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



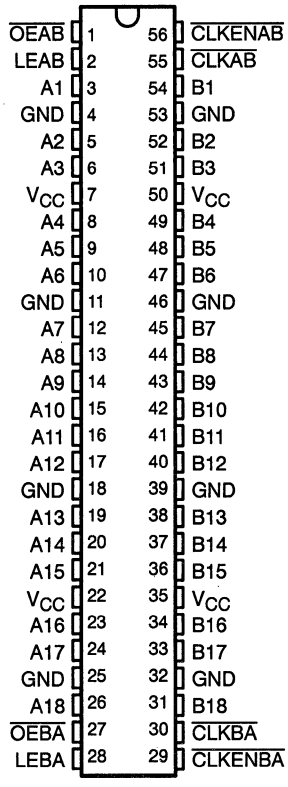
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- *UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16600 . . . WD PACKAGE
SN74LVT16600 . . . DGG OR DL PACKAGE
(TOP VIEW)



PRODUCT PREVIEW

description

The 'LVT16600 are 18-bit universal bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These 18-bit universal bus transceivers combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Widebus and UBT are trademarks of Texas Instruments Incorporated.

description (continued)

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock ($\overline{CLKAB}$ and $\overline{CLKBA}$) inputs. The clock can be controlled by the clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if $\overline{CLKAB}$ is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the high-to-low transition of $\overline{CLKAB}$. Output enable $\overline{OEAB}$ is active low. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state. Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, $\overline{CLKBA}$, and $\overline{CLKENBA}$.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVT16600 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT16600 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16600 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS					OUTPUT
$\overline{CLKENAB}$	$\overline{OEAB}$	LEAB	$\overline{CLKAB}$	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
H	L	L	X	X	B_0‡
L	L	L	↓	L	L
L	L	L	↓	H	H
L	L	L	H	X	B_0‡
L	L	L	L	X	B_0§

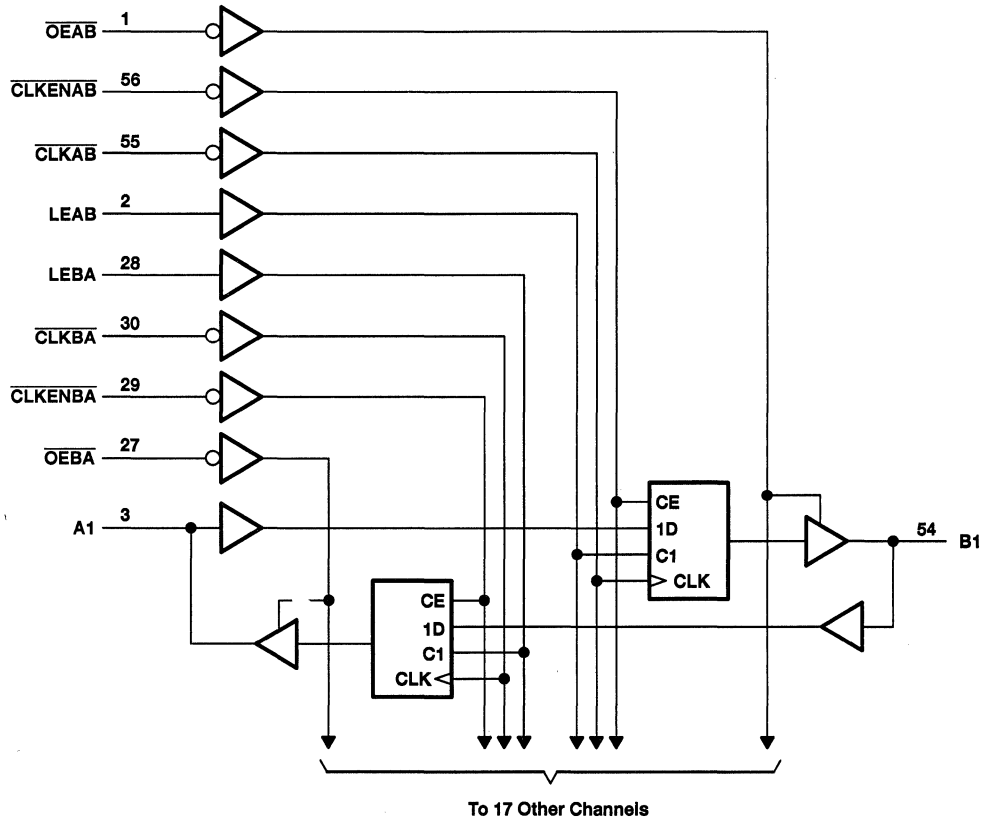
† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, $\overline{CLKBA}$, and $\overline{CLKENBA}$.

‡ Output level before the indicated steady-state input conditions were established

§ Output level before the indicated steady-state input conditions were established, provided that $\overline{CLKAB}$ was low before LEAB went low

PRODUCT PREVIEW

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16600 ..... 96 mA
SN74LVT16600 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16600 ..... 48 mA
SN74LVT16600 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			SN54LVT16600		SN74LVT16600		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

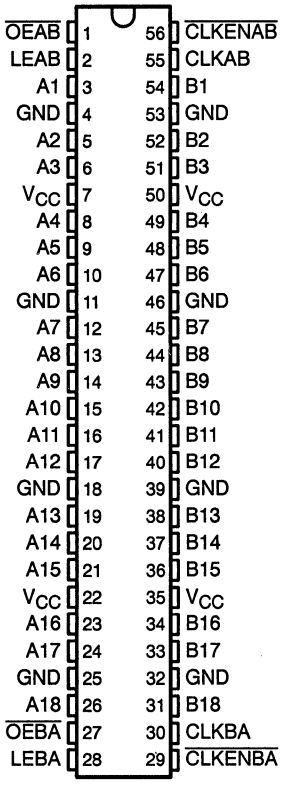
PARAMETER	TEST CONDITIONS			SN54LVT16600			SN74LVT16600			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				5			5	
		V_I = 0				–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.12			0.12	mA
			Outputs low			5			5	
			Outputs disabled			0.12			0.12	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				3.5			3.5		pF
C_{io}	V_O = 3 V or 0				12			12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

PRODUCT PREVIEW

- State-of-the-Art Advanced BICMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- *UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16601 . . . WD PACKAGE
SN74LVT16601 . . . DGG OR DL PACKAGE
(TOP VIEW)



PRODUCT PREVIEW

description

The 'LVT16601 are 18-bit universal bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These 18-bit universal bus transceivers combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

Widebus and UBT are trademarks of Texas Instruments Incorporated.

description (continued)

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. The clock can be controlled by the clock-enable ($\overline{CLKENAB}$ and $\overline{CLKENBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. Output enable $\overline{OEAB}$ is active low. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state. Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CLKENBA}$.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVT16601 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT16601 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16601 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS					OUTPUT
$\overline{CLKENAB}$	$\overline{OEAB}$	LEAB	CLKAB	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
H	L	L	X	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	L	L	X	B_0‡
L	L	L	H	X	B_0§

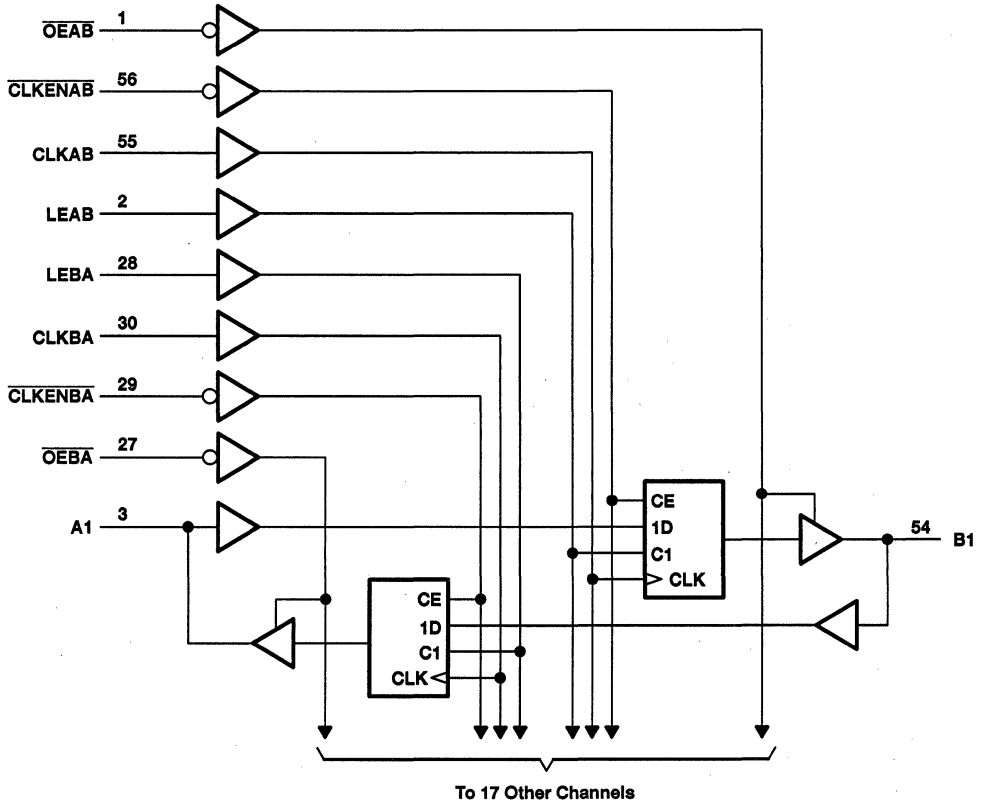
† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CLKENBA}$.

‡ Output level before the indicated steady-state input conditions were established

§ Output level before the indicated steady-state input conditions were established, provided that CLKAB was low before LEAB went low

PRODUCT PREVIEW

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16601 ..... 96 mA
SN74LVT16601 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16601 ..... 48 mA
SN74LVT16601 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			SN54LVT16601		SN74LVT16601		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

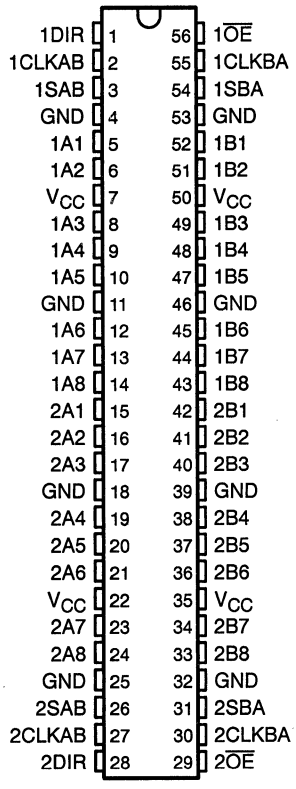
PARAMETER	TEST CONDITIONS			SN54LVT16601			SN74LVT16601			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				5			5	
		V_I = 0				–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.12			0.12	mA
			Outputs low			5			5	
			Outputs disabled			0.12			0.12	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				3.5			3.5		pF
C_{io}	V_O = 3 V or 0				12			12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

PRODUCT PREVIEW

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16646 . . . WD PACKAGE
SN74LVT16646 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT16646 are 16-bit bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'LVT16646.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs are provided to control the transceiver functions. In the transceiver mode, data present at the high-impedance port may be stored in either register or in both. The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. The direction control (DIR) determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data may be stored in one register and/or B data may be stored in the other register.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

When an output function is disabled, the input function is still enabled and may be used to store and transmit data. Only one of the two buses, A or B, may be driven at a time.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

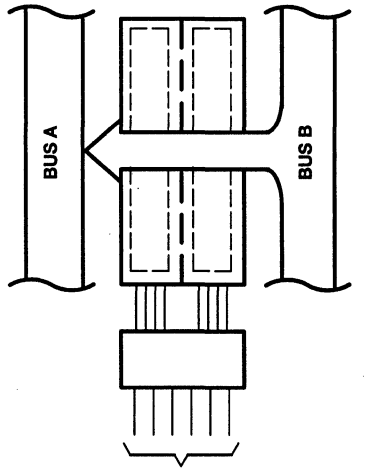
The SN74LVT16646 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT16646 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16646 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

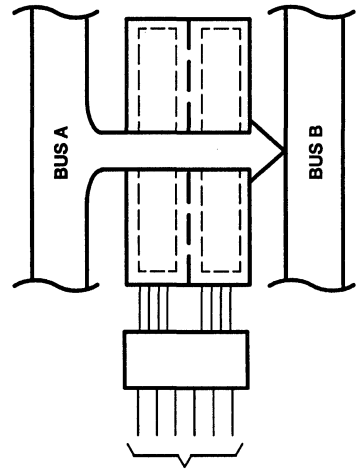
INPUTS						DATA I/Os		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1 THRU A8	B1 THRU B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

† The data output functions may be enabled or disabled by various signals at $\overline{OE}$ and DIR. Data input functions are always enabled; i.e., data at the bus pins will be stored on every low-to-high transition of the clock inputs.



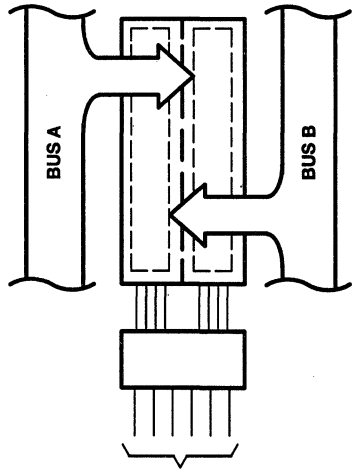
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



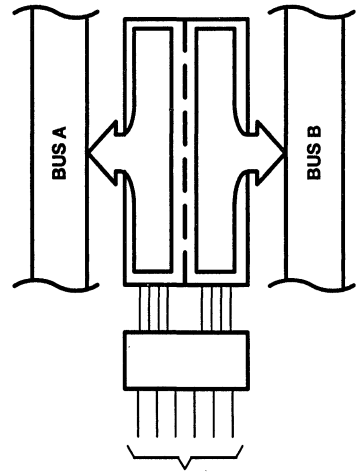
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B

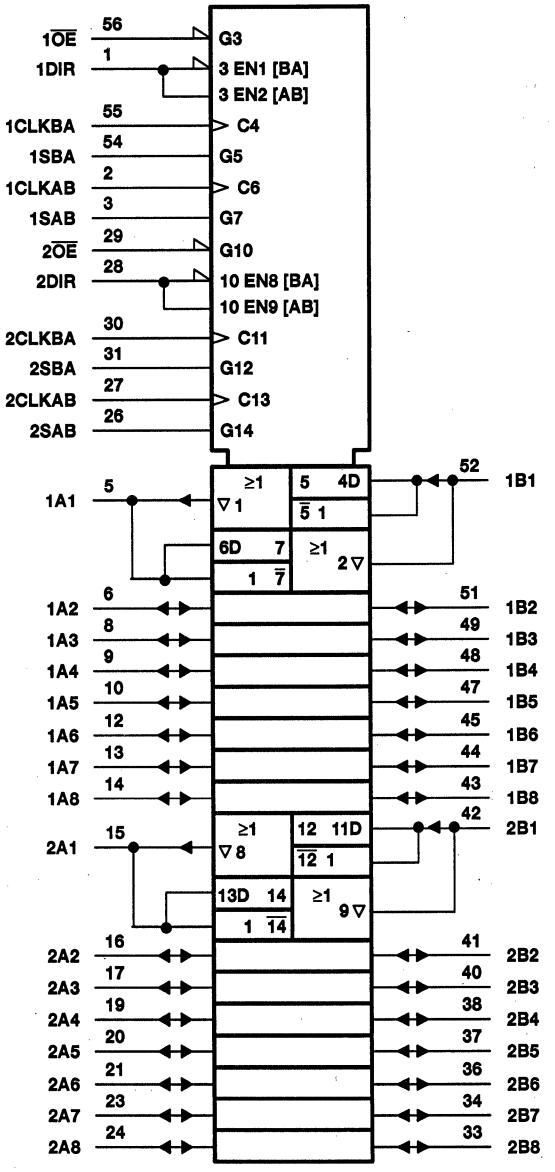


$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA
TO A AND/OR B

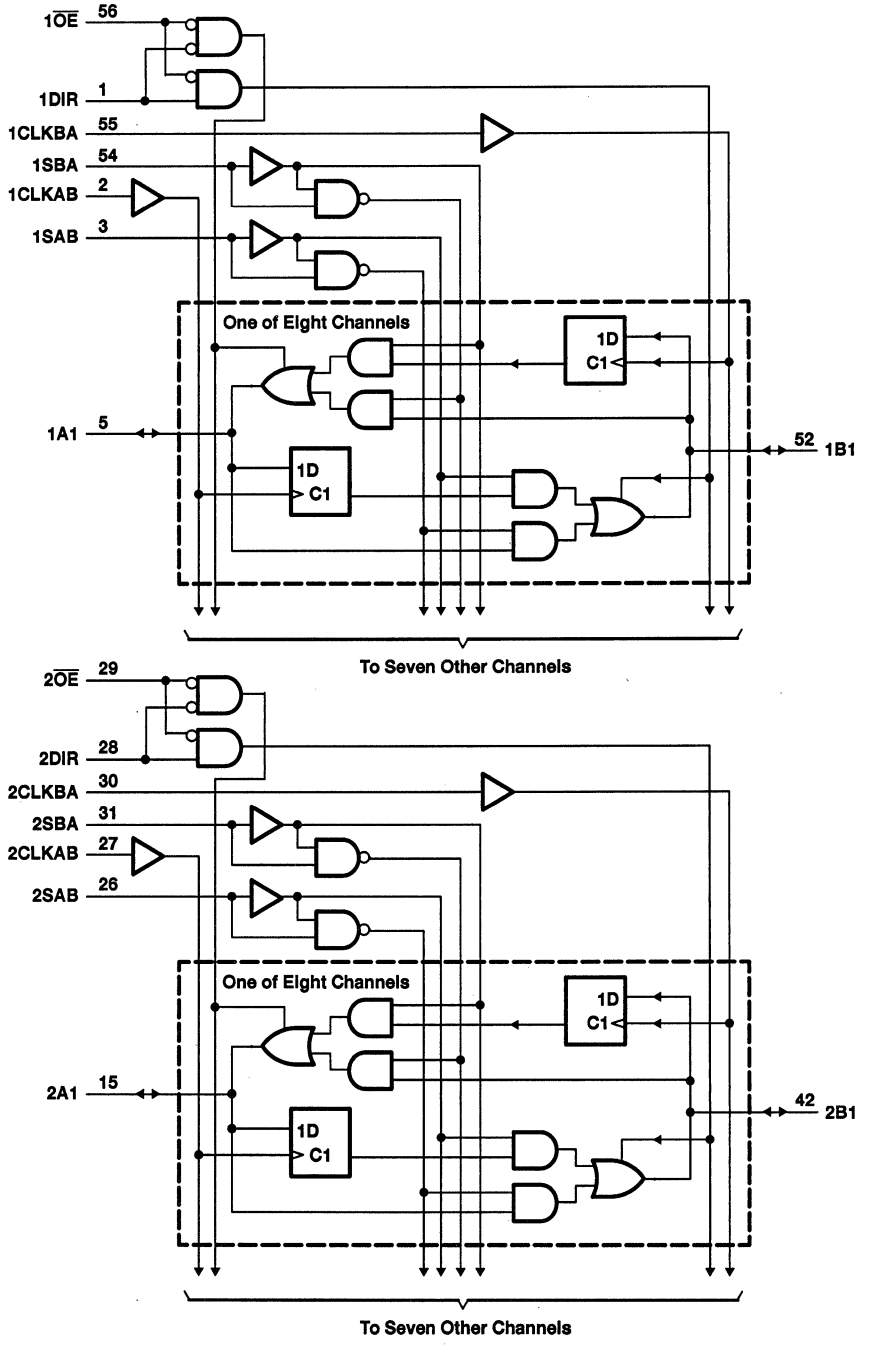
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16646 ..... 96 mA
SN74LVT16646 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16646 ..... 48 mA
SN74LVT16646 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT16646		SN74LVT16646		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT16646			SN74LVT16646			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				5			5	
		V_I = 0				–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.12			0.12	mA
			Outputs low			5			5	
			Outputs disabled			0.12			0.12	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				3.5			3.5		pF
C_{io}	V_O = 3 V or 0				12			12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

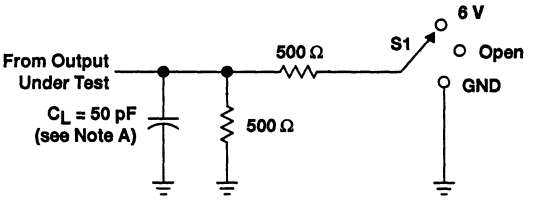
			SN54LVT16646				SN74LVT16646				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high	1.3		1.4		1.3		1.4		ns
		Data low	2.4		3		2.4		3		
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑	Data high	0.5		0		0.5		0		ns
		Data low	0.6		0.5		0.5		0.5		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT16646				SN74LVT16646					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150				150					MHz
t_{PLH}	CLKBA or CLKAB	A or B	1.8	6		6.9	1.8	3.8	5.7		6.7	ns
t_{PHL}			2.1	5.9		6.6	2.1	3.9	5.7		6.5	
t_{PLH}	A or B	B or A	1.3	4.9		5.6	1.3	3	4.7		5.4	ns
t_{PHL}			1	4.8		5.8	1	3.1	4.7		5.6	
t_{PLH}	SBA or SAB‡	A or B	1.4	6.4		7.4	1.4	4	6.2		7.2	ns
t_{PHL}			1.4	6.4		7.4	1.4	4.3	6.2		7.2	
t_{PZH}	$\overline{OE}$	A or B	1	5.7		7.4	1	3	5.4		6.4	ns
t_{PZL}			1	6		7.5	1	3.1	5.6		6.5	
t_{PHZ}	$\overline{OE}$	A or B	2.3	6.7		7.1	2.3	4.6	6.5		6.9	ns
t_{PLZ}			2.2	6		6.5	2.2	4.5	5.8		5.9	
t_{PZH}	DIR	A or B	1	5.9		7.7	1	3.3	5.7		6.7	ns
t_{PZL}			1.2	5.9		7.3	1.2	3.5	5.8		6.7	
t_{PHZ}	DIR	A or B	1.7	7.3		8.5	1.7	4.7	7.2		8.3	ns
t_{PLZ}			1.5	7.8		7.4	1.5	4.9	6.6		7.2	

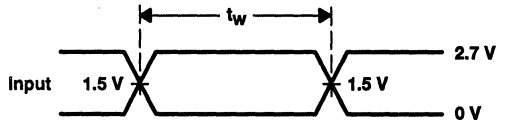
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ These parameters are measured with the internal output state of the storage register opposite to that of the bus input.

PARAMETER MEASUREMENT INFORMATION

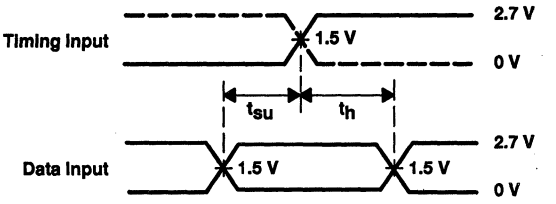


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

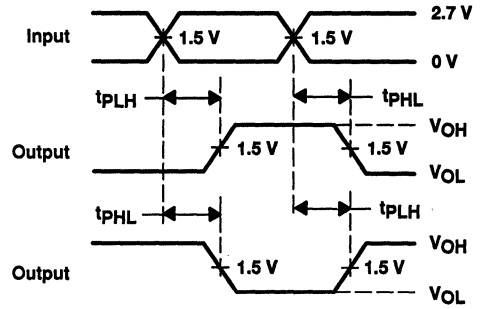
LOAD CIRCUIT FOR OUTPUTS



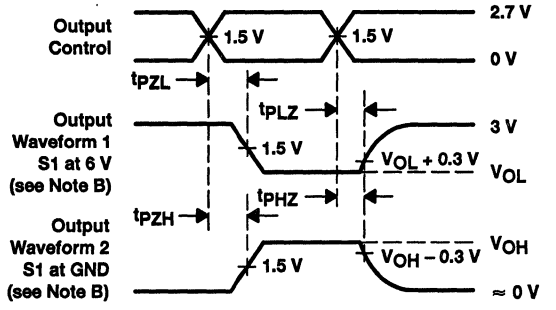
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



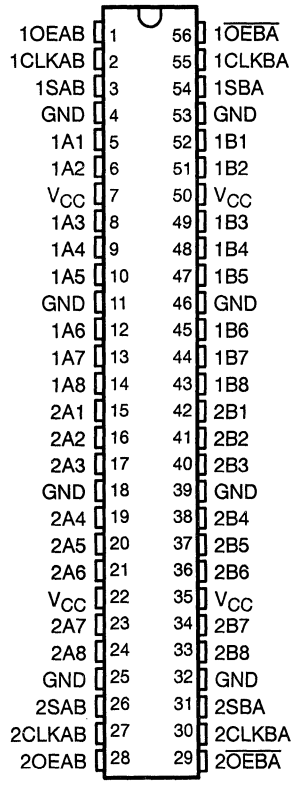
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16652 . . . WD PACKAGE
SN74LVT16652 . . . DGG OR DL PACKAGE
(TOP VIEW)



PRODUCT PREVIEW

description

The 'LVT16652 are 16-bit bus transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as two 8-bit transceivers or one 16-bit transceiver.

Complementary output-enable (OEAB and $\overline{OEBA}$) inputs are provided to control the transceiver functions. Select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. A low input level selects real-time data, and a high input level selects stored data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the 'LVT16652.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

Data on the A or B bus, or both, can be stored in the internal D flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs regardless of the levels on the select-control or output-enable inputs. When SAB and SBA are in the real-time transfer mode, it is also possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{\text{OEBA}}$. In this configuration, each output reinforces its input. When all other data sources to the two sets of bus line are at high impedance, each set of bus lines remains at its last level configuration.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The SN74LVT16652 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54LVT16652 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16652 is characterized for operation from –40°C to 85°C.

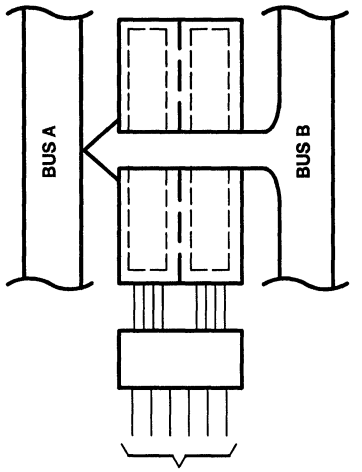
FUNCTION TABLE

INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{\text{OEBA}}$	CLKAB	CLKBA	SAB	SBA	A1 THRU A8	B1 THRU B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

† The data output functions may be enabled or disabled by a variety of level combinations at OEAB or $\overline{\text{OEBA}}$. Data input functions are always enabled; i.e., data at the bus pins is stored on every low-to-high transition on the clock inputs.

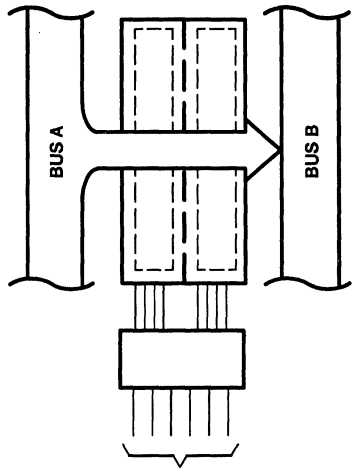
‡ Select control = L; clocks can occur simultaneously.
Select control = H; clocks must be staggered in order to load both registers.

PRODUCT PREVIEW



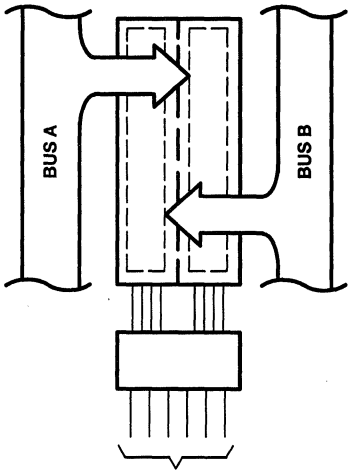
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



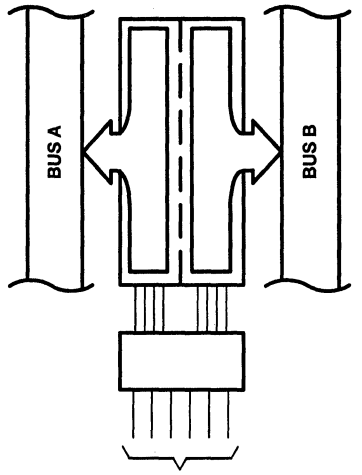
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B



OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	L	H or L	H or L	H	H

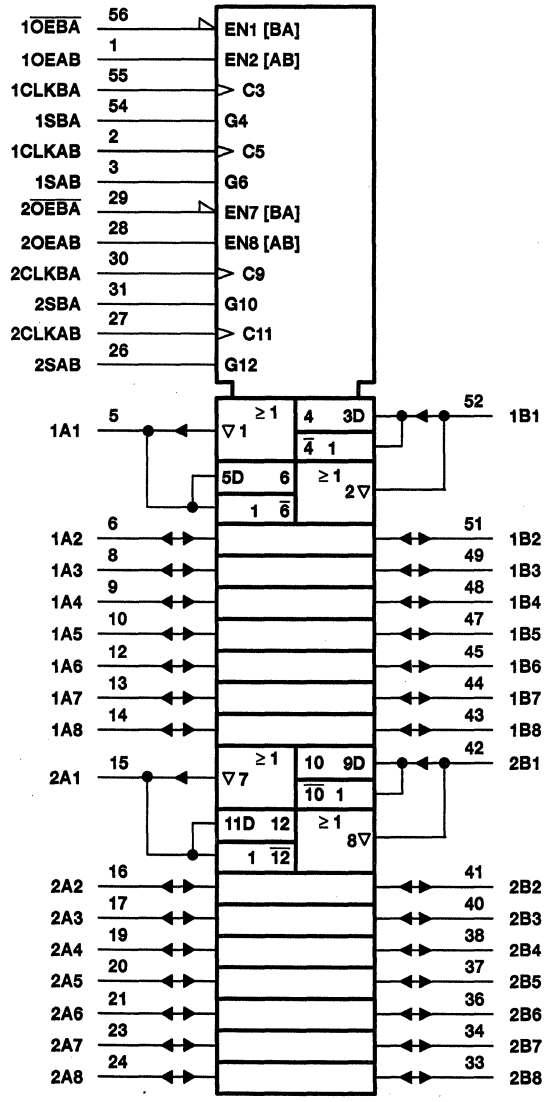
TRANSFER STORED DATA
TO A AND/OR B

Figure 1. Bus-Management Functions

PRODUCT PREVIEW

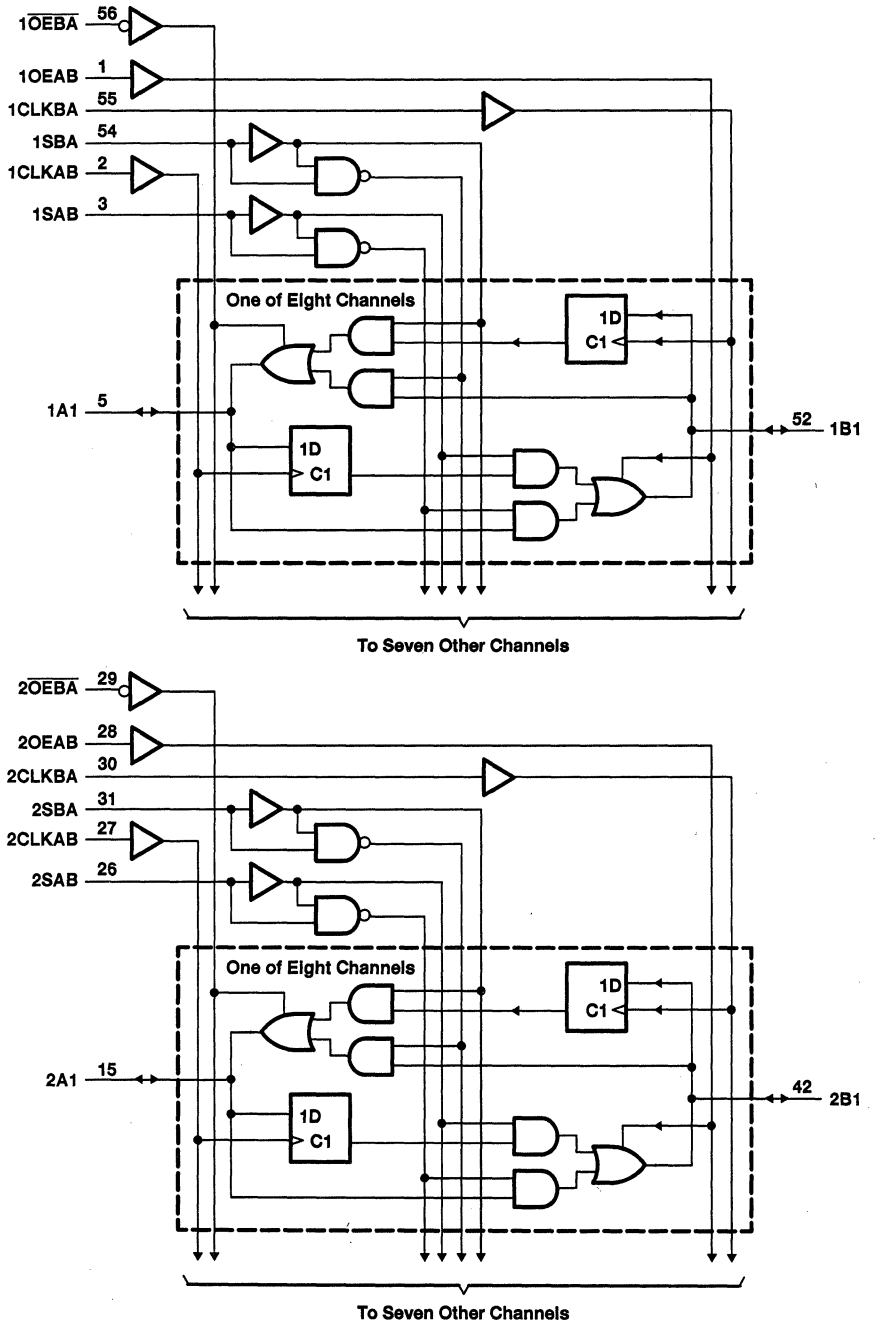
PRODUCT PREVIEW

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16652 ..... 96 mA
SN74LVT16652 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16652 ..... 48 mA
SN74LVT16652 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			SN54LVT16652		SN74LVT16652		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

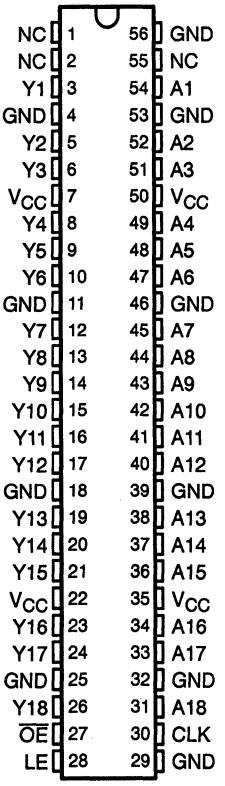
PARAMETER	TEST CONDITIONS			SN54LVT16652 MIN	SN54LVT16652 TYP†	SN54LVT16652 MAX	SN74LVT16652 MIN	SN74LVT16652 TYP†	SN74LVT16652 MAX	UNIT
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V	Control inputs			10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}	A or B ports§			5			5	
		V_I = 0	A or B ports§			–10			–10	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V	A or B ports	–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.1			0.1	mA
			Outputs low			5			5	
			Outputs disabled			0.1			0.1	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				3.5			3.5		pF
C_{io}	V_O = 3 V or 0				12			12		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

PRODUCT PREVIEW

- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation**
- **Member of the Texas Instruments *Widebus*™ Family**
- **Supports Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Supports Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Supports Live Insertion**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages Using 25-mil Center-to-Center Spacings**

DGG OR DL PACKAGE
(TOP VIEW)



NC – No internal connection

description

The SN74LVT16835 is an 18-bit universal bus driver designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

Data flow from A to Y is controlled by the output-enable ($\overline{OE}$) input. This device operates in the transparent mode when the latch-enable (LE) input is high. The A data is latched if the clock (CLK) input is held at a high or low logic level. If LE is low, the A-bus data is stored in the latch/flip-flop on the low-to-high transition of the clock. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVT16835 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the input/output (I/O) pins and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN74LVT16835 is characterized for operation from −40°C to 85°C.

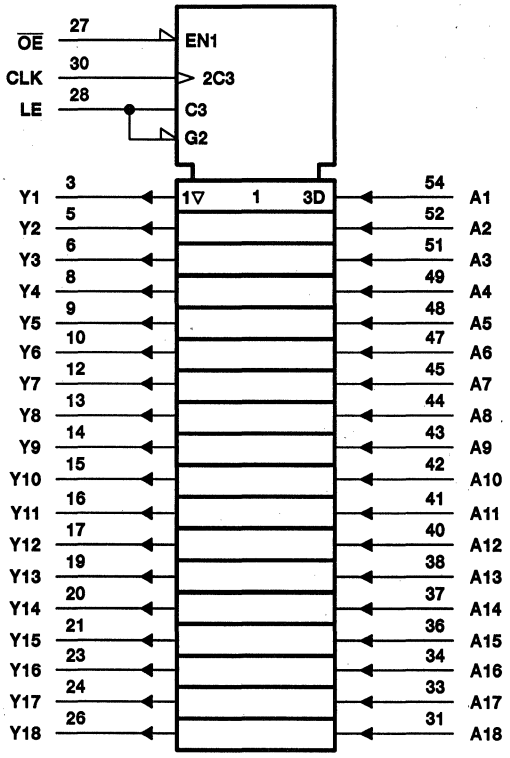
Widebus is a trademark of Texas Instruments Incorporated.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	LE	CLK	A	Y
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	↑	L	L
L	L	↑	H	H
L	L	H	X	Y_0†
L	L	L	X	Y_0‡

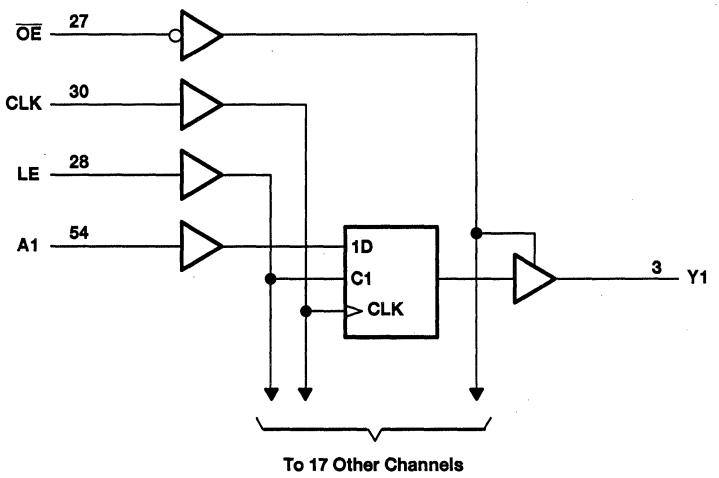
† Output level before the indicated steady-state input conditions were established, provided that CLK was high before LE went low
‡ Output level before the indicated steady-state input conditions were established

logic symbol§



§ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O ..... 128 mA
Current into any output in the high state, I_O (see Note 2) ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Operating free-air temperature range, T_A ..... −40°C to 85°C
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage		2		V
V_{IL}	Low-level input voltage			0.8	V
V_I	Input voltage			5.5	V
I_{OH}	High-level output current			−32	mA
I_{OL}	Low-level output current			64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			MIN	TYP†	MAX	UNIT
V_{IK}		V_{CC} = 2.7 V,	I_I = −18 mA				−1.2	V
V_{OH}		V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA		V_{CC}−0.2			V
		V_{CC} = 2.7 V,	I_{OH} = − 8 mA		2.4			
		V_{CC} = 3 V	I_{OH} = −32 mA		2			
V_{OL}		V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2	V
			I_{OL} = 24 mA				0.5	
		V_{CC} = 3 V	I_{OL} = 16 mA				0.4	
			I_{OL} = 32 mA				0.5	
			I_{OL} = 64 mA				0.55	
I_I		V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10	µA
	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND				±1	
	A inputs	V_{CC} = 3.6 V	V_I = V_{CC}				1	
			V_I = 5.5 V				20	
			V_I = 0				−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V				±100	µA
$I_{I(hold)}$	A inputs	V_{CC} = 3 V	V_I = 0.8 V		75			µA
			V_I = 2 V		−75			
I_{OZH}		V_{CC} = 3.6 V,	V_O = 3 V				1	µA
I_{OZL}		V_{CC} = 3.6 V,	V_O = 0.5 V				−1	µA
I_{CC}		V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.12	mA
				Outputs low			5	
				Outputs disabled			0.12	
ΔI_{CC}§		V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} − 0.6 V,				0.2	mA
C_i	Control inputs	V_I = 3 V or 0				3.5		pF
	Data pins					4.5		
C_o		V_O = 3 V or 0				11		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

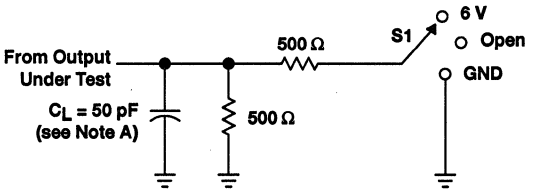
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	125	MHz
t_w	Pulse duration	LE high	3.3		3.3		ns
		CLK high or low	3.3		3.3		
t_{su}	Setup time	Data before CLK↑	1.6		2.1		ns
		Data before LE↓, CLK high	2.6		1.9		
		Data before LE↓, CLK low	2		1.3		
t_h	Hold time	Data after CLK↑	2		2.1		ns
		Data after LE↓	0.9		1.2		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP†	MAX	MIN	MAX	
f_{max}			150			150		MHz
t_{PLH}	A	Y	1.7	3	5.4		6.8	ns
t_{PHL}			1.6	3.2	5.9		7.7	
t_{PLH}	LE	Y	2.3	4	7		8.5	ns
t_{PHL}			2.7	4.3	7.9		9.7	
t_{PLH}	CLK	Y	2.5	4.1	7.9		9.2	ns
t_{PHL}			3.5	5.4	8.9		10.4	
t_{PZH}	$\overline{OE}$	Y	1.2	3	5		5.9	ns
t_{PZL}			1.5	3	5.8		6.9	
t_{PHZ}	$\overline{OE}$	Y	2.7	4.6	7.4		8.3	ns
t_{PLZ}			2.8	4.7	6.7		7.2	

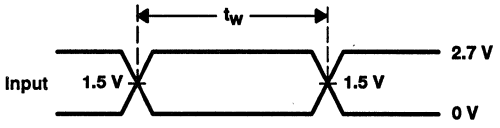
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

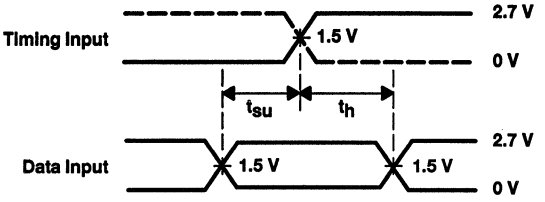


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

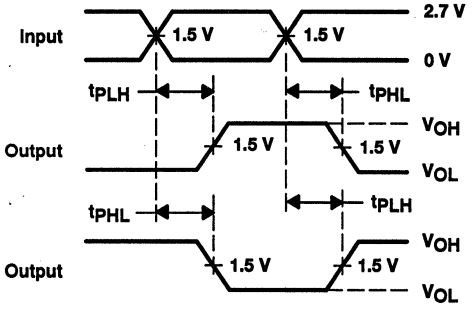
LOAD CIRCUIT FOR OUTPUTS



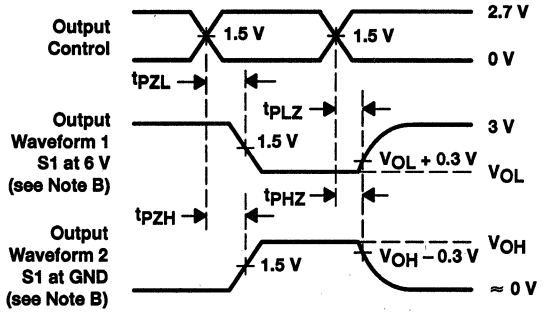
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



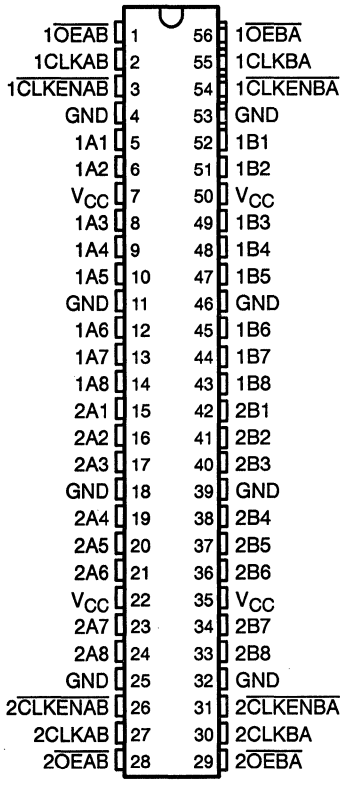
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low-Static Power Dissipation
- Members of the Texas Instruments *Widebus*™ Family
- Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})
- Support Unregulated Battery Operation Down to 2.7 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors
- Support Live Insertion
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

SN54LVT16952 . . . WD PACKAGE
SN74LVT16952 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'LVT16952 are 16-bit registered transceivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input provided that the clock-enable ($\overline{CLKENAB}$ or $\overline{CLKENBA}$) input is low. Taking the output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) input low accesses the data on either port.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

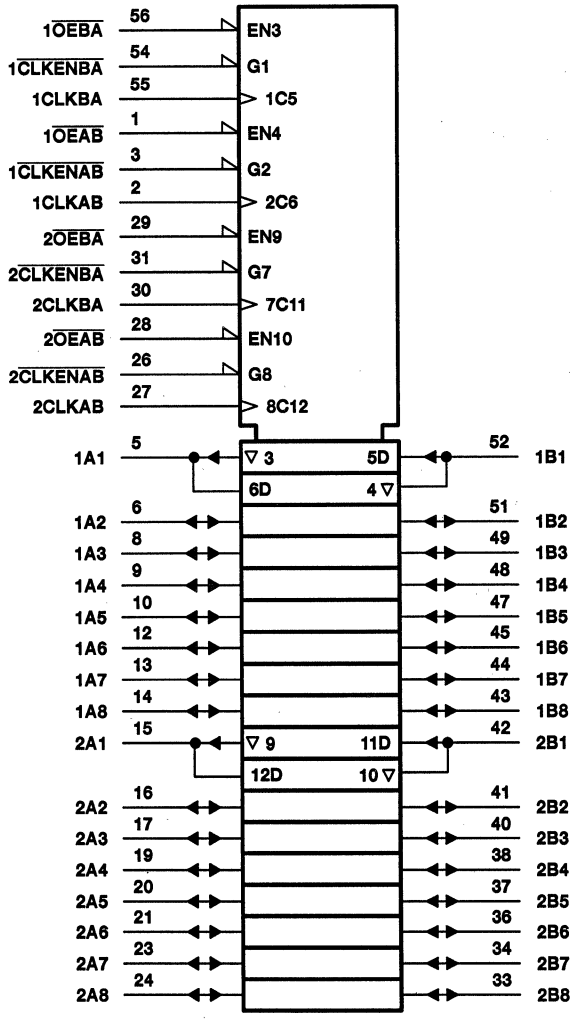
The SN74LVT16952 is available in TI's shrink small-outline (DL) and thin shrink small-outline (DGG) packages, which provide twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

Widebus is a trademark of Texas Instruments Incorporated.

description (continued)

The SN54LVT16952 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT16952 is characterized for operation from –40°C to 85°C.

logic symbol†



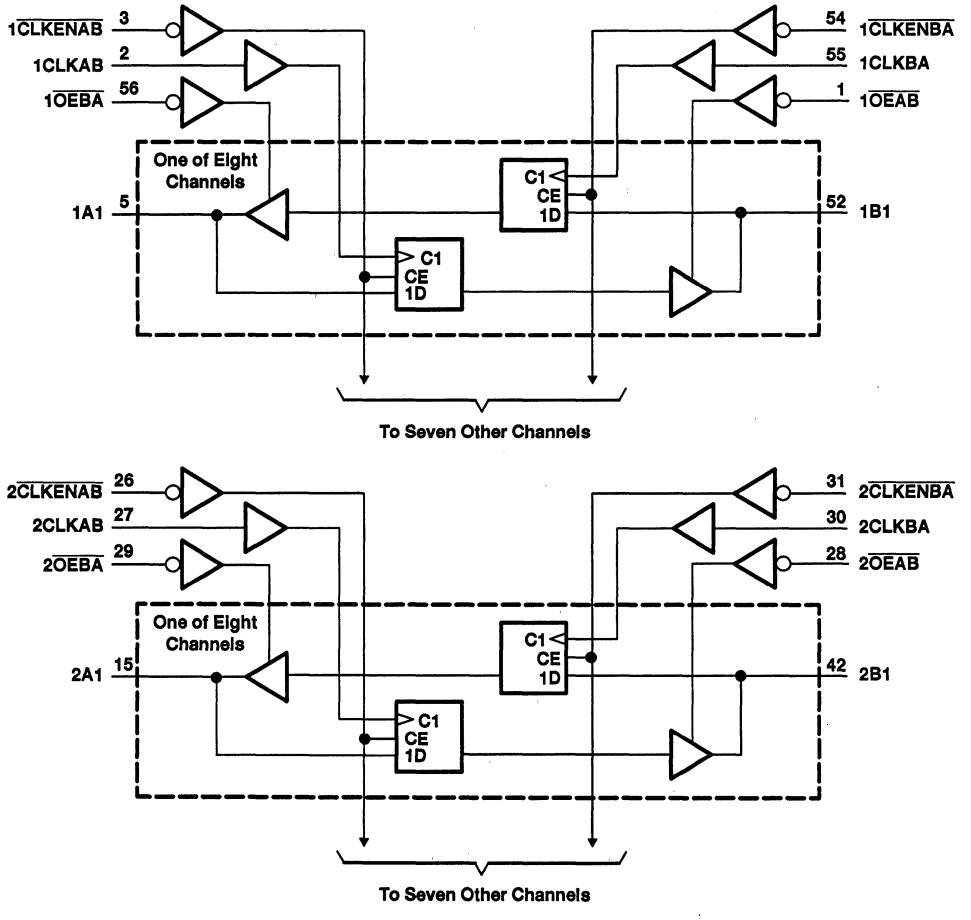
† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CLKENAB}$	CLKAB	$\overline{OEAB}$	A	B
H	X	L	X	B_0‡
X	L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

† A-to-B data flow is shown; B-to-A data flow is similar but uses $\overline{CLKENBA}$, CLKBA, and $\overline{OEBA}$.
‡ Level of B before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) .... −0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT16952 ..... 96 mA
SN74LVT16952 ..... 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT16952 ..... 48 mA
SN74LVT16952 ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT16952		SN74LVT16952		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			−24		−32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		−55	125	−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT16952			SN74LVT16952			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			20			20	
		V_I = V_{CC}				1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high			0.12			0.12	mA
			Outputs low			5			5	
			Outputs disabled			0.12			0.12	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.2			0.2	mA
C_i	V_I = 3 V or 0				4			4		pF
C_{io}	V_O = 3 V or 0				13			13		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused pins at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

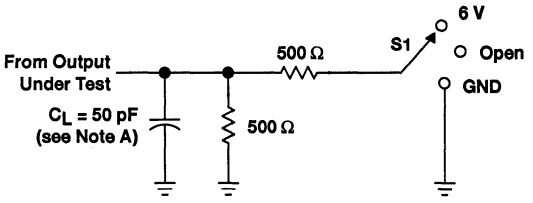
			SN54LVT16952				SN74LVT16952				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration	CLKEN high	3.3		3.3		3.3		3.3		ns
		CLK high or low	3.3		3.3		3.3		3.3		
t_{su}	Setup time	A or B before CLK	2.1		2.9		2.1		2.9		ns
		$\overline{CLKEN}$ before CLK	1.2		1.6		1.2		1.6		
t_h	Hold time	A or B after CLK	0.7		0.7		0.7		0.7		ns
		$\overline{CLKEN}$ after CLK	1.4		1.5		1.4		1.5		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT16952				SN74LVT16952					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150		150		150			150		MHz
t_{PLH}	CLKBA or CLKAB	A or B	2	5.9		7.4	2	3.4	5.8		7.1	ns
t_{PHL}			2	6		7	2	3.4	5.8		6.9	
t_{PZH}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	1	6.3		7.3	1	2.7	5.6		6.7	ns
t_{PZL}			1.2	6.8		8.2	1.2	2.7	6.5		8	
t_{PHZ}	$\overline{OEBA}$ or $\overline{OEAB}$	A or B	2.3	7		7.6	2.3	3.9	6.3		6.9	ns
t_{PLZ}			2.2	5.8		6	2.2	3.9	5.1		5.3	

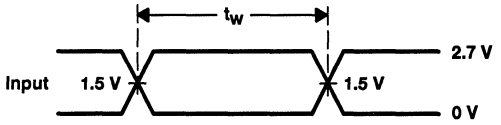
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

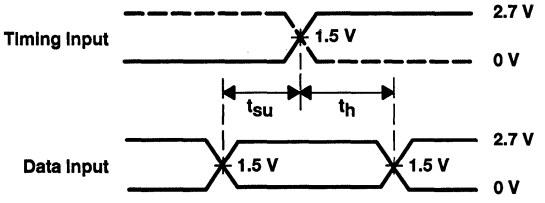


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

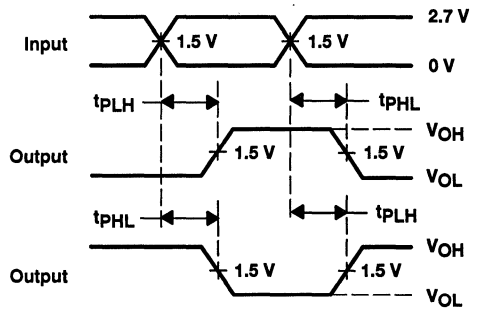
LOAD CIRCUIT FOR OUTPUTS



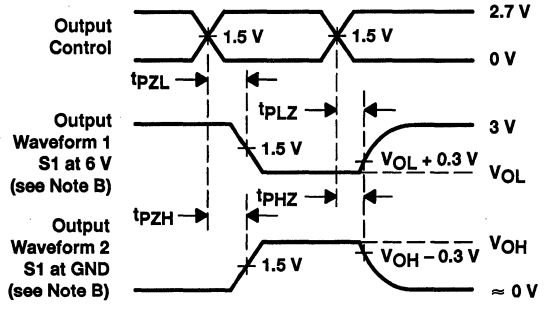
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

LVT JTAG/IEEE 1149.1

Features	Benefits
• Compatibility with IEEE Standard 1149.1-1990 (JTAG) test access port (TAP) and boundary-scan architecture	• Adherence to well-established industry standard, ensuring access to a board range of supporting software and test equipment
• Effectively place a unique digital test probe on each signal pin	• Improved test access into complex circuit board assemblies for board manufacturing test and design verification/debug
• TI extensions beyond 1149.1 required instructions: – Parallel Signature Analysis (PSA) – Pseudo-Random Pattern Generation (PRPG)	• Built-in self-test features provide near-at-speed test capability for improved test flexibility, throughput, and effectiveness
• EPIC-IIB™ submicron process with special low-voltage enhancements	• High-performance, low-power, high-drive, low-noise equivalents of standard LVT buffers/drivers/transceivers offering system and test designers flexible integration options
• Expanded V_{CC} range from 2.7 V to 3.6 V	
• 18-bit and 20-bit UBT™ architectures	• Advanced integration, as one UBT™ can replace most common bus-interface logic
• Widebus™ functions available in space-saving EIAJ TSSOP, JEDEC SSOP, and EIAJ TQFP fine-pitch surface-mount packaging	• Increased functional and component density supporting tight board space budgets
• Maximum propagation delays < 6 ns	• Speed equivalency to standard LVT product, resulting in minimal performance penalty for boundary-scan implementation
• Bus-hold circuitry at I/O signal pins	• Reduced component count by eliminating need for external tie-off resistors
• Series-resistor options on B-port ('LVT182 series)	• Reduce component count by eliminating need for external line-termination resistors
• Members of a broad family of Texas Instruments boundary-scan logic	• Compatibility with a full line of scan-support functions, including test bus controllers and addressable-scan ports, providing a complete solution for boundary-scan-based system testing

Today's designs are based on evermore complex ICs, fine-pitch packaging, and denser board layouts. These factors limit test access and greatly complicate traditional methods of functional and in-circuit manufacturing test and design verification/debug. The IEEE 1149.1 (JTAG) boundary-scan test standard was created to address these issues. TI has taken a leading role in the industry in supplying logic that integrates IEEE 1149.1 (JTAG) test methods.

Features and benefits of TI LVT boundary-scan logic products are on the facing page and a list of available LVT scannable bus-interface devices is presented below. Data sheets for the entire family are in the *1994 Boundary-Scan Logic/IEEE 1149.1 (JTAG) Data Book, lit# SCTD002.* Please contact your local TI sales representative or TI authorized distributor for copies.

The following table lists LVT IEEE 1149.1 (JTAG) devices currently available or planned. Customers interested in learning more about TI's plans for these devices should contact the Advanced System Logic Marketing hotline at (903) 868-5202.

DEVICE		PIN COUNT	DESCRIPTION
SN54LVT18245	SN74LVT18245	56	18-bit bus transceiver
SN54LVT182245	SN74LVT182245	56	18-bit bus transceiver with series resistor option
	SN74LVT18502	64	18-bit universal bus transceiver
	SN74LVT182502	64	18-bit universal bus transceiver with series resistor option
	SN74LVT18504	64	20-bit universal bus transceiver
SN54LVT182504	SN74LVT182504	64	20-bit universal bus transceiver with series resistor option
SN54LVT18640	SN74LVT18640	56	18-bit inverting bus transceiver
SN54LVT182640	SN74LVT182640	56	18-bit inverting bus transceiver with series resistor option
SN54LVT18646	SN74LVT18646	64	18-bit transceiver and register
SN54LVT182646	SN74LVT182646	64	18-bit transceiver and register with series resistor option
SN54LVT18652	SN74LVT18652	64	18-bit transceiver and register
SN54LVT182652	SN74LVT182652	64	18-bit transceiver and register with series resistor option

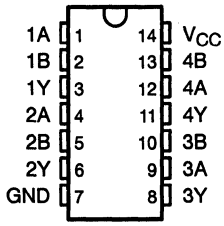
Contents

Contents

SCAS279B – JANUARY 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-input positive-NAND gate is designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVC00 performs the Boolean functions $Y = \overline{A \bullet B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

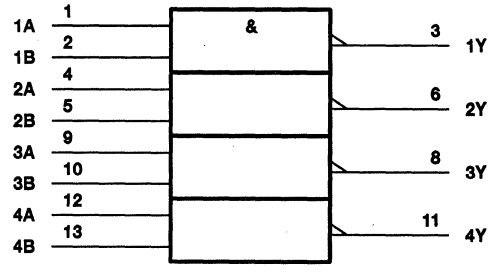
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC00 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)

EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 μA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	μA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND	3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

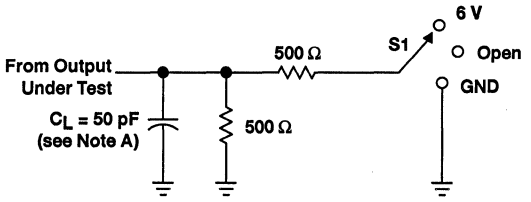
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	6		7	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

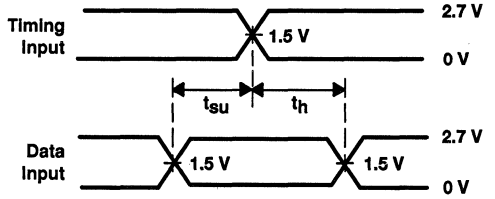
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	9.5	pF

PARAMETER MEASUREMENT INFORMATION

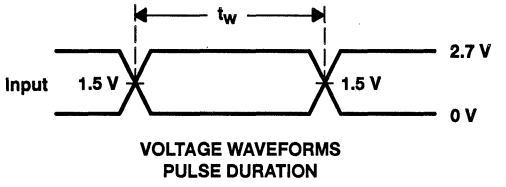


LOAD CIRCUIT

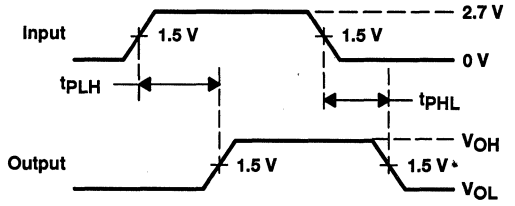
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



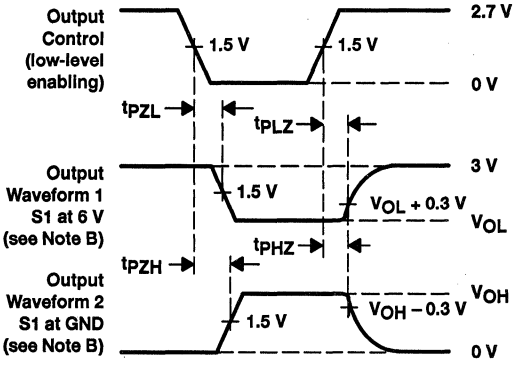
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



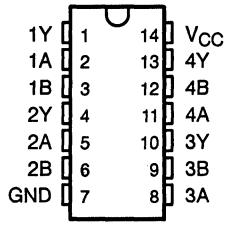
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-input positive-NOR gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC02 performs the Boolean functions $Y = \overline{A + B}$ or $Y = \overline{A} \bullet \overline{B}$ in positive logic.

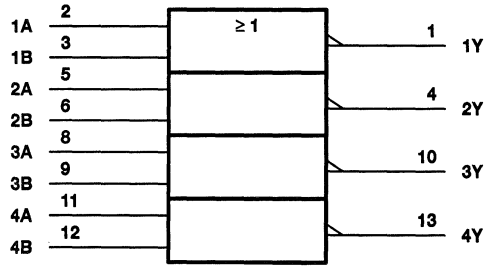
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC02 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

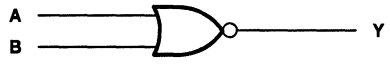
INPUTS		OUTPUT
A	B	Y
H	X	L
X	H	L
L	L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)



EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

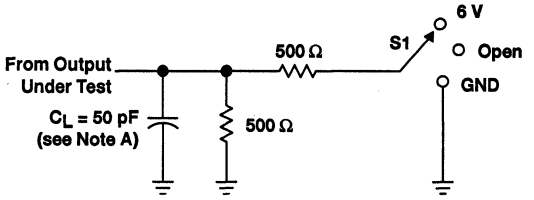
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	6		7	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

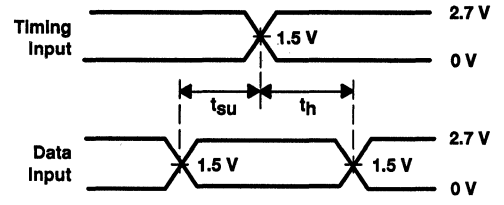
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	9.5	pF

PARAMETER MEASUREMENT INFORMATION

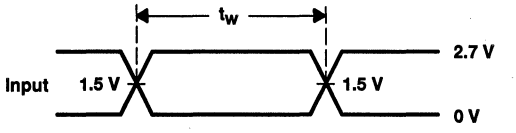


LOAD CIRCUIT

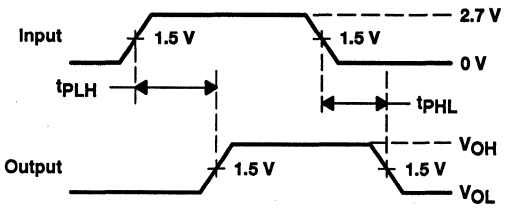
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



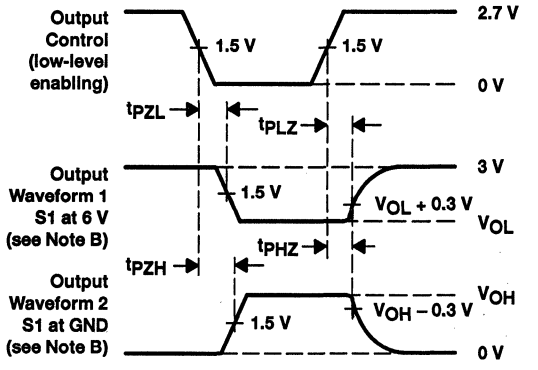
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

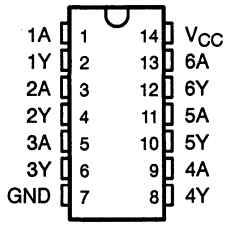
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

SCAS281B – JANUARY 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This hex inverter contains six independent inverters designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVC04 performs the Boolean function $Y = \overline{A}$.

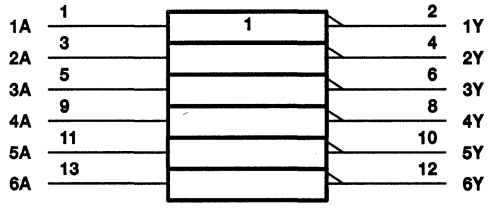
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC04 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each inverter)

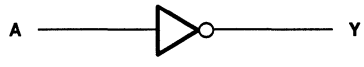
INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each inverter (positive logic)



EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

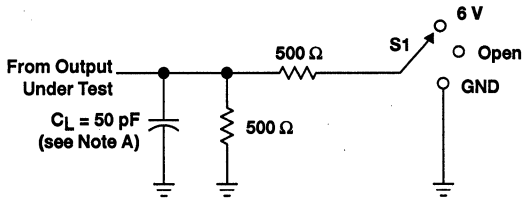
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	6		7	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

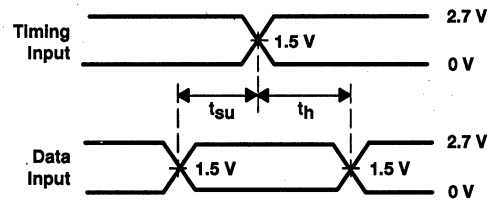
PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF,	f = 10 MHz	8	pF

PARAMETER MEASUREMENT INFORMATION

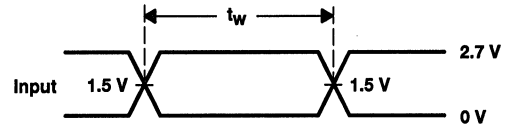


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

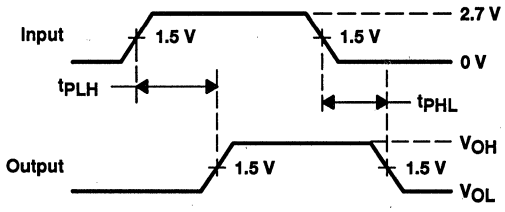
LOAD CIRCUIT



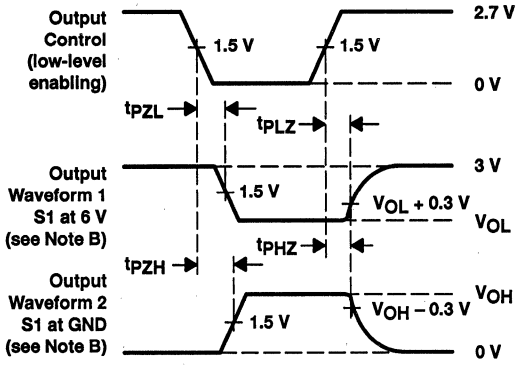
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

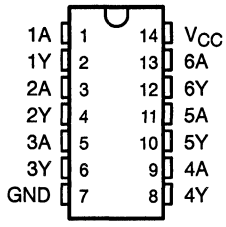
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

SCAS282B – JANUARY 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This hex inverter is designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVCU04 contains six independent inverters with unbuffered outputs. The device performs the Boolean function $Y = \overline{A}$.

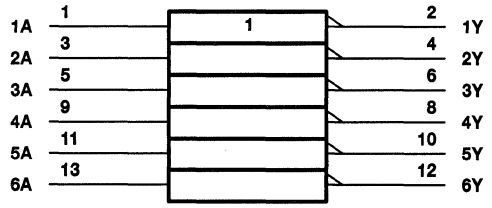
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVCU04 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

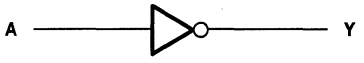
INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each inverter (positive logic)



EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V	2.16		V
		V_{CC} = 3 V	2.4		
		V_{CC} = 3.6 V	2.88		
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.65	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA,	V_{IH} = 2.16 V	2.7 V			0.2	V
	I_{OL} = 100 µA,	V_{IH} = 2.88 V	3.6 V			0.2	
	I_{OL} = 12 mA,	V_{IH} = 2.16 V	2.7 V			0.4	
	I_{OL} = 24 mA,	V_{IH} = 2.4 V	3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

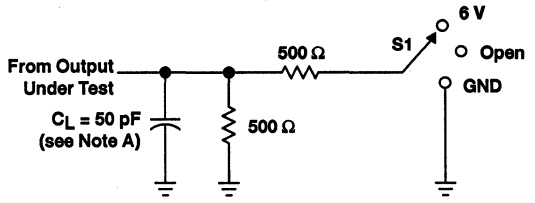
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	5		6	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

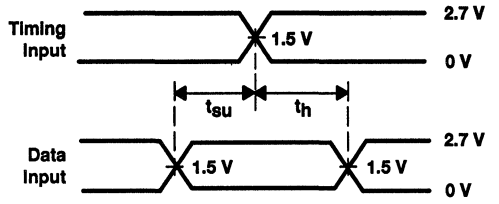
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF, f = 10 MHz	5	pF

PARAMETER MEASUREMENT INFORMATION

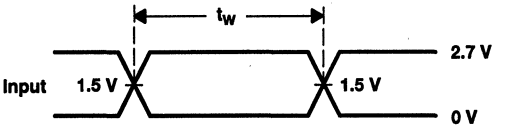


LOAD CIRCUIT

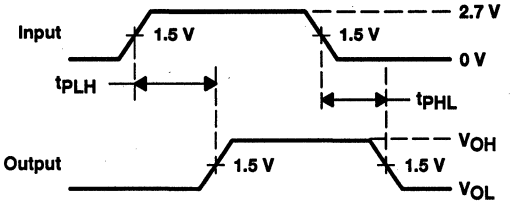
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



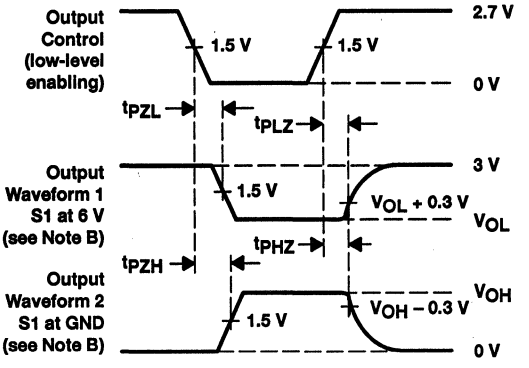
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



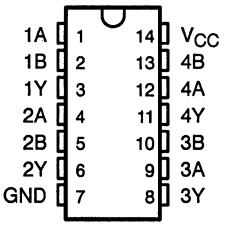
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-input positive-AND gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC08 performs the Boolean functions $Y = A \bullet B$ or $Y = \overline{\overline{A} + \overline{B}}$ in positive logic.

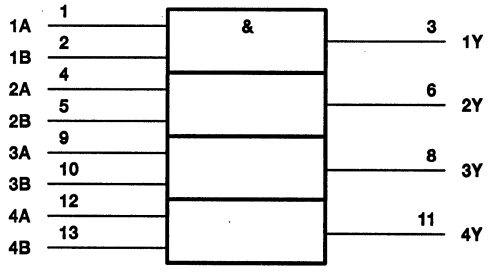
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-/5-V system environment.

The SN74LVC08 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	H	H
L	X	L
X	L	L

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)

EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	8	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 μA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	μA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND	3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

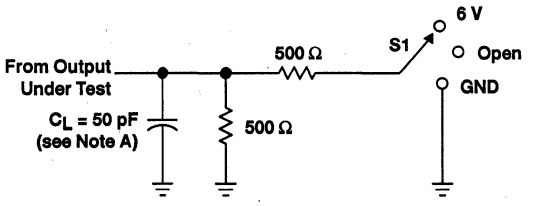
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	6		7	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

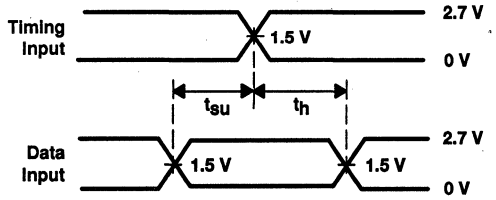
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	10	pF

PARAMETER MEASUREMENT INFORMATION

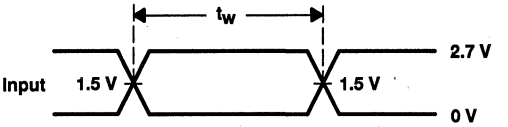


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

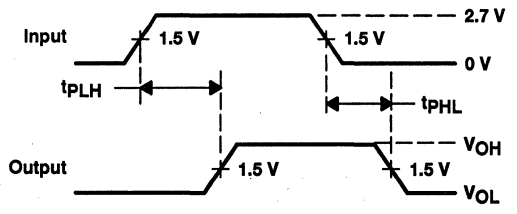
LOAD CIRCUIT



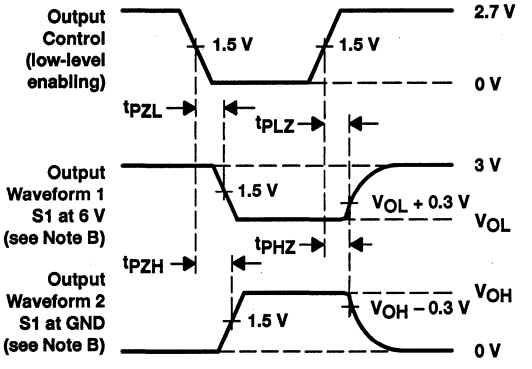
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



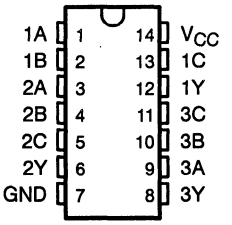
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This triple 3-input positive-NAND gate is designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVC10 performs the Boolean functions $Y = \overline{A \bullet B \bullet C}$ or $Y = \overline{A} + \overline{B} + \overline{C}$ in positive logic.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

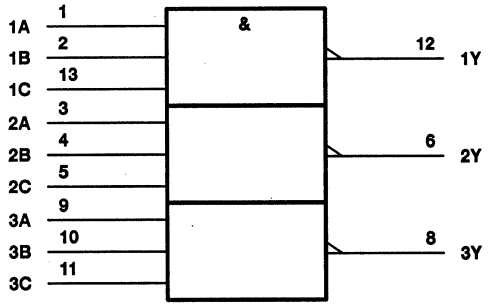
The SN74LVC10 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS			OUTPUT
A	B	C	Y
H	H	H	L
L	X	X	H
X	L	X	H
X	X	L	H

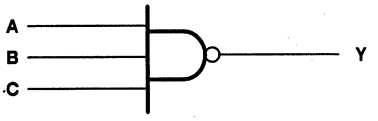
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

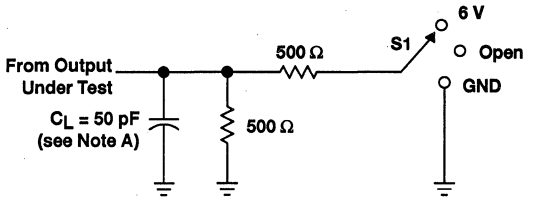
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	6		7	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

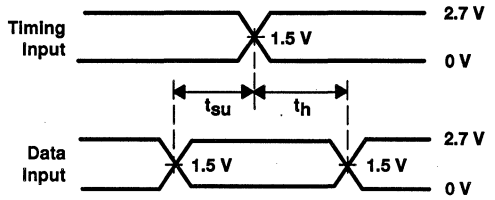
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	11	pF

PARAMETER MEASUREMENT INFORMATION

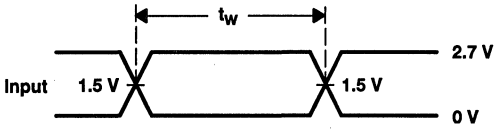


LOAD CIRCUIT

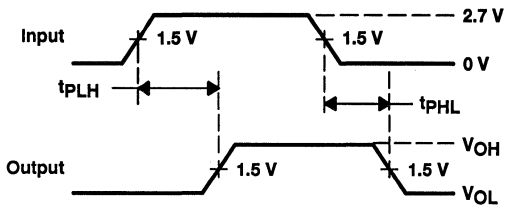
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



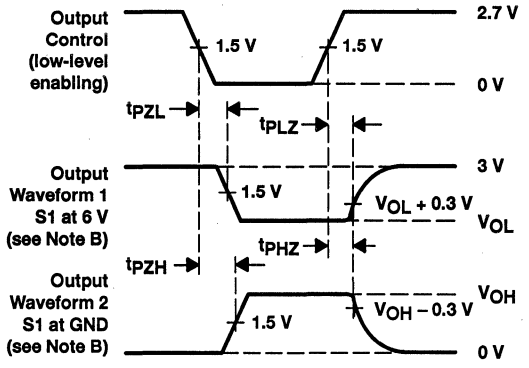
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



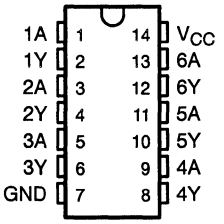
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This hex Schmitt-trigger inverter is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC14 contains six independent inverters. The device performs the Boolean function $Y = \overline{A}$.

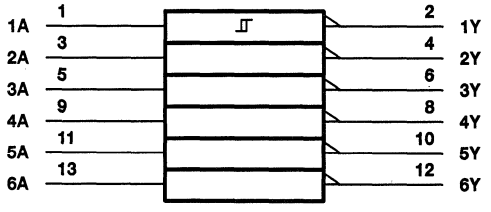
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC14 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each inverter (positive logic)

EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{T+} Positive-going threshold			2.7 V	0.8		2	V
			3 V	0.8		2	
			3.6 V	0.8		2	
V_{T-} Negative-going threshold			2.7 V	0.4		1.4	V
			3 V	0.6		1.5	
			3.6 V	0.8		1.8	
ΔV_T Hysteresis ($V_{T+} - V_{T-}$)			2.7 V	0.3		1.1	V
			3 V	0.3		1.2	
			3.6 V	0.3		1.2	
V_{OH}	$I_{OH} = -100$ μA		MIN to MAX	$V_{CC}-0.2$			V
	$I_{OH} = -12$ mA		2.7 V	2.2			
			3 V	2.4			
	$I_{OH} = -24$ mA		3 V	2.2			
V_{OL}	$I_{OL} = 100$ μA		MIN to MAX			0.2	V
	$I_{OL} = 12$ mA		2.7 V			0.4	
	$I_{OL} = 24$ mA		3 V			0.55	
I_I	$V_I = 5.5$ V or GND		3.6 V			±5	μA
I_{CC}	$V_I = V_{CC}$ or GND,	$I_O = 0$	3.6 V			10	μA
ΔI_{CC}	One input at $V_{CC} - 0.6$ V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	$V_I = V_{CC}$ or GND		3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at $V_{CC} = 3.3$ V, $T_A = 25°C$.

switching characteristics over recommended operating free-air temperature range, $C_L = 50$ pF (unless otherwise noted) (see Figure 1)

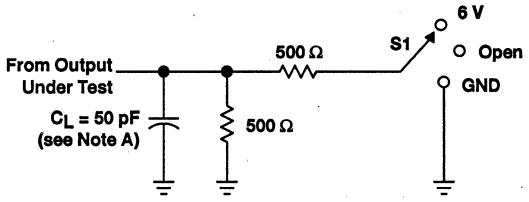
PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 3.3$ V ± 0.3 V		$V_{CC} = 2.7$ V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	7		7.5	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, $V_{CC} = 3.3$ V, $T_A = 25°C$

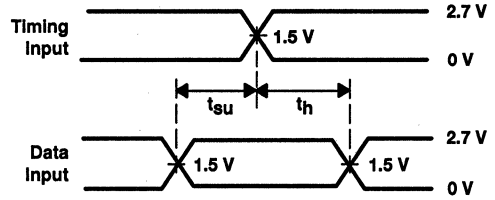
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	$C_L = 50$ pF, f = 10 MHz	7	pF

PARAMETER MEASUREMENT INFORMATION

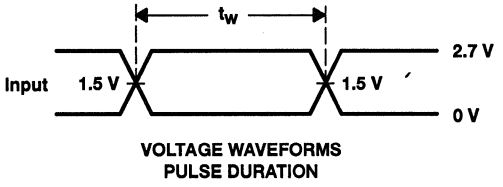


LOAD CIRCUIT

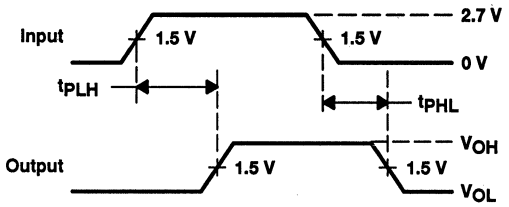
TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 6 V GND



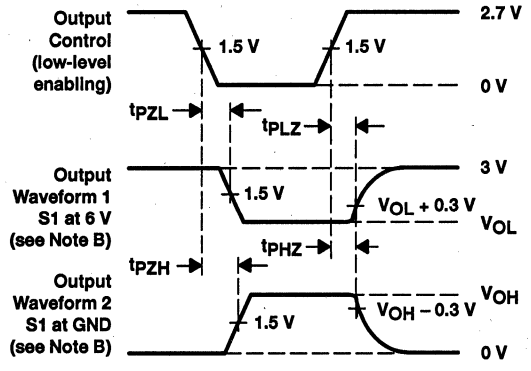
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



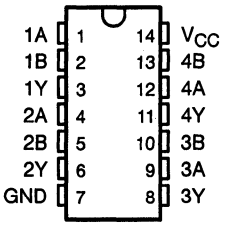
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-input positive-OR gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC32 performs the Boolean functions $Y = A + B$ or $Y = \overline{A} \bullet \overline{B}$ in positive logic.

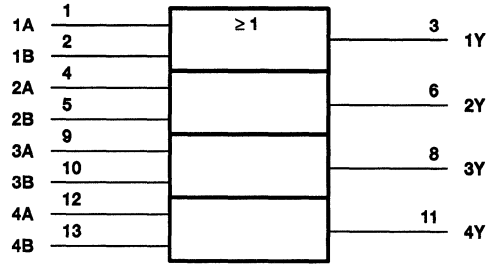
Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC32 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	X	H
X	H	H
L	L	L

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)

EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	7	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

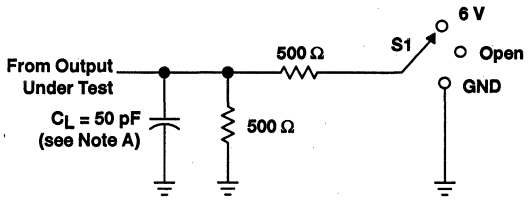
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1.5	6		7	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

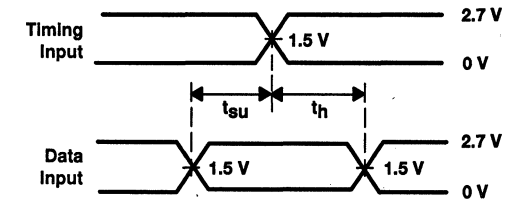
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	12.5	pF

PARAMETER MEASUREMENT INFORMATION

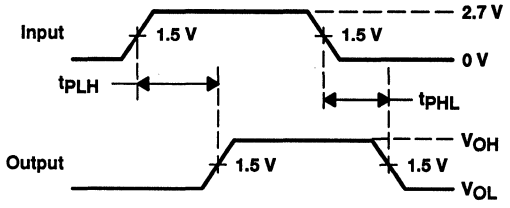


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

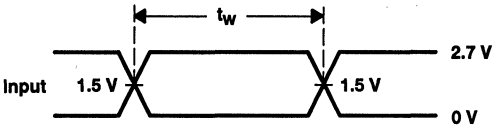
LOAD CIRCUIT



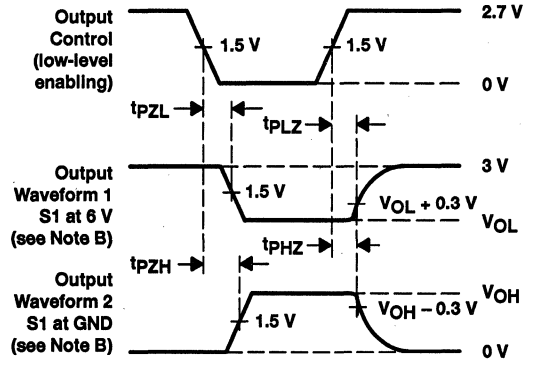
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



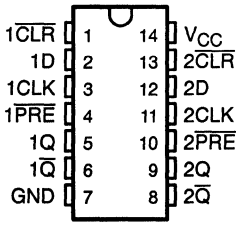
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This dual positive-edge-triggered D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

A low level at the preset ($\overline{PRE}$) or clear ($\overline{CLR}$) inputs sets or resets the outputs regardless of the levels of the other inputs. When $\overline{PRE}$ and $\overline{CLR}$ are inactive (high), data at the data (D) input meeting the setup time requirements is transferred to the outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the D input may be changed without affecting the levels at the outputs.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC74 is characterized for operation from –40°C to 85°C.

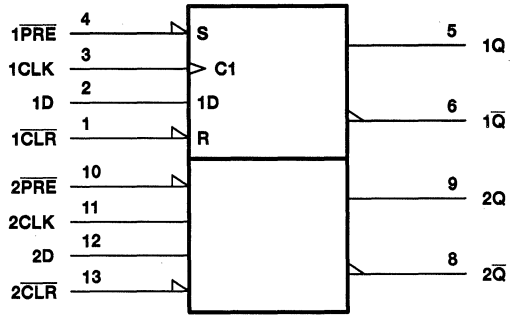
FUNCTION TABLE

INPUTS				OUTPUTS	
$\overline{PRE}$	$\overline{CLR}$	CLK	D	Q	$\overline{Q}$
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H†	H†
H	H	↑	H	H	L
H	H	↑	L	L	H
H	H	L	X	Q_0	$\overline{Q}_0$

† This configuration is nonstable; that is, it does not persist when $\overline{PRE}$ or $\overline{CLR}$ returns to its inactive (high) level.

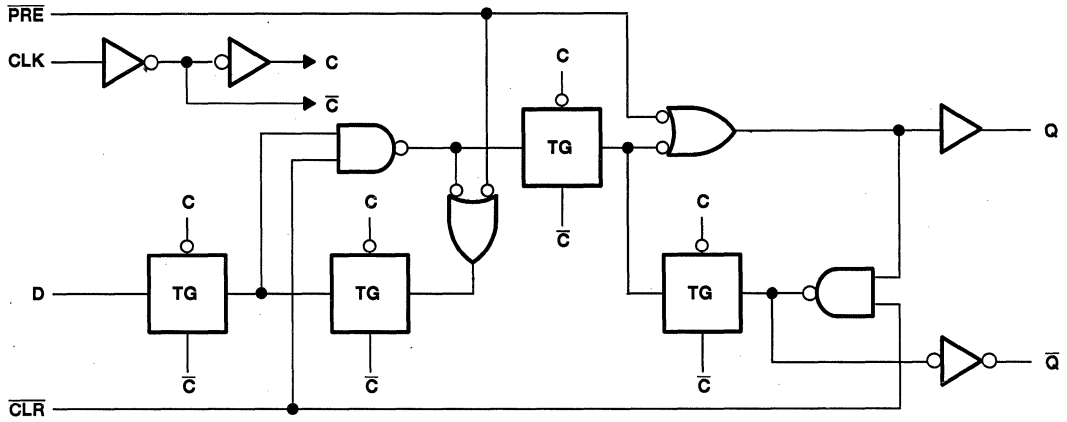
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each flip-flop (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	100	0	83	MHz
t_w	Pulse duration	$\overline{PRE}$ or $\overline{CLR}$ low	4		5		ns
		CLK high or low	5		6		
t_{su}	Setup time before CLK↑	Data	3		4		ns
		$\overline{PRE}$ or $\overline{CLR}$ inactive	2		3		
t_h	Hold time, data after CLK↑		1		2		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

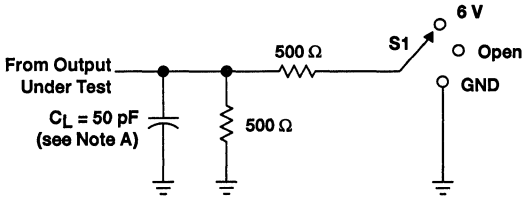
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			100		83		MHz
t_{pd}	CLK	Q or $\overline{Q}$	1	6.5		7	ns
	$\overline{PRE}$ or $\overline{CLR}$		1	8		9	
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

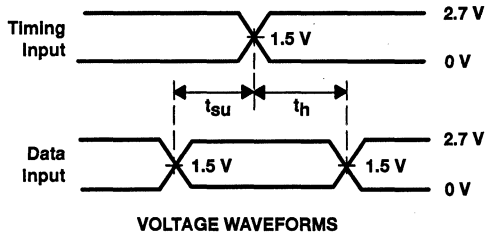
PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	C_L = 50 pF,	f = 10 MHz	27	pF

PARAMETER MEASUREMENT INFORMATION

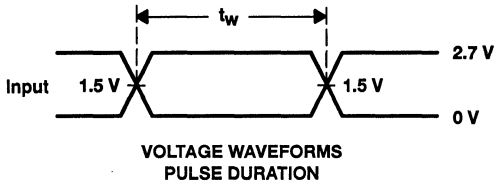


LOAD CIRCUIT

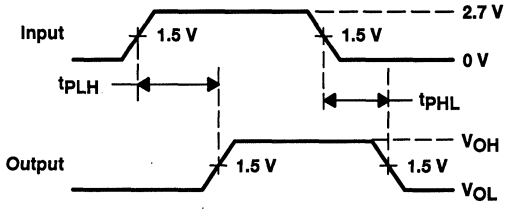
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



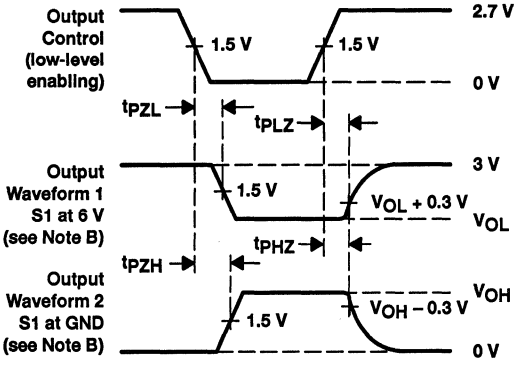
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



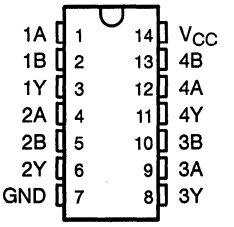
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-input exclusive-OR gate is designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVC86 performs the Boolean functions $Y = A \oplus B$ or $Y = \overline{A}B + A\overline{B}$ in positive logic.

A common application is as a true/complement element. If one of the inputs is low, the other input is reproduced in true form at the output. If one of the inputs is high, the signal on the other input is reproduced inverted at the output.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

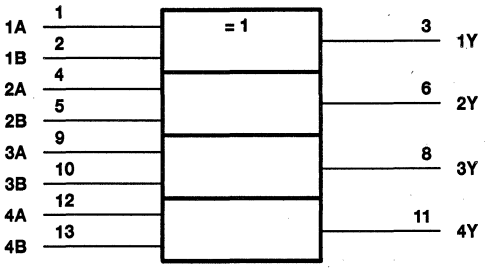
The SN74LVC86 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

EPIC is a trademark of Texas Instruments Incorporated.

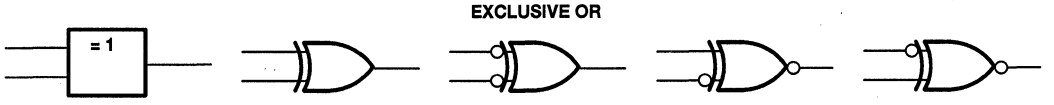
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

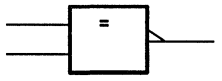
exclusive-OR logic

An exclusive-OR gate has many applications, some of which can be represented better by alternative logic symbols.



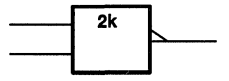
These five equivalent exclusive-OR symbols are valid for an SN74LVC86 gate in positive logic; negation may be shown at any two ports.

LOGIC-IDENTITY ELEMENT



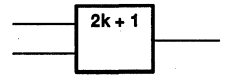
The output is active (low) if all inputs stand at the same logic level (i.e., A = B).

EVEN-PARITY ELEMENT



The output is active (low) if an even number of inputs (i.e., 0 or 2) are active.

ODD-PARITY ELEMENT



The output is active (high) if an odd number of inputs (i.e., only 1 of the 2) are active.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	9	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

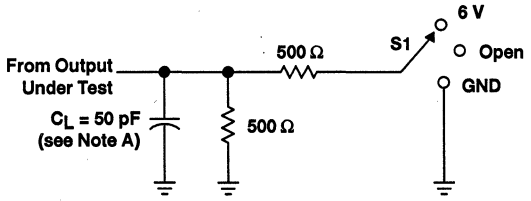
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	6.5		7.5	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

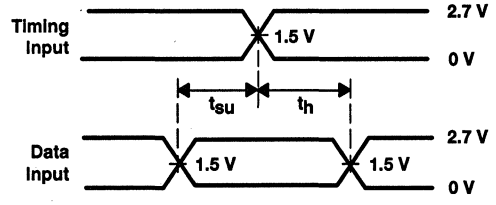
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	8.5	pF

PARAMETER MEASUREMENT INFORMATION

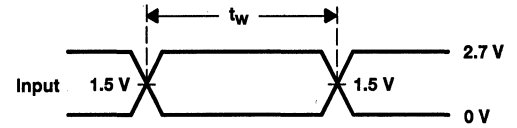


LOAD CIRCUIT

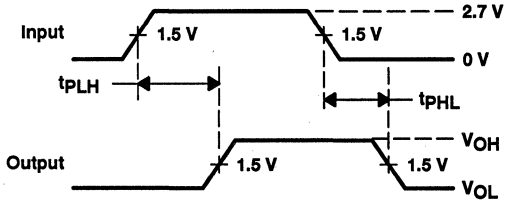
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



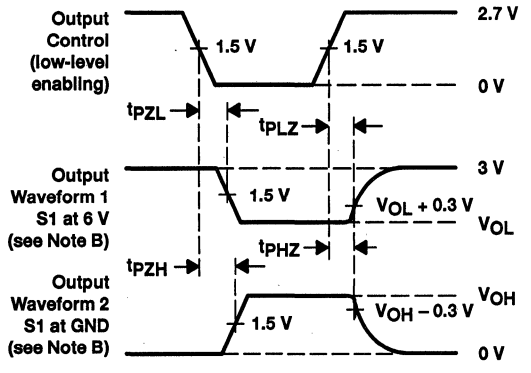
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



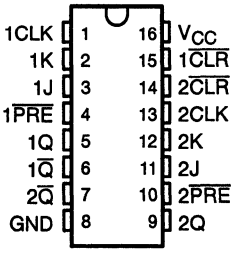
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This dual negative-edge-triggered J-K flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

A low level at the preset ($\overline{PRE}$) or clear ($\overline{CLR}$) inputs sets or resets the outputs regardless of the levels of the other inputs. When $\overline{PRE}$ and $\overline{CLR}$ are inactive (high), data at the J and K inputs meeting the setup time requirements is transferred to the outputs on the negative-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the J and K inputs can be changed without affecting the levels at the outputs. The SN74LVC112 can perform as a toggle flip-flop by tying J and K high.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices in a mixed 3.3-V/5-V system environment.

The SN74LVC112 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

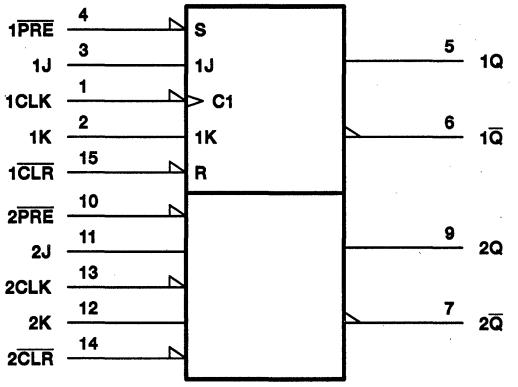
INPUTS					OUTPUTS	
$\overline{PRE}$	$\overline{CLR}$	CLK	J	K	Q	$\overline{Q}$
L	H	X	X	X	H	L
H	L	X	X	X	L	H
L	L	X	X	X	H†	H†
H	H	↓	L	L	Q_0	$\overline{Q}_0$
H	H	↓	H	L	H	L
H	H	↓	L	H	L	H
H	H	↓	H	H	Toggle	
H	H	H	X	X	Q_0	$\overline{Q}_0$

† The output levels in this configuration may not meet the minimum levels for V_{OH}. Furthermore, this configuration is nonstable; that is, it does not persist when either $\overline{PRE}$ or $\overline{CLR}$ returns to its inactive (high) level.

PRODUCT PREVIEW

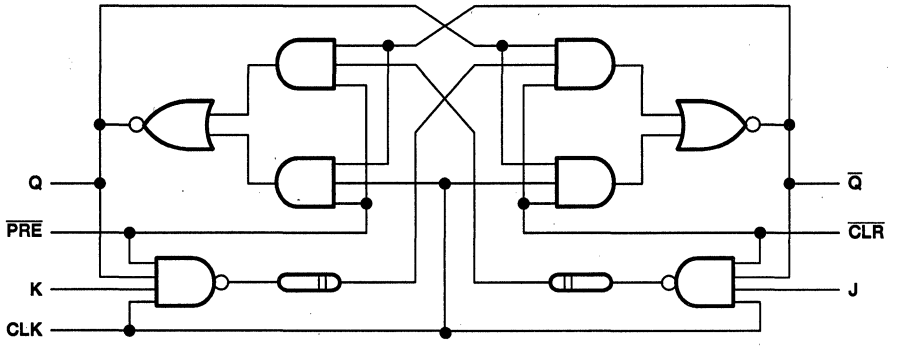
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each flip-flop (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

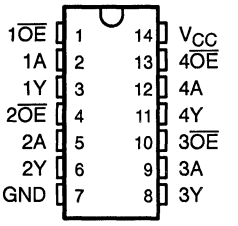
PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V				pF
C_o	V_O = V_{CC} or GND	3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple bus buffer gate is designed for 2.7-V to 3.6-V V_{CC} operation. The SN74LVC125 features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable ($\overline{OE}$) input is high.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

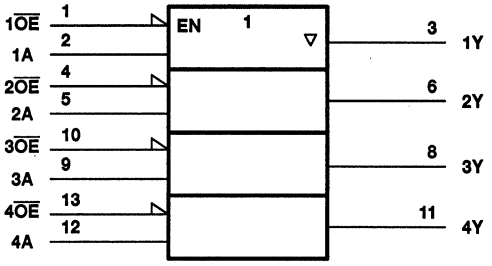
The SN74LVC125 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

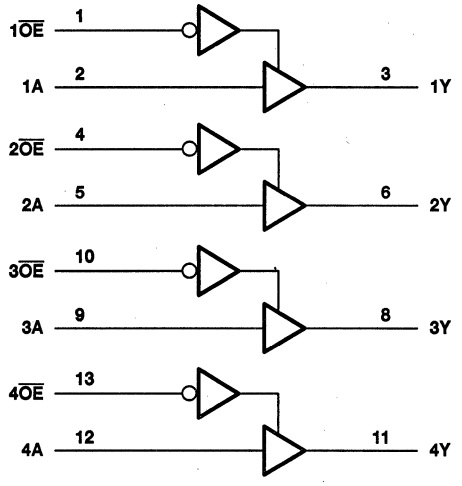
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	8	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = − 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = − 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF
C_o	V_O = V_{CC} or GND		3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

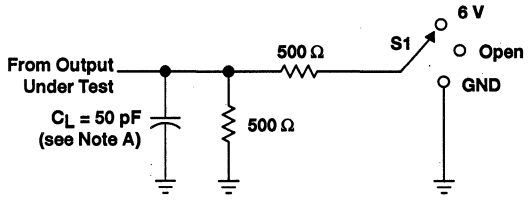
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	6.5		7	ns
t_{en}	$\overline{OE}$	Y	1	7		8	ns
t_{dis}	$\overline{OE}$	Y	1	5.5		6.5	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

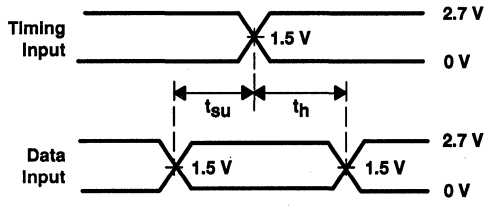
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	15	pF

PARAMETER MEASUREMENT INFORMATION

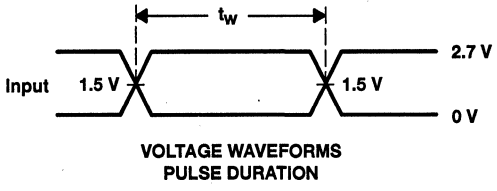


LOAD CIRCUIT

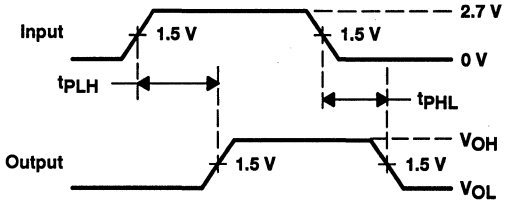
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



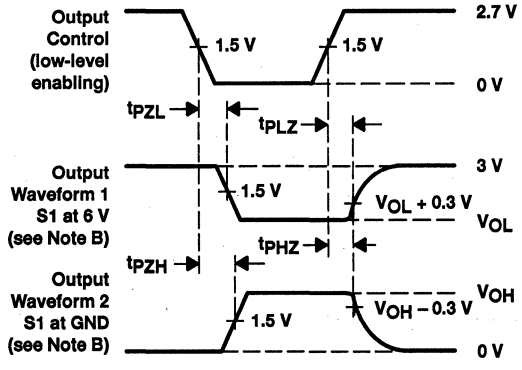
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



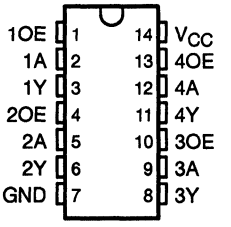
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple bus buffer gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC126 features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (OE) input is low.

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC126 is characterized for operation from −40°C to 85°C.

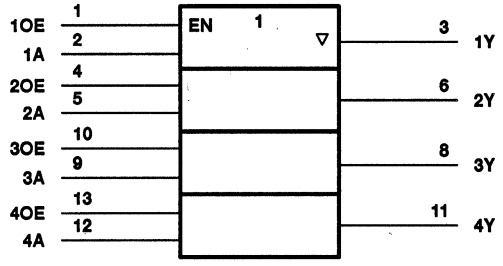
FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
OE	A	Y
H	H	H
H	L	L
L	X	Z

PRODUCT PREVIEW

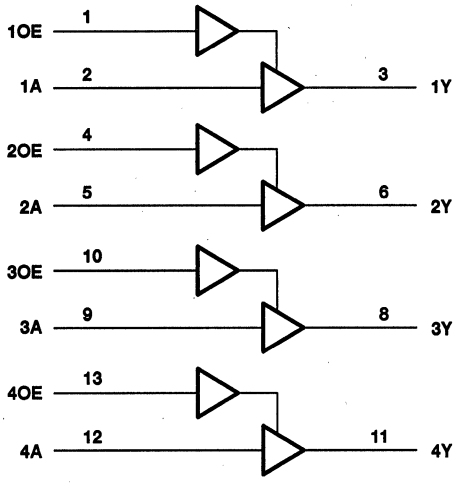
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CO} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

PRODUCT PREVIEW

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

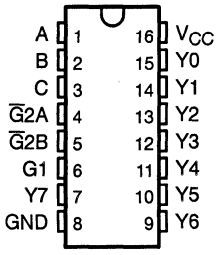
PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V				pF
C_o	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This 3-line to 8-line decoder/demultiplexer with latches on three address inputs is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC137 is designed for high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, this decoder can be used to minimize the effects of system decoding. When employed with high-speed memories utilizing a fast enable circuit, the delay times of this decoder and the enable time of the memory are usually less than the typical access time of the memory. This means that the effective system delay introduced by the decoder is negligible.

When the latch-enable ($\overline{G}$2A) input is low, the SN74LVC137 acts as a decoder/demultiplexer. When $\overline{G}$2A transitions from low to high, the address present at the inputs (A, B, and C) is stored in the latches. Further address changes are ignored provided $\overline{G}$2A remains high. The output-enable (G1 and $\overline{G}$2B) inputs control the outputs independently of the select or latch-enable inputs. All of the outputs are forced high if G1 is low or $\overline{G}$2B is high.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices in a mixed 3.3-V/5-V system environment.

The SN74LVC137 is characterized for operation from –40°C to 85°C.

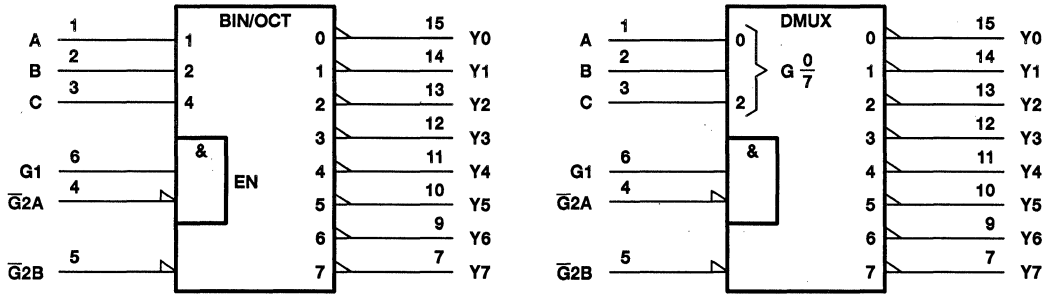
FUNCTION TABLE

LATCH ENABLE	OUTPUT-ENABLE		SELECT INPUTS			OUTPUTS							
$\overline{G}$2A	G1	$\overline{G}$2B	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	X	H	X	X	X	H	H	H	H	H	H	H	H
X	L	X	X	X	X	H	H	H	H	H	H	H	H
L	H	L	L	L	L	L	H	H	H	H	H	H	H
L	H	L	L	L	H	H	L	H	H	H	H	H	H
L	H	L	L	H	L	H	H	L	H	H	H	H	H
L	H	L	L	H	H	H	H	H	L	H	H	H	H
L	H	L	H	L	L	H	H	H	H	L	H	H	H
L	H	L	H	L	H	H	H	H	H	H	L	H	H
L	H	L	H	H	L	H	H	H	H	H	H	L	H
L	H	L	H	H	H	H	H	H	H	H	H	H	L
H	H	L	X	X	X	Outputs corresponding to stored address = L; all other outputs = H							

PRODUCT PREVIEW

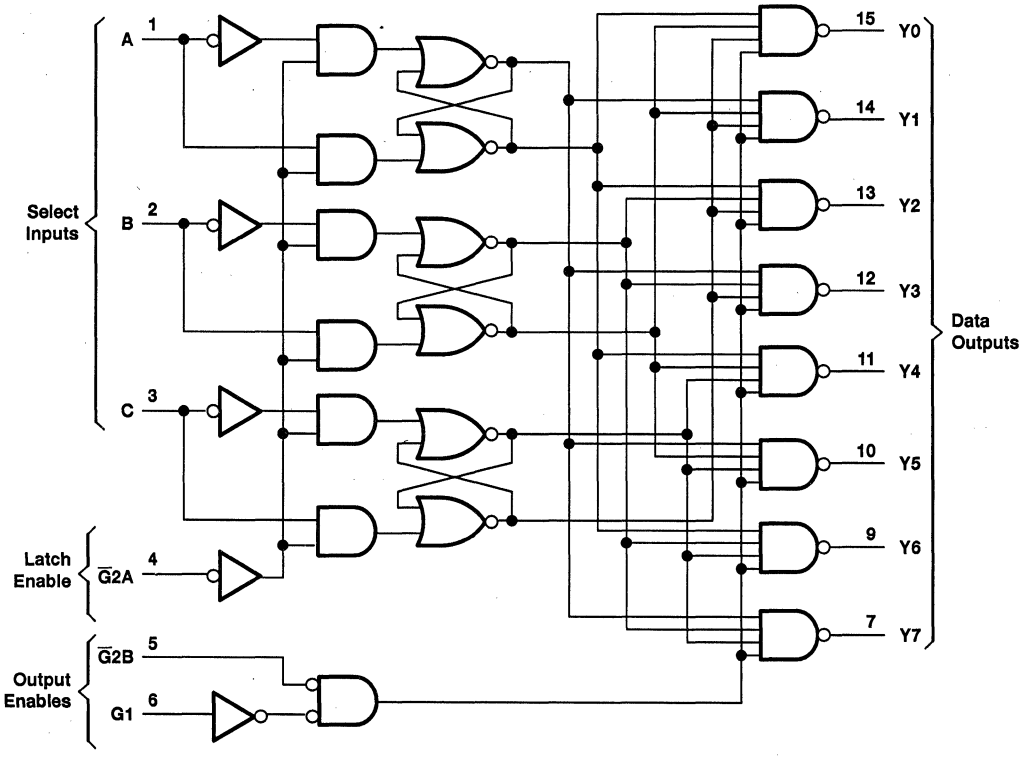
EPIC is a trademark of Texas Instruments Incorporated.

logic symbols (alternatives)†



† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V				pF
C_o	V_O = V_{CC} or GND	3.3 V				pF

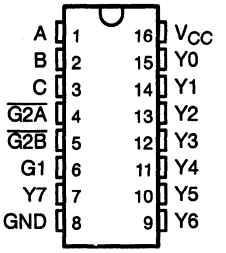
† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

SCAS291B – MARCH 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This 3-line to 8-line decoder/demultiplexer is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC138 is designed for high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, this decoder minimizes the effects of system decoding. When employed with high-speed memories utilizing a fast enable circuit, the delay times of this decoder and the enable time of the memory are usually less than the typical access time of the memory. This means that the effective system delay introduced by the decoder is negligible.

The conditions at the binary-select inputs and the three enable inputs select one of eight input lines. Two active-low enable inputs and one active-high enable input reduce the need for external gates or inverters when expanding. A 24-line decoder can be implemented without external inverters and a 32-line decoder requires only one inverter. An enable input can be used as a data input for demultiplexing applications.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

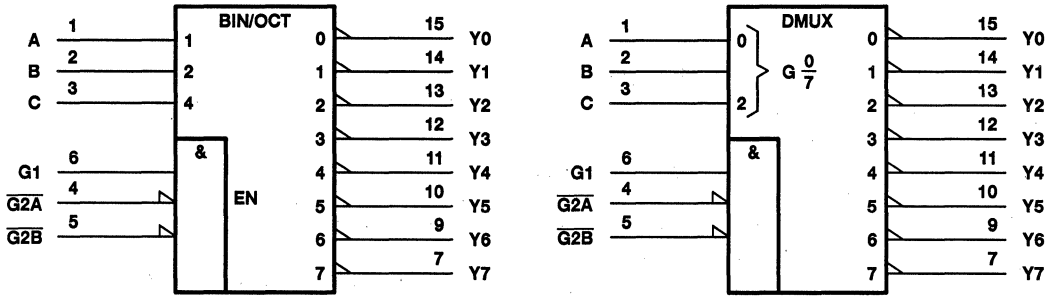
The SN74LVC138 is characterized for operation from −40°C to 85°C.

EPIC is a trademark of Texas Instruments Incorporated.

FUNCTION TABLE

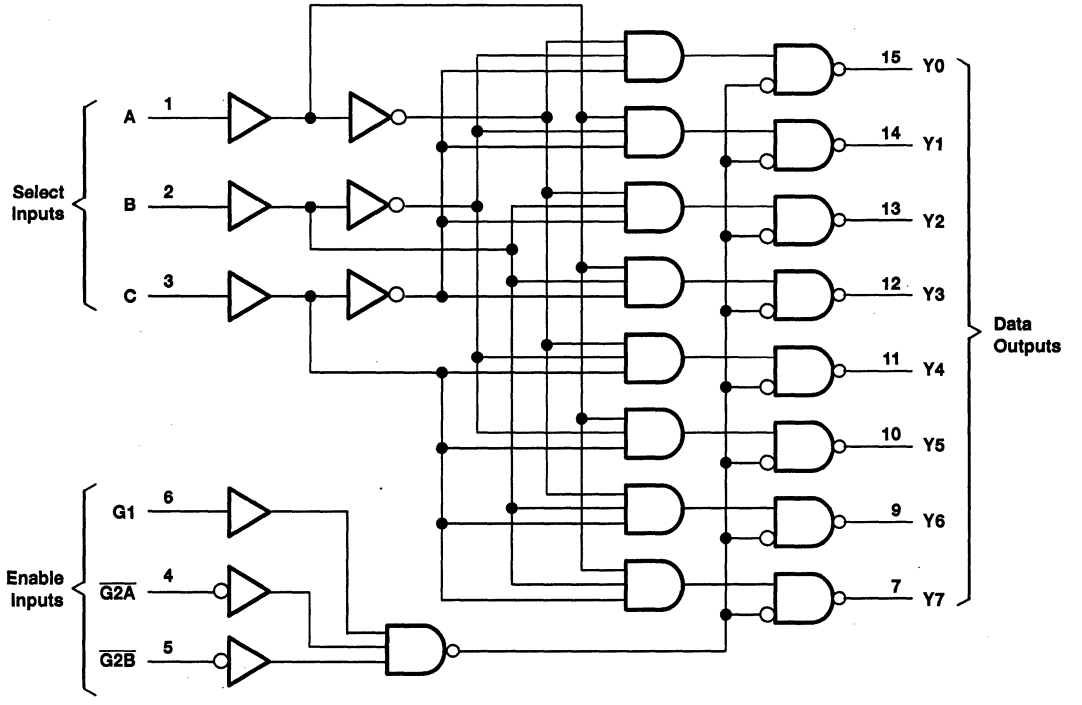
ENABLE INPUTS			SELECT INPUTS			OUTPUTS							
G1	$\overline{G2A}$	$\overline{G2B}$	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	H	X	X	X	X	H	H	H	H	H	H	H	H
X	X	H	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	H	L	H	H	H	H
H	L	L	H	L	L	H	H	H	H	L	H	H	H
H	L	L	H	L	H	H	H	H	H	H	L	H	H
H	L	L	H	H	L	H	H	H	H	H	H	L	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

logic symbols (alternatives)†



† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air): (see Note 3) D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 μA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	μA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_o	V_O = V_{CC} or GND	3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

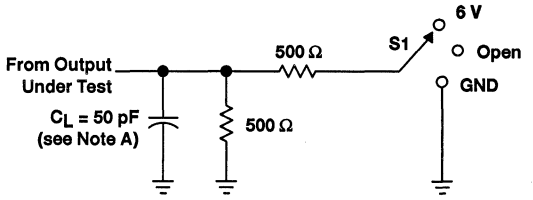
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B or C	Y	1	6.7		7.9	ns
	$\overline{G2A}$ or $\overline{G2B}$		1	6.5		7.4	
	G1		1	5.8		6.4	
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

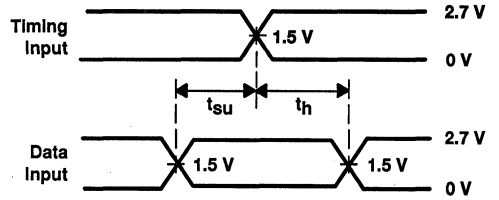
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	27	pF

PARAMETER MEASUREMENT INFORMATION

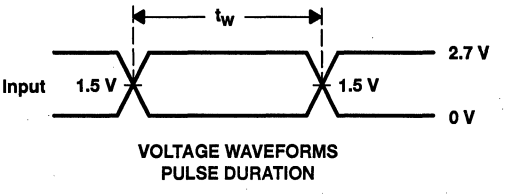


LOAD CIRCUIT

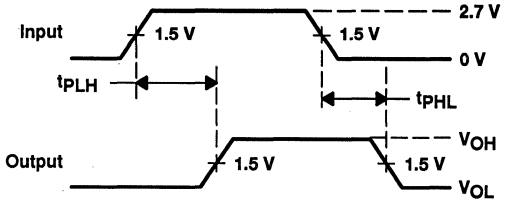
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



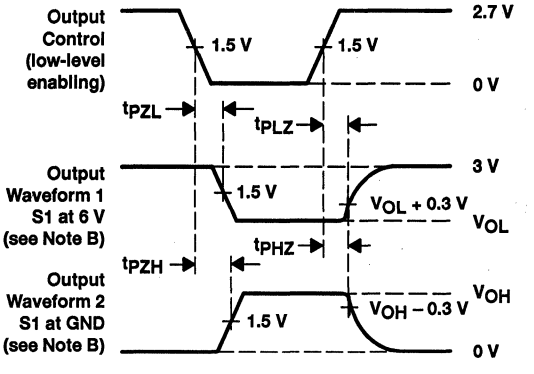
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

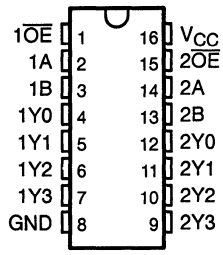
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

SCAS341A – MARCH 1994 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This dual 2-line to 4-line decoder/demultiplexer is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC139 is designed to be used in high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, this decoder can be used to minimize the effects of system decoding. When employed with high-speed memories utilizing a fast enable circuit, the delay times of this decoder and the enable time of the memory are usually less than the typical access time of the memory. This means that the effective system delay introduced by the decoder is negligible.

The device comprises two individual 2-line to 4-line decoders in a single package. The active-low output-enable ($\overline{OE}$) input can be used as a data line in demultiplexing applications. These decoders/demultiplexers feature fully buffered inputs, each of which represents only one normalized load to its driving circuit.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices in a mixed 3.3-V/5-V system environment.

The SN74LVC139 is characterized for operation from –40°C to 85°C.

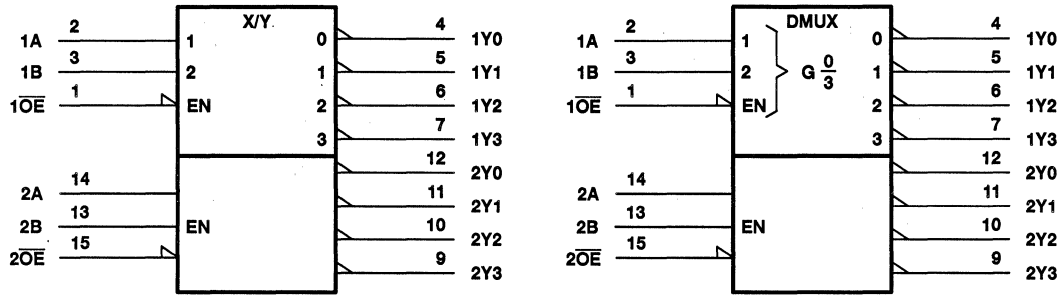
FUNCTION TABLE

INPUTS			OUTPUTS			
$\overline{OE}$	SELECT					
	B	A	Y0	Y1	Y2	Y3
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L

PRODUCT PREVIEW

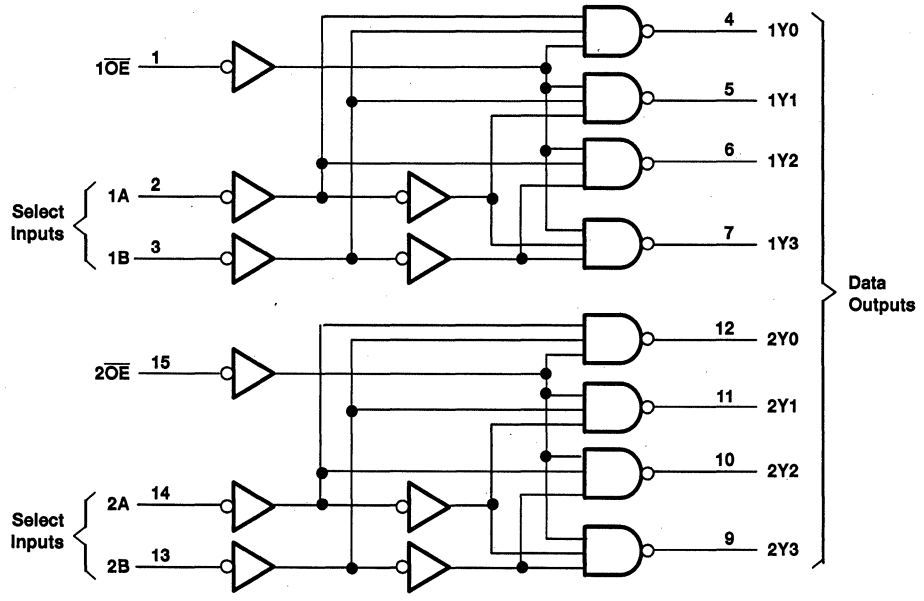
EPIC is a trademark of Texas Instruments Incorporated.

logic symbols (alternatives)†



† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V				pF
C_o	V_O = V_{CC} or GND		3.3 V				pF

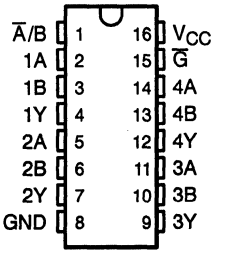
† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

SCAS292B – JANUARY 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-line to 1-line data selector/multiplexer is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC157 features a common strobe ($\overline{G}$) input. When the strobe is high, all outputs are low. When the strobe is low, a 4-bit word is selected from one of two sources and is routed to the four outputs. The device provides true data.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

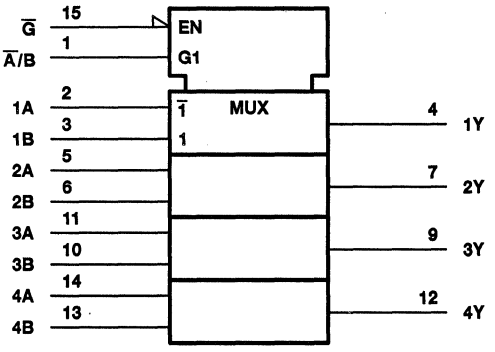
The SN74LVC157 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{G}$	$\overline{A}$/B	A	B	Y
H	X	X	X	L
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

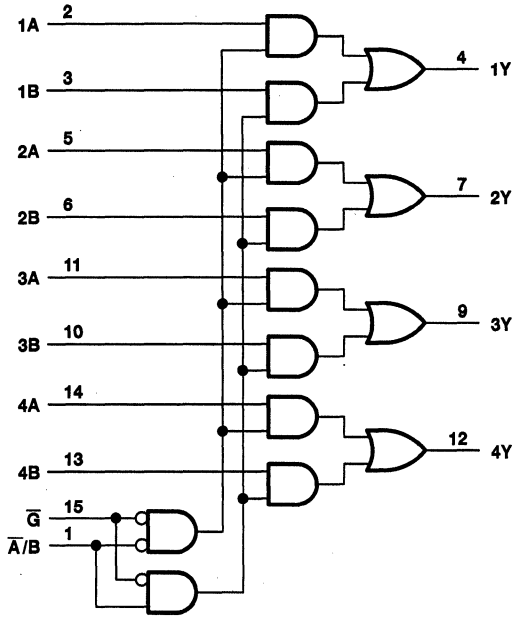
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = − 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = − 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

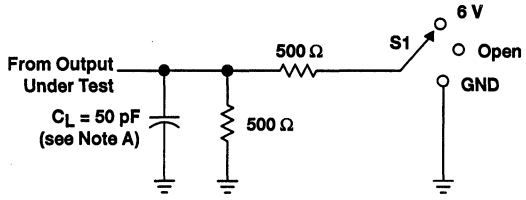
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	5.8		6.3	ns
	$\overline{A}$/B		1	7.5		8.5	
	$\overline{G}$		1	7.5		8.5	
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

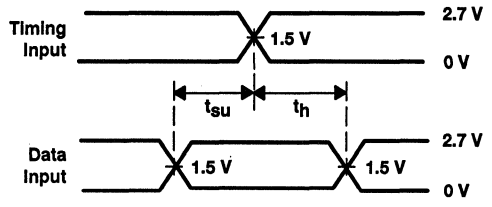
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	16	pF

PARAMETER MEASUREMENT INFORMATION

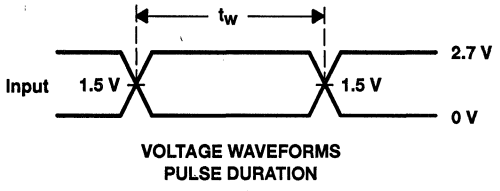


LOAD CIRCUIT

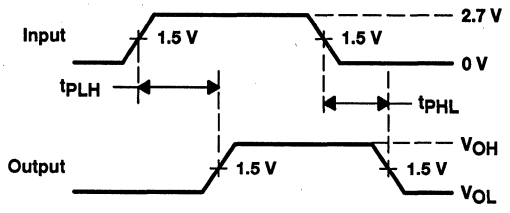
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



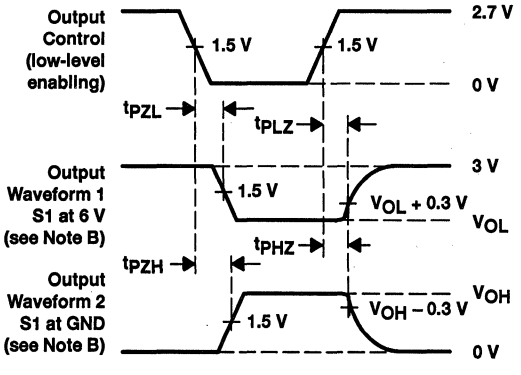
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

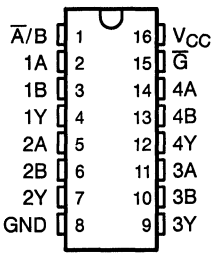
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

SCAS342A – MARCH 1994 – REVISED JULY 1995

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Inputs Accept Voltages to 5.5 V**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-line to 1-line data selector/multiplexer is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC158 features a direct strobe ($\overline{G}$) input. When the strobe is high, all outputs are high. When the strobe is low, a 4-bit word is selected from one of two sources and is routed to the four outputs. The SN74LVC158 provides inverted data.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices in a mixed 3.3-V/5-V system environment.

The SN74LVC158 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

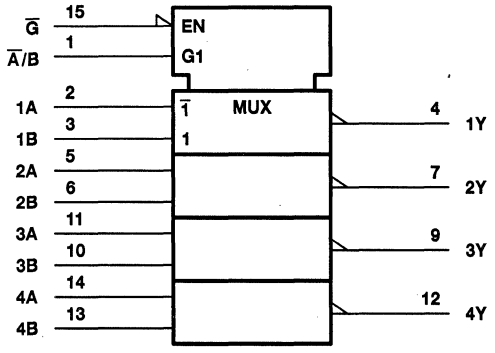
INPUTS				OUTPUT
$\overline{G}$	$\overline{A}$/B	A	B	Y
H	X	X	X	H
L	L	L	X	H
L	L	H	X	L
L	H	X	L	H
L	H	X	H	L

PRODUCT PREVIEW

EPIC is a trademark of Texas Instruments Incorporated.

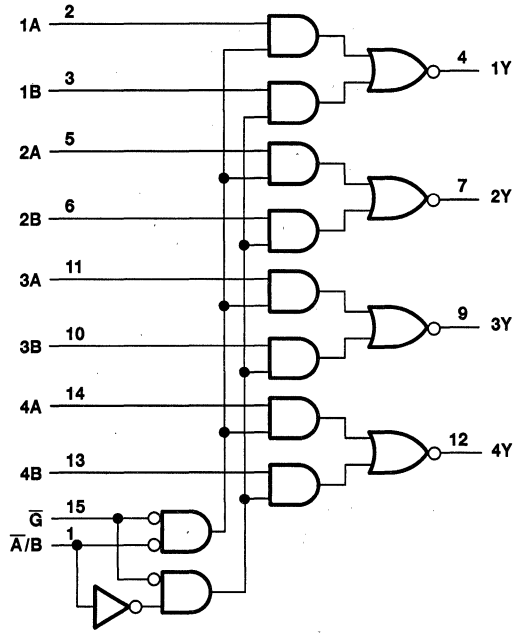
PRODUCT PREVIEW

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

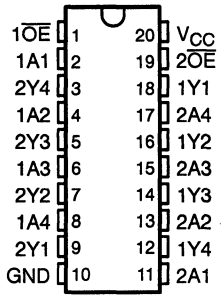
PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = −100 μA	MIN to MAX	V_{CC}−0.2			V
	I_{OH} = −12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = −24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 μA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	μA
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±10	μA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND	3.3 V				pF
C_o	V_O = V_{CC} or GND	3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC240 is designed specifically to improve the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The SN74LVC240 is organized as two 4-bit buffers/drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

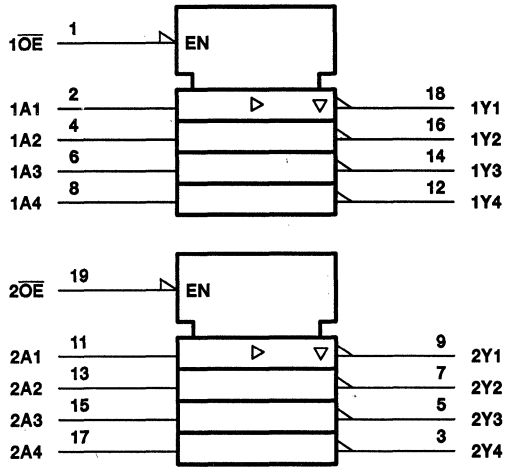
The SN74LVC240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

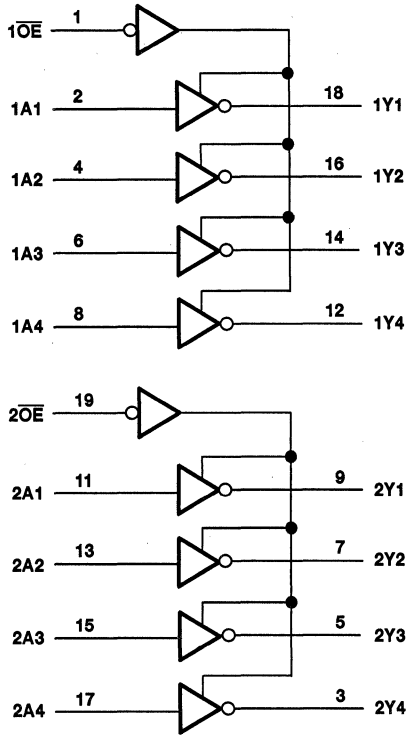
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Operating free-air temperature range, T_A ..... −40°C to 85°C
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		5.5		pF
C_o	V_O = V_{CC} or GND		3.3 V		5.8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

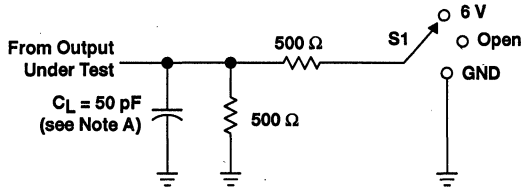
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	7.5		8.5	ns
t_{en}	$\overline{OE}$	Y	1.5	8		9	ns
t_{dis}	$\overline{OE}$	Y	1.5	7.5		8.5	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

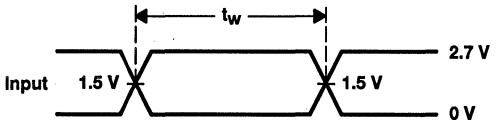
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	24	pF
		Outputs disabled		2.5	

PARAMETER MEASUREMENT INFORMATION

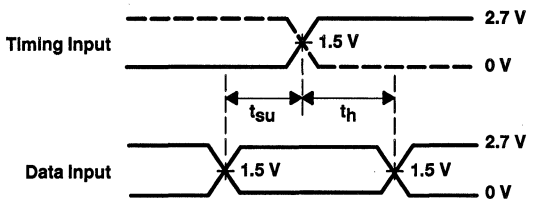


LOAD CIRCUIT FOR OUTPUTS

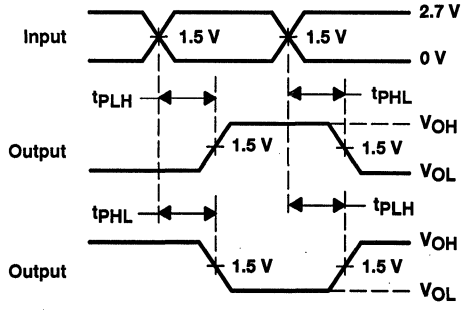
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



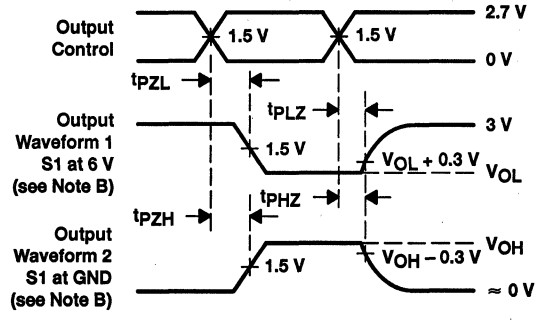
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



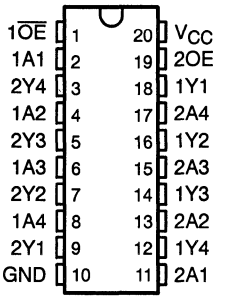
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/line driver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC241 is designed specifically to improve both the performance and density of 3-state memory-address drivers, clock drivers, and bus-oriented receivers and transmitters. Taken together with the 'LVC240 and 'LVC244, these devices provide the choice of selected combinations of inverting and noninverting outputs, symmetrical $\overline{OE}$ (active-low output-enable) inputs, and complementary OE and $\overline{OE}$ inputs.

The SN74LVC241 is organized as two 4-bit line drivers with separate output-enable ($1\overline{OE}$, 2OE) inputs. When $1\overline{OE}$ is low or 2OE is high, the device passes data from the A inputs to the Y outputs. When $1\overline{OE}$ is high or 2OE is low, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking or the current-sourcing capability of the driver.

The SN74LVC241 is characterized for operation from –40°C to 85°C.

FUNCTION TABLES

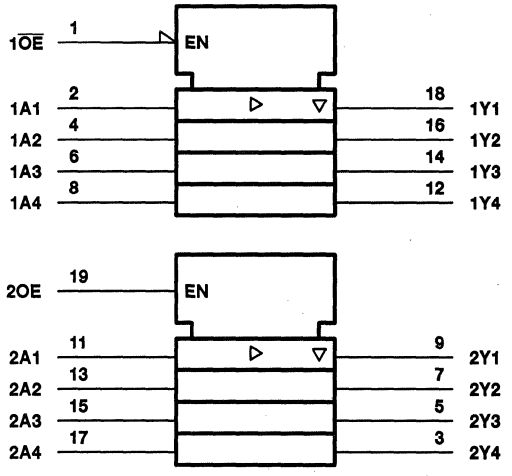
INPUTS		OUTPUT
$1\overline{OE}$	1A	1Y
L	H	H
L	L	L
H	X	Z

INPUTS		OUTPUT
2OE	2A	2Y
H	H	H
H	L	L
L	X	Z

PRODUCT PREVIEW

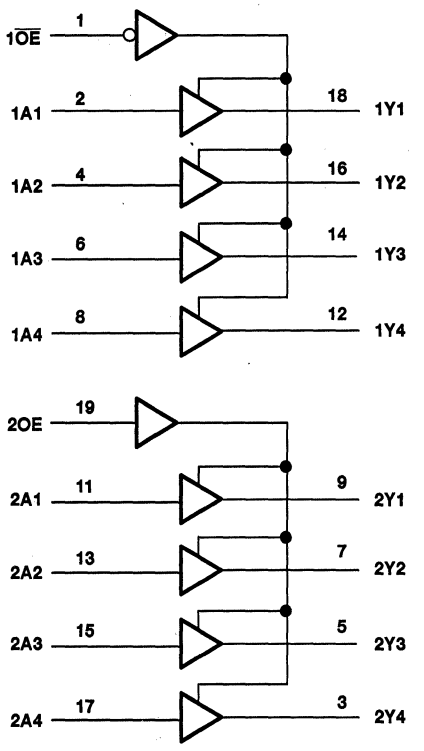
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

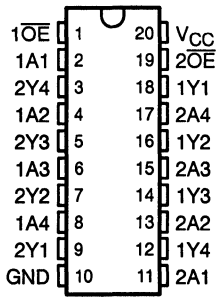
PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = –12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = –24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}	V_O = 5.5 V or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V				pF
C_o	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/line driver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC244A is organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

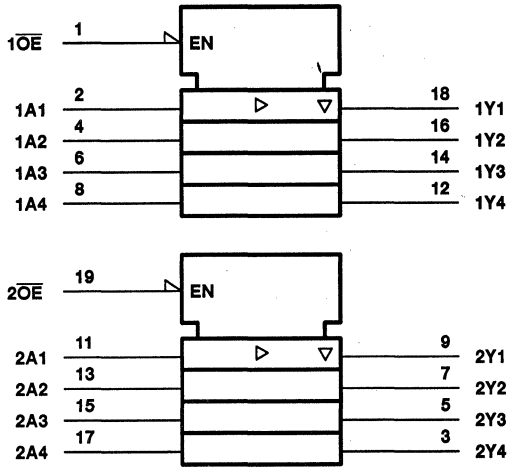
The SN74LVC244A is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

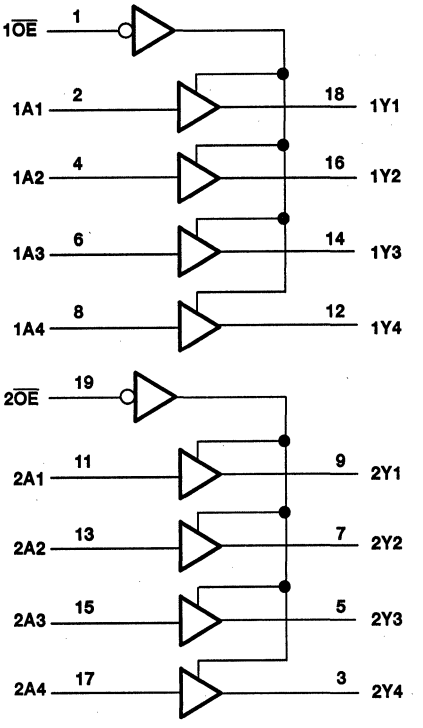
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... –50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... –65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{OZ}	V_O = 5.5 V or GND		3.6 V			±10	μA
	V_O = 3.6 V or 5.5 V		MIN to MAX			±50	
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		3.1		pF
C_o	V_O = V_{CC} or GND		3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

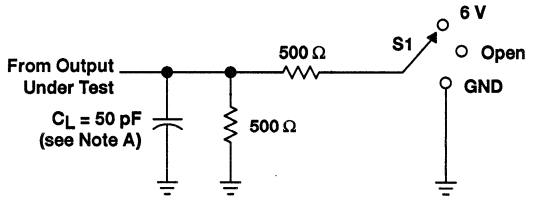
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	6.5		7.5	ns
t_{en}	$\overline{OE}$	Y	1.5	8		9	ns
t_{dis}	$\overline{OE}$	Y	1.5	7		8	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

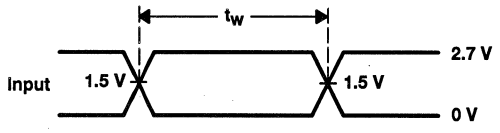
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	30	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

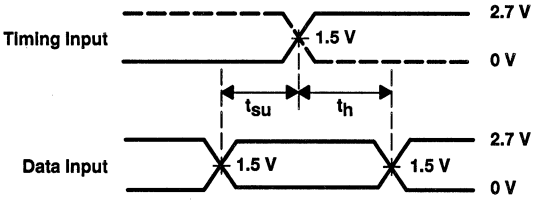


LOAD CIRCUIT FOR OUTPUTS

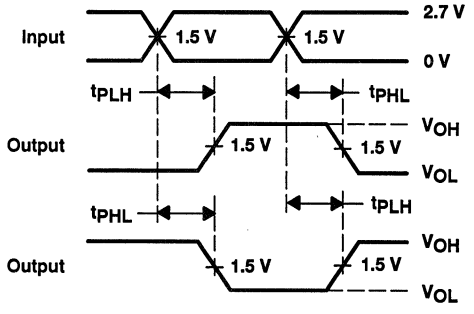
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



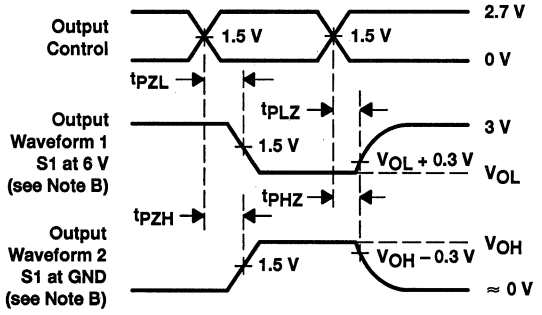
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



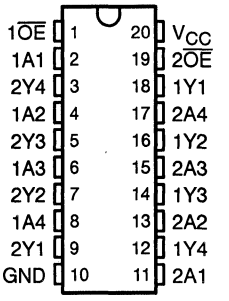
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-833C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Shrink Small-Outline (DB), Plastic Small-Outline (DW), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/line driver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVCH244 is organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

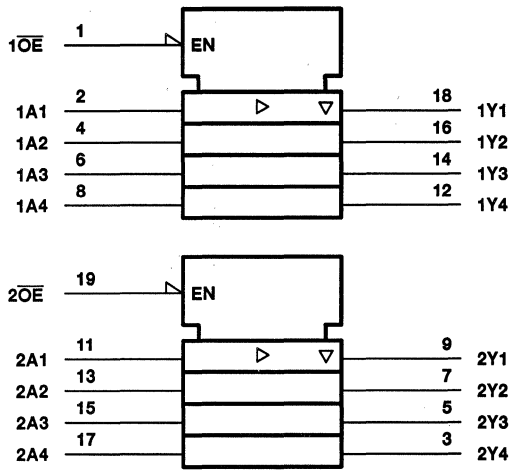
The SN74LVCH244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

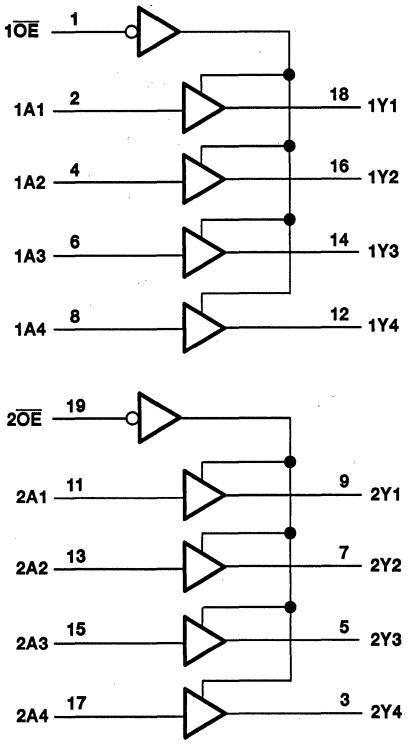
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage data inputs		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
$I_{I(hold)}$	V_I = 0.8 V	3 V	75			µA
	V_I = 2 V	3 V	–75			
	V_I = 0 to 3.6 V	3.6 V			±500	
I_{OZ}	V_O = V_{CC} or GND	MIN to MAX			±10	µA
	V_O = 3.6 V or 5.5 V				±50	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		3.1		pF
C_o	V_O = V_{CC} or GND	3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

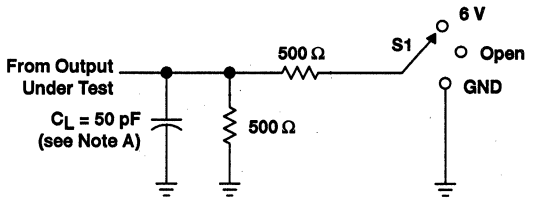
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1.5	6.5		7.5	ns
t_{en}	$\overline{OE}$	Y	1.5	8		9	ns
t_{dis}	$\overline{OE}$	Y	1.5	7		8	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

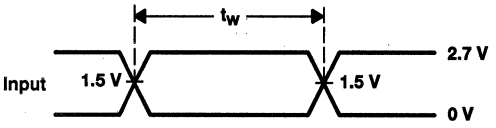
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	33	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

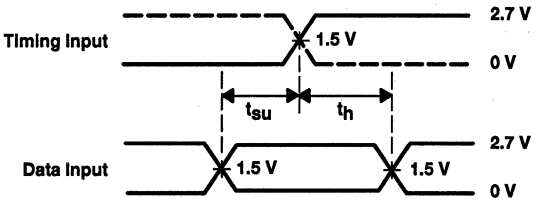


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

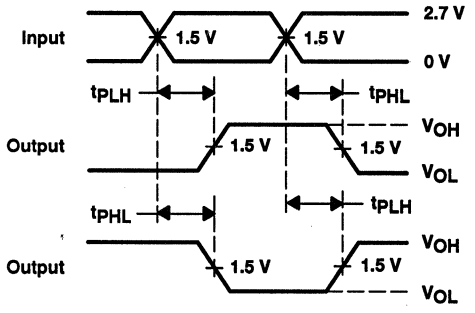
LOAD CIRCUIT FOR OUTPUTS



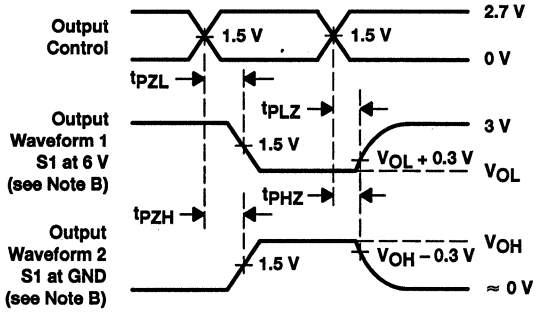
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



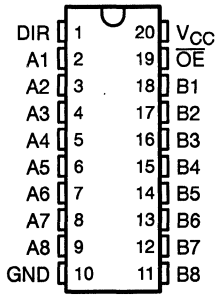
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC245A is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

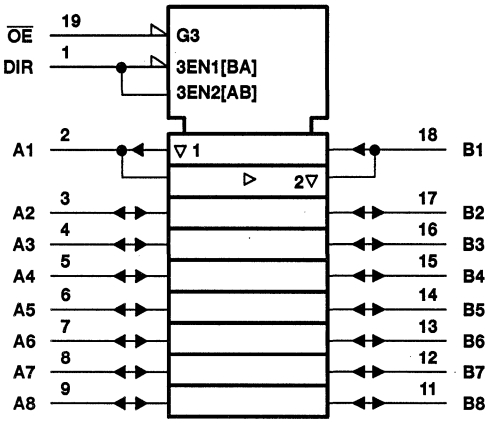
The SN74LVC245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

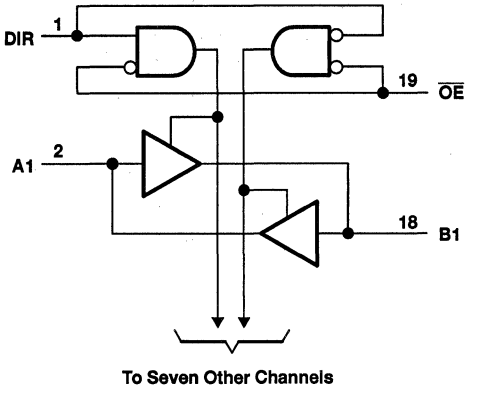
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
		I_{OH} = – 12 mA	2.7 V	2.2			
			3 V	2.4			
		I_{OH} = – 24 mA	3 V	2.2			
V_{OL}		I_{OL} = 100 µA	MIN to MAX			0.2	V
		I_{OL} = 12 mA	2.7 V			0.4	
		I_{OL} = 24 mA	3 V			0.55	
I_I		V_I = 5.5 V or GND	3.6 V			±5	µA
I_{OZ}§		V_O = 5.5 V or GND	3.6 V			±10	µA
		V_O = 3.6 V or 5.5 V	MIN to MAX			±50	
I_{CC}		V_I = V_{CC} or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND	3.3 V		3.3		pF
C_{io}	A or B ports	V_O = V_{CC} or GND	3.3 V		5.4		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

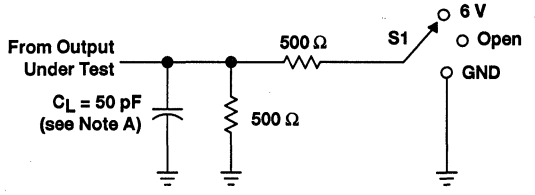
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	6.5		7.5	ns
t_{en}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
t_{dis}	$\overline{OE}$	A or B	1.5	7.5		8.5	ns
$t_{sk(o)}$¶				1			ns

¶ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

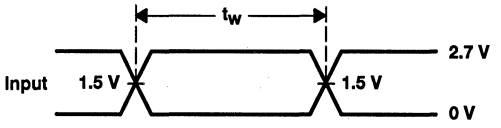
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	33	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

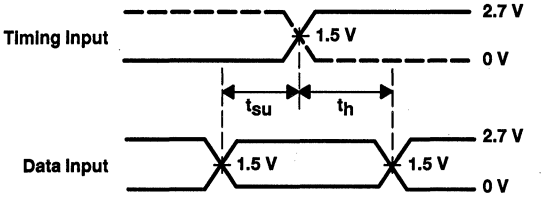


LOAD CIRCUIT FOR OUTPUTS

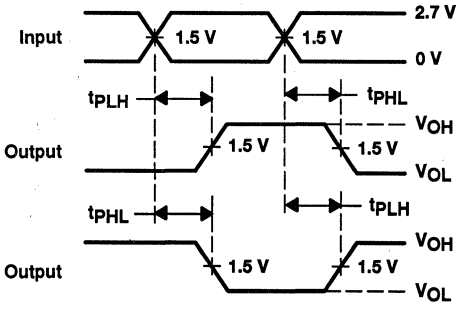
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



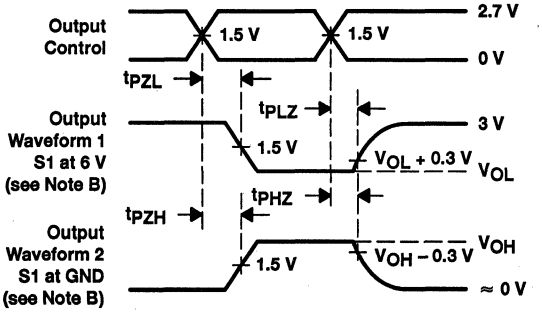
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



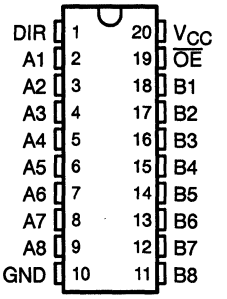
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-833C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltages With 3.3-V V_{CC})
- Bus Hold on Data Inputs Eliminates the Need for External Pullup Resistors
- Package Options Include Shrink Small-Outline (DB), Plastic Small-Outline (DW), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVCH245 is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

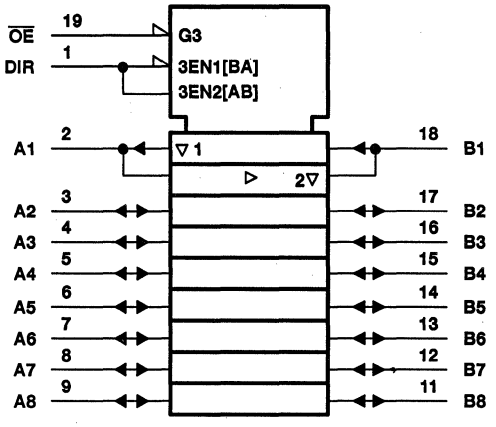
The SN74LVCH245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

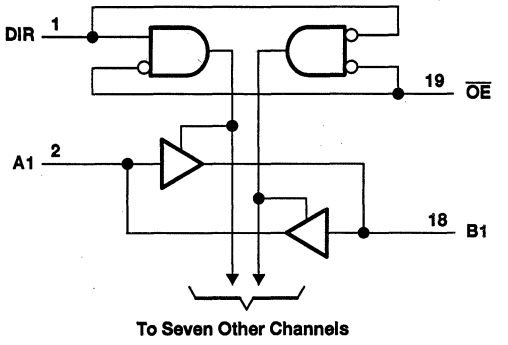
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage data inputs		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = – 12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = – 24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.8 V		3 V	75			µA
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		MIN to MAX			±10	µA
		V_O = 3.6 V or 5.5 V					±50	
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.3		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		5.4		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

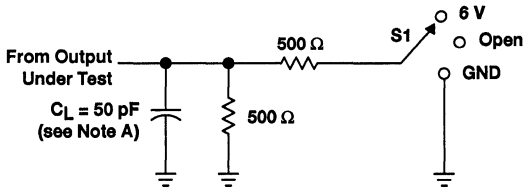
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	7		8	ns
t_{en}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
t_{dis}	$\overline{OE}$	A or B	1.5	7.5		8.5	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

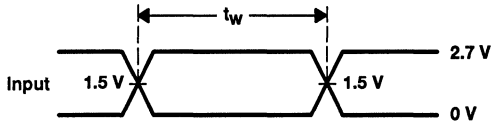
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	36	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

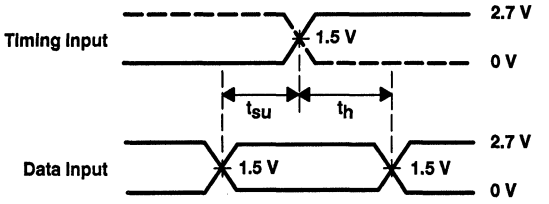


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

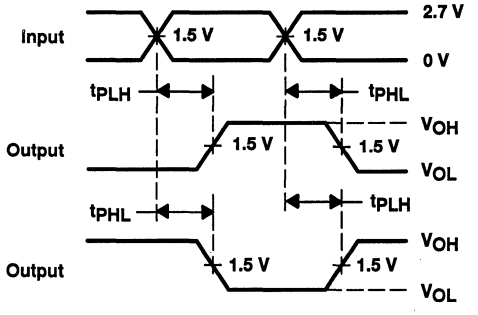
LOAD CIRCUIT FOR OUTPUTS



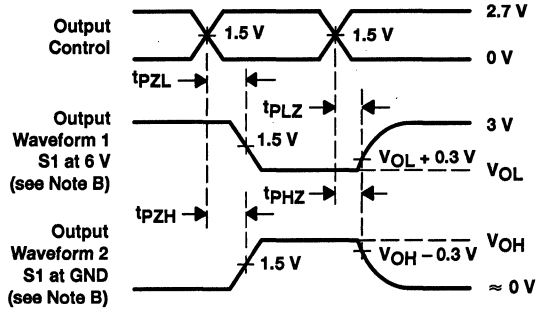
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



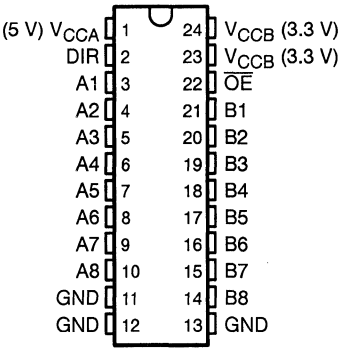
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- 3.3-V to 5-V Bidirectional Level Shifter
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 8-bit (octal) noninverting bus transceiver contains two separate supply rails; B port has V_{CCB}, which is set at 3.3 V, and A port has V_{CCA}, which is set to operate at 5 V. This allows for translation from a 3.3-V to a 5-V environment and vice versa.

The SN74LVC4245 is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

The SN74LVC4245 pinout allows the designer to switch to a normal all-3.3-V or all-5-V 20-pin '245 device without board re-layout. The designer uses the datapaths for pins 2 through 11 and 14 through 23 of the SN74LVC4245 to achieve the conventional '245 layout.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC4245 is characterized for operation from –40°C to 85°C.

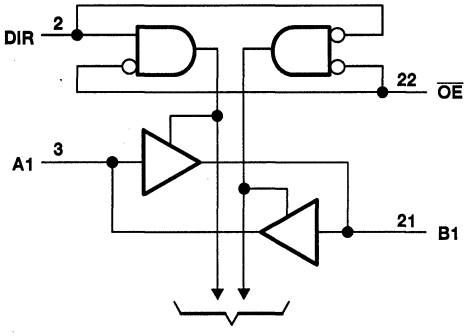
FUNCTION TABLE

INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

PRODUCT PREVIEW

EPIC is a trademark of Texas Instruments Incorporated.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range for V_{CCA} at 5 V (unless otherwise noted)†

Supply voltage range, V_{CCA}	−0.5 V to 6.5 V
Input voltage range, V_I (see Note 1)	−0.5 V to V_{CCA} + 0.5 V
Output voltage range, V_O (see Note 1)	−0.5 V to V_{CCA} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CCA}$)	−50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CCA}$)	±50 mA
Continuous output current, I_O (V_O = 0 to V_{CCA})	±50 mA
Continuous current through each V_{CCA} or GND	±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DB package	0.65 W
DW package	1.7 W
PW package	0.7 W
Storage temperature range, T_{stg}	−65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. This value is limited to 6 V maximum.
2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range for V_{CCB} at 3.3 V (unless otherwise noted)†

Supply voltage range, V_{CCB} ..... −0.5 V to 4.6 V
Input voltage range, V_I (except I/O ports) (see Note 3) ..... −0.5 V to 4.6 V
Input voltage range, V_I (I/O ports) (see Note 3) ..... −0.5 V to V_{CCB} + 0.5 V
Output voltage range, V_O (see Note 3) ..... −0.5 V to V_{CCB} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CCB}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CCB}) ..... ±50 mA
Continuous current through V_{CCB} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.
3. This value is limited to 4.6 V maximum.

recommended operating conditions for V_{CCA} at 5 V (see Note 4)

		MIN	MAX	UNIT
V_{CCA}	Supply voltage	4.5	5.5	V
V_{IH}	High-level input voltage	2		V
V_{IL}	Low-level input voltage		0.8	V
V_I	Input voltage	0	V_{CCA}	V
V_O	Output voltage	0	V_{CCA}	V
I_{OH}	High-level output current		−24	mA
I_{OL}	Low-level output current		24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_A	Operating free-air temperature	−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

recommended operating conditions for V_{CCB} at 3.3 V (see Note 4)

			MIN	MAX	UNIT
V_{CCB}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CCB} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CCB} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CCB}	V
V_O	Output voltage		0	V_{CCB}	V
I_{OH}	High-level output current	V_{CCB} = 2.7 V		−12	mA
		V_{CCB} = 3 V		−24	
I_{OL}	Low-level output current	V_{CCB} = 2.7 V		12	mA
		V_{CCB} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range for V_{CCA} = 5 V (unless otherwise noted) (see Note 5)

PARAMETER		TEST CONDITIONS		V_{CCA}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		4.5 V	4.3			V
				5.5 V	5.3			
		I_{OH} = –24 mA		4.5 V	3.7			
				5.5 V	4.7			
V_{OL}		I_{OL} = 100 µA		4.5 V			0.2	V
				5.5 V			0.2	
		I_{OL} = 24 mA		4.5 V			0.55	
				5.5 V			0.55	
I_I	Control inputs	$V_I = V_{CCA}$ or GND		5.5 V			5	µA
I_{OZ}‡	A or B ports	$V_O = V_{CCA}$ or GND		5.5 V				µA
I_{CC}		$V_I = V_{CCA}$ or GND,	I_O = 0	5.5 V				µA
ΔI_{CC}§		One input at 3.4 V,	Other inputs at V_{CCA} or GND					µA
C_i	Control inputs	$V_I = V_{CCA}$ or GND		5 V				pF
C_{io}	A or B ports	$V_O = V_{CCA}$ or GND		5 V				pF

† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or the corresponding V_{CC}.
NOTE 5: V_{CCB} = 2.7 V to 3.6 V

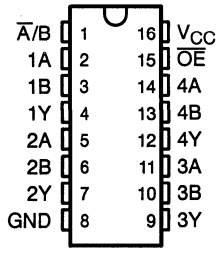
electrical characteristics over recommended operating free-air temperature range for V_{CCB} = 3.3 V (unless otherwise noted) (see Note 6)

PARAMETER		TEST CONDITIONS		V_{CCB}¶	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	$V_I = V_{CCB}$ or GND		3.6 V			5	µA
I_{OZ}‡		$V_O = V_{CCB}$ or GND		3.6 V				µA
I_{CC}		$V_I = V_{CCB}$ or GND,	I_O = 0	3.6 V				µA
ΔI_{CC}§		One input at V_{CCB} – 0.6 V,	Other inputs at V_{CCB} or GND	2.7 V to 3.6 V				µA
C_i	Control inputs	$V_I = V_{CCB}$ or GND		3.3 V				pF
C_{io}	A or B ports	$V_O = V_{CCB}$ or GND		3.3 V				pF

† All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or the corresponding V_{CC}.
¶ For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
NOTE 6: V_{CCA} = 5 V ± 0.5 V

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-line to 1-line data selector/multiplexer is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC257 is designed to multiplex signals from 4-bit data sources to 4-output data lines in bus-organized systems. The 3-state outputs do not load the data lines when the output enable ($\overline{OE}$) input is at a high logic level.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

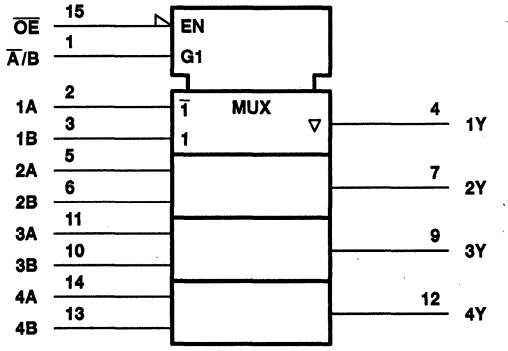
The SN74LVC257 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	A/B	A	B	Y
H	X	X	X	Z
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

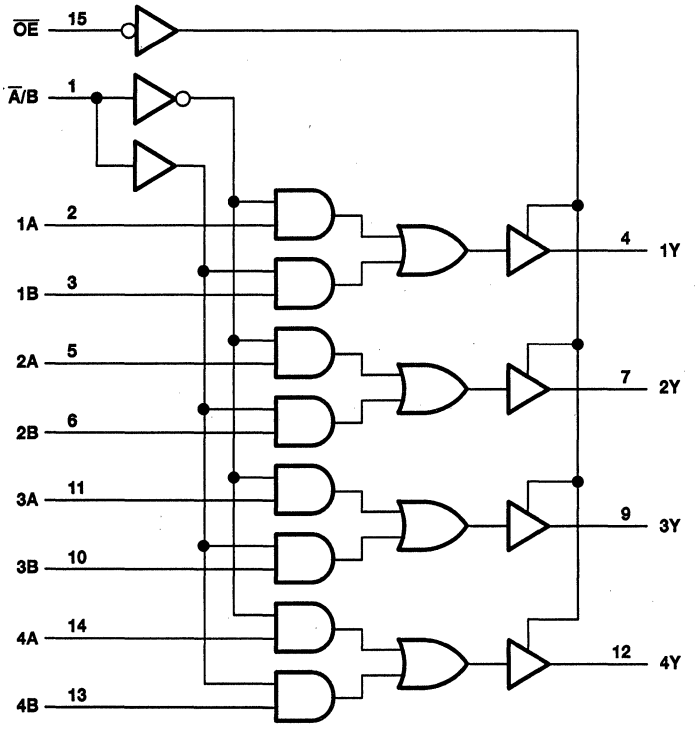
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND	MIN to MAX			±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		5		pF
C_o	V_O = V_{CC} or GND	3.3 V		5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

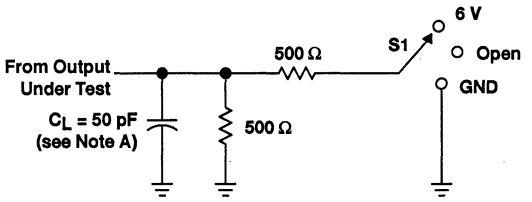
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	1	7		8	ns
	$\overline{A}$/B		1	8		9	
t_{en}	$\overline{OE}$	Y	1	8		9	ns
t_{dis}	$\overline{OE}$	Y	1	6		6.5	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

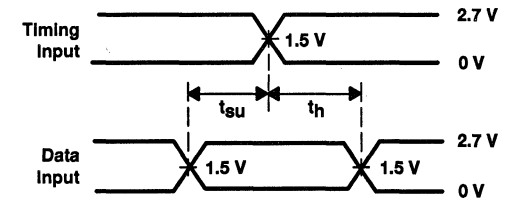
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	15.5	pF

PARAMETER MEASUREMENT INFORMATION

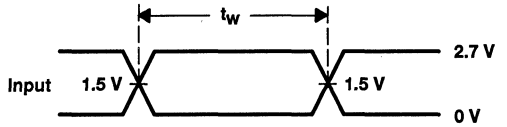


LOAD CIRCUIT

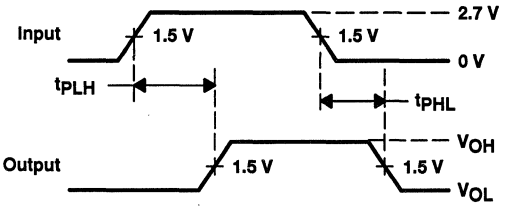
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



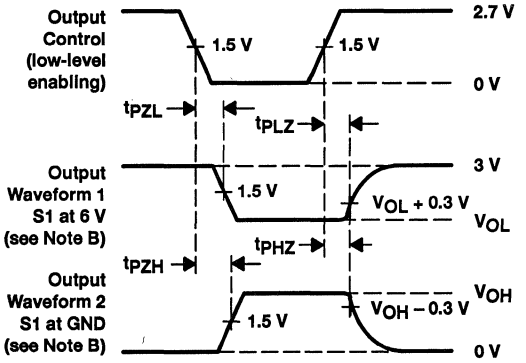
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



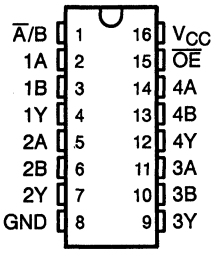
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages
- Inputs Accept Voltages to 5.5 V

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-line to 1-line data selector/multiplexer is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC258 is designed to multiplex signals from 4-bit data sources to 4-output data lines in bus-organized systems. The 3-state outputs do not load the data lines when the output enable ($\overline{OE}$) input is at a high logic level.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC258 is characterized for operation from –40°C to 85°C.

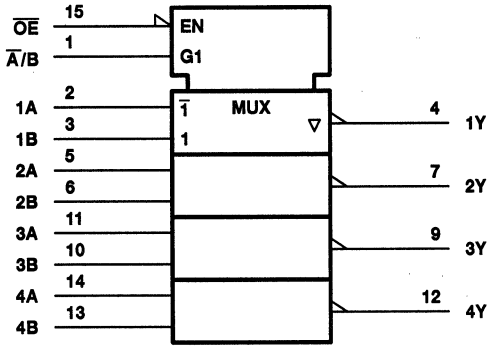
FUNCTION TABLE

INPUTS				OUTPUT
$\overline{OE}$	$\overline{A}$/B	A	B	Y
H	X	X	X	Z
L	L	L	X	H
L	L	H	X	L
L	H	X	L	H
L	H	X	H	L

PRODUCT PREVIEW

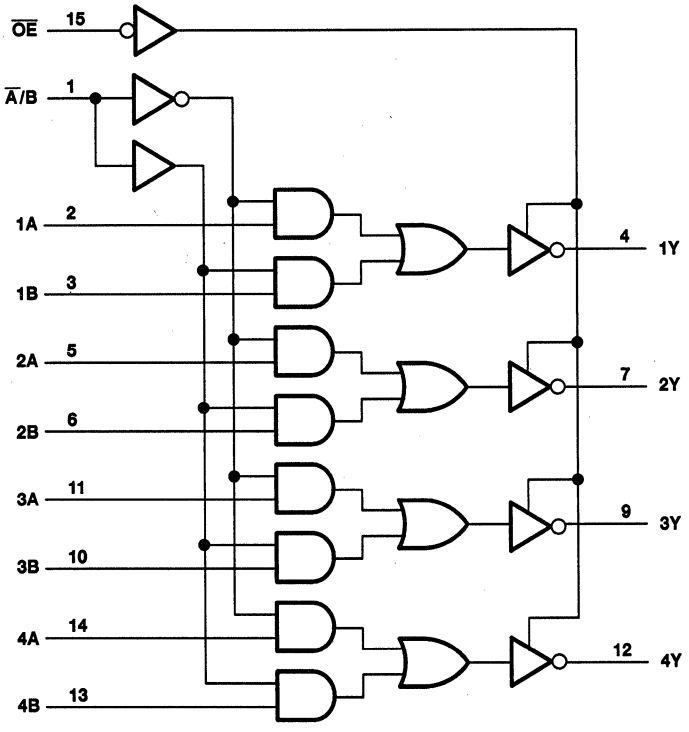
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCT PREVIEW

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state
or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high
or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

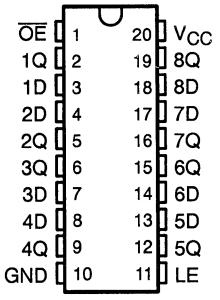
PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = V_{CC} or GND	3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND	MIN to MAX			±10	µA
	V_O = 3.6 V to 5.5 V				±50	
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V				pF
C_o	V_O = V_{CC} or GND	3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal transparent D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

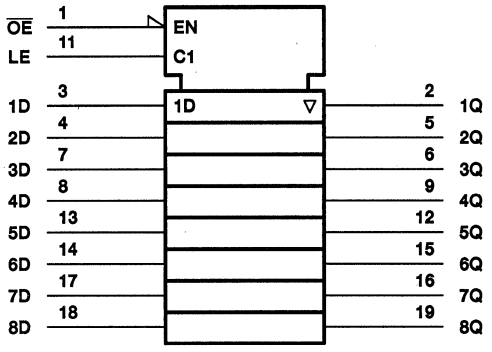
The SN74LVC373A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each latch)

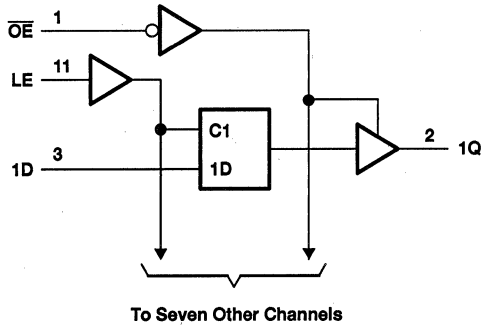
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND		MIN to MAX			±10	µA
	V_O = 3.6 V or 5.5 V					±50	
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	V_O = V_{CC} or GND		3.3 V		3.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3.3		3.3		ns
t_{su}	Setup time, data before LE↓	2		2		ns
t_h	Hold time, data after LE↓	1.5		1.5		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

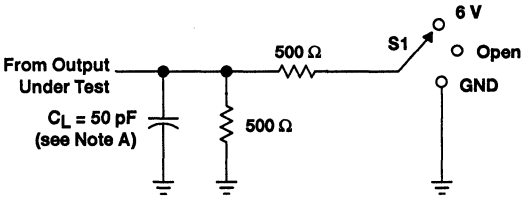
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1.5	7.5		8.5	ns
	LE		2	8.5		9.5	
t_{en}	$\overline{OE}$	Q	1.5	7.5		8.5	ns
t_{dis}	$\overline{OE}$	Q	1.5	7		8	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

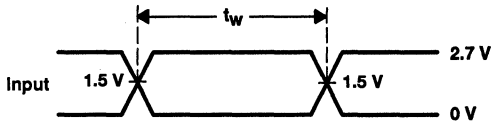
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 50 pF, f = 10 MHz	20	pF
		Outputs disabled		3.5	

PARAMETER MEASUREMENT INFORMATION

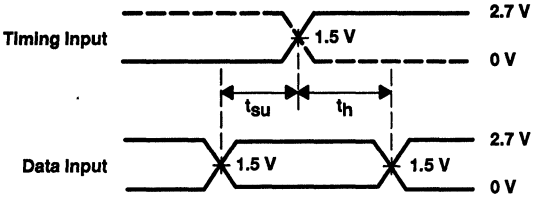


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

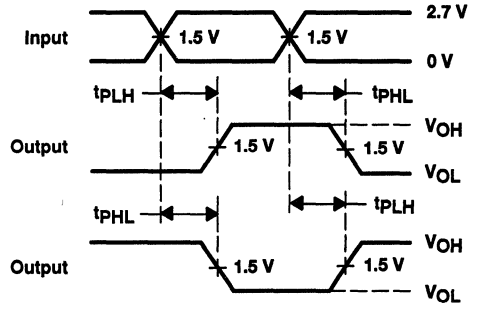
LOAD CIRCUIT FOR OUTPUTS



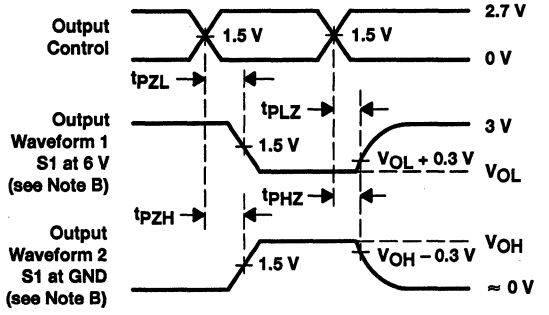
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



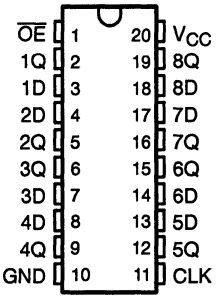
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal edge-triggered D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC374A features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, input/output (I/O) ports, bidirectional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

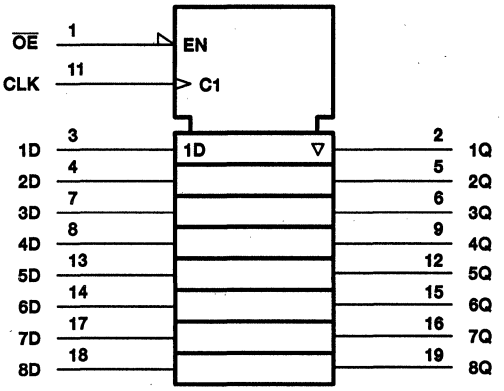
The SN74LVC374A is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

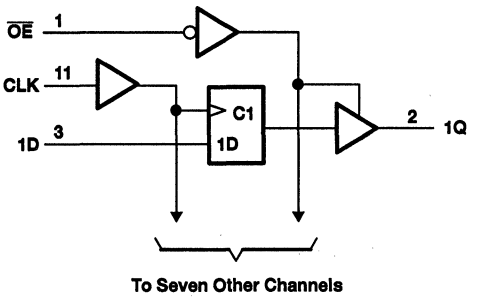
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high impedance state or power off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	μA
I_{OZ}	V_O = V_{CC} or GND		MIN to MAX			±10	μA
	V_O = 3.6 V or 5.5 V					±50	
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	V_O = V_{CC} or GND		3.3 V		3.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	100	0	80	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.5		1.5		ns
t_h	Hold time, data after CLK↑	1.5		1.5		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

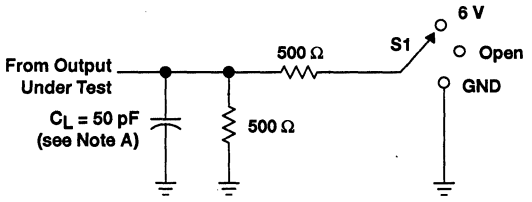
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			100		80		MHz
t_{pd}	CLK	Q	1.5	8.5		9.5	ns
t_{en}	$\overline{OE}$	Q	1.5	8.5		9.5	ns
t_{dis}	$\overline{OE}$	Q	1.5	7		8	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

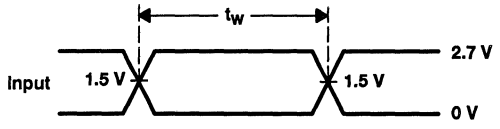
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 50 pF, f = 10 MHz	18	pF
		Outputs disabled		9	

PARAMETER MEASUREMENT INFORMATION

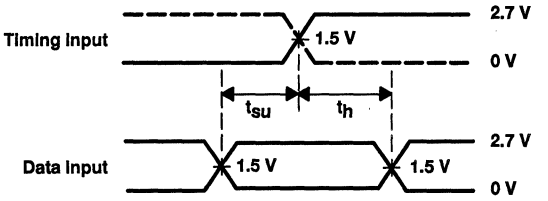


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

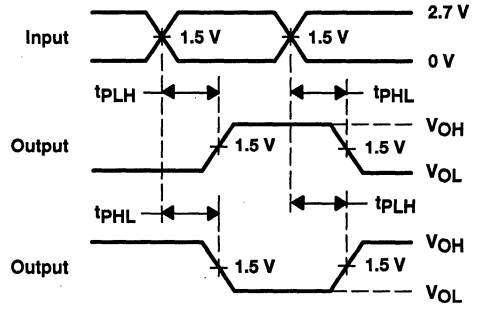
LOAD CIRCUIT FOR OUTPUTS



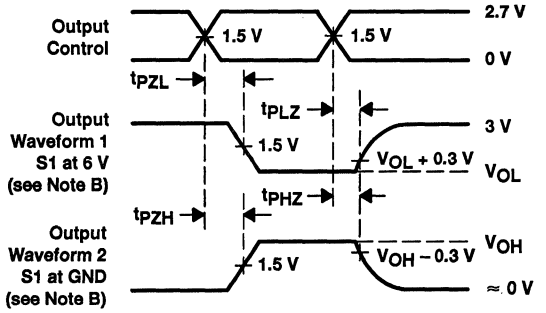
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



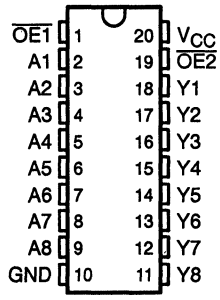
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC540 is ideal for driving bus lines or buffer memory address registers. The device features inputs and outputs on opposite sides of the package that facilitate printed-circuit-board layout.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

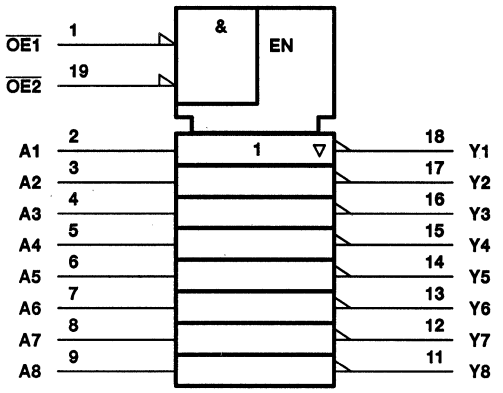
The SN74LVC540 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z

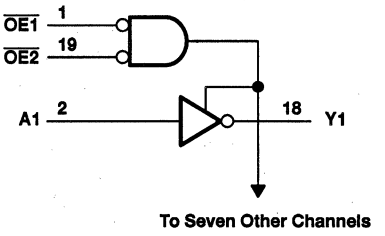
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7	2.2			
		3	2.4			
	I_{OH} = – 24 mA	3	2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7			0.4	
	I_{OL} = 24 mA	3			0.55	
I_I	V_I = 5.5 V or GND	3.6			±5	µA
I_{OZ}	V_O = V_{CC} or GND	3.6			±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3		5.5		pF
C_o	V_O = V_{CC} or GND	3.3		5.8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

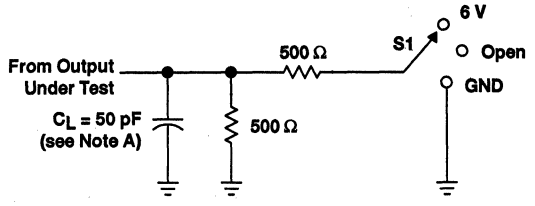
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	7.5		8.5	ns
t_{en}	$\overline{OE}$	Y	1.5	8		9	ns
t_{dis}	$\overline{OE}$	Y	1.5	7.5		8.5	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

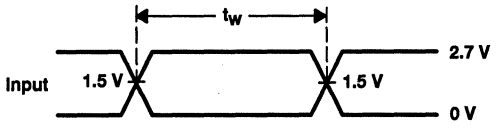
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	27	pF
		Outputs disabled		2.4	

PARAMETER MEASUREMENT INFORMATION

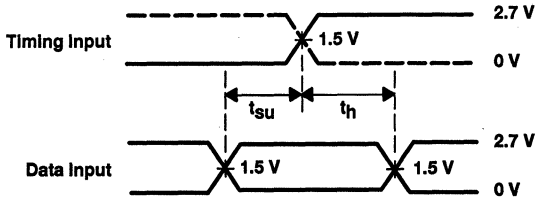


LOAD CIRCUIT FOR OUTPUTS

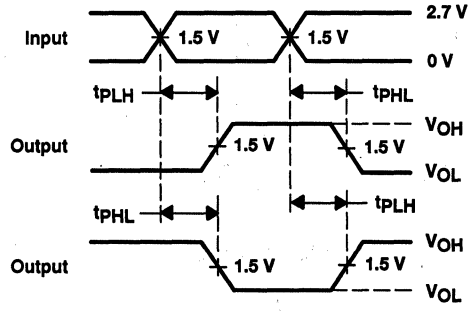
TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 6 V GND



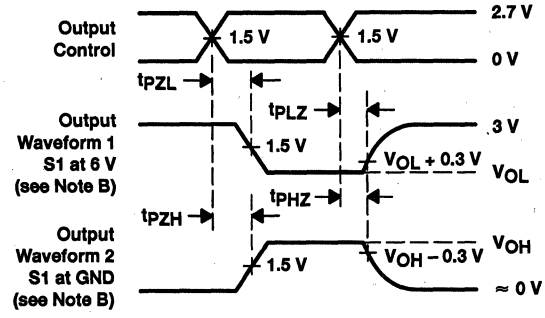
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



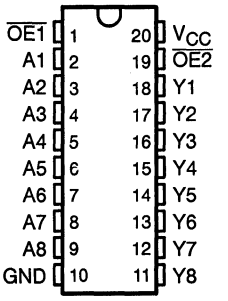
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC541 is ideal for driving bus lines or buffering memory address registers. The device features inputs and outputs on opposite sides of the package to facilitate printed-circuit-board layout.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all eight outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

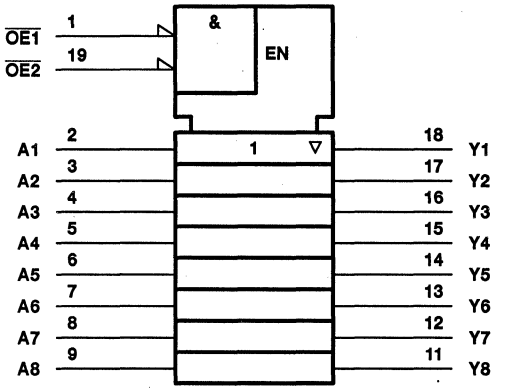
The SN74LVC541 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

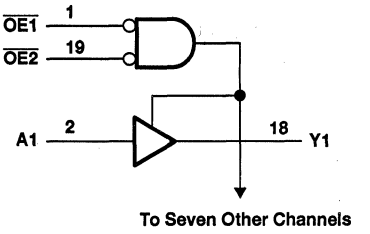
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7	2.2			
			3	2.4			
	I_{OH} = – 24 mA		3	2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7			0.4	
	I_{OL} = 24 mA		3			0.55	
I_I	V_I = 5.5 V or GND		3.6			±5	µA
I_{OZ}	V_O = V_{CC} or GND		3.6			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3		5.5		pF
C_o	V_O = V_{CC} or GND		3.3		5.8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

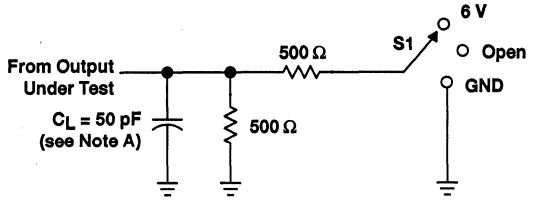
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	7		8	ns
t_{en}	$\overline{OE}$	Y	1.5	8		9	ns
t_{dis}	$\overline{OE}$	Y	1.5	7.5		8.5	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

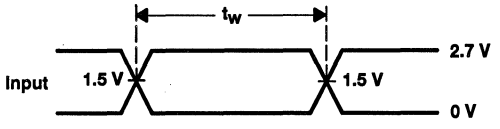
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	26.7	pF
		Outputs disabled		1.8	

PARAMETER MEASUREMENT INFORMATION

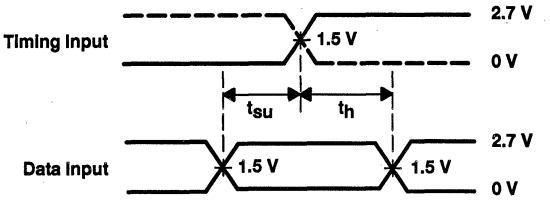


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

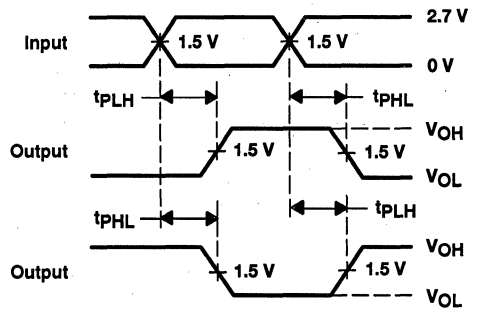
LOAD CIRCUIT FOR OUTPUTS



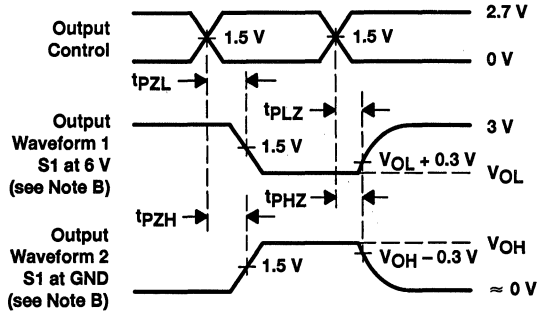
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



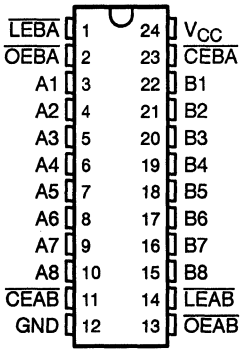
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal registered transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC543 contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ places the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow for B to A is similar to that of A to B but uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC543 is characterized for operation from −40°C to 85°C.

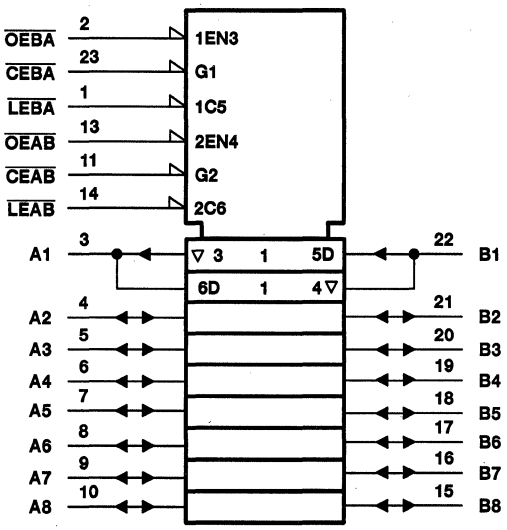
FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

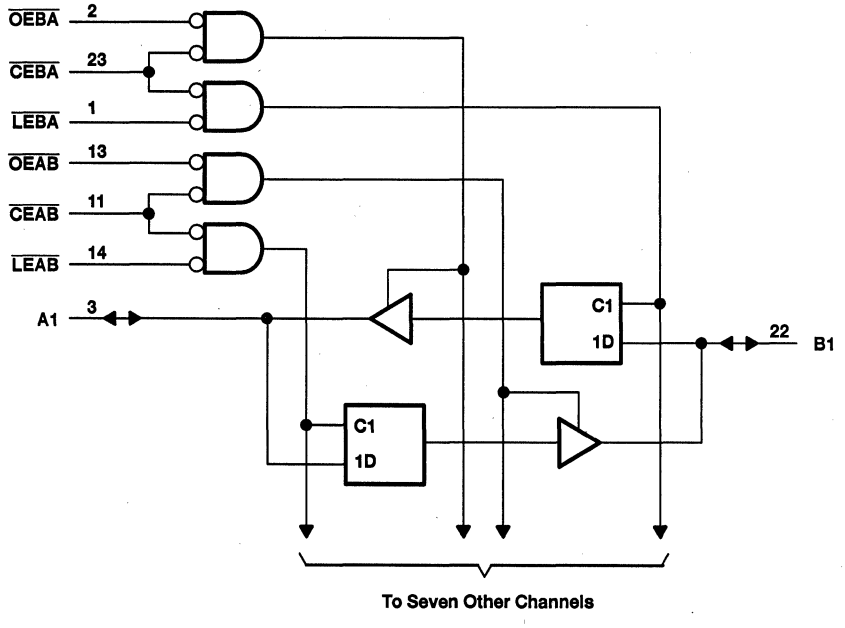
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage	Control inputs	0	5.5	V
		Data inputs	0	V_{CC}	
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = – 12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = – 24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.6		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.2		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration	4		4		ns
t_{su}	Setup time, data before $\overline{LE}$↑ or $\overline{CE}$↑	1.5		1.5		ns
t_h	Hold time, data after $\overline{LE}$↑ or $\overline{CE}$↑	2.5		2.5		ns

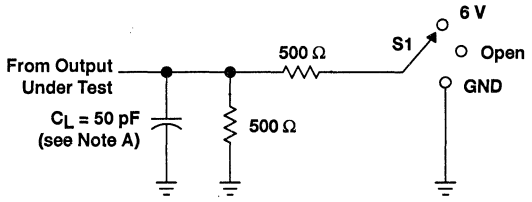
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	8		9	ns
	$\overline{LE}$		1.5	9.5		10.5	
t_{en}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
	$\overline{CE}$		1.5	9		10	
t_{dis}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
	$\overline{CE}$		1.5	9		10	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

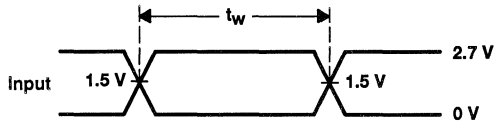
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	32	pF
		Outputs disabled		4.6	

PARAMETER MEASUREMENT INFORMATION

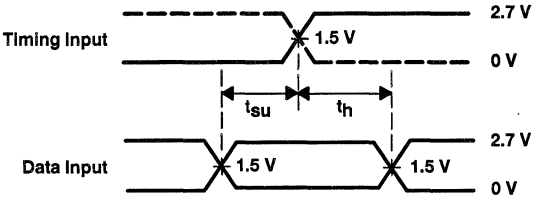


LOAD CIRCUIT FOR OUTPUTS

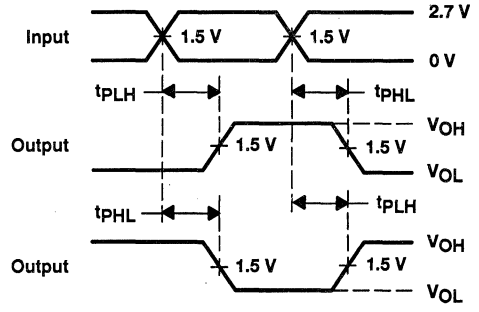
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



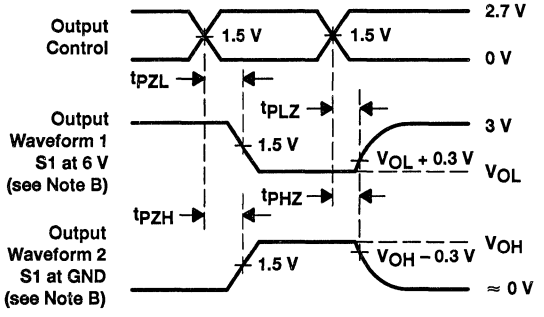
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



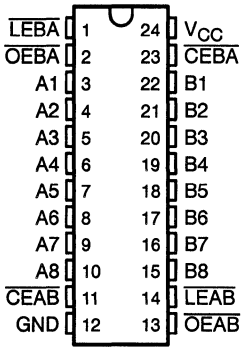
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal registered transceiver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC544 contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ places the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the inverted data present at the output of the A latches. Data flow from B to A is similar to A to B, but requires using the $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC544 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

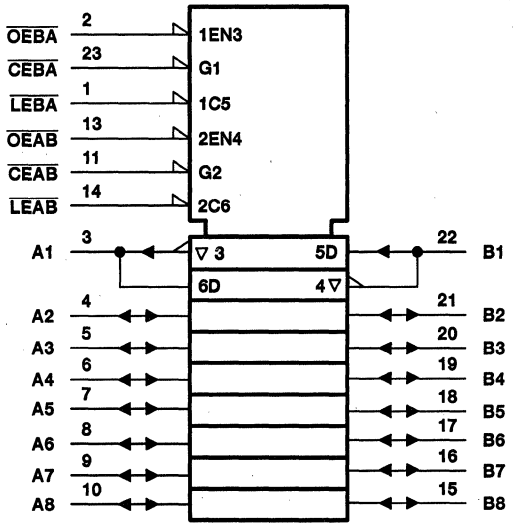
INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
L	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	H
L	L	L	H	L

† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

PRODUCT PREVIEW

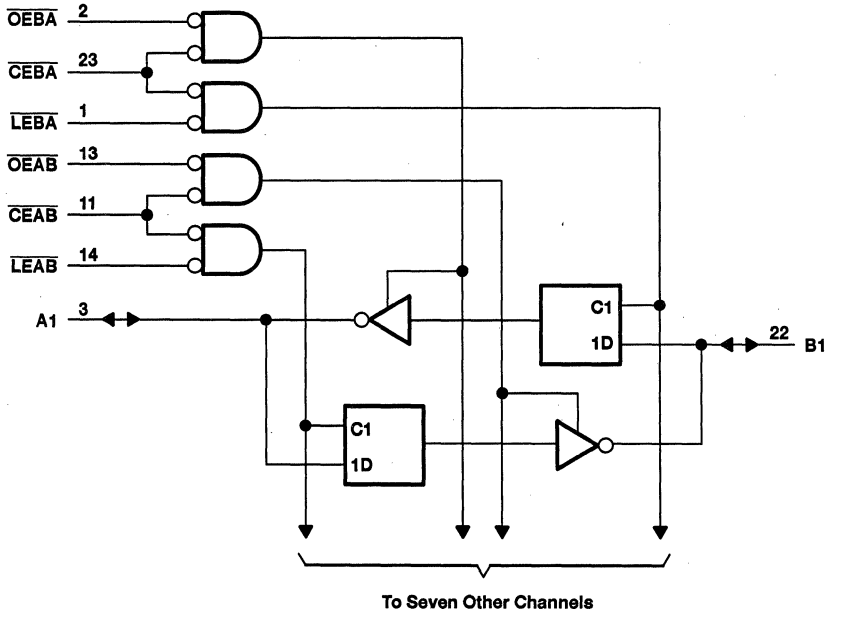
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high impedance state or power off state,
V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

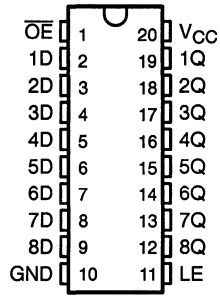
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = – 12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = – 24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	μA
I_{OZ}§		V_O = 5.5 V or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

PRODUCT PREVIEW

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal transparent D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC573A features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, input/output (I/O) ports, bidirectional bus drivers, and working registers.

While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without the need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

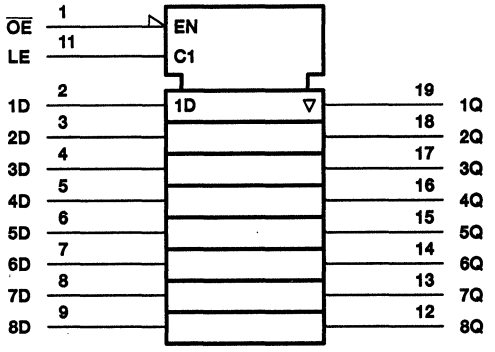
The SN74LVC573A is characterized for operation from –40°C to 85°C.

EPIC is a trademark of Texas Instruments Incorporated.

FUNCTION TABLE
(each latch)

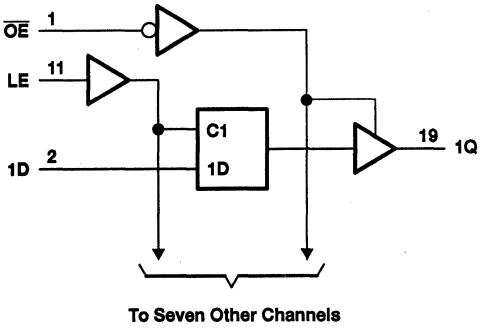
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high impedance state or power off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 3)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND		MIN to MAX			±10	µA
	V_O = 3.6 V or 5.5 V					±50	
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	V_O = V_{CC} or GND		3.3 V		3.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	3.3		3.3		ns
t_{su}	Setup time, data before LE↓	2		2		ns
t_h	Hold time, data after LE↓	1.5		1.5		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

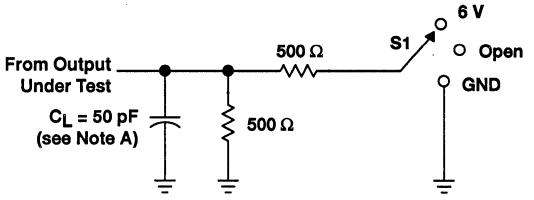
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1.5	7.5		8.5	ns
	LE		2	8.5		9.5	
t_{en}	$\overline{OE}$	Q	1.5	7.5		8.5	ns
t_{dis}	$\overline{OE}$	Q	1.5	7		8	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

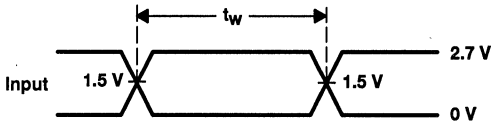
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 50 pF, f = 10 MHz	20	pF
		Outputs disabled		3.5	

PARAMETER MEASUREMENT INFORMATION

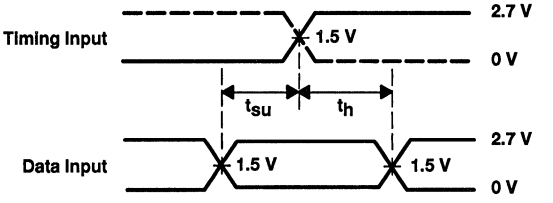


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

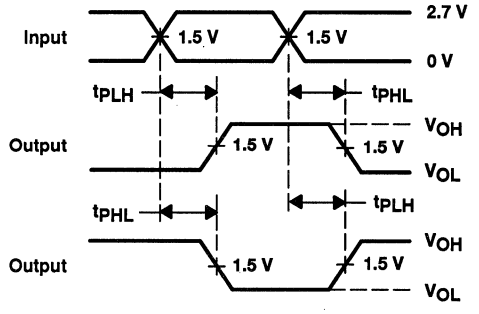
LOAD CIRCUIT FOR OUTPUTS



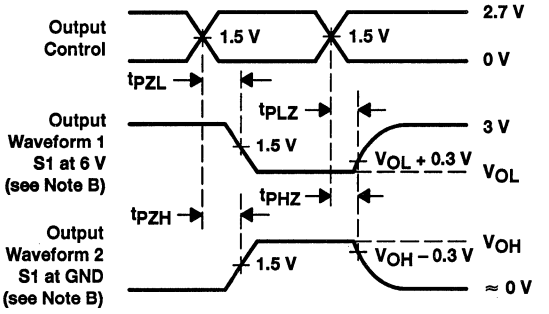
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



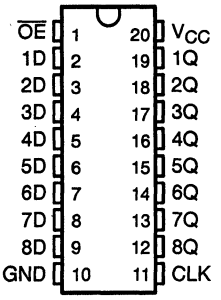
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal edge-triggered D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC574A features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

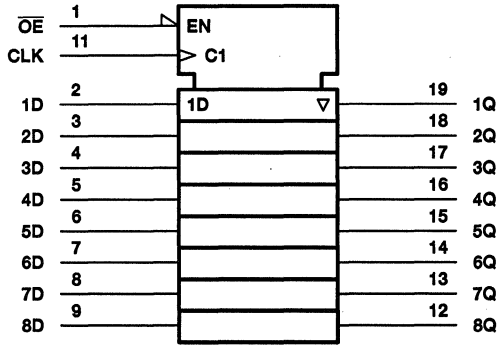
The SN74LVC574A is characterized for operation from –40°C to 85°C.

EPIC is a trademark of Texas Instruments Incorporated.

FUNCTION TABLE
(each flip-flop)

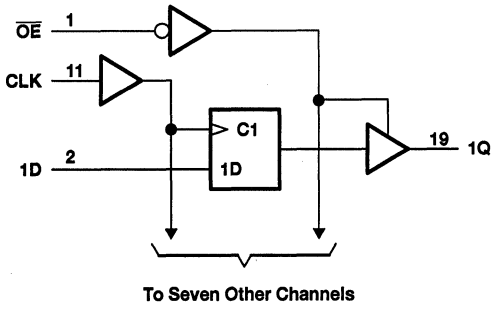
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high impedance state or power off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2.2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND		MIN to MAX			±10	µA
	V_O = 3.6 V or 5.5 V					±50	
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	V_O = V_{CC} or GND		3.3 V		3.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

timing characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	100	0	80	MHz
t_w	Pulse duration, CLK high or low	3.3		3.3		ns
t_{su}	Setup time, data before CLK↑	1.5		1.5		ns
t_h	Hold time, data after CLK↑	1.5		1.5		ns

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

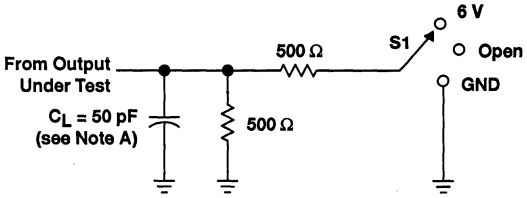
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			100		80		MHz
t_{pd}	D	Q	1.5	8.5		9.5	ns
t_{en}	$\overline{OE}$	Q	1.5	7.5		8.5	ns
t_{dis}	$\overline{OE}$	Q	1.5	7		8	ns
$t_{sk(o)}$†				1			ns

† Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

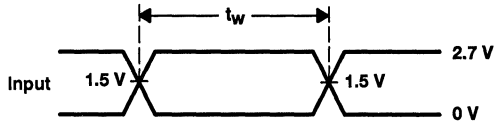
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 50 pF, f = 10 MHz	18	pF
		Outputs disabled		9	

PARAMETER MEASUREMENT INFORMATION

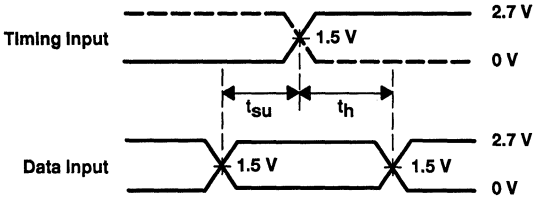


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

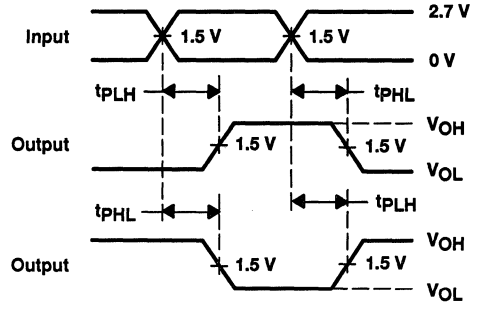
LOAD CIRCUIT FOR OUTPUTS



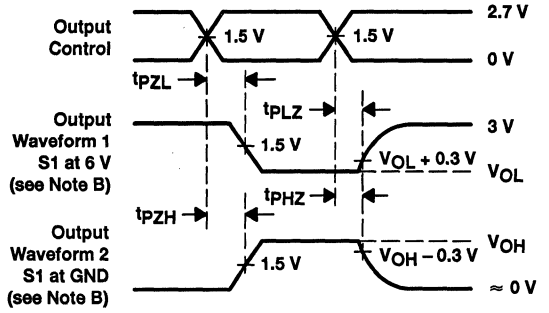
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



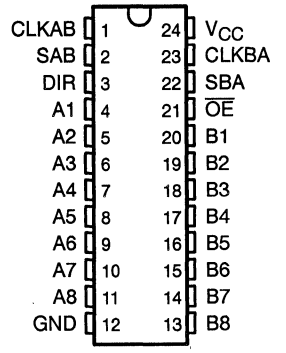
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal bus transceiver and register is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC646 consists of bus-transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74LVC646.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs control the transceiver functions. In the transceiver mode, data present at the high-impedance port can be stored in either register or in both.

The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. DIR determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data can be stored in one register and B data can be stored in the other register.

When an output function is disabled, the input function is still enabled and can be used to store and transmit data. Only one of the two buses, A or B, may be driven at a time.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

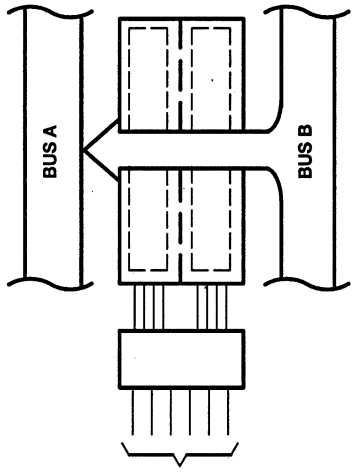
The SN74LVC646 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE

INPUTS						DATA I/Os		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1 – A8	B1 – B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

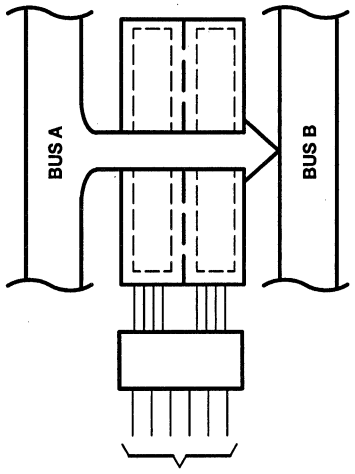
† The data output functions may be enabled or disabled by various signals at the $\overline{OE}$ and DIR inputs. Data input functions are always enabled; i.e., data at the bus pins is stored on every low-to-high transition of the clock inputs.

EPIC is a trademark of Texas Instruments Incorporated.



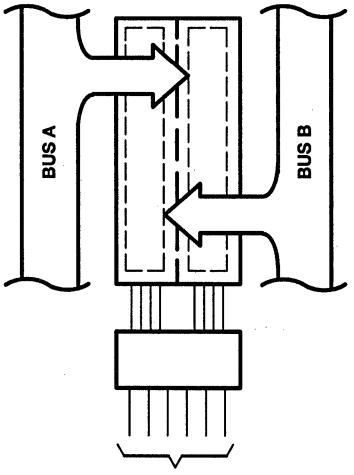
21 $\overline{OE}$	3 DIR	1 CLKAB	23 CLKBA	2 SAB	22 SBA
L	L	X	X	X	L

REAL-TIME TRANSFER BUS B TO BUS A



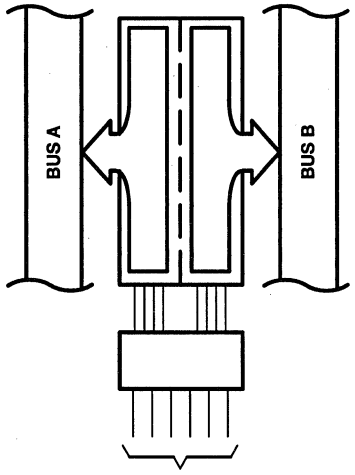
21 $\overline{OE}$	3 DIR	1 CLKAB	23 CLKBA	2 SAB	22 SBA
L	H	X	X	L	X

REAL-TIME TRANSFER BUS A TO BUS B



21 $\overline{OE}$	3 DIR	1 CLKAB	23 CLKBA	2 SAB	22 SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM A, B, OR A AND B

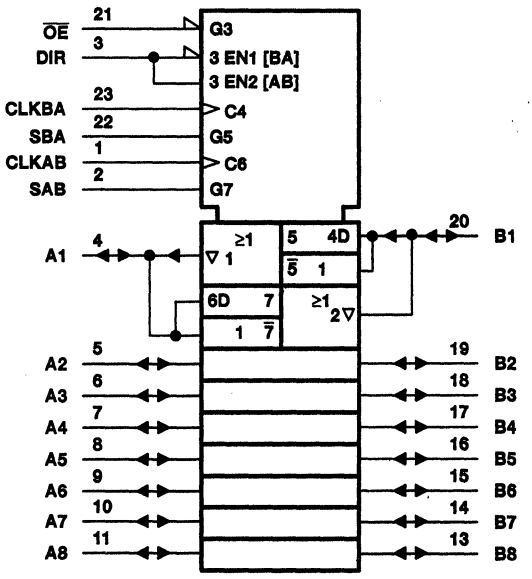


21 $\overline{OE}$	3 DIR	1 CLKAB	23 CLKBA	2 SAB	22 SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA TO A AND/OR B

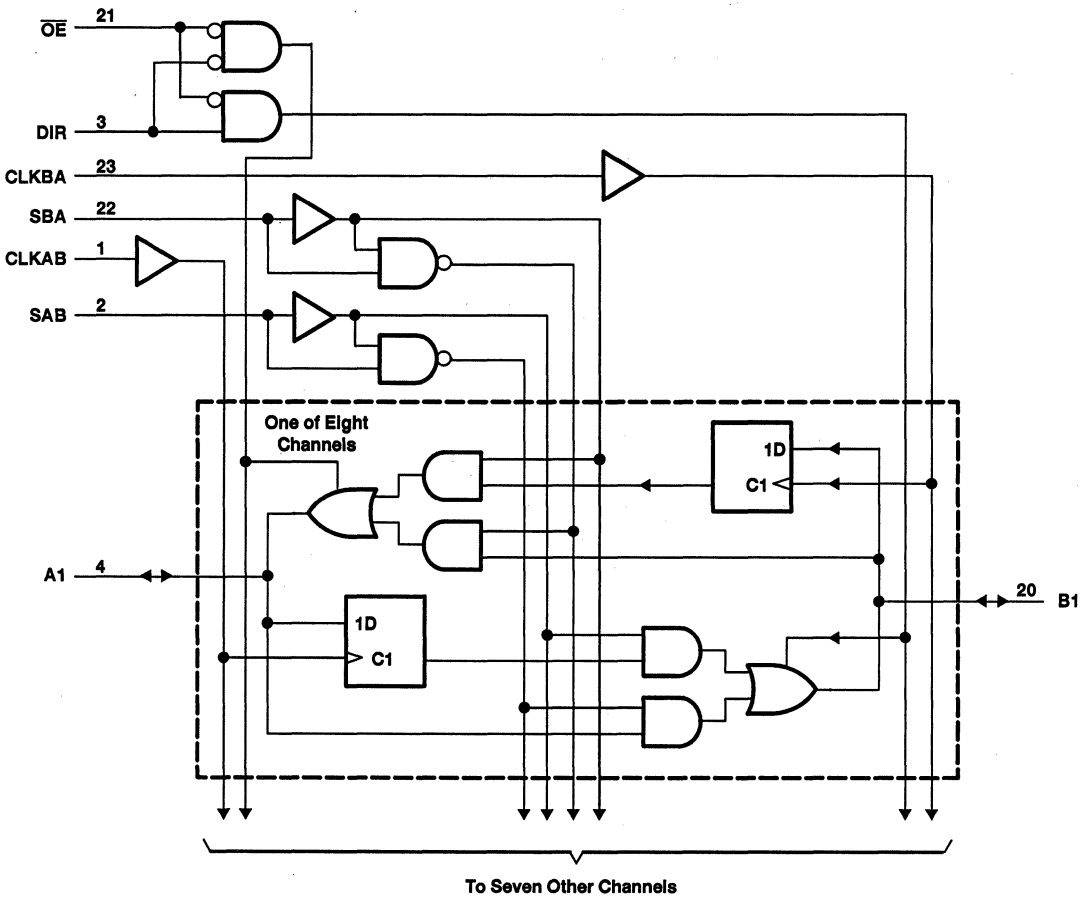
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 3)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage	Control inputs	0	5.5	V
		Data inputs	0	V_{CC}	
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA	MIN to MAX	V_{CC}–0.2			V
		I_{OH} = – 12 mA	2.7 V	2.2			
			3 V	2.4			
		I_{OH} = – 24 mA	3 V	2			
V_{OL}		I_{OL} = 100 μA	MIN to MAX			0.2	V
		I_{OL} = 12 mA	2.7 V			0.4	
		I_{OL} = 24 mA	3 V			0.55	
I_I		V_I = 5.5 V or GND	3.6 V			±5	μA
I_{OZ}§		V_O = V_{CC} or GND	3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND, I_O = 0	3.6 V			20	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND	3.3 V		4.6		pF
C_{io}	A or B ports	V_O = V_{CC} or GND	3.3 V		7.2		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration	5		5		ns
t_{su}	Setup time, data before CLK↑	5		5		ns
t_h	Hold time, data after CLK↑	1		1		ns

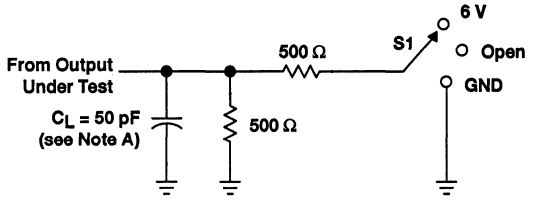
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			100		80		MHz
t_{pd}	A or B	B or A	1.5	8		9.2	ns
	CLK	A or B	1.5	9		11	
	SBA or SAB	A or B	1.5	9		11	
t_{en}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
t_{dis}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
t_{en}	DIR	A or B	1.5	9		10	ns
t_{dis}	DIR	A or B	1.5	9		10	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

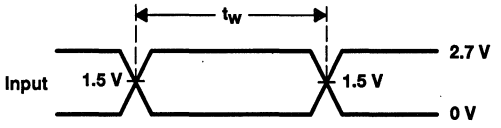
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	38	pF
		Outputs disabled		4.2	

PARAMETER MEASUREMENT INFORMATION

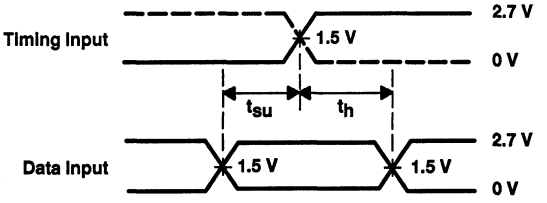


LOAD CIRCUIT FOR OUTPUTS

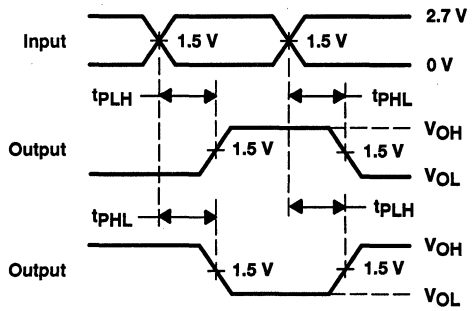
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



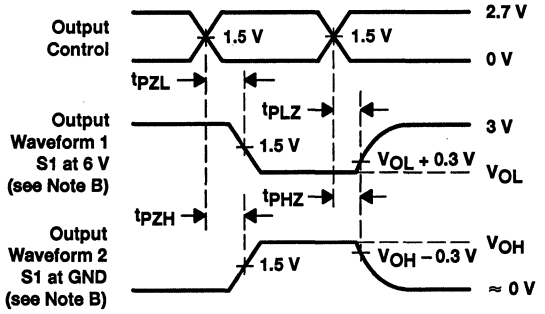
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



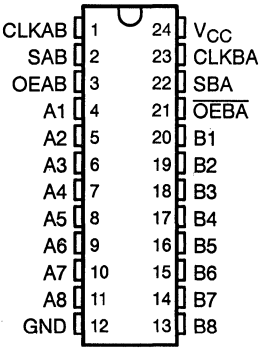
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal bus transceiver and register is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC652 consists of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers.

Output-enable (OEAB and $\overline{\text{OEBA}}$) inputs are provided to control the transceiver functions. Select-control (SAB and SBA) inputs are provided to select whether real-time or stored data is transferred. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. A low input selects real-time data, and a high input selects stored data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74LVC652.

Data on the A or B data bus, or both, can be stored in the internal D-type flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs regardless of the select- or enable-control pins. When SAB and SBA are in the real-time transfer mode, it is possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{\text{OEBA}}$. In this configuration, each output reinforces its input. When all other data sources to the two sets of bus lines are at high impedance, each set of bus lines remains at its last state.

To ensure the high-impedance state during power up or power down, $\overline{\text{OEBA}}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

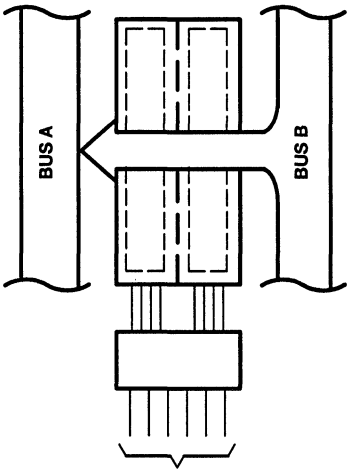
The SN74LVC652 is characterized for operation from –40°C to 85°C.

EPIC is a trademark of Texas Instruments Incorporated.

FUNCTION TABLE

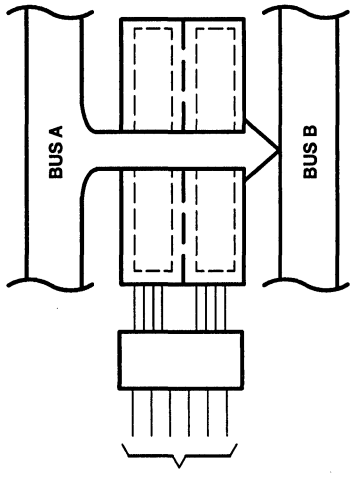
INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA	A1 THRU A8	B1 THRU B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and stored B data to A bus

† The data output functions may be enabled or disabled by a variety of level combinations at the OEAB or $\overline{OEBA}$ inputs. Data input functions are always enabled; i.e., data at the bus pins is stored on every low-to-high transition on the clock inputs.
‡ Select control = L; clocks can occur simultaneously.
Select control = H; clocks must be staggered in order to load both registers.



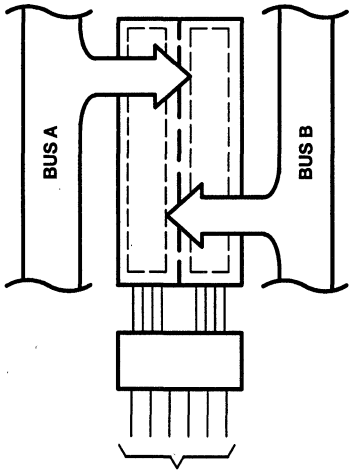
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



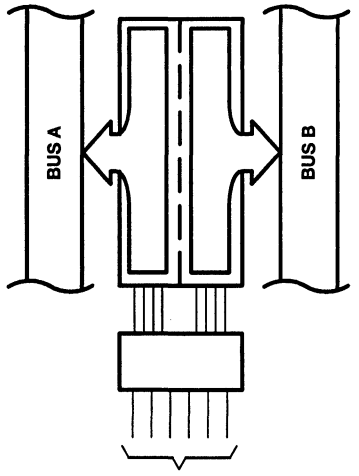
3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B

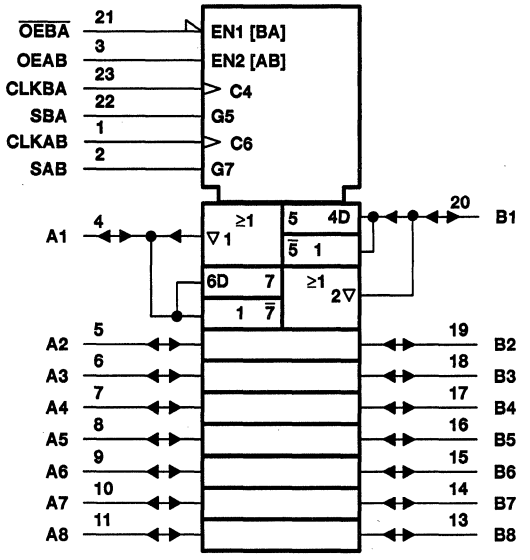


3	21	1	23	2	22
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	L	H or L	H or L	H	H

TRANSFER STORED DATA
TO A AND/OR B

Figure 1. Bus-Management Functions

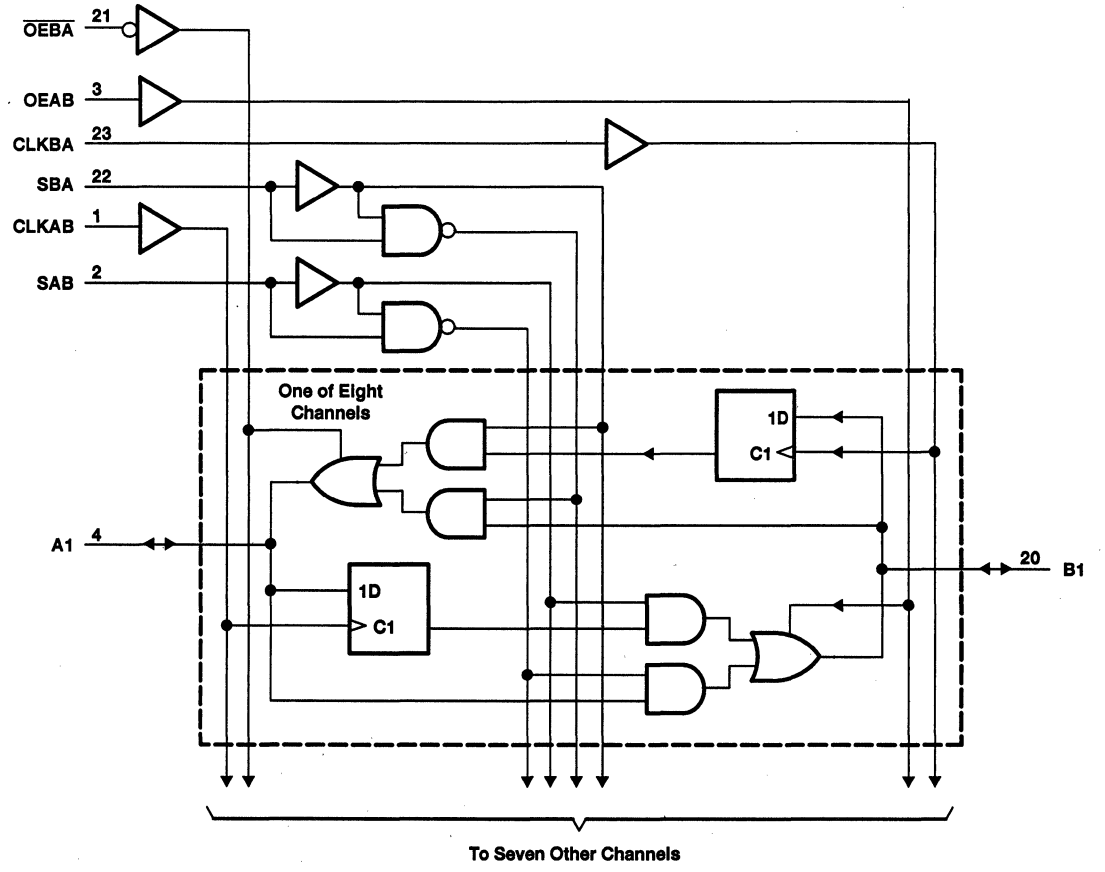
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage	Control inputs	0	5.5	V
		Data inputs	0	V_{CC}	
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = – 12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = – 24 mA		3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	μA
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.6		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.2		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency	0	100	0	80	MHz
t_w	Pulse duration	5		5		ns
t_{su}	Setup time, data before CLK↑	5		5		ns
t_h	Hold time, data after CLK↑	1		1		ns

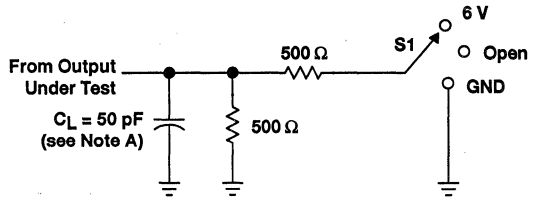
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			100		80		MHz
t_{pd}	A or B	B or A	1.5	8		9.2	ns
	CLK	A or B	1.5	9		11	
	SAB or SBA	A or B	1.5	9		11	
t_{en}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
t_{dis}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
t_{en}	OE	A or B	1.5	9		10	ns
t_{dis}	OE	A or B	1.5	9		10	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

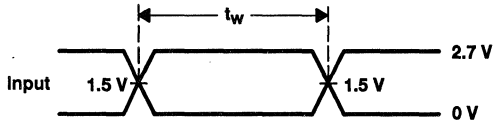
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	38	pF
		Outputs disabled		4.2	

PARAMETER MEASUREMENT INFORMATION

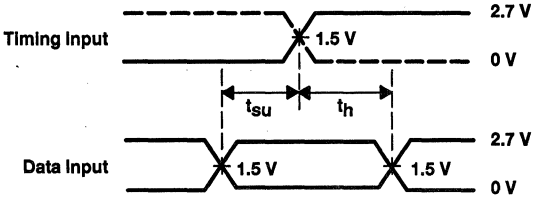


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

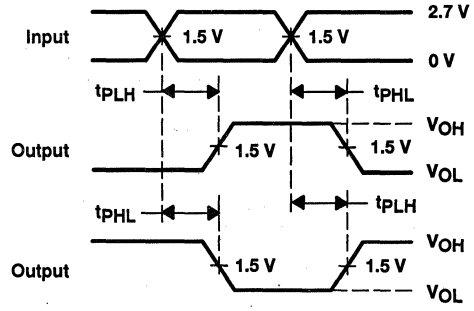
LOAD CIRCUIT FOR OUTPUTS



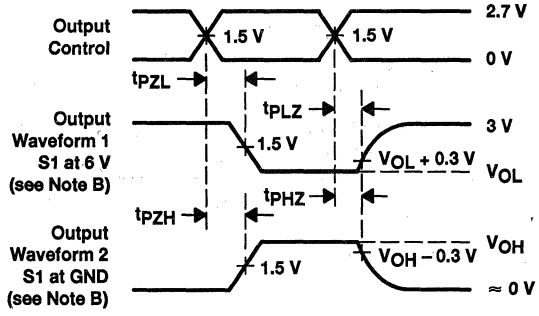
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



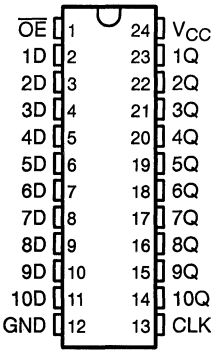
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages
- Inputs Accept Voltages to 5.5 V

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit bus-interface flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC821 features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing wider buffer registers, I/O ports, bidirectional bus drivers with parity, and working registers.

The ten flip-flops are edge-triggered D-type flip-flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the ten outputs in either a normal logic state (high or low level) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

The output-enable ($\overline{OE}$) input does not affect the internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the high-impedance state.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC821 is characterized for operation from −40°C to 85°C.

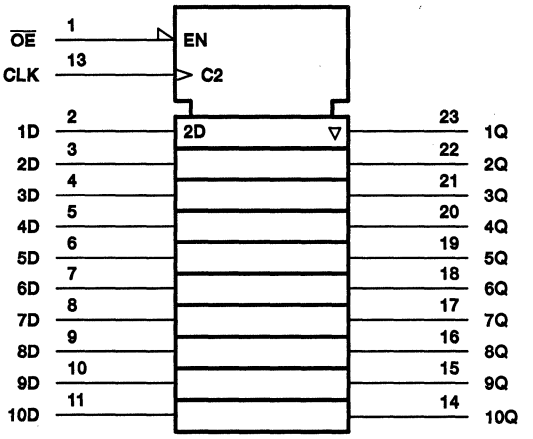
FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

PRODUCT PREVIEW

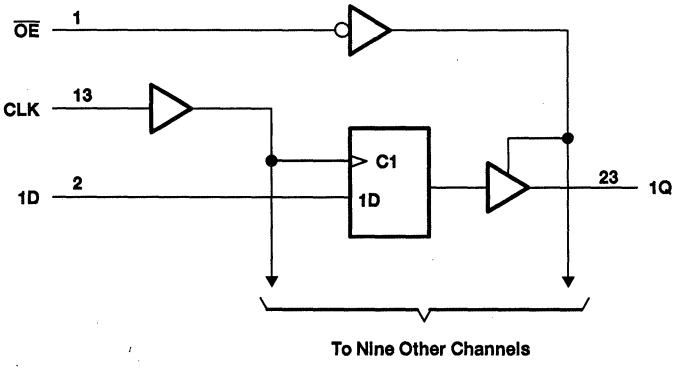
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

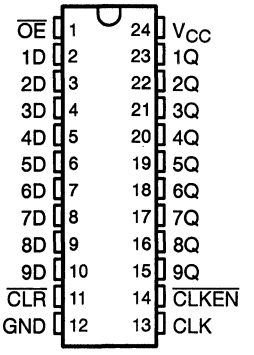
PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = –24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{OZ}	V_O = 5.5 V or GND	3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V				pF
C_o	V_O = V_{CC} or GND	3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ Typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 9-bit bus-interface flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC823 is designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing wider buffer registers, I/O ports, bidirectional bus drivers with parity, and working registers.

With the clock-enable ($\overline{CLKEN}$) input low, the nine D-type edge-triggered flip-flops enter data on the low-to-high transitions of the clock. Taking $\overline{CLKEN}$ high disables the clock buffer, latching the outputs. The SN74LVC823 has noninverting data (D) inputs. Taking the clear ($\overline{CLR}$) input low causes the nine Q outputs to go low independently of the clock.

A buffered output-enable ($\overline{OE}$) input can be used to place the nine outputs in either a normal logic state (high or low logic levels) or a high-impedance state. The output-enable ($\overline{OE}$) input does not affect the internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

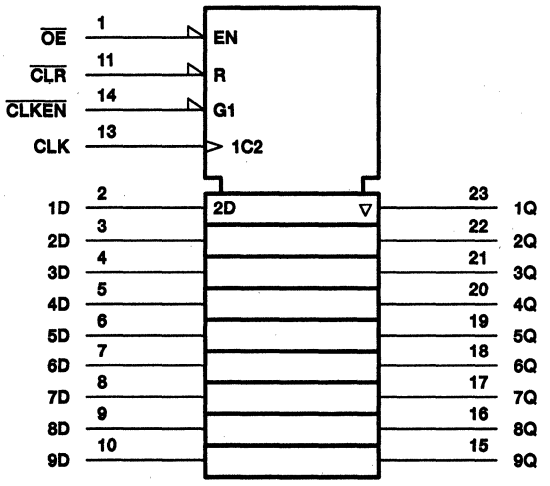
The SN74LVC823 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS					OUTPUT
$\overline{OE}$	$\overline{CLR}$	$\overline{CLKEN}$	CLK	D	Q
L	L	X	X	X	L
L	H	L	↑	H	H
L	H	L	↑	L	L
L	H	H	X	X	Q_0
H	X	X	X	X	Z

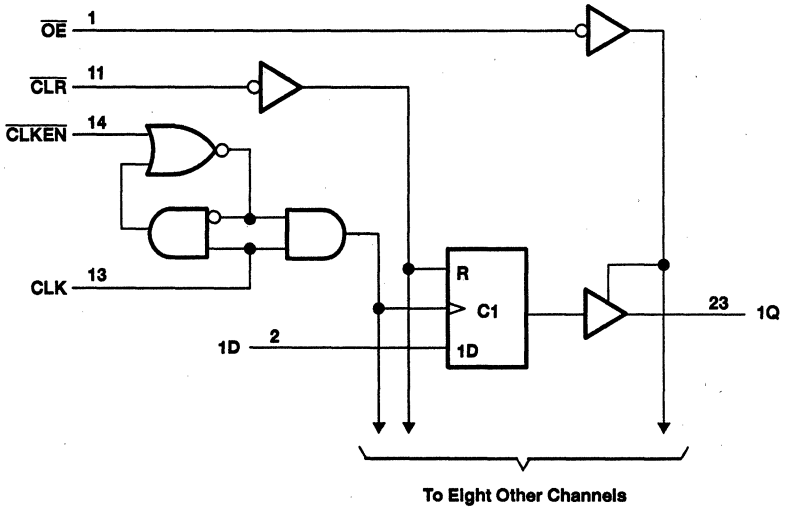
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		9		pF
C_o	V_O = V_{CC} or GND	3.3 V		10		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	100	0	80	MHz
t_w	Pulse duration	$\overline{CLR}$ low	5		5		ns
		CLK high or low	4		4		
t_{su}	Setup time, data before CLK↑	$\overline{CLR}$ inactive	1		1		ns
		Data	2		3		
		$\overline{CLKEN}$ low	3.5		4.5		
t_h	Hold time, data after CLK↑	Data	2		2		ns
		$\overline{CLKEN}$ low	0.5		0.5		

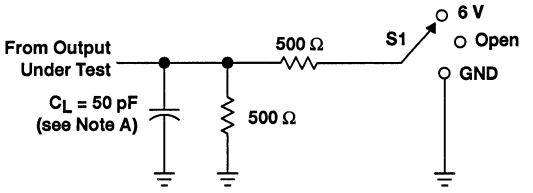
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			100		80		MHz
t_{pd}	CLK	Q	2	8	2	9	ns
	$\overline{CLR}$	Q	1.5	8	1.5	9	
t_{en}	$\overline{OE}$	Q	1.5	8.5	1.5	9.5	ns
t_{dis}	$\overline{OE}$	Q	1.5	8	1.5	9	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

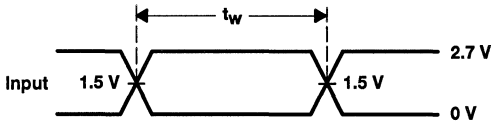
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 50 pF, f = 10 MHz	22	pF
		Outputs disabled		12	

PARAMETER MEASUREMENT INFORMATION

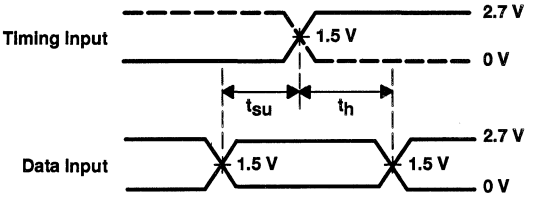


LOAD CIRCUIT FOR OUTPUTS

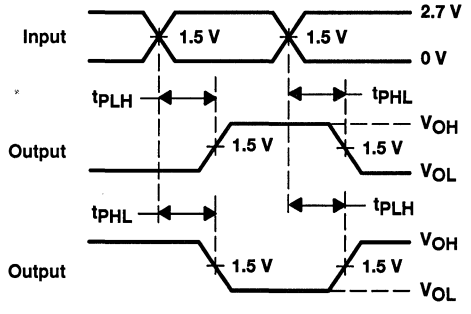
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



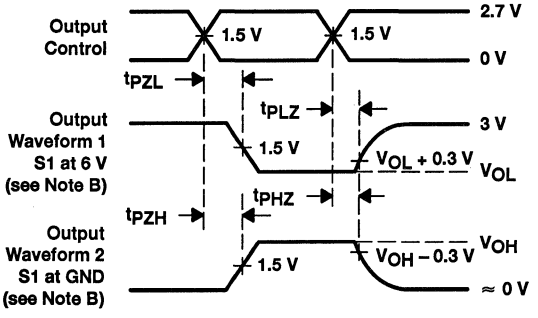
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



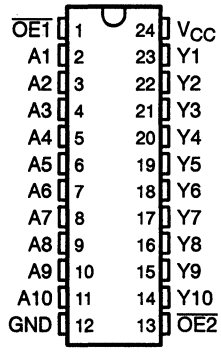
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit buffer/bus driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC827 provides a high-performance bus interface for wide data paths or buses carrying parity.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all ten outputs are in the high-impedance state. The SN74LVC827 provides true data at its outputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

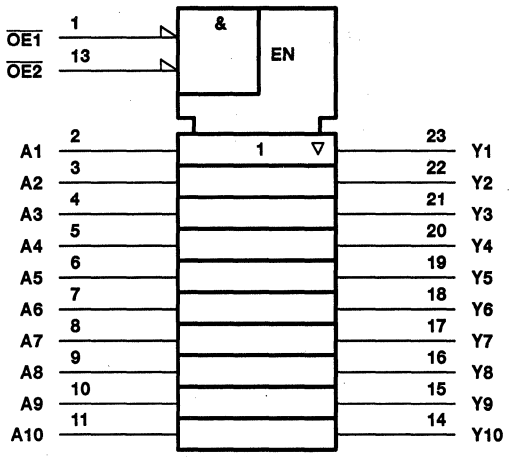
The SN74LVC827 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

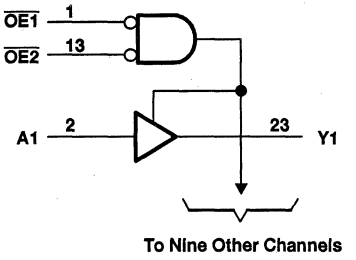
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA		2.7 V	2.2			
			3 V	2.4			
	I_{OH} = – 24 mA		3 V	2			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 12 mA		2.7 V			0.4	
	I_{OL} = 24 mA		3 V			0.55	
I_I	V_I = 5.5 V or GND		3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		9		pF
C_o	V_O = V_{CC} or GND		3.3 V		10		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

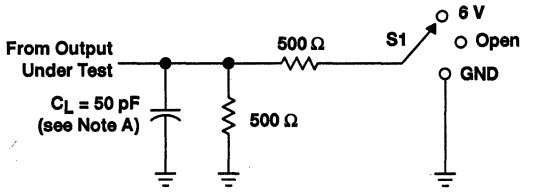
switching characteristics over recommended operating free-air temperature range, CL = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	7		8	ns
t_{en}	$\overline{OE}$	Y	1.5	9		11	ns
t_{dis}	$\overline{OE}$	Y	1.5	8		9	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

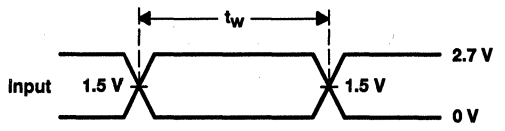
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	25	pF
		Outputs disabled		2.5	

PARAMETER MEASUREMENT INFORMATION

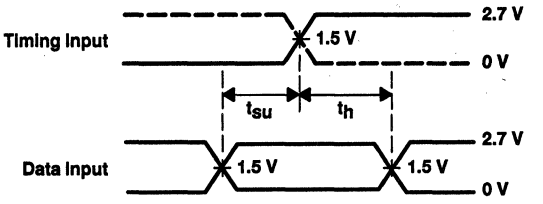


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

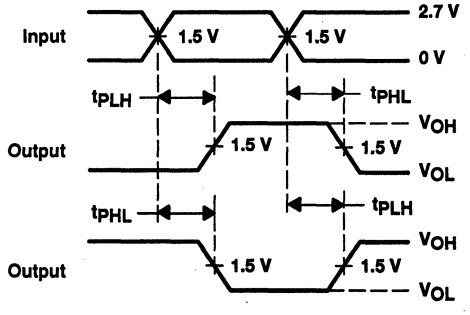
LOAD CIRCUIT FOR OUTPUTS



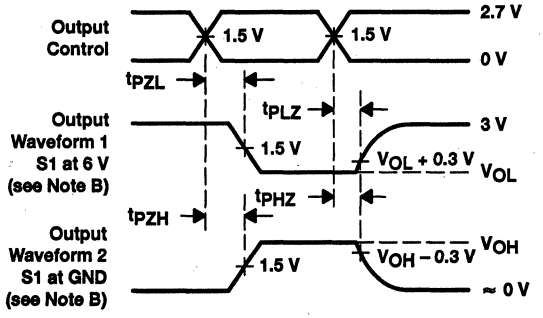
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



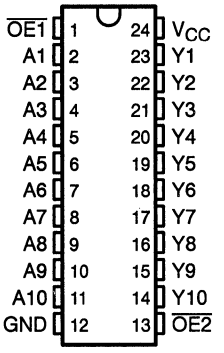
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit buffer/bus driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC828 provides a high-performance bus interface for wide datapaths or buses carrying parity.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all ten outputs are in the high-impedance state. The SN74LVC828 provides inverting data at its outputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

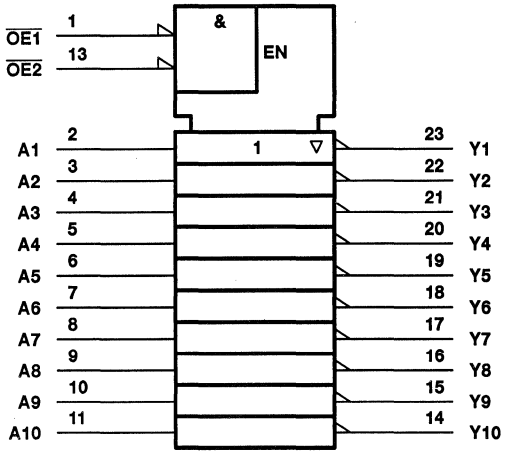
The SN74LVC828 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z

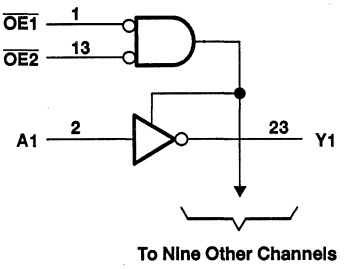
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{OZ}	V_O = V_{CC} or GND	3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		9		pF
C_o	V_O = V_{CC} or GND	3.3 V		10		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

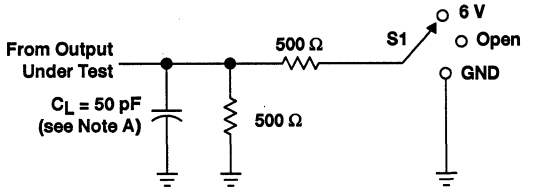
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	8		9	ns
t_{en}	$\overline{OE}$	Y	1.5	9		10	ns
t_{dis}	$\overline{OE}$	Y	1.5	8		9	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

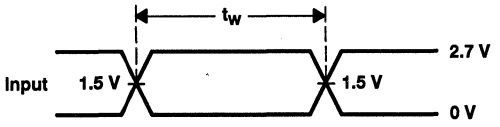
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	27	pF
		Outputs disabled		2.4	

PARAMETER MEASUREMENT INFORMATION

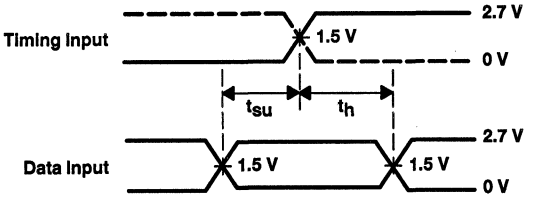


LOAD CIRCUIT FOR OUTPUTS

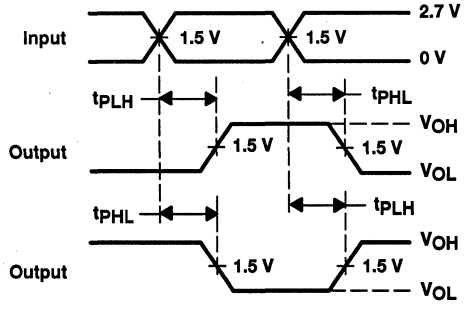
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



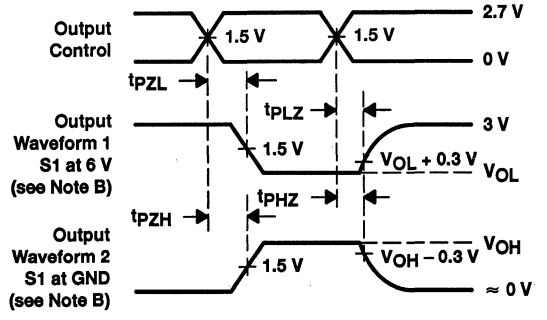
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



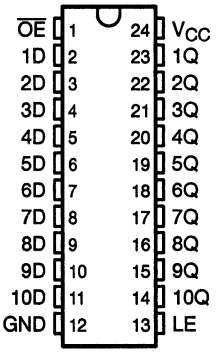
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit bus-interface D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC841 is designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The ten latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the ten outputs in either a normal logic state (high or low levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

The output-enable ($\overline{OE}$) input does not affect the internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC841 is characterized for operation from –40°C to 85°C.

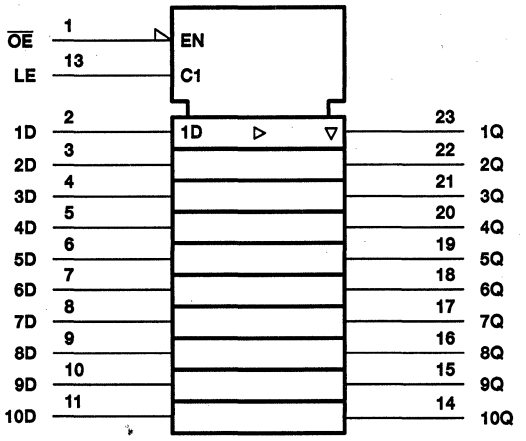
FUNCTION TABLE

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

PRODUCT PREVIEW

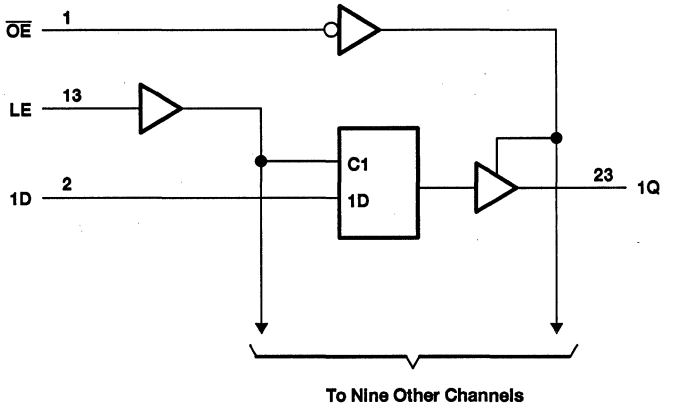
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high impedance state or power off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

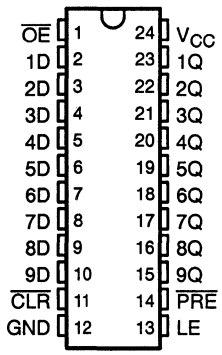
PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{OZ}	V_O = 5.5 V or GND	3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V				pF
C_o	V_O = V_{CC} or GND	3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 9-bit bus-interface D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC843 is designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The nine latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the nine outputs in either a normal logic state (high or low levels) or a high-impedance state. The outputs are also in the high-impedance state during power-up and power-down conditions. The outputs remain in the high-impedance state while the device is powered down. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

The output-enable ($\overline{OE}$) input does not affect the internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC843 is characterized for operation from −40°C to 85°C.

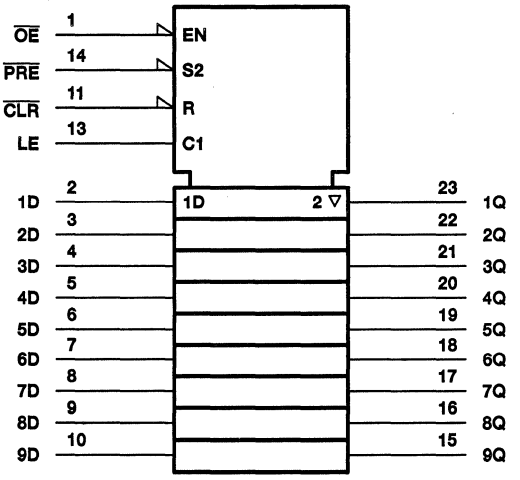
FUNCTION TABLE

INPUTS					OUTPUT
$\overline{PRE}$	$\overline{CLR}$	$\overline{OE}$	LE	D	Q
L	X	L	X	X	H
H	L	L	X	X	L
H	H	L	H	L	L
H	H	L	H	H	H
H	H	L	L	X	Q_0
X	X	H	X	X	Z

PRODUCT PREVIEW

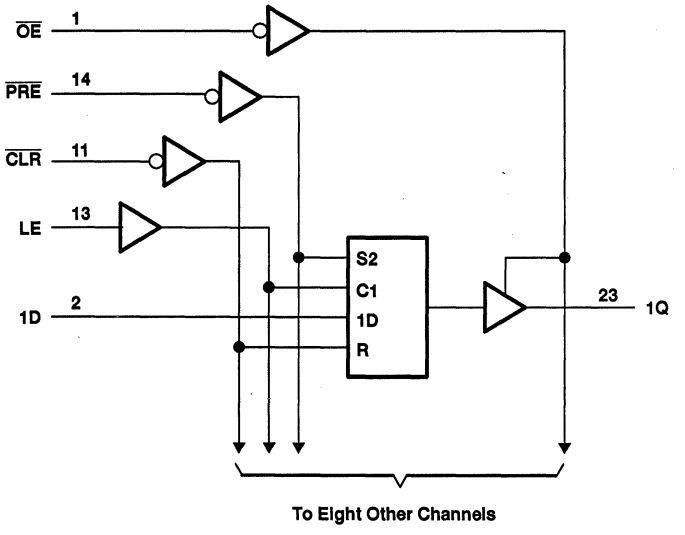
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high impedance state
or power off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high
or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

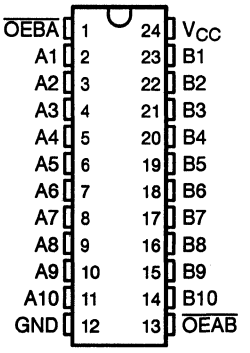
PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{OZ}	V_O = 5.5 V or GND	3.6 V			±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V				pF
C_o	V_O = V_{CC} or GND	3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC861 is designed for asynchronous communication between data buses. The control-function implementation allows for maximum flexibility in timing.

This device allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending upon the logic levels at the output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

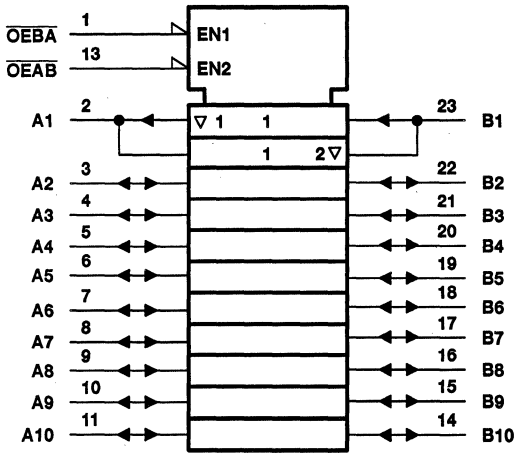
The SN74LVC861 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

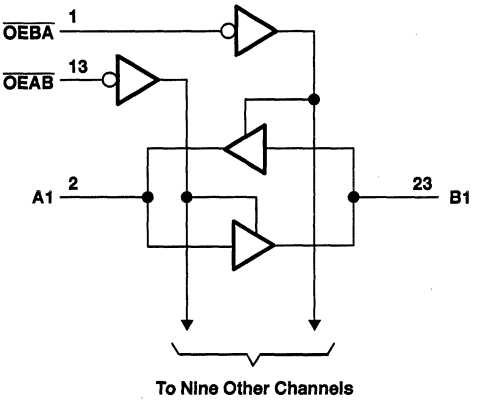
INPUTS		OPERATION
$\overline{OEAB}$	$\overline{OEBA}$	
L	H	A data to B bus
H	L	B data to A bus
H	H	Isolation
L	L	Latch A and B (A = B)

EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage	Control inputs	0	5.5	V
		Data inputs	0	V_{CC}	
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA	MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −12 mA	2.7 V	2.2			
			3 V	2.4			
		I_{OH} = −24 mA	3 V	2			
V_{OL}		I_{OL} = 100 μA	MIN to MAX			0.2	V
		I_{OL} = 12 mA	2.7 V			0.4	
		I_{OL} = 24 mA	3 V			0.55	
I_I		V_I = V_{CC} or GND	3.6 V			±5	μA
I_{OZ}§		V_O = V_{CC} or GND	3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND, I_O = 0	3.6 V			20	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND	3.3 V		9		pF
C_{io}	A or B ports	V_O = V_{CC} or GND	3.3 V		10		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

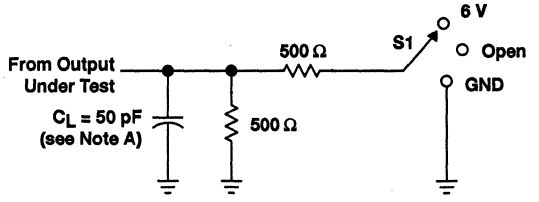
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	7		8	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1.5	9		10	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1.5	8		9	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

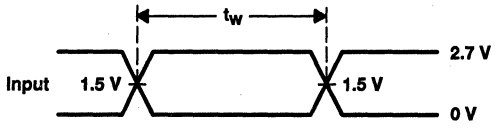
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	28	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

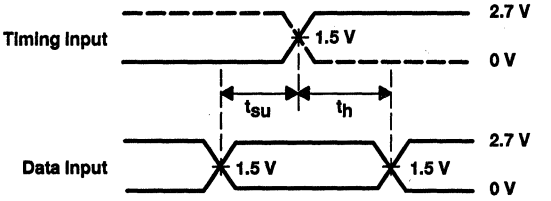


LOAD CIRCUIT FOR OUTPUTS

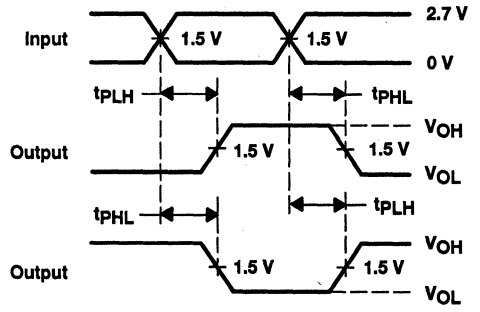
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



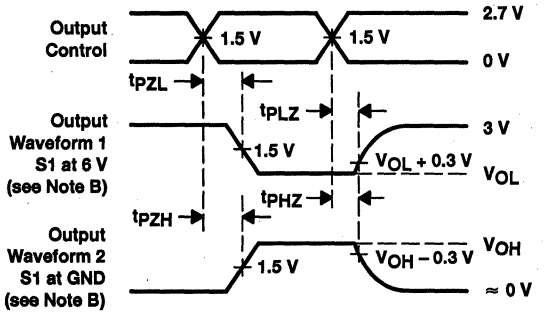
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



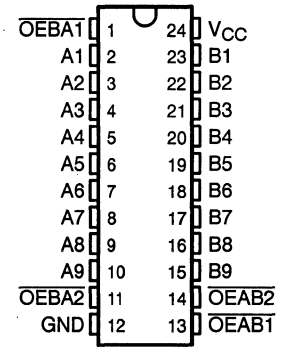
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 9-bit bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC863 is designed for asynchronous communication between data buses. The control-function implementation allows for maximum flexibility in timing.

This device allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending upon the logic levels at the output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) inputs.

The outputs are in the high-impedance state during power-up and power-down conditions. The outputs remain in the high-impedance state while the device is powered down.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

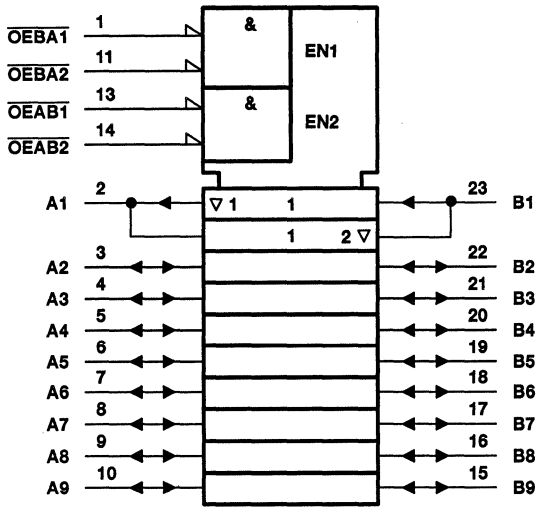
The SN74LVC863 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS				OPERATION
$\overline{OEAB1}$	$\overline{OEAB2}$	$\overline{OEBA1}$	$\overline{OEBA2}$	
L	L	L	L	Latch A and B
L	L	H	X	A to B
L	L	X	H	
H	X	L	L	B to A
X	H	L	L	
H	X	H	X	Isolation
H	X	X	H	
X	H	X	H	
X	H	H	X	

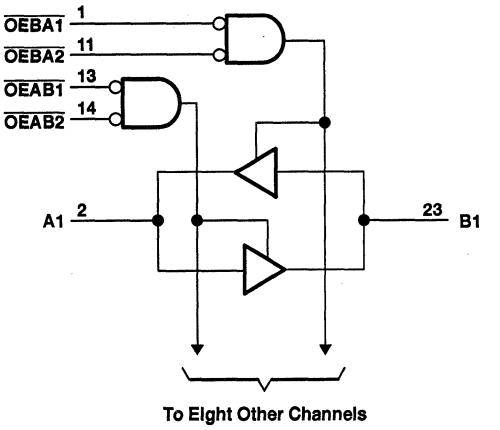
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage	Control inputs	0	5.5	V
		Data inputs	0	V_{CC}	
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA	MIN to MAX	V_{CC}–0.2			V
		I_{OH} = – 12 mA	2.7 V	2.2			
			3 V	2.4			
		I_{OH} = – 24 mA	3 V	2			
V_{OL}		I_{OL} = 100 μA	MIN to MAX			0.2	V
		I_{OL} = 12 mA	2.7 V			0.4	
		I_{OL} = 24 mA	3 V			0.55	
I_I		V_I = 5.5 V or GND	3.6 V			±5	μA
I_{OZ}§		V_O = V_{CC} or GND	3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND, I_O = 0	3.6 V			20	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND	3.3 V		9		pF
C_{io}	A or B ports	V_O = V_{CC} or GND	3.3 V		10		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

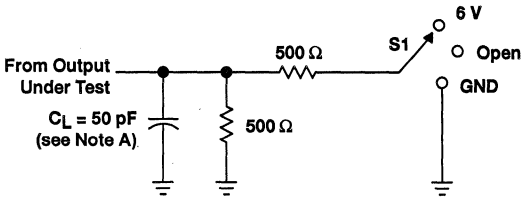
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	7		8	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1.5	9		10	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	A or B	1.5	8		9	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

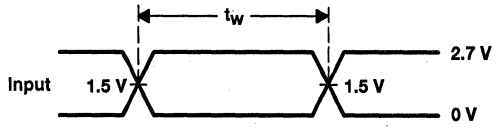
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	27	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

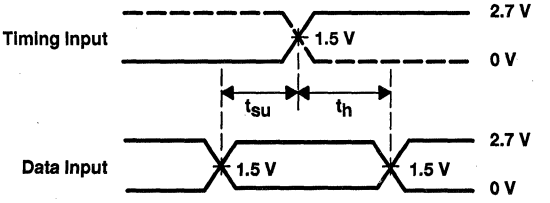


TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 6 V GND

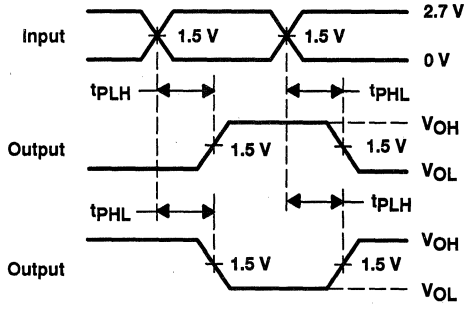
LOAD CIRCUIT FOR OUTPUTS



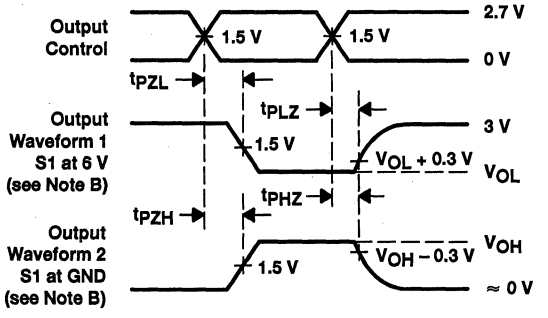
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

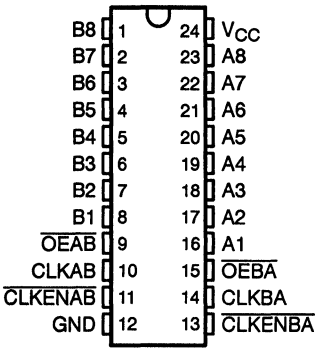
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal bus transceiver and register is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC2952 consists of two 8-bit back-to-back registers that store data flowing in both directions between two bidirectional buses. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input provided that the clock-enable ($\overline{CLKENAB}$ or $\overline{CLKENBA}$) input is low. Taking the output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) input low accesses the data on either port.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC2952 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE†

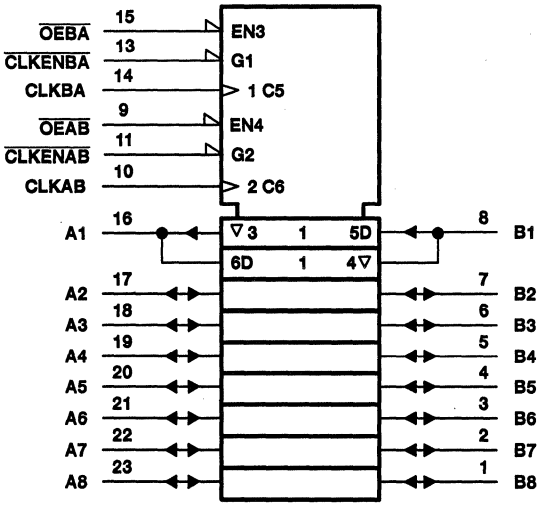
INPUTS				OUTPUT
$\overline{CLKENAB}$	CLKAB	$\overline{OEAB}$	A	B
H	X	L	X	B_0‡
X	H or L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

† A-to-B data flow is shown; B-to-A data flow is similar but uses $\overline{CLKENBA}$, CLKBA, and $\overline{OEBA}$.
‡ Level of B before the indicated steady-state input conditions were established

PRODUCT PREVIEW

EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†

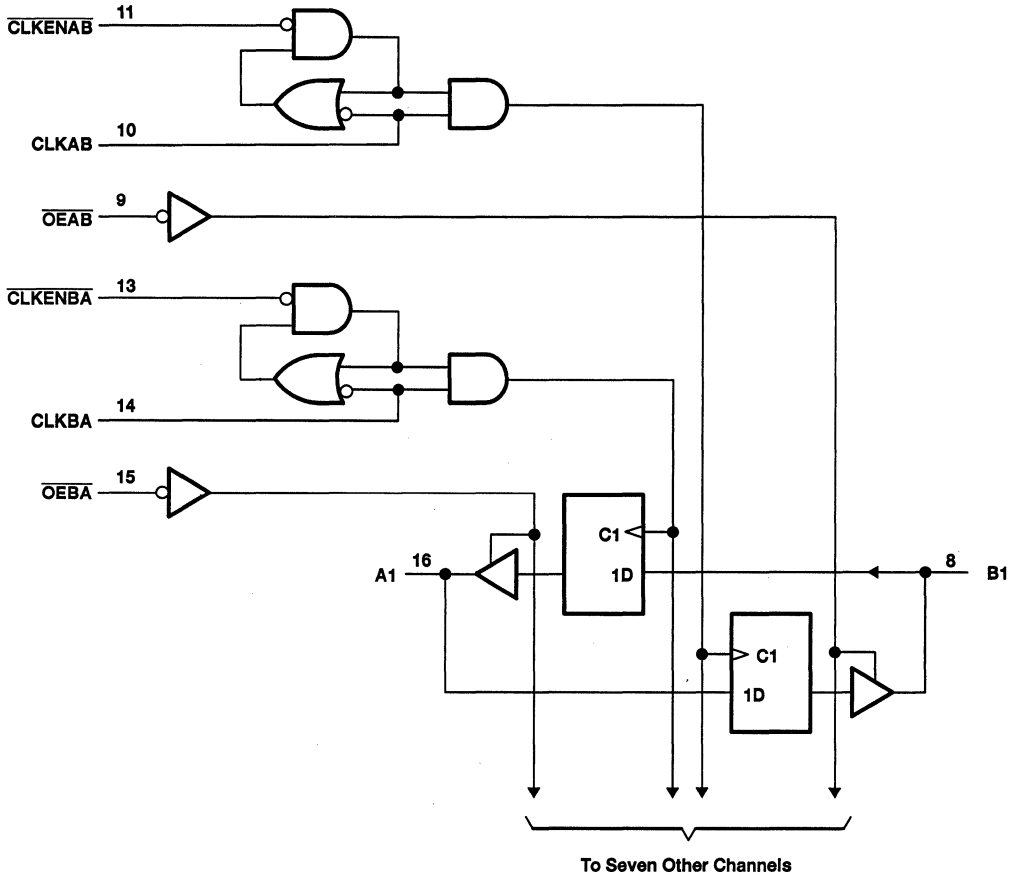


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

PRODUCT PREVIEW

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high impedance state
or power off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high
or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.65 W
DW package ..... 1.7 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
		I_{OH} = – 12 mA	2.7 V	2.2			
			3 V	2.4			
		I_{OH} = – 24 mA	3 V	2.2			
V_{OL}		I_{OL} = 100 µA	MIN to MAX			0.2	V
		I_{OL} = 12 mA	2.7 V			0.4	
		I_{OL} = 24 mA	3 V			0.55	
I_I		V_I = 5.5 V or GND	3.6 V			±5	µA
I_{OZ}§		V_O = 5.5 V or GND	3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND, I_O = 0	3.6 V			20	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND	3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND	3.3 V				pF

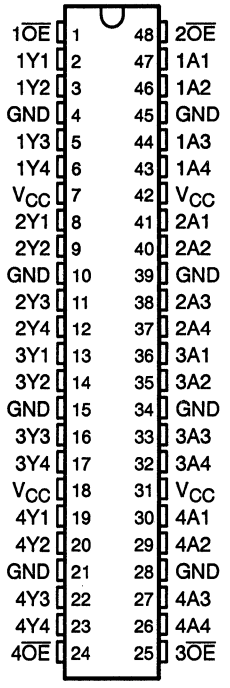
† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

PRODUCT PREVIEW

Contents

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC16240 is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. This device provides inverting outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVC16240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

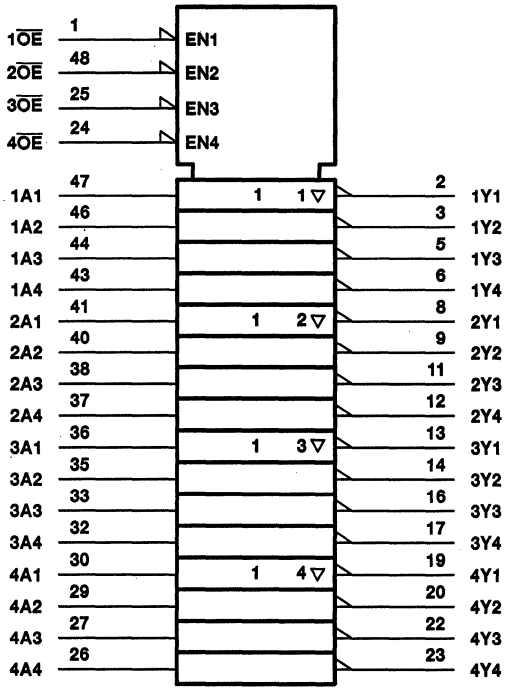
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

PRODUCT PREVIEW

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

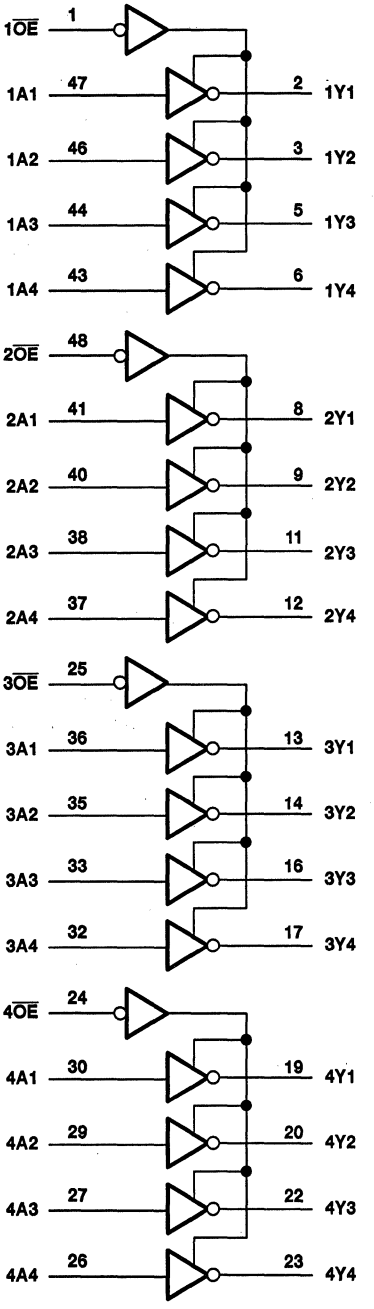
PRODUCT PREVIEW

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	5.5	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

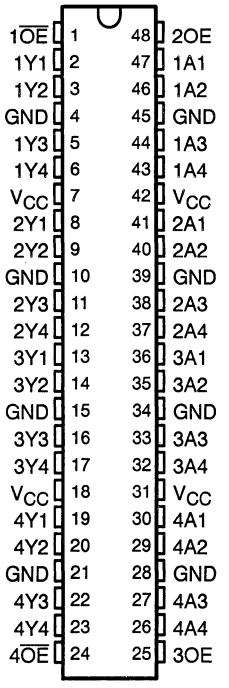
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	µA
$I_{I(hold)}$	Data inputs	V_I = 0.8 V		3 V	75			µA
		V_I = 2 V			–75			
I_{OZ}		V_O = 5.5 V or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i		V_I = V_{CC} or GND		3.3 V				pF
C_o		V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC16241 is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. This device provides true outputs and complementary output-enable (OE and $\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVC16241 is characterized for operation from –40°C to 85°C.

PRODUCT PREVIEW

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

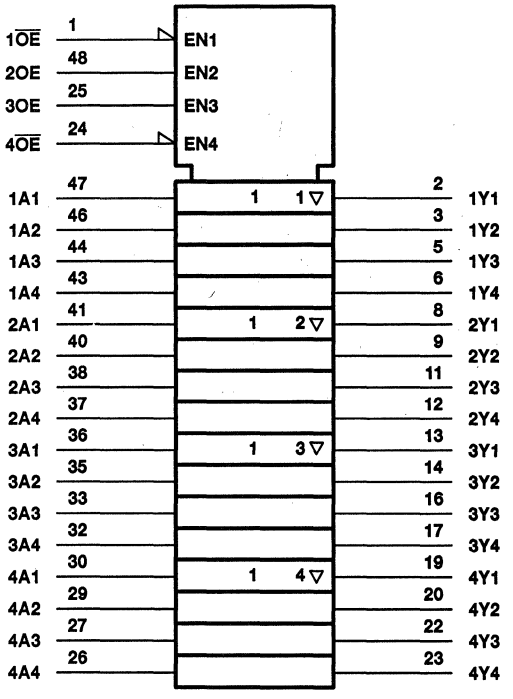
PRODUCT PREVIEW

FUNCTION TABLES

INPUTS		OUTPUTS
$1\overline{OE}$, $4\overline{OE}$	1A, 4A	1Y, 4Y
L	H	H
L	L	L
H	X	Z

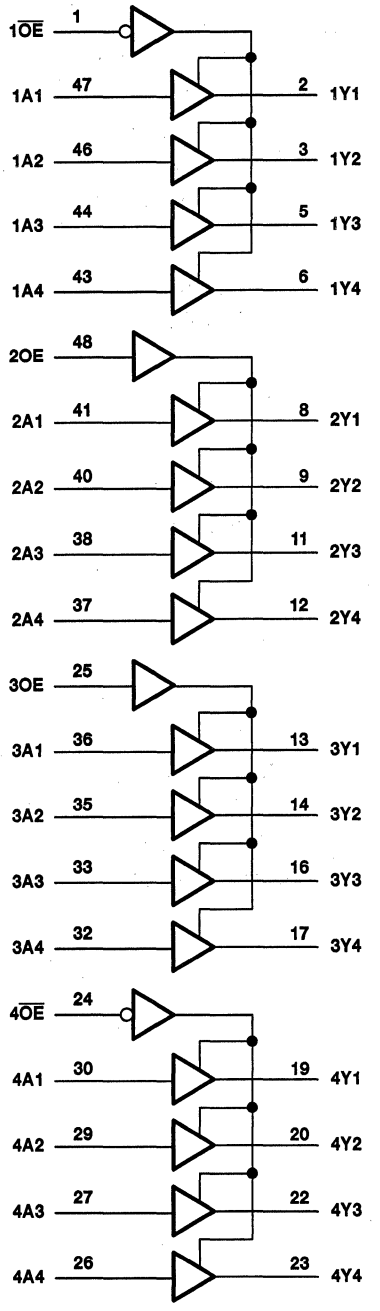
INPUTS		OUTPUTS
2OE, 3OE	2A, 3A	2Y, 3Y
H	H	H
H	L	L
L	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state
or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high
or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

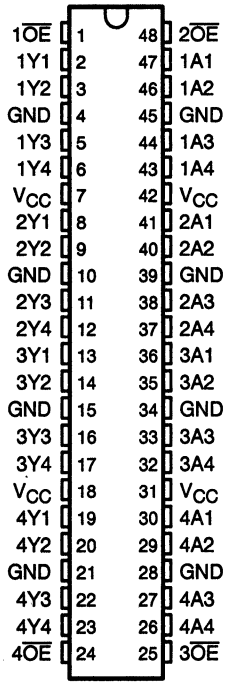
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	μA
$I_{I(hold)}$	Data inputs	V_I = 0.8 V		3 V	75			μA
		V_I = 2 V			–75			
I_{OZ}		V_O = 5.5 V or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i		V_I = V_{CC} or GND		3.3 V				pF
C_o		V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC16244A is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

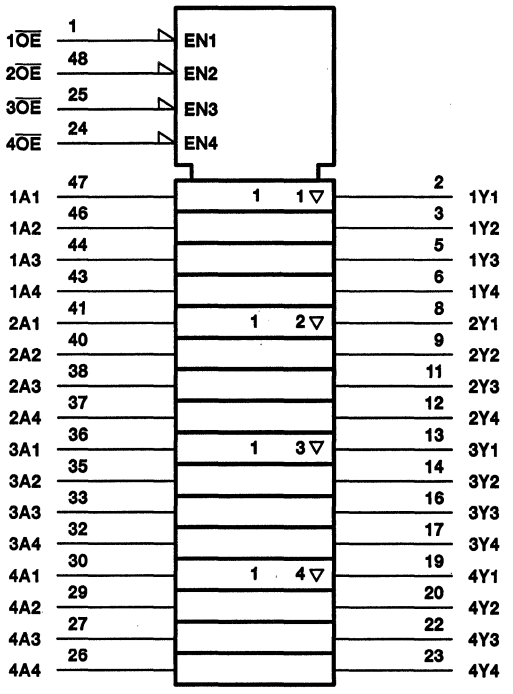
The SN74LVC16244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

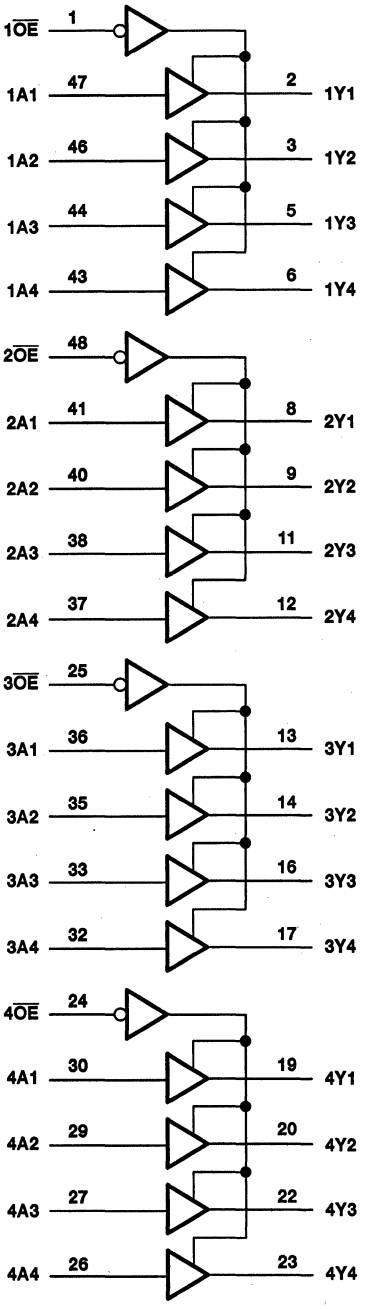
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state
or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high
or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Operating free-air temperature range, T_A ..... −40°C to 85°C
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7 V	2			
	I_{OH} = –12 mA	3 V	2.2			
	I_{OH} = –24 mA	3 V	2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	µA
I_{off}	V_I or V_O = 5.5 V	0			50	µA
I_{OZ}	V_O = 0 to 5.5 V	3.6 V			±20	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3 V		4.7		pF
C_o	V_O = V_{CC} or GND	3.3 V		6.1		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

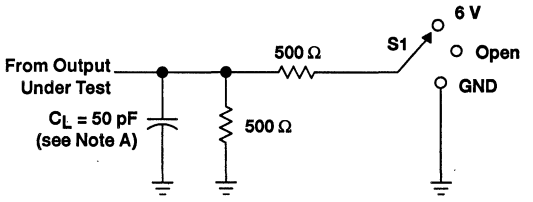
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	5.2		5.8	ns
t_{en}	$\overline{OE}$	Y	1.5	7.5		8.2	ns
t_{dis}	$\overline{OE}$	Y	1.5	7		7.7	ns
$t_{sk(o)}$§				1			ns

§ Skew between any tow outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

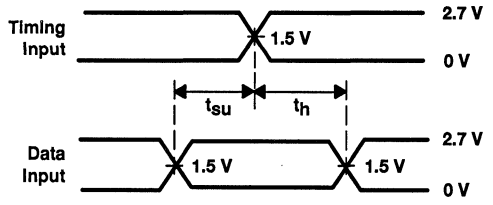
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	20.2	pF
		Outputs disabled		3.6	

PARAMETER MEASUREMENT INFORMATION

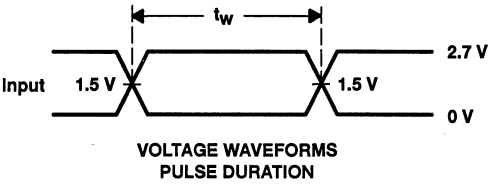


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

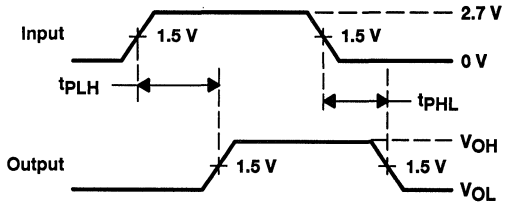
LOAD CIRCUIT



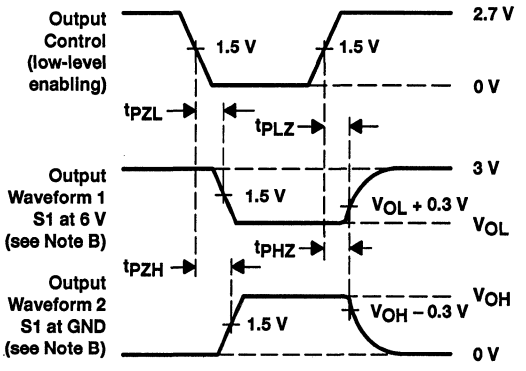
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



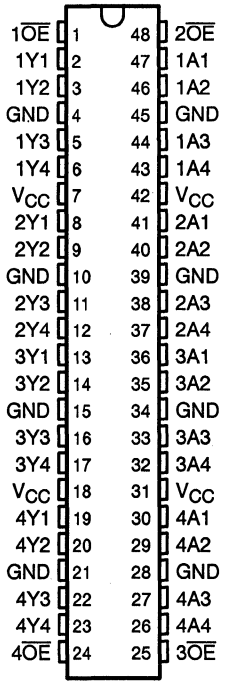
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16244A is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

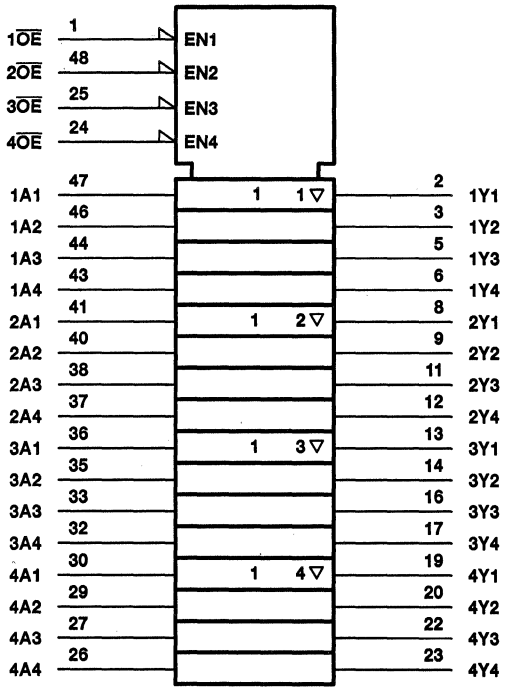
The SN74LVCH16244A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

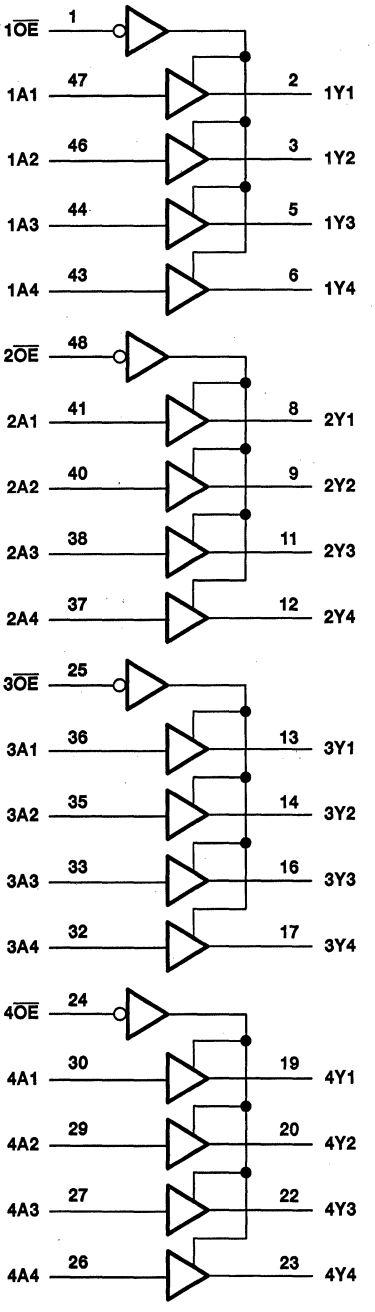
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state
or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high
or low state, V_O (see Note 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 µA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = –12 mA	2.7	2.2			
		3	2.4			
	I_{OH} = –24 mA	3	2			
V_{OL}	I_{OL} = 100 µA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7			0.4	
	I_{OL} = 24 mA	3			0.55	
I_I	V_I = 5.5 V or GND	3.6			±5	µA
$I_{I(hold)}$	V_I = 0.8 V	3	75			µA
	V_I = 2 V		–75			
	V_I = 0 to 3.6 V	3.6			±500	
I_{off}	V_I or V_O = 5.5 V	0			±50	µA
I_{OZ}	V_O = 0 to 5.5 V	3.6			±20	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND	3.3		4.7		pF
C_o	V_O = V_{CC} or GND	3.3		6.1		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

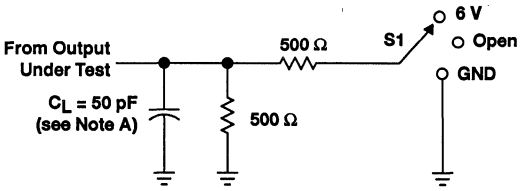
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	5.2		5.8	ns
t_{en}	$\overline{OE}$	Y	1.5	7.5		8.2	ns
t_{dis}	$\overline{OE}$	Y	1.5	7		7.7	ns
$t_{sk(o)}$§				1			ns

§ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, T_A = 25°C

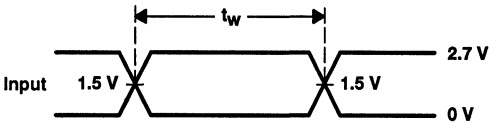
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	20.2	pF
		Outputs disabled		3.6	

PARAMETER MEASUREMENT INFORMATION

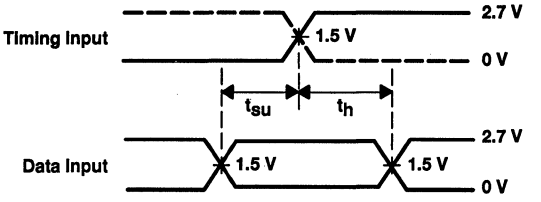


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

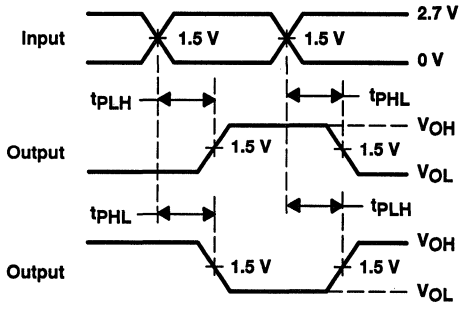
LOAD CIRCUIT FOR OUTPUTS



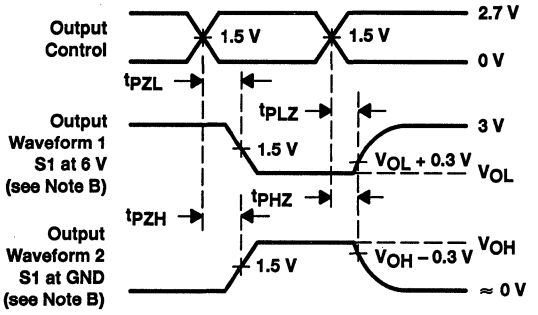
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



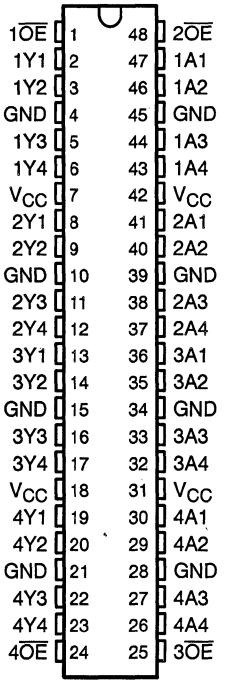
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- Member of the Texas Instruments *Widebus*™ Family
- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Output Ports Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC162244 is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. It provides true outputs and symmetrical active-low output-enable ($\overline{OE}$) inputs. The outputs, which are designed to sink up to 12 mA, include 26-Ω resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

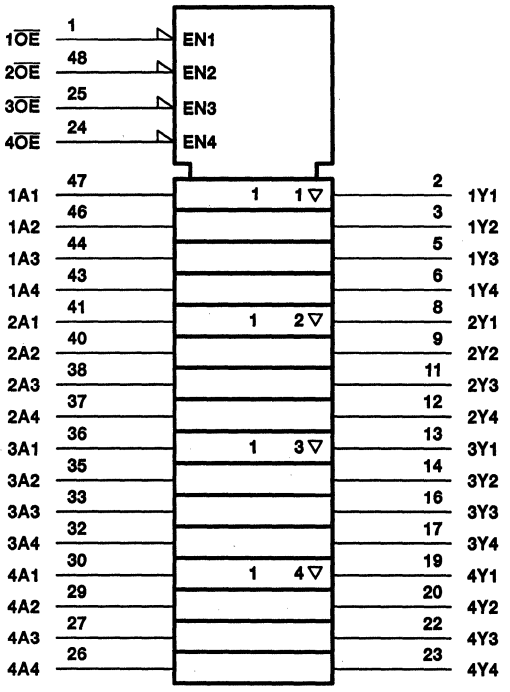
The SN74LVC162244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 4-bit buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

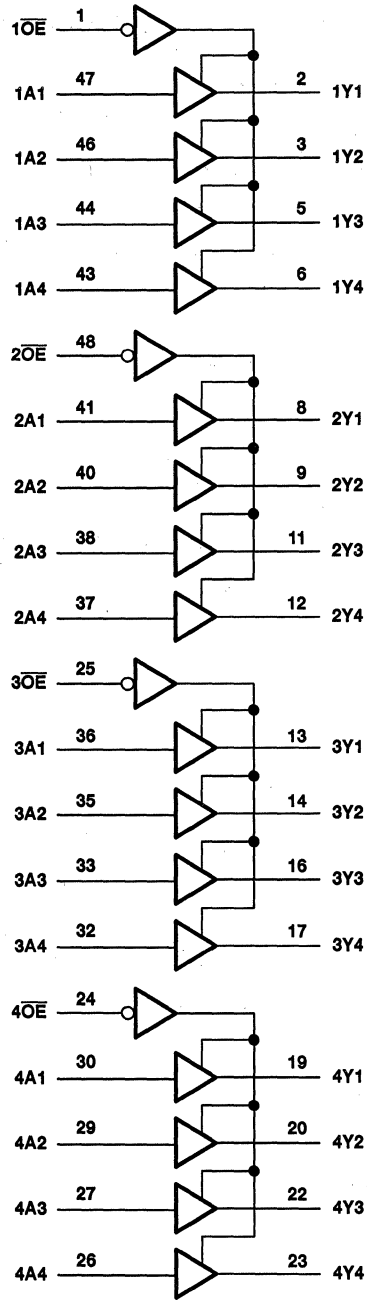
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−8	mA
		V_{CC} = 3 V		−12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		8	mA
		V_{CC} = 3 V		12	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 2 V	3	2.4			
		I_{OH} = –8 mA,	V_{IH} = 2 V	2.7	2			
		I_{OH} = –12 mA,	V_{IH} = 2 V	3	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.8 V	3			0.55	
		I_{OL} = 8 mA,	V_{IL} = 0.8 V	2.7			0.6	
		I_{OL} = 12 mA,	V_{IL} = 0.8 V	3			0.8	
I_I		V_I = V_{CC} or GND		3.6			±5	µA
$I_{I(hold)}$		V_I = 0.8 V		3	75			µA
		V_I = 2 V		3	–75			
		V_I = 0 to 3.6 V		3.6			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6			20	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3		2.5		pF
C_o	A or B ports	V_O = V_{CC} or GND		3.3		3.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

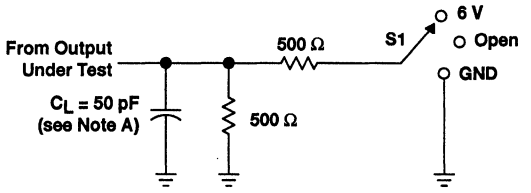
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1.5	7	1.5	8	ns
t_{en}	$\overline{OE}$	Y	1.5	9	1.5	10	ns
t_{dis}	$\overline{OE}$	Y	1.5	7	1.5	8	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

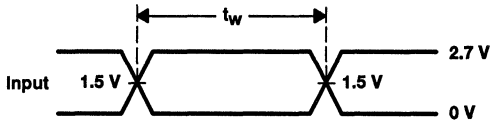
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	20	pF
		Outputs disabled		2	

PARAMETER MEASUREMENT INFORMATION

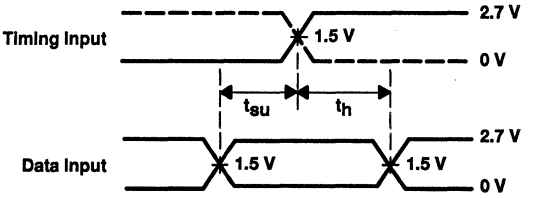


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

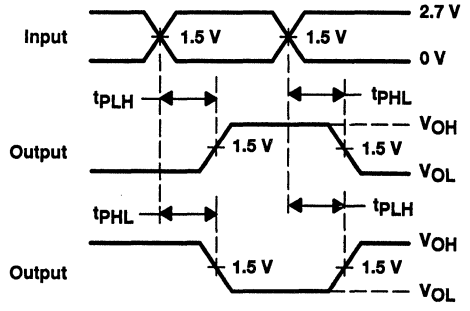
LOAD CIRCUIT FOR OUTPUTS



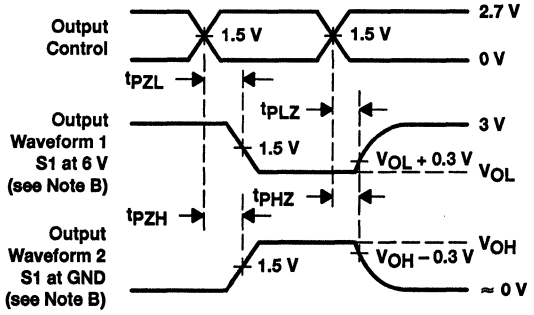
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



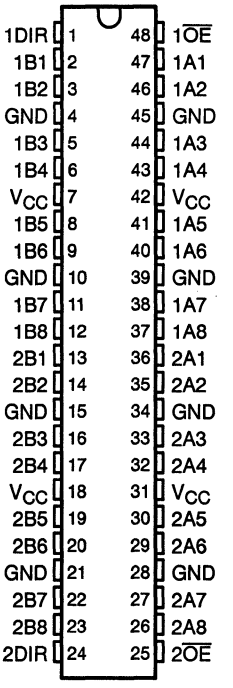
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC16245A is designed for asynchronous communication between data buses. The control function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

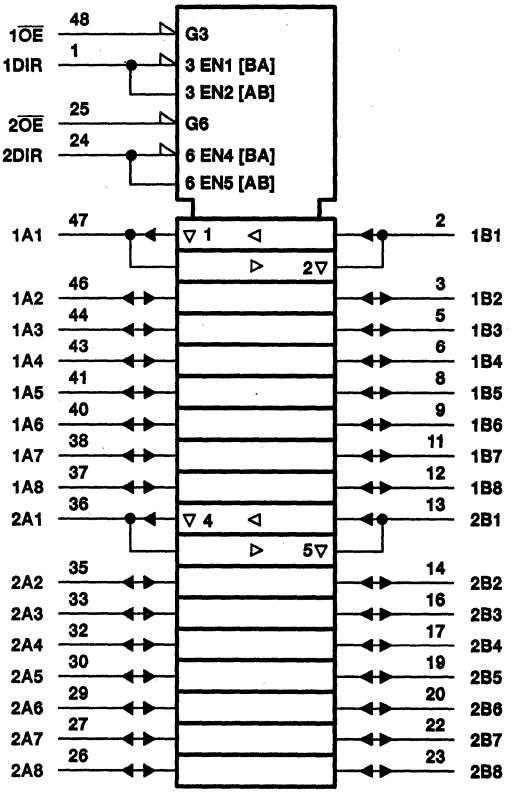
The SN74LVC16245A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

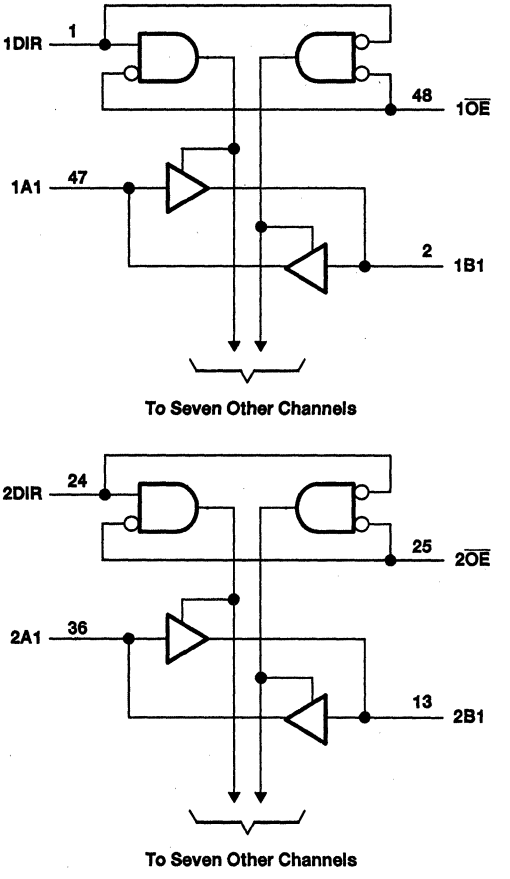
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Voltage applied to any output in the high-impedance state
or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 6.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	5	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2			
		I_{OH} = –12 mA		3 V	2.2			
		I_{OH} = –24 mA		3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	μA
I_{off}		V_I or V_O = 5.5 V		0			50	μA
I_{OZ}§		V_O = 0 to 5.5 V		3.6 V			±20	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5.4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

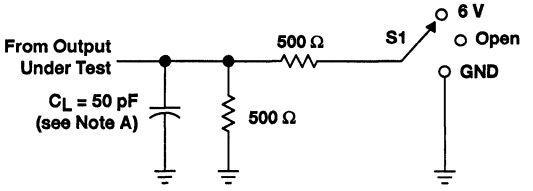
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A	Y	1	5.2		5.8	ns
t_{en}	$\overline{OE}$	Y	1.5	7.2		8	ns
t_{dis}	$\overline{OE}$	Y	1.5	7.2		8	ns
$t_{sk(o)}$¶				1			ns

¶ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

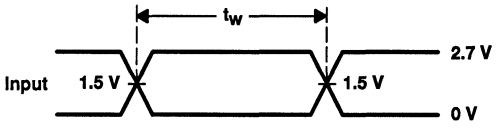
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	24	pF
		Outputs disabled		3.7	

PARAMETER MEASUREMENT INFORMATION

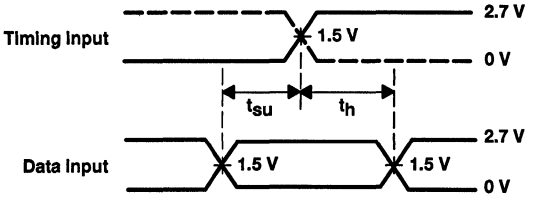


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

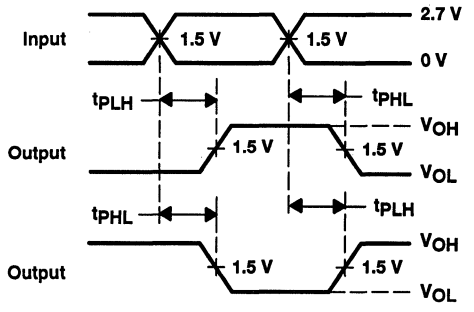
LOAD CIRCUIT FOR OUTPUTS



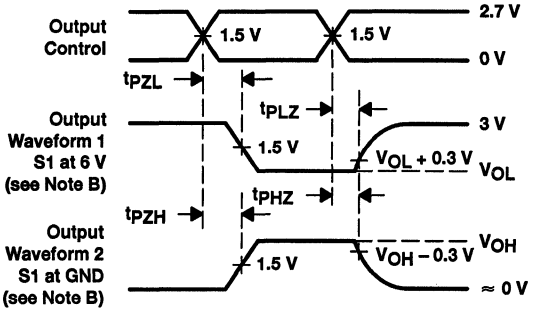
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



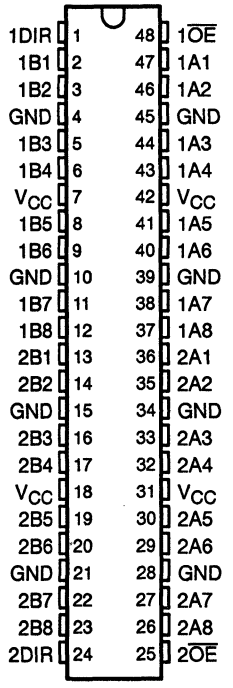
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PZL} and t_{PZH} are the same as t_{en}.
F. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCH16245 is designed for asynchronous communication between data buses. The control function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

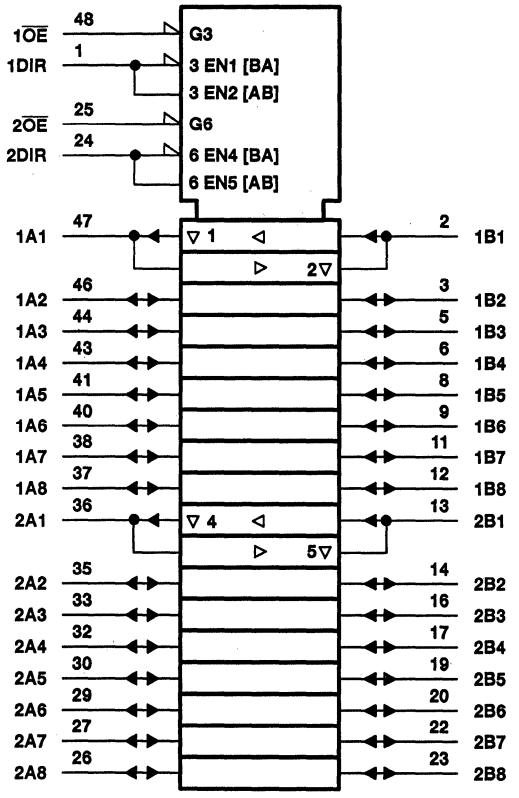
The SN74LVCH16245 is characterized for operation from −40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 8-bit section)

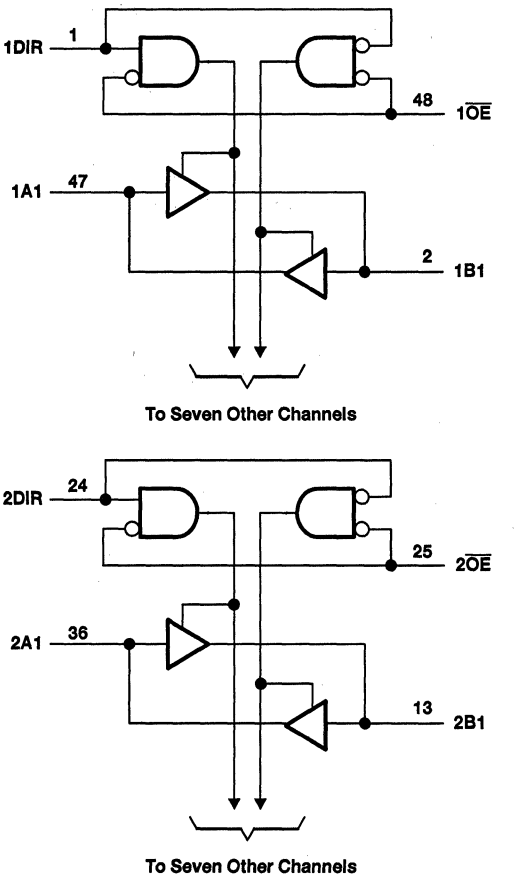
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Voltage applied to any output in the high-impedance state or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through each V_{CC} or GND ..... ±100 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3-state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	5	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2			
				3 V	2.2			
		I_{OH} = –24 mA		3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	V_I = 5.5 V or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.8 V		3 V	75			µA
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{off}		V_I or V_O = 5.5 V		0			50	µA
I_{OZ}§		V_O = 0 to 5.5 V		3.6 V			±20	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5.4		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		9		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

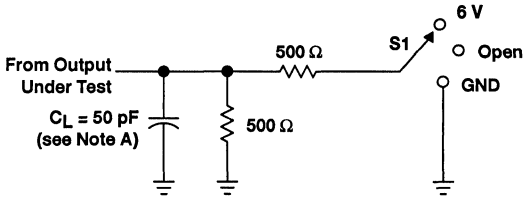
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1	5.2		5.8	ns
t_{en}	$\overline{OE}$	A or B	1.5	7.2		8	ns
t_{dis}	$\overline{OE}$	A or B	1.5	7.2		8	ns
$t_{sk(o)}$¶				1			ns

¶ Skew between any two outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

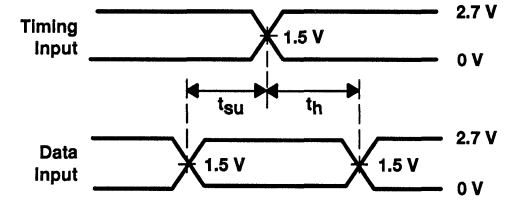
PARAMETER			TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF,	f = 10 MHz	24	pF
		Outputs disabled			3.7	

PARAMETER MEASUREMENT INFORMATION

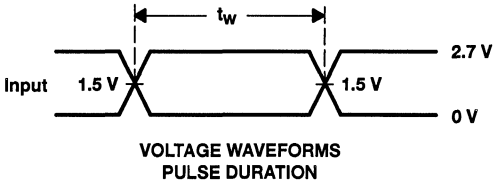


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

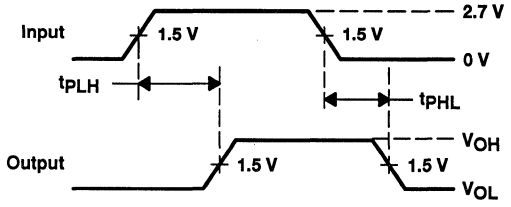
LOAD CIRCUIT



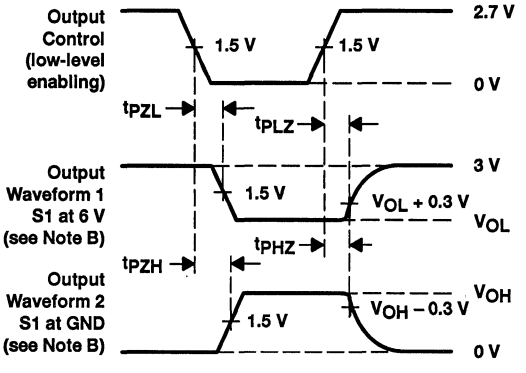
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



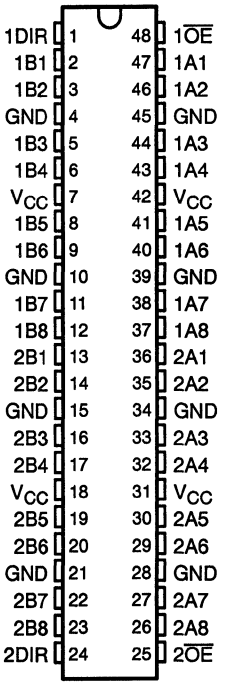
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **All Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required**
- **Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVCR162245 is designed for asynchronous communication between data buses. The control function implementation minimizes external timing requirements.

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

All outputs, which are designed to sink up to 12 mA, include 26-Ω resistors to reduce overshoot and undershoot.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

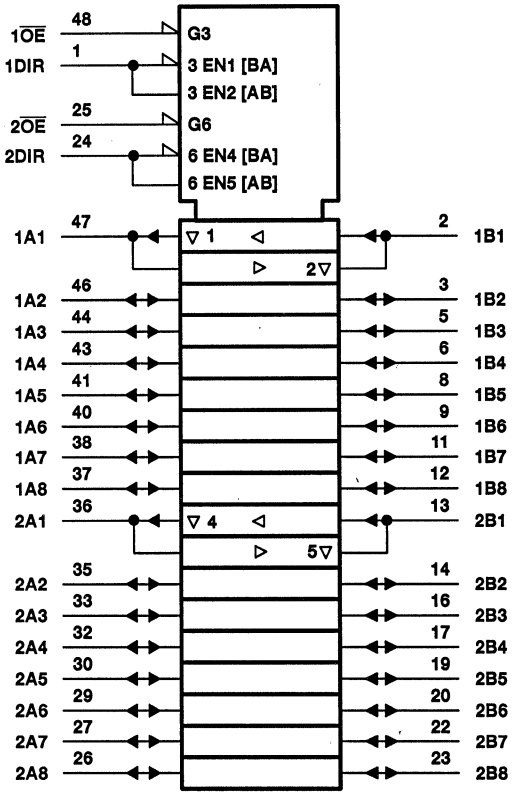
The SN74LVCR162245 is characterized for operation from −40°C to 85°C.

EPIC and Widebus are a trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 8-bit section)

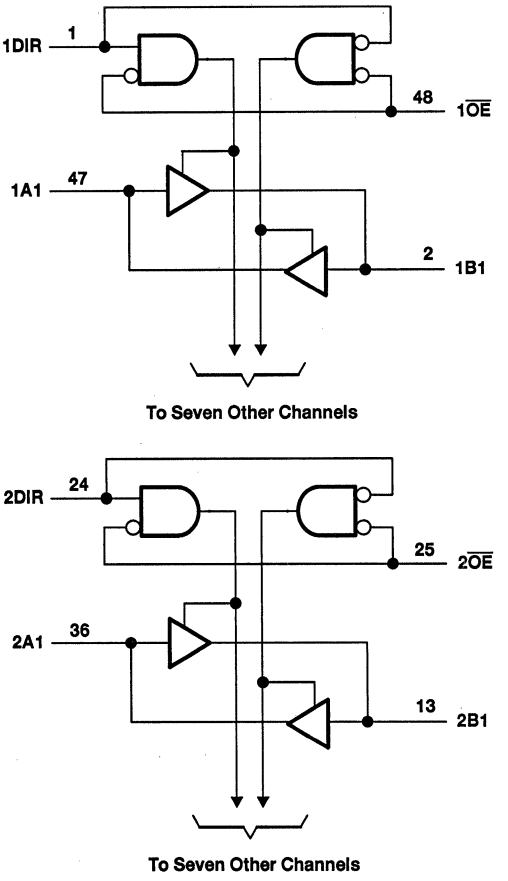
INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, VI: Except I/O ports (see Note 1) ..... −0.5 V to V_{CC} + 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−8	mA
		V_{CC} = 3 V		−12	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		8	mA
		V_{CC} = 3 V		12	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −4 mA,	V_{IH} = 2 V	2.7 V	2.2			
		I_{OH} = −8 mA,	V_{IH} = 2 V	2.7 V	2			
		I_{OH} = −6 mA,	V_{IH} = 2 V	3 V	2.4			
		I_{OH} = −12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}		I_{OH} = −100 µA		MIN to MAX			0.2	V
		I_{OH} = −4 mA,	V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OH} = −8 mA,	V_{IL} = 0.8 V	2.7 V			0.6	
		I_{OH} = −6 mA,	V_{IL} = 0.8 V	3 V			0.55	
		I_{OH} = −12 mA,	V_{IL} = 0.8 V	3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.8 V		3 V	75			µA
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6 V			±500	µA
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		2.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		3.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

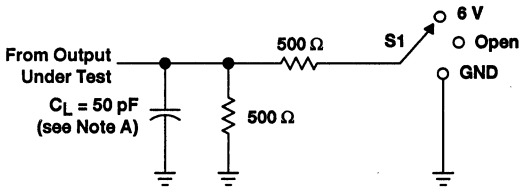
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	7.5	1.5	8.5	ns
t_{en}	$\overline{OE}$	A or B	1.5	9	1.5	10	ns
t_{dis}	$\overline{OE}$	A or B	1.5	7.5	1.5	8.5	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

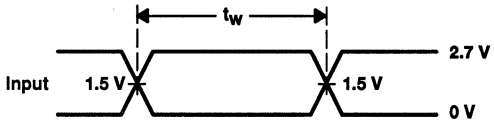
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	20	pF
		Outputs enabled		2	

PARAMETER MEASUREMENT INFORMATION

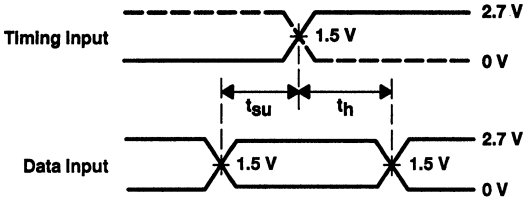


LOAD CIRCUIT FOR OUTPUTS

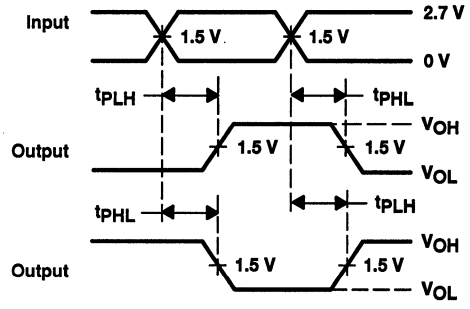
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



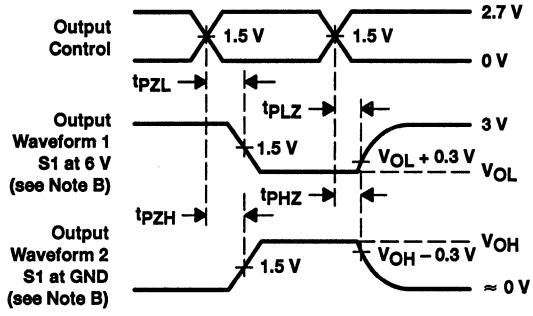
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



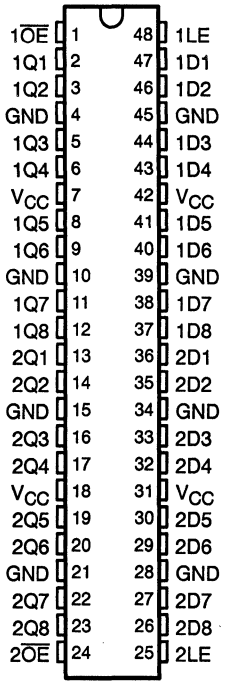
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{den}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit transparent D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC16373 is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. It can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

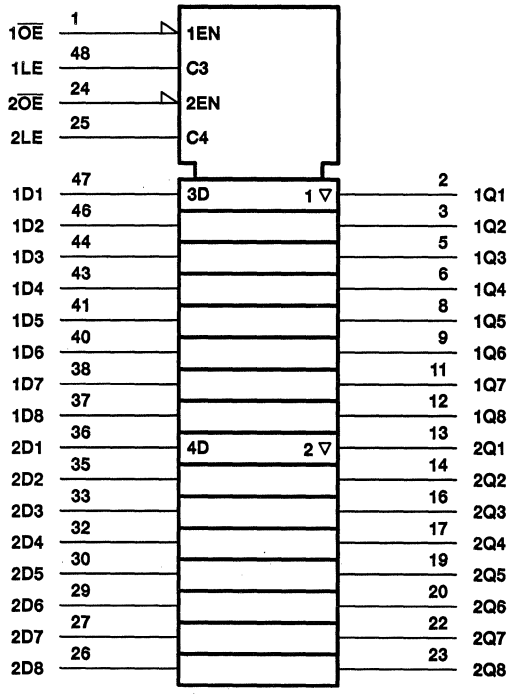
The SN74LVC16373 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each 8-bit section)

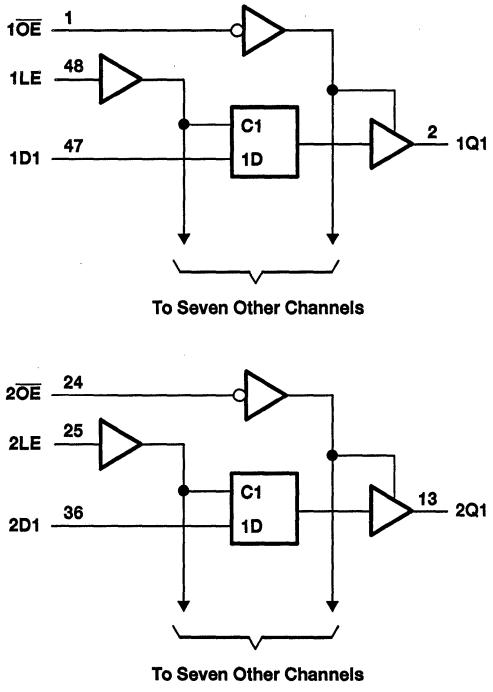
INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7	2.2			
				3	2.4			
		I_{OH} = –24 mA		3	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7			0.4	
		I_{OL} = 24 mA		3			0.55	
I_I		V_I = V_{CC} or GND		3.6			±5	µA
$I_{I(hold)}$	Data inputs	V_I = 0.8 V		3	75			µA
		V_I = 2 V			–75			
I_{OZ}		V_O = V_{CC} or GND		3.6			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i		V_I = V_{CC} or GND		3.3		3.5		pF
C_o		V_O = V_{CC} or GND		3.3		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	4		4		ns
t_{su}	Setup time, data before LE↓	2		2		ns
t_h	Hold time, data after LE↓	2		2		ns

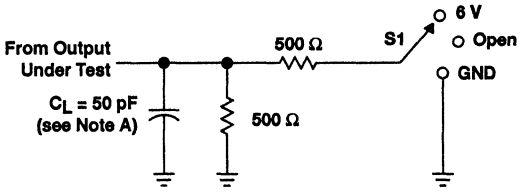
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	D	Q	1.5	7		8	ns
	LE		2	8		9	
t_{en}	$\overline{OE}$	Q	1.5	8		9	ns
t_{dis}	$\overline{OE}$	Q	1.5	7		8	ns

operating characteristics, T_A = 25°C

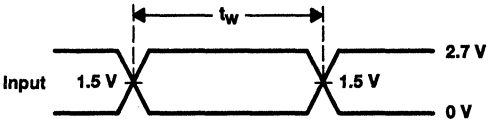
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 50 pF, f = 10 MHz	20	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

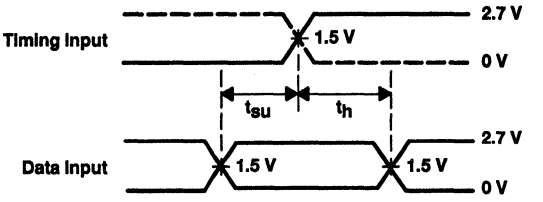


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

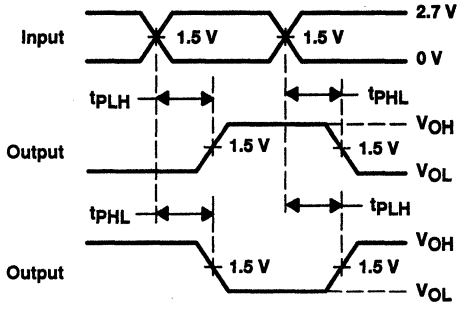
LOAD CIRCUIT FOR OUTPUTS



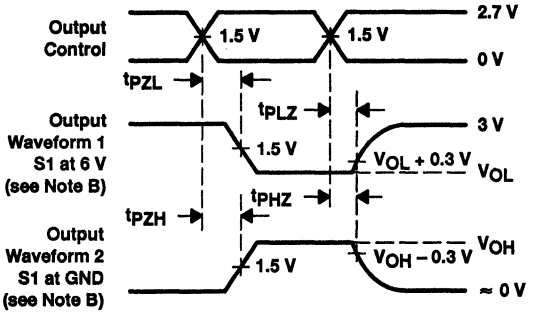
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



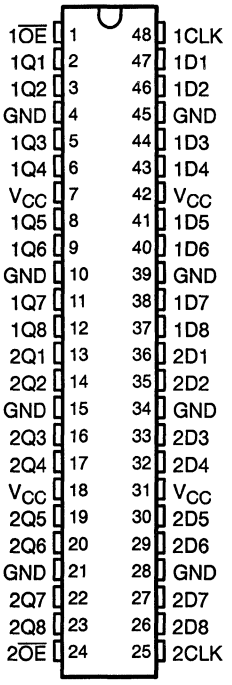
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit edge-triggered D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC16374 is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. On the positive transition of the clock (CLK) input, the Q outputs of the flip-flop take on the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the flip-flop. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

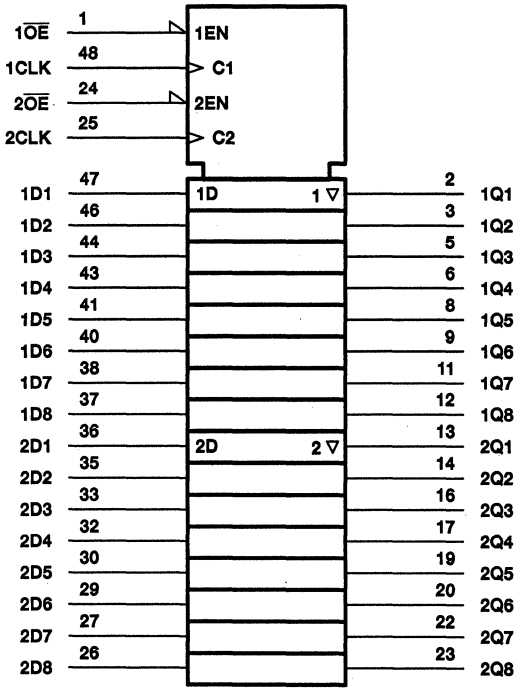
The SN74LVC16374 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE
(each flip-flop)

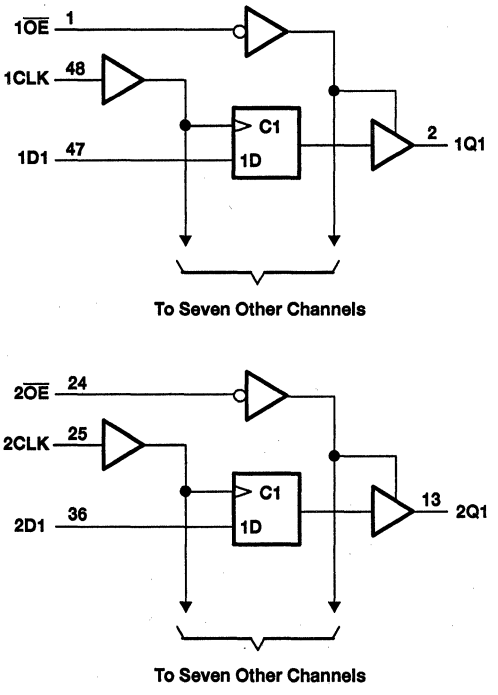
INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q_0
H	X	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$	Data inputs	V_I = 0.8 V		3 V	75			µA
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V		3.6 V			±500	
I_{OZ}		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i		V_I = V_{CC} or GND		3.3 V		3.5		pF
C_o		V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

timing requirements over recommended operating free-air temperature range (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	100	0	80	MHz
t_w	Pulse duration, CLK high or low		4		4		ns
t_{su}	Setup time, data before CLK↑	High or low	2		3		ns
t_h	Hold time, data after CLK↑	High or low	1.5		1.5		ns

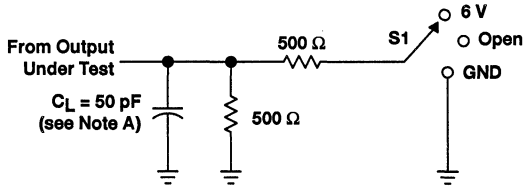
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			100		80		MHz
t_{pd}	CLK	Q	1.5	7.5	1.5	8.5	ns
t_{en}	$\overline{OE}$	Q	1.5	7.5	1.5	8.5	ns
t_{dis}	$\overline{OE}$	Q	1.5	7	1.5	8	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

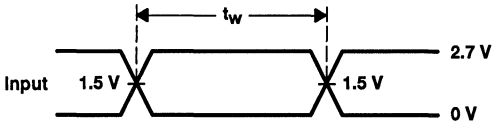
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 50 pF, f = 10 MHz	22	pF
		Outputs disabled		9	

PARAMETER MEASUREMENT INFORMATION

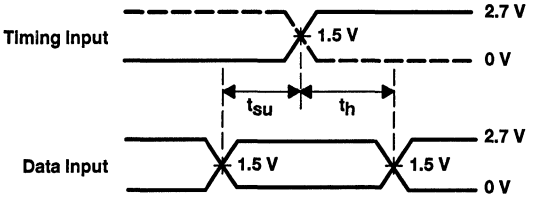


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

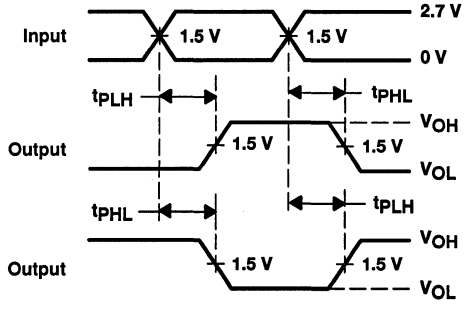
LOAD CIRCUIT FOR OUTPUTS



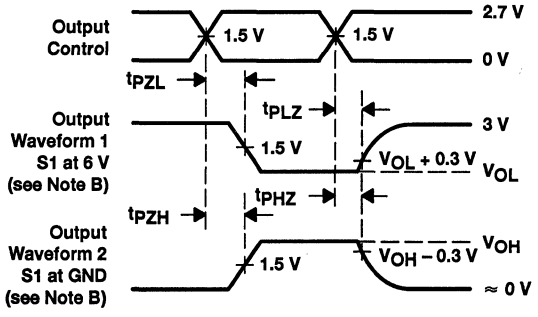
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



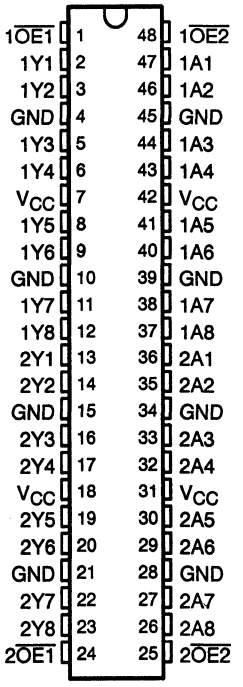
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

- Member of the Texas Instruments *Widebus*™ Family
- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC16540 provides a high-performance bus interface for wide datapaths.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ($\overline{OE1}$ or $\overline{OE2}$) input is high, all corresponding outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC16540 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

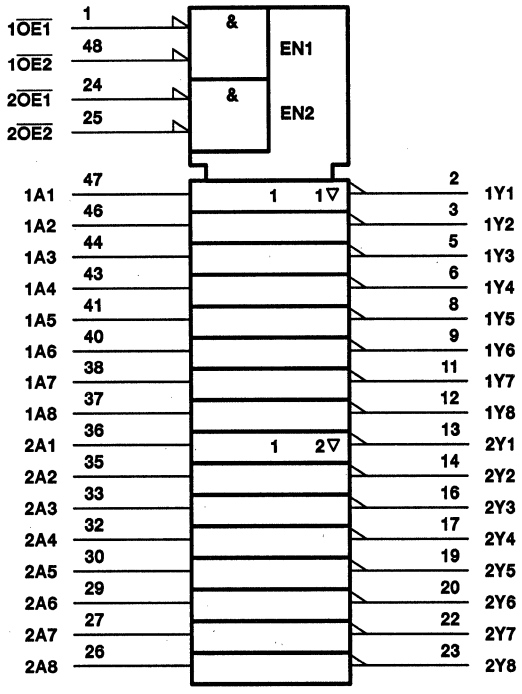
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	H
L	L	H	L
H	X	X	Z
X	H	X	Z

PRODUCT PREVIEW

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

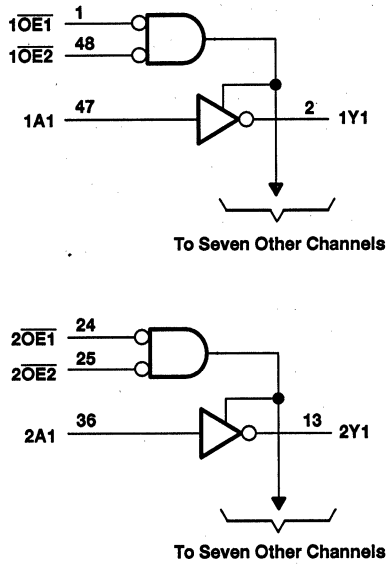
PRODUCT PREVIEW

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

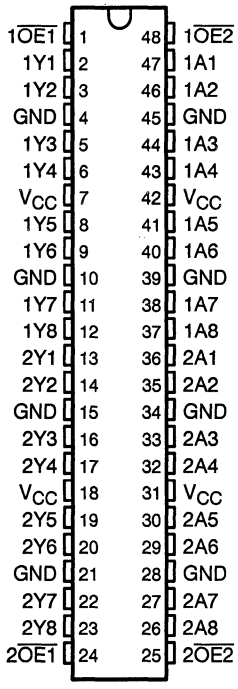
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = −24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	μA
$I_{I(hold)}$	Data inputs	V_I = 0.8 V		3 V	75			μA
		V_I = 2 V			−75			
I_{OZ}		V_O = 5.5 V or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i		V_I = V_{CC} or GND		3.3 V				pF
C_o		V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- Member of the Texas Instruments *Widebus*™ Family
- *EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC16541 is a noninverting 16-bit buffer composed of two 8-bit sections with separate output-enable signals. For either 8-bit buffer section, the two output-enable ($1\overline{OE1}$ and $1\overline{OE2}$ or $2\overline{OE1}$ and $2\overline{OE2}$) inputs must both be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 8-bit buffer section are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC16541 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each 8-bit section)

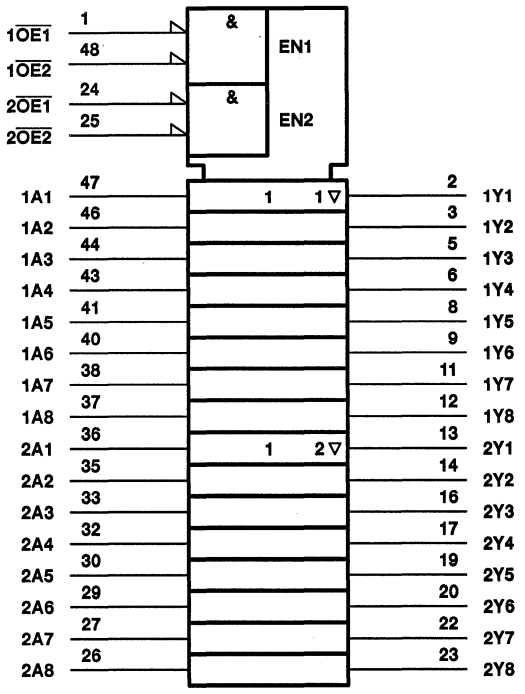
INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

PRODUCT PREVIEW

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

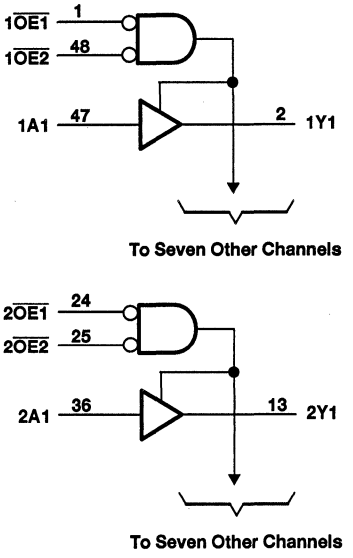
PRODUCT PREVIEW

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 6.5 V
Input voltage range, V_I ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state or power-off state, V_O (see Note 1) ..... −0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 0.85 W
DL package ..... 1.2 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

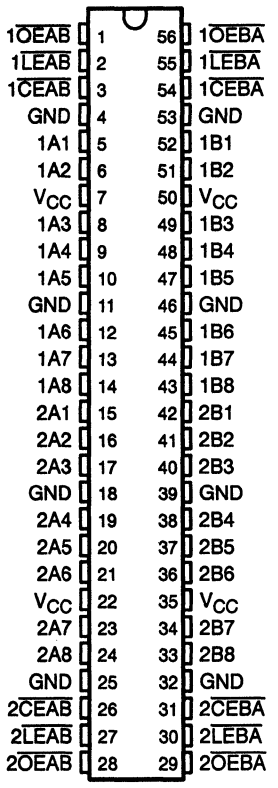
PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 µA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	µA
$I_{I(hold)}$	Data inputs	V_I = 0.8 V		3 V	75			µA
		V_I = 2 V			–75			
I_{OZ}		V_O = 5.5 V or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	µA
C_i		V_I = V_{CC} or GND		3.3 V				pF
C_o		V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are measured at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit registered transceiver is designed for low-voltage (3.3-V) V_{CC} operation.

The SN74LVC16543 can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low in order to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ puts the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar but requires using the $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$ inputs.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVC16543 is characterized for operation from –40°C to 85°C.

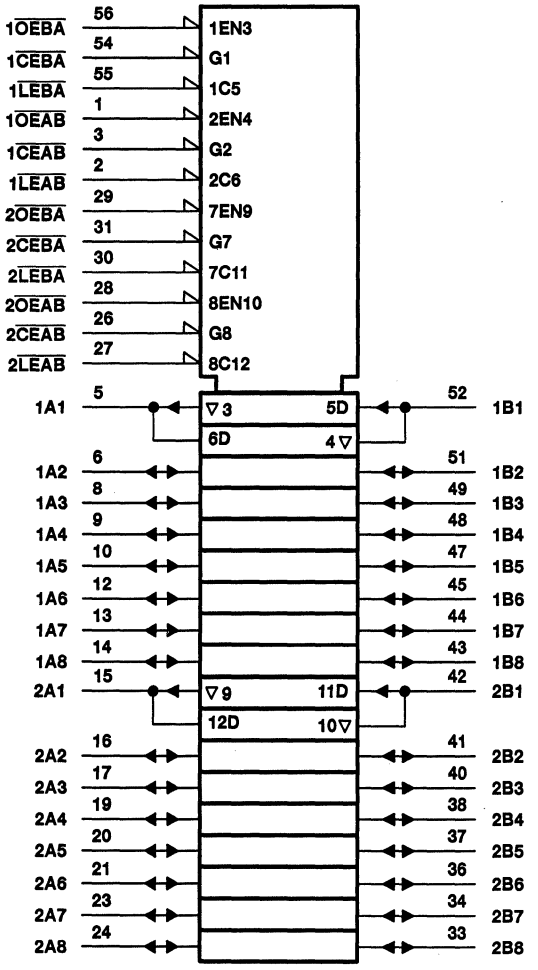
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE† (each 8-bit section)

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

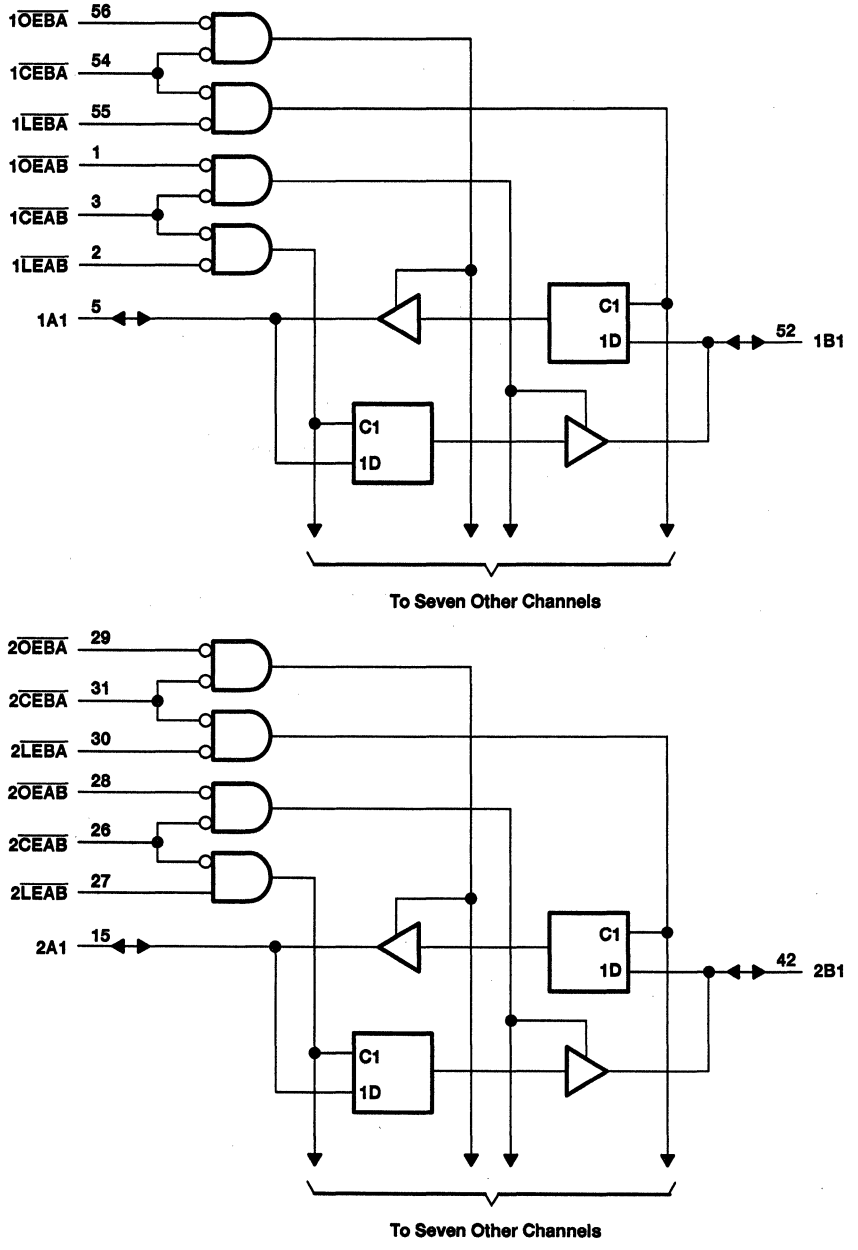
† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... −50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	$V_I = V_{CC}$ or GND		3.6 V			±5	μA
$I_{I(hold)}$	A or B ports	V_I = 0.8 V		3 V	75			μA
		V_I = 2 V			–75			
I_{OZ}§		$V_O = V_{CC}$ or GND		3.6 V			±10	μA
I_{CC}		$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	$V_I = V_{CC}$ or GND		3.3 V		3		pF
C_{io}	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

		V_{CC} = 3.3 V ±0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, $\overline{LE}$ or $\overline{CE}$ low	4		4		ns
t_{su}	Setup time, Data before $\overline{LE}$, $\overline{CE}$	2		2		ns
t_h	Hold time, Data after $\overline{LE}$, $\overline{CE}$	2		2		ns

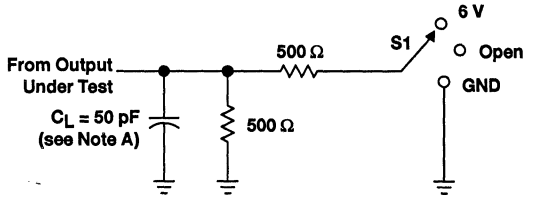
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ±0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	8	1.5	9	ns
t_{pd}	$\overline{LE}$	A or B	1.5	9	1.5	10	ns
t_{en}	$\overline{CE}$	A or B	1.5	9	1.5	10	ns
t_{dis}	$\overline{CE}$	A or B	1.5	9	1.5	10	ns
t_{en}	$\overline{OE}$	A or B	1.5	8.5	1.5	9.5	ns
t_{dis}	$\overline{OE}$	A or B	1.5	8.5	1.5	9.5	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

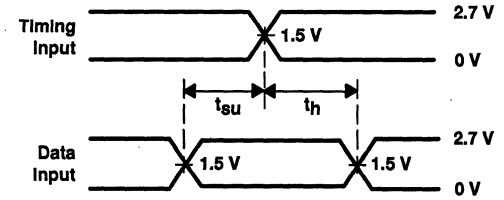
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	21	pF
		Outputs disabled		3.5	

PARAMETER MEASUREMENT INFORMATION

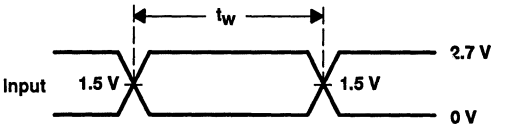


LOAD CIRCUIT

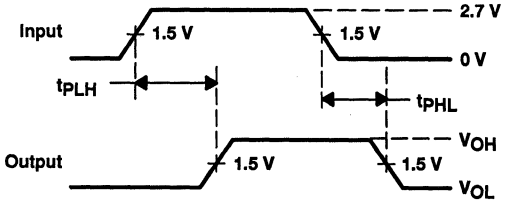
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



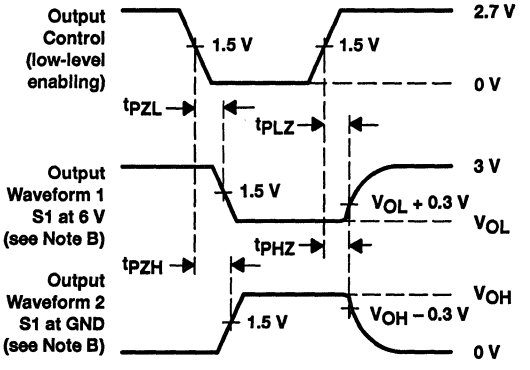
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

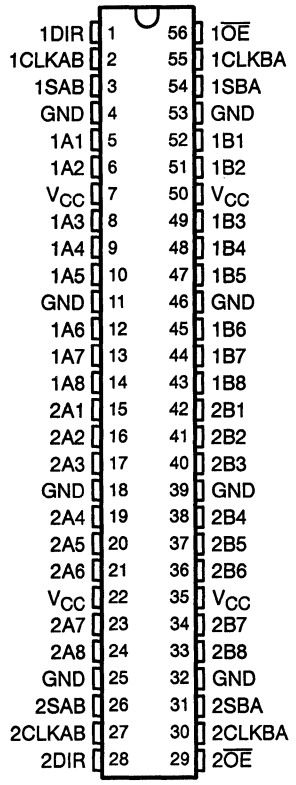


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit bus transceiver and register is designed for low-voltage (3.3-V) V_{CC} operation.

The SN74LVC16646 can be used as two 8-bit transceivers or one 16-bit transceiver. The device consists of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers.

Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74LVC16646.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs control the transceiver functions. In the transceiver mode, data present at the high-impedance port may be stored in either register or in both. The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. DIR determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data may be stored in one register and/or B data may be stored in the other register.

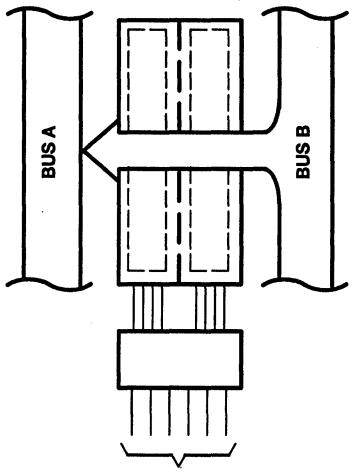
When an output function is disabled, the input function is still enabled and can be used to store and transmit data. Only one of the two buses, A or B, may be driven at a time.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry holds unused or floating data inputs at a valid logic level.

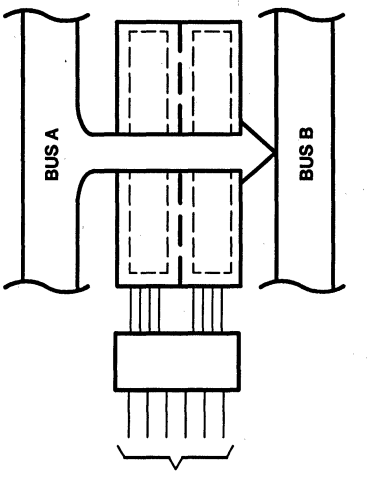
The SN74LVC16646 is characterized for operation from –40°C to 85°C.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.



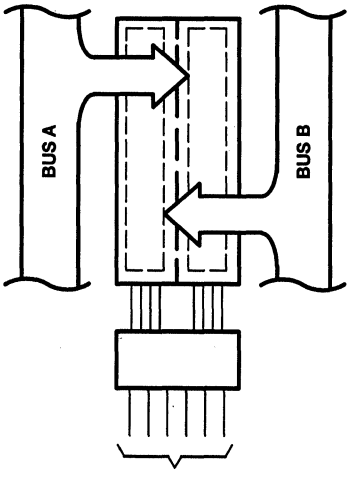
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



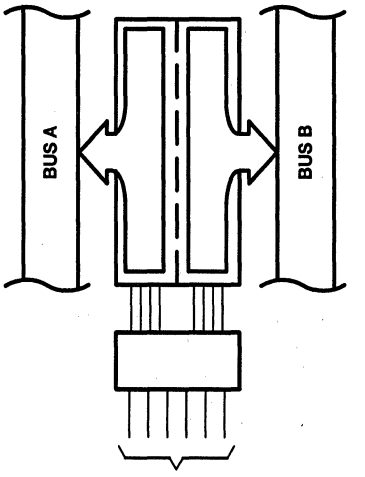
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B

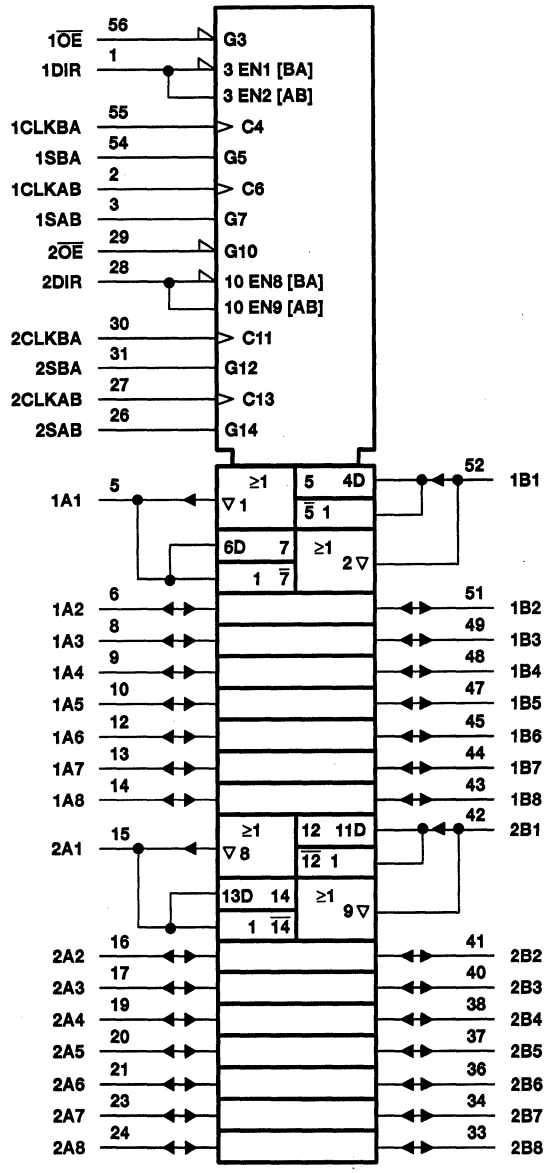


$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA
TO A AND/OR B

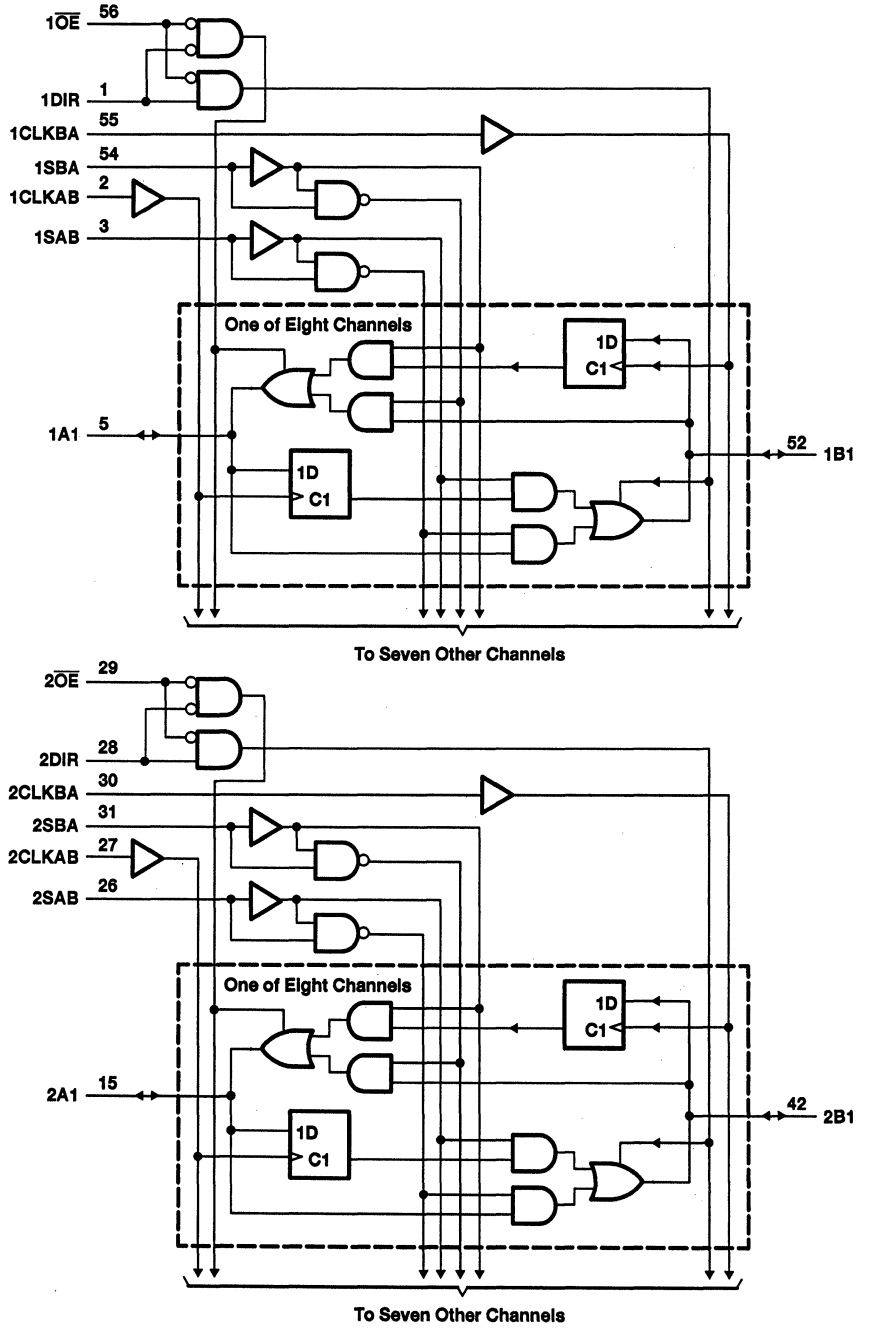
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



FUNCTION TABLE

INPUTS						DATA I/Os		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1 THRU A8	B1 THRU B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

† The data output functions may be enabled or disabled by various signals at the $\overline{OE}$ and DIR inputs. Data input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		−12	mA
		V_{CC} = 3 V		−24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		−40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
		I_{OH} = −12 mA		2.7	2.2			
				3	2.4			
		I_{OH} = −24 mA		3	2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7			0.4	
		I_{OL} = 24 mA		3			0.55	
I_I	Control inputs	V_I = V_{CC} or GND		3.6			±5	μA
$I_{I(hold)}$	A or B ports	V_I = 0.8 V		3	75			μA
		V_I = 2 V			−75			
		V_I = 0 to 3.6 V		3.6			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6			40	μA
ΔI_{CC}		One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3		3		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	100	0	80	MHz
t_w	Pulse duration, CLK high or low		4.5		4.5		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high or low	5		5		ns
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑	Data high or low	0		0		ns

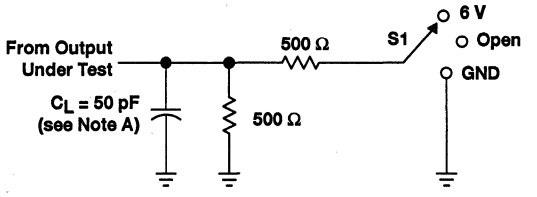
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			100		80		MHz
t_{pd}	A or B	B or A	1.5	7		8	ns
	CLKAB or CLKBA	A or B	1.5	8.5		9.5	
	SAB or SBA		1.5	8.5		9.5	
t_{en}	$\overline{OE}$	A or B	1.5	8		9	ns
	DIR		1.5	8		9	
t_{dis}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
	DIR		1.5	8.5		9.5	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

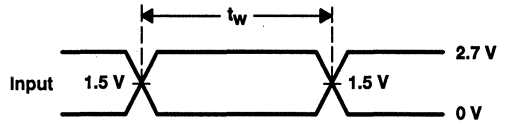
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	17	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

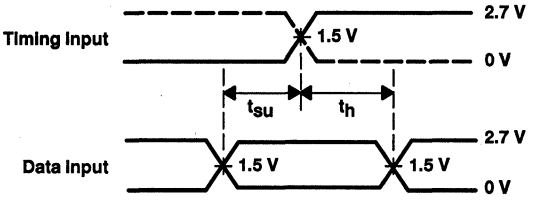


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

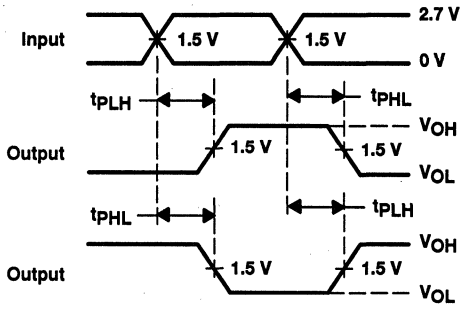
LOAD CIRCUIT FOR OUTPUTS



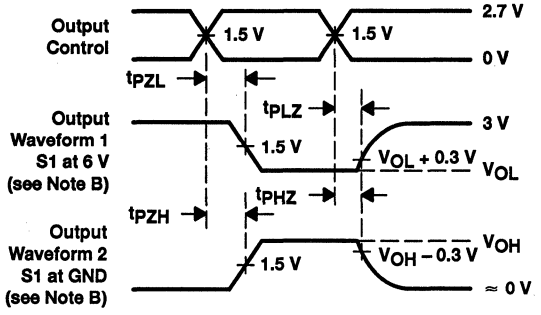
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



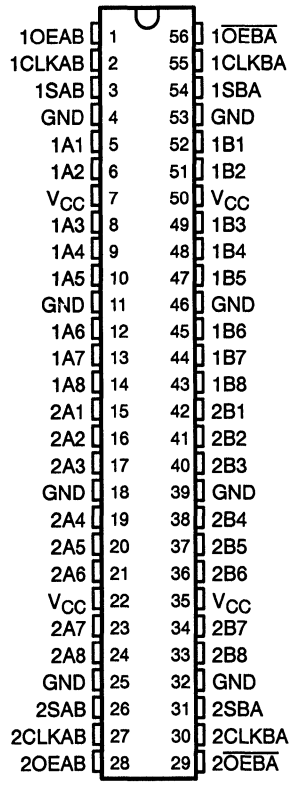
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit bus transceiver and register is designed for low-voltage (3.3-V) V_{CC} operation.

The SN74LVC16652 consists of D-type flip-flops and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal storage registers. The device can be used as two 8-bit transceivers or one 16-bit transceiver.

Complementary output-enable (OEAB and $\overline{\text{OEBA}}$) inputs control the transceiver functions. Select-control (SAB and SBA) inputs select whether real-time or stored data is transferred. A low input level selects real-time data, and a high input level selects stored data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74LVC16652.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

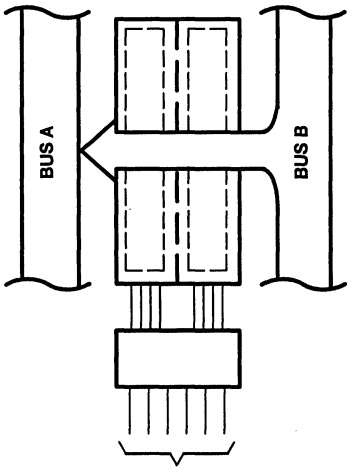
description (continued)

Data on the A or B bus, or both, can be stored in the internal D flip-flops by low-to-high transitions at the appropriate clock (CLKAB or CLKBA) inputs regardless of the levels on the select-control or output-enable inputs. When SAB and SBA are in the real-time transfer mode, it is also possible to store data without using the internal D-type flip-flops by simultaneously enabling OEAB and $\overline{\text{OEBA}}$. In this configuration, each output reinforces its input. When all other data sources to the two sets of bus lines are at high impedance, each set of bus lines remains at its last level configuration.

To ensure the high-impedance state during power up or power down, $\overline{\text{OEBA}}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

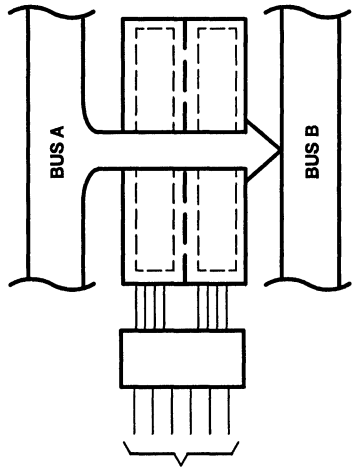
Active bus-hold circuitry holds unused or floating data inputs at a valid logic level.

The SN74LVC16652 is characterized for operation from –40°C to 85°C.



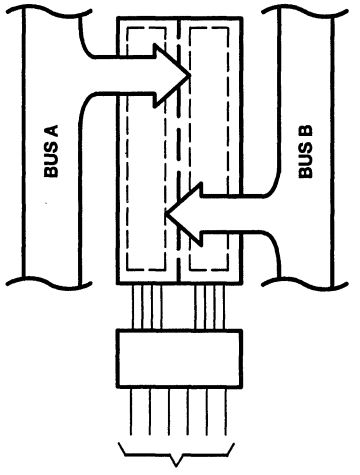
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



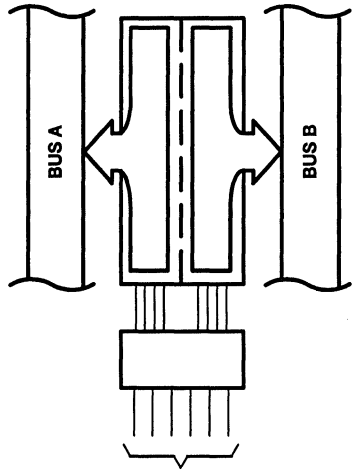
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B

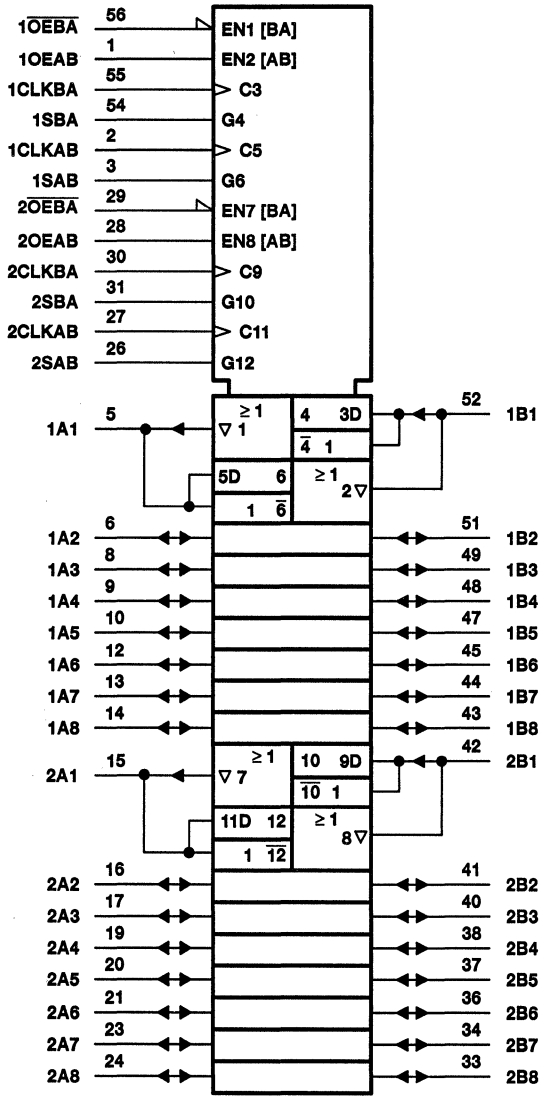


OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA
H	L	H or L	H or L	H	H

TRANSFER STORED DATA
TO A AND/OR B

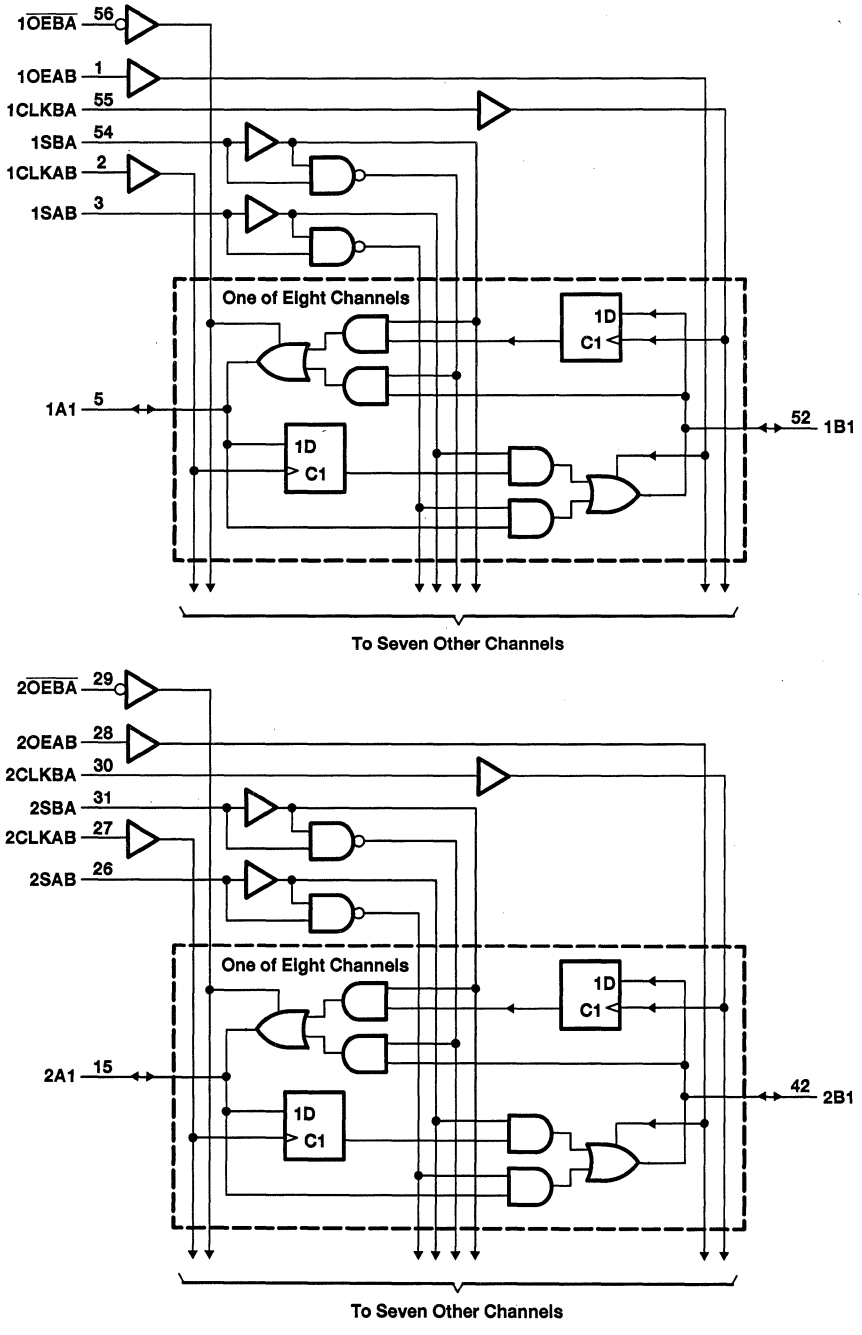
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



FUNCTION TABLE

INPUTS						DATA I/O†		OPERATION OR FUNCTION
OEAB	$\overline{OEBA}$	CLKAB	CLKBA	SAB	SBA	A1 THRU A8	B1 THRU B8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified‡	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified‡	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and Stored B data to A bus

† The data output functions may be enabled or disabled by a variety of level combinations at the OEAB or $\overline{OEBA}$ inputs. Data input functions are always enabled; i.e., data at the bus terminals is stored on every low-to-high transition on the clock inputs.
‡ Select control = L; clocks can occur simultaneously.
Select control = H; clocks must be staggered in order to load both registers.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to 4.6 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

§ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta V$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA	MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA	2.7	2.2			
			3	2.4			
		I_{OH} = –24 mA	3	2			
V_{OL}		I_{OL} = 100 μA	MIN to MAX			0.2	V
		I_{OL} = 12 mA	2.7			0.4	
		I_{OL} = 24 mA	3			0.55	
I_I	Control inputs	V_I = V_{CC} or GND	3.6			±5	μA
$I_{I(hold)}$	A or B ports	V_I = 0.8 V	3	75			μA
		V_I = 2 V		–75			
		V_I = 0 to 3.6 V	3.6			±500	
I_{OZ}§		V_O = V_{CC} or GND	3.6			±10	μA
I_{CC}		V_I = V_{CC} or GND, I_O = 0	3.6			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND	3.3		3		pF
C_{io}	A or B ports	V_O = V_{CC} or GND	3.3		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	100	0	80	MHz
t_w	Pulse duration, CLK high or low		4.5		4.5		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high or low	5		5		ns
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑	Data high or low	0		0		ns

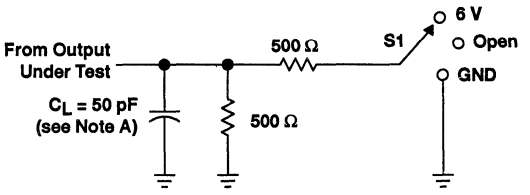
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{max}			100		80		MHz
t_{pd}	A or B	B or A	1.5	7		8	ns
	CLKAB or CLKBA	A or B	1.5	8.5		9.5	
	SAB or SBA		1.5	8.5		9.5	
t_{en}	$\overline{OE}$ or OE	A or B	1.5	8		9	ns
t_{dis}	$\overline{OE}$ or OE	A or B	1.5	8.5		9.5	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

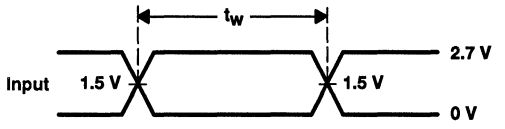
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	25	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

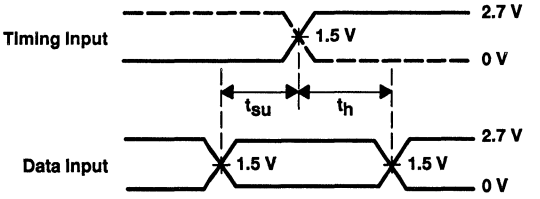


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

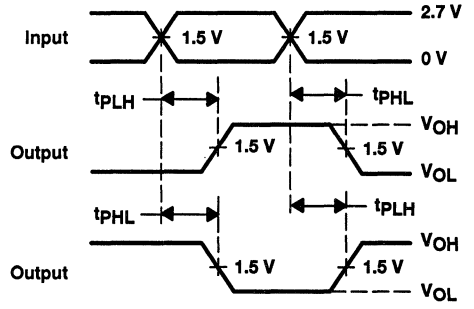
LOAD CIRCUIT FOR OUTPUTS



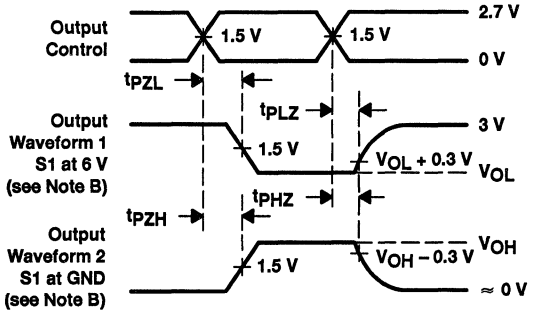
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



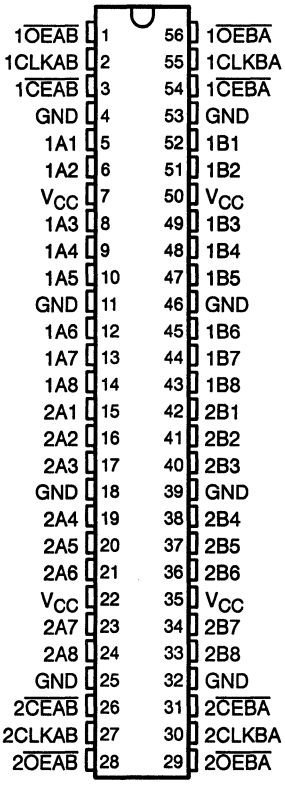
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit registered transceiver is designed for low-voltage (3.3-V) V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC16952 contains two sets of D-type flip-flops for temporary storage of data flowing in either direction. It can be used as two 8-bit transceivers or one 16-bit transceiver. Data on the A or B bus is stored in the registers on the low-to-high transition of the clock (CLKAB or CLKBA) input provided that the clock-enable ($\overline{CEAB}$ or $\overline{CEBA}$) input is low. Taking the output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) input low accesses the data on either port.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74LVC16952 is characterized for operation from –40°C to 85°C.

PRODUCT PREVIEW

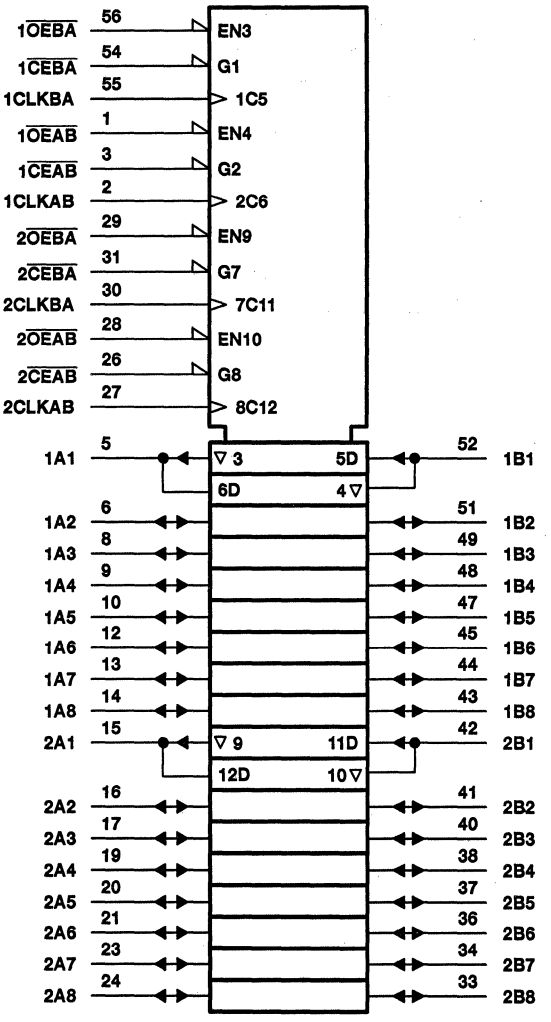
EPIC and Widebus are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CLKENAB}$	CLKAB	$\overline{OEAB}$	A	B
H	X	L	X	B_0‡
X	L	L	X	B_0‡
L	↑	L	L	L
L	↑	L	H	H
X	X	H	X	Z

† A-to-B data flow is shown; B-to-A data flow is similar but uses $\overline{CLKENBA}$, CLKBA, and $\overline{OEBA}$.
‡ Level of B before the indicated steady-state input conditions were established

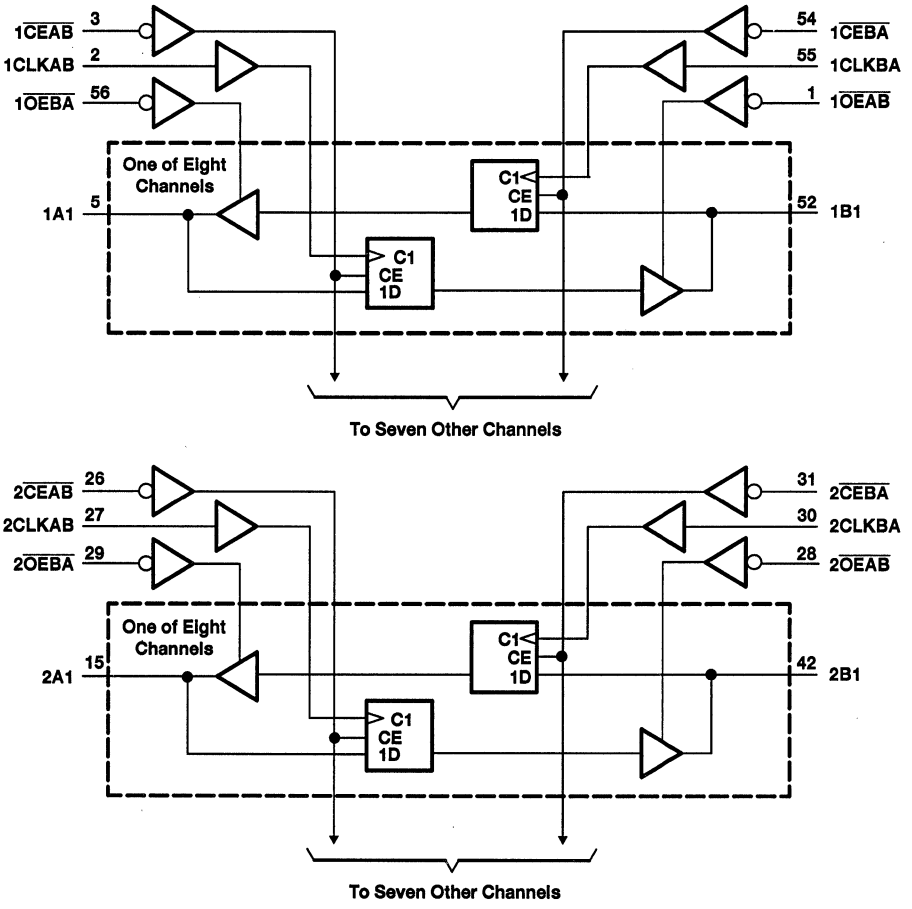
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

PRODUCT PREVIEW

logic diagram (positive logic)



PRODUCT PREVIEW

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... –0.5 V to 6.5 V
Input voltage range, V_I ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance state
or power-off state, V_O (see Note 1) ..... –0.5 V to 6.5 V
Voltage range applied to any output in the high
or low state, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) ..... –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	μA
$I_{I(hold)}$	A or B ports	V_I = 0.8 V		3 V	75			μA
		V_I = 2 V			–75			
I_{OZ}§		V_O = 5.5 V or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V				pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

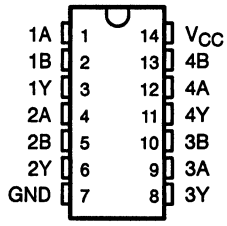
PRODUCT PREVIEW

Contents

SCLS182A – FEBRUARY 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-input positive-NAND gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV00 performs the Boolean functions $Y = \overline{A \bullet B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

The SN74LV00 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

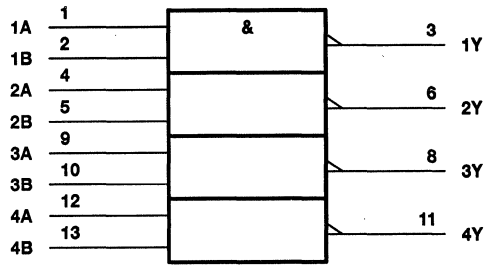
The SN74LV00 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

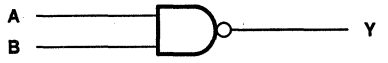
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

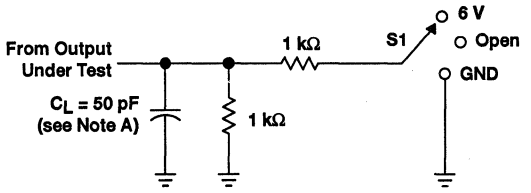
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		9	18		23	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

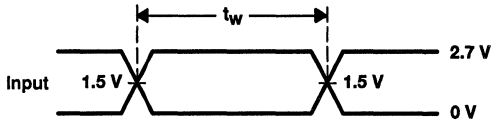
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	23	pF

PARAMETER MEASUREMENT INFORMATION

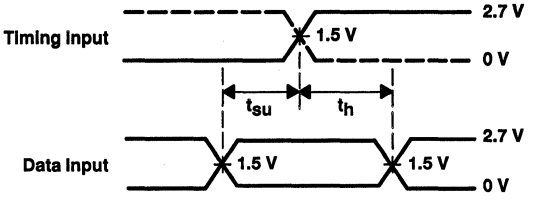


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

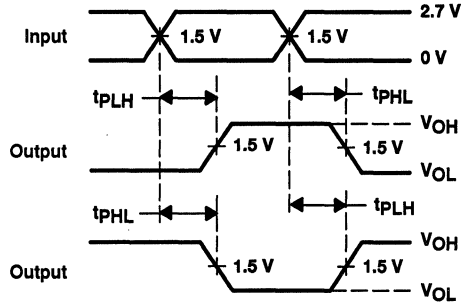
LOAD CIRCUIT FOR OUTPUTS



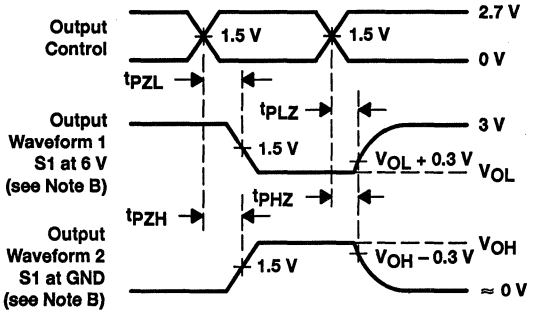
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



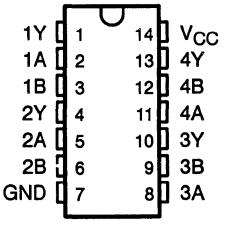
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-input positive-NOR gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV02 performs the Boolean functions $Y = \overline{A + B}$ or $Y = \overline{A} \bullet \overline{B}$ in positive logic.

The SN74LV02 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

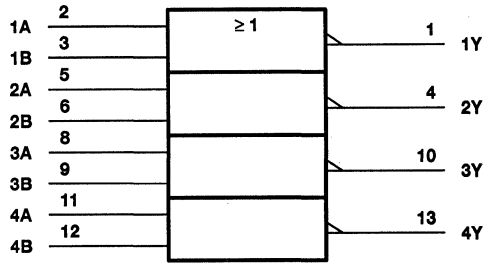
The SN74LV02 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	X	L
X	H	L
L	L	H

EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

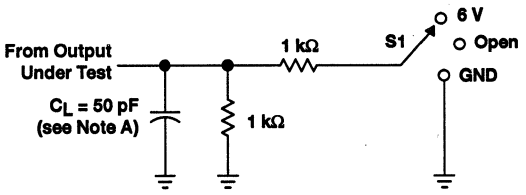
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		9	16		20	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

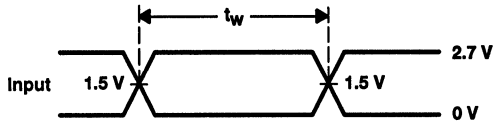
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	16	pF

PARAMETER MEASUREMENT INFORMATION

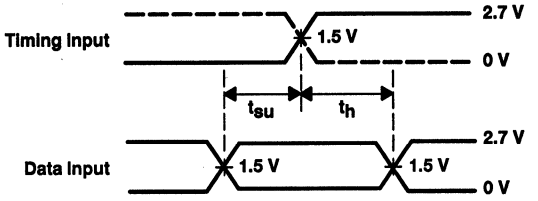


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

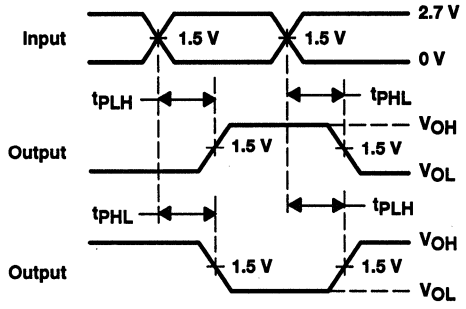
LOAD CIRCUIT FOR OUTPUTS



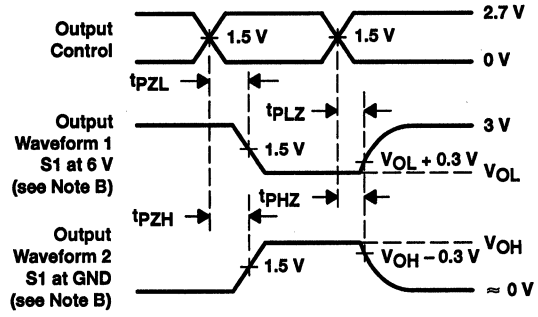
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

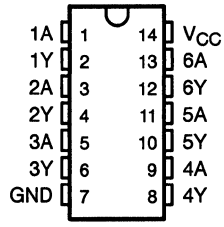
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

SCLS184A – FEBRUARY 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This hex inverter is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV04 contains six independent inverters. The device performs the Boolean function $Y = \overline{A}$.

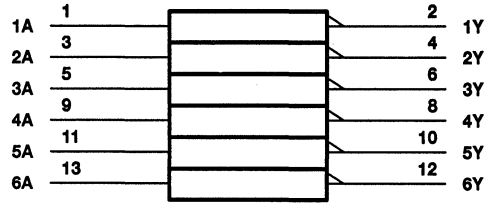
The SN74LV04 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN74LV04 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

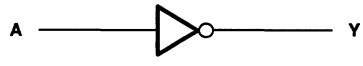
INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each inverter (positive logic)



EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}‡	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = −6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	$V_I = V_{CC}$ or GND		3.6 V			±1	µA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	$V_I = V_{CC}$ or GND		3.3 V		2.5		pF

‡ For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

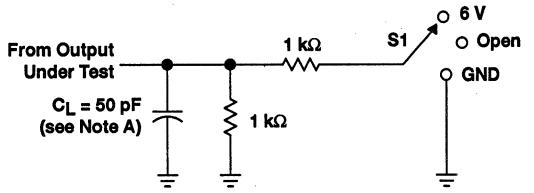
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		7	15		19	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

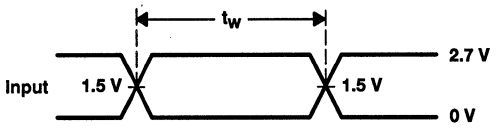
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF, f = 10 MHz	18	pF

PARAMETER MEASUREMENT INFORMATION

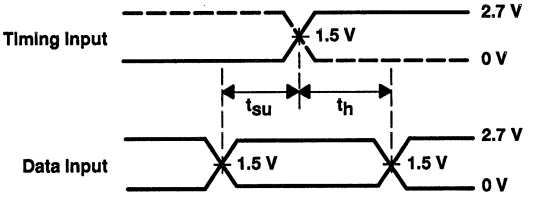


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

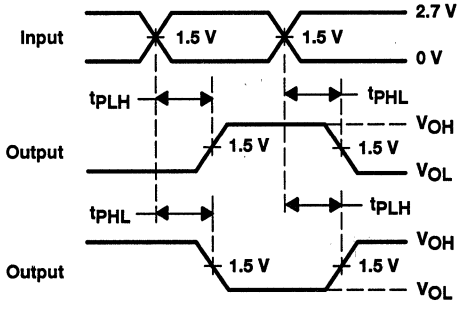
LOAD CIRCUIT FOR OUTPUTS



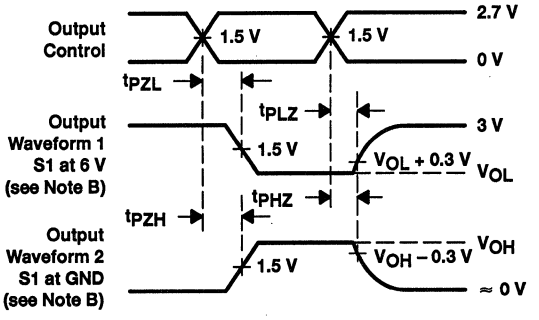
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

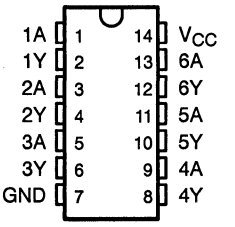
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

SCLS185A – FEBRUARY 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This hex inverter is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVU04 contains six independent inverters with unbuffered outputs. The device performs the Boolean function $Y = \overline{A}$.

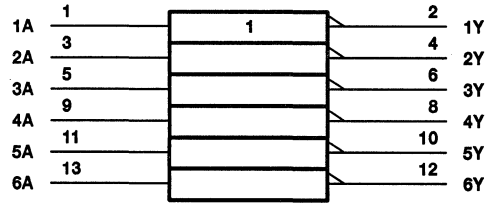
The SN74LVU04 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN74LVU04 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

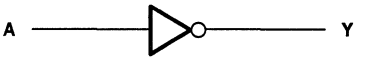
INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each inverter (positive logic)



EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2.4			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.5	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}‡	MIN	TYP	MAX	UNIT
V_{OH}	$V_I = V_{IL}$,	I_{OH} = −100 µA	MIN to MAX	V_{CC}−0.5			V
	V_I = GND,	I_{OH} = − 6 mA	3 V	2.4			
V_{OL}	$V_I = V_{IH}$,	I_{OL} = 100 µA	MIN to MAX			0.5	V
	$V_I = V_{CC}$,	I_{OL} = 6 mA	3 V			0.4	
I_I	$V_I = V_{CC}$ or GND		3.6 V			±1	µA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	$V_I = V_{CC}$ or GND		3.3 V		7		pF

‡ For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

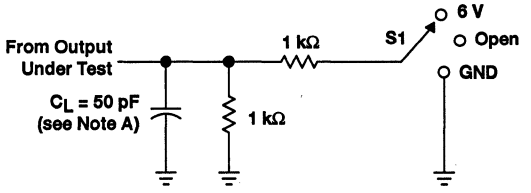
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		6	14		18	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

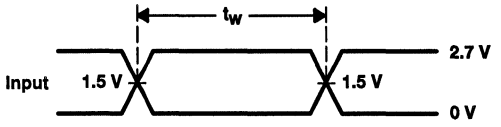
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF, f = 10 MHz	7	pF

PARAMETER MEASUREMENT INFORMATION

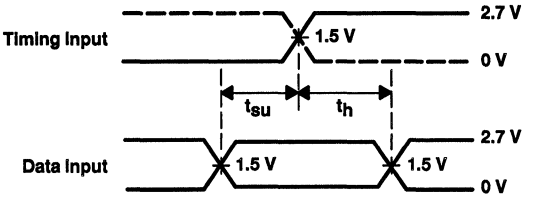


LOAD CIRCUIT FOR OUTPUTS

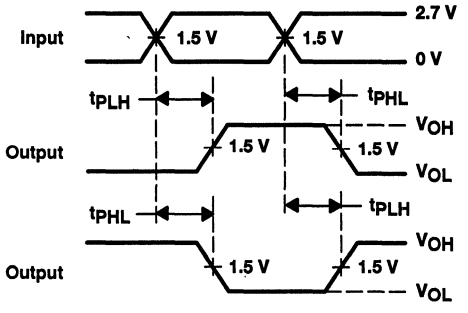
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



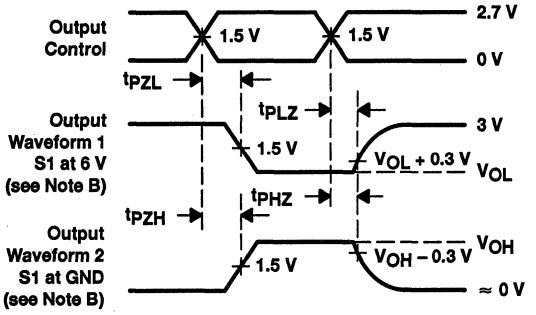
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



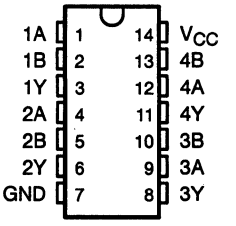
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-input positive-AND gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV08 performs the Boolean functions $Y = A \bullet B$ or $Y = \overline{\overline{A} + \overline{B}}$ in positive logic.

The SN74LV08 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

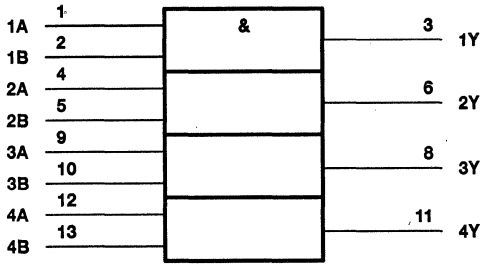
The SN74LV08 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	H	H
L	X	L
X	L	L

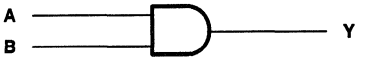
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or DW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

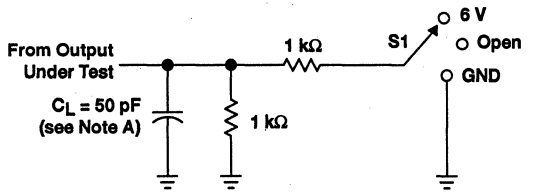
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		10	18		23	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

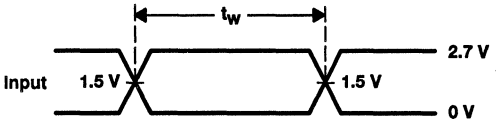
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	24	pF

PARAMETER MEASUREMENT INFORMATION

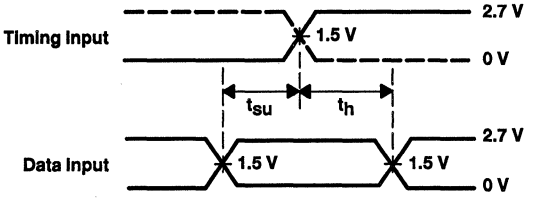


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

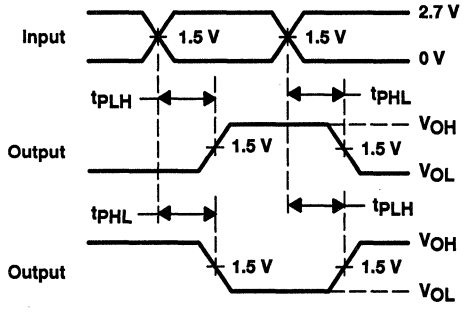
LOAD CIRCUIT FOR OUTPUTS



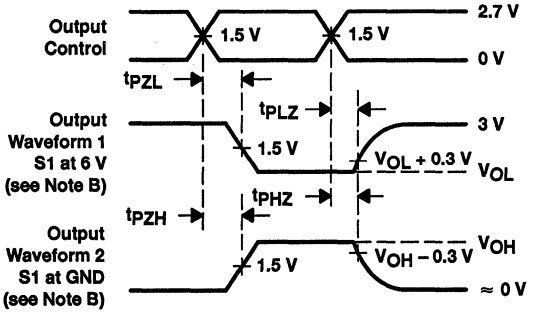
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



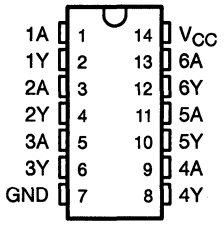
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This hex Schmitt-trigger inverter is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV14 contains six independent inverters. The device performs the Boolean function $Y = \overline{A}$.

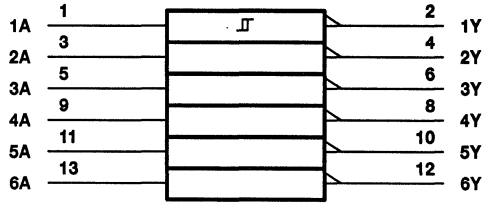
The SN74LV14 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN74LV14 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each inverter)

INPUT A	OUTPUT Y
H	L
L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each inverter (positive logic)

EPIC is a trademark of Texas Instruments Incorporated.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2.4			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.4	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{T+} Positive-going threshold			2.7 V	1		2	V
			3 V	1.2		2.2	
			3.6 V	1.5		2.4	
V_{T-} Negative-going threshold			2.7 V	0.4		1.4	V
			3 V	0.6		1.5	
			3.6 V	0.8		1.8	
ΔV_T Hysteresis ($V_{T+} - V_{T-}$)			2.7 V	0.3		1.1	V
			3 V	0.4		1.2	
			3.6 V	0.4		1.2	
V_{OH}	$I_{OH} = -100$ μA		MIN to MAX	$V_{CC}-0.2$			V
	$I_{OH} = -6$ mA		3 V	2.4			
V_{OL}	$I_{OL} = 100$ μA		MIN to MAX			0.2	V
	$I_{OL} = 6$ mA		3 V			0.4	
I_I	$V_I = V_{CC}$ or GND		3.6 V			±1	μA
I_{CC}	$V_I = V_{CC}$ or GND,	$I_O = 0$	3.6 V			20	μA
ΔI_{CC}	One input at $V_{CC} - 0.6$ V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	$V_I = V_{CC}$ or GND		3.3 V		2.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

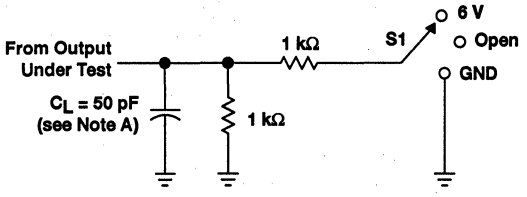
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		13	30		36	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

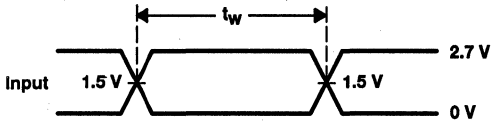
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per inverter	C_L = 50 pF, f = 10 MHz	22	pF

PARAMETER MEASUREMENT INFORMATION

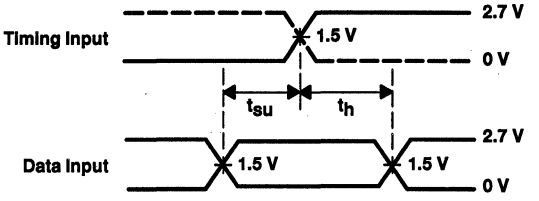


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

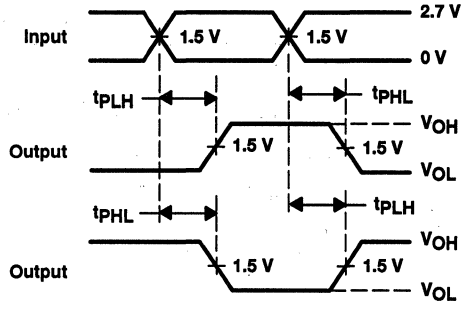
LOAD CIRCUIT FOR OUTPUTS



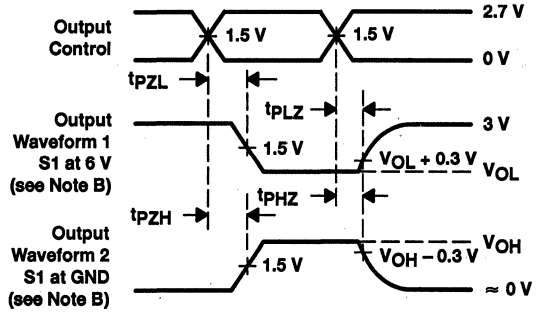
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



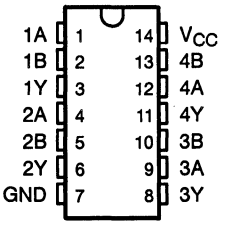
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple 2-input positive-OR gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV32 performs the Boolean functions $Y = A + B$ or $Y = \overline{\overline{A} \bullet \overline{B}}$ in positive logic.

The SN74LV32 is packaged in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

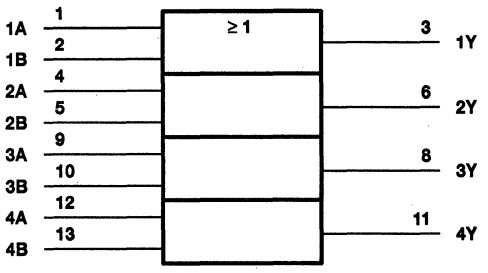
The SN74LV32 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

INPUTS		OUTPUT
A	B	Y
H	X	H
X	H	H
L	L	L

EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

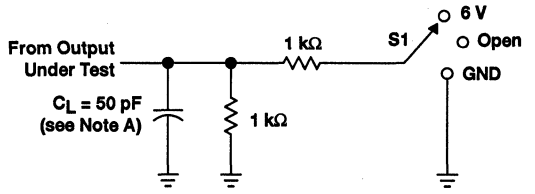
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		8	17		22	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

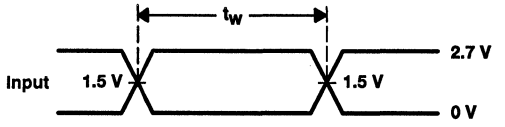
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per gate	C_L = 50 pF, f = 10 MHz	23	pF

PARAMETER MEASUREMENT INFORMATION

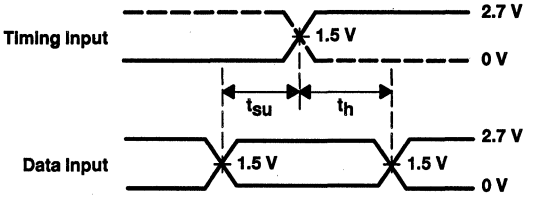


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

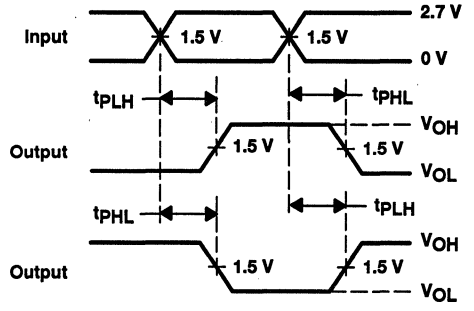
LOAD CIRCUIT FOR OUTPUTS



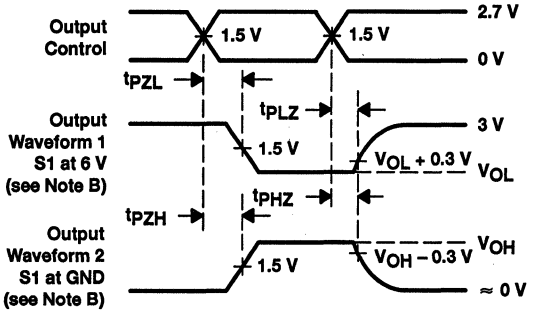
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

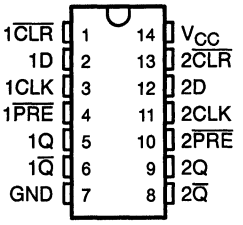
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

SCLS189A – FEBRUARY 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This dual positive-edge-triggered D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

A low level at the preset ($\overline{PRE}$) or clear ($\overline{CLR}$) inputs sets or resets the outputs regardless of the levels of the other inputs. When $\overline{PRE}$ and $\overline{CLR}$ are inactive (high), data at the data (D) inputs meeting the setup time requirements is transferred to the outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the D input may be changed without affecting the levels at the outputs.

The SN74LV74 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN74LV74 is characterized for operation from –40°C to 85°C.

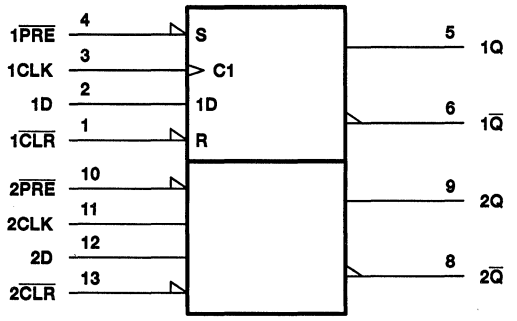
FUNCTION TABLE

INPUTS				OUTPUTS	
$\overline{PRE}$	$\overline{CLR}$	CLK	D	Q	$\overline{Q}$
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H†	H†
H	H	↑	H	H	L
H	H	↑	L	L	H
H	H	L	X	Q_0	$\overline{Q}_0$

† This configuration is nonstable; that is, it does not persist when $\overline{PRE}$ or $\overline{CLR}$ returns to its inactive (high) level.

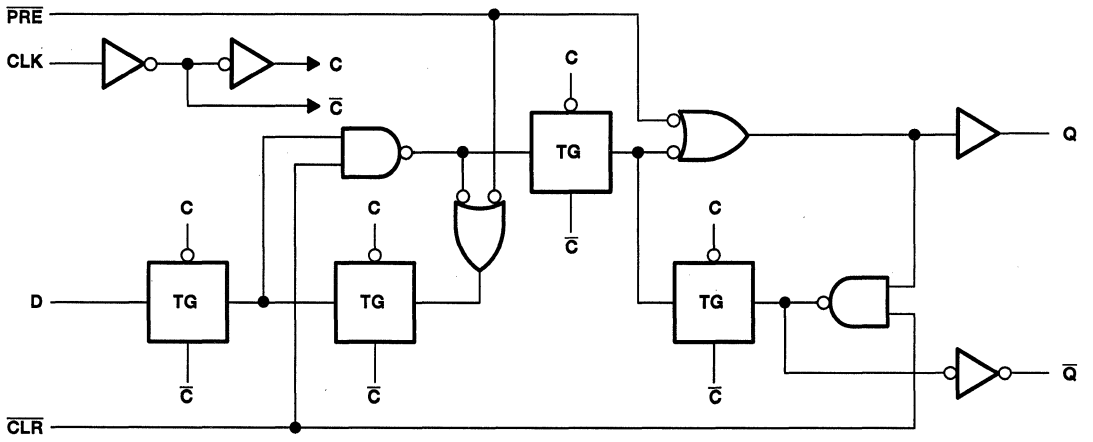
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each flip-flop (positive logic)



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}‡	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = −6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	$V_I = V_{CC}$ or GND		3.6 V			±1	µA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	$V_I = V_{CC}$ or GND		3.3 V		2.5		pF

‡ For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	24	0	19	MHz
t_w	Pulse duration	$\overline{PRE}$ or $\overline{CLR}$ low	20		25		ns
		CLK high or low	20		25		
t_{su}	Setup time, data before CLK↑	Data	13		16		ns
		$\overline{PRE}$ or $\overline{CLR}$ inactive	8		10		
t_h	Hold time, data after CLK↑		3		3		ns

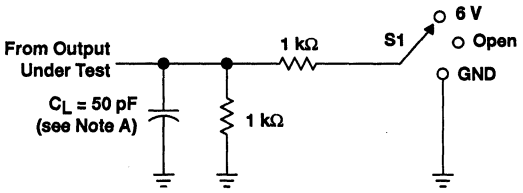
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
f_{max}			24	100		19		MHz
t_{pd}	$\overline{PRE}$ or $\overline{CLR}$	Q or $\overline{Q}$		16	34		43	ns
	CLK			15	28		35	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

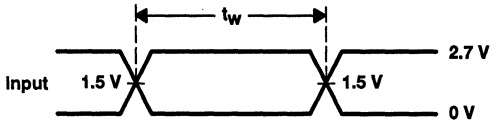
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	C_L = 50 pF, f = 10 MHz	32	pF

PARAMETER MEASUREMENT INFORMATION

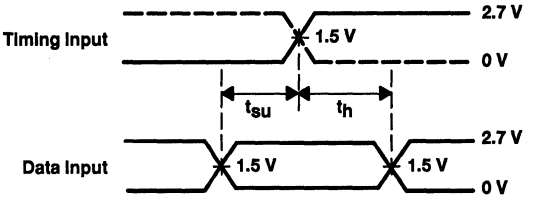


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

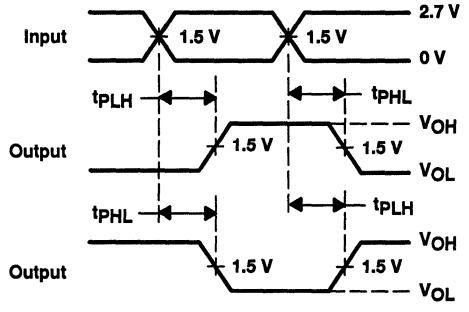
LOAD CIRCUIT FOR OUTPUTS



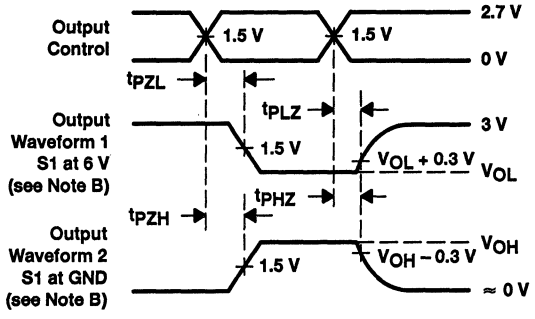
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



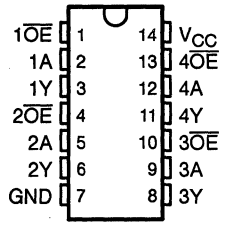
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This quadruple bus buffer gate is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV125 features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable ($\overline{OE}$) input is high.

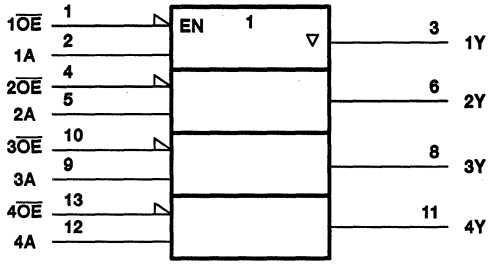
The SN74LV125 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

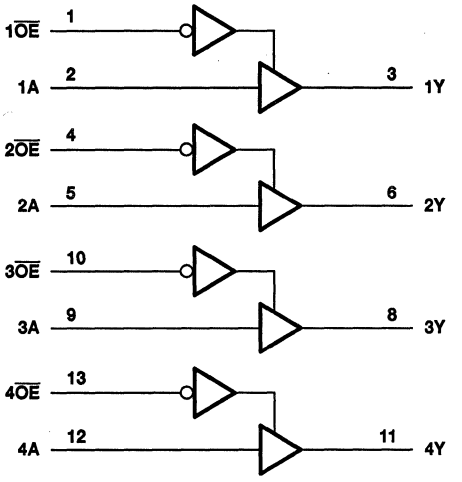
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Operating free-air temperature range, T_A ..... −40°C to 85°C
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−8	mA
I_{OL}	Low-level output current				8	mA
$\Delta t/\Delta V$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	I_{OH} = −100 µA		MIN to MAX‡	V_{CC}−0.2			V
	I_{OH} = −8 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX‡			0.2	V
	I_{OL} = 8 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	µA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_o	V_O = V_{CC} or GND		3.3 V		8		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

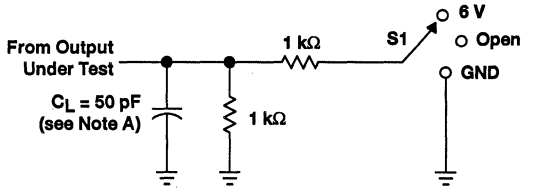
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP†	MAX	MIN	MAX	
t_{pd}	A	Y		10	21		26	ns
t_{en}	$\overline{OE}$	Y		11	29		36	ns
t_{dis}	$\overline{OE}$	Y		10	26		32	ns

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

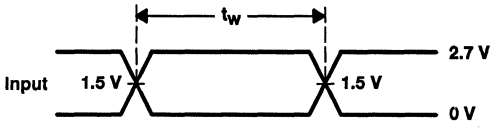
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	45	pF
		Outputs disabled		5	

PARAMETER MEASUREMENT INFORMATION

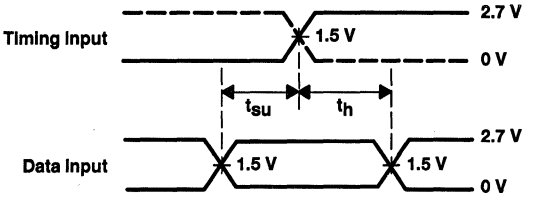


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

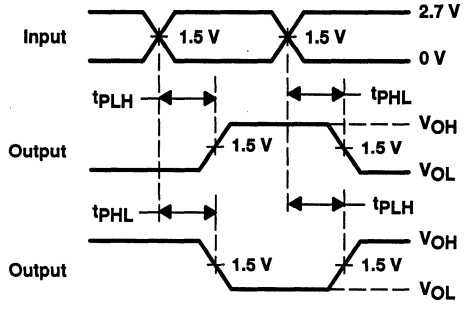
LOAD CIRCUIT FOR OUTPUTS



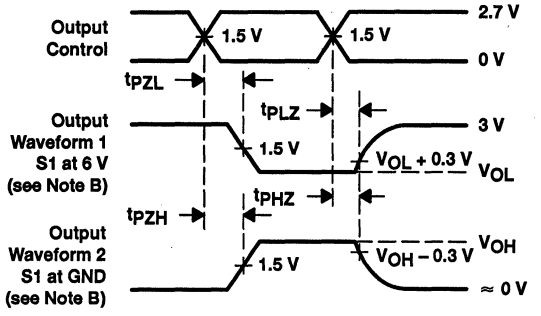
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

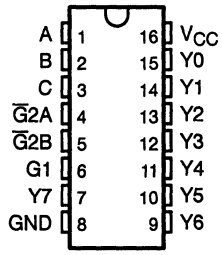
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

SCLS190A – FEBRUARY 1993 – REVISED JULY 1995

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This 3-line to 8-line decoder/demultiplexer is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV138 is designed to be used in high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, this decoder can be used to minimize the effects of system decoding. When employed with high-speed memories utilizing a fast enable circuit, the delay times of this decoder and the enable time of the memory are usually less than the typical access time of the memory. This means that the effective system delay introduced by the decoder is negligible.

The conditions at the binary-select inputs and the three enable inputs select one of eight input lines. Two active-low and one active-high enable inputs reduce the need for external gates or inverters when expanding. A 24-line decoder can be implemented without external inverters and a 32-line decoder requires only one inverter. An enable input can be used as a data input for demultiplexing applications.

The SN74LV138 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

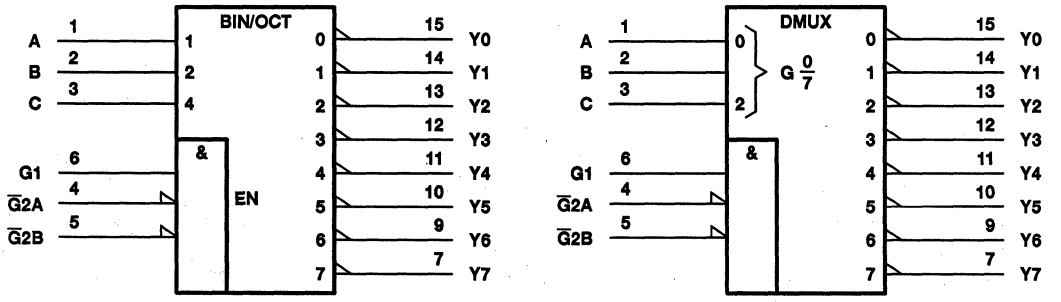
The SN74LV138 is characterized for operation from –40°C to 85°C.

EPIC is a trademark of Texas Instruments Incorporated.

FUNCTION TABLE

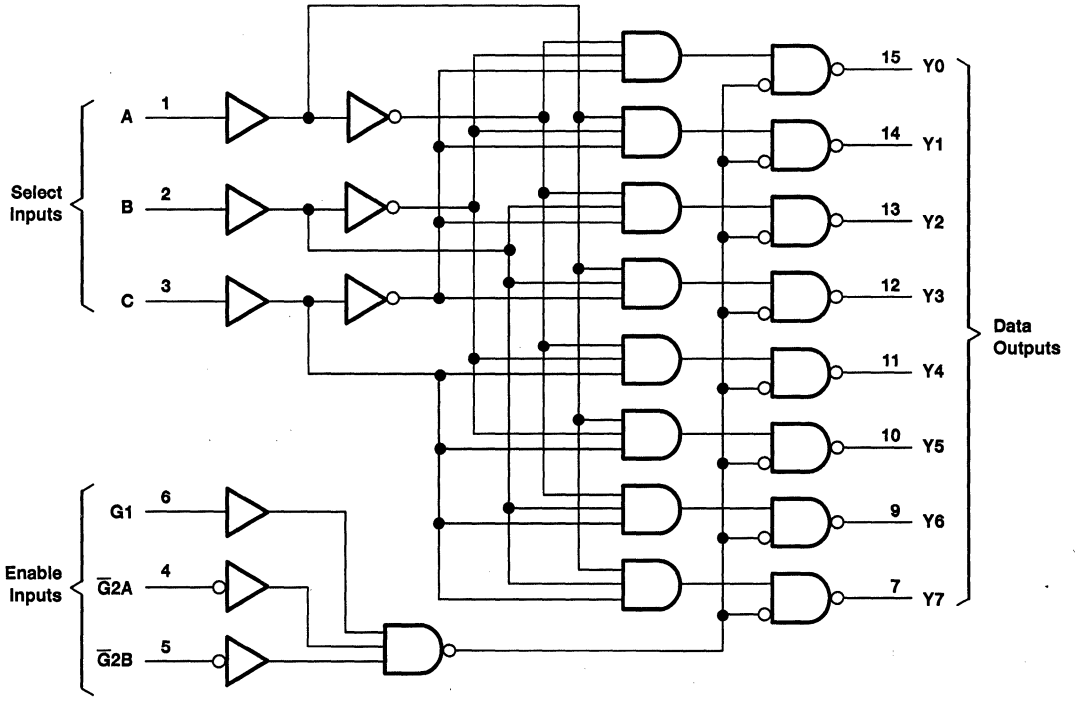
ENABLE INPUTS			SELECT INPUTS			OUTPUTS							
G1	$\overline{G2A}$	$\overline{G2B}$	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	H	X	X	X	X	H	H	H	H	H	H	H	H
X	X	H	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	H	L	H	H	H	H
H	L	L	H	L	L	H	H	H	H	L	H	H	H
H	L	L	H	L	H	H	H	H	H	H	L	H	H
H	L	L	H	H	L	H	H	H	H	H	H	L	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

logic symbols (alternatives)†



† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}‡	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = −6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	$V_I = V_{CC}$ or GND		3.6 V			±1	µA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	$V_I = V_{CC}$ or GND		3.3 V		2.5		pF

‡ For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

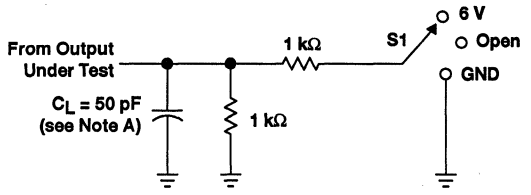
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y		14	29		36	ns
	Enable			16	33		41	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

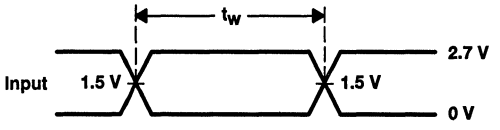
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per channel	C_L = 50 pF, f = 10 MHz	47	pF

PARAMETER MEASUREMENT INFORMATION

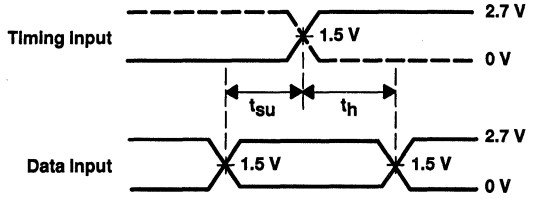


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

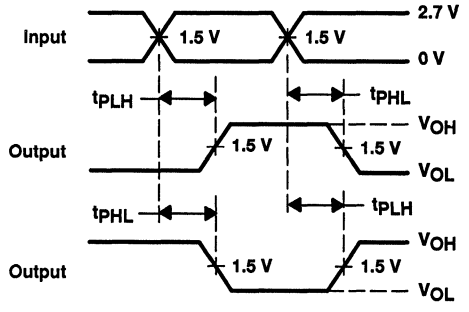
LOAD CIRCUIT FOR OUTPUTS



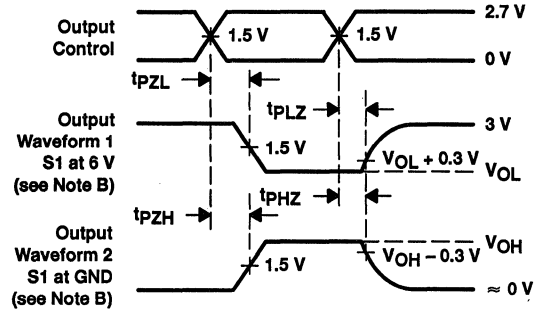
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



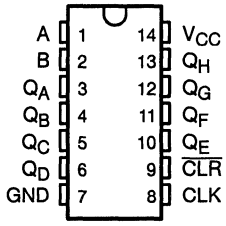
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This 8-bit parallel-out serial shift register is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV164 features AND-gated serial (A and B) inputs and an asynchronous clear ($\overline{CLR}$) input. The gated serial inputs permit complete control over incoming data as a low at either input inhibits entry of the new data and resets the first flip-flop to the low level at the next clock pulse. A high-level input enables the other input, which then determines the state of the first flip-flop. Data at the serial inputs may be changed while the clock is high or low, provided the minimum setup time requirements are met. Clocking occurs on the low-to-high-level transition of the clock (CLK) input.

The SN74LV164 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN74LV164 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

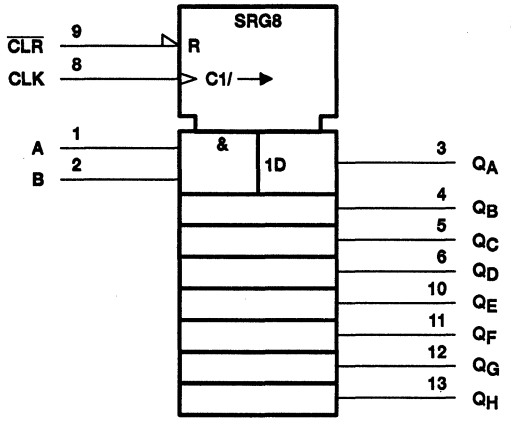
INPUTS				OUTPUTS		
$\overline{CLR}$	CLK	A	B	Q_A	$Q_B \ldots Q_H$	
L	X	X	X	L	L	L
H	L	X	X	Q_{A0}	Q_{B0}	Q_{H0}
H	↑	H	H	H	Q_{An}	Q_{Gn}
H	↑	L	X	L	Q_{An}	Q_{Gn}
H	↑	X	L	L	Q_{An}	Q_{Gn}

Q_{A0}, Q_{B0}, Q_{H0} = the level of Q_A, Q_B, or Q_H, respectively, before the indicated steady-state inputs conditions were established

Q_{An}, Q_{Gn} = the level of Q_A or Q_G before the most recent ↑ transition of the clock: indicates a 1-bit shift

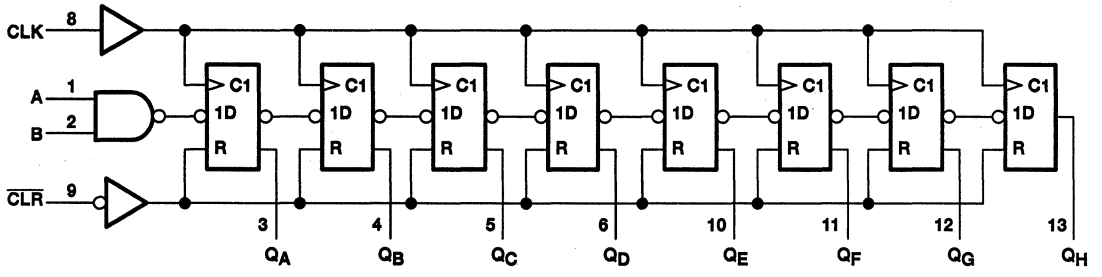
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†

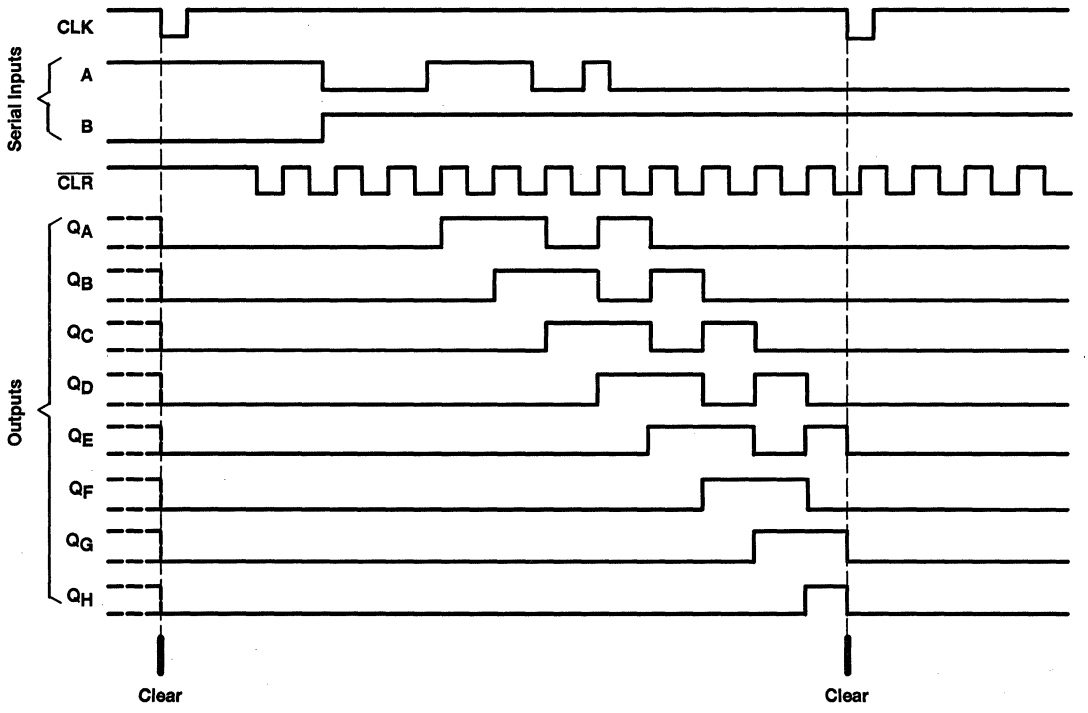


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



typical clear, shift, and clear sequences



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): D package ..... 1.25 W
DB or PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = − 6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	24	0	19	MHz
t_w	Pulse duration	$\overline{CLR}$ low	20		25		ns
		CLK high or low	20		25		
t_{su}	Setup time, data before CLK↑	Data	13		16		ns
		$\overline{CLR}$ inactive	11		14		
t_h	Hold time, data after CLK↑		5		5		ns

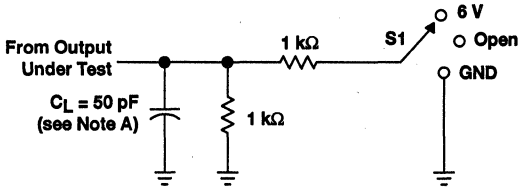
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
f_{max}			24	75		19		MHz
t_{pd}	CLK	Q		16	29		36	ns
t_{PHL}	$\overline{CLR}$	Q		16	29		36	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

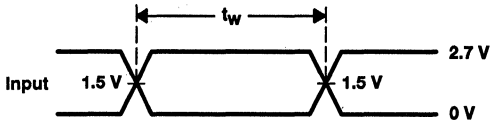
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	74	pF

PARAMETER MEASUREMENT INFORMATION

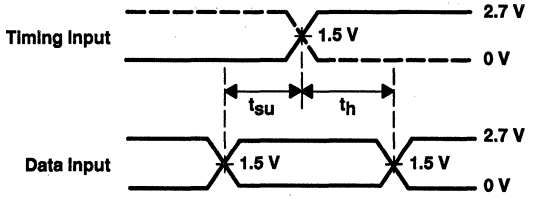


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

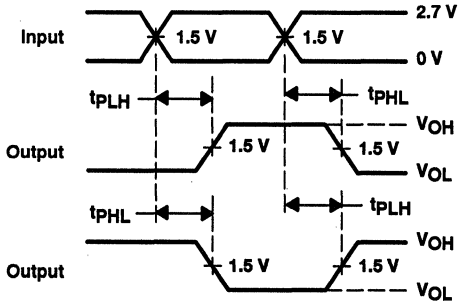
LOAD CIRCUIT FOR OUTPUTS



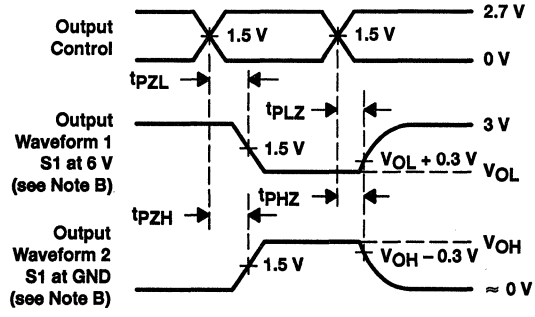
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



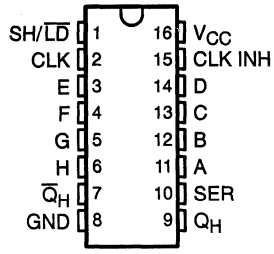
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- EPIC™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) < 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17

D, DB, OR PW PACKAGE
(TOP VIEW)



description

The SN74LV165 is a parallel-load, 8-bit shift register designed for 2.7-V to 3.6-V V_{CC} operation.

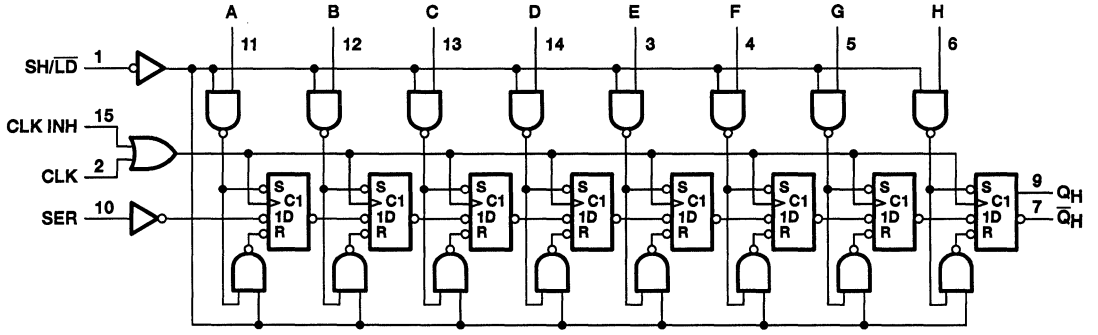
When the device is clocked, data is shifted toward the serial output Q_H. Parallel-in access to each stage is provided by eight individual direct data inputs that are enabled by a low level at the SH/$\overline{LD}$ input. The SN74LV165 features a clock inhibit function and a complemented serial output $\overline{Q}_H$.

Clocking is accomplished by a low-to-high transition of the clock (CLK) input while SH/$\overline{LD}$ is held high and clock inhibit (CLK INH) is held low. The functions of the CLK and CLK INH inputs are interchangeable. Since a low CLK input and a low-to-high transition of CLK INH accomplishes clocking, CLK INH should be changed to the high level only while CLK is high. Parallel loading is inhibited when SH/$\overline{LD}$ is held high. The parallel inputs to the register are enabled while SH/$\overline{LD}$ is held low independently of the levels of CLK, CLK INH, or SER.

FUNCTION TABLE

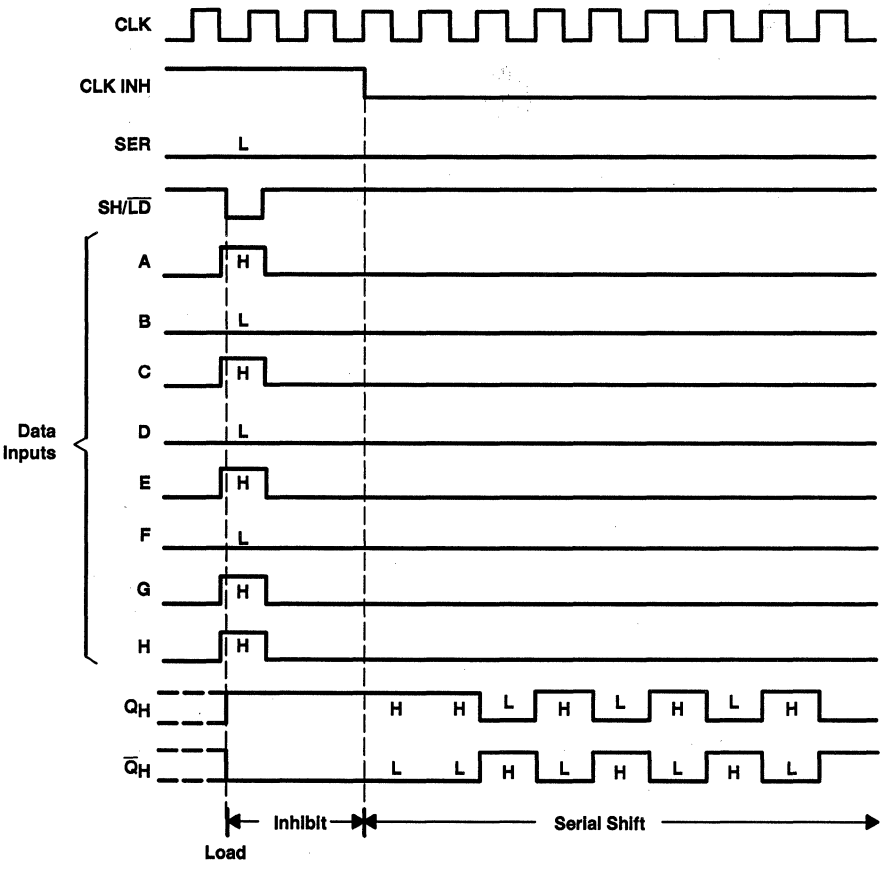
INPUTS			OPERATION
SH/$\overline{LD}$	CLK	CLK INH	
L	X	X	Parallel load
H	H	X	Q_0
H	X	H	Q_0
H	L	↑	Shift
H	↑	L	Shift

logic diagram (positive logic)



EPIC is a trademark of Texas Instruments Incorporated.

typical shift, load, and inhibit sequences



TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ± 20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ± 50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ± 25 mA
Continuous current through V_{CC} or GND ..... ± 50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.55 W
D package ..... 1.30 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}‡	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = −6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	$V_I = V_{CC}$ or GND		3.6 V			±1	μA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	$V_I = V_{CC}$ or GND		3.3 V		2.5		pF

‡ For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	24	0	19	MHz
t_w	Pulse duration	$\overline{CLK}$ high or low	20		25		ns
		SH/$\overline{LD}$ low	20		25		
t_{su}	Setup time	SH/$\overline{LD}$ high before $\overline{CLK}\uparrow$	15		19		ns
		SER before $\overline{CLK}\uparrow$	13		16		
		CLK INH before $\overline{CLK}\uparrow$	13		16		
		Data before SH/$\overline{LD}\uparrow$	15		19		
t_h	Hold time	SER data after $\overline{CLK}\uparrow$	8		8		ns
		Parallel data after SH/$\overline{LD}\uparrow$	8		8		

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

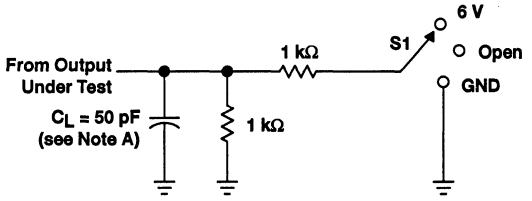
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
f_{max}			24	75		19		MHz
t_{pd}	CLK	Q_H or $\overline{Q}_H$		20	44		55	ns
	SH/$\overline{LD}$			19	41		51	
	H			15	34		43	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

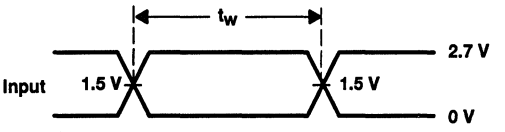
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 10 MHz	33	pF

PARAMETER MEASUREMENT INFORMATION

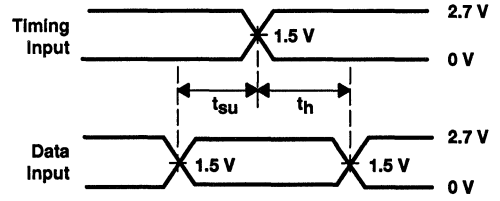
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



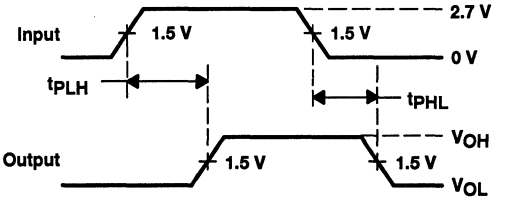
LOAD CIRCUIT



VOLTAGE WAVEFORMS



VOLTAGE WAVEFORMS



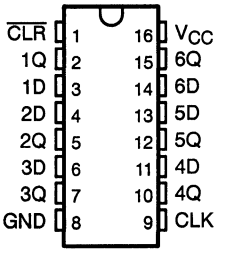
VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.
B. The outputs are measured one at a time with one transition per measurement.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

D, DB, OR PW PACKAGE
(TOP VIEW)



description

This hex D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV174 is a monolithic positive-edge-triggered flip-flop with a direct clear ($\overline{CLR}$) input. Information at the data (D) inputs meeting the setup time requirements is transferred to the outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going edge of the clock pulse. When the clock (CLK) input is at either the high or low level, the D-input signal has no effect at the output.

The SN74LV174 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

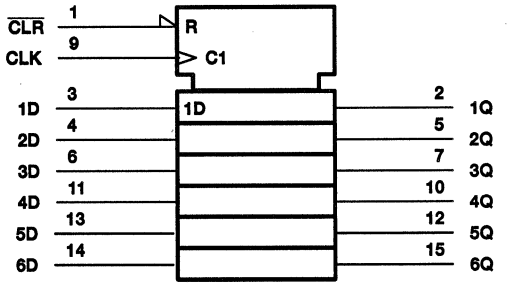
The SN74LV174 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS			OUTPUT
$\overline{CLR}$	CLK	D	Q
L	X	X	L
H	↑	H	H
H	↑	L	L
H	L	X	Q_0

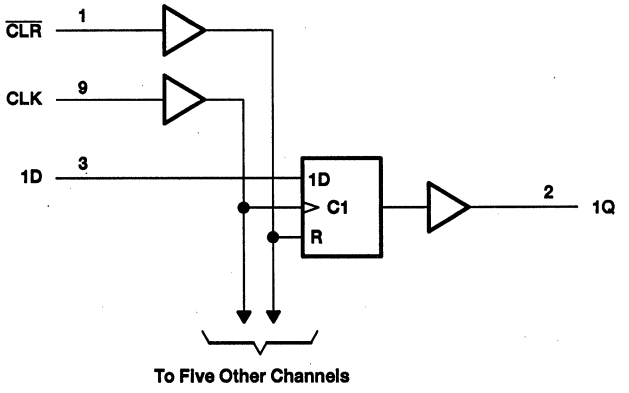
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): D package ..... 1.3 W
DB package ..... 0.55 W
PW package ..... 0.5 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = − 6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	24	0	19	MHz
t_w	Pulse duration	$\overline{CLR}$ low	20		25		ns
		CLK high or low	20		25		
t_{su}	Setup time before CLK↑	Data	13		16		ns
		$\overline{CLR}$ inactive	5		5		
t_h	Hold time, data after CLK↑		5		5		ns

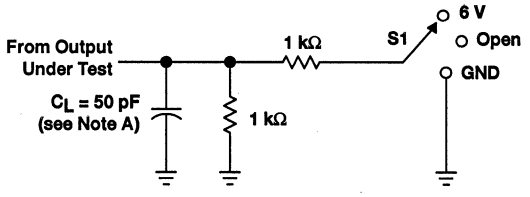
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
f_{max}			24	80		19		MHz
t_{pd}	$\overline{CLR}$	Q		12	26		33	ns
	CLK			13	33		41	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

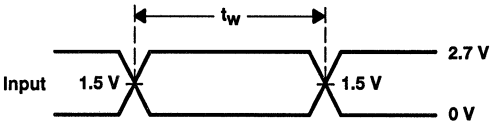
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	C_L = 50 pF, f = 10 MHz	24	pF

PARAMETER MEASUREMENT INFORMATION

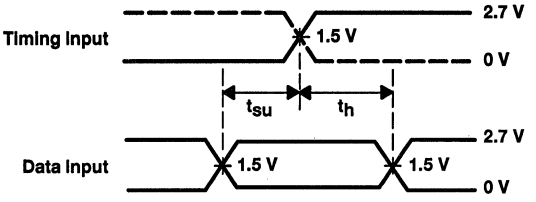


LOAD CIRCUIT FOR OUTPUTS

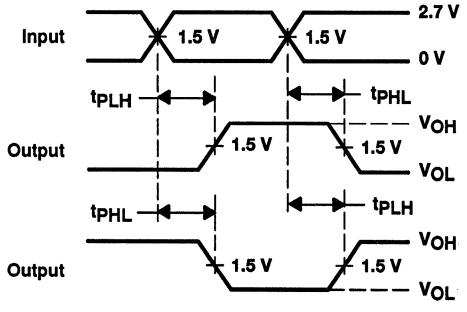
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



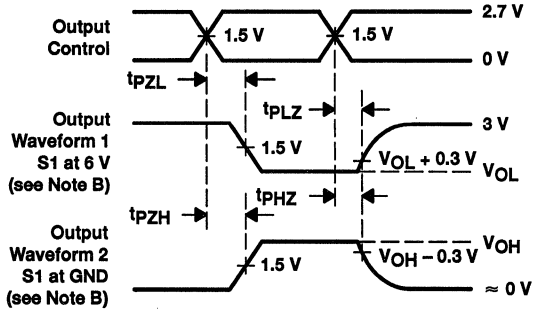
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



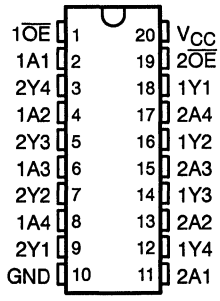
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV240 is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The SN74LV240 is organized as two 4-bit buffers/line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

The SN74LV240 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

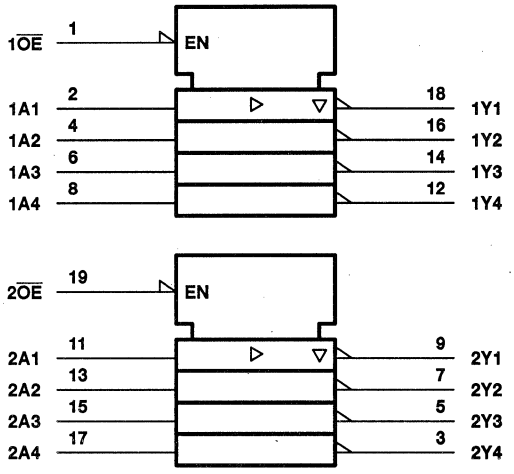
The SN74LV240 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	L
L	L	H
H	X	Z

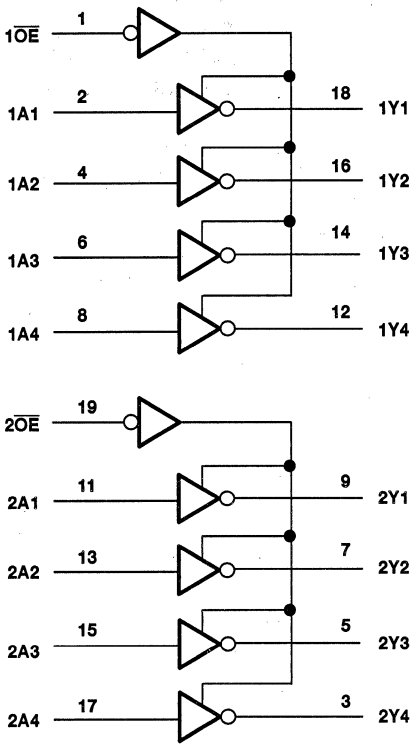
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−8	mA
I_{OL}	Low-level output current				8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = −100 µA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = −8 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 8 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	µA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	V_O = V_{CC} or GND		3.3 V		8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

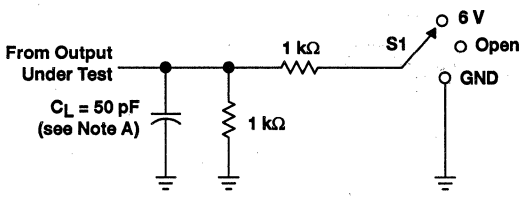
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		10	21		26	ns
t_{en}	$\overline{OE}$	Y		15	28		35	ns
t_{dis}	$\overline{OE}$	Y		17	27		33	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

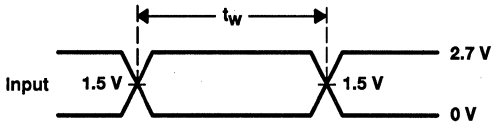
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	45	pF
		Outputs disabled		2.5	

PARAMETER MEASUREMENT INFORMATION

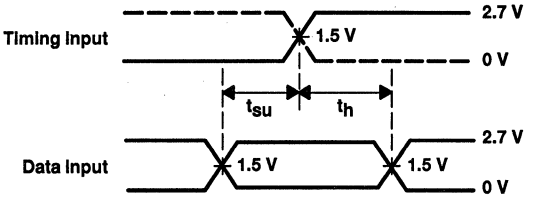


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

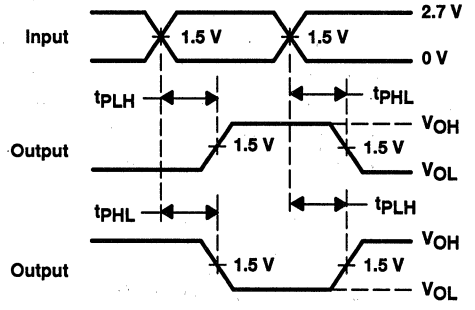
LOAD CIRCUIT FOR OUTPUTS



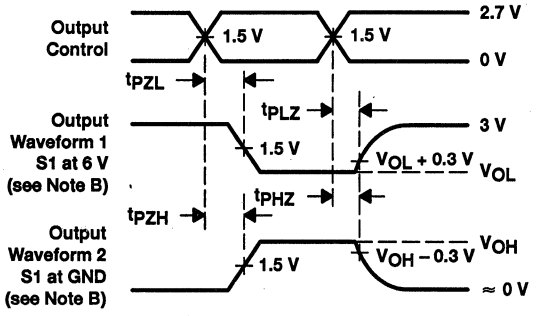
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



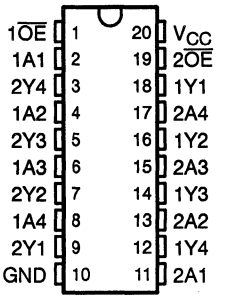
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal buffer/line driver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV244 is designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters.

The SN74LV244 is organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

The SN74LV244 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

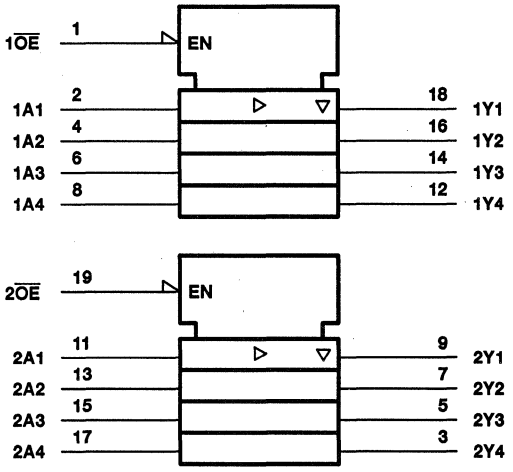
The SN74LV244 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

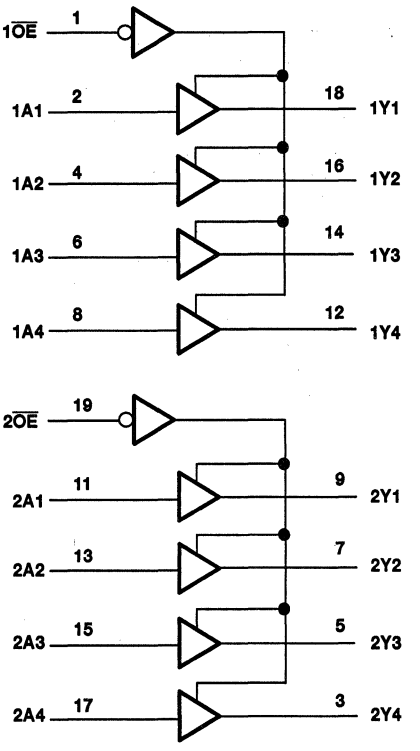
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at $T_A = 55°C$ (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				–8	mA
I_{OL}	Low-level output current				8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		–40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 8 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 8 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	μA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±5	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		3		pF
C_o	V_O = V_{CC} or GND		3.3 V		8		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

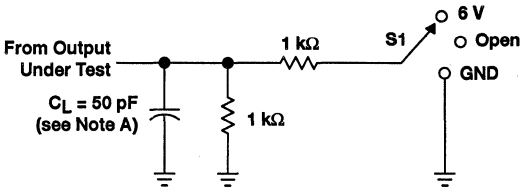
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A	Y		10	19		24	ns
t_{en}	$\overline{OE}$	Y		14	26		33	ns
t_{dis}	$\overline{OE}$	Y		15	26		32	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

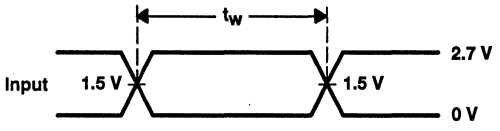
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per buffer/driver	Outputs enabled	C_L = 50 pF, f = 10 MHz	40	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

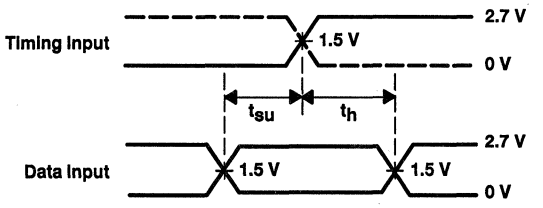


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

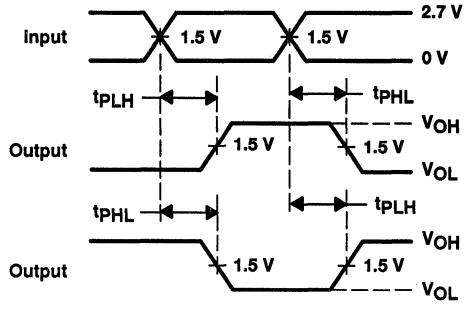
LOAD CIRCUIT FOR OUTPUTS



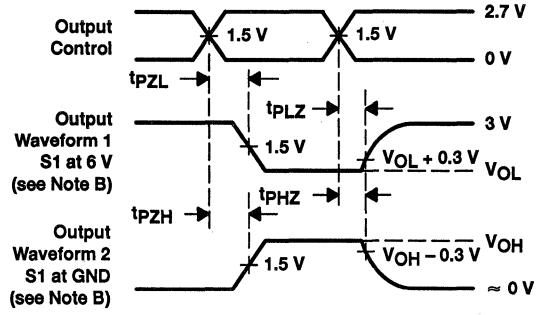
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



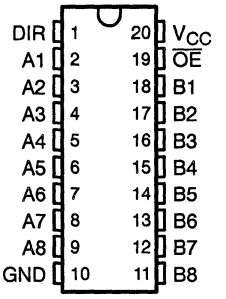
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal bus transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV245 is designed for asynchronous communication between data buses. The device transmits data from the A bus to the B bus or from the B bus to the A bus, depending upon the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so the buses are effectively isolated.

The SN74LV245 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

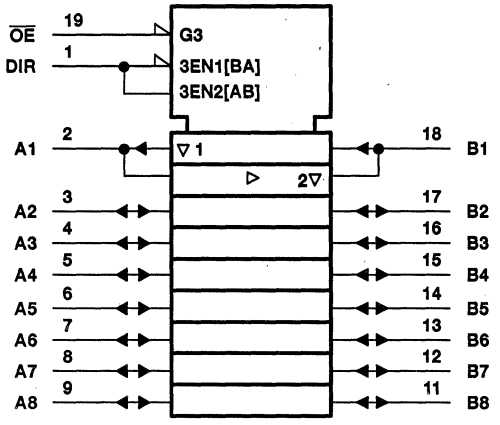
The SN74LV245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS		OPERATION
$\overline{OE}$	DIR	
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

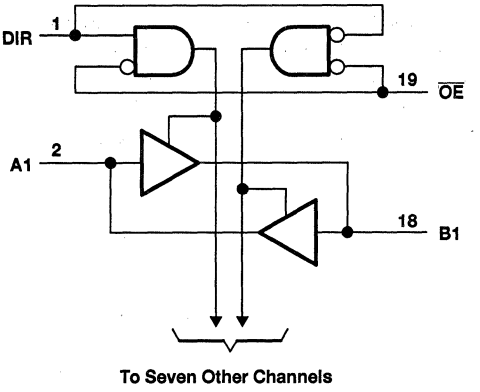
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
I/O ports (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.55 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				–8	mA
I_{OL}	Low-level output current				8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		50	ns/V
T_A	Operating free-air temperature		–40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
		I_{OH} = – 8 mA		3 V	2.4			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 8 mA		3 V			0.4	
I_I		V_I = V_{CC} or GND		3.6 V			±1	μA
I_{OZ}‡		V_O = V_{CC} or GND		3.6 V			±5	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		2.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.

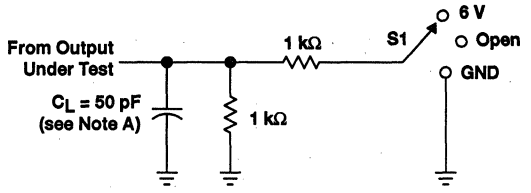
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	A or B	B or A		8	16		20	ns
t_{en}	$\overline{OE}$	A or B		13	23		29	ns
t_{dis}	$\overline{OE}$	A or B		14	25		31	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

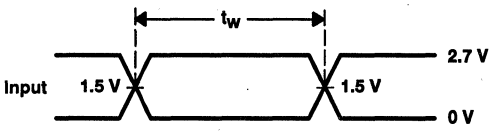
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	36	pF
		Outputs disabled		4	

PARAMETER MEASUREMENT INFORMATION

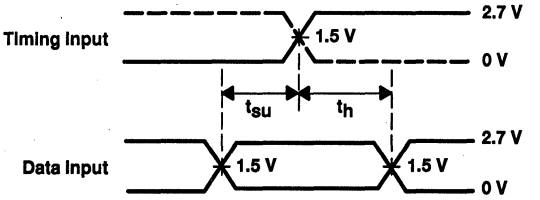


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

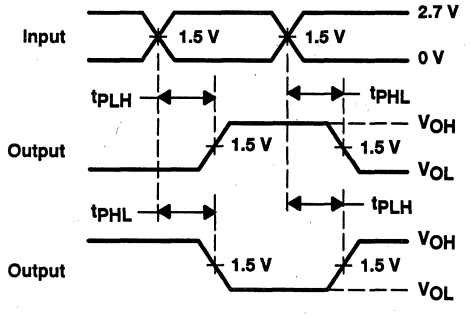
LOAD CIRCUIT FOR OUTPUTS



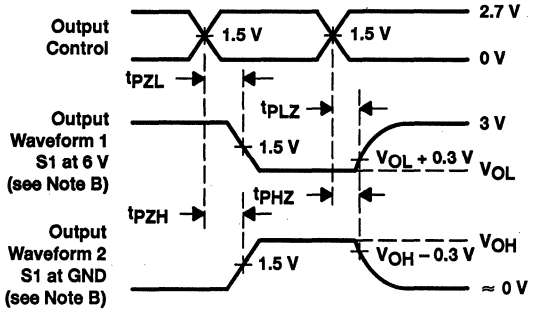
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



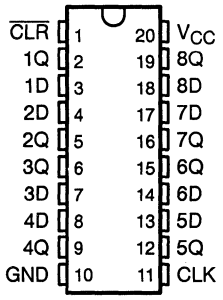
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV273 is a positive-edge-triggered flip-flop with a direct clear ($\overline{CLR}$) input. Information at the data (D) inputs meeting the setup time requirements is transferred to the Q outputs on the positive-going edge of the clock pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock (CLK) input is at either the high or low level, the D-input signal has no effect at the output.

The SN74LV273 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

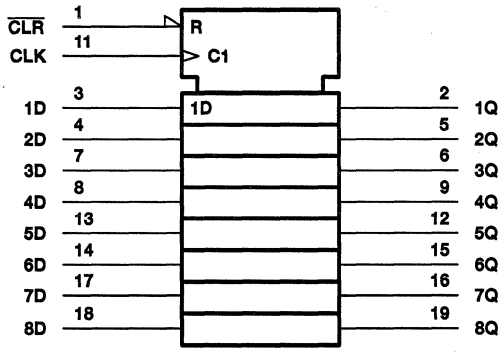
The SN74LV273 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{CLR}$	CLK	D	Q
L	X	X	L
H	↑	H	H
H	↑	L	L
H	L	X	Q_0

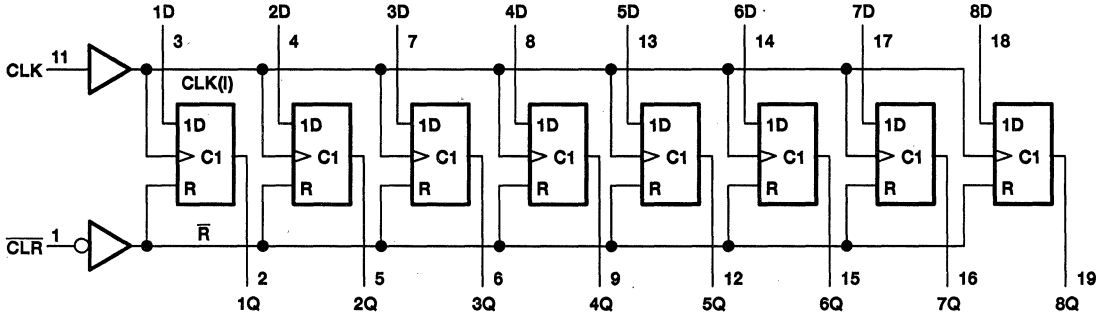
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±25 mA
Continuous current through V_{CC} or GND ..... ±50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−6	mA
I_{OL}	Low-level output current				6	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = −100 μA		MIN to MAX	V_{CC}−0.2			V
	I_{OH} = − 6 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 6 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}	One input at V_{CC} − 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	24	0	19	MHz
t_w	Pulse duration	$\overline{CLR}$ low	20		25		ns
		CLK high or low	20		25		
t_{su}	Setup time before CLK↑	Data	16		20		ns
		$\overline{CLR}$ inactive	5		5		
t_h	Hold time, data after CLK↑		5		5		ns

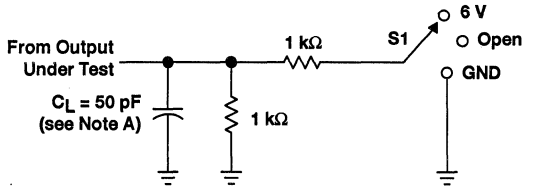
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
f_{max}				90		19		MHz
t_{pd}	CLK	Q		12	25		31	ns
t_{PHL}	$\overline{CLR}$	Q		13	26		33	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

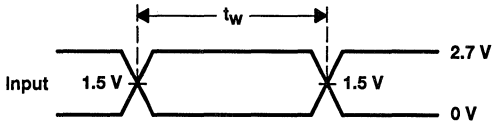
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	C_L = 50 pF, f = 10 MHz	32	pF

PARAMETER MEASUREMENT INFORMATION

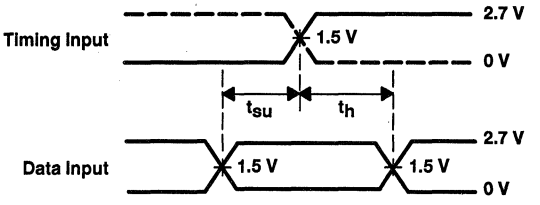


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

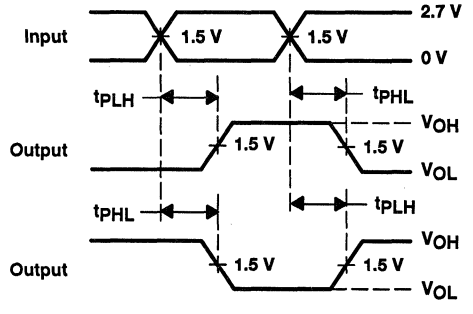
LOAD CIRCUIT FOR OUTPUTS



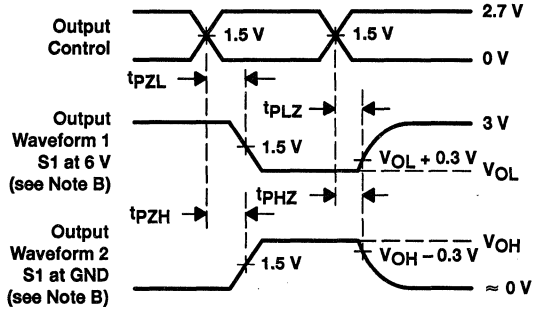
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



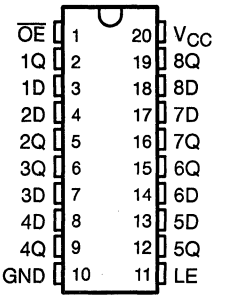
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal transparent D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation.

While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The SN74LV373 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

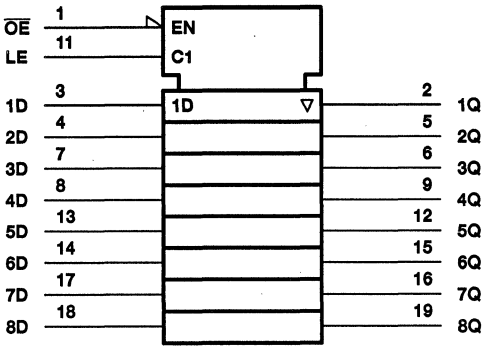
The SN74LV373 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each latch)

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

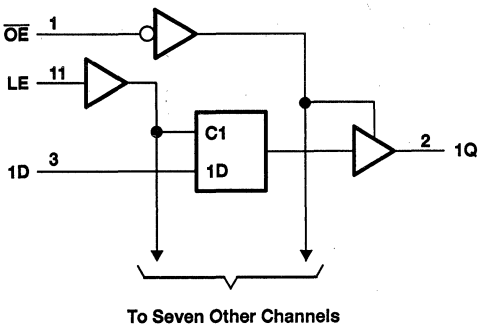
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−8	mA
I_{OL}	Low-level output current				8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 8 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 8 mA		3 V			0.4	
I_I	$V_I = V_{CC}$ or GND		3.6 V			±1	µA
I_{OZ}	$V_O = V_{CC}$ or GND		3.6 V			±5	µA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	$V_I = V_{CC}$ or GND		3.3 V		2.5		pF
C_o	$V_O = V_{CC}$ or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high		20		25		ns
t_{su}	Setup time, data before LE↓	High or low	10		13		ns
t_h	Hold time, data after LE↓	High or low	10		10		ns

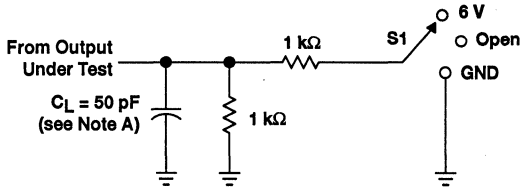
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	D	Q		11	25		31	ns
	LE			15	29		36	
t_{en}	$\overline{OE}$	Q		15	29		36	ns
t_{dis}	$\overline{OE}$	Q		15	29		36	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

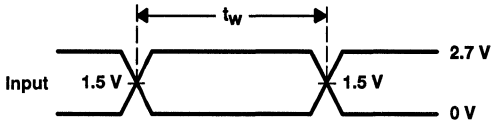
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 50 pF, f = 10 MHz	47	pF
		Outputs disabled		29	

PARAMETER MEASUREMENT INFORMATION

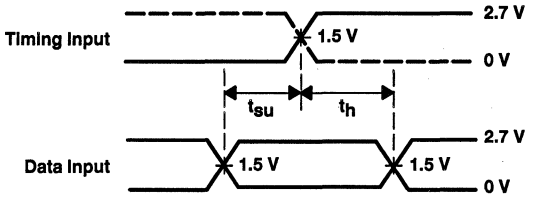


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

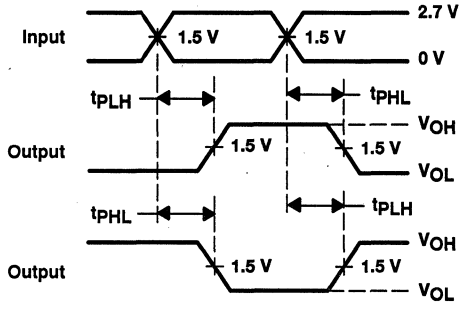
LOAD CIRCUIT FOR OUTPUTS



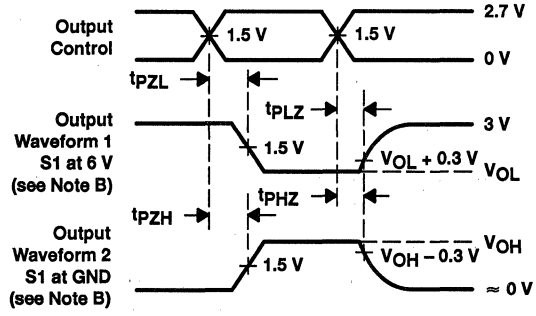
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



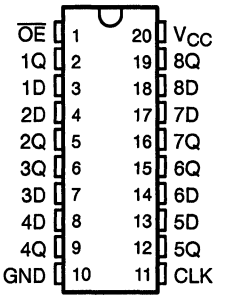
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal edge-triggered D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV374 features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either as normal logic state (high or low logic levels) or high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The SN74LV374 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

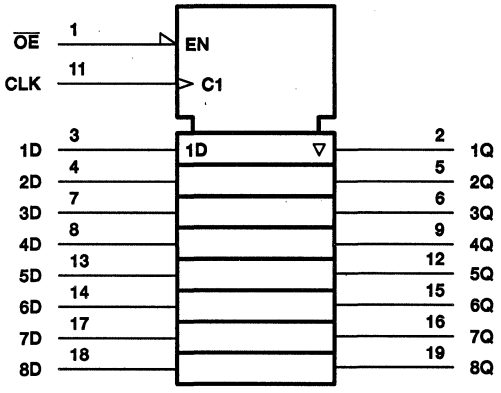
The SN74LV374 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

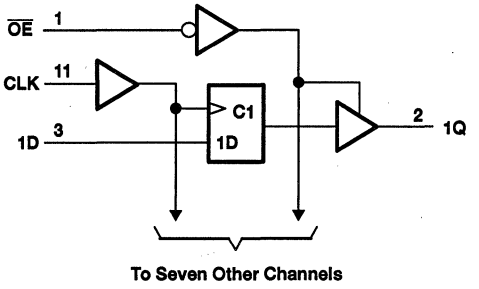
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				–8	mA
I_{OL}	Low-level output current				8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		–40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = –100 μA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 8 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 μA		MIN to MAX			0.2	V
	I_{OL} = 8 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	μA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±5	μA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF
C_o	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	24	0	19	MHz
t_w	Pulse duration, CLK high or low		20		25		ns
t_{su}	Setup time before CLK↑	High or low	13		16		ns
t_h	Hold time, data after CLK↑		5		5		ns

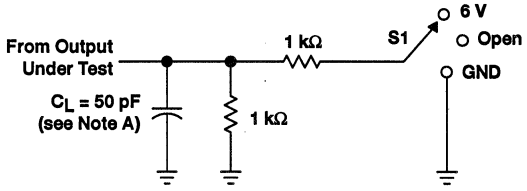
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
f_{max}			24	75		19		MHz
t_{pd}	CLK	Q		14	30		38	ns
t_{en}	$\overline{OE}$	Q		15	29		36	ns
t_{dis}	$\overline{OE}$	Q		15	29		36	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

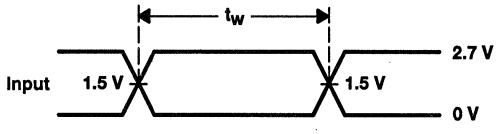
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 50 pF, f = 10 MHz	52	pF
		Outputs disabled		34	

PARAMETER MEASUREMENT INFORMATION

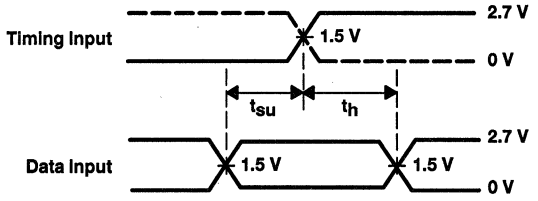


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

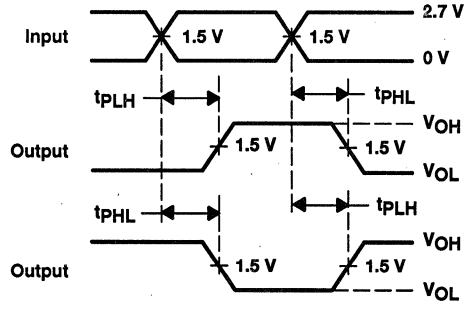
LOAD CIRCUIT FOR OUTPUTS



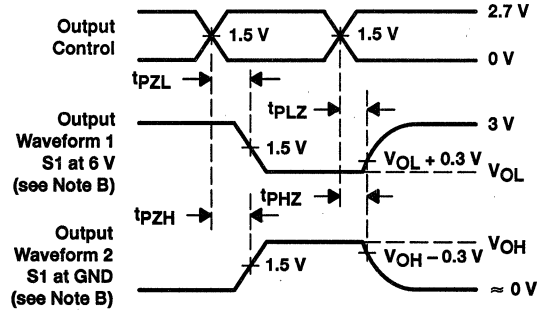
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



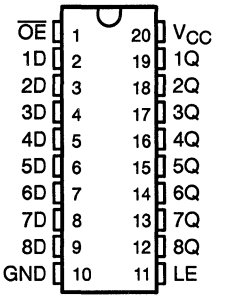
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal transparent D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV573 features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The SN74LV573 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

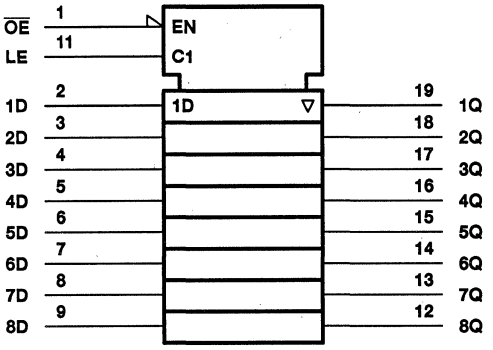
The SN74LV573 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each latch)

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

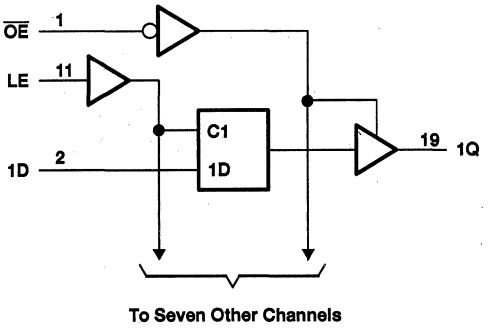
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−8	mA
I_{OL}	Low-level output current				8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 8 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 8 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	µA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF
C_o	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration, LE high	20		25		ns
t_{su}	Setup time, data before LE↓	10		13		ns
t_h	Hold time, data after LE↓	8		8		ns

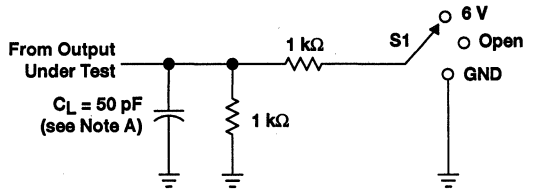
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
t_{pd}	D	Q		11	29		36	ns
	LE			15	30		38	
t_{en}	$\overline{OE}$	Q		13	26		33	ns
t_{dis}	$\overline{OE}$	Q		15	32		39	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

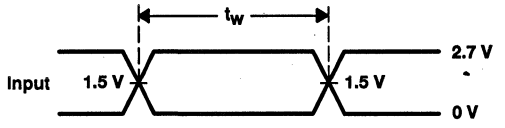
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per latch	Outputs enabled	C_L = 50 pF, f = 10 MHz	30	pF
		Outputs disabled		14	

PARAMETER MEASUREMENT INFORMATION

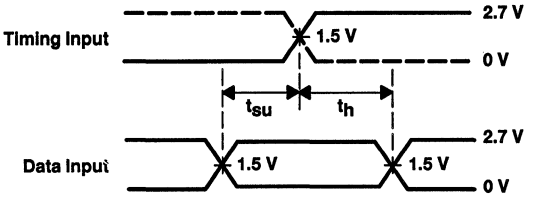


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

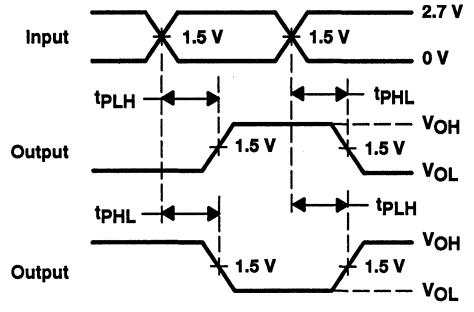
LOAD CIRCUIT FOR OUTPUTS



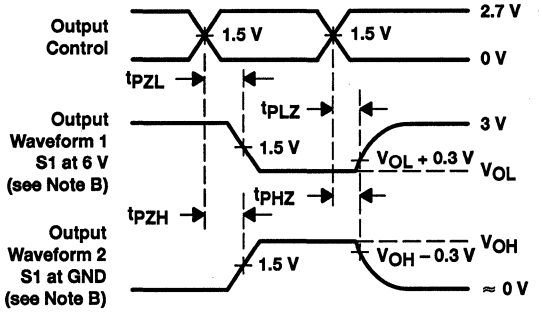
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



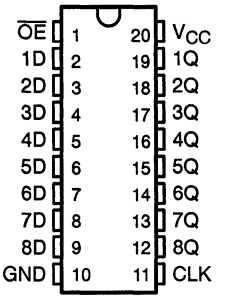
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

- *EPIC*™ (Enhanced-Performance Implanted CMOS) 2-μ Process
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This octal edge-triggered D-type flip-flop is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LV574 features 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. This device is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

On the positive transition of the clock (CLK) input, the Q outputs are set to the logic levels set up at the data (D) inputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

$\overline{OE}$ does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The SN74LV574 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

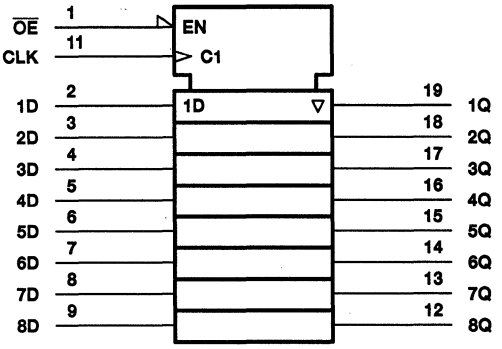
The SN74LV574 is characterized for operation from −40°C to 85°C.

FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

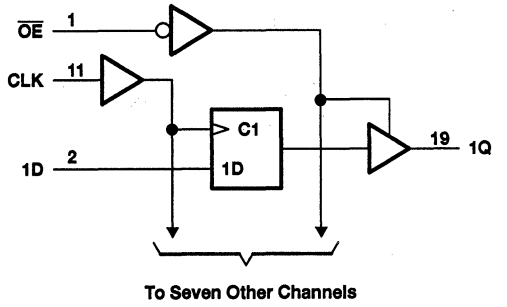
EPIC is a trademark of Texas Instruments Incorporated.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) ..... −0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) ..... ±20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) ..... ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) ..... ±35 mA
Continuous current through V_{CC} or GND ..... ±70 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package ..... 0.6 W
DW package ..... 1.6 W
PW package ..... 0.7 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

‡ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2			V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V			0.8	V
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current				−8	mA
I_{OL}	Low-level output current				8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate		0		100	ns/V
T_A	Operating free-air temperature		−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}†	MIN	TYP	MAX	UNIT
V_{OH}	I_{OH} = –100 µA		MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 8 mA		3 V	2.4			
V_{OL}	I_{OL} = 100 µA		MIN to MAX			0.2	V
	I_{OL} = 8 mA		3 V			0.4	
I_I	V_I = V_{CC} or GND		3.6 V			±1	µA
I_{OZ}	V_O = V_{CC} or GND		3.6 V			±5	µA
I_{CC}	V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	µA
C_i	V_I = V_{CC} or GND		3.3 V		2.5		pF
C_o	V_O = V_{CC} or GND		3.3 V		7		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	24	0	19	MHz
t_w	Pulse duration, CLK high or low		20		25		ns
t_{su}	Setup time before CLK↑	High or low	13		16		ns
t_h	Hold time, data after CLK↑		5		5		ns

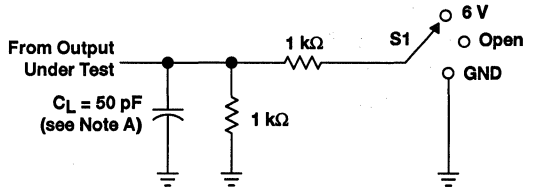
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
f_{max}			24	70		19		MHz
t_{pd}	CLK	Q		14	30		38	ns
t_{en}	$\overline{OE}$	Q		13	27		34	ns
t_{dis}	$\overline{OE}$	Q		15	29		36	ns

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

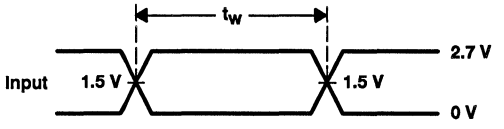
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per flip-flop	Outputs enabled	C_L = 50 pF, f = 10 MHz	40	pF
		Outputs disabled		22	

PARAMETER MEASUREMENT INFORMATION

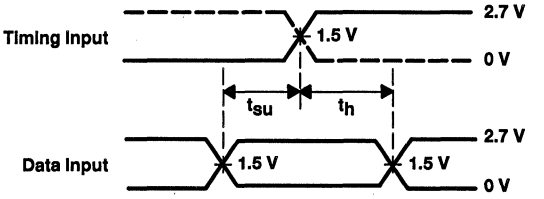


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

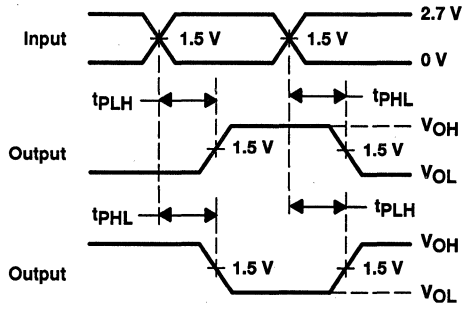
LOAD CIRCUIT FOR OUTPUTS



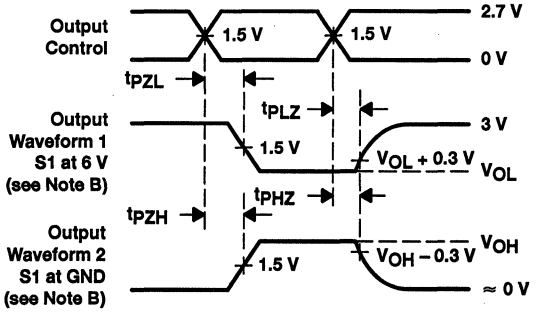
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

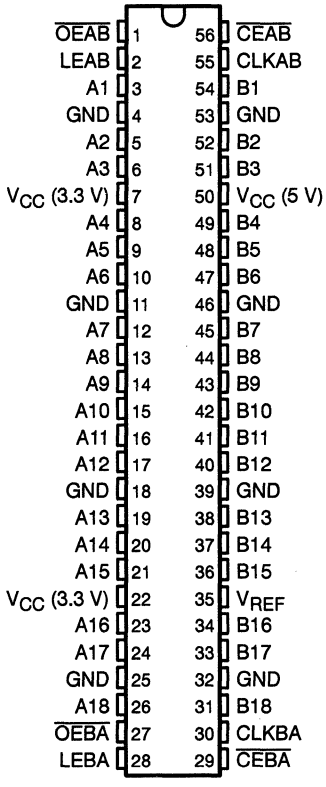
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

Contents

- **Translate Between GTL Logic Levels and LVTTL or 5-V TTL Logic Levels**
- **Members of the Texas Instruments *Widebus*™ Family**
- **Support Mixed-Mode Signal Operation on A Port**
- **Universal Bus Transceiver (*UBT*™) Combines D-Type Latches and D-Type Flip-Flops With Qualified Storage Enable**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors on A Port**
- **Flow-Through Architecture Optimizes Printed-Circuit-Board Layout**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Ceramic Flat (WD) Packages**

SN54GTL16612 . . . WD PACKAGE
SN74GTL16612 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

These 18-bit bus transceivers combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes.

The B port operates at GTL levels while the A port and control inputs are compatible with LVTTL or 5-V TTL logic levels.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. The clock or latch-enable can be controlled by the clock-enable ($\overline{CEAB}$ and $\overline{CEBA}$) inputs. For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if $\overline{CEAB}$ is low and CLKAB is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the low-to-high transition of CLKAB if $\overline{CEAB}$ is also low. $\overline{OEAB}$ is active low. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state. Data flow for B to A is similar to that for A to B but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CEBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54GTL16612 is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74GTL16612 is characterized for operation from −40°C to 85°C.

Widebus and UBT are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE†

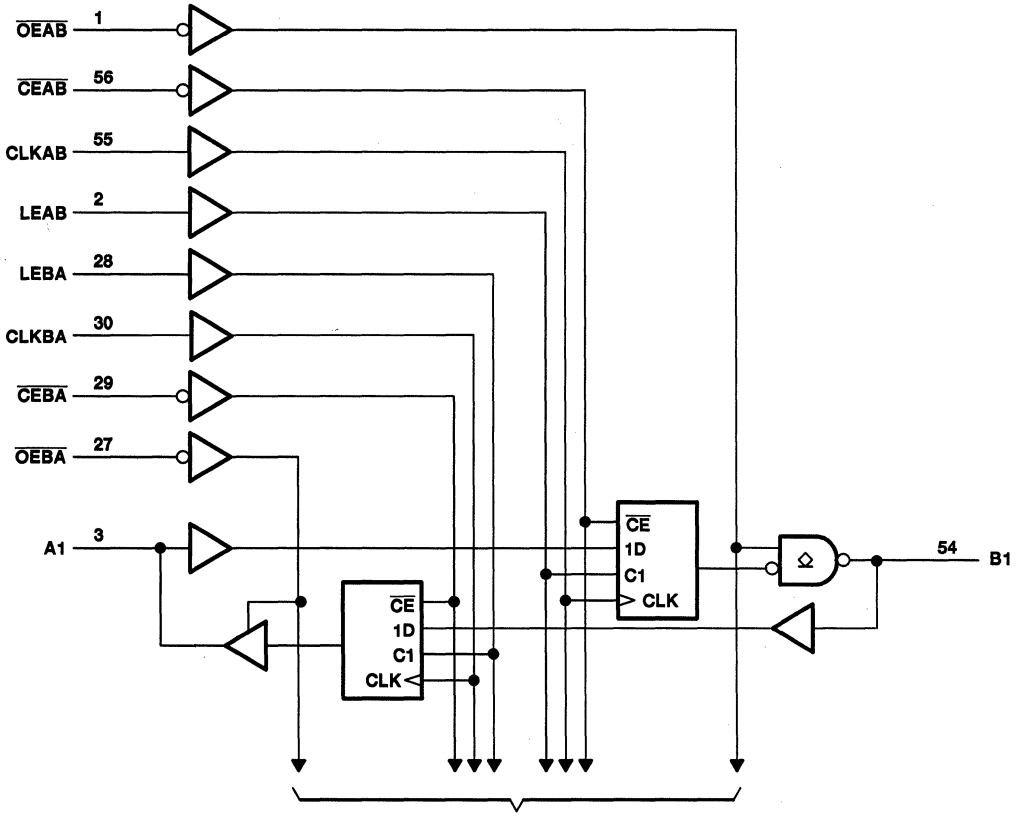
INPUTS					OUTPUT	MODE
$\overline{CEAB}$	$\overline{OEAB}$	LEAB	CLKAB	A	B	
X	H	X	X	X	Z	Latched storage of A data
L	L	L	H	X	B_0‡	
L	L	L	L	X	B_0§	
X	L	H	X	L	L	Transparent
X	L	H	X	H	H	
L	L	L	↑	L	L	Clocked storage of A data
L	L	L	↑	H	H	
H	L	L	X	X	B_0§	Clock inhibit

† A-to-B data flow is shown: B-to-A data flow is similar but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CEBA}$.

‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

§ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}: 3.3 V ..... −0.5 V to 4.6 V
5 V ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1): A port ..... −0.5 V to 7 V
B port ..... −0.5 V to 4.6 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1): A port ..... −0.5 V to 7 V
B port ..... −0.5 V to 4.6 V
Current into any A-port output in the low state, I_O ..... 128 mA
Current into any B-port output in the low state, I_O ..... 80 mA
Current into any A-port output in the high state, I_O (see Note 2) ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54GTL16612			SN74GTL16612			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage, 3.3 V		3.15	3.3	3.45	3.15	3.3	3.45	V
	Supply voltage, 5 V		4.75	5	5.25	4.75	5	5.25	
V_{REF}	Supply voltage			0.8			0.8		V
V_I	Input voltage	B port			V_{CC} (3.3 V)			V_{CC} (3.3 V)	V
		Except B port			5.5			5.5	
V_{IH}	High-level input voltage	B port	V_{REF} +50 mV			V_{REF} +50 mV			V
		Except B port	2			2			
V_{IL}	Low-level input voltage	B port			V_{REF} −50 mV			V_{REF} −50 mV	V
		Except B port			0.8			0.8	
I_{IK}	Input clamp current				−18			−18	mA
I_{OH}	High-level output current	A port			−32			−32	mA
I_{OL}	Low-level output current	A port			64			64	mA
		B port			40			40	
T_A	Operating free-air temperature		−55		125	−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range, V_{REF} = 0.8 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54GTL16612			SN74GTL16612			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	I_I = −18 mA			−1.2			−1.2	V
V_{OH}	A port	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA	V_{CC} − 0.2			V_{CC} − 0.2			V
		V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	I_{OH} = − 8 mA	2.4			2.4			
			I_{OH} = − 32 mA	2			2			
V_{OL}	A port	V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 64 mA			0.55			0.55	
	B port	V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	I_{OL} = 40 mA			0.4			0.4	
I_I	Control inputs	V_{CC} = 0 or MAX‡,	V_I = 5.5 V			10			10	µA
	A port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			−30			−30	
	B port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V	V_I = V_{CC} (3.3 V)			5			5	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V			100			100	µA
$I_{I(hold)}$	A port	V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	−75			−75			
I_{OZH}	A port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V	V_O = 3 V			1			1	µA
	B port		V_O = 1.2 V			10			10	
I_{OZL}	A port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V	V_O = 0.5 V			−1			−1	µA
	B port		V_O = 0.4 V			−10			−10	
I_{CC} (3.3 V)	A or B port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V, I_O = 0, V_I = V_{CC} (3.3 V) or GND	Outputs high			1			1	mA
			Outputs low			5			5	
			Outputs disabled			1			1	
I_{CC} (5 V)	A or B port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V, I_O = 0, V_I = V_{CC} (3.3 V) or GND	Outputs high			120			120	mA
			Outputs low			120			120	
			Outputs disabled			120			120	
ΔI_{CC}§		V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V, A or control inputs at V_{CC} (3.3 V) or GND, One input at 2.7 V				1			1	mA
C_i	Control inputs	V_I = 3.15 V or 0			3.5			3.5		pF
C_{io}	A port	V_O = 3.15 V or 0			12			12		pF
	B port	Per IEEE Standard 1149.0-1991				5			5	

† All typical values are at V_{CC} (3.3 V) = 3.3 V, V_{CC} (5 V) = 5 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{REF} = 0.8 V (unless otherwise noted)

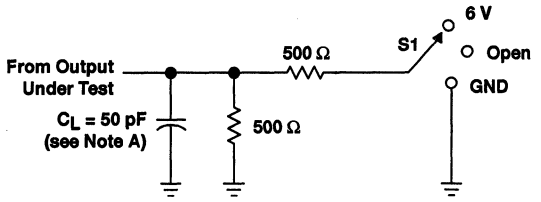
			SN54GTL16612		SN74GTL16612		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	95	0	95	MHz
t_w	Pulse duration	LEAB or LEBA high	3.3		3.3		ns
		CLKAB or CLKBA high or low	5.6		5.6		
t_{su}	Setup time	A before CLKAB↑	0.9		0		ns
		B before CLKBA↑	3.4		2.5		
		A before LEAB↓	1.2		0.4		
		B before LEBA↓	1		0.9		
		$\overline{CEAB}$ before CLKAB↑	2.1		1		
		$\overline{CEBA}$ before CLKBA↑	2.6		2.1		
t_h	Hold time	A after CLKAB↑	2.9		2.7		ns
		B after CLKBA↑	4.1		0.4		
		A after LEAB↓	4.5		3.4		
		B after LEBA↓	4.3		3.3		
		$\overline{CEAB}$ after CLKAB↑	2		1.5		
		$\overline{CEBA}$ after CLKBA↑	0.5		0.4		

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{REF} = 0.8 V (see Figure 1)

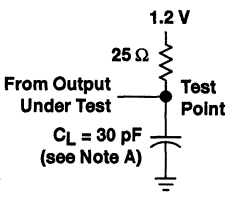
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54GTL16612			SN74GTL16612			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
f_{max}			95			95			MHz
t_{PLH}	A	B	1	2.6	3.8	1	2.6	3.8	ns
t_{PHL}			1	2.2	4	1	2.2	4	
t_{PLH}	LEAB	B	1.8	3.6	5.4	1.8	3.6	5.4	ns
t_{PHL}			1.5	3.3	5.5	1.5	3.3	5.5	
t_{PLH}	CLKAB	B	1.8	3.7	5.3	1.8	3.7	5.3	ns
t_{PHL}			1.5	3.3	5.5	1.5	3.3	5.5	
t_{PLH}	$\overline{OEAB}$	B	1.6	3.3	4.7	1.6	3.3	4.7	ns
t_{PHL}			1.3	3.2	5.5	1.3	3.2	5.5	
t_r	Transition time, B outputs (0.5 V to 1 V)			1.3			1.3		ns
t_f	Transition time, B outputs (1 V to 0.5 V)			0.5			0.5		ns
t_{PLH}	B	A	2	4.8	6.9	2	4.8	6.9	ns
t_{PHL}			1.4	3.6	5.1	1.4	3.6	5.1	
t_{PLH}	LEBA	A	2.1	4.3	6.1	2.1	4.3	6.1	ns
t_{PHL}			1.9	3.6	5.1	1.9	3.6	5.1	
t_{PLH}	CLKBA	A	2.3	4.5	6.4	2.3	4.5	6.4	ns
t_{PHL}			2.2	4	5.6	2.2	4	5.6	
t_{en}	$\overline{OEBA}$	A	1.9	4.7	7.2	1.9	4.7	7.2	ns
t_{dis}			2.5	4.6	6.9	2.5	4.6	6.9	

† All typical values are at V_{CC} (3.3 V) = 3.3 V, V_{CC} (5 V) = 5 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

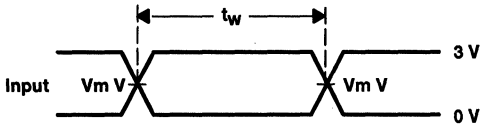


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

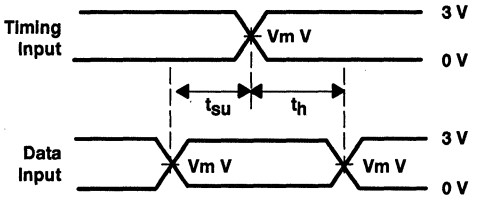


LOAD CIRCUIT FOR A OUTPUTS

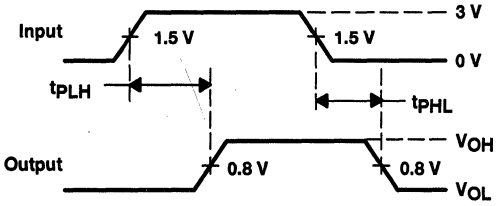
LOAD CIRCUIT FOR B OUTPUTS



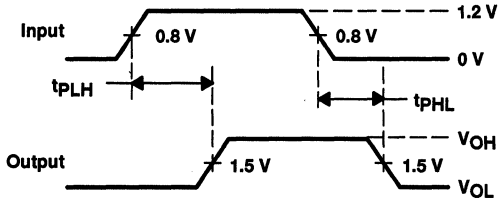
VOLTAGE WAVEFORMS
PULSE DURATION
(Vm = 1.5 V for A port and 0.8 V for B port)



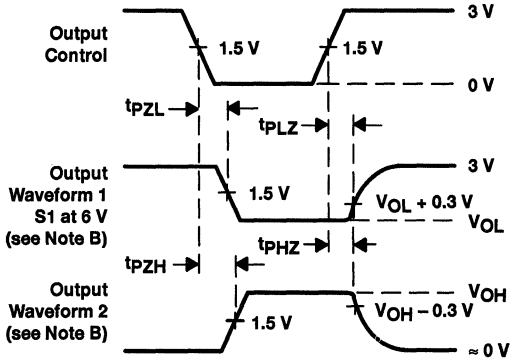
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES
(Vm = 1.5 V for A port and 0.8 V for B port)



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
(A port to B port)



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
(B port to A port)



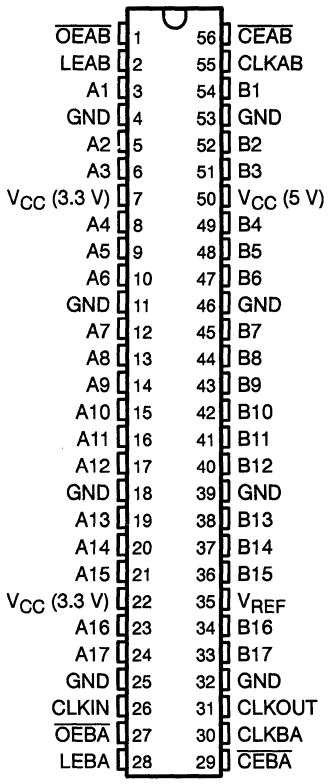
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
(A port)

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms

- **Translate Between GTL Signal Levels and LVTTL or 5-V TTL Signal Levels**
- **Members of the Texas Instruments *Widebus*™ Family**
- **Support Mixed-Mode Signal Operation on A Port**
- **Universal Bus Transceiver (*UBT*™) Combines D-Type Latches and D-Type Flip-Flops With Qualified Storage Enable**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors on A Port**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Ceramic Flat (WD) Packages**

SN54GTL16616 . . . WD PACKAGE
SN74GTL16616 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

These 17-bit registered bus transceivers combine D-type latches and D-type flip-flops to allow data flow in transparent, latched, and clocked modes. The 'GTL16616 provide for a copy of CLKAB at GTL logic levels (CLKOUT) and also provide a conversion of the GTL clock to a TTL environment (CLKIN).

The B port operates at GTL levels while the A port and control inputs are compatible with LVCMOS, LVTTL, or 5-V TTL logic levels.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. The clock or latch-enable can be controlled by the clock-enable ($\overline{CEAB}$ and $\overline{CEBA}$) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if $\overline{CEAB}$ is low and CLKAB is held at a high or low logic level. If LEAB is low, the A-bus data is stored in the latch/flip-flop on the low-to-high transition of CLKAB if $\overline{CEAB}$ is also low. $\overline{OEAB}$ is active low. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state. Data flow for B to A is similar to that of A to B but uses $\overline{OEBA}$, LEBA, CLKBA, and $\overline{CEBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74GTL16616 is available in TI's shrink small-outline package (DL), which provides twice the I/O pin count and functionality of standard small-outline packages in the same printed-circuit-board area.

The SN54GTL16616 is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74GTL16616 is characterized for operation from −40°C to 85°C.

Widebus and UBT are trademarks of Texas Instruments Incorporated.

FUNCTION TABLE†

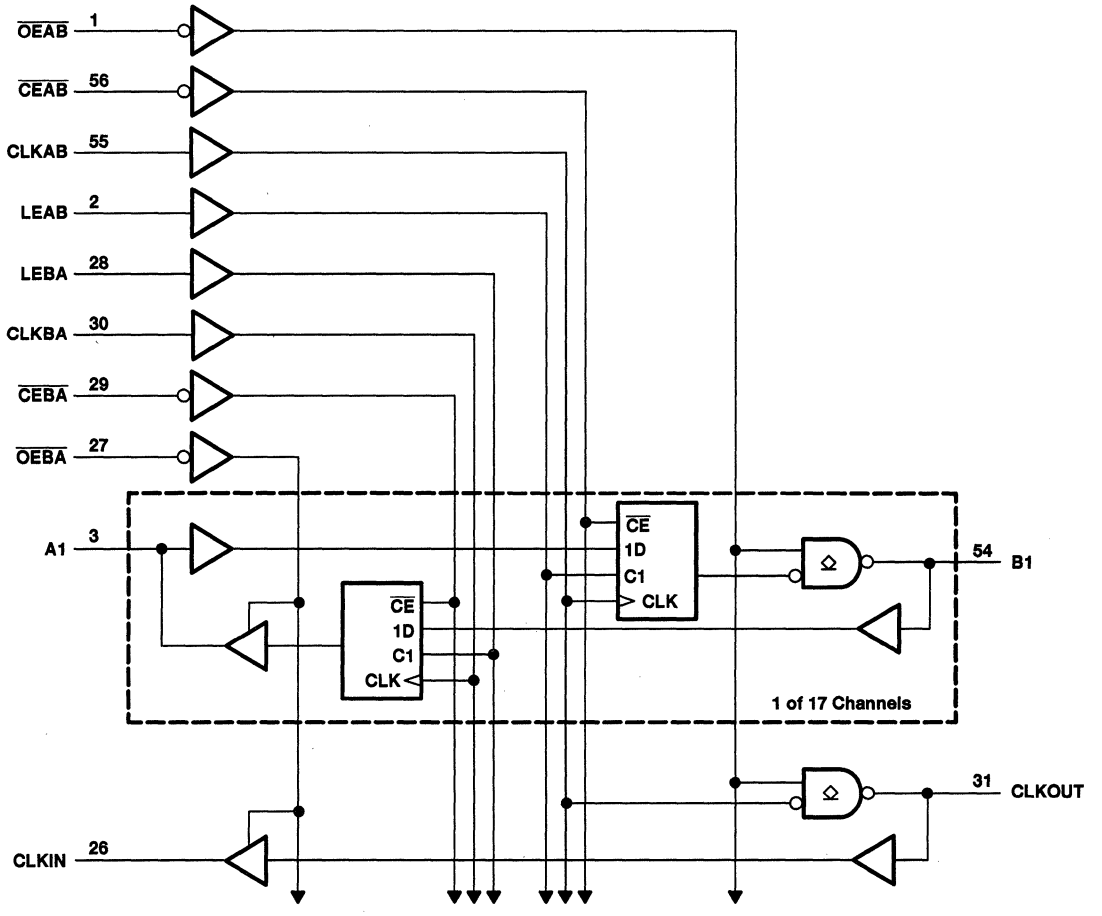
INPUTS					OUTPUT	MODE
$\overline{CEAB}$	$\overline{OEAB}$	LEAB	CLKAB	A	B	
X	H	X	X	X	Z	Latched storage of A data
L	L	L	H or L	X	B_0‡	
L	L	L	H or L	X	B_0§	
X	L	H	X	L	L	Transparent
X	L	H	X	H	H	
L	L	L	↑	L	L	Clocked storage of A data
L	L	L	↑	H	H	
H	L	L	X	X	B_0§	Clock inhibit

† A-to-B data flow is shown: B-to-A data flow is similar but uses $\overline{OEBA}$, LEBA, $\overline{CLKBA}$, and $\overline{CEBA}$.

‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

§ Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}: 3.3 V ..... −0.5 V to 4.6 V
5 V ..... −0.5 V to 7 V
Input voltage range, V_I (see Note 1): A port ..... −0.5 V to 7 V
B port ..... −0.5 V to 4.6 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1): A port ..... −0.5 V to 7 V
B port ..... −0.5 V to 4.6 V
Current into any A-port output in the low state, I_O ..... 128 mA
Current into any B-port output in the low state, I_O ..... 80 mA
Current into any A-port output in the high state, I_O (see Note 2) ..... 64 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54GTL16616			SN74GTL16616			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage, 3.3 V		3.15	3.3	3.45	3.15	3.3	3.45	V
	Supply voltage, 5 V		4.75	5	5.25	4.75	5	5.25	
V_{REF}	Supply voltage			0.8			0.8		V
V_I	Input voltage	B port			V_{CC} (3.3 V)			V_{CC} (3.3 V)	V
		Except B port			5.5			5.5	
V_{IH}	High-level input voltage	B port	V_{REF} +50 mV			V_{REF} +50 mV			V
		Except B port	2			2			
V_{IL}	Low-level input voltage	B port			V_{REF} −50 mV			V_{REF} −50 mV	V
		Except B port			0.8			0.8	
I_{IK}	Input clamp current				−18			−18	mA
I_{OH}	High-level output current	A port			−32			−32	mA
I_{OL}	Low-level output current	A port			64			64	mA
		B port			40			40	
T_A	Operating free-air temperature		−55		125	−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range, V_{REF} = 0.8 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54GTL16616			SN74GTL16616			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	I_I = −18 mA			−1.2			−1.2	V
V_{OH}	A port	V_{CC} = MIN to MAX‡,	I_{OH} = −100 μA	V_{CC} − 0.2			V_{CC} − 0.2			V
		V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	I_{OH} = −8 mA	2.4			2.4			
			I_{OH} = −32 mA	2			2			
V_{OL}	A port	V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	I_{OL} = 100 μA			0.2			0.2	V
			I_{OL} = 16 mA			0.4			0.4	
			I_{OL} = 32 mA			0.5			0.5	
			I_{OL} = 64 mA			0.55			0.55	
	B port	V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	I_{OL} = 40 mA			0.4			0.4	
I_I	Control inputs	V_{CC} = 0 or MAX‡,	V_I = 5.5 V			10			10	μA
	A port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V	V_I = 5.5 V			20			20	
			V_I = V_{CC}			1			1	
			V_I = 0			−30			−30	
	B port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V	V_I = V_{CC} (3.3 V)			5			5	
			V_I = 0			−5			−5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V			100			100	μA
$I_{I(hold)}$	A port	V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V	V_I = 0.8 V	75			75			μA
			V_I = 2 V	−75			−75			
I_{OZH}	A port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V	V_O = 3 V			1			1	μA
	B port		V_O = 1.2 V			10			10	
I_{OZL}	A port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V	V_O = 0.5 V			−1			−1	μA
	B port		V_O = 0.4 V			−10			−10	
I_{CC} (3.3 V)	A or B port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V, I_O = 0, V_I = V_{CC} (3.3 V) or GND	Outputs high			1			1	mA
			Outputs low			5			5	
			Outputs disabled			1			1	
I_{CC} (5 V)	A or B port	V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V, I_O = 0, V_I = V_{CC} (3.3 V) or GND	Outputs high			120			120	mA
			Outputs low			120			120	
			Outputs disabled			120			120	
ΔI_{CC}§		V_{CC} (3.3 V) = 3.45 V, A or control inputs at V_{CC} (3.3 V) or GND, One input at 2.7 V	V_{CC} (5 V) = 5.25 V,			1			1	mA
C_i	Control inputs	V_I = 3.15 V or 0			3.5			3.5		pF
C_{io}	A port	V_O = 3.15 V or 0			12			12		pF
	B port	Per IEEE 1194.0-1991				5			5	

† All typical values are at V_{CC} (3.3 V) = 3.3 V, V_{CC} (5 V) = 5 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{REF} = 0.8 V (unless otherwise noted)

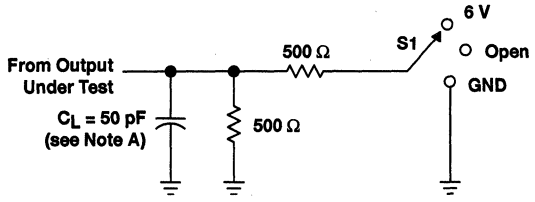
			SN54GTL16616		SN74GTL16616		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	95	0	95	MHz
t_w	Pulse duration	LEAB or LEBA high	3.3		3.3		ns
		CLKAB or CLKBA high or low	5.5		5.5		
t_{su}	Setup time	A before CLKAB↑	1.1		1.1		ns
		B before CLKBA↑	2.6		2.6		
		A before LEAB↓	0		0		
		B before LEBA↓	1		1		
		$\overline{CEAB}$ before CLKAB↑	1.8		1.8		
		$\overline{CEBA}$ before CLKBA↑	2.1		2.1		
t_h	Hold time	A after CLKAB↑	1.6		1.6		ns
		B after CLKBA↑	0.2		0.2		
		A after LEAB↓	4.3		4.3		
		B after LEBA↓	2.8		2.8		
		$\overline{CEAB}$ after CLKAB↑	0.8		0.8		
		$\overline{CEBA}$ after CLKBA↑	0.7		0.7		

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{REF} = 0.8 V (see Figure 1)

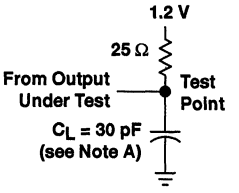
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54GTL16616			SN74GTL16616			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
f_{max}			95			95			MHz
t_{PLH}	A	B	1	2.5	3.8	1	2.5	3.8	ns
t_{PHL}			1	2	3.8	1	2	3.8	
t_{PLH}	LEAB	B	1.5	3.4	5.1	1.5	3.4	5.1	ns
t_{PHL}			1.4	3.2	5.1	1.4	3.2	5.1	
t_{PLH}	CLKAB	B	1.5	3.6	5	1.5	3.6	5	ns
t_{PHL}			1.4	4.1	5	1.4	4.1	5	
t_{PLH}	CLKAB	CLKOUT	3.4	6	7.7	3.4	6	7.7	ns
t_{PHL}			4.3	7.4	10.4	4.3	7.4	10.4	
t_{PLH}	$\overline{OEAB}$	B	1.3	3.2	5	1.3	3.2	5	ns
t_{PHL}			1.1	3.1	5	1.1	3.1	5	
t_r	Transition time, B outputs (0.5 V to 1 V)			1.2			1.2		ns
t_f	Transition time, B outputs (1 V to 0.5 V)			0.7			0.7		ns
t_{PLH}	B	A	2.1	4.4	6.5	2.1	4.4	6.5	ns
t_{PHL}			1.3	3.3	4.8	1.3	3.3	4.8	
t_{PLH}	LEBA	A	1.7	3.9	6	1.7	3.9	6	ns
t_{PHL}			1.3	3.3	4.6	1.3	3.3	4.6	
t_{PLH}	CLKBA	A	1.7	4.1	6.3	1.7	4.1	6.3	ns
t_{PHL}			1.4	3.6	5.3	1.4	3.6	5.3	
t_{PLH}	CLKOUT	CLKIN	6.5	10.5	14.3	6.5	10.5	14.3	ns
t_{PHL}			5.1	8.8	11.8	5.1	8.8	11.8	
t_{en}	$\overline{OEBA}$	A	1.8	4.7	6.9	1.8	4.7	6.9	ns
t_{dis}			2	4.7	6.7	2	4.7	6.7	

† All typical values are at V_{CC} (3.3 V) = 3.3 V, V_{CC} (5 V) = 5 V, T_A = 25°C.

PARAMETER MEASUREMENT INFORMATION

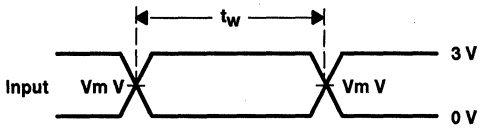


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

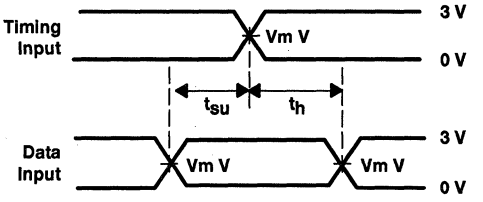


LOAD CIRCUIT FOR A OUTPUTS

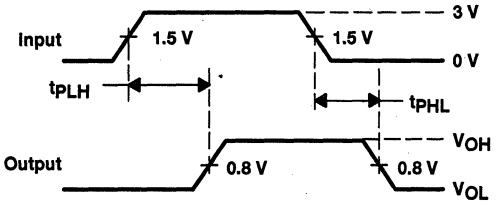
LOAD CIRCUIT FOR B OUTPUTS



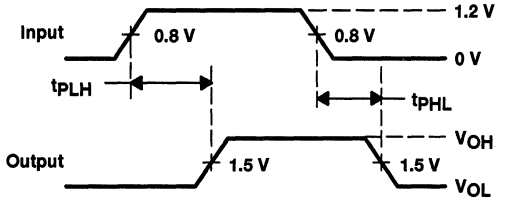
VOLTAGE WAVEFORMS
PULSE DURATION
(Vm = 1.5 V for A port and 0.8 V for B port)



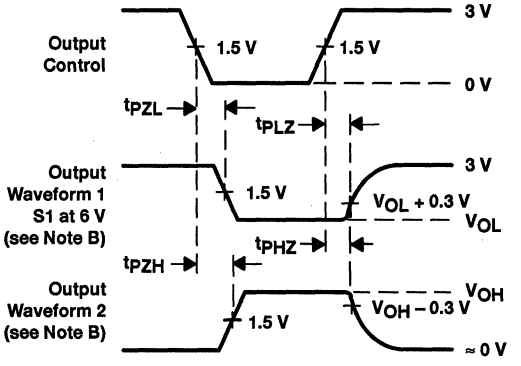
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES
(Vm = 1.5 V for A port and 0.8 V for B port)



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
(A port to B port)



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
(B port to A port)



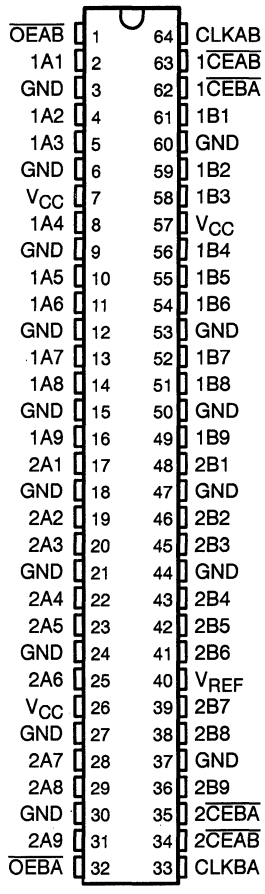
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
(A port)

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms

- **Translate Between GTL/GTL+ Signal Levels and LVTTL**
- **Members of the Texas Instruments *Widebus*™ Family**
- **Support GTL/GTL+ Signal Operation on B Port**
- **D-Type Flip-Flops With Qualified Storage Enable**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors on A Port**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Packaged in Plastic Thin Shrink Small-Outline (DGG) Package**

DGG PACKAGE
(TOP VIEW)



description

The 'GTL16622 18-bit registered bus transceivers contain two sets of D-type flip-flops for temporary storage of data flowing in either direction.

The B port operates at GTL/GTL+ levels, while the A port and control inputs are compatible with LVTTL logic level.

Data flow in each direction is controlled by output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) and the clock (CLKAB and CLKBA) inputs. The clock-enable ($\overline{CEAB}$ and $\overline{CEBA}$) inputs are designed to control nine bits at a time, which makes the device more versatile.

For A-to-B data flow, the devices operate on the low-to-high transition of CLKAB if $\overline{CEAB}$ is low. When $\overline{OEAB}$ is low, the outputs are active. When $\overline{OEAB}$ is high, the outputs are in the high-impedance state. Data flow for B to A is similar to that for A to B but uses $\overline{OEBA}$, CLKBA, and $\overline{CEBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54GTL16622 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74GTL16622 is characterized for operation from –40°C to 85°C.

ADVANCE INFORMATION

Widebus is a trademark of Texas Instruments Incorporated.

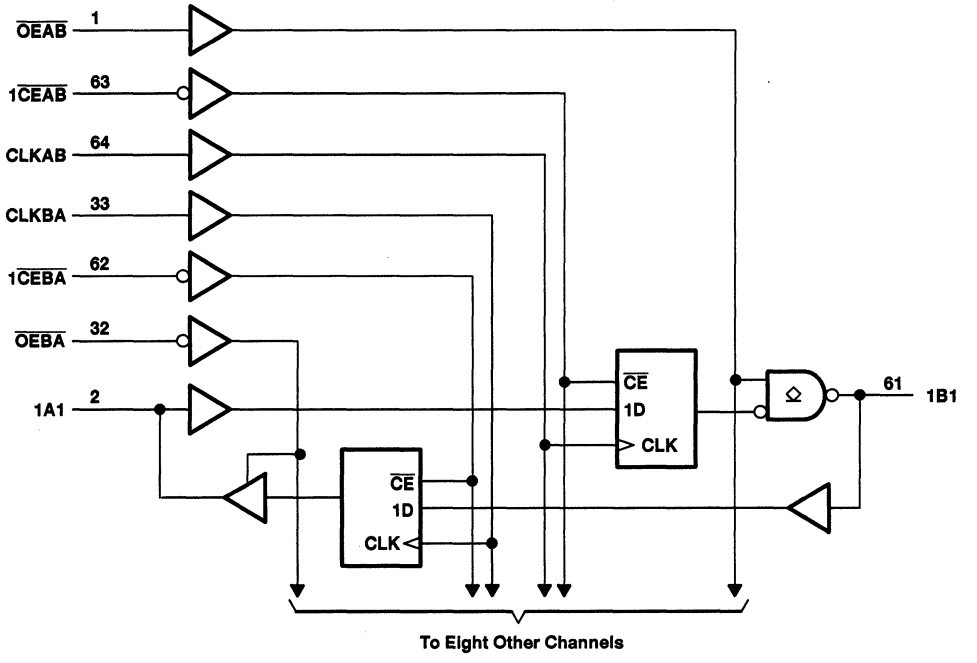
FUNCTION TABLE†

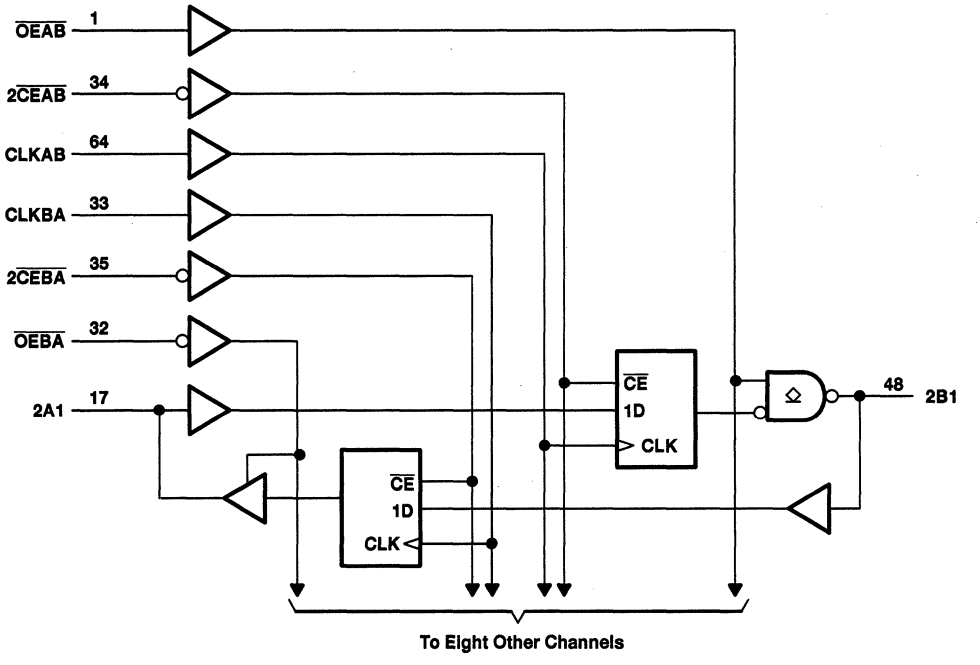
INPUTS				OUTPUT	MODE
$\overline{CEAB}$	$\overline{OEAB}$	CLKAB	A	B	
X	H	X	X	Z	
H	L	X	X	B_0‡	Latched storage of A data
X	L	H or L	X	B_0‡	
L	L	↑	L	L	Clocked storage of A data
L	L	↑	H	H	

† A-to-B data flow is shown: B-to-A data flow is similar but uses $\overline{OEBA}$, CLKBA, and $\overline{CEBA}$.
‡ Output level before the indicated steady-state input conditions were established

ADVANCE INFORMATION

logic diagram (positive logic)





ADVANCE INFORMATION

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1): A port ..... −0.5 V to 4.6 V
B port ..... −0.5 V to 4.6 V
Voltage range applied to any output in the high or
power-off state, V_O (see Note 1): A port ..... −0.5 V to 4.6 V
B port ..... −0.5 V to 4.6 V
Current into any A-port output in the low state, I_O ..... 48 mA
Current into any B-port output in the low state, I_O ..... 100 mA
Current into any A-port output in the high state, I_O (see Note 2) ..... 48 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$) ..... −50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3) ..... 1 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54GTL16622			SN74GTL16622			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage		3.15	3.3	3.45	3.15	3.3	3.45	V
V_{TT}	Termination voltage		1.14	1.5	1.65	1.14	1.5	1.65	
V_{REF}	Supply voltage		0.74	1	1.1	0.74	1	1.1	V
V_I	Input voltage	B port			V_{CC}			V_{CC}	V
		Except B port			5.5			5.5	
V_{IH}	High-level input voltage	B port	V_{REF} +50 mV			V_{REF} +50 mV			V
		Except B port	2			2			
V_{IL}	Low-level input voltage	B port			V_{REF} −50 mV			V_{REF} −50 mV	V
		Except B port			0.8			0.8	
I_{IK}	Input clamp current				−18			−18	mA
I_{OH}	High-level output current	A port			−24			−24	mA
I_{OL}	Low-level output current	A port			24			24	mA
		B port			50			50	
T_A	Operating free-air temperature		−55		125	−40		85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

ADVANCE INFORMATION

electrical characteristics over recommended operating free-air temperature range, V_{REF} = 1 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54GTL16622			SN74GTL16622			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 3.15 V,	I_I = −18 mA			−1.2			−1.2	V
V_{OH}	A port	V_{CC} = MIN to MAX‡,	I_{OH} = −100 µA	V_{CC} − 0.2			V_{CC} − 0.2			V
		V_{CC} = 3.15 V	I_{OH} = −8 mA	2.4			2.4			
			I_{OH} = −24 mA	2			2			
V_{OL}	A port	V_{CC} = 3.15 V	I_{OL} = 100 µA			0.2			0.2	V
			I_{OL} = 8 mA			0.4			0.4	
			I_{OL} = 24 mA			0.5			0.5	
	B port	V_{CC} = MIN to MAX‡,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 3.15 V	I_{OL} = 10 mA			0.2			0.2	
			I_{OL} = 40 mA			0.4			0.4	
			I_{OL} = 50 mA			0.55			0.55	
I_I		V_{CC} = 3.45 V,	V_I = V_{CC} or GND			±5			±5	µA
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 5.5 V			100			100	µA
$I_{I(hold)}$	A port	V_{CC} = 3.15 V	V_I = 0.8 V	75			75			µA
			V_I = 2 V	−75			−75			
I_{OZH}	A port	V_{CC} = 3.45 V	V_O = 3 V			1			1	µA
	B port		V_O = 1.5 V			10			10	
I_{OZL}	A port	V_{CC} = 3.45 V	V_O = 0.5 V			−1			−1	µA
	B port		V_O = 0.4 V			−10			−10	
I_{CC}	A or B port	V_{CC} = 3.45 V, I_O = 0, V_I = V_{CC} or GND	Outputs high							mA
			Outputs low							
			Outputs disabled							
ΔI_{CC}§		V_{CC} = 3.45 V, A or control inputs at V_{CC} or GND, One input at 2.7 V				1			1	mA
C_i	Control inputs	V_I = 3.15 V or 0			3.5			3.5		pF
C_{io}	A port	V_O = 3.15 V or 0			7			7		pF
	B port	Per IEEE Standard 1149.0-1991			6			6		

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

ADVANCE INFORMATION

timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V (unless otherwise noted)

			SN54GTL16622		SN74GTL16622		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0		0	200	MHz
t_w	Pulse duration, CLK high or low		2		2		ns
t_{su}	Setup time	Data before CLK↑	2		2		ns
		$\overline{CE}$ before CLK↑	3		3		
t_h	Hold time	Data after CLK↑	0		0		ns
		$\overline{CE}$ after CLK↑	0		0		

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54GTL16622			SN74GTL16622			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
f_{max}						200			MHz
t_{PLH}	CLKAB	B						5	ns
t_{PHL}								5.5	
t_{PLH}	$\overline{OEAB}$	B						5	ns
t_{PHL}								5	
Slew rate	Both transitions					0.3		0.8	V/ns
t_r	Transition time, B outputs (0.6 V to 1.3 V)					0.9		2.3	ns
t_f	Transition time, B outputs (1.3 V to 0.6 V)					0.9		2.3	ns
t_{PLH}	CLKBA	A						5	ns
t_{PHL}								5	
t_{en}	$\overline{OEBA}$	A						6.5	ns
t_{dis}								6	

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

ADVANCE INFORMATION

timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.2 V and V_{REF} = 0.8 V (unless otherwise noted)

			SN54GTL16622		SN74GTL16622		UNIT
			MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0		0	200	MHz
t_w	Pulse duration, CLK high or low						ns
t_{su}	Setup time	Data before CLK↑					ns
		$\overline{CE}$ before CLK↑					
t_h	Hold time	Data after CLK↑					ns
		$\overline{CE}$ after CLK↑					

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.2 V and V_{REF} = 0.8 V (see Figure 1)

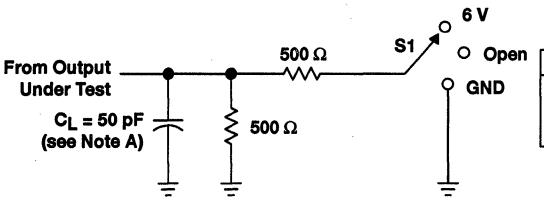
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54GTL16622			SN74GTL16622			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
f_{max}						200			MHz
t_{PLH}	CLKAB	B							ns
t_{PHL}									
t_{PLH}	$\overline{OEAB}$	B							ns
t_{PHL}									
Slew rate	Both transitions								V/ns
t_r	Transition time, B outputs (0.6 V to 1 V)								ns
t_f	Transition time, B outputs (1 V to 0.6 V)								ns
t_{PLH}	CLKBA	A							ns
t_{PHL}									
t_{en}	$\overline{OEBA}$	A							ns
t_{dis}									

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

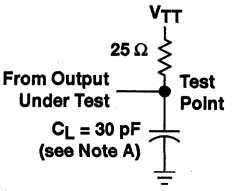
ADVANCE INFORMATION

ADVANCE INFORMATION

PARAMETER MEASUREMENT INFORMATION
V_{TT} = 1.5 V, V_{REF} = 1 V

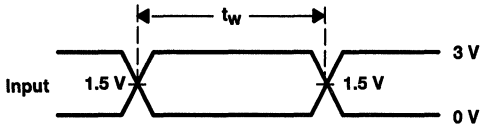


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

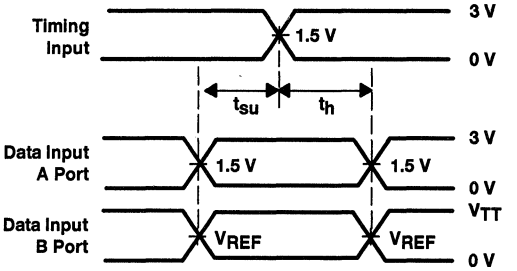


LOAD CIRCUIT FOR A OUTPUTS

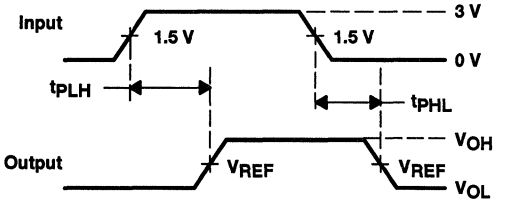
LOAD CIRCUIT FOR B OUTPUTS



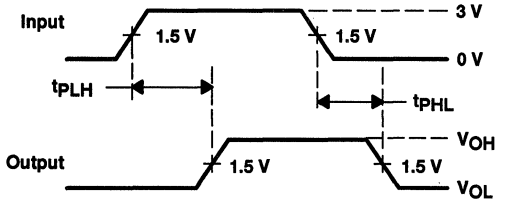
VOLTAGE WAVEFORMS
PULSE DURATION



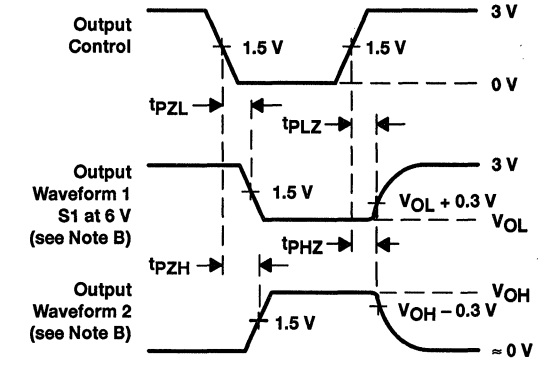
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES
(Vm = 1.5 V for A port and 0.8 V for B port)



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
(A to B port)



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
(B to A port)



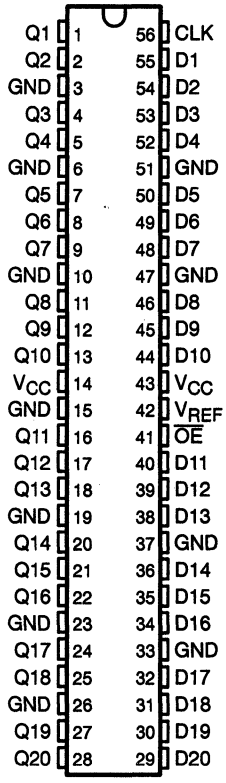
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
(A port)

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms

- *EPIC-IIB*™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Members of the Texas Instruments *Widebus*™ Family
- Provide GTL Signals Levels on Both Inputs and Outputs
- Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise
- Flow-Through Architecture Optimizes PCB Layout
- Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages, and Ceramic Flat (WD) Package

SN54GTL16921 . . . WD PACKAGE
SN74GTL16921 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

The 'GTL16921 have 20 single-bit flip-flops, which are designed to provide terminated GTL logic levels.

These devices can be used as one 20-bit flip-flop. The 20 flip-flops are edge-triggered D-type flip-flops. The 'GTL16921 provide true data at the Q outputs on the positive transition of the clock (CLK) input.

The output-enable ($\overline{OE}$) input can be used to place the outputs in a high state.The output-enable input does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The SN54GTL16921 is characterized for operation over the full military temperature range of −55°C to 125°C. The SN74GTL16921 is characterized for operation from 0°C to 70°C.

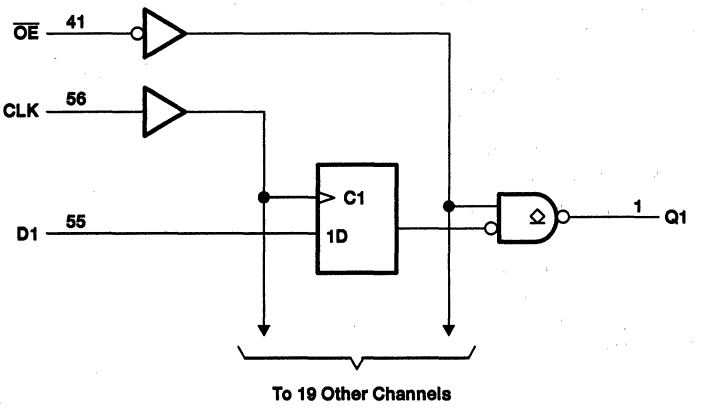
FUNCTION TABLE
(each flip-flop)

INPUTS			OUTPUT
$\overline{OE}$	CLK	D	Q
L	↑	H	H
L	↑	L	L
L	L	X	Q_0
H	X	X	Z

PRODUCT PREVIEW

EPIC-IIB and Widebus are trademarks of Texas Instruments Incorporated.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} ..... −0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) ..... −0.5 V to 4.6 V
Current into any output in the low state, I_O ..... 80 mA
Input clamp current, I_{IK} ($V_I < 0$) ..... −50 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > 0$) ..... ±50 mA
Continuous current through V_{CC} or GND ..... ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DGG package ..... 1 W
DL package ..... 1.4 W
Storage temperature range, T_{stg} ..... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions

		SN54GTL16921			SN74GTL16921			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
V_{CC}	Supply voltage	3		3.6	3		3.6	V
V_{REF}	Supply voltage	0.74	0.8	0.87	0.74	0.8	0.87	V
V_I	Input voltage	0		V_{CC}	0		V_{CC}	V
V_{OH}	High-level output voltage			3.6			3.6	V
V_{IH}	High-level input voltage	V_{REF} +50 mV			V_{REF} +50 mV			V
V_{IL}	Low-level input voltage			V_{REF} – 50 mV			V_{REF} – 50 mV	V
I_{IK}	Input clamp current			–18			–18	mA
I_{OL}	Low-level output current			40			40	mA
T_A	Operating free-air temperature	–55		125	0		70	°C

electrical characteristics over recommended operating free-air temperature range, V_{REF} = 0.8 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54GTL16921			SN74GTL16921			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 3 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OL}		V_{CC} = 3 V,	I_{OL} = 40 mA			0.4			0.4	V
I_I		V_{CC} = 3 V	$V_I = V_{CC}$			5			5	µA
			V_I = 0			–5			–5	
I_{OH}		V_{CC} = 3 V,	V_{OH} = 3.6 V							µA
I_{CC}	Outputs high	V_{CC} = 3 V,	I_O = 0,							mA
	Outputs low	$V_I = V_{CC}$ or GND								
C_i		Per IEEE1194.0-1991			4			4		pF
C_o		Per IEEE1194.0-1991			6			6		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

Contents

Mixing It Up With 3.3 Volts

Ken Ristow
Steve Perna
Advanced System Logic – Semiconductor Group

SCBA005

IMPORTANT NOTICE

Texas Instruments Incorporated (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to current specifications in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Please be aware that TI products are not intended for use in life-support appliances, devices, or systems. Use of TI product in such applications requires the written approval of the appropriate TI officer. Certain applications using semiconductor devices may involve potential risks of personal injury, property damage, or loss of life. In order to minimize these risks, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards. Inclusion of TI products in such applications is understood to be fully at the risk of the customer using TI devices or systems.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

Printed in the U.S.A.

Contents

List of Illustrations

Introduction

The evolution to a 3.3-V supply voltage is being driven by a complex matrix of requirements. Leading the way are the characteristics of advanced semiconductor processing and the need to reduce system power without a corresponding tradeoff in system performance. Reduction of the horizontal and vertical feature sizes of transistors is the most common method of increasing the density of cells that can be contained in an integrated circuit. These feature sizes or geometries are typically represented as minimum process dimensions for advanced products such as dynamic random access memories (DRAMs).

DRAM manufacturers have forecasted that all 64M-bit versions will be developed for operation from a supply voltage of 3.3 ± 0.3 V. For 16M-bit DRAM products, there is no such rule of thumb as certain vendors expect to operate from 3.3 V, while others offer different product versions with differing voltage levels. An approach used by several manufacturers is to provide 5-V power-supply operation externally with internal step-down conversion to 3.3 V. For static random access memories (SRAMs), manufacturers have announced that most 16M versions will operate at 3.3 V or lower (down to 2.7 V).

Typical 1M-bit DRAM geometries are on the order of 1.2 μm and it is not a problem to apply a 5-V power supply to this type of product. However, as the feature sizes of DRAMs shrink, the stresses of 5-V operation can preclude their reliable operation due to high field-effect failures. One such effect is hot-carrier injection that over time increases the transistor's threshold, leading to eventual nonoperation. Another field-effect concern is the breakdown of the transistor's gate oxide causing internal shorts; therefore, reducing the supply voltage is one way to ensure reliable operation of devices fabricated in state-of-the-art processes.

The reduction of V_{CC} from 5 V to 3.3 V reduces the power consumed by the device, which increases system reliability while reducing costs associated with the removal of the heat. The power consumption of a device is primarily a function of its capacitive load, frequency of operation, and supply voltage. However, capacitive load and frequency have a linear effect on a device's power consumption while supply voltage has a square relationship. Because of this square relationship, a small reduction in voltage significantly reduces the power consumed, as illustrated in Figure 1, and is a driving factor to 3.3-V operation.

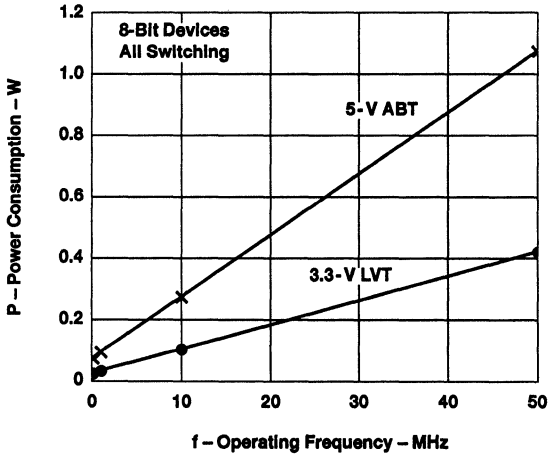


Figure 1. 3-V to 5-V Power Versus Frequency Comparison

The Market for Low Voltage

User demand for low-voltage products can be grouped into specific brackets depending on their performance-power priorities. End equipments, such as multiuser servers, engineering workstations, high-end desktop PCs, and other high-performance motherboards, favor high performance over low power, but are interested in 3.3-V products to reduce or eliminate bulky, noisy cooling fans in the attempt to shrink external case size for better desktop fit. Some end equipments favor low power at the expense of high performance such as battery-powered notebooks and palmtop computers, portable test equipment, and point-of-sale terminals. A few end equipments require equal priority for high performance and low power, such as laptop computers, automotive, and air/space products.

The universal benefits to users of low-voltage products are higher reliability and lower cost. The higher reliability is relative to standard 5-V solutions and results from lower stress gradients on device junctions and oxides, lower buildup of heat due to lower power consumption, and improved signal integrity from the reduction in ground bounce and signal noise. Lower power consumption usually yields lower costs since power costs money to generate and heat costs money to dissipate. All things considered, it is desirable to use inexpensive plastic packages instead of metal or ceramic to dissipate heat. For battery users, an added benefit of the lower power consumption of low-voltage products is one of increased battery lifetime.

Of all the end-equipment groups that can benefit from the use of low-voltage products, it appears that demand will be initially driven by battery-operated computers. This market segment is defined by notebook and palmtop computers, as well as point-of-sale terminals, which are designed to capture data at remote field sites and either store it for downloading later or transmit it real time via an on-board transmitter. The goal for these systems is to have a battery life of eight to ten hours, roughly the equivalent of one workday or the time to complete a transcontinental airplane trip.

The unregulated battery market is itself quite varied however, because different batteries exhibit very different voltage characteristics between fully charged and discharged states. Two AA batteries provide for 3-V supply when charged, decreasing to about 2.7 V after use. Three NiCad batteries provide for a baseline 3.6-V supply fully charged, but the spread actually runs from about 3.3 V up to 3.9 V. For now, the unregulated battery market demands low-voltage products that are optimized to run from 2.7 V up as high as 3.9 V. Since performance is directly related to supply voltage, it is more important for device optimization to be extended down to 2.7 V, where devices slow down appreciably.

There are some barriers for low-voltage acceptance in the short term. Specification standardization remains an issue. Also, the access to adequate supplies of 3.3-V devices can be a problem. Generally, DRAM memories are leading the way into 3.3-V operation with SRAM memories close behind. Coupled with the low-voltage microprocessors now available, systems are being implemented with the core components operating at 3.3 V. Hindering the migration to a full 3.3-V system is the availability of support products such as: disk drives, LCDs, A/D converters, RF transmitters, and EPROMS.

Migration to 3.3 V

The need to migrate to power supplies with supply voltages less than 3.3 V has been an issue since 1984 when two JEDEC standards were adopted. Standard 8.0 was intended to address both regulated (3-V to 3.6-V) and unregulated (2-V to 3.6-V) battery applications. Standard 8.1 was intended to address higher-performance applications operating from a regulated power supply that could interface to a standard 5-V TTL device as well as a low-voltage device. Essentially Standard 8.0 established regulated low-voltage CMOS (LVCMOS) and unregulated low-voltage battery-operated (LVBO) interfaces, and Standard 8.1 established the low-voltage TTL (LVTTL) interface.

Committee members have since determined that the original two standards are inadequate. Since most systems currently require a TTL interface, Standard 8.1 LVTTL is the most critical one being reviewed now. When ratified, the new LVTTL standard will present methods for interfacing with 5-V systems and contain a provision for battery-operated systems. Until this happens, a generic lack of compatibility will exist between the various 3.3-V and 5-V interfaces.

Existing solutions for 3.3-V operation have historically been 5-V products and processes characterized for 3.3-V operation. A CMOS process is typically chosen because of the scaling effect of the inverter thresholds with respect to the supply voltage. HCMOS and Advanced CMOS devices support both 5-V and 3.3-V operation by this method. One drawback is slower propagation delay when compared to parts specifically designed for 3-V operation. A limitation of many of these devices is their inability to directly interface to a 5-V system when running off a 3.3-V supply, due to diodes from the input and input/output (I/O) pins to V_{CC}. This limits input voltages to V_{CC} + 0.5 V and limits direct connection to a 5-V system.

Mixed-Mode Operation

This dilemma of device incompatibility between the large installed base of 5-V systems with the newly emerging 3.3-V systems is a serious industry concern. Mixed-mode operation allows for direct communication between the two systems. Devices that support this mode must be designed for maximum input voltages of 5.5 V, without any long-term reliability issues. Another concern is that the output drive must be capable of driving a standard-TTL backplane, while still providing for rail-to-rail switching for compatibility with 3-V CMOS systems.

Figure 2 compares the standard-TTL dc interface levels with two of the emerging low-voltage standards. Low-voltage CMOS (LVCMOS) is a pure CMOS specification that specifies low current rail-to-rail output drive along with input voltage levels, V_{IH} and V_{IL}, which are ratios of V_{CC}. Low-voltage TTL (LVTTL) utilizes the standard-TTL input levels of 0.8 V and 2 V, as well as specifying a higher dc output drive than LVCMOS. To ensure interoperability between these three varied standards, a multipurposed low-voltage interface device must meet all of the requirements of the three different specifications.

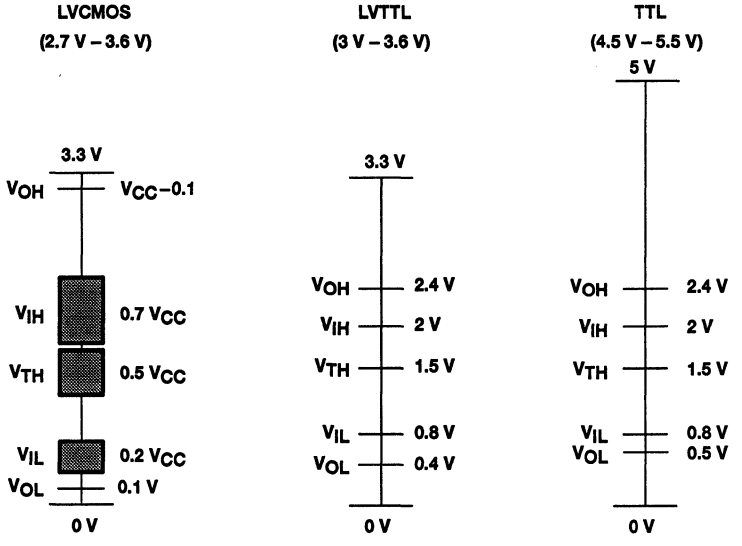


Figure 2. Comparison of 3.3-V and 5-V Interfaces

LVT Family Characteristics

To address the need for a complete low-voltage interface solution, Texas Instruments has developed a new generation of logic devices capable of mixed-mode operation. The LVT series of devices rely on a state-of-the-art submicron BiCMOS process to provide up to a 90% reduction in static power dissipation over ABT devices and provides the following family characteristics:

5.5-V maximum input voltage

Specified 2.7-V to 3.6-V supply voltage

I/O structures that support power-on (live) insertion

Standard TTL output drives of:
V_{OH} = 2 V at I_{OH} = –32 mA
V_{OL} = 0.55 V at I_{OL} = 64 mA

Rail-to-rail switching for driving CMOS

Maximum supply currents of:
I_{CCL} = 15 mA
I_{CCH} = 250 µA
I_{CCZ} = 250 µA

Propagation delays of:
t_{pd} < 4.6 ns
t_{pd} (LE to Q) < 5.1 ns
t_{pd} (CLK to Q) < 6.3 ns

Surface-mount packaging support including fine-pitch packages:
48- and 56-pin SSOP for LVT Widebus™
20- and 24-pin TSSOP for standard LVT

LVT input/output characteristics

Figure 3 shows a simplified LVT output and illustrates the mixed-mode signal drive designed into the output stage. This combination of a high-drive TTL stage with the rail-to-rail CMOS switching gives the LVT series of product extreme application flexibility. These parts have the same drive characteristics as 5-V ABT devices, as shown in Figure 4, providing the dc drive needed for existing 5-V backplanes and allowing for a simple solution to reduce system power via the migration to 3.3-V operation.

Not only can LVT devices operate as 3-V-to-5-V level translators by supporting input or I/O voltages of 5.5 V with V_{CC} = 2.7 V to 3.6 V, the inputs can withstand 5.5 V even when V_{CC} = 0 V. This allows for the devices to be used under partial system power-down applications or when live insertion is required.

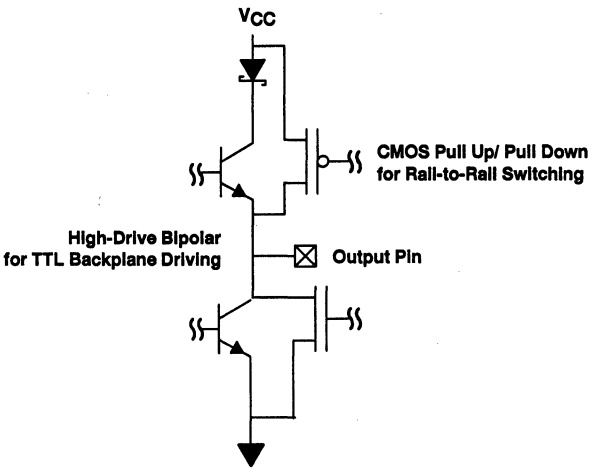


Figure 3. Simplified LVT Output Structure

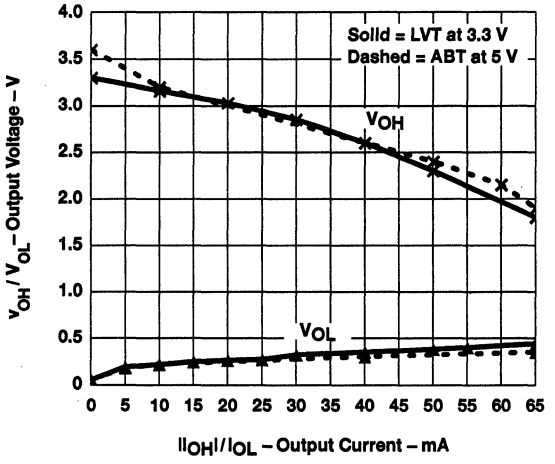


Figure 4. ABT Versus LVT Output Drive Comparison

Bus Hold

Many times devices are used in applications that do not provide a pullup or pulldown voltage to the input or I/O pin when the driving device goes into a high-impedance state, as in the case of CMOS buses or nonbused lines. To prevent application problems or oscillations, a large pullup resistor is typically used, but this consumes board area and contributes to driver loading. The LVT series of devices incorporate active circuitry that holds unused or floating inputs or I/Os at a valid logic level. This circuitry provides for a typical holding current, ±100 μA, that is sufficient enough to overcome any CMOS-type leakages. Since this is an active circuit, it does take current, approximately ±500 μA, to toggle the state of the input. This current is negligible when compared to the magnitude of current that is needed to charge a capacitive load and does not affect the propagation delay of the driving output.

Conclusion

LVT devices solve the system need for a transparent interface between the low-voltage and 5-V sections by providing for mixed-signal operation. The devices support live insertion or partial-power applications while providing low-input leakage currents. The outputs are capable of driving today's 5-V backplanes with a considerable reduction in the device's power consumption and are packaged in state-of-the-art fine-pitch surface-mount packages.

Low-Cost, Low-Power Level Shifting in Mixed-Voltage Systems

Mark McClear
Advanced System Logic – Semiconductor Group

SCBA002

TEXAS INSTRUMENTS

IMPORTANT NOTICE

Texas Instruments Incorporated (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to current specifications in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Please be aware that TI products are not intended for use in life-support appliances, devices, or systems. Use of TI product in such applications requires the written approval of the appropriate TI officer. Certain applications using semiconductor devices may involve potential risks of personal injury, property damage, or loss of life. In order to minimize these risks, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards. Inclusion of TI products in such applications is understood to be fully at the risk of the customer using TI devices or systems.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

Printed in the U.S.A.

Contents

List of Illustrations

Introduction

The increasing demand for lower system power consumption has brought many new design challenges. Among them is the problem of safely and efficiently interfacing the various switching levels in today's mixed 3.3-V and 5-V systems while maintaining the lowest possible total-system power consumption. Two competing methods of accomplishing this mixed-mode signal translation have emerged:

Split-rail or dual 3.3-V and 5-V V_{CC} devices

Completely 5-V tolerant, pure 3.3-V V_{CC} components

This application report deals with the pros and cons of using both device types and offers additional suggestions for even greater system-power savings.

Split-Rail Level Shifters

Split-rail level shifters are a class of transceiver devices that have both a 5-V and 3.3-V V_{CC} rail. Products in this class can be used effectively as level shifters and datapath voltage translators, but the following precautions are usually recommended:

Dual-V_{CC} rail devices typically have strict power sequencing requirements to prevent leakage or even damage to the devices in the event that one V_{CC} rail ramps faster than the other. These stringent requirements are often difficult to meet from a system-timing standpoint and offer little flexibility for partial system power down or other advanced power-saving design techniques.

Simply because the device has a 5-V V_{CC} pin does not necessarily ensure that the part will actually switch all the way to the 5-V rail. Switching to 5 V is one way to reduce the power consumption in 5-V memories or other pure 5-V CMOS circuits that are driven by a level-shifter device (this application report demonstrates others as well).

A quick check of the data sheet for the product in question reveals if the part drives all the way to the 5-V rail. If the output high voltage (V_{OH}) minimum is around 4.44 V, it does drive to the rail. Five-volt level shifters with TTL-compatible outputs typically drive only to around 3.6 V.

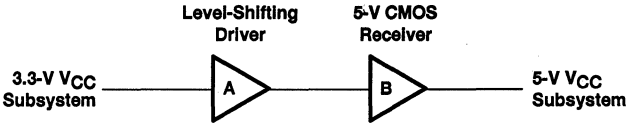
5-V Tolerant, Pure 3.3-V V_{CC} Level Shifters

A second class of products created to meet these design challenges offers the same voltage translation and level-shifting capabilities as the split-rail devices previously mentioned. From a single V_{CC} source, they avoid the power-sequencing problems of the split rails and are also offered in a number of functions, bit widths, and storage options. The one potential drawback of the single-V_{CC} products is that the outputs do not pull all the way to the 5-V V_{CC} rail . . . but is this really a drawback?

The Misconception About ΔI_{CC}

The component selection of a level shifter impacts two major aspects of total system-power dissipation:

The impact that the V_{OH} level of the driving part (A in Figure 1) has on the power dissipation of the receiving device (B in Figure 1), commonly known as ΔI_{CC}, and the power of the device itself.



Note: Unidirectional mode illustrated for simplicity.

Figure 1. Basic Logic Data Transceiver

ΔI_{CC} is the added power dissipation induced into a TTL-compatible 5-V CMOS device (B in Figure 1) due to the V_{OH} level of the driving device (A in Figure 1). It would correctly be expected that a TTL-compatible 5-V CMOS product have higher power dissipation if it was driven by a device with a V_{OH} of 3.6 V than if that same device was driven by a 5-V V_{OH} driver.

Figure 2 shows a typical CMOS input stage and the ΔI_{CC} current associated with switching the device through the input voltage range from 0 to V_{CC}.

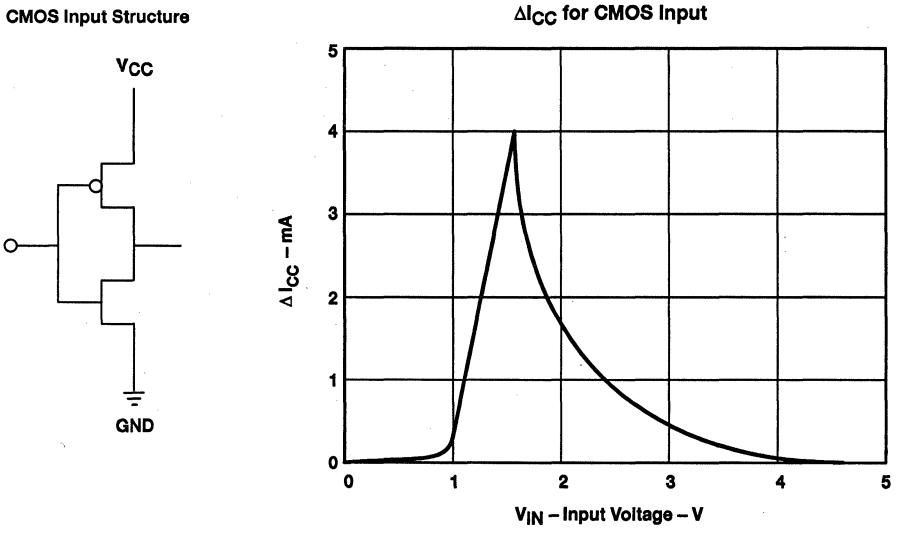


Figure 2. Basic CMOS Input Structure and Typical ΔI_{CC} Current

As expected, the ΔI_{CC} current approaches zero at the V_{CC} and ground rails, and peaks in the TTL-threshold region of 1.5 V.

Figure 3 is a graph of the ΔI_{CC} (i.e., additional I_{CC}) that is induced into a 16-bit device (all outputs switching) as a function of V_{OH} and frequency.

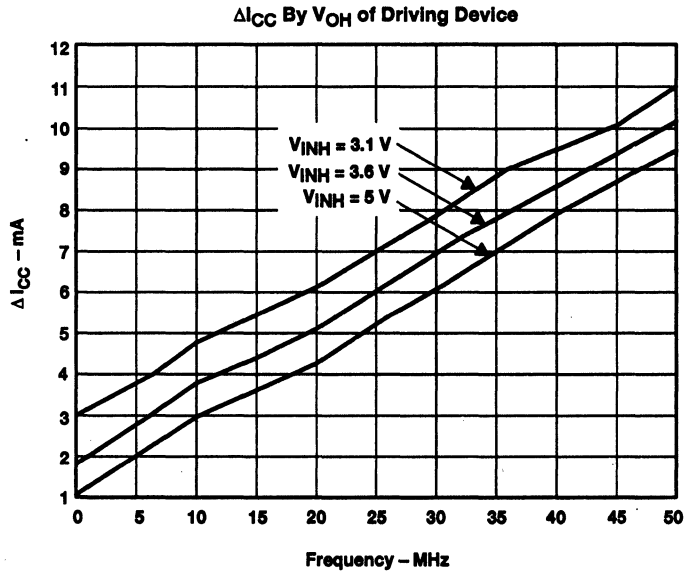


Figure 3. ΔI_{CC} – 16-Bit Device

As shown in Figure 3, ΔI_{CC} is in fact 2 to 3 mA higher for the case where V_{OH} is only 3.1 V than for the same device driven to the 5-V rail by a pure 5-V CMOS device. From this, one might be tempted to conclude that the best possible solution would be to always select a part that switches all the way to the 5-V rail, but this conclusion fails to consider the system-power impact of the driving device.

Figure 4 shows the V_{OH} of two devices: the FCT164245 split-rail device from Integrated Device Technologies and the 'LVT16245A from Texas Instruments.

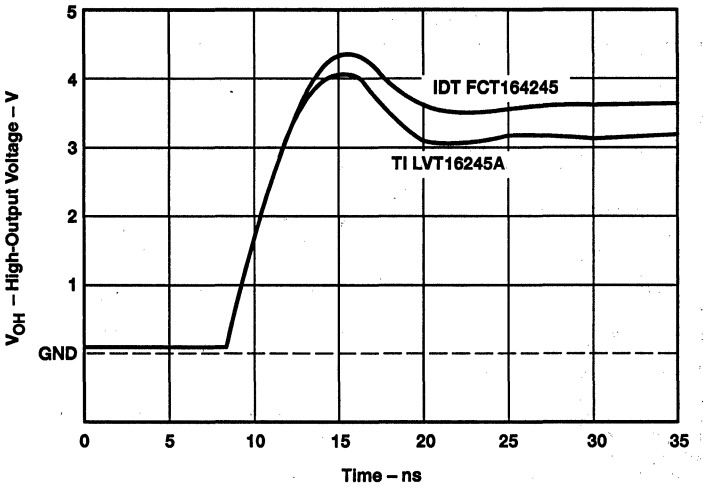


Figure 4. V_{OH} of FCT164245 and 'LVT16245A

From Figure 4, it can be correctly concluded that the induced ΔI_{CC} current in a part driven by the LVT part would be higher than the FCT device. The problem with this conclusion is that ΔI_{CC} is only one of the two components of total-system power dissipation that selection of a level-shifter device has from system standpoint.

Figure 5 shows the total power dissipation of the same IDT split-rail device, the TI 'LVT16245A, and the worst-case ΔI_{CC} (V_{OH} = 3.1 V) graphed on the same vertical scale.

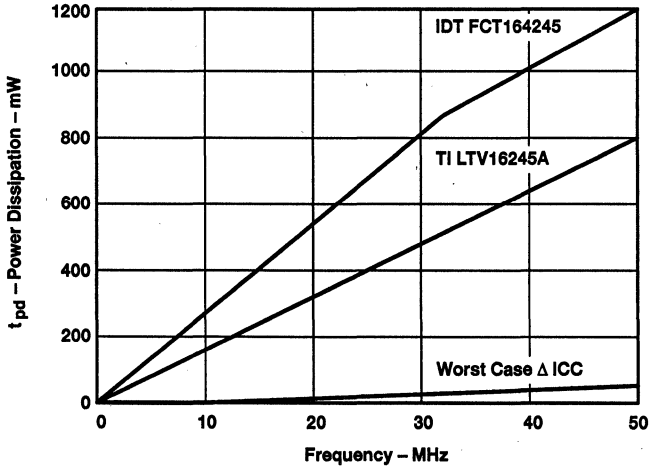


Figure 5. Total-System Power-Dissipation Impact

From Figure 5, it can be seen that even if a split-rail device pulls all the way to the 5-V rail (which the IDT part does not), the power savings in ΔI_{CC} is more than offset by the huge switching currents that the split rail draws from the 5-V rail. The negative implications on heating, reliability, and battery life are obvious.

More Savings Are Possible

Some systems use a means of power savings known as partial power down. In partial power-down mode, a system basically shuts off the V_{CC} to some unused circuits during times of inactivity, thus eliminating even low standby currents. All of the members of TI's low-voltage technology (LVT) product line previously mentioned offer a parametric specification I_{off}, which ensures that the output pins of the parts remain in a high-impedance state when the supply voltage is at 0 V. This prevents an inactive LVT device from dragging down the bus of an active part in the system and allows the LVT part to become a partition for the partially powered-down unused subsystem. The LVT device still functions as a level shifter and voltage translator when power is restored to the inactive subsystem.

Another aspect of system power dissipation is the use of passive resistor pullups to keep a local bus from floating and causing damage to the devices on the bus. Pullups were sufficient for the older desktop systems where power consumption was not as much of a concern, but pullup resistors in portable equipment can have a serious impact on battery life, and as such must be addressed.

Products like the 'LVT16245A (and others) from TI have a circuit feature called a bus-hold cell (shown in Figure 6). This cell eliminates these passive components and all of the procurement costs, board space, bus parasitics, and, also, power dissipation associated with them. The bus-hold cell does not load down the bus or add any significant power dissipation to the LVT device.

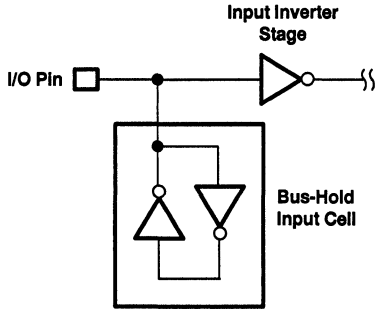


Figure 6. LVT Bus-Hold Cell

Conclusion

Mixed 3.3-V and 5-V systems can be optimized for low power and low cost by the judicious selection of the appropriate voltage-level shifter component. Split-rail level shifters can affect this voltage translation, but selection of this device is burdened with serious design tradeoffs in power sequencing, partial system power down, and system power dissipation. Further savings in both power and component cost can be realized if the component selected has a bus-hold cell or other means of eliminating passive system components.

LVT Family Characteristics

Ken Ristow
Advanced System Logic – Semiconductor Group

SCEA002

TEXAS INSTRUMENTS

IMPORTANT NOTICE

Texas Instruments Incorporated (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to current specifications in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Please be aware that TI products are not intended for use in life-support appliances, devices, or systems. Use of TI product in such applications requires the written approval of the appropriate TI officer. Certain applications using semiconductor devices may involve potential risks of personal injury, property damage, or loss of life. In order to minimize these risks, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards. Inclusion of TI products in such applications is understood to be fully at the risk of the customer using TI devices or systems.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

Printed in the U.S.A.

Introduction

To address the need for a complete low-voltage interface solution, Texas Instruments has developed a new generation of logic devices capable of mixed-mode operation. The LVT series rely on a state-of-the-art submicron BiCMOS process to provide up to a 90% reduction in static power dissipation over ABT, as well as the following family characteristics:

5.5-V maximum input voltage

Specified 2.7-V to 3.6-V supply voltage

I/O structures which support live insertion

Standard TTL output drives of:
V_{OH} = 2 V at I_{OH} = −32 mA
V_{OL} = 0.55 V at I_{OL} = 64 mA

Rail-to-rail switching for driving CMOS

Maximum supply currents of:
$I_{CCL} \leq 15$ mA
$I_{CCH} \leq 200$ µA
$I_{CCZ} \leq 200$ µA

Propagation delays of:
$t_{pd} < 4.6$ ns
t_{pd} (LE to Q) < 5.1 ns
t_{pd} (CLK to Q) < 6.3 ns

Surface mount packaging support including fine-pitch packages:
48-/56-pin SSOP and TSSOP for LVT Widebus™
20-/24-pin SOIC and TSSOP for standard LVT

LVT Input/Output Characteristics

Figure 1 shows a simplified LVT output and illustrates the mixed-mode-signal drive designed into the output stage. This combination of a high-drive TTL stage along with the rail-to-rail CMOS switching gives the LVT series of product extreme application flexibility. These parts have the same drive characteristics as 5-V ABT devices (see Figure 2), and provide the dc drive needed for existing 5-V backplanes. This allows for a simple solution to reduce system power via the migration to 3.3-V operation.

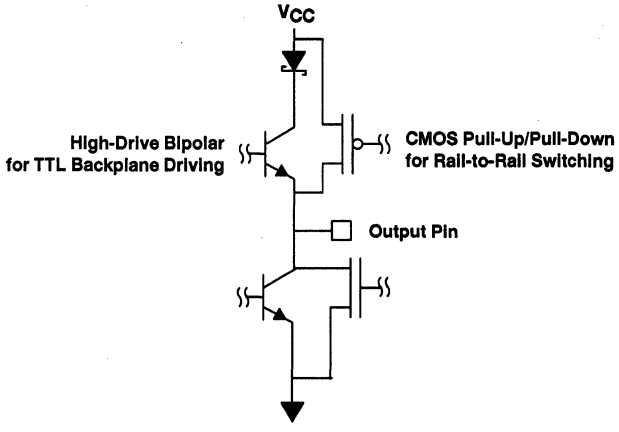


Figure 1. Simplified LVT Output Structure

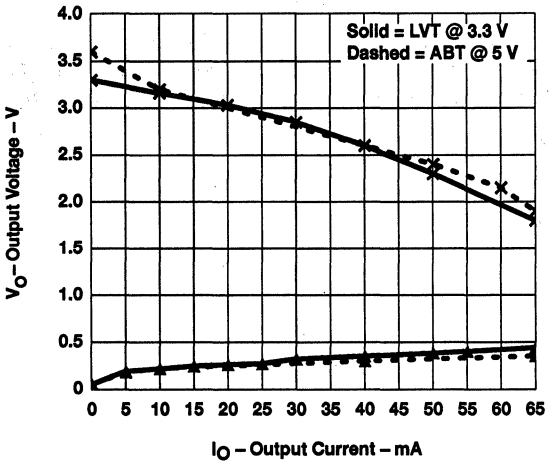


Figure 2. ABT Versus LVT Output-Drive Comparison

Not only can LVT devices operate as 3-V to 5-V level translators by supporting input or I/O voltages of 5.5 V with V_{CC} = 2.7 V to 3.6 V, the inputs can withstand 5.5 V even when V_{CC} = 0 V. This allows for the devices to be used under partial system power-down applications or those which require live insertion.

Bus Hold

Many times, devices are used in applications that do not provide a pullup or pulldown voltage to the input or I/O pin when the driving device goes into a high-impedance state, as in the case of CMOS buses or nonbused lines. To prevent application problems or oscillations, a large pullup resistor is typically used, but this consumes board area and contributes to driver loading. The LVT series of devices incorporate active circuitry that holds unused or floating inputs or I/Os at a valid logic level. This circuitry provides for a typical holding current, ±100 μA, that is sufficient enough to overcome any CMOS-type leakages. Since this is an active circuit, it does take current, approximately ±500 μA, to toggle the state of the input. This current is trivial when compared to the tens of mA of current that is needed to charge a capacitive load, thereby not affecting the propagation delay of the driving output.

Conclusion

LVT devices solve the system need for a transparent seam between the low-voltage and 5-V sections by providing for mixed-signal operation. The devices support live-insertion or partial-power applications, while providing for low-input leakage currents. The outputs are capable of driving today's 5-V backplanes, with a considerable reduction in device power consumption, as well as being packaged in state-of-the-art fine-pitch surface-mount packages.

'LVT244 Characteristics

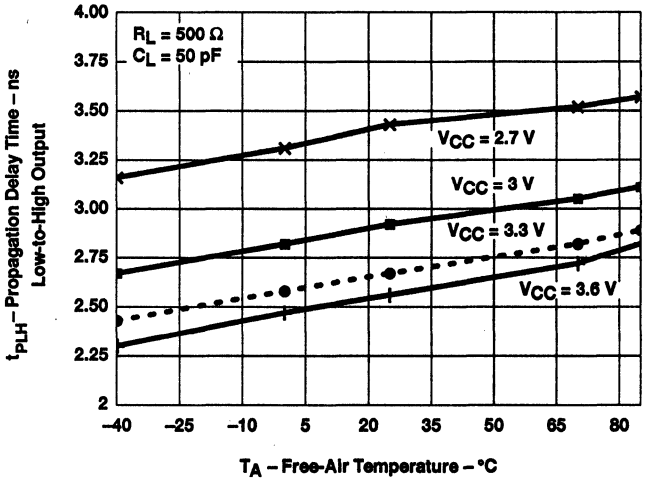


Figure 3. Propagation Delay Versus Free-Air Temperature

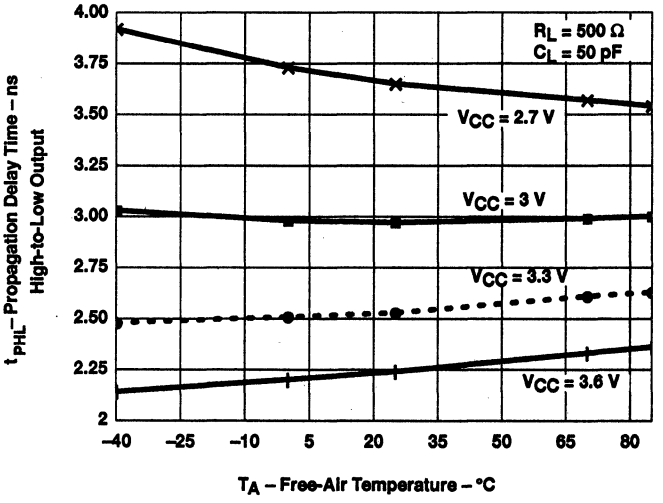


Figure 4. Propagation Delay Versus Free-Air Temperature

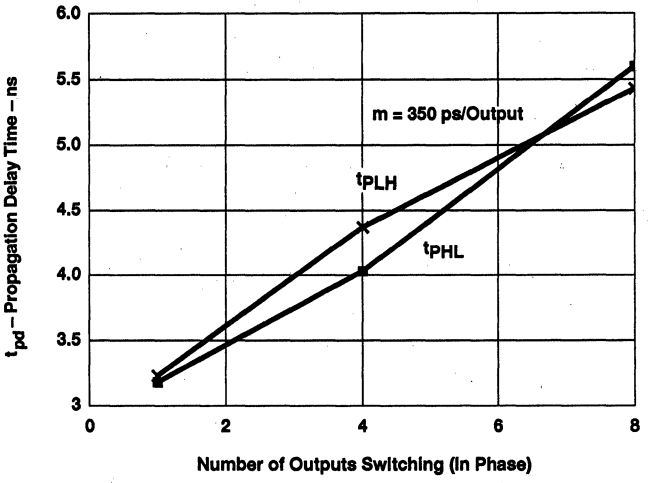


Figure 5. Propagation Delay Versus Outputs Switching

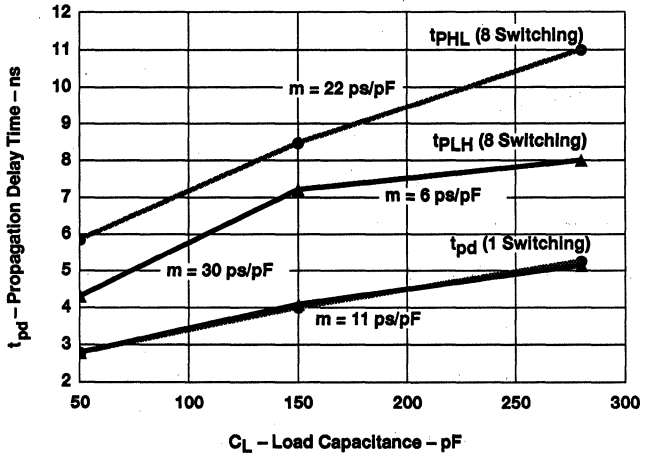


Figure 6. Propagation Delay Versus Load Capacitance

'LVT244 Typical dc Characteristics

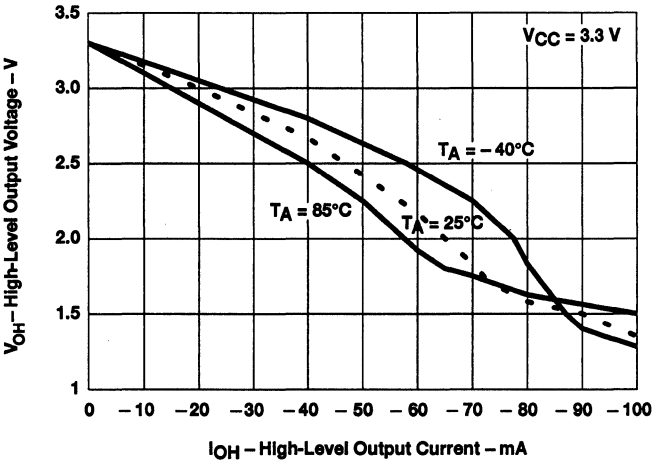


Figure 7. High-Level Output Voltage Versus High-Level Output Current

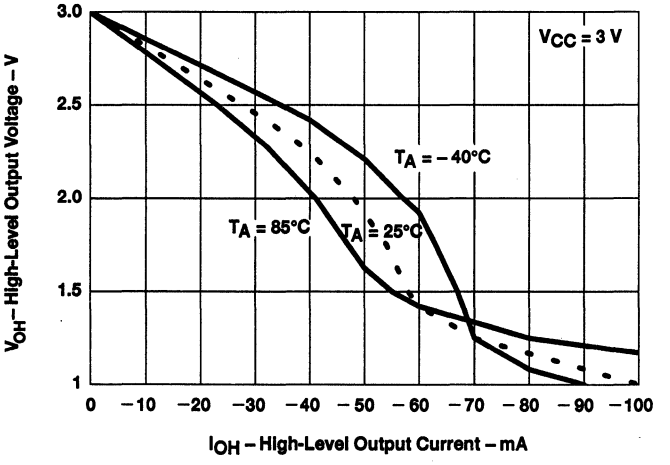


Figure 8. High-Level Output Voltage Versus High-Level Output Current

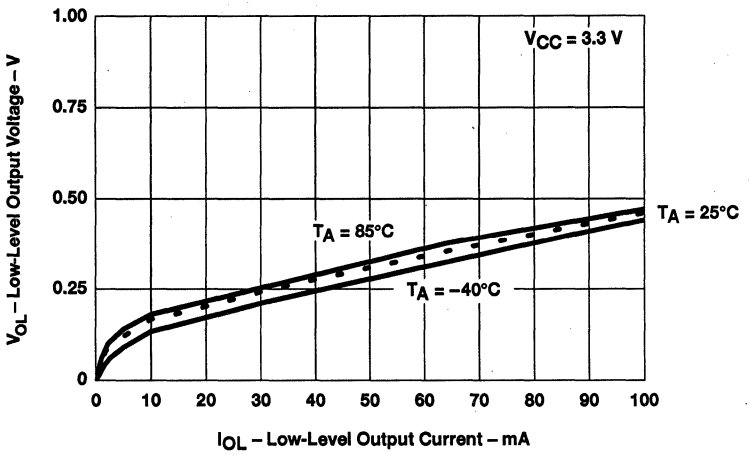


Figure 9. Low-Level Output Voltage Versus Low-Level Output Current

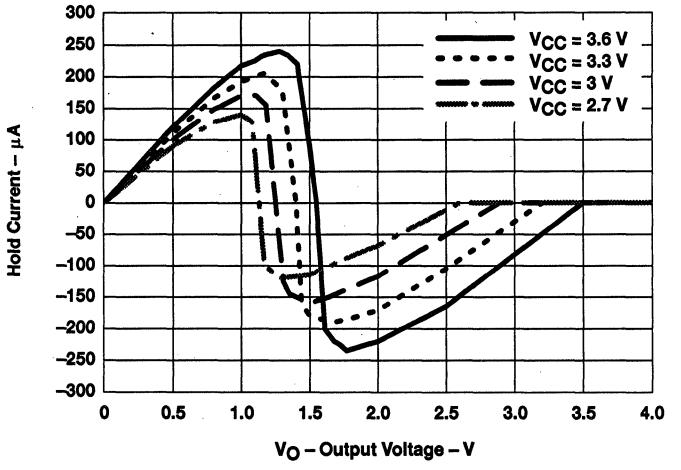


Figure 10. Hold Current Versus Output Voltage

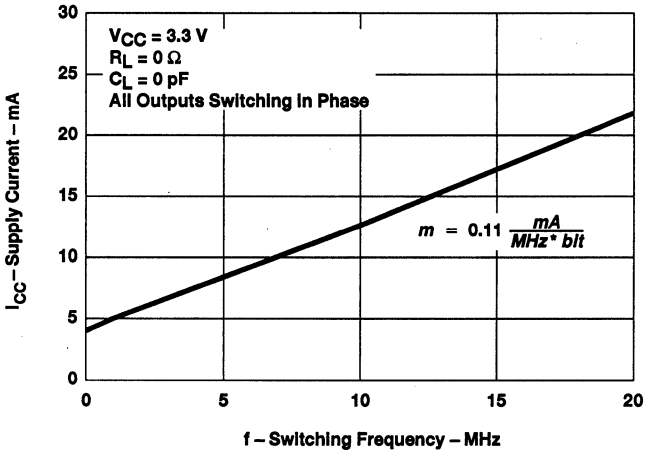


Figure 11. Supply Current Versus Switching Frequency

Unloaded t_r and t_f Rates

The circuit shown in Figure 12 was used to measure the unloaded transition rates of the output.

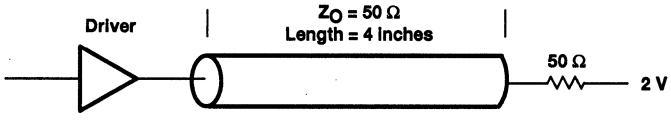


Figure 12. Load Circuit

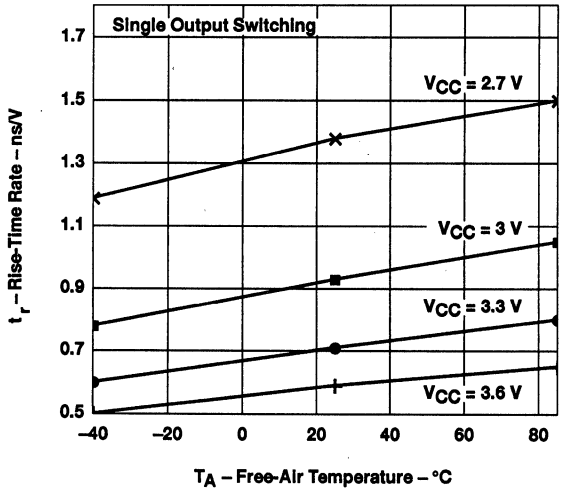


Figure 13. Rise-Time Rate Versus Free-Air Temperature

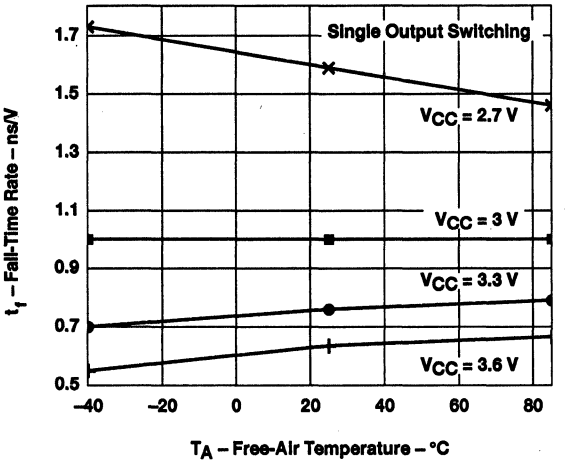


Figure 14. Fall-Time Rate Versus Free-Air Temperature

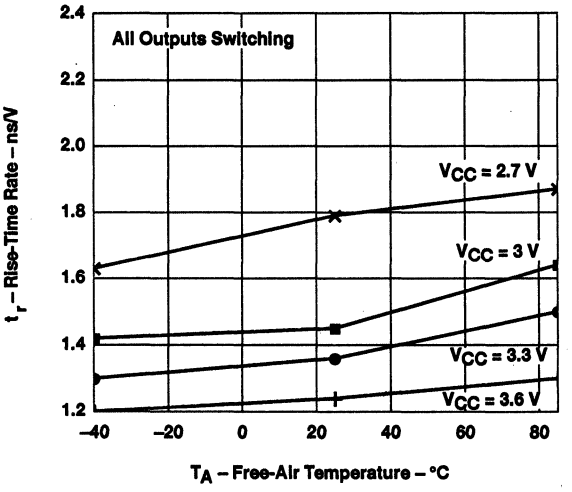


Figure 15. Rise-Time Rate Versus Free-Air Temperature

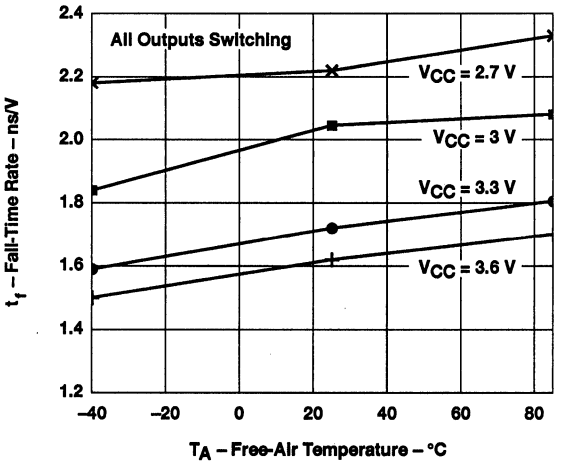


Figure 16. Fall-Time Rate Versus Free-Air Temperature

'LVT646 Characteristics

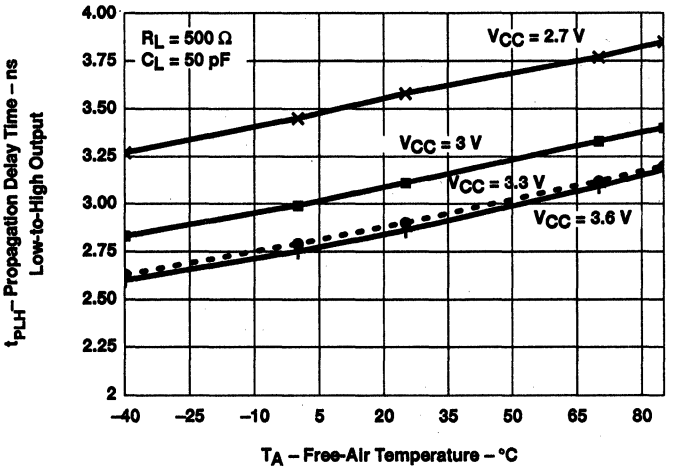


Figure 17. Through-Mode Propagation Delay Versus Free-Air Temperature

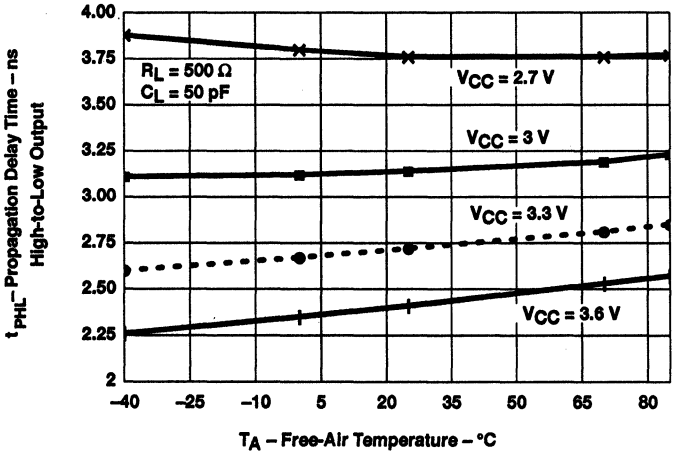


Figure 18. Through-Mode Propagation Delay Versus Free-Air Temperature

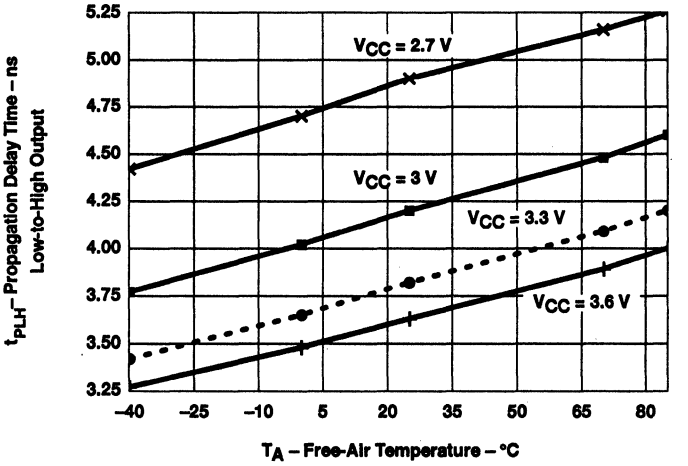


Figure 19. Clock-to-Q Propagation Delay Versus Free-Air Temperature

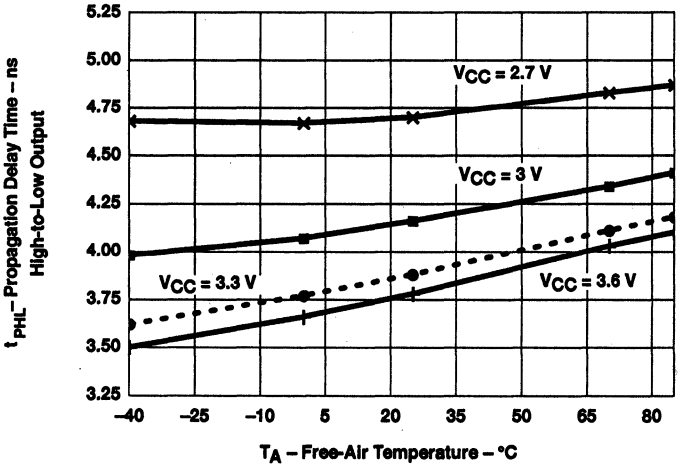


Figure 20. Clock-to-Q Propagation Delay Versus Free-Air Temperature

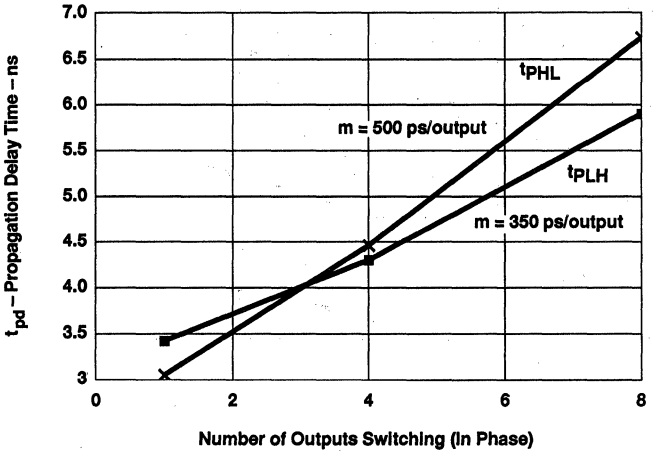


Figure 21. Propagation Delay Versus Outputs Switching

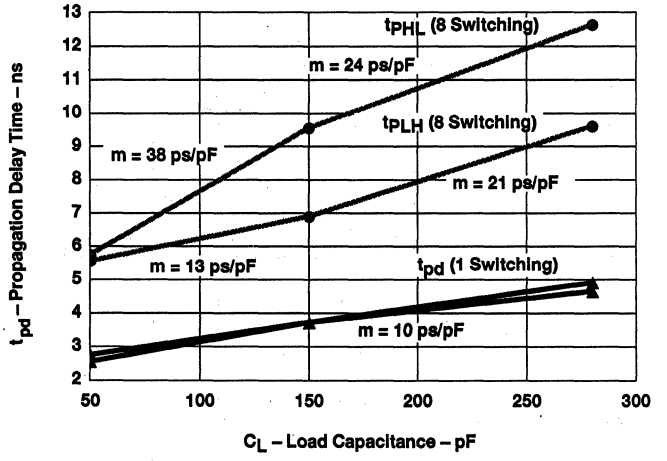
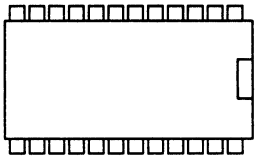


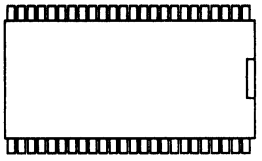
Figure 22. Propagation Delay Versus Load Capacitance

Packaging Options



24-Pin SOIC (DW)†
Area = 165 mm^2
Height = 2.65 mm
Lead pitch = 1.27 mm

Widebus™



48-Pin SSOP (DL)†
Area = 171 mm^2
Height = 2.74 mm
Lead pitch = 0.635 mm

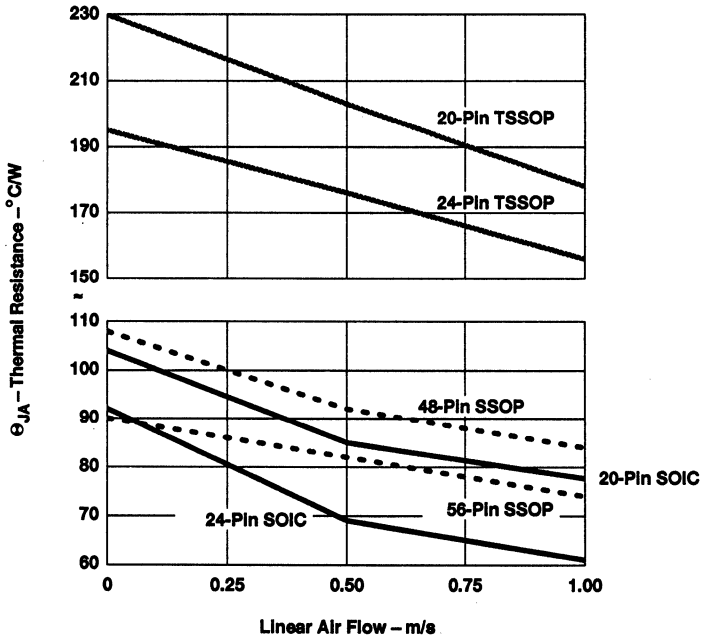
24-Pin TSSOP (PW)†
Area = 54 mm^2
Height = 1.1 mm
Lead Pitch = 0.65 mm

Shrink Widebus™

48-Pin TSSOP (DGG)†
Area = 108 mm^2
Height = 1.1 mm
Lead Pitch = 0.5 mm

† TI package designators

Thermal Characteristics

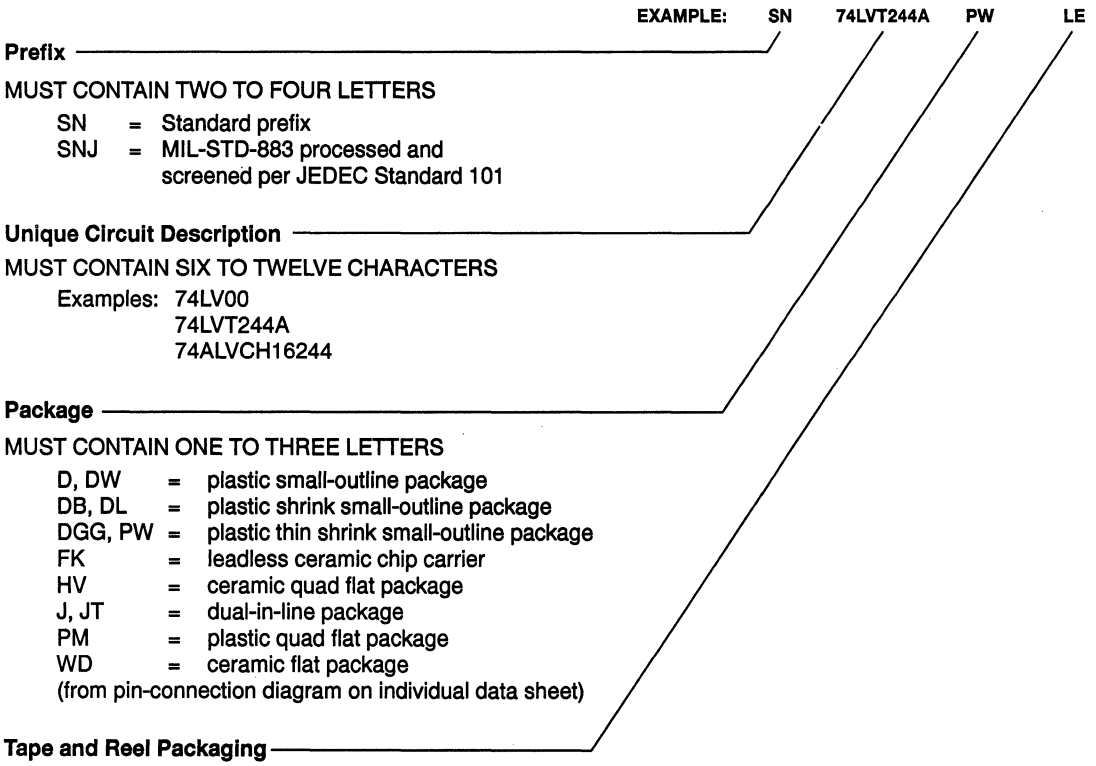


Widebus and Shrink Widebus are trademarks of Texas Instruments Incorporated.

Contents

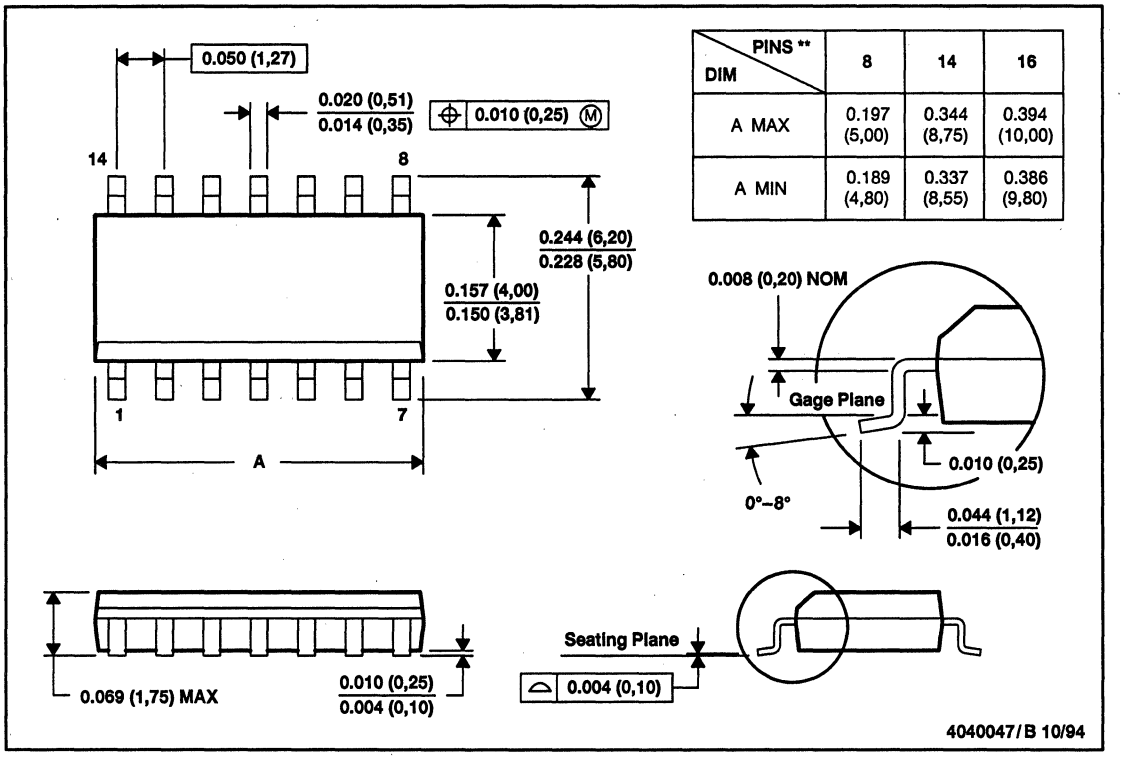
Electrical characteristics presented in this data book, unless otherwise noted, apply for the circuit type(s) listed in the page heading regardless of package. The availability of a circuit function in a particular package is denoted by an alphabetical reference above the pin-connection diagram(s). These alphabetical references refer to mechanical outline drawings shown in this section.

Factory orders for circuits described in this catalog should include a three-part type number as explained in the following example.



D (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14 PIN SHOWN

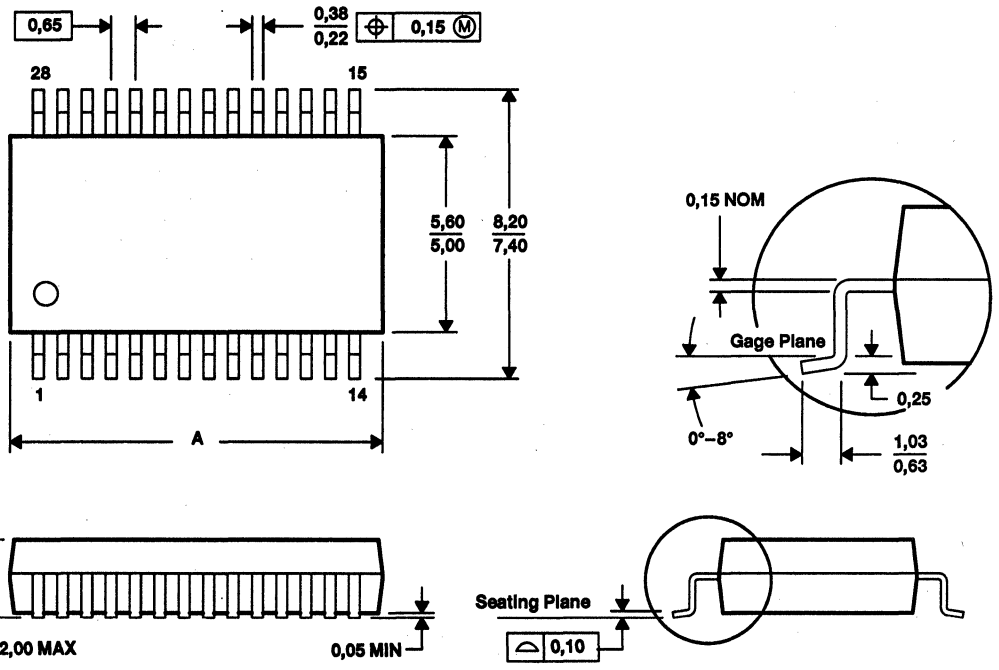


DIM \ PINS **	8	14	16
A MAX	0.197 (5,00)	0.344 (8,75)	0.394 (10,00)
A MIN	0.189 (4,80)	0.337 (8,55)	0.386 (9,80)

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Four center pins are connected to die mount pad.
E. Falls within JEDEC MS-012

DB (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

28 PIN SHOWN



DIM \ PINS **	14	16	20	24	28	30	38
A MAX	6,50	6,50	7,50	8,50	10,50	10,50	12,90
A MIN	5,90	5,90	6,90	7,90	9,90	9,90	12,30

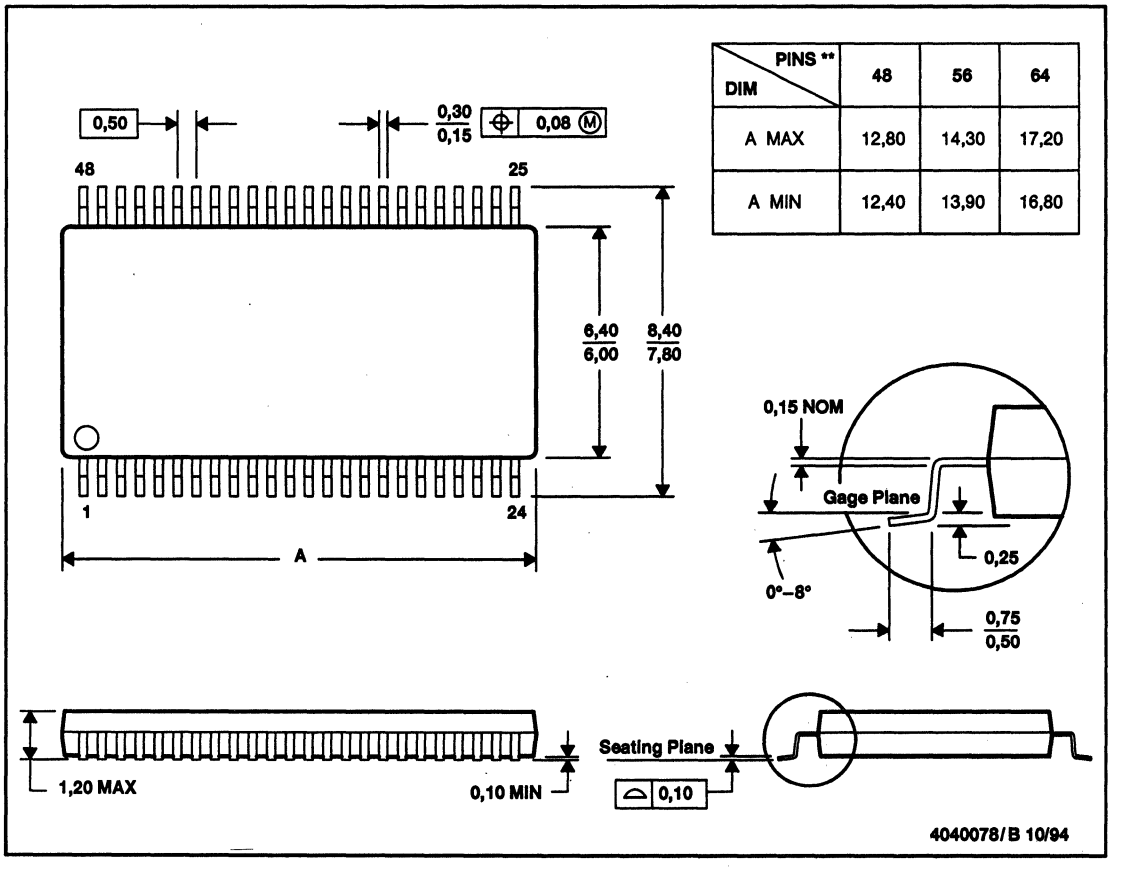
4040065 / B 10/94

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-150

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

DGG (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

48 PIN SHOWN

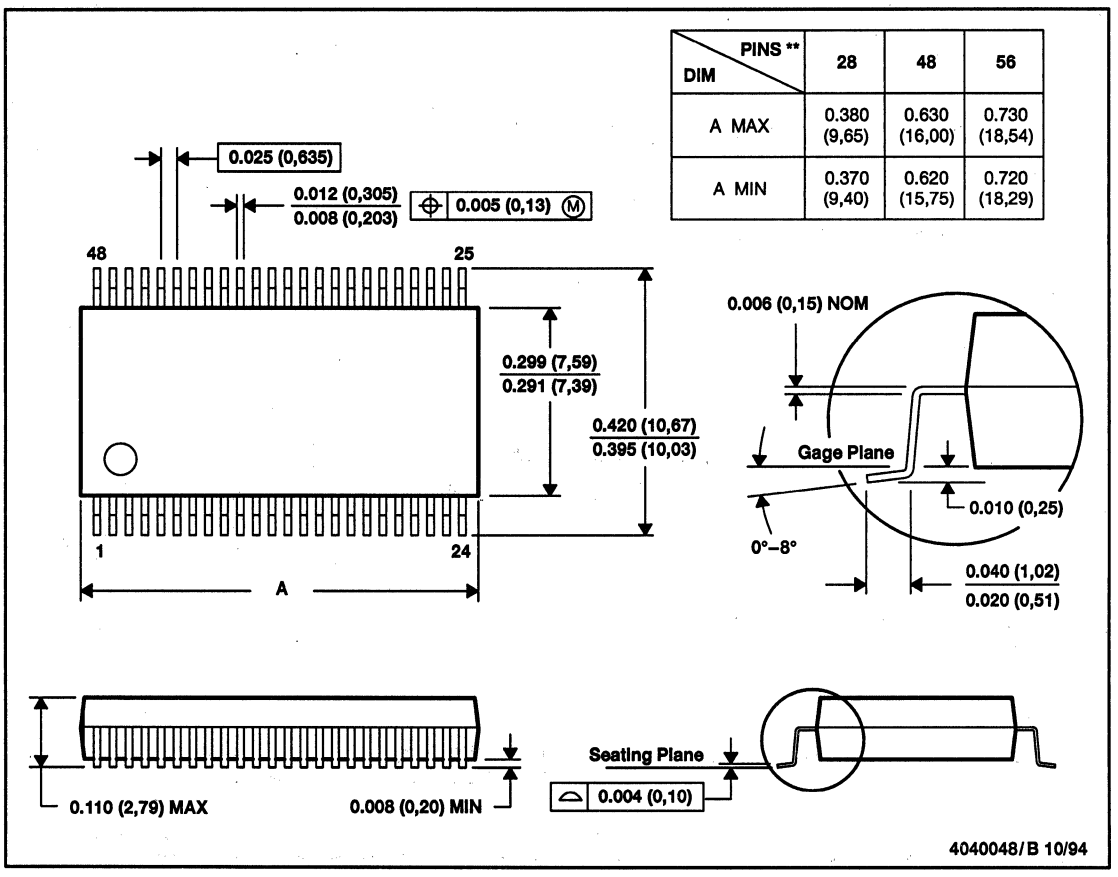


DIM \ PINS **	48	56	64
A MAX	12,80	14,30	17,20
A MIN	12,40	13,90	16,80

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.

DL (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

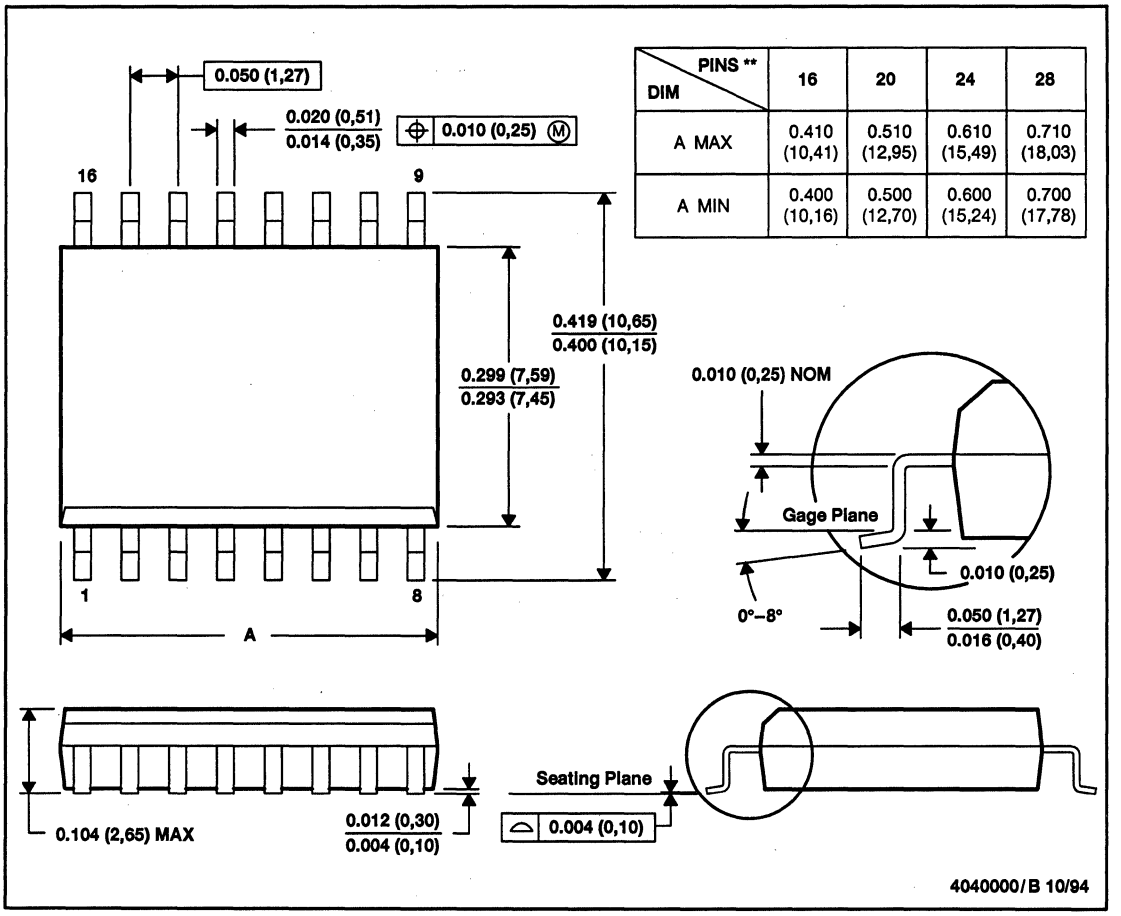
48 PIN SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

DW (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

16 PIN SHOWN

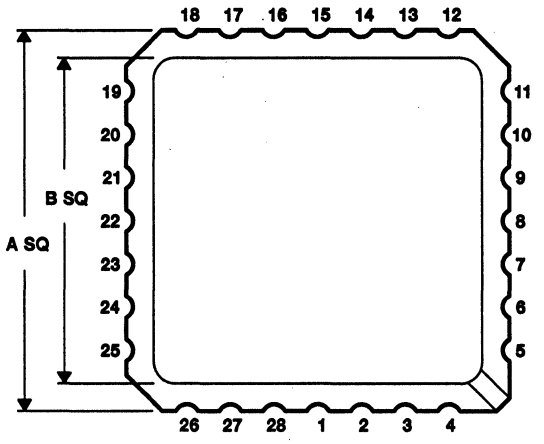


DIM \ PINS **	16	20	24	28
A MAX	0.410 (10,41)	0.510 (12,95)	0.610 (15,49)	0.710 (18,03)
A MIN	0.400 (10,16)	0.500 (12,70)	0.600 (15,24)	0.700 (17,78)

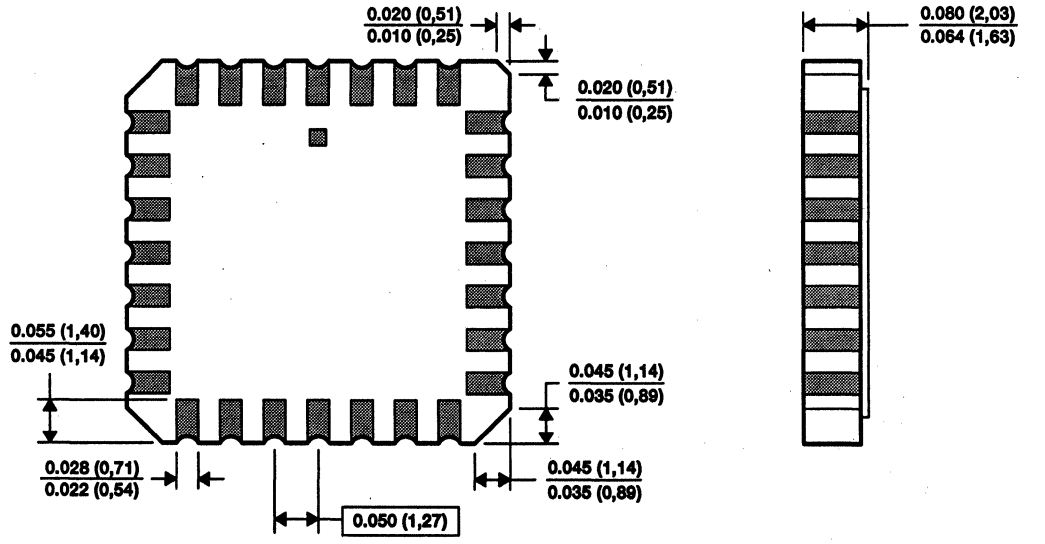
NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS-013

FK (S-CQCC-N)** **LEADLESS CERAMIC CHIP CARRIER**

28 TERMINAL SHOWN



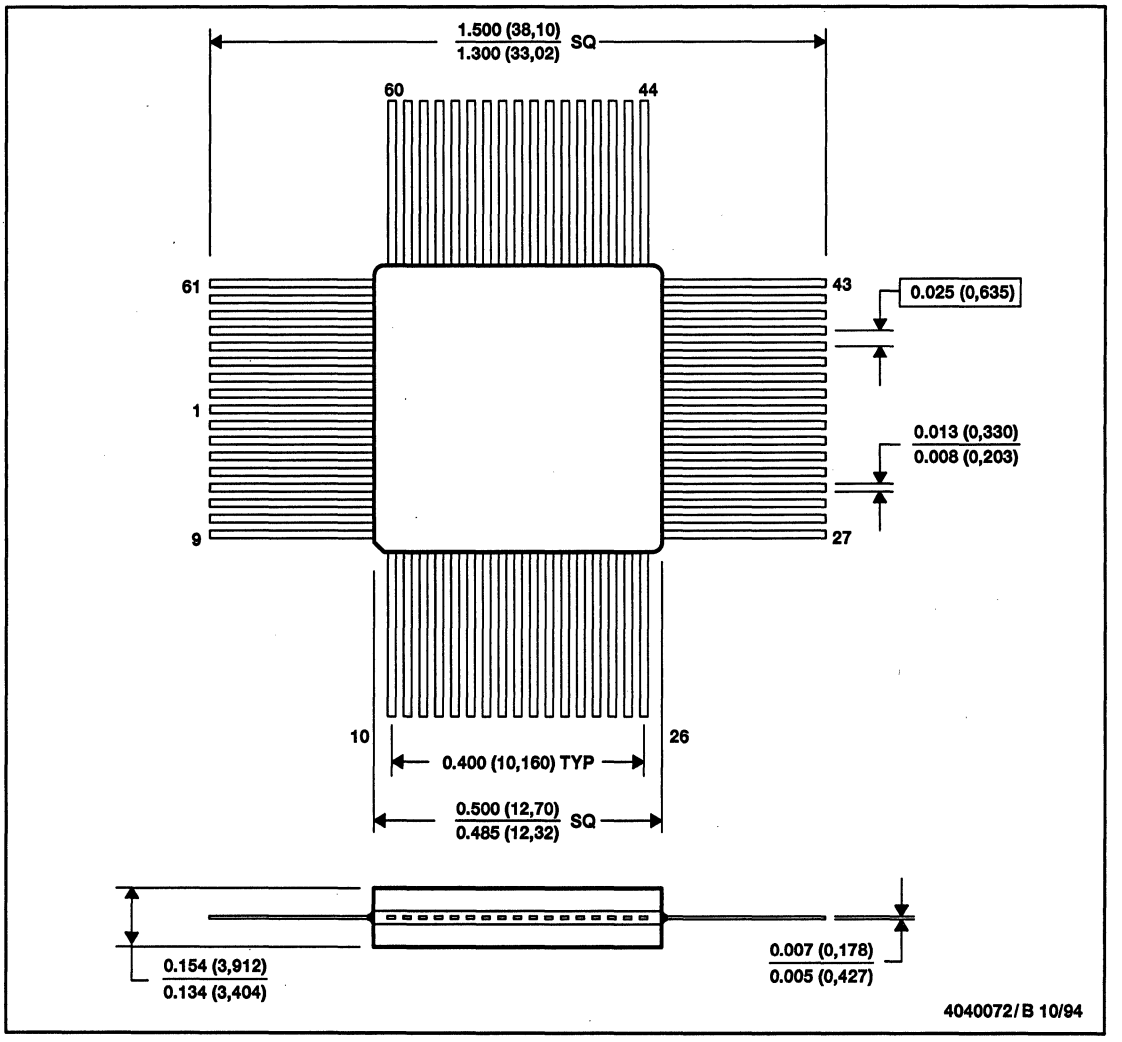
NO. OF TERMINALS **	A		B	
	MIN	MAX	MIN	MAX
20	0.342 (8,69)	0.358 (9,09)	0.307 (7,80)	0.358 (9,09)
28	0.422 (11,23)	0.458 (11,63)	0.406 (10,31)	0.458 (11,63)
44	0.640 (16,26)	0.660 (16,76)	0.495 (12,58)	0.560 (14,22)
52	0.730 (18,78)	0.761 (19,32)	0.485 (12,58)	0.560 (14,22)
68	0.938 (23,83)	0.962 (24,43)	0.850 (21,6)	0.858 (21,8)
84	1.141 (28,99)	1.165 (29,59)	1.047 (26,6)	1.063 (27,0)



4040140/B 10/94

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a metal lid.
D. The terminals are gold plated.
E. Falls within JEDEC MS-004

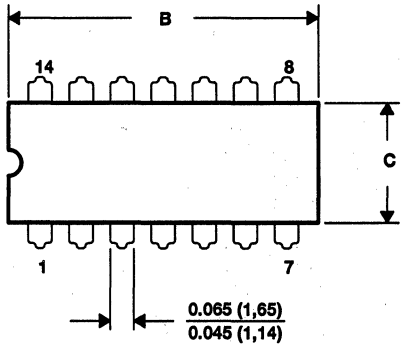
HV (S-GDFP-F68) **CERAMIC QUAD FLATPACK**



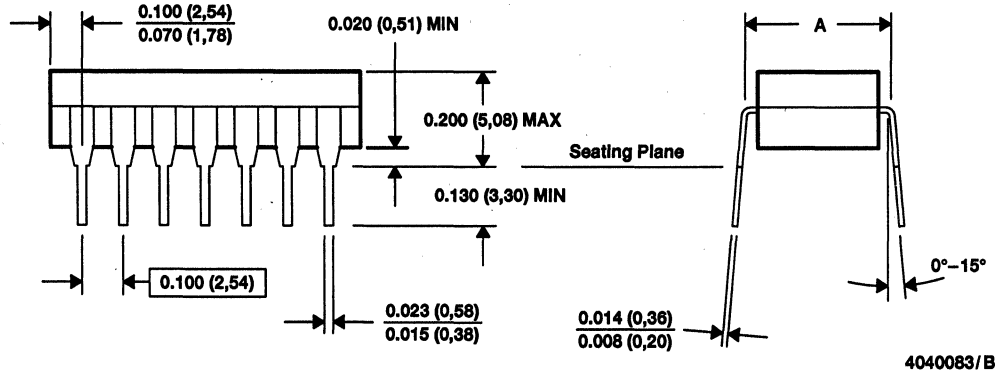
NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.

J (R-GDIP-T)** **CERAMIC DUAL-IN-LINE PACKAGE**

14 PIN SHOWN



DIM \ PINS **	14	16	18	20	22
A MAX	0.310 (7,87)	0.310 (7,87)	0.310 (7,87)	0.310 (7,87)	0.410 (10,41)
A MIN	0.290 (7,37)	0.290 (7,37)	0.290 (7,37)	0.290 (7,37)	0.390 (9,91)
B MAX	0.785 (19,94)	0.785 (19,94)	0.910 (23,10)	0.975 (24,77)	1.100 (28,00)
B MIN	0.755 (19,18)	0.755 (19,18)	—	0.930 (23,62)	—
C MAX	0.280 (7,11)	0.300 (7,62)	0.300 (7,62)	0.300 (7,62)	0.388 (9,65)
C MIN	0.245 (6,22)	0.245 (6,22)	0.245 (6,22)	0.245 (6,22)	—



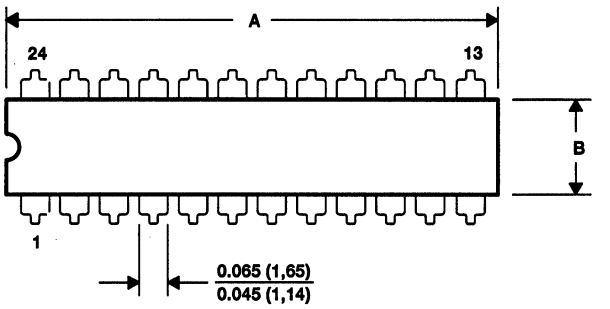
4040083/B 10/94

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
E. Falls within MIL-STD-1835 GDIP1-T14, GDIP1-T16, GDIP1-T18, GDIP1-T20, and GDIP1-T22

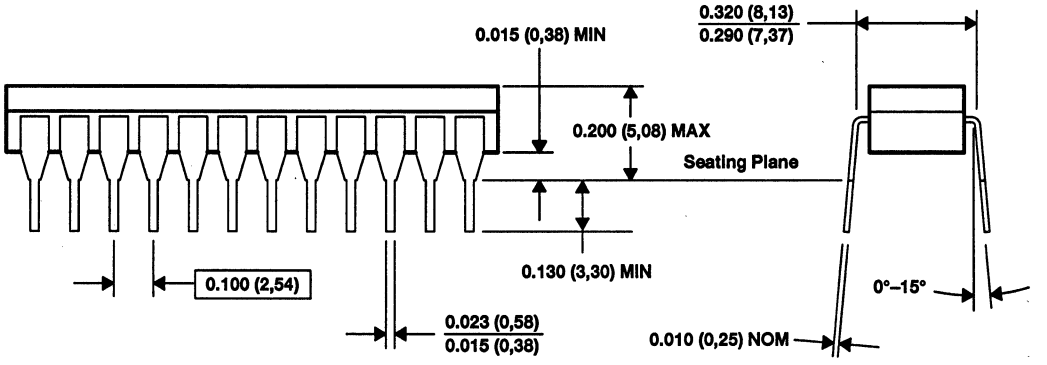
TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

JT (R-GDIP-T)** **CERAMIC DUAL-IN-LINE PACKAGE**

24 PIN SHOWN



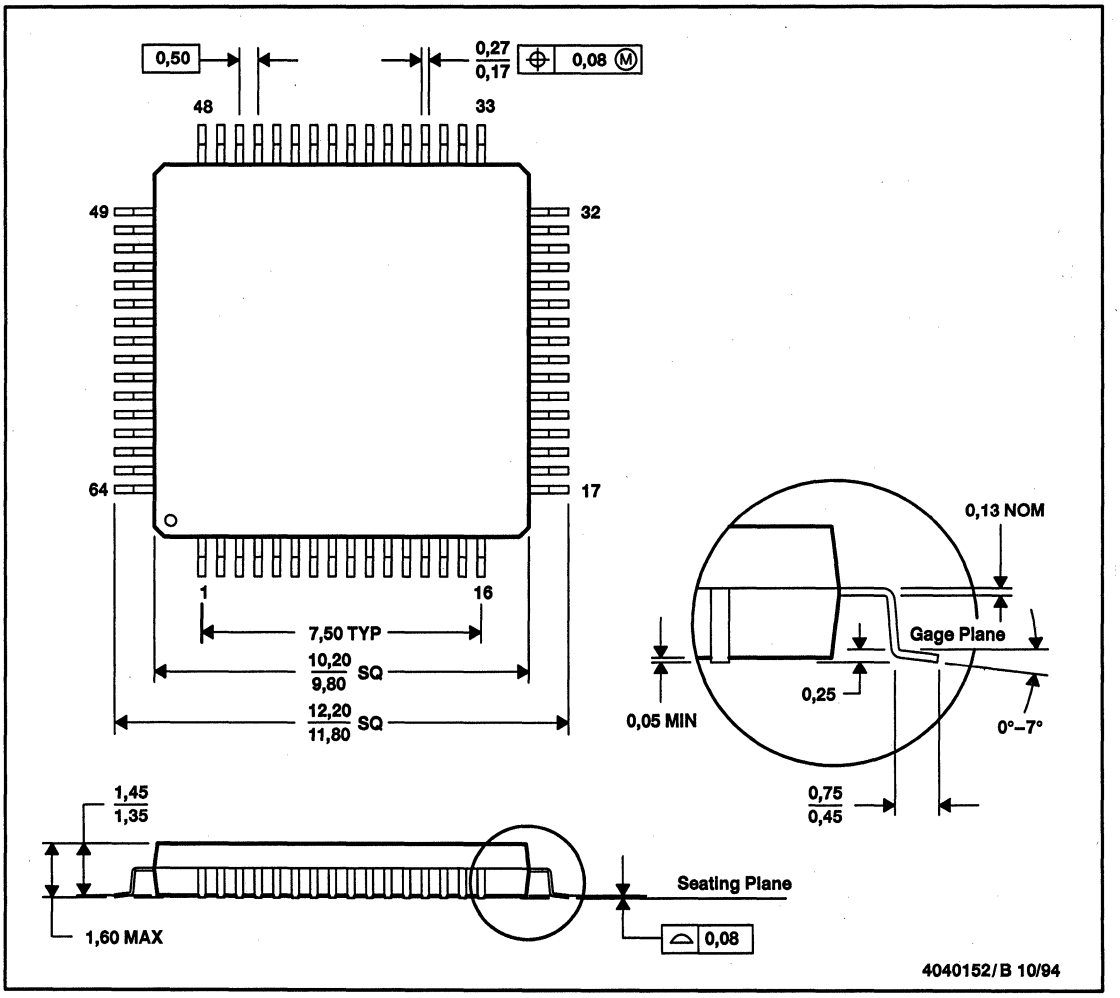
DIM \ PINS**	24	28
A MAX	1.280 (32,51)	1.460 (37,08)
A MIN	1.240 (31,50)	1.440 (36,58)
B MAX	0.300 (7,62)	0.291 (7,39)
B MIN	0.245 (6,22)	0.285 (7,24)



4040110/B 10/94

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
E. Falls within MIL-STD-1835 GDIP-T24 and GDIP-T28 and JEDEC MO-058AA and MO-058AB

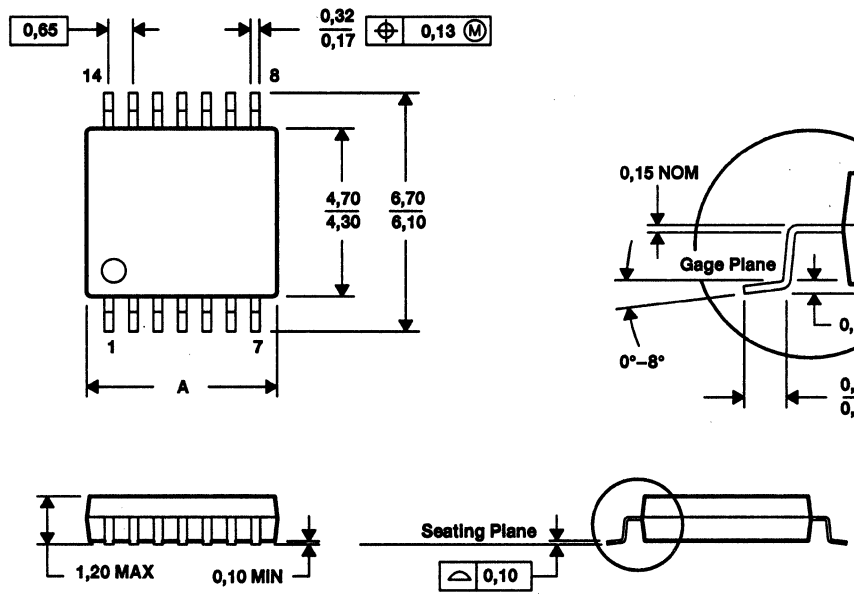
PM (S-PQFP-G64) **PLASTIC QUAD FLATPACK**



NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Falls within JEDEC MO-136

PW (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14 PIN SHOWN



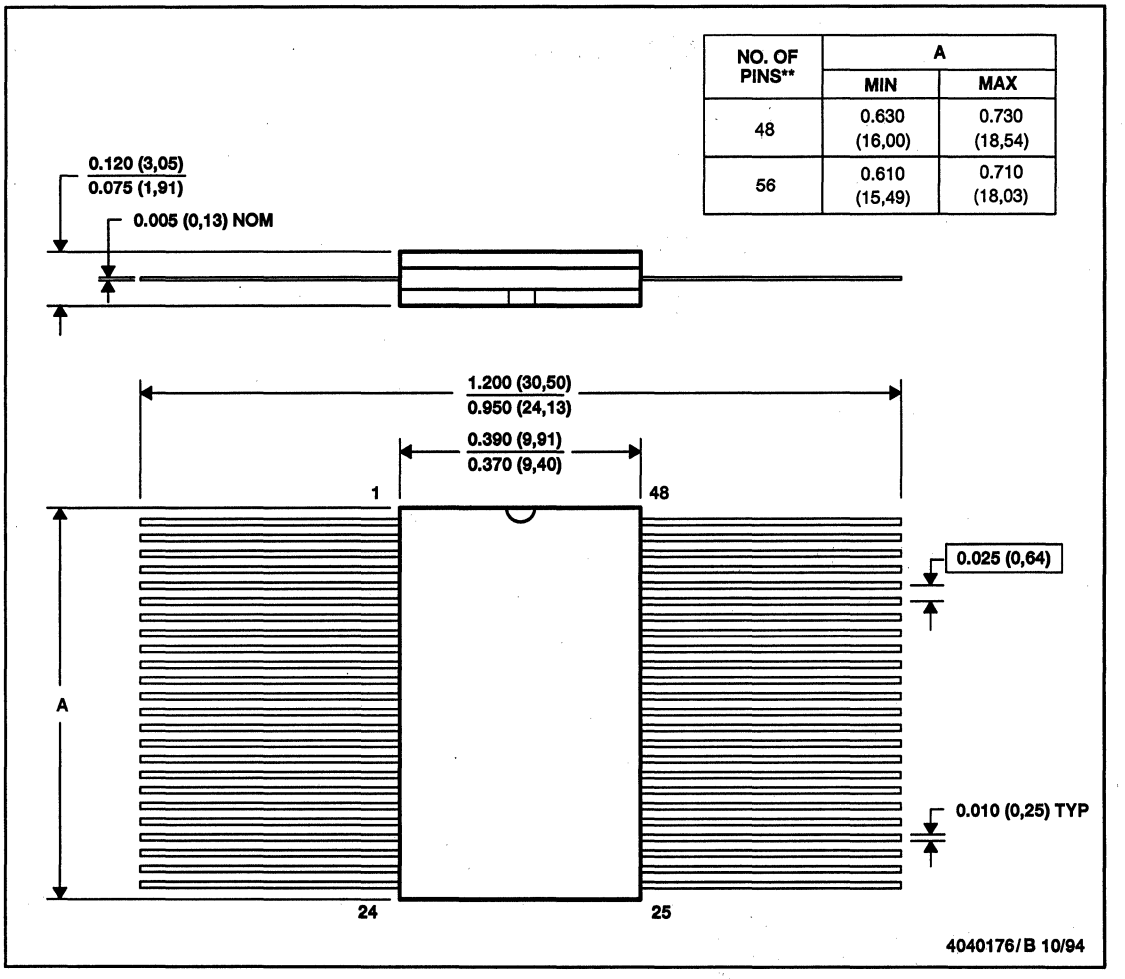
DIM \ PINS **	8	14	16	20	24	28
A MAX	3,30	5,30	5,30	6,80	8,10	10,00
A MIN	2,90	4,90	4,90	6,40	7,70	9,60

4040064/B 10/94

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

WD (R-GDFP-F)** **CERAMIC DUAL FLATPACK**

48 PIN SHOWN



NO. OF PINS**	A	
	MIN	MAX
48	0.630 (16,00)	0.730 (18,54)
56	0.610 (15,49)	0.710 (18,03)

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for pin identification only.
E. Falls within MIL-STD-1835: GDFP1-F48 and JEDEC MO-146AA
GDFP1-F56 and JEDEC MO-146AB

NOTES

NOTES

NOTES

TI Worldwide Sales and Representative Offices

AUSTRALIA / NEW ZEALAND: Texas Instruments Australia Ltd.: Melbourne [61] 3-696-1211, Fax 3-696-4446; **Sydney** 2-910-3100, Fax 2-805-1186.
BELGIUM: Texas Instruments Belgium S.A./N.V.: Brussels [32] (02) 726 75 80, Fax (02) 726 72 76.
BRAZIL: Texas Instrumentos Electronicos do Brasil Ltda.: Sao Paulo [55] 11-535-5133.
CANADA: Texas Instruments Canada Ltd.: Montreal (514) 421-2750; **Ottawa** (613) 726-3201; Fax 726-6363; **Toronto** (905) 884-9181; Fax 884-0062.
DENMARK: Texas Instruments A/S: Ballerup [45] (44) 68 74 00.
FRANCE/MIDDLE EAST/AFRICA: Texas Instruments France: Velizy-Villacoublay [33] (1) 30 70 10 01, Fax (1) 30 70 10 54.
GERMANY: Texas Instruments Deutschland GmbH.: Freising [49] (08161) 800, Fax (08161) 80 45 16; **Hannover** (0511) 90 49 60, Fax (0511) 64 90 331; **Ostfildern** (0711) 340 30, Fax (0711) 340 32 57.
HONG KONG: Texas Instruments Hong Kong Ltd.: Kowloon [852] 2956-7288, Fax 2956-2200.
HUNGARY: Texas Instruments Representation: Budapest [36] (1) 269 83 10, Fax (1) 267 13 57.
IRELAND: Texas Instruments Ireland Ltd.: Dublin [353] (01) 475 52 33, Fax (01) 478 14 63.
ITALY: Texas Instruments Italia S.p.A.: Agrate Brianza [39] (039) 684 21, Fax (039) 684 29 12; **Rome** (06) 657 26 51.
JAPAN: Texas Instruments Japan Ltd.: Kanazawa [81] 0762-23-5471, Fax 0762-23-1583; **Kita Kanto** 0485-22-2440, Fax 0485-23-5787; **Kyoto** 075-341-7713, Fax 075-341-7724; **Kyushu** 0977-73-1557, Fax 0977-73-1583; **Matsumoto** 0263-33-1060, Fax 0263-35-1025; **Nagoya** 052-232-5601, Fax 052-232-7888; **Osaka** 06-204-1881, Fax 06-204-1895; **Tachikawa** 0425-27-6760, Fax 0425-27-6426; **Tokyo** 03-3769-8700, Fax 03-3457-6777; **Yokohama** 045-338-1220, Fax 045-338-1255.
KOREA: Texas Instruments Korea Ltd.: Seoul [82] 2-551-2804, Fax 2-551-2828.
MAINLAND CHINA: Texas Instruments China Inc.: Beijing [86] 10-500-2255, Ext. 3750, Fax 10-500-2705.
MALAYSIA: Texas Instruments Malaysia Sdn Bhd: Kuala Lumpur [60] 3-208-6001, Fax 3-230-6605.
MEXICO: Texas Instruments de Mexico S.A. de C.V.: Colonia del Valle [52] 5-639-9740.
NORWAY: Texas Instruments Norge A/S: Oslo [47] (02) 264 75 70.
PHILIPPINES: Texas Instruments Asia Ltd.: Metro Manila [63] 2-636-0980, Fax 2-631-7702.
SINGAPORE (& INDIA, INDONESIA, THAILAND): Texas Instruments Singapore (PTE) Ltd.: Singapore [65] 390-7100, Fax 390-7062.
SPAIN/PORTUGAL: Texas Instruments España S.A.: Madrid [34] (1) 372 80 51, Fax (1) 307 68 64.
SUOMI/FINLAND: Texas Instruments/OY: Espoo [358] (0) 43 54 20 33, Fax (0) 46 73 23.
SWEDEN: Texas Instruments International Trade Corporation (Sverigefilialen): Kista [46] (08) 752 58 00, Fax (08) 751 97 15.
SWITZERLAND: Texas Instruments Switzerland AG: Dietikon [41] 886-2-3771450.
TAIWAN: Texas Instruments Taiwan Limited: Taipei [886] 2-378-6800, Fax 2-377-2718.
THE NETHERLANDS: Texas Instruments Holland, B.V. Amsterdam [31] (020) 546 98 00, Fax (020) 646 31 36.
UNITED KINGDOM: Texas Instruments Ltd.: Northampton [44] (01604) 66 30 00, Fax (01604) 66 30 01.

UNITED STATES: Texas Instruments Incorporated: ALABAMA: Huntsville (205) 430-0114; **ARIZONA: Phoenix** (602) 224-7800; **CALIFORNIA: Irvine** (714) 660-1200; **Los Angeles** (818) 704-8100; **San Diego** (619) 278-9600; **San Jose** (408) 894-9000; **COLORADO: Denver** (303) 488-9300; **CONNECTICUT: Wallingford** (203) 269-0074; **FLORIDA: Fort Lauderdale** (305) 425-7805; **Orlando** (407) 667-5308; **Tampa** (813) 573-0331; **GEORGIA: Atlanta** (770) 662-7967; **ILLINOIS: Chicago** (708) 517-4500; **INDIANA: Indianapolis** (317) 573-6400; **KANSAS: Kansas City** (913) 451-4511; **MARYLAND: Baltimore** (410) 312-7900; **MASSACHUSETTS: Boston** (617) 895-9100; **MICHIGAN: Detroit** (810) 305-5700; **MINNESOTA: Minneapolis** (612) 828-9300; **NEW JERSEY: Edison** (908) 906-0033; **NEW MEXICO: Albuquerque** (505) 345-2555; **NEW YORK: Long Island** (516) 454-6601; **Poughkeepsie** (914) 897-2900; **Rochester** (716) 385-6770; **NORTH CAROLINA: Charlotte** (704) 522-5487; **Raleigh** (919) 876-2725; **OHIO: Cleveland** (216) 328-2149; **Dayton** (513) 427-6200; **OREGON: Portland** (503) 643-6758; **PENNSYLVANIA: Philadelphia** (610) 825-9500; **PUERTO RICO: Hato Rey** (809) 753-8700; **TEXAS: Austin** (512) 250-6769; **Dallas** (214) 917-1264; **Houston** (713) 778-6592; **Midland** (915)561-6521; **WISCONSIN: Milwaukee** (414) 798-5021.

North American Authorized Distributors

COMMERCIAL	
Almac / Arrow	800-426-1410 / 800-452-9185 Oregon only
Anthem Electronics	800-826-8436
Arrow / Schweber	800-777-2776
Future Electronics (Canada)	800-388-8731
Hamilton Hallmark	800-332-8638
Marshall Industries	800-522-0084 or www.marshall.com
Wyle	800-414-4144
OBSOLETE PRODUCTS	
Rochester Electronics	508-462-9332
MILITARY	
Alliance Electronics Inc	800-608-9494
Future Electronics (Canada)	800-388-8731
Hamilton Hallmark	800-332-8638
Zeus, An Arrow Company	800-524-4735
CATALOG	
Allied Electronics	800-433-5700
Arrow Advantage	800-777-2776
Newark Electonics	800-367-3573

For Distributors outside North America, contact your local Sales Office.

A111395

Printed in the USA

TEXAS INSTRUMENTS

TEXAS INSTRUMENTS

Printed in U.S.A.
0296–CP

SCBD003B